



Expertise Applied | Answers Delivered

Three images of thyristor components. The left image shows several black thyristors with three white leads. The middle image shows a collection of black thyristors with three white leads. The right image shows several black thyristors with three white leads.

PRODUCT
CATALOG
& DESIGN
GUIDE

Datasheet.Live

THYRISTOR

Power Switching Semiconductor Products

Littelfuse Circuit Protection Solutions Portfolio

Consumer Electronics | Telecom | White Goods | Medical Equipment | TVSS and Power Systems

DESIGN SUPPORT

Live Application Design and Technical Support—Tap into our expertise. Littelfuse engineers are available around the world to help you address design challenges and develop unique, customized solutions for your products.

Product Sampling Programs—Most of our products are available as samples for testing and verification within your circuit design. Visit Littelfuse.com or contact a Littelfuse product representative for additional information.

Product Evaluation Labs and Services—Littelfuse global labs are the hub of our new product development initiatives, and also provide design and compliance support testing as an added-value to our customers.



OVERVOLTAGE SUPPRESSION TECHNOLOGIES (1-6)

1. TVS Diodes — Suppress overvoltage transients such as Electrical Fast Transients (EFT), inductive load switching and lightning in a wide variety of applications in the computer, industrial, telecom and automotive markets.

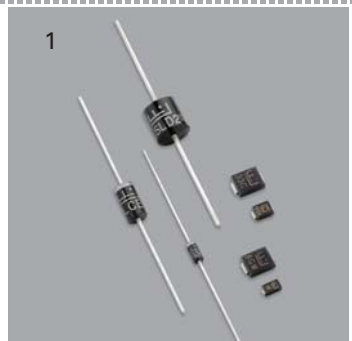
2. Varistors — Multiple forms, from Metal Oxide Varistors (MOVs) that suppress transient voltages to Multi-Layer Varistors (MLVs) designed for applications requiring protection from various transients in computers and handheld devices as well as industrial and automotive applications.

3. SIDACtor® Devices — Complete line of protection thyristor products specifically designed to suppress overvoltage transients in a broad range of telecom and datacom applications.

4. Gas Plasma Arrestors (GDTs) — Available in small footprint leaded and surface mount configurations, Littelfuse GDTs respond fast to transient overvoltage events, reducing the risk of equipment damage.

5. Silicon Protection Arrays — Designed specifically to protect analog and digital signal lines from electrostatic discharge (ESD) and other overvoltage transients.

6. PulseGuard® ESD Suppressors — Available in various surface mount form factors to protect high-speed digital lines without causing signal distortion.



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Protection folio

Supplies | Lighting | General Electronics

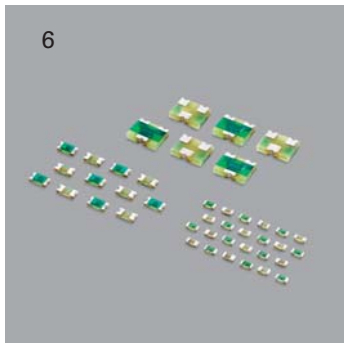
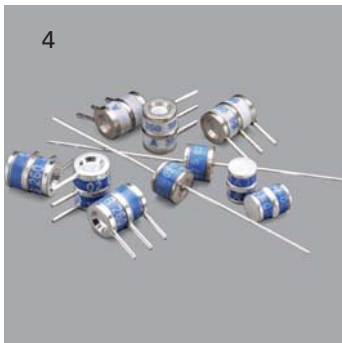
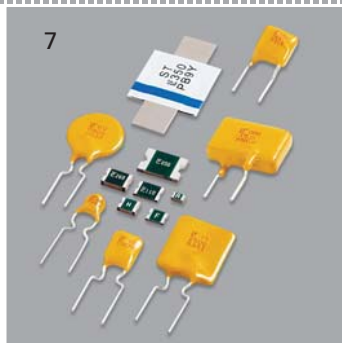
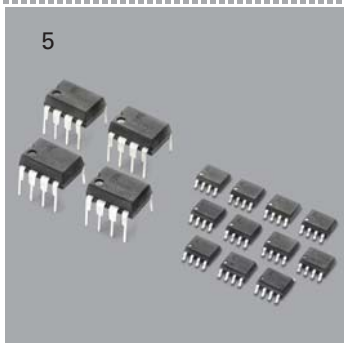
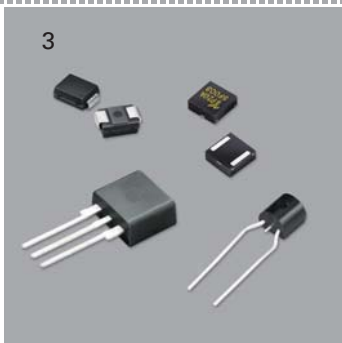
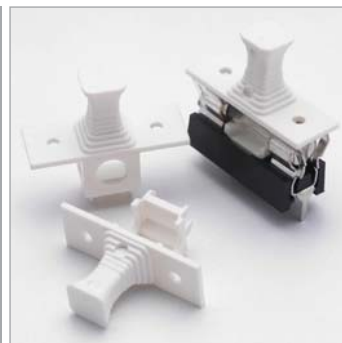
SWITCHING TECHNOLOGIES

Switching Thyristors—

Solid-state switches used to control the flow of electrical current in applications, capable of withstanding rated blocking/off-state voltage until triggered to on-state.

ACCESSORIES

In addition to our broad portfolio of circuit protection technologies, we offer an array of **fuse holders** including circuit board, panel or in-line wire mounted devices to support a wide range of application requirements.



OVERCURRENT PROTECTION TECHNOLOGIES (7-8)

7. Positive Temperature Coefficient Devices (PTCs)—

Provide resettable overcurrent protection for a wide range of applications.

8. Fuses — Full range including surface mount, axial, glass or ceramic, thin-film or Nano² style, fast-acting or SloBlo[®], MINI[®] and ATO[®] fuses.

www.littelfuse.com for more information.



Circuit Protection with Thyristor Voltage Suppressors

Littelfuse Thyristors are solid state switches that are normally open circuits (very high impedance), capable of withstanding rated blocking/off-state voltage until triggered to on state. They are commonly used to control the flow of electrical currents to protect electronics from damaging voltage transients.

Thyristors can be used to protect a wide range of electronic components and are commonly used in home appliances, electrical tools, and outdoor equipment. They are also often used in variable-speed electric motors, power supplies for electrochemical processes, lighting and heating control, and controllers for electric utility power systems.

The Littelfuse line of Thyristors include Sensitive Triacs, Triacs, Quadrac® Devices, Alternistor Triacs, Sensitive SCRs, SCRs, Rectifiers, DIACs and SIDACs.

Features

- High Voltage and Ampere ratings
- Unidirectional and Bidirectional transient voltage protection
- Automatically triggered "off" for specified periods of time
- RoHS compliant
- Glass-passivated junctions
- High voltage capability – up to 1000 V
- High surge capability – up to 950 A

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Disclaimers

Life support applications

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Littelfuse customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Littelfuse for any damage resulting from such applications.

Right to make changes

Littelfuse reserves the right to make any and all changes to the products described herein in order to improve design and/or performance. When the product is in full production, relevant changes will be communicated via a Product/Process Change Notification (PCN). Littelfuse assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

PRODUCT SELECTION TABLE

Reference

Type		Sensitive Triac, Triac, & Alternistor Triac														Quadrac
SERIES	Standard	QxX8Ex QxXx		Qx01Ex QxNx		Qxx04xx	Qxx06xx	Qxx08xx	Qxx10xx		Qxx15xx	Qxx25xx		Qxx35xx	Qxx40xx	QxxxLT
	Sensitive	LxX8Ex, LxXx	LX8	Lx01Ex LxNx	L01	Lxx04xx	Lxx06xx	Lxx08xx								
	Alternistor						Qxx06xHx	Qxx08xHx	Qxx10xHx	Qxx12xHx	Qxx16xHx	Qxx25xHx	HQ6025xH5	Qxx35xHx		QxxxLTH
Datasheet Page #		15	25	33	43	51	61	75	89	99	107	117	129	137	147	155
Thru-Hole Packages		TO-92		TO-220 Isl., TO-220 Non-Isl., TO-251		TO-220 Isl., TO-220 Non-Isl.,		TO-218 Isl., TO-218X Isl TO-220 Isl TO-220 Non-Isl. TO-3	TO-220 Isl TO-220 Non-Isl TO-3	TO-218 Isl TO-218X Isl	TO-220 Isl	TO-220 Isl TO-218X Isl TO-218 Isl TO-218 Non-Isl TO-3	TO-220 Isl TO-220 Non-Isl TO-218 Isl	TO-220 Isl TO-218X Isl TO-3	TO-218 TO-218X	TO-220
Surface Mount Packages		SOT-223, Compak		TO-252	TO-252, TO-263	TO-263	TO-263	TO-263	—	—	TO-263 TO-263 Isl	TO-263	TO-263	TO-263		
$I_{T(RMS)}$		0.08 A	0.08 A	1.0 A	1.0 A	4 A	6 A	8 A	10 A	12 A	15 & 16 A	25 A	25 A	30 & 35 A	40 A	4 - 15 A
V_{DRM}/V_{RRM}		600 V	600 V	600 V	800 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	1000 V	600 V	400 to 800 V	400 to 1000 V	400 to 600 V
$I_{GT(IQ1)}$		3 to 25 mA	3 to 5 mA	3 to 25 mA	3 to 10 mA	3 to 25 mA	5 to 50 mA	5 to 50 mA	25 to 50 mA	10 to 50 mA	10 to 80 mA	50 to 80 mA	50 mA	50 mA	80 to 100 mA	

Triac & Quadrac Products

Type		Sensitive SCR & Non-Sensitive SCR															
SERIES	Standard			Sx01E SxN1				Sxx06x	Sxx08x	Sxx10x	Sxx12x	Sxx15x Sxx16x	Sxx20x Sxx25x	Sxx35x	Sxx40x	Sxx55x	Sxx65x & Sxx70x
	Sensitive	EC103xx SxSx	SxX8xSx		TCR22-x	Sx02xS	Sxx04xSx	Sxx06xSx	Sxx08xSx	Sxx10xSx							
Datasheet Page #		163	173	183	193	201	209	217	227	239	249	257	265	275	283	291	301
Thru-Hole Packages		TO-92	TO-92	TO-92	TO-92	TO-92	TO-251	TO-251 TO-220 TO-220 IsI	TO-251 TO-220 TO-220 IsI	TO-251 TO-220 TO-220 IsI	TO-251 TO-220 Non IsI	TO-220 Non IsI	TO-220 TO-220 IsI	TO-218X TO-218AC	TO-220 IsI	TO-220 Non IsI TO-218X TO-218AC	TO-218X TO-218AC
Surface Mount Packages		Compak	SOT-89- SOT223 Compak	Compak	TO-252	SOT-223	TO-252	TO-252	TO-252	TO-252	TO-252	TO-252 TO-263	TO-263	——	TO-263	TO-263	——
I _{T(RMS)}		0.8 A	0.8 A	1 A	1 A	1.5 A	4 A	6 A	8 A	10 A	12 A	15 & 16 A	20 & 25 A	35 A	40 A	55 A	65 & 70 A
V _{DRM} /V _{RRM}		400 to 600 V	400 to 800 V	400 to 600 V	400 to 600 V	400 to 600 V	400 to 600 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V	400 to 1000 V
I _{GT (Q1)}		12 to 500 mA	5 to 20 mA	10 mA	10 mA	200 mA	50 to 500 mA	0.2 to 15 mA	0.2 to 15 mA	0.2 to 15 mA	20 mA	30 mA	30 to 35 mA	40 mA	40 mA	40 mA	50 mA

SCR Product Products

Type	SIDAC	High Energy SIDAC	Multipulse SIDAC	DIAC
SERIES	Kxxxzy-307	Kxxx0yH	Kxxx1G MP	HTxxx HTMxxx STxxx
Datasheet Page #	309	321	331	337
Thru-Hole Packages	DO-15, TO-92	DO-15 TO-92	DO-15	DO-35
Surface Mount Packages	DO-214	DO-214	DO-214	SOD-80 Minimelf DO-214
Switching Vbo	79 to 280 V	190 to 280 V	190 to 280 V	27 to 70 V
V_{BO} Symetry	—	—	—	down to 1 V
V_{BB}	—	—	—	up to 10 V
I_H	150 mA	160 mA typ	150 mA	—
I_{TSM}	20 A			—
static dv/dt	1500 V/us			—
t_{comm}	N/A	100 us	N/A	—
di/dt	150 A/us			—
T_J	up to 125 C	up to 125 C	up to 135 C	—

Type	Rectifiers	
SERIES	Dxx15L Dxx20L Dxx25L	
Datasheet Page #	345	
Thru-Hole Package		TO-220 Isl.
$I_{F(RMS)}$	RMS forward current	15-25A
$I_{F(AV)}$	Average forward current	9.5 - 15.9A
I_{FSM}	Peak non-repetitive surge current	single half cycle; f = 50Hz; T_J (initial) = 25°C
		188 - 300A
I_{FSM}	Peak non-repetitive surge current	single half cycle; f = 60Hz; T_J (initial) = 25°C
		225 - 350A
I^2t	I^2t Value for fusing	210 - 508 A²s
T_{stg}	Storage temperature range	-40 to 150 °C
T_J	Operating junction temperature range	-40 to 125 °C

DIAC, SIDAC & Rectifier Products

Product Descriptions

Thyristors

A Thyristor is any semiconductor switch with a bi-stable action depending on p-n-p-n regenerative feedback. Thyristors are normally two- or three-terminal devices for either unidirectional or bi-directional circuit configurations. Thyristors can have many forms, but they have certain commonalities. All Thyristors are solid state switches that are normally open circuits (very high impedance), capable of withstanding rated blocking/off-state voltage until triggered to on state. When triggered to on state, Thyristors become a low-impedance current path until principle current either stops or drops below a minimum holding level. After a Thyristor is triggered to on-state condition, the trigger current can be removed without turning off the device. Thyristors are used to control the flow of electrical currents in applications including:

- Home appliances (lighting, heating, temperature control, alarm activation, fan speed)
- Electrical tools (for controlled actions such as motor speed, stapling event, battery charging)
- Outdoor equipment (water sprinklers, gas engine ignition, electronic displays, area lighting, sports equipment, physical fitness)

Sensitive Triacs

Littelfuse's sensitive gate Triacs are AC bidirectional silicon switches that provide guaranteed gate trigger current levels in Quadrants I, II, III, and IV. Interfacing to microprocessors or other equipment with single polarity gate triggering is made possible with sensitive gate Triacs. Gate triggering currents of 3 mA, 5 mA, 10 mA, or 20 mA may be specified.

Sensitive gate Triacs are capable of controlling AC load currents from 0.8 A to 8 A rms and can withstand operating voltages from 400 V to 600 V.

Standard Triacs

Littelfuse's products are bidirectional AC switches, capable of controlling loads from 0.8 A to 35 A rms with 10 mA, 25 mA, and 50 mA I_{GT} in operating Quadrants I, II and III.

Triacs are useful in full-wave AC applications to control AC power either through full-cycle switching or phase control of current to the load element. These Triacs are rated to block voltage in the "OFF" condition from 400 V minimum with selected products capable of 1000 V operation. Typical applications include motor speed controls, heater controls, and incandescent light controls.

Quadrac

Quadrac devices, originally developed by Littelfuse, are Triacs and Alternistor Triacs with a DIAC trigger mounted inside the same package. These devices save the user the expense and assembly time of buying a discrete DIAC and assembling in conjunction with a gated Triac.

The Quadrac is offered in capacities from 4 A to 15 A rms and voltages from 400 V to 600 V.

Alternistor Triacs

The Alternistor Triac is specifically designed for applications required to switch highly inductive loads. The design of this special chip effectively offers the same performance as two Thyristors (SCRs) wired inverse parallel (back-to-back).

This new chip construction provides the equivalent of two electrically-separate SCR structures, providing enhanced dv/dt characteristics while retaining the advantages of a single-chip device.

Littelfuse manufactures 6 A to 40 A Alternistor Triac with blocking voltage rating from 400 V to 1000 V. Alternistor Triacs are offered in TO-220, TO-218, and TO-218X packages with isolated and non-isolated versions.

Sensitive SCRs

Littelfuse's sensitive gate SCRs are Silicon-Controlled Rectifiers representing the best in design, performance, and packaging techniques for low- and medium-current applications.

Anode currents of 0.8 A to 10 A rms can be controlled by sensitive gate SCRs with gate drive currents ranging from 12 μ A to 500 μ A. Sensitive gate SCRs are ideally suited for interfacing to integrated circuits or in applications where high current load requirements and limited gate drive current capabilities exist. Examples include ignition circuits, motor controls, and DC latching for alarms in smoke detectors. Sensitive gate SCRs are available in voltage ratings to 600 V.

SCRs

Littelfuse's SCR products are half-wave, Silicon-Controlled Rectifiers that represent the state of the art in design and performance.

Load current capabilities range from 1 A to 70 A rms, and voltages from 400 V to 1000 V may be specified to meet a variety of application needs.

Because of its unidirectional switching capability, the SCR is used in circuits where high surge currents or latching action is required. It may also be used for half-wave-type circuits where gate-controlled rectification action is required. Applications include crowbars in power supplies, camera flash units, smoke alarms, motor controls, battery chargers, and engine ignition.

Surge current ratings are available from 30 A in the TO-92 packaging to 950 A in the TO-218X package.

Rectifiers

Littelfuse manufactures 15 A to 25 A rms Rectifiers with voltages rated from 400 V to 1000 V. Due to the electrically isolated TO-220 package, these Rectifiers may be used in common anode or common cathode circuits using only one part type, thereby simplifying stock requirements.

DIACs

DIACs are trigger devices used in phase control circuits to provide gate pulses to a Triac or SCR. They are voltage-triggered bidirectional silicon devices housed in DO-35 glass axial lead packages and DO-214 surface mount packages.

DIAC voltage selections from 27 V to 70 V provide trigger pulses closely matched in symmetry at the positive and negative breakover points to minimize DC component in the load circuit.

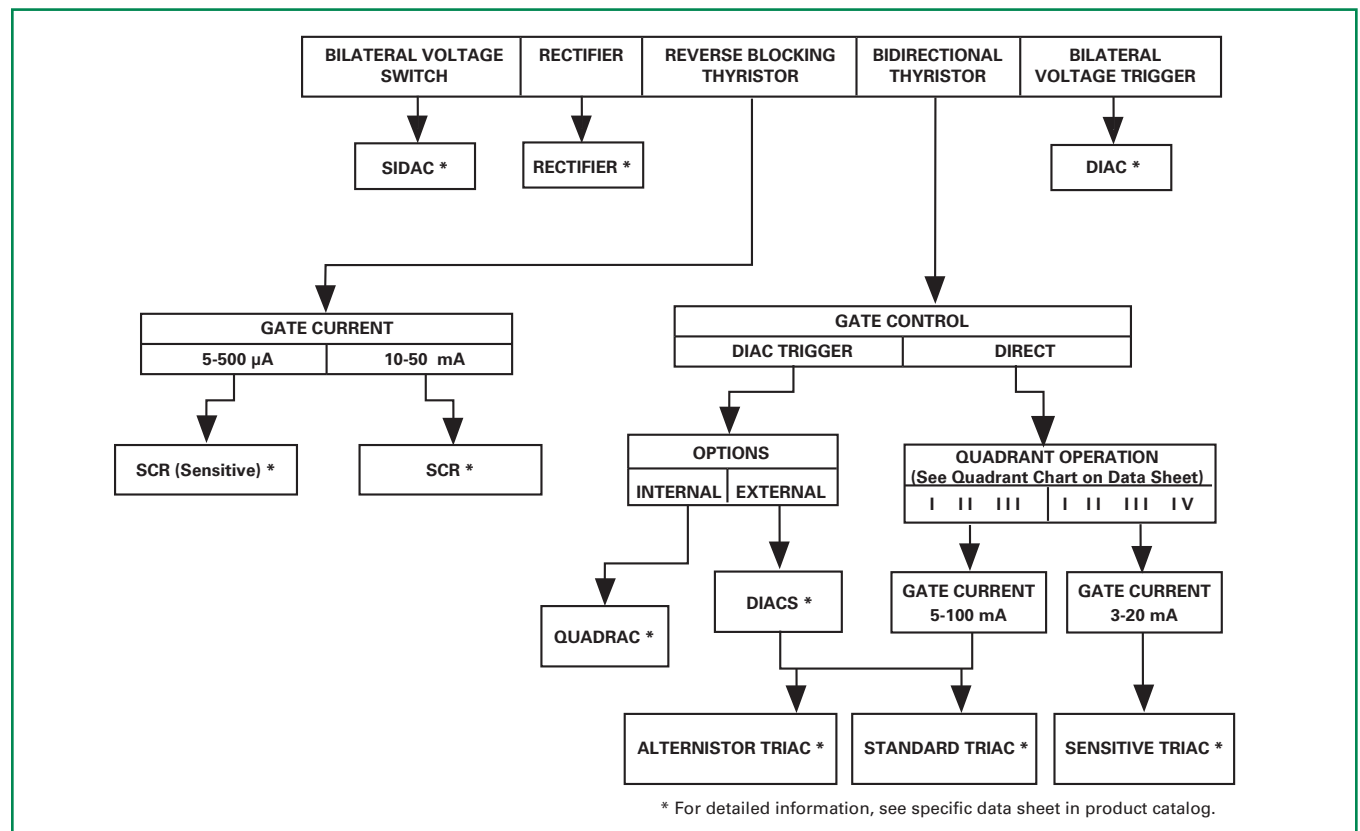
Some applications include gate triggers for light controls, dimmers, power pulse circuits, voltage references in AC power circuits, and Triac triggers in motor speed controls.

SIDACs











SIDACs represent a unique set of Thyristor qualities. The SIDAC is a bidirectional voltage triggered switch. Some characteristics of this device include a normal 95 V to 330 V switching point, negative resistance range, latching characteristics at turn-on, and a low on-state voltage drop.


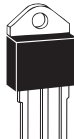

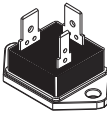
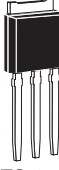
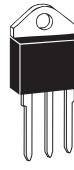


One-cycle surge current capability up to 20 A makes the SIDAC an ideal product for dumping charged capacitors through an inductor in order to generate high-voltage pulses. Applications include light controls, high-pressure sodium lamp starters, power oscillators, and high-voltage power supplies.

Circuit Requirement Diagram



Product Packages

Package Code					Surface-Mount						
		Y	G	E	MM	B	S	C	T	D	N
Product Type	Current (Amps)										
Sensitive Triac	0.8			X				X	X		
	1			X				X	X		
	4									X	
	6									X	
	8									X	
Standard Triac	0.8			X				X			
	1			X				X			
	4									X	
	6										X
	8										X
	10										X
	15										X
	25										X
Alternistor	35										
	6									X	X
	8									X	X
	10									X	X
	12										X
	16										X
	25										X
	30										
Quadrac	35										X
	40										
	4										
	6										
	8										
Sensitive SCR	10										
	15										
	0.8			X		X		X	X		
	1.5			X					X		
	4									X	
SCR	6									X	
	8									X	
	10									X	
	12									X	
	15										
	16			X				X			X
	20										
	25										X
	35										
	40										X
	55										X
	65										
	70										
Rectifier	15										
	20										
	25										
DIAC		X			X		X				
SIDAC			X	X			X				

Isolated Mounting Tab				Non-isolated Mounting Tab				Package Code	
L	K	J	P	V	M	W	R		
									
TO-220	TO-218	TO-218X	TO-3 Fastpak	TO-251 V-Pak	TO-218	TO-218X	TO-220	Current (Amps)	Product Type
								0.8	Sensitive Triac
				X				1	
X				X				4	
X				X				6	
X				X				8	Standard Triac
								0.8	
								1	
X				X				4	
X							X	6	
X							X	8	
X							X	10	
X							X	15	
			X				X	25	Alternistor
			X				X	35	
X				X			X	6	
X				X			X	8	
X							X	10	
X							X	12	
X							X	16	
X	X	X					X	25	
X								30	Quadrac
							X	35	
	X	X						40	
X								4	
X								6	
X								8	Sensitive SCR
X								10	
X								15	
								0.8	
								1.5	
				X				4	SCR
X				X				6	
X				X				8	
X				X			X	10	
X				X			X	12	
X								15	Rectifier
							X	16	
X								20	
X							X	25	
	X	X						35	
					X	X	X	40	
	X	X						55	
						X		65	
								70	DIAC
X								15	
X								20	
X								25	SIDAC

Quality and Reliability Assurance

Littelfuse Quality Policy

Littelfuse is committed to being sensitive to customer expectations and providing quality products and services at a competitive price. In support of this commitment, Littelfuse will:

- **Encourage** quality awareness and quality performance in all associates at all levels of the company through management leadership;
- **Promote** the participation of all associates in making individual contributions to the quality improvement process;
- **Support** continuous quality improvements by providing our associates with necessary training, tools and information feedback to enable enhancement of the quality of our products and services;
- **Develop** relationships with suppliers who consistently demonstrate their ability to fulfill quality, price and delivery objectives that are mutually beneficial; and;
- **Build** quality into our products and services, striving for zero defects in everything we do, thereby reducing cost and increasing **Total Customer Satisfaction**.

Quality Management Principles

The Littelfuse, Inc. Des Plaines and NADC Facilities' Management Team understand and concur with the following eight management principles:

- **Customer focus:** Littelfuse depends on its customers and makes every effort to understand their current and future needs. Littelfuse strives to meet customer requirements and to exceed customer expectations.
- **Leadership:** Leaders establish unity of purpose and direction for the Littelfuse organization. Our leaders should create and maintain the internal environment in which our associates can become fully involved in achieving the Littelfuse objectives.
- **Involvement of people:** Littelfuse associates at all levels are the essence of Littelfuse. Their full involvement enables their abilities to be used for the benefit of Littelfuse.
- **Process approach:** The results desired by Littelfuse are achieved more efficiently when activities and related resources are managed as a process.
- **System approach to management:** Identifying, understanding and managing interrelated processes as a system contributes to effectiveness and efficiency in achieving Littelfuse objectives.
- **Continual improvement:** Continual improvement of the overall performance should be a permanent objective of Littelfuse.
- **Factual approach to decision making:** Effective

decisions are based on the analysis of data and information at Littelfuse.

- **Mutually beneficial supplier relationships:** Littelfuse and its suppliers are interdependent and a mutually beneficial relationship enhances the ability of both to create value.

Quality Assurance

Incoming Material Quality

Littelfuse "Vendor Analysis" programs provide stringent requirements before components are delivered to Littelfuse. In addition, purchased materials are tested rigidly at incoming inspection for specification compliance prior to acceptance for use.

Process Controls

From silicon slice input through final testing, we use statistical methods to control all critical processes. Process audits and lot inspections are performed routinely at all stages of the manufacturing cycle.

Parametric Testing

All devices are 100% computer tested for specific electrical characteristics at critical processing points.

Final Inspection

Each completed manufacturing lot is sampled and tested for compliance with electrical and mechanical requirements.

Reliability Testing

Random samples are taken from various product families for ongoing reliability testing.

Finished Goods Inspection

Product assurance inspection is performed immediately prior to shipping.

Design Assurance

The design and production of Littelfuse devices is a demanding and challenging task. Disciplined skills coupled with advanced computer-aided design, production techniques, and test equipment are essential elements in Littelfuse's ability to meet your demands for the very highest levels of quality.

All products must first undergo rigid quality design reviews and pass extensive environmental life testing. Littelfuse uses Statistical Process Control (SPC) with associated control charts throughout to monitor the manufacturing processes.

Only those products which pass tests designed to assure Littelfuse's high quality and reliability standards, while economically satisfying customer requirements, are approved for shipment. All new products and materials must receive approval of QRA prior to being released to production.

The combination of reliability testing, process controls, and lot tracking assures the quality and reliability of Littelfuse's

devices. Since even the best control systems cannot overcome measurement limitations, Littelfuse designs and manufactures its own computerized test equipment.

Littelfuse's Reliability Engineering Group conducts ongoing product reliability testing to further confirm the design and manufacturing parameters.

Reliability Stress Tests

The following table contains brief descriptions of the reliability tests commonly used in evaluating Littelfuse

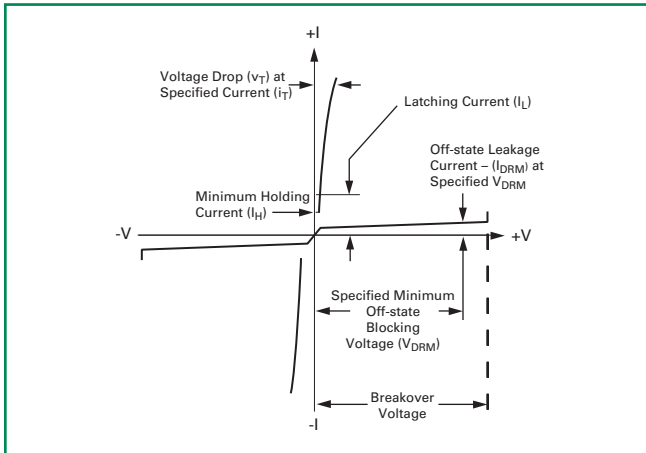
product reliability on a periodic basis. These tests are applied across product lines depending on product availability and test equipment capacities. Other tests may be performed when appropriate.

Test Type	Typical Conditions	Test Description	Standards
High Temperature AC Blocking	Rated V_{DRM} (VAC-peak), 110°C up to 125°C, 1008 hours	Evaluation of the reliability of product under bias conditions and elevated temperature	MIL-STD-750 (Method 1040)
High Temperature Storage Life	150°C, 1008 hours	Evaluation of the effects on devices after long periods of storage at high temperature	MIL-STD-750 (Method 1031)
Biased Temperature & Humidity	160V _{DC} , 85°C, 85% RH, 168 up to 1008 hours	Evaluation of the reliability of non-hermetic packaged devices in humid environments	EIA/JEDEC, JESD22-A101
Temperature Cycle [Air to Air]	-65°C to 150°C, 15-minute dwell, 10 up to 500 cycles	Evaluation of the device's ability to withstand the exposure to extreme temperatures and the forces of TCE during transitions between temperatures	MIL-STD-750 (Method 1051), EIA/JEDEC, JESD22-A104
Thermal Shock [Liquid to Liquid]	0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles	Evaluation of the device's ability to withstand the sudden changes in temperature and exposure to extreme temperatures	MIL-STD-750 (Method 1056)
Autoclave (PCT)	121°C, 100%RH, 2atm, 24 up to 168 hours	Accelerated environmental test to evaluate the moisture resistance of plastic packages	EIA/JEDEC, JESD22-A102
Resistance to Solder Heat	260°C, 10 seconds	Evaluation of the device's ability to withstand the temperatures as seen in wave soldering operations	MIL-STD-750 (Method 2031)
Solderability	Steam Aging (1 to 8 hrs) 245°C Solder Temperature	Evaluation of the solderability of device terminals after simulated aging	ANSI J-STD-002
Lead Bend	225g weight, three 90° bends	Evaluation of resistance of device leads to metal fatigue	MIL-STD-750 (Method 2036)
Moisture Sensitivity Level	85%RH, 85°C, 168hrs 3 reflow cycles (260C peak)	Evaluation to determine device immunity to moisture	JEDEC J-STD-020 Level 1
ESD	HBM, 8kV CDM, 15kV	Evaluation to determine device immunity to electro-static discharge	JESD22-A114, MIL-STD-883D 3015.7, JESD22-C101

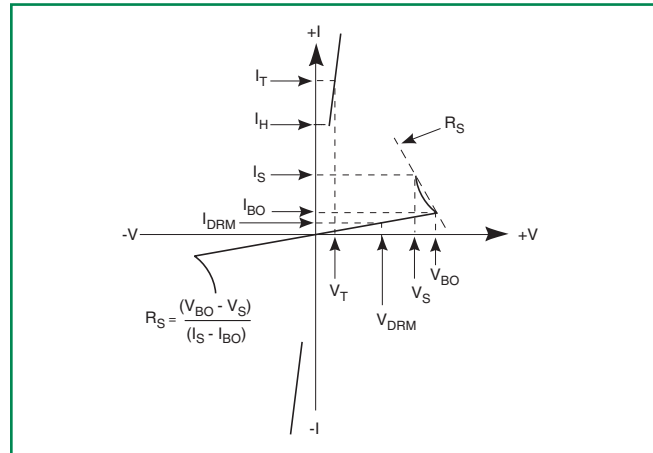
Flammability Test

For the UL 94V0 flammability test, all epoxies used in Littelfuse encapsulated devices are recognized by Underwriters Laboratories.

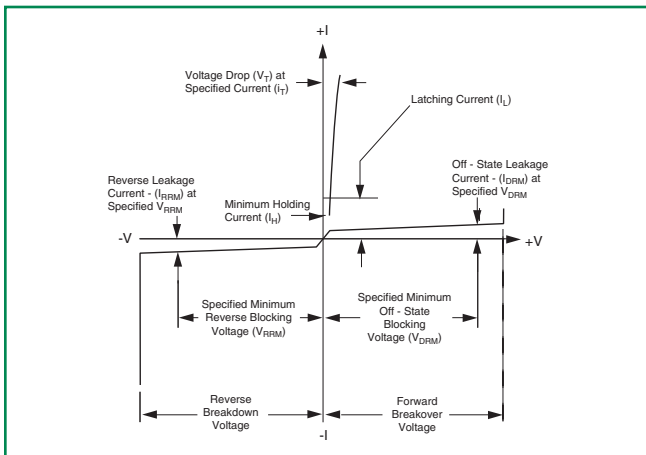
V-I Characteristics of Thyristor Devices



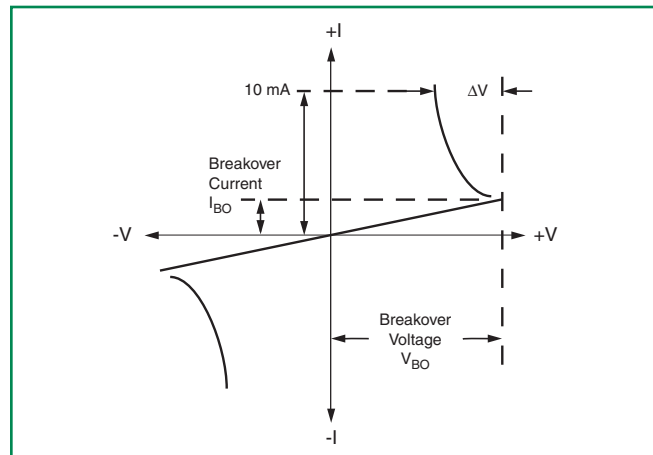
V-I Characteristics of Triac Device



V-I Characteristics of SIDAC Device with Negative Resistance



V-I Characteristics of SCR Device



V-I Characteristics of Bilateral Trigger DIAC

Electrical Parameter Terminology

Diode Rectifiers

di/dt (Critical Rate-of-rise of On-state Current) - Maximum value of the rate-of-rise of on-state current which a Thyristor can withstand without deleterious effect.

dv/dt (Critical Rate-of-rise of Off-state Voltage or Static dv/dt) - Minimum value of the rate-of-rise of principal voltage which will cause switching from the off state to the on state.

dv/dt(c) Critical Rate-of-rise of Commutation Voltage of a Triac (Commutating dv/dt) - Minimum value of the rate-of-rise of principal voltage which will cause switching from the off state to the on state immediately following on-state current conduction in the opposite quadrant.

I²t (RMS Surge (Non-repetitive) On-state Fusing Current) - Measure of let-through energy in terms of current and time for fusing purposes.

I_{BO} (Breakover Current) - Principal current at the breakover point.

I_{DRM} (Repetitive Peak Off-state Current) - Maximum leakage current that may occur under the conditions of V_{DRM}.

I_{GT} (Gate Trigger Current) - Minimum gate current required to switch a Thyristor from the off state to the on state.

I_H (Holding Current) - Minimum principal current required to maintain the Thyristor in the on state.

I_{PP} (Peak Pulse Current) - Peak pulse current at a short time duration and specified waveshape.

I_{RRM} (Repetitive Peak Reverse Current) - Maximum leakage current that may occur under the conditions of V_{RRM}.

I_S (Switching Current) - Current at V_S when a SIDAC switches from the clamping state to on state.

I_{T(RMS)} (On-state Current) - Anode cathode principal current that may be allowed under stated conditions, usually the full-cycle RMS current.

I_{TSM} (Surge (Non-repetitive) On-state Current) - Peak single cycle AC current pulse allowed.

P_{G(AV)} (Average Gate Power Dissipation) - Value of gate power which may be dissipated between the gate and main terminal 1 (or cathode) average over a full cycle.

P_{GM} (Peak Gate Power Dissipation) - Maximum power which may be dissipated between the gate and main terminal 1 (or cathode) for a specified time duration.

R_{θJA} (Thermal Resistance, Junction-to-Ambient) - Temperature difference between the Thyristor junction and ambient divided by the power dissipation causing the temperature difference under conditions of thermal equilibrium.

Note: Ambient is defined as the point where temperature does not change as a result of the dissipation.

R_{θJC} (Thermal Resistance, Junction-to-case) - Temperature difference between the Thyristor junction and the Thyristor case divided by the power dissipation causing the temperature difference under conditions of thermal equilibrium.

t_{gt} (Gate-controlled Turn-on Time) - Time interval between the 10% rise of the gate pulse and the 90% rise of the principal current pulse during switching of a Thyristor from the off state to the on state.

t_q (Circuit-commutated Turn-off Time) - Time interval between the instant when the principal current has decreased to zero after external switching of the principal voltage circuit and the instant when the SCR is capable of supporting a specified principal voltage without turning on.

V_{BO} (Breakover Voltage) - Principal voltage at the breakover point.

V_{DRM} (Repetitive Peak Off-state Voltage) - Maximum allowable instantaneous value of repetitive off-state voltage that may be applied across a bidirectional Thyristor (forward or reverse direction) or SCR (forward direction only).

V_{GT} (Gate Trigger Voltage) - Minimum gate voltage required to produce the gate trigger current.

V_{RRM} (Repetitive Peak Reverse Voltage) - Maximum allowable instantaneous value of a repetitive reverse voltage that may be applied across an SCR without causing reverse current avalanche.

V_S (Switching Voltage) - Voltage point after V_{BO} when a SIDAC switches from a clamping state to on state.

V_T (On-state Voltage) - Principal voltage when the Thyristor is in the on state.

Diode Rectifiers

I_{F(AV)} (Average Forward Current) - Average forward conduction current.

I_{FM} (Maximum (Peak) Reverse Current) - Maximum reverse leakage current that may occur at rated V_{RRM}.

I_{F(RMS)} (RMS Forward Current) - RMS forward conduction current.

I_{FSM} (Maximum (Peak) Forward (Non-repetitive) Surge Current) - Maximum (peak) forward single cycle AC surge current allowed for specified duration.

V_{FM} (Maximum (Peak) Forward Voltage Drop) - Maximum (peak) forward voltage drop from the anode to cathode at stated conditions.

V_R (Reverse Blocking Voltage) - Maximum allowable DC reverse blocking voltage that may be applied to the rectifier.

V_{RRM} (Maximum (Peak) Repetitive Reverse Voltage) - Maximum peak allowable value of a repetitive reverse voltage that may be applied to the rectifier.

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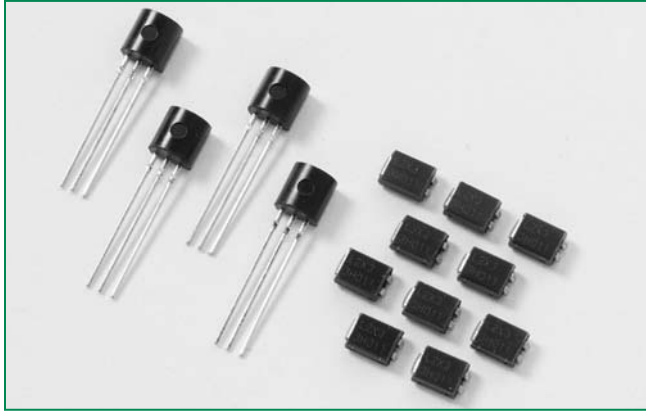
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RoHS LxX8Ex & LxXx & QxX8E & QxXx Series



Description

0.8 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Features

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 10 A

Applications

Excellent for lower current heating controls, water valves, and solenoids.

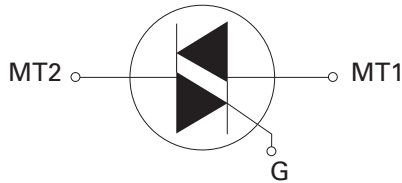
Typical applications are AC solid-state switches, home/ brown goods and white goods appliances.

Sensitive gate Triacs can be directly driven by microprocessor or popular opto-couplers/isolators.

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	400 to 600	V
$I_{GT(Q1)}$	3 to 25	mA

Schematic Symbol



Absolute Maximum Ratings — Sensitive Triacs (4 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	LxX8y/LxXy	$T_C = 50^\circ\text{C}$	0.8	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	8.3	A
		f = 60 Hz	t = 16.7 ms	10	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		0.41	A ² s
di/dt	Critical rate of rise of on-state current ($I_G = 50\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_J = 110^\circ\text{C}$	20	A/ μs
I_{GTM}	Peak gate trigger current	$t_p = 10\mu\text{s}$	$T_J = 110^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 110^\circ\text{C}$	0.2	W
T_{stg}	Storage temperature range	LxX8Ey	-65 to 150		$^\circ\text{C}$
		LxXy	-40 to 150		
T_J	Operating junction temperature range	LxX8Ey	-65 to 110		$^\circ\text{C}$
		LxXy	-40 to 110		

Note: x = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triac

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	QxXE8y/ QxXy	$T_c = 60^\circ\text{C}$	0.8	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	f = 50 Hz	t = 20 ms	8.3	A
		f = 60 Hz	t = 16.7 ms	10	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		0.41	A ² s
di/dt	Critical rate of rise of on-state current ($I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_j = 125^\circ\text{C}$	20	A/ μs
I_{GTM}	Peak gate trigger current	$t_p = 10 \mu\text{s};$ $I_{GT} \leq I_{GTM}$	$T_j = 125^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^\circ\text{C}$	0.2	W
T_{stg}	Storage junction temperature range		L/QxX8Ey	-65 to 150	$^\circ\text{C}$
			L/QxXy	-40 to 150	
T_j	Operating junction temperature range		L/QxX8Ey	-65 to 125	$^\circ\text{C}$
			L/QxXy	-40 to 125	

Note: x = voltage, y = sensitivity

Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		LxX8E3 LxX3	LxX8E5 LxX5	LxX8E6 LxX6	LxX8E8 LxX8	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 30 \Omega$	I – II – III	MAX.	3	5	5	10	mA
		IV		3	5	10	20	
V_{GT}		ALL	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 110^\circ\text{C}$	ALL	MIN.	0.2				V
I_H	$I_T = 100\text{mA}$		MAX.	5	10	10	15	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_j = 100^\circ\text{C}$	400V	TYP.	15	15	25	30	V/ μs
		600V		10	10	20	25	
(dv/dt)c	(di/dt)c = 0.43 A/ms $T_j = 110^\circ\text{C}$		TYP.	0.5	1	1	2	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 1.13 \text{ A(pk)}$		TYP.	2.8	3.0	3.0	3.2	μs

Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		QxX8E3 QxX3	QxX8E4 QxX4	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	10	25	mA
		IV	TYP.	25	50	
V_{GT}		I – II – III	MAX.	1.3	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^\circ\text{C}$	ALL	MIN.	0.2	0.2	V
I_H	$I_T = 200\text{mA}$		MAX.	15	25	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_j = 125^\circ\text{C}$	400V	MIN.	25	35	V/ μs
		600V		15	25	
(dv/dt)c	(di/dt)c = 0.43 A/ms $T_j = 125^\circ\text{C}$		TYP.	1	1	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 1.13 \text{ A(pk)}$		TYP.	2.5	3.0	μs

Note: x = voltage

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions				Value	Unit
V_{TM}	$I_{TM} = 1.13\text{A}$ $t_p = 380\ \mu\text{s}$	MAX.			1.60	V
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$	MAX.	LxX8Ey / LxXy	$T_J = 25^\circ\text{C}$	400-600V	2 μA
				$T_J = 110^\circ\text{C}$	400-600V	0.1 mA
			QxX8Ey / QxXy	$T_J = 25^\circ\text{C}$	400-600V	5 μA
				$T_J = 125^\circ\text{C}$	400-600V	1 mA

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	L/QxX8Ey	60	$^\circ\text{C/W}$
		L/QxXy	60*	
$R_{\theta(J-A)}$	Junction to ambient	L/QxX8Ey	135	$^\circ\text{C/W}$

Note: * = Mounted on 1 cm² 1 copper (two-ounce) foil surface

Figure 1: Definition of Quadrants

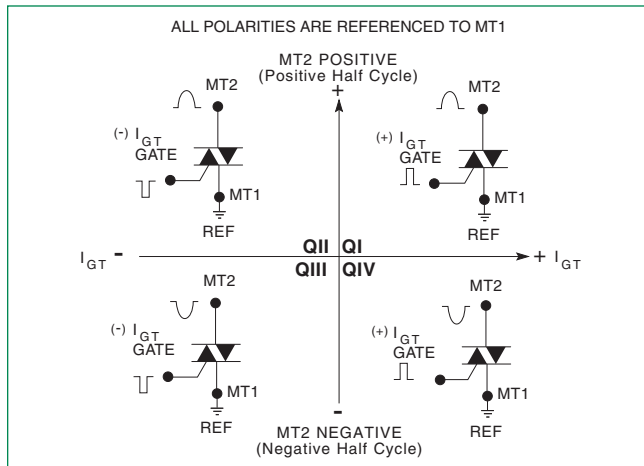


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

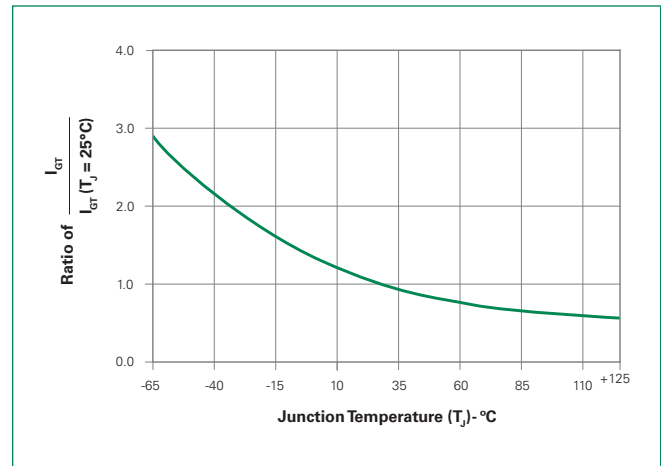


Figure 3: Normalized DC Holding Current vs. Junction Temperature

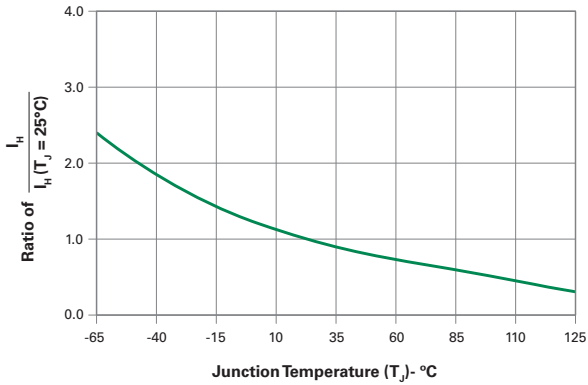


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

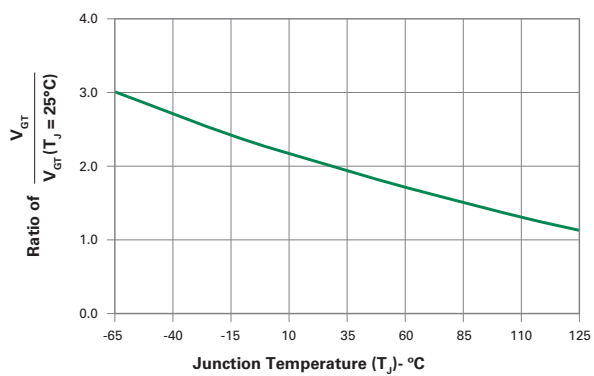


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

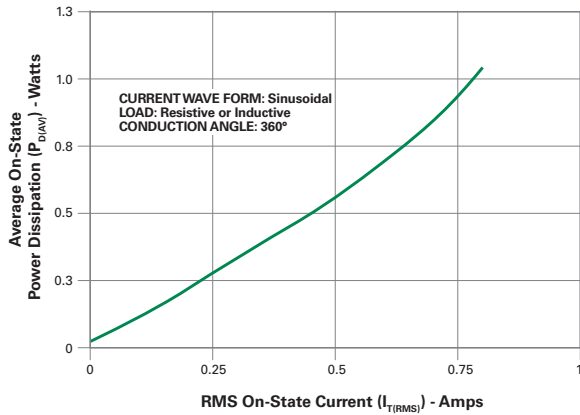


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

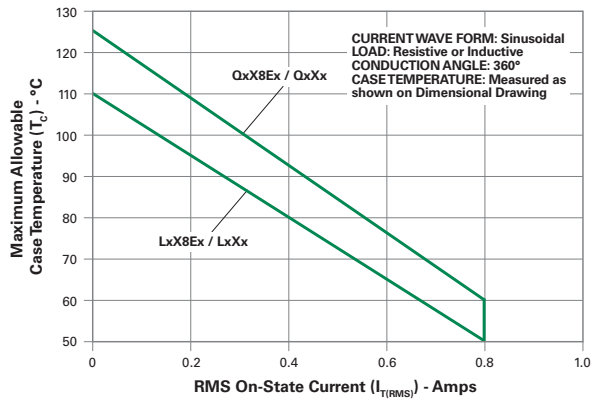


Figure 7: Maximum Allowable Ambient Temperature vs. On-State Current

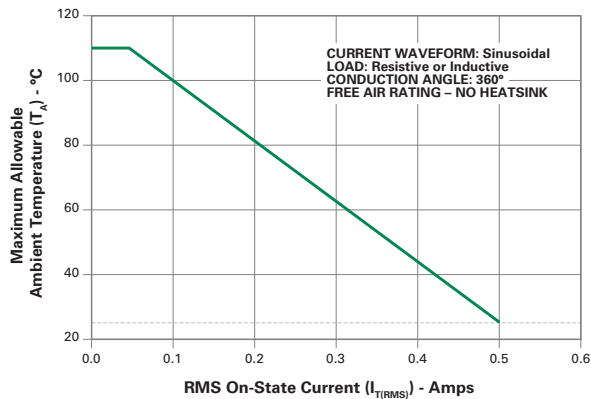


Figure 8: On-State Current vs. On-State Voltage (Typical)

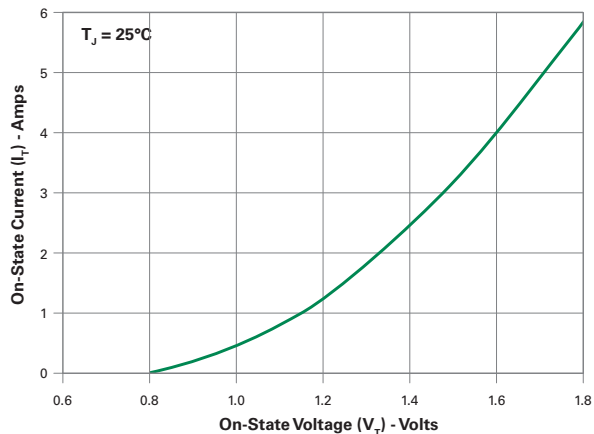
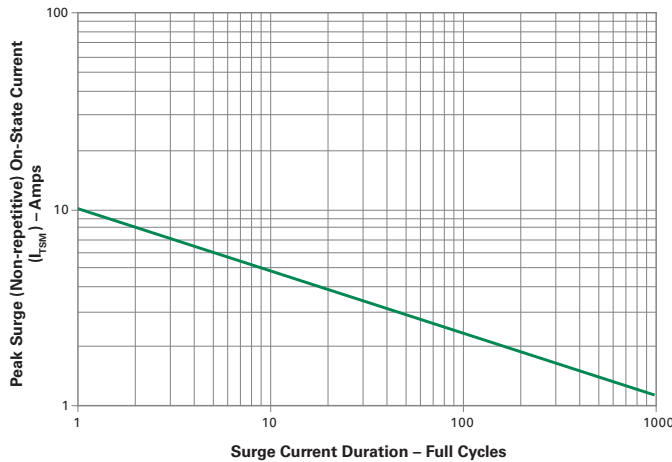


Figure 9: Surge Peak On-State Current vs. Number of Cycles



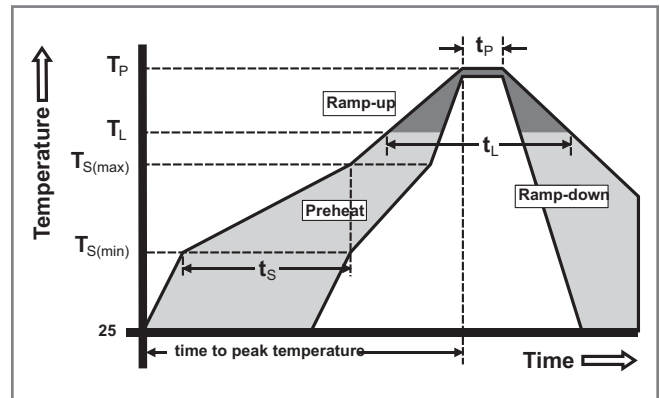
Supply Frequency: 60Hz Sinusoidal
Load: Resistive
RMS On-State ($I_{T(RMS)}$): Max Rated Value at Specific Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

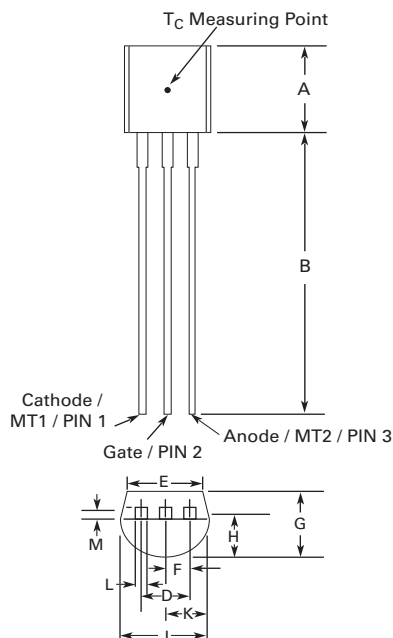
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

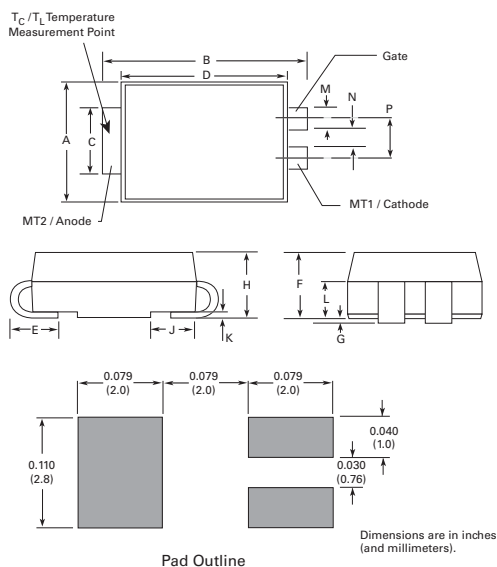
Dimensions — TO-92 (E Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500		12.70	
D	0.095	0.105	2.41	2.67
E	0.150		3.81	
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43

All leads insulated from case. Case is electrically nonconductive.

Dimensions — Compak (C Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.140	0.155	3.56	3.94
B	0.205	0.220	5.21	5.59
C	0.077	0.083	1.96	2.11
D	0.166	0.180	4.22	4.57
E	0.036	0.063	0.91	1.60
F	0.066	0.083	1.67	2.11
G	0.004	0.008	0.10	0.20
H	0.077	0.086	1.96	2.18
J	0.043	0.053	1.09	1.35
K	0.008	0.012	0.20	0.30
L	0.039	0.049	0.99	1.24
M	0.022	0.028	0.56	0.71
N	0.027	0.033	0.69	0.84
P	0.052	0.058	1.32	1.47

Product Selector

Part Number	Voltage		Gate Sensitivity Quadrants		Type	Package
	400V	600V	I – II – III	IV		
LxX8E3	X	X	3 mA	3 mA	Sensitive Triac	TO-92
LxX3	X	X	3 mA	3 mA	Sensitive Triac	Compak
LxX8E5	X	X	5 mA	5 mA	Sensitive Triac	TO-92
LxX5	X	X	5 mA	5 mA	Sensitive Triac	Compak
LxX8E6	X	X	5 mA	10 mA	Sensitive Triac	TO-92
LxX8E8	X	X	10 mA	20 mA	Sensitive Triac	TO-92
QxX8E3	X	X	10 mA		Standard Triac	TO-92
QxX3	X	X	10 mA		Standard Triac	Compak
QxX8E4	X	X	25 mA		Standard Triac	TO-92
QxX4	X	X	25 mA		Standard Triac	Compak

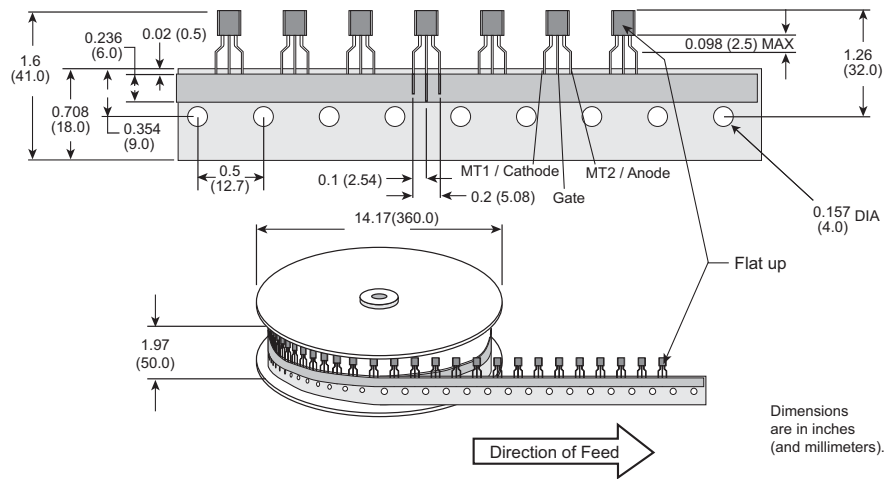
Note: x = voltage

Packing Options

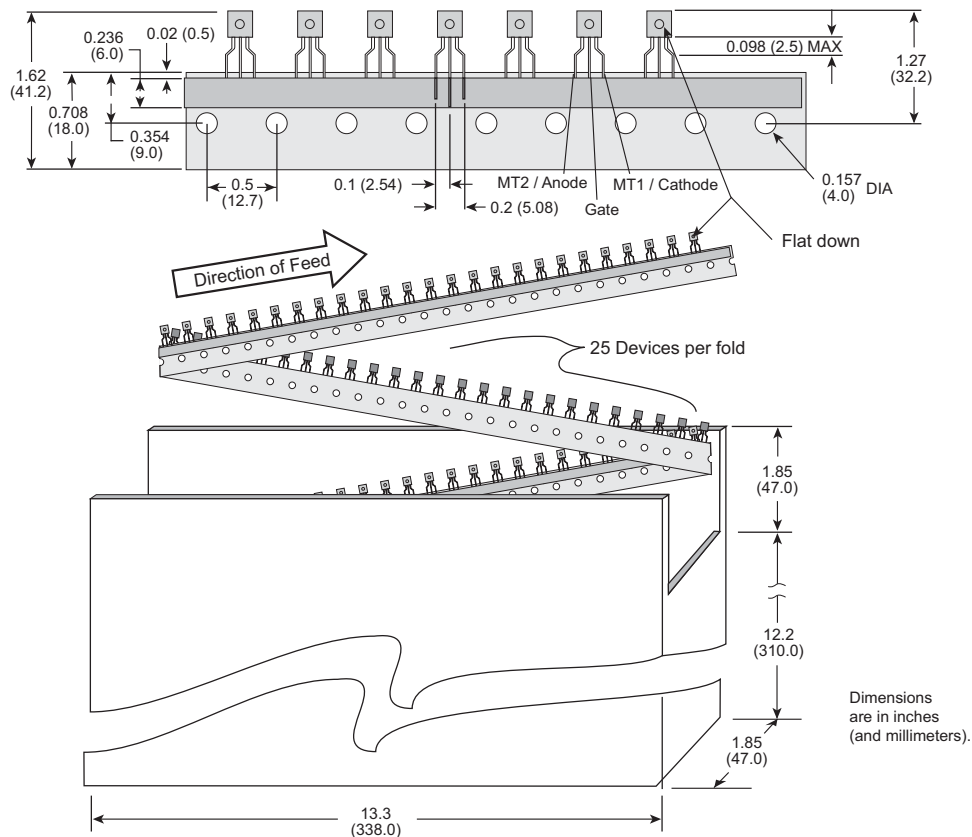
Part Number	Marking	Weight	Packing Mode	Base Quantity
L/QxX8Ey	L/QxX8Ey	0.188 g	Bulk	2000
L/QxX8EyRP	L/QxX8Ey	0.188 g	Reel Pack	2000
L/QxX8EyAP	L/QxX8Ey	0.188 g	Ammo Pack	2000
L/QxXyRP	L/QxXy	0.081 g	Embossed Carrier	2500

Note: x = voltage, y = sensitivity

Meets all EIA-468-B 1994 Standards

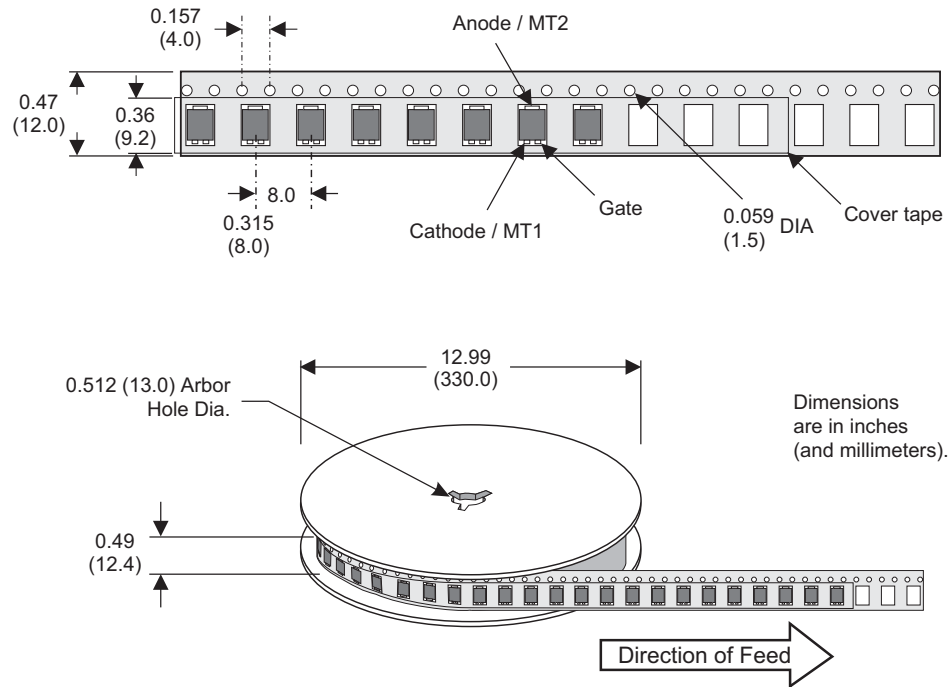


Meets all EIA-468-B 1994 Standards

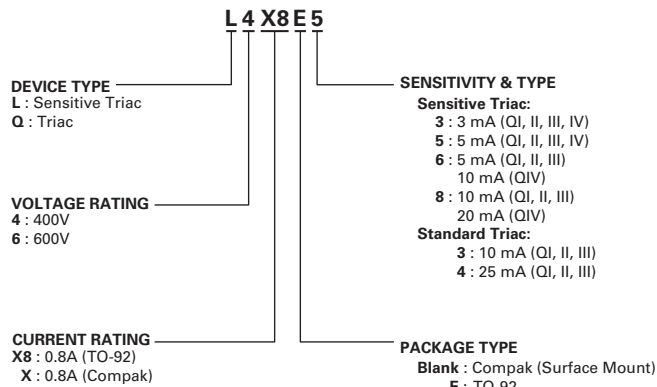


Compak Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-1 Standards



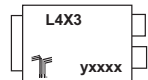
Part Numbering System



Part Marking System

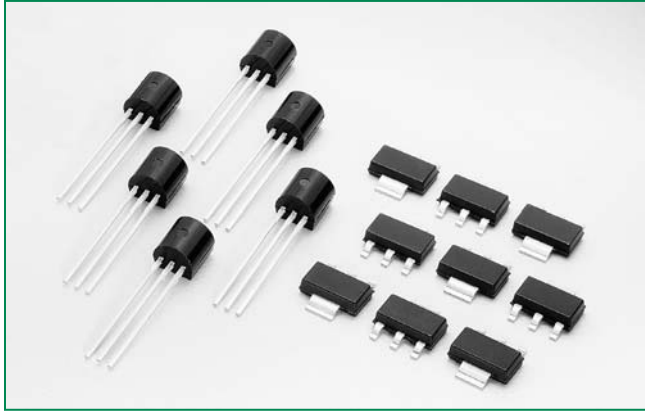
TO-92 (E Package)

Compak (C Package)





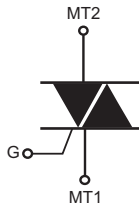
RoHS **LX8 Series**



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	400 to 600	V
I_{GT}	3 to 5	mA

Schematic Symbol



Description

New 0.8 Amp bi-directional solid state switch series offering direct interface to microprocessor drivers in economical TO-92 and surface mount packages. The die voltage blocking junctions are glass-passivated to ensure long term reliability and parametric stability.

Features & Benefits

- RoHS compliant
- Blocking voltage (V_{DRM}) capability — up to 600V
- Surge capability > 9.5Amps
- Static dv/dt > 10 Volts/ μ sec
- Thru hole and surface mount packages

Applications

The LX8 EV Series is especially designed for low current applications such as heating controls in hair care products, as well as replacement of mechanical switch contacts where long life is required.

Absolute Maximum Ratings

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-92	$T_C = 50^{\circ}C$	0.8A	A
		SOT-223	$T_L = 90^{\circ}C$		
I_{TSM}	Non repetitive surge peak on-state current (Single cycle, T_J initial = $25^{\circ}C$)	TO-92	F = 50 Hz	8.0	A
		SOT-223	F = 60 Hz	9.5	
I^2t	I^2t Value for fusing	$t_p = 10$ ms	F = 50 Hz	0.32	A^2s
		$t_p = 8.3$ ms	F = 60 Hz	0.37	
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$	TO-92 SOT-223	$T_J = 110^{\circ}C$	20	A/ μs
I_{GTM}	Peak gate current	$t_p = 10$ μs	$T_J = 110^{\circ}C$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 110^{\circ}C$	0.1	W
T_{stg}	Storage junction temperature range			-40 to 150	$^{\circ}C$
T_J	Operating junction temperature range			-40 to 110	$^{\circ}C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Quadrant	Limit	Value		Unit
					LX803xy	LX807xy	
I_{GT}	DC Gate Trigger Current	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III IV	MAX.	3 5	5 7	mA
V_{GT}	DC Gate Trigger Voltage		ALL	MAX.	1.3	1.3	V
I_H	Holding Current	Gate Open		MAX.	5	5	mA
dv/dt	Critical Rate-of-Rise of Off-State Voltage	$T_J = 110^\circ\text{C}$ $V_D = V_{DRM}$ Exponential Waveform Gate Open		MIN.	10	10	V/ μs
$(dv/dt)_c$	Critical Rate-of-Rise of Commutating Voltage	$(di/dt)_c = 0.43\text{A/ms}$ $T_J = 110^\circ\text{C}$		MIN.	1.5	1.5	V/ μs
t_{gt}	Turn-On Time	$I_G = 25\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 1.2\text{A (pk)}$		MAX.	2.0	2.0	μs

NOTE: x = voltage, y = package

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value	Unit
V_{TM}	Peak On-State Voltage	$I_{TM} = 1.13\text{A (pk)}$	MAX	1.60	V
I_{DRM}	Off-State Current, Peak Repetitive	$V_D = V_{DRM}$ $T_J = 25^\circ\text{C}$	MAX	5	μA
		$V_D = V_{DRM}$ $T_J = 110^\circ\text{C}$		100	μA

Thermal Resistances

Symbol	Description	Test Conditions	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	$I_T = 0.8\text{A}_{(RMS)}^1$	TO-92	60
			SOT-223	25
$R_{th(j-a)}$	Junction to ambient	$I_T = 0.8\text{A}_{(RMS)}^1$	TO-92	150
			SOT-223	60

¹ 60Hz AC resistive load condition, 100% conduction.

Figure 1: Definition of Quadrants

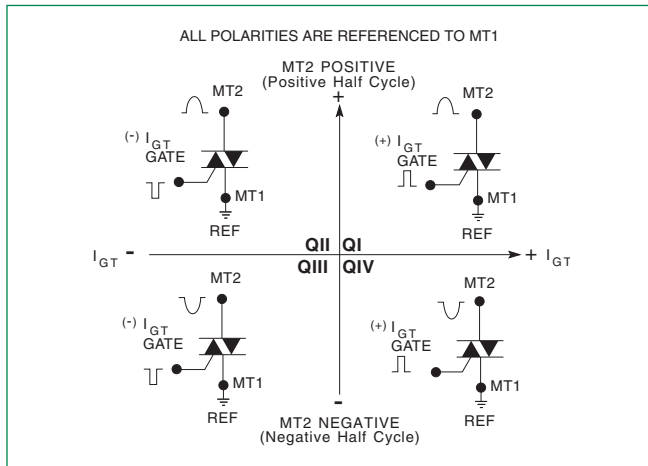


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

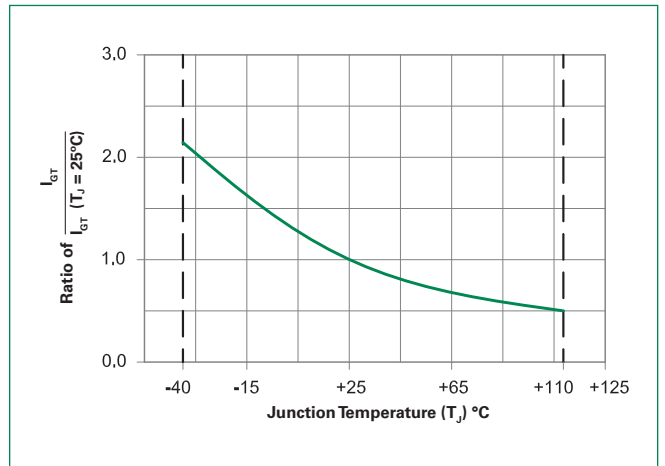


Figure 3: Normalized DC Holding Current vs. Junction Temperature

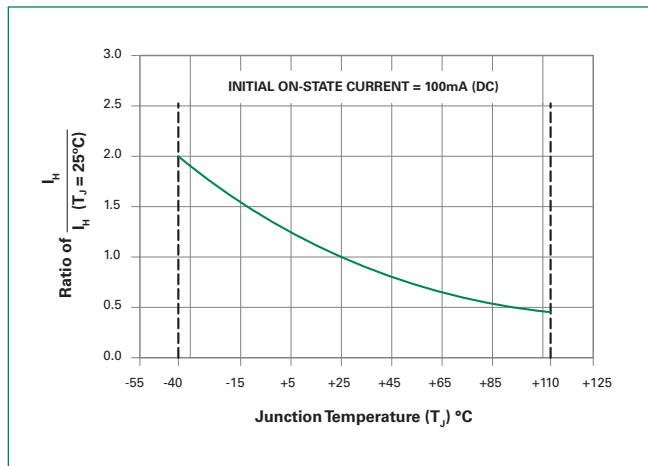


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

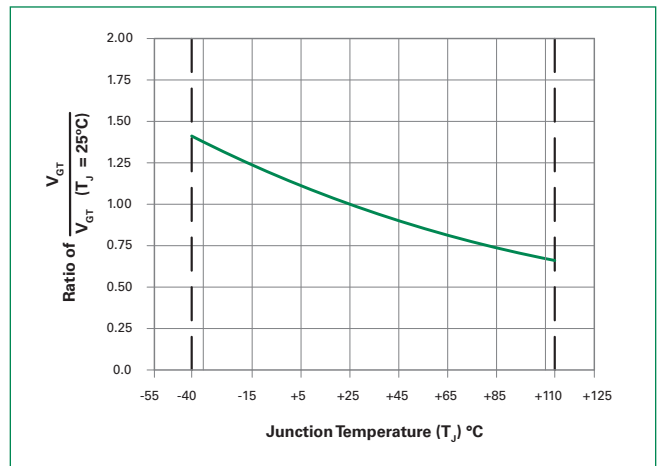


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

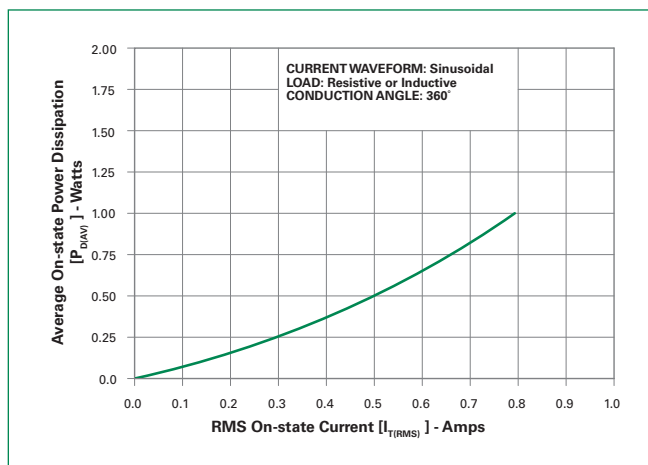


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

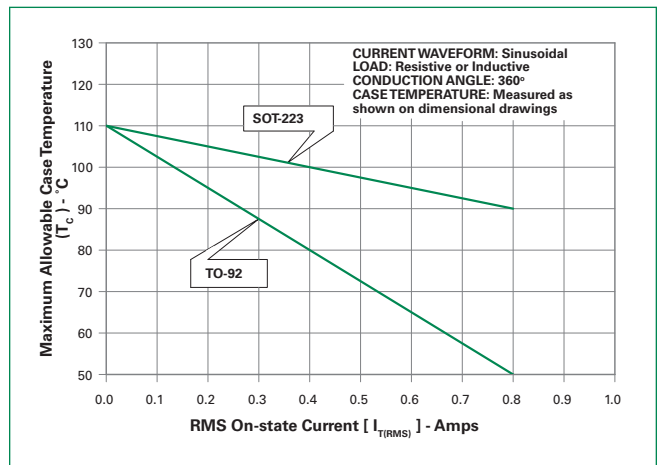
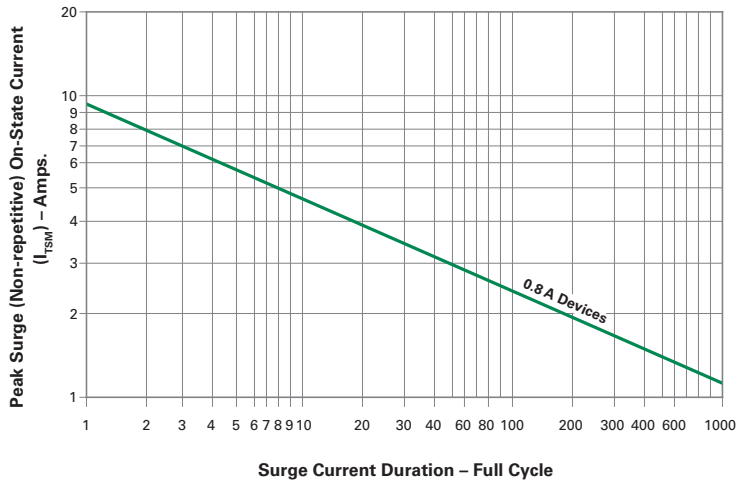


Figure 7: Surge Peak On-State Current vs. Number of Cycles



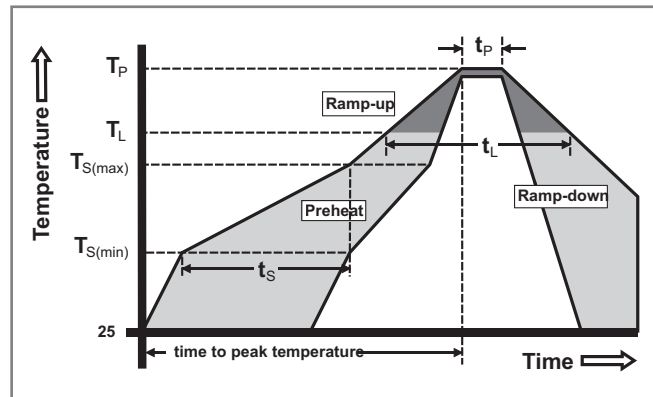
Supply Frequency: 60Hz Sinusoidal
Load: Resistive
RMS On-State Current (I_{T(RMS)}): Max Rated Value at Specific Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min (T _{s(min)})	150°C
	- Temperature Max (T _{s(max)})	200°C
	- Time (min to max) (t _s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T _L) to peak		5°C/second max
T _{S(max)} to T _L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T _L) (Liquidus)	217°C
	- Time (min to max) (t _s)	60 – 150 seconds
Peak Temperature (T _p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T _p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Lead Material	Copper Alloy

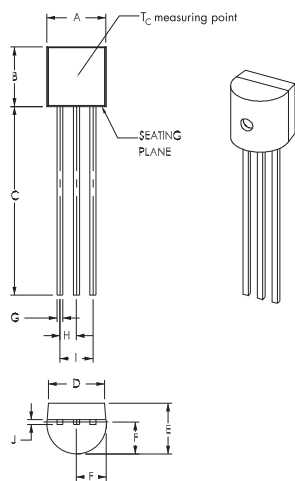
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Reliability/Environmental Tests

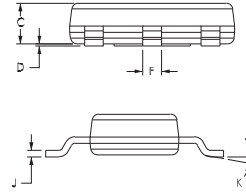
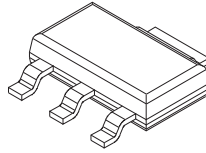
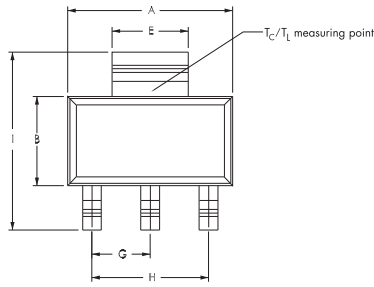
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 110°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-92 (E Package)

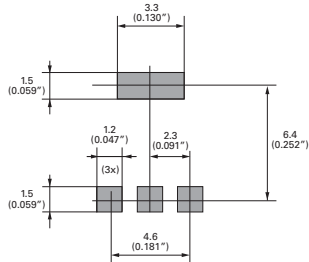


Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.175	—	0.205	4.450	—	5.200
B	0.170	—	0.210	4.320	—	5.330
C	0.500	—	—	12.700	—	—
D	0.135	0.165	—	3.430	4.190	—
E	0.125	—	0.165	3.180	—	4.190
F	0.080	0.095	0.105	2.040	2.400	2.660
G	0.016	—	0.021	0.407	—	0.533
H	0.045	0.050	0.055	1.150	1.270	1.390
I	0.095	0.100	0.105	2.420	2.540	2.660
J	0.015	—	0.020	0.380	—	0.500

Dimensions – SOT-223



Pad Layout for SOT-223



Dimensions in Millimeters (Inches)

Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.248	0.256	0.264	6.30	6.50	6.70
B	0.130	0.138	0.146	3.30	3.50	3.70
C	—	—	0.071	—	—	1.80
D	0.001	—	0.004	0.02	—	0.10
E	0.114	0.118	0.124	2.90	3.00	3.15
F	0.024	0.027	0.034	0.60	0.70	0.85
G	—	0.090	—	—	2.30	—
H	—	0.181	—	—	4.60	—
I	0.264	0.276	0.287	6.70	7.00	7.30
J	0.009	0.010	0.014	0.24	0.26	0.35
K	10° MAX					

Product Selector

Part Number	Voltage	Gate Sensitivity Quadrants		Package
		I – II – III	IV	
LX803DE	400 V	3 mA	5 mA	TO-92
LX803ME	600 V	3 mA	5 mA	TO-92
LX803DT	400 V	3 mA	5 mA	SOT-223
LX803MT	600 V	3 mA	5 mA	SOT-223
LX807DE	400 V	5 mA	7 mA	TO-92
LX807ME	600 V	5 mA	7 mA	TO-92
LX807DT	400 V	5 mA	7 mA	SOT-223
LX807MT	600 V	5 mA	7 mA	SOT-223

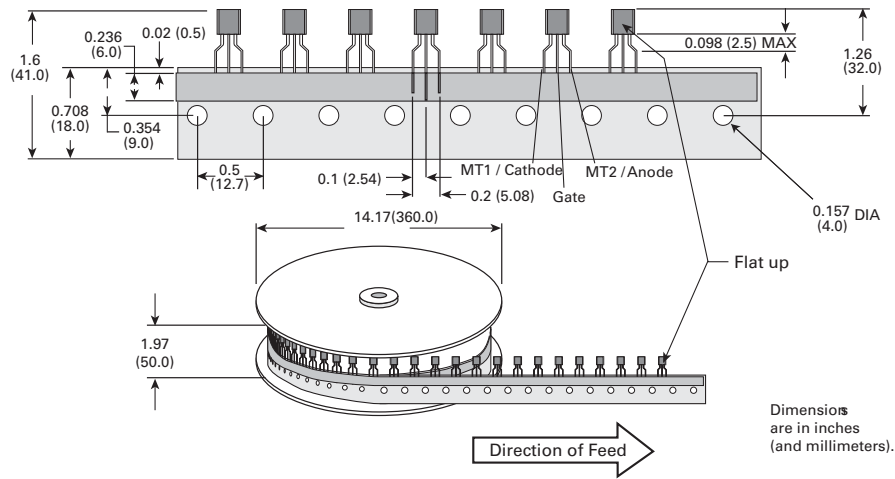
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
LX8xyE	LX8xyE	0.170 g	Bulk	2500
LX8xyEAP	LX8xyE	0.170 g	Ammo Pack	2000
LX8xyERP	LX8xyE	0.170 g	Tape & Reel	2000
LX8xyTRP	LX8xyT	0.120 g	Tape & Reel	1000

Note: xx = gate sensitivity, y = voltage

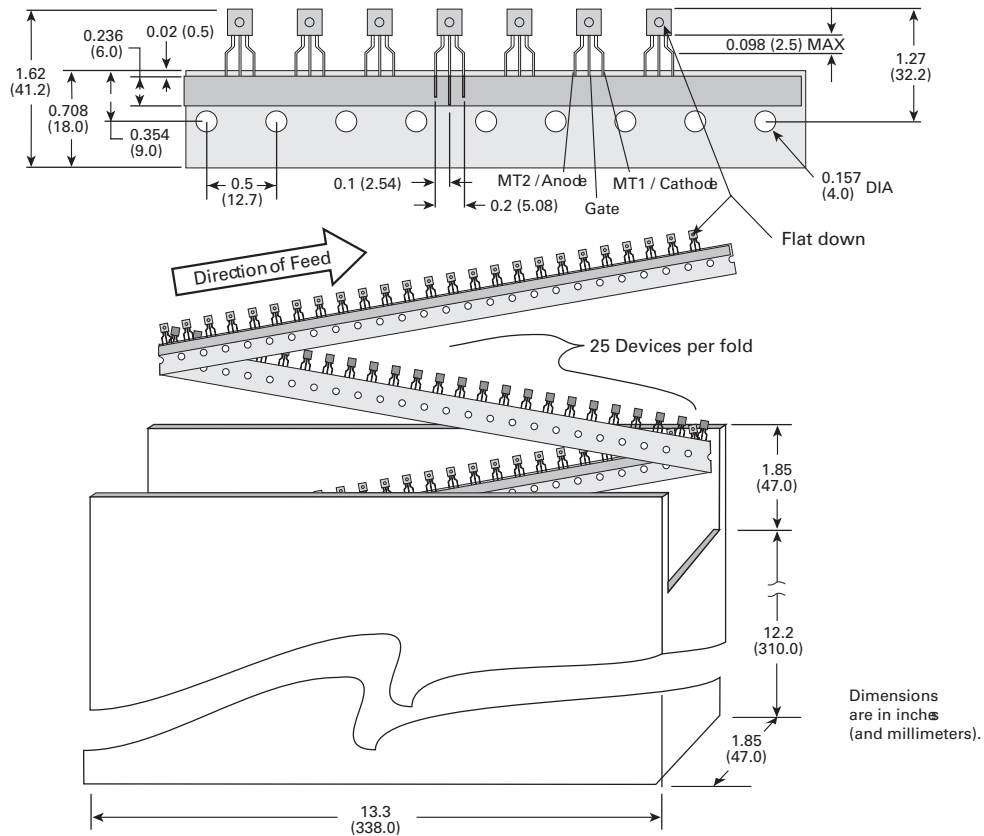
TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards

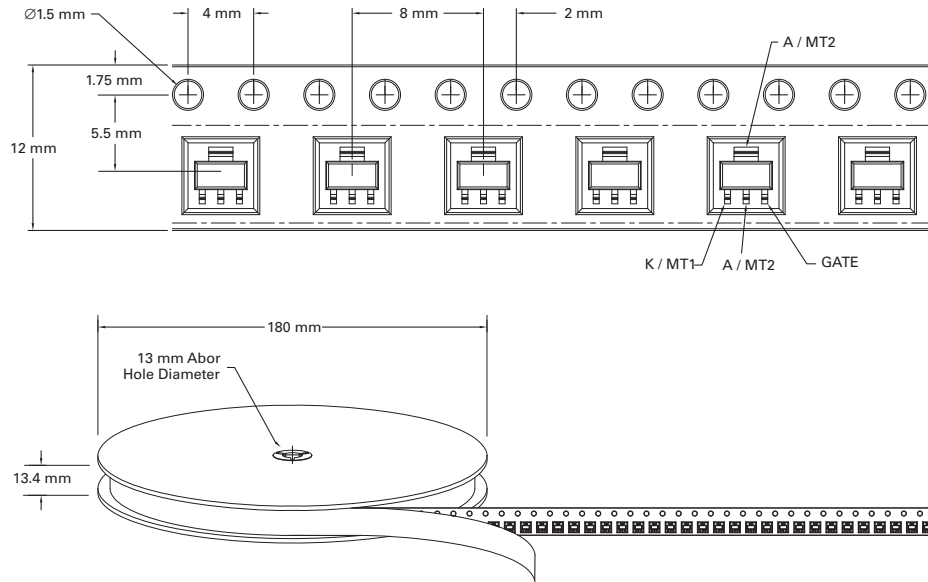


TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

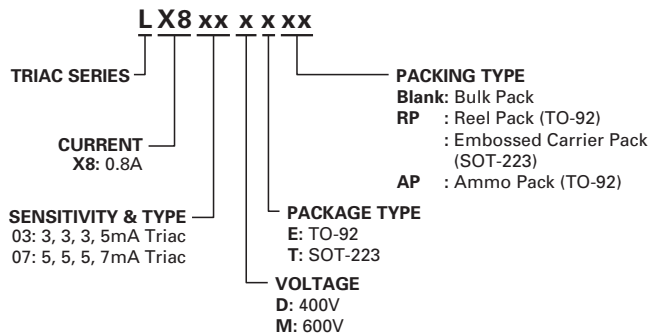
Meets all EIA-468-B 1994 Standards



SOT-223 Reel Pack (RP) Specifications

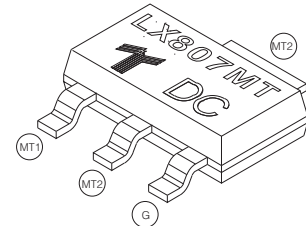
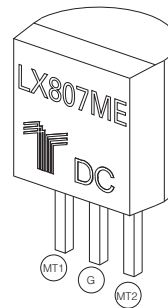


Part Numbering System

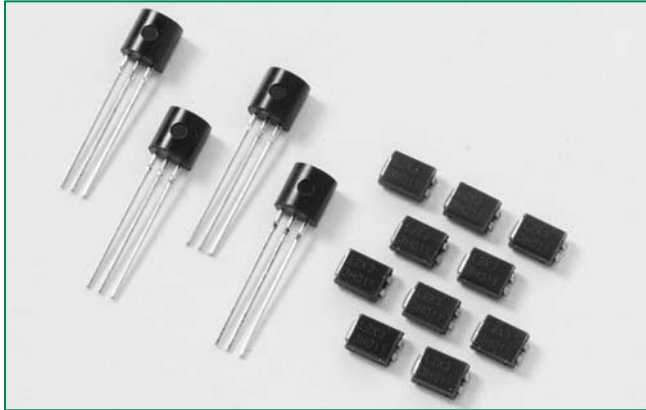


Part Marking System

DC
Date Code
(2 Digits Min.)
Number = Year
Letter = Month



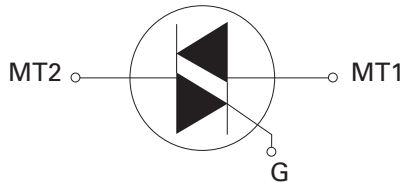
RoHS Lx01Ex & LxNx & Qx01Ex & QxNx Series



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	400 to 600	V
$I_{GT(Q1)}$	3 to 25	mA

Schematic Symbol



Description

1 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 20 A

Applications

Excellent for lower current heating controls, water valves, and solenoids.

Typical applications are AC solid-state switches, home/ brown goods and white goods appliances.

Sensitive gate Triacs can be directly driven by microprocessor or popular opto-couplers/isolators.

Absolute Maximum Ratings — Sensitive Triacs (4 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Lx01Ey/LxNy	$T_c = 50^\circ\text{C}$	1	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	$f = 50 \text{ Hz}$	$t = 20 \text{ ms}$	16.7	A
		$f = 60 \text{ Hz}$	$t = 16.7 \text{ ms}$	20	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$		1.6	A^2s
di/dt	Critical rate of rise of on-state current ($I_g = 50\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	$f = 120 \text{ Hz}$	$T_j = 110^\circ\text{C}$	20	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$	$T_j = 110^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 110^\circ\text{C}$		0.2	W
T_{stg}	Storage temperature range	Lx01Ey	-65 to 150		$^\circ\text{C}$
		LxNy	-40 to 125		
T_j	Operating junction temperature range	Lx01Ey	-65 to 110		$^\circ\text{C}$
		LxNy	-40 to 110		

Note: x = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triacs

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qx01Ey/QxNy	$T_c = 60^\circ\text{C}$	1	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	16.7	A
		f = 60 Hz	t = 16.7 ms	60	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		1.6	A ² s
di/dt	Critical rate of rise of on-state current ($I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_J = 125^\circ\text{C}$	20	A/ μs
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s};$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.2	W
T_{stg}	Storage temperature range		L/Qx01Ey	-65 to 150	$^\circ\text{C}$
			L/QxNy	-40 to 150	
T_J	Operating junction temperature range		L/Qx01Ey	-65 to 125	$^\circ\text{C}$
			L/QxNy	-40 to 125	

Note: x = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		Lx01E3 LxN3	Lx01E5 LxN5	Lx01E6 LxN6	Lx01E8 LxN8	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	3	5	5	10	mA
		IV		3	5	10	20	
V_{GT}		ALL	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2				V
I_H	$I_T = 100\text{mA}$		MAX.	5	10	10	15	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	400V	TYP.	20	20	30	35	V/ μs
		600V		10	10	20	25	
(dv/dt)c	(di/dt)c = 0.54 A/ms $T_J = 110^\circ\text{C}$		TYP.	0.5	1	1	1	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 1.41$ A(pk)		TYP.	2.8	3.0	3.0	3.2	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Qx01E3 QxN3	Qx01E4 QxN4	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	10	25	mA
		IV	TYP.	25	50	
V_{GT}		I – II – III	MAX.	1.3	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$	ALL	MIN.	0.2	0.2	V
I_H	$I_T = 200\text{mA}$		MAX.	15	25	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	30	40	V/ μs
		600V		20	30	
(dv/dt)c	(di/dt)c = 0.54 A/ms $T_J = 125^\circ\text{C}$		TYP.	1	1	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 1.41$ A(pk)		TYP.	2.5	3.0	μs

Note: x = voltage, y = sensitivity

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions				Value	Unit
V_{TM}	$I_{TM} = 1.41\text{A}$ $t_p = 380\ \mu\text{s}$	MAX.			1.60	V
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$	MAX.	Lx01Ey / LxNy	$T_J = 25^\circ\text{C}$	400-600V	2 μA
				$T_J = 110^\circ\text{C}$	400-600V	0.1 mA
			Qx01Ey / QxNy	$T_J = 25^\circ\text{C}$	400-600V	5 μA
				$T_J = 125^\circ\text{C}$	400-600V	1 mA

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	L/Qx01Ey	50	$^\circ\text{C}/\text{W}$
		L/QxNy	40*	
$R_{\theta(J-A)}$	Junction to ambient	L/Qx01Ey	95	$^\circ\text{C}/\text{W}$

Note: * = Mounted on 1 cm² copper (two-ounce) foil surface

Figure 1: Definition of Quadrants

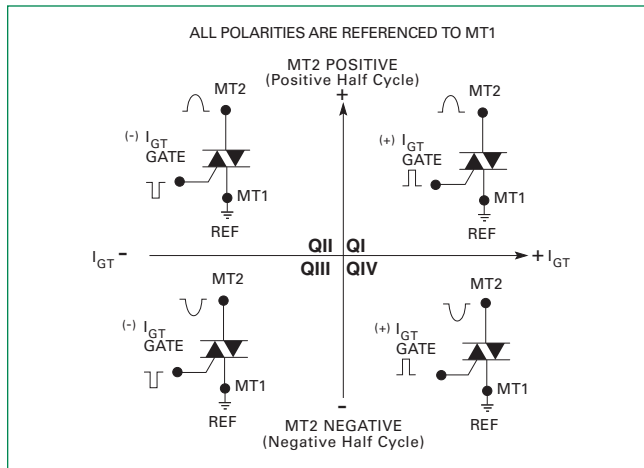


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

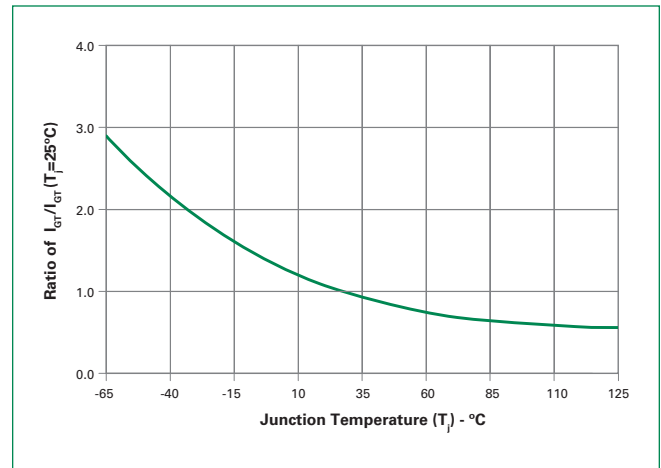


Figure 3: Normalized DC Holding Current vs. Junction Temperature

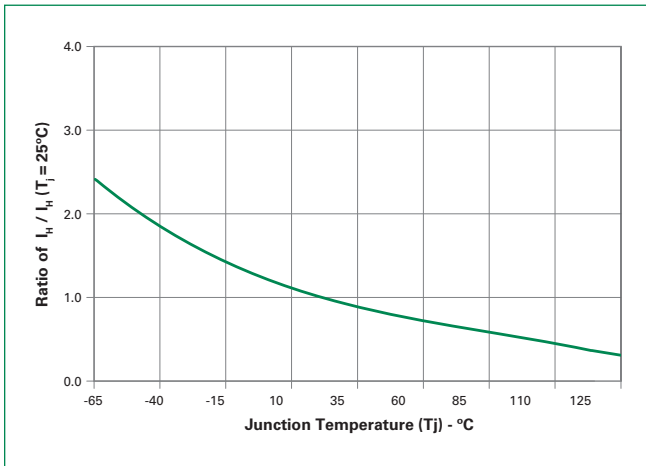


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

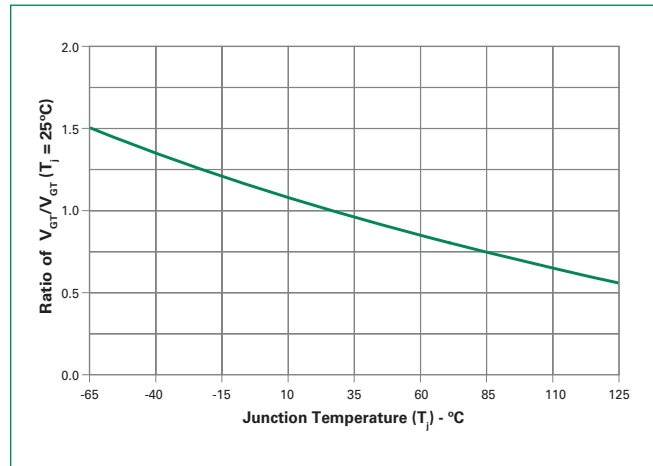


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

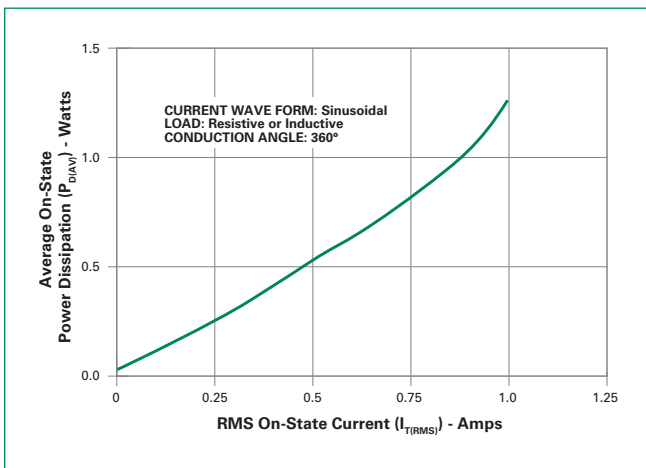


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

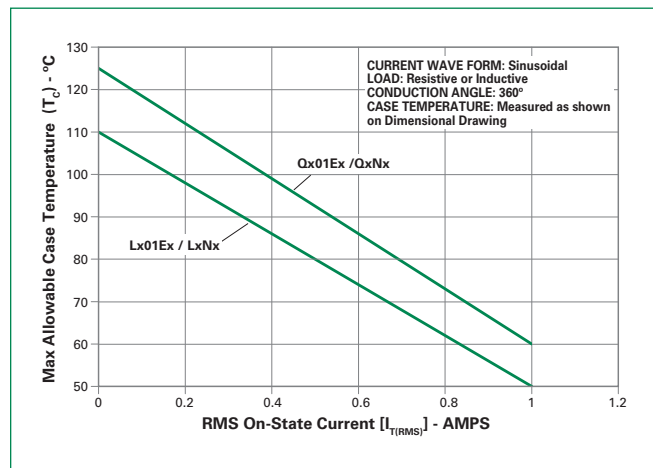


Figure 7: Maximum Allowable Ambient Temperature vs. On-State Current

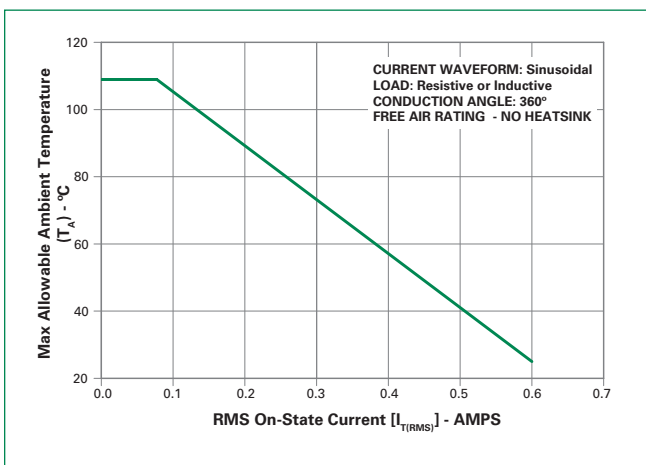


Figure 8: On-State Current vs. On-State Voltage (Typical)

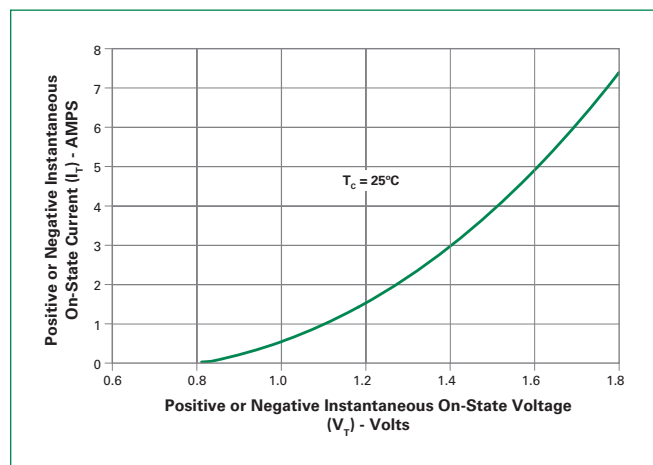
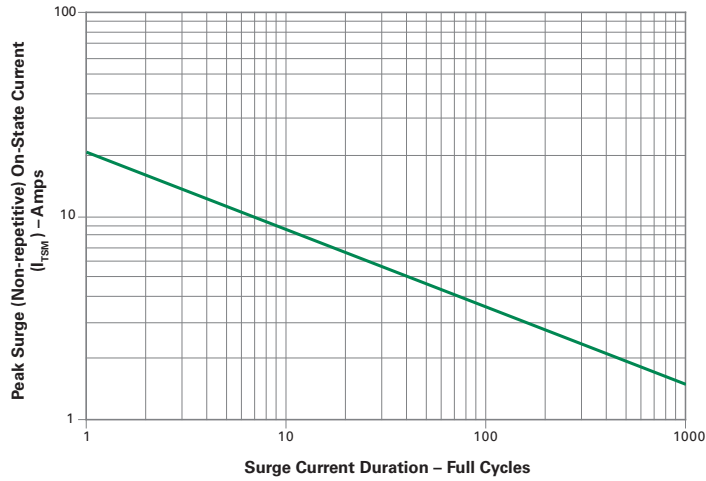


Figure 9: Surge Peak On-State Current vs. Number of Cycles



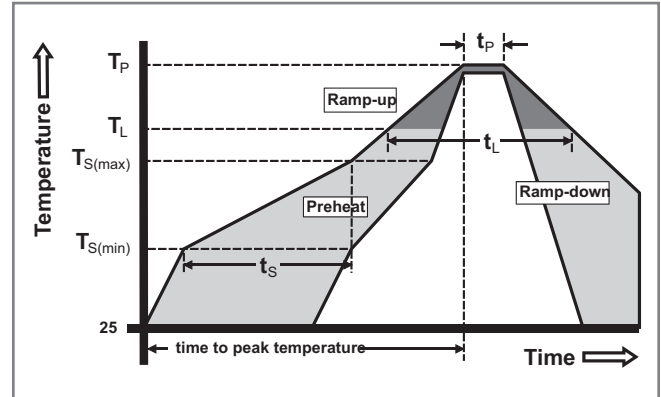
Supply Frequency: 60Hz Sinusoidal
Load: Resistive
RMS On-State [$I_{T(RMS)}$]: Max Rated Value at Specific Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260°C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

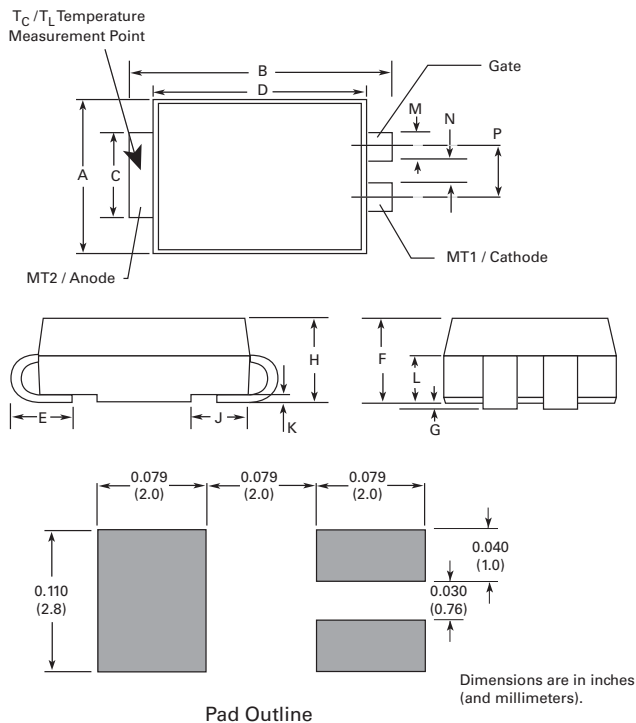
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

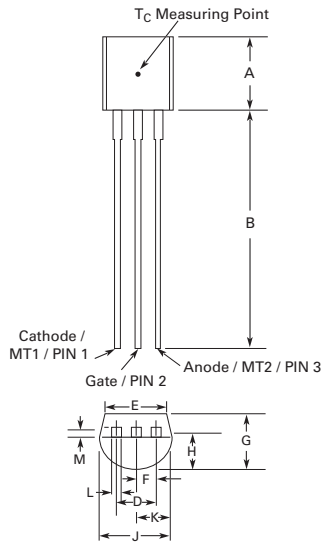
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions - Compak (C Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.140	0.155	3.56	3.94
B	0.205	0.220	5.21	5.59
C	0.077	0.083	1.96	2.11
D	0.166	0.180	4.22	4.57
E	0.036	0.063	0.91	1.60
F	0.066	0.083	1.67	2.11
G	0.004	0.008	0.10	0.20
H	0.077	0.086	1.96	2.18
J	0.043	0.053	1.09	1.35
K	0.008	0.012	0.20	0.30
L	0.039	0.049	0.99	1.24
M	0.022	0.028	0.56	0.71
N	0.027	0.033	0.69	0.84
P	0.052	0.058	1.32	1.47

Dimensions - TO-92 (E Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500	-	12.70	-
D	0.095	0.105	2.41	2.67
E	0.150	-	3.81	-
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43

All leads insulated from case. Case is electrically nonconductive.

Product Selector

Part Number	Voltage		Gate Sensitivity Quadrants		Type	Package
	400V	600V	I – II – III	IV		
Lx01E3	X	X	3 mA	3 mA	Sensitive Triac	TO-92
LxN3	X	X	3 mA	3 mA	Sensitive Triac	Compak
Lx01E5	X	X	5 mA	5 mA	Sensitive Triac	TO-92
LxN5	X	X	5 mA	5 mA	Sensitive Triac	Compak
Lx01E6	X	X	5 mA	10 mA	Sensitive Triac	TO-92
Lx01E8	X	X	10 mA	20 mA	Sensitive Triac	TO-92
Qx01E3	X	X	10 mA		Standard Triac	TO-92
QxN3	X	X	10 mA		Standard Triac	Compak
Qx01E4	X	X	25 mA		Standard Triac	TO-92
QxN4	X	X	25 mA		Standard Triac	Compak

Note: x- voltage

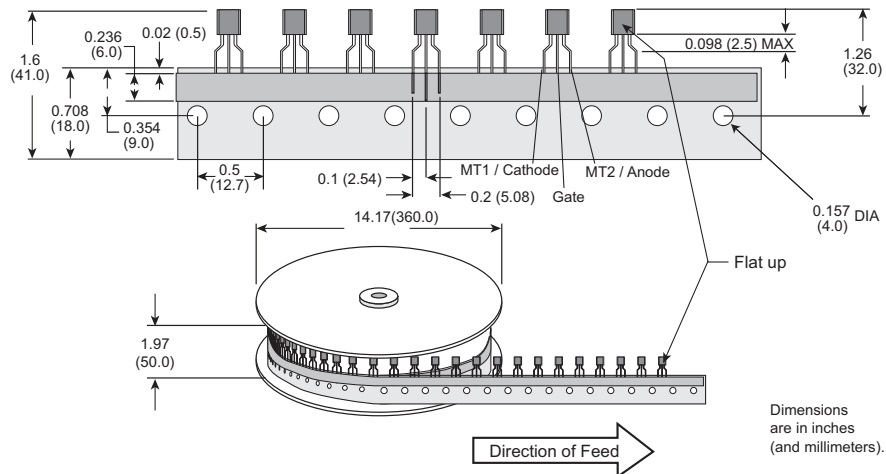
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
L/Qx01Ey	L/Qx01Ey	0.188 g	Bulk	2000
L/Qx01EyRP	L/Qx01Ey	0.188 g	Reel Pack	2000
L/Qx01EyAP	L/Qx01Ey	0.188 g	Ammo Pack	2000
L/QxNyRP	L/QxNy	0.081 g	Embossed Carrier	2500

Note: x = Voltage; y = Sensitivity

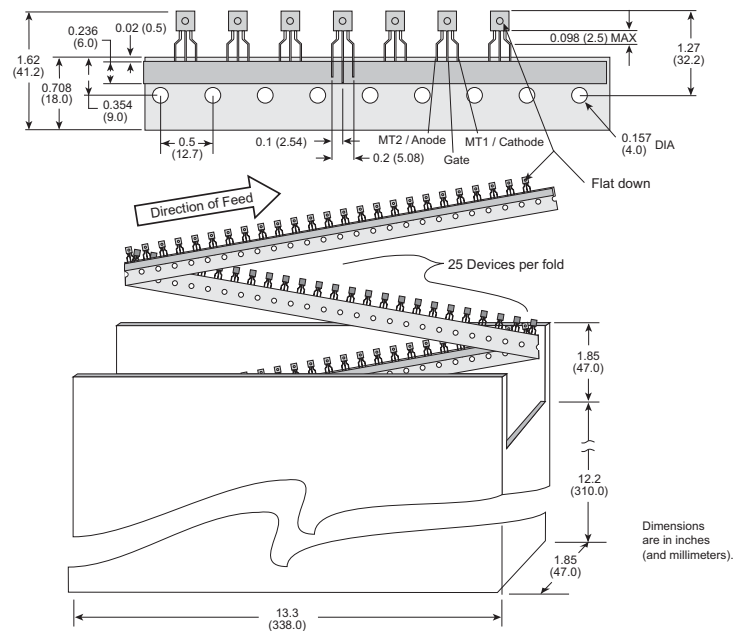
TO-92 (3-lead) Reel Pack (RP) Radial Leaded

Meets all EIA-468-B 1994 Standards



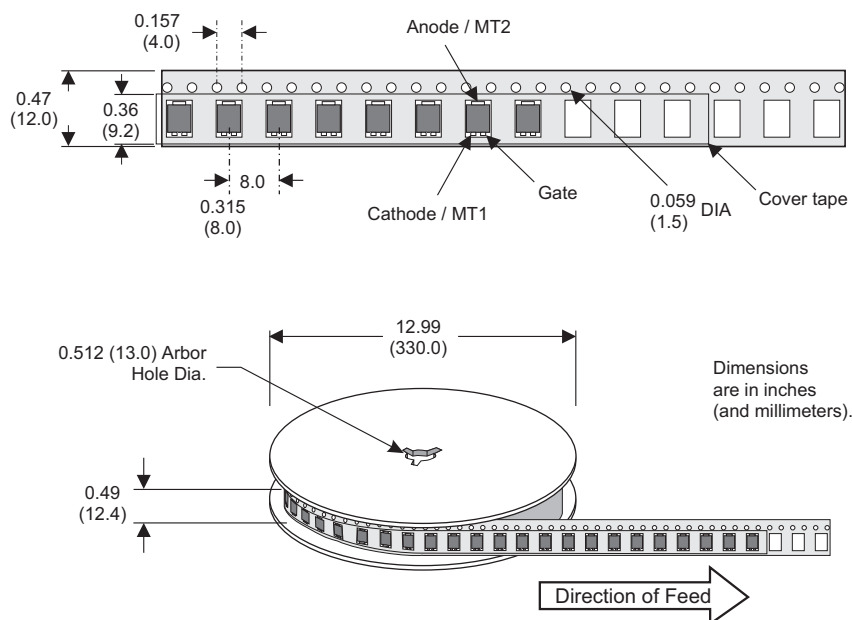
TO-92 (3-lead) Ammo Pack (AP) Radial Leaded

Meets all EIA-468-B 1994 Standards

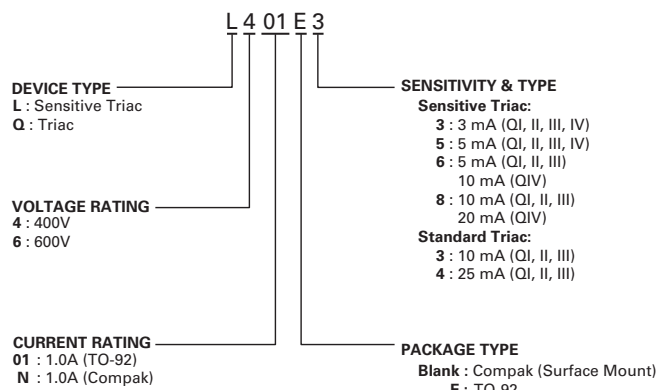


Compak Embossed Carrier Reel Pack (RP)

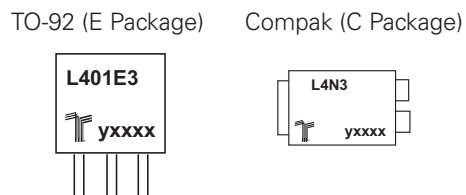
Meets all EIA-481-1 Standards



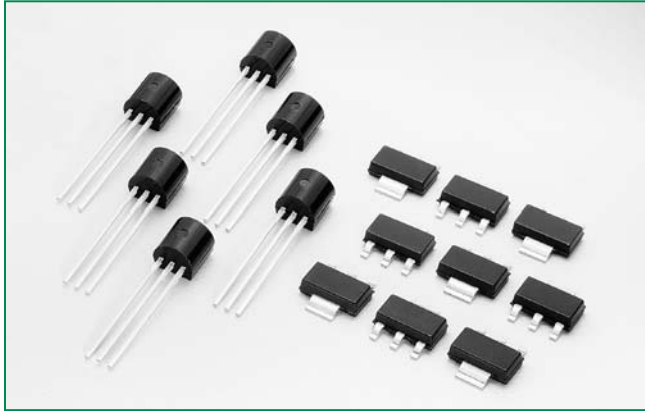
Part Numbering System



Part Marking System



RoHS **L01 Series**



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	400 to 800	V
I_{GT}	3 to 10	mA

Description

New 1 Amp bi-directional solid state switch series offering direct interface to microprocessor drivers in economical TO-92 and surface mount packages. The die voltage blocking junctions are glass-passivated to ensure long term reliability and parametric stability.

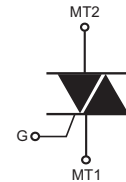
Features

- RoHS compliant
- Blocking voltage (V_{DRM}) capability — up to 800V
- Surge capability > 10Amps
- Static $dv/dt > 20$ Volts/ μ sec
- Thru hole and surface mount packages

Applications

The L01 EV Series is especially designed for white goods applications such as valve controls in washing machines as well as replacement of mechanical and hybrid relays where long life is required.

Schematic Symbol



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-92 $T_c = 50^\circ\text{C}$	1.0A A
		SOT-223 $T_L = 90^\circ\text{C}$	
I_{TSM}	Non repetitive surge peak on-state current (Single cycle, T_j initial = 25°C)	TO-92 SOT-223 $F = 50$ Hz	10 12 A
		$F = 60$ Hz	
I^2t	I^2t Value for fusing	$t_p = 10$ ms $F = 50$ Hz	0.50 0.59 A^2s
		$t_p = 8.3$ ms $F = 60$ Hz	
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$	TO-92 SOT-223 $T_j = 125^\circ\text{C}$	20 $\text{A}/\mu\text{s}$
I_{GTM}	Peak gate current	$t_p = 10$ μs $T_j = 125^\circ\text{C}$	1 A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.1 W
T_{stg}	Storage junction temperature range		-40 to 150 $^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 125 $^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Quadrant	Limit	Value			Unit
					L0103xy	L0107xy	L0109xy	
I_{GT}	DC Gate Trigger Current	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III IV	MAX.	3 5	5 7	10 10	mA
V_{GT}	DC Gate Trigger Voltage		ALL	MAX.	—	1.3	—	V
I_H	Holding Current	Gate Open		MAX.	7	10	10	mA
dv/dt	Critical Rate-of-Rise of Off-State Voltage	$T_J = 110^\circ\text{C}$ $V_D = V_{DRM}$ Exponential Waveform Gate Open		MIN.	10	20	50	V/ μs
$(dv/dt)_c$	Critical Rate-of-Rise of Commutating Voltage	$(di/dt)_c = 0.54\text{A/ms}$ $T_J = 110^\circ\text{C}$		MIN.	0.5	1.0	2.0	V/ μs
T_{gt}	Turn-On Time	$I_G = 25\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 1.2\text{A (pk)}$		MAX.	2.0	2.0	2.0	μs

Note: x = voltage, y = package

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value	Unit
V_{TM}	Peak On-State Voltage	$I_{TM} = 1.4\text{A (pk)}$	MAX	1.60	V
I_{DRM}	Off-State Current, Peak Repetitive	$V_D = V_{DRM}$ $T_J = 25^\circ\text{C}$	MAX	5	μA
		$V_D = V_{DRM}$ $T_J = 125^\circ\text{C}$		500	μA

Thermal Resistances

Symbol	Description	Test Conditions		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	$I_T = 1.0\text{A}_{(RMS)}$ ¹	TO-92	50	$^\circ\text{C/W}$
			SOT-223	23	
$R_{th(j-a)}$	Junction to ambient	$I_T = 1.0\text{A}_{(RMS)}$ ¹	TO-92	100	$^\circ\text{C/W}$
			SOT-223	55	

¹ 60Hz AC resistive load condition, 100% conduction.

Figure 1: Definition of Quadrants

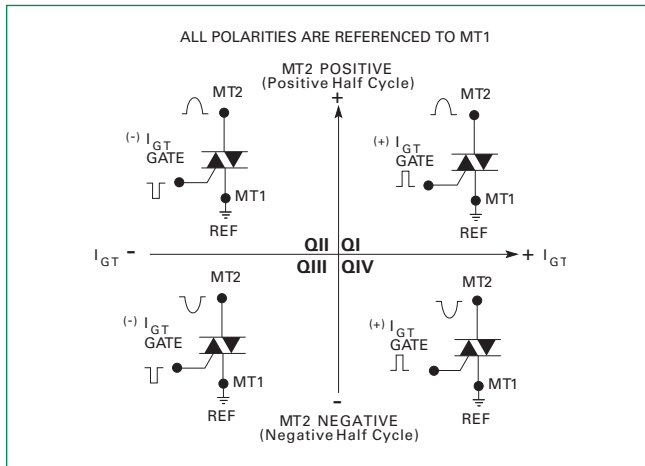


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

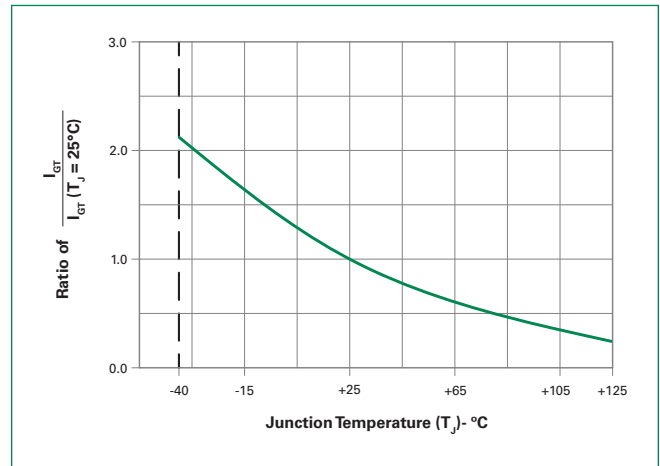


Figure 3: Normalized DC Holding Current vs. Junction Temperature

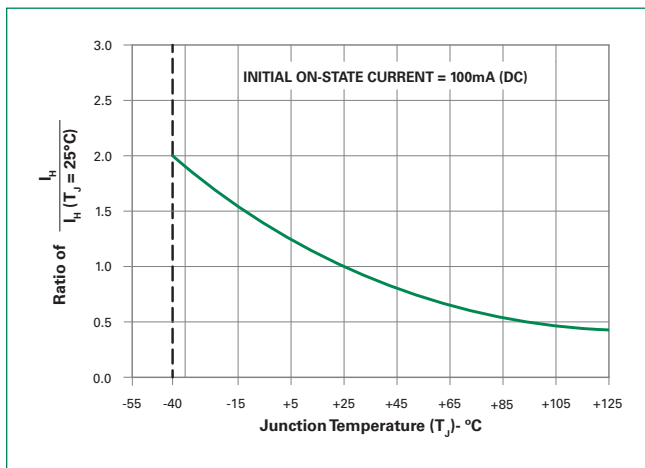


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

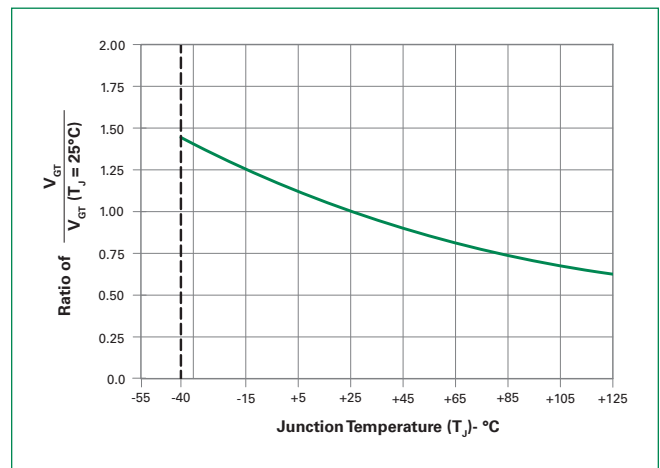


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

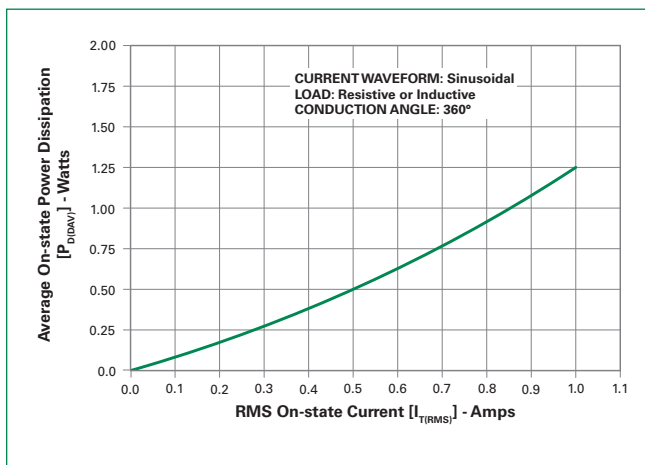


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

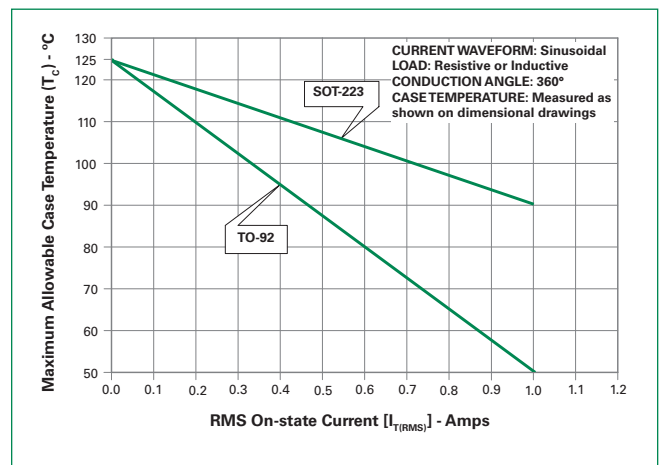
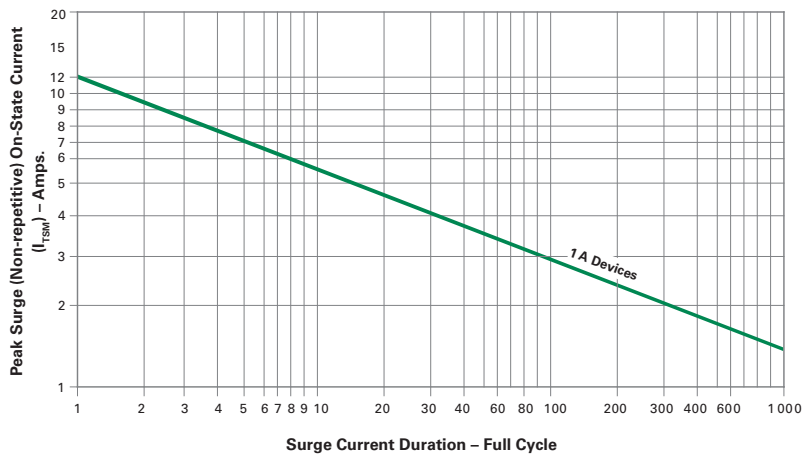


Figure 7: Surge Peak On-State Current vs. Number of Cycles

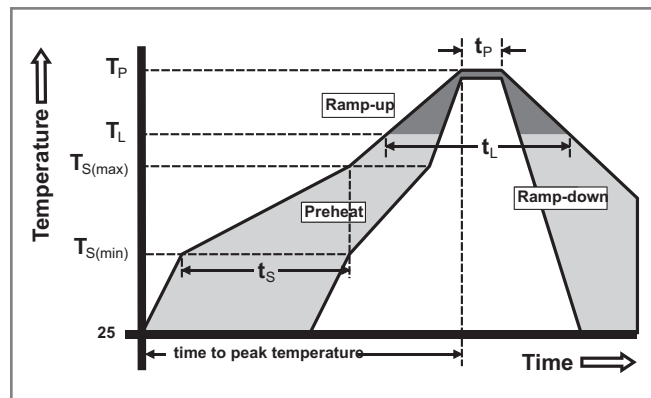


Supply Frequency: 60Hz Sinusoidal
Load: Resistive
RMS On-State Current (I_{T(RMS)}): Max Rated Value at Specific Case Temperature

Notes:
1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min (T _{s(min)})	150°C
	- Temperature Max (T _{s(max)})	200°C
	- Time (min to max) (t _s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T _L) to peak		5°C/second max
T _{s(max)} to T _L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T _L) (Liquidus)	217°C
	- Time (min to max) (t _s)	60 – 150 seconds
Peak Temperature (T _p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T _p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Lead Material	Copper Alloy

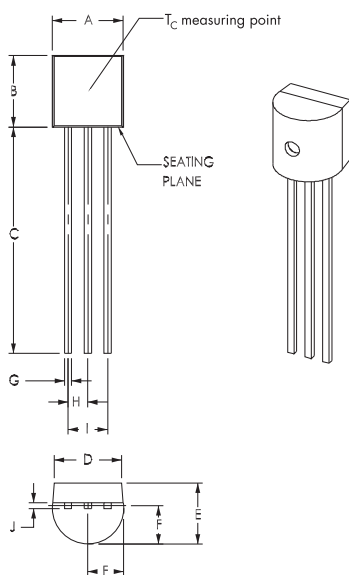
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

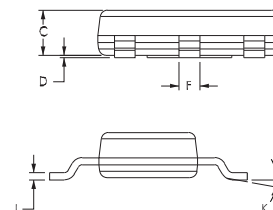
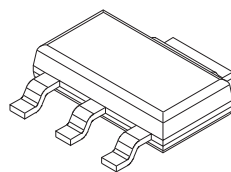
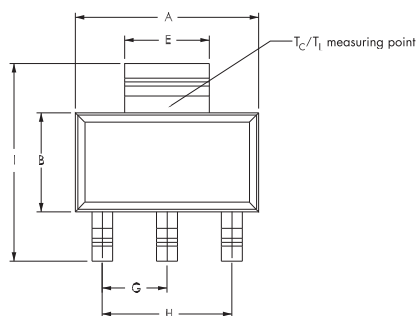
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-92 (E Package)

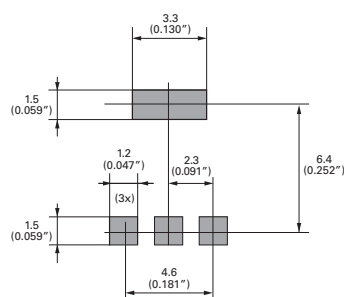


Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.175	—	0.205	4.450	—	5.200
B	0.170	—	0.210	4.320	—	5.330
C	0.500	—	—	12.700	—	—
D	0.135	0.165	—	3.430	4.190	—
E	0.125	—	0.165	3.180	—	4.190
F	0.080	0.095	0.105	2.040	2.400	2.660
G	0.016	—	0.021	0.407	—	0.533
H	0.045	0.050	0.055	1.150	1.270	1.390
I	0.095	0.100	0.105	2.420	2.540	2.660
J	0.015	—	0.020	0.380	—	0.500

Dimensions – SOT-223



Pad Layout for SOT-223



Dimensions in Millimeters (Inches)

Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.248	0.256	0.264	6.30	6.50	6.70
B	0.130	0.138	0.146	3.30	3.50	3.70
C	—	—	0.071	—	—	1.80
D	0.001	—	0.004	0.02	—	0.10
E	0.114	0.118	0.124	2.90	3.00	3.15
F	0.024	0.027	0.034	0.60	0.70	0.85
G	—	0.090	—	—	2.30	—
H	—	0.181	—	—	4.60	—
I	0.264	0.276	0.287	6.70	7.00	7.30
J	0.009	0.010	0.014	0.24	0.26	0.35
K	10° MAX					

Product Selector

Part Number	Voltage	Gate Sensitivity Quadrants		Package
		I II III	IV	
L0103DE	400 V	3 mA	5 mA	TO-92
L0103ME	600 V	3 mA	5 mA	TO-92
L0103NE	800 V	3 mA	5 mA	TO-92
L0103DT	400 V	3 mA	5 mA	SOT-223
L0103MT	600 V	3 mA	5 mA	SOT-223
L0103NT	800 V	3 mA	5 mA	SOT-223
L0107DE	400 V	5 mA	7 mA	TO-92
L0107ME	600 V	5 mA	7 mA	TO-92
L0107NE	800 V	5 mA	7 mA	TO-92
L0107DT	400 V	5 mA	7 mA	SOT-223
L0107MT	600 V	5 mA	7 mA	SOT-223
L0107NT	800 V	5 mA	7 mA	SOT-223
L0109DE	400 V	10 mA	10 mA	TO-92
L0109ME	600 V	10 mA	10 mA	TO-92
L0109NE	800 V	10 mA	10 mA	TO-92
L0109DT	400 V	10 mA	10 mA	SOT-223
L0109MT	600 V	10 mA	10 mA	SOT-223
L0109NT	800 V	10 mA	10 mA	SOT-223

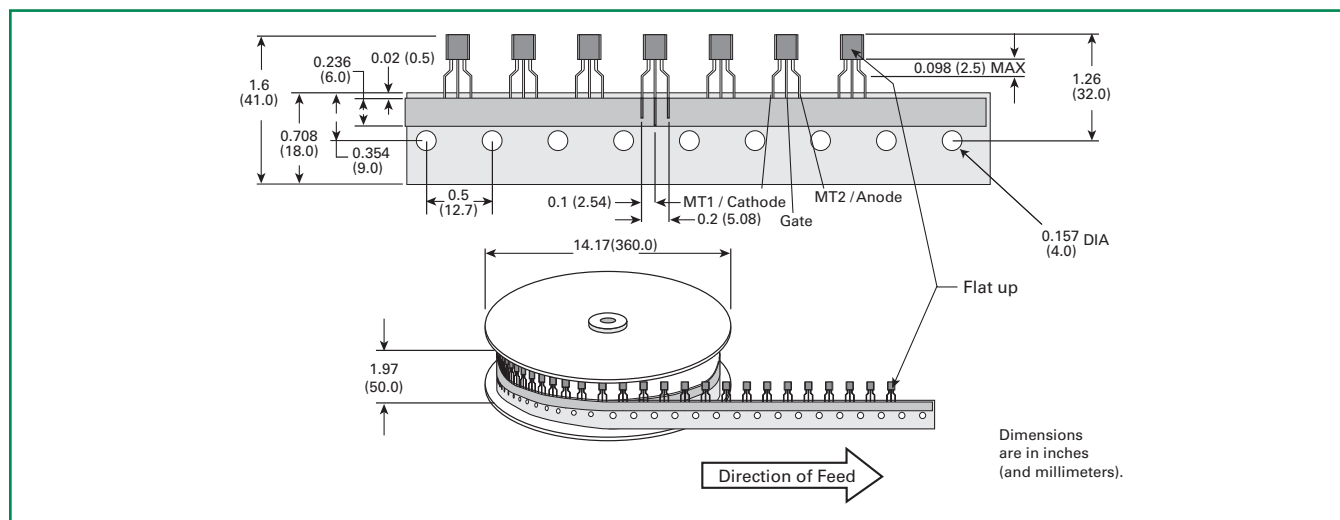
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
L01xxyE	L01xxyE	0.170 g	Bulk	2500
L01xxyEAP	L01xxyE	0.170 g	Ammo Pack	2000
L01xxyERP	L01xxyE	0.170 g	Tape & Reel	2000
L01xxyTRP	L01xxyT	0.120 g	Tape & Reel	1000

Note: xx = gate sensitivity, y = voltage

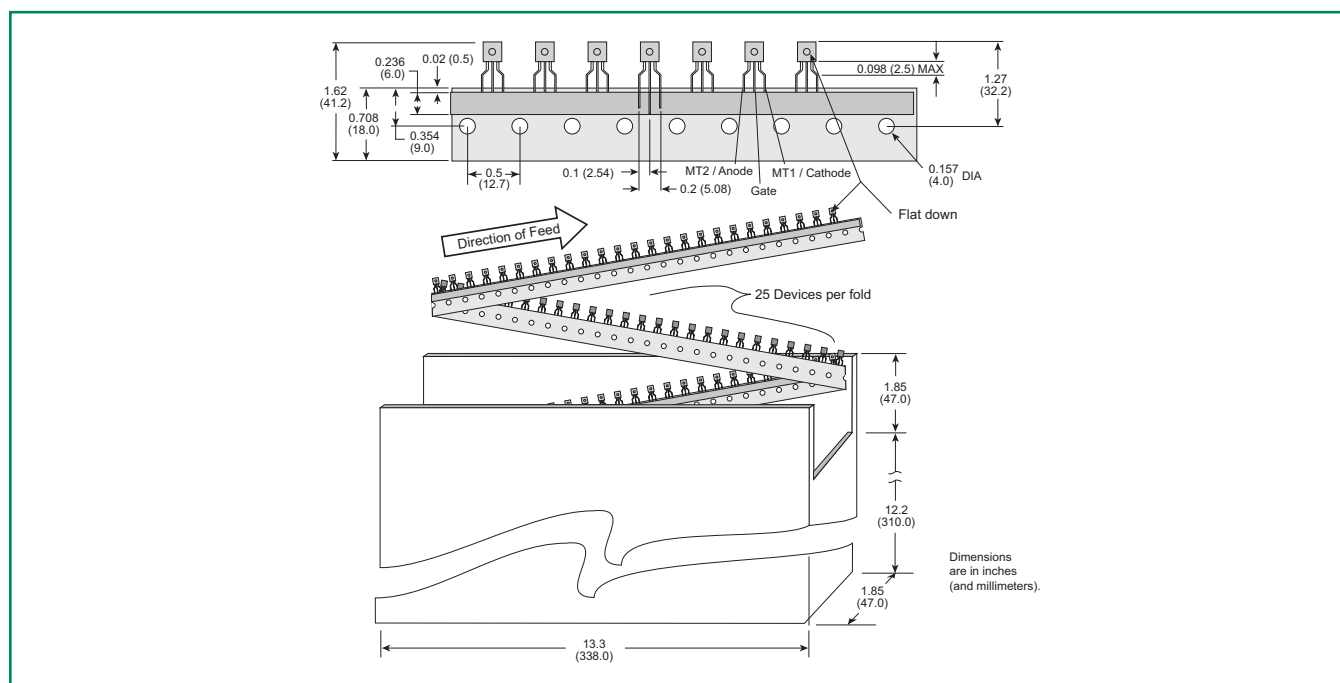
TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards

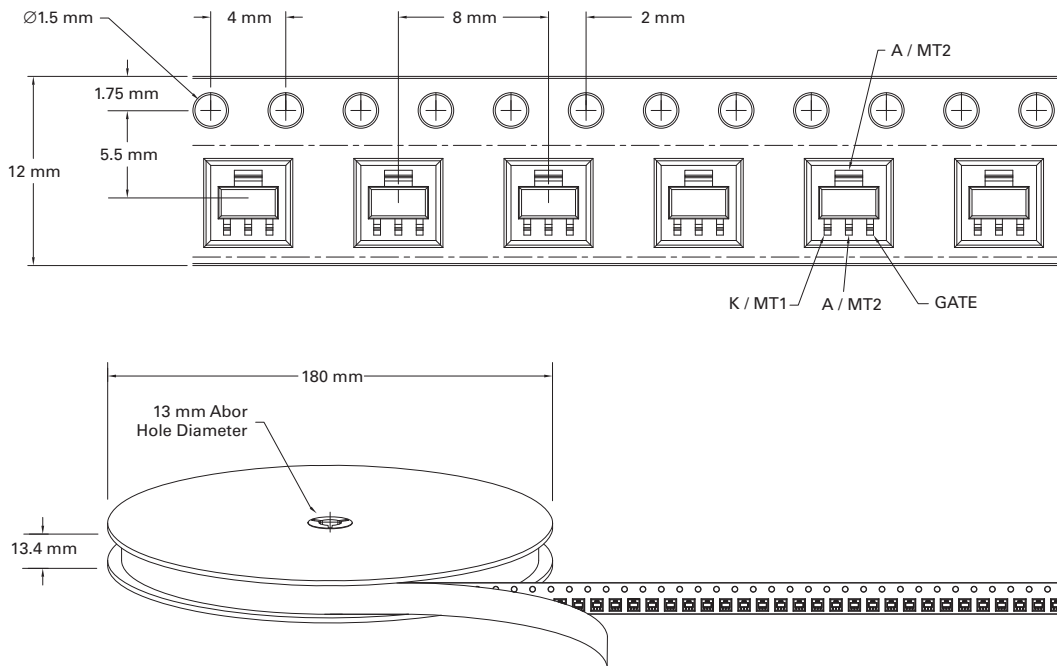


TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

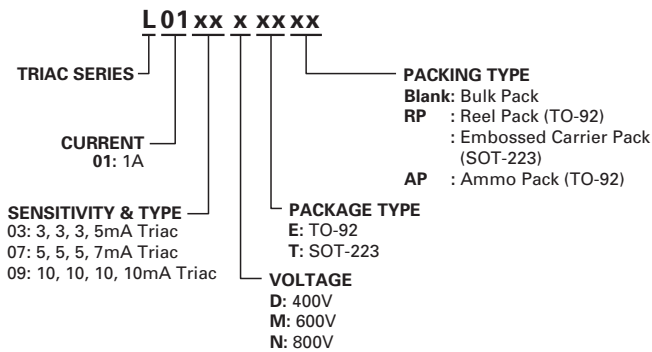
Meets all EIA-468-B 1994 Standards



SOT-223 Reel Pack (RP) Specifications

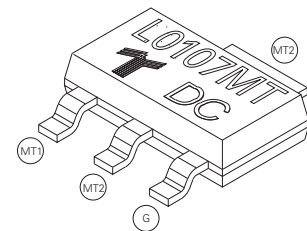
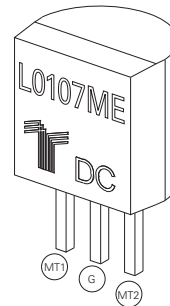


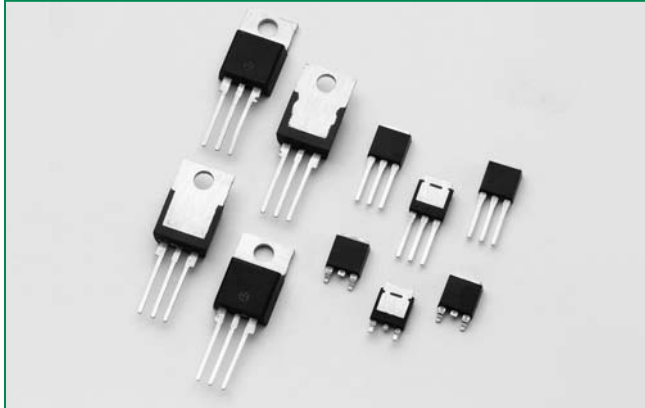
Part Numbering System



Part Marking System

DC
Date Code
(2 Digits Min.)
Number = Year
Letter = Month





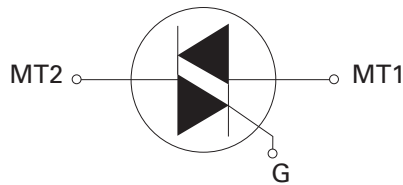
Agency Approval

Agency	Agency File Number
	L Package : E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	3 to 25	mA

Schematic Symbol



Description

4 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 55 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Typical applications are AC solid-state switches, power tools, home/brown goods and white goods appliances.

Sensitive gate Triacs can be directly driven by microprocessor or popular opto-couplers/isolators.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Sensitive Triacs (4 Quadrants)

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	Lxx04Ly / Lxx04Dy	T _c = 85°C	4	A
		Lxx04Ry / Lxx04Vy	T _c = 75°C		
I _{TSM}	Non repetitive surge peak on-state current (full cycle, T _j initial = 25°C)	f = 50 Hz	t = 20 ms	33	A
		f = 60 Hz	t = 16.7 ms	40	
I ² t	I ² t Value for fusing	t _p = 8.3 ms		6.6	A²s
di/dt	Critical rate of rise of on-state current (I _G = 50mA with ≤ 0.1µs rise time)	f = 120 Hz	T _J = 110°C	50	A/µs
I _{GTM}	Peak gate trigger current	t _p ≤ 10 µs	T _J = 110°C	1.2	A
P _{G(AV)}	Average gate power dissipation		T _J = 110°C	0.3	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 110	°C

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triacs

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx04Ly / Qxx04Dy	$T_c = 95^\circ\text{C}$	4	A
		Qxx04Ry / Qxx04Vy	$T_c = 85^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	46	A
		f = 60 Hz	t = 16.7 ms	55	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		12.5	A^2s
di/dt	Critical rate of rise of on-state current ($I_G = 50\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_J = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10\mu\text{s};$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	1.2	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.3	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		Lxx04x3	Lxx04x5	Lxx04x6	Lxx04x8	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\Omega$	I – II – III	MAX.	3	5	5	10	mA
		IV		3	5	10	20	
V_{GT}		ALL	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2				V
I_H	$I_T = 100\text{mA}$		MAX.	5	10	10	15	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	400V	TYP.	25	25	30	35	$\text{V}/\mu\text{s}$
		600V		15	15	20	25	
(dv/dt)c	(di/dt)c = 2.16 A/ms $T_J = 110^\circ\text{C}$		TYP.	0.5	1	1	1	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 5.6\text{A(pk)}$		TYP.	2.8	3.0	3.0	3.2	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Qxx04x3	Qxx04x4	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\Omega$	I – II – III	MAX.	10	25	mA
		IV	TYP.	25	50	
V_{GT}		I – II – III	MAX.	1.3	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{k}\Omega$ $T_J = 125^\circ\text{C}$	ALL	MIN.	0.2	0.2	V
I_H	$I_T = 200\text{mA}$		MAX.	20	30	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	40	75	$\text{V}/\mu\text{s}$
		600V		30	50	
		800V			40	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V			50	
(dv/dt)c	(di/dt)c = 2.16 A/ms $T_J = 125^\circ\text{C}$		TYP.	2	2	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 5.6\text{A(pk)}$		TYP.	2.5	3.0	μs

Note: xx = voltage, x = package

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions					Value	Unit
V_{TM}	$I_{TM} = 5.6\text{A}$ $t_p = 380\text{ }\mu\text{s}$		MAX.			1.60	V
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$	MAX.	Lxx04xy	$T_J = 25^\circ\text{C}$	400-600V	5	μA
				$T_J = 110^\circ\text{C}$	400-600V	200	μA
			Qxx04xy	$T_J = 25^\circ\text{C}$	400-1000V	10	μA
				$T_J = 125^\circ\text{C}$	400-800V	2	mA
				$T_J = 100^\circ\text{C}$	1000V	3	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)		L/Qxx04Dy	$^\circ\text{C/W}$
			L/Qxx04Ly	
			L/Qxx04Ry / L/Qxx04Vy	
$R_{\theta(J-A)}$	Junction to ambient		L/Qxx04Ly	$^\circ\text{C/W}$
			L/Qxx04Ry / L/Qxx04Vy	

Note: xx = voltage, x = package, y = sensitivity

Figure 1: Definition of Quadrants

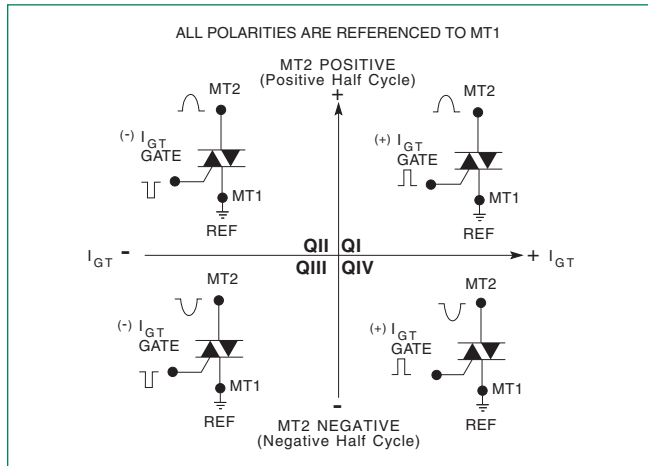


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

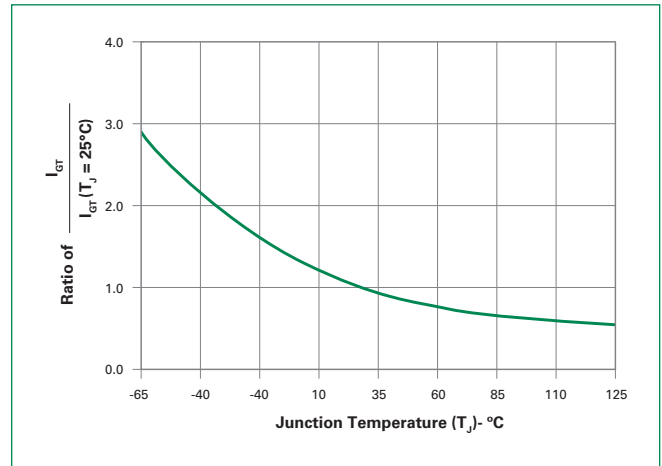


Figure 3: Normalized DC Holding Current vs. Junction Temperature

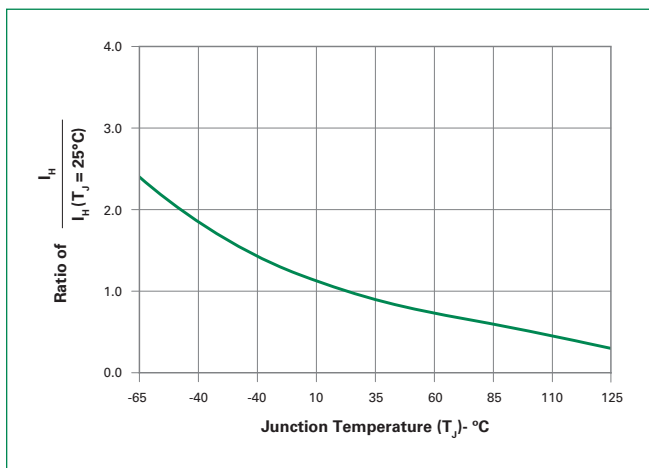


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

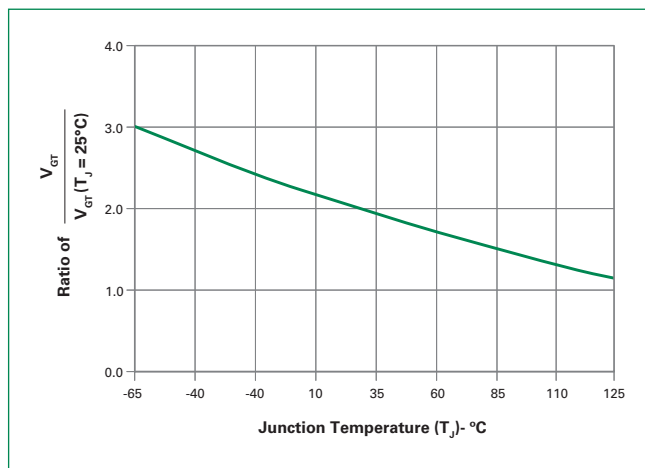


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

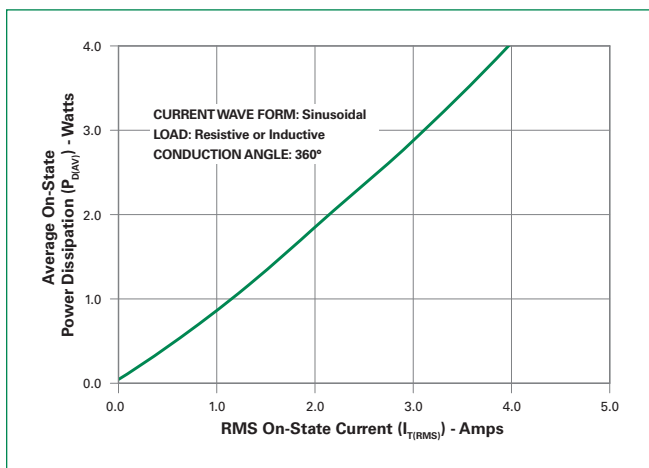


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

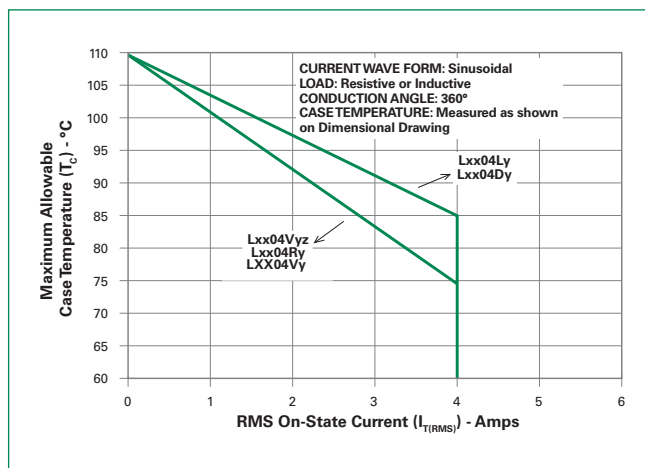


Figure 7: Maximum Allowable Case Temperature vs. On-State Current

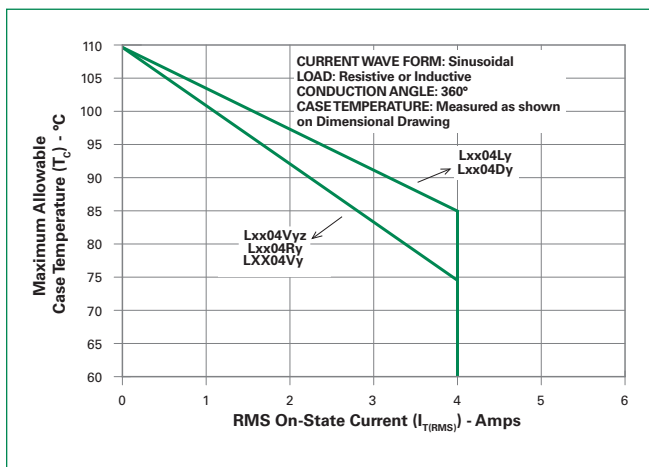
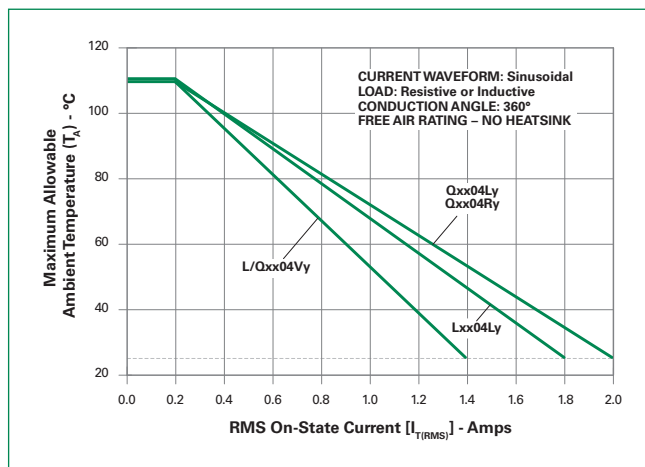


Figure 8: Maximum Allowable Ambient Temperature vs. On-State Current



Note: xx = voltage, y = sensitivity

Figure 9: On-State Current vs. On-State Voltage (Typical)

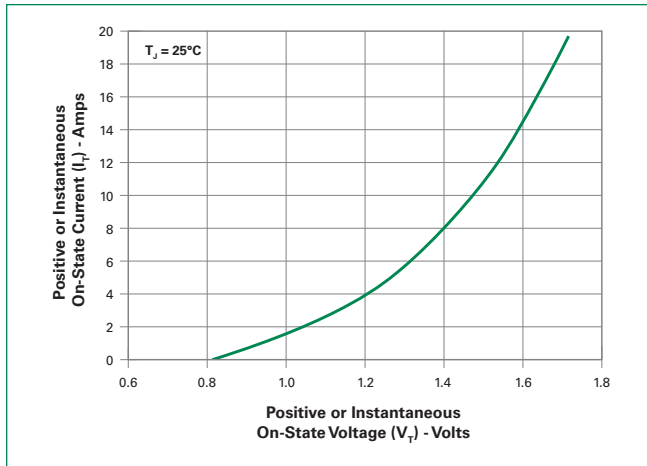
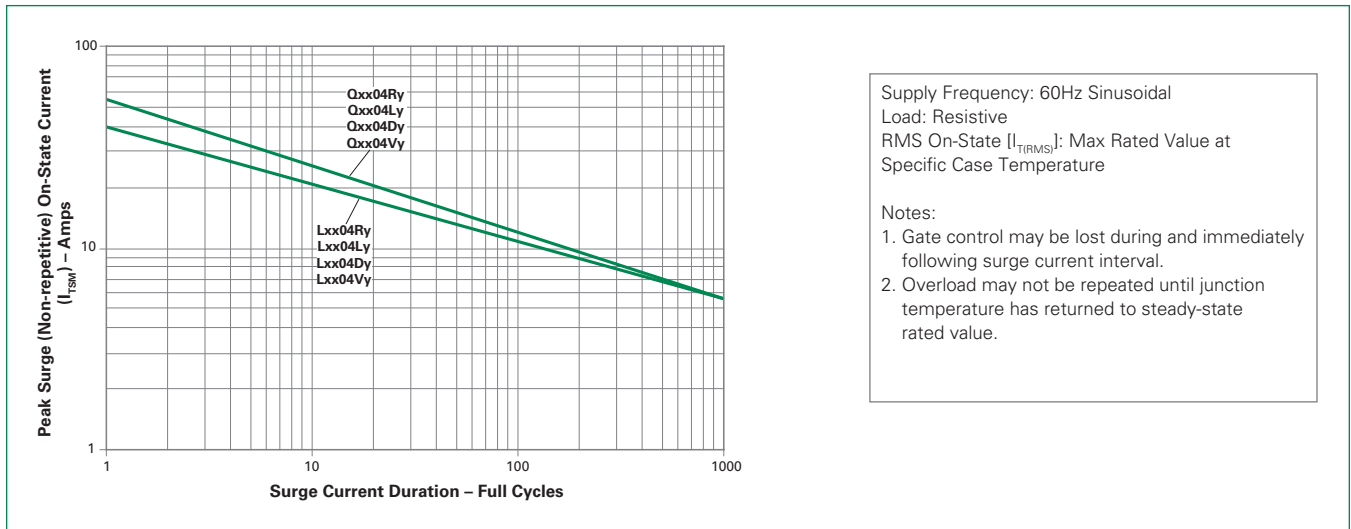


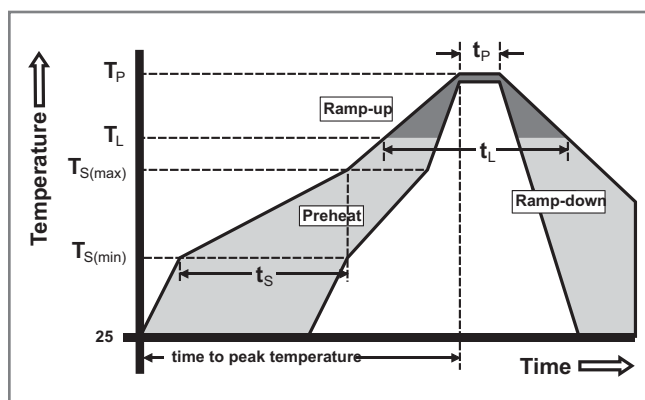
Figure 10: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage, y = sensitivity

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260°C $+0/-5$
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

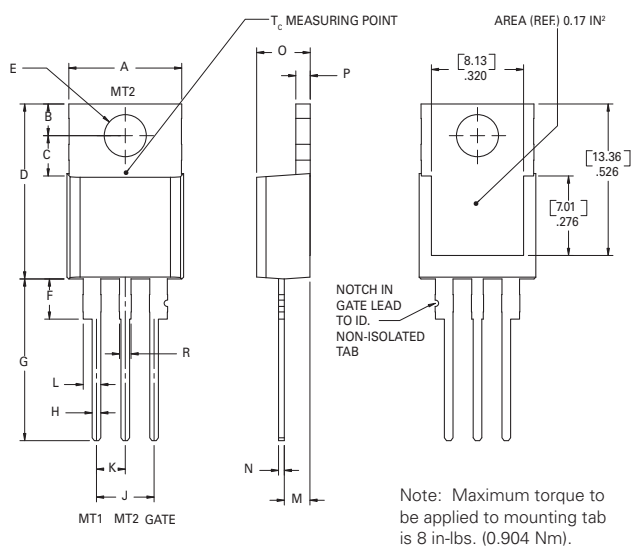
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

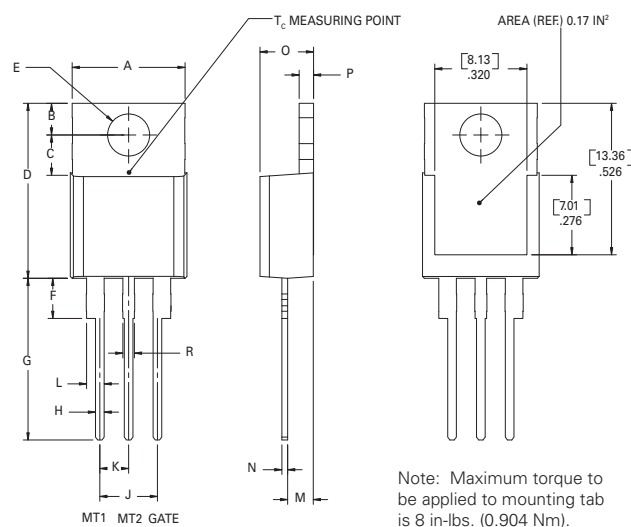
Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

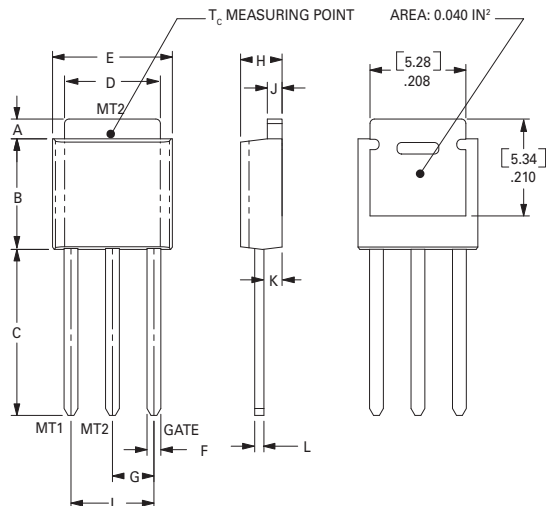
4.0A TRIACS

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



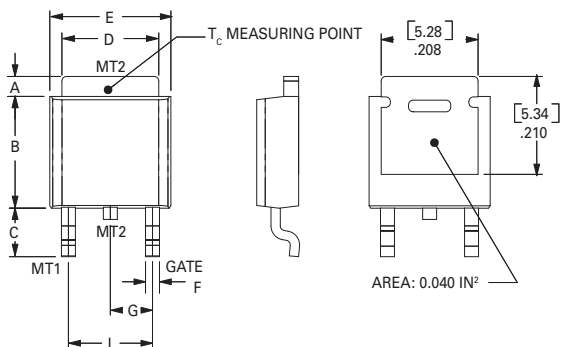
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-251AA (V-Package) — V-PAK Through Hole

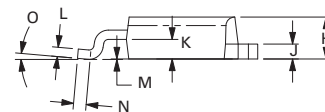
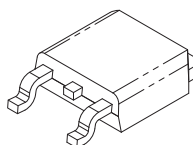
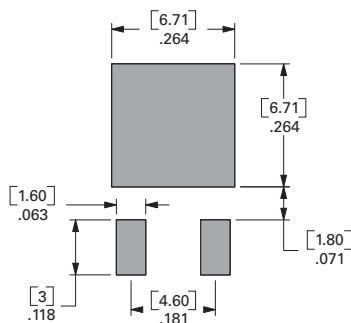


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



Pad Layout for TO-252AA (D-Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Product Selector

Part Number	Voltage				Gate Sensitivity Quadrants		Type	Package
	400V	600V	800V	1000V	I – II – III	IV		
Lxx04L3	X	X			3 mA	3 mA	Sensitive Triac	TO-220L
Lxx04D3	X	X			3 mA	3 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R3	X	X			3mA	3mA	Sensitive Triac	TO-220R
Lxx04V3	X	X			3 mA	3 mA	Sensitive Triac	TO-251 V-PAK
Lxx04L5	X	X			5 mA	5 mA	Sensitive Triac	TO-220L
Lxx04D5	X	X			5 mA	5 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R5	X	X			5mA	5mA	Sensitive Triac	TO-220R
Lxx04V5	X	X			5 mA	5 mA	Sensitive Triac	TO-251 V-PAK
Lxx04L6	X	X			5 mA	10 mA	Sensitive Triac	TO-220L
Lxx04D6	X	X			5 mA	10 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R6	X	X			5mA	10mA	Sensitive Triac	TO-220R
Lxx04V6	X	X			5 mA	10 mA	Sensitive Triac	TO-251 V-PAK
Lxx04L8	X	X			10 mA	20 mA	Sensitive Triac	TO-220L
Lxx04D8	X	X			10 mA	20 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R8	X	X			10mA	20mA	Sensitive Triac	TO-220R
Lxx04V8	X	X			10 mA	20 mA	Sensitive Triac	TO-251 V-PAK
Qxx04L3	X	X			10 mA		Standard Triac	TO-220L
Qxx04D3	X	X			10 mA		Standard Triac	TO-252 D-PAK
Qxx04V3	X	X			10 mA		Standard Triac	TO-251 V-PAK
Qxx04R3	X	X			10mA		Standard Triac	TO-220R
Qxx04L4	X	X	X	X	25 mA		Standard Triac	TO-220L
Qxx04D4	X	X	X	X	25 mA		Standard Triac	TO-252 D-PAK
Qxx04R4	X	X	X	X	25mA		Standard Triac	TO-220R
Qxx04V4	X	X	X	X	25 mA		Standard Triac	TO-251 V-PAK

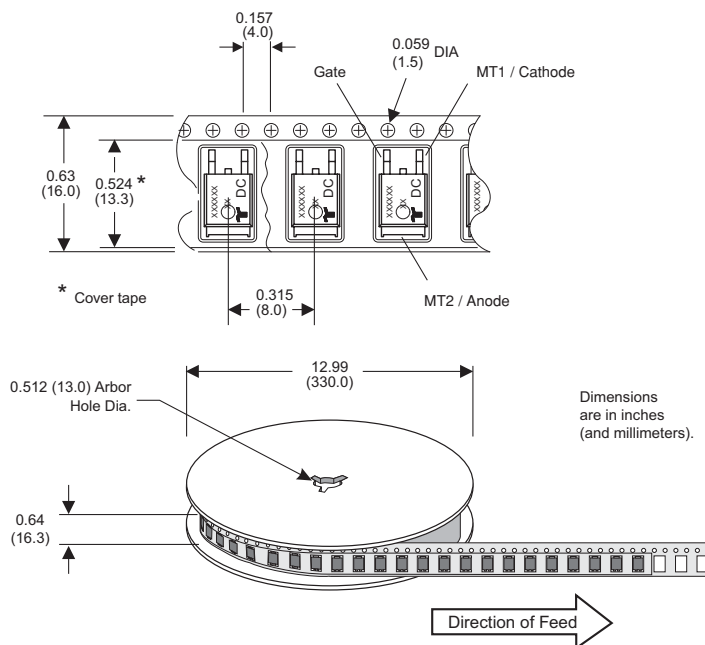
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
L/Q004L/Ry/TP	L/Qxx04L/Ry	2.2 g	Bulk	500
L/Qxx04LyTP	L/Qxx04Ly	2.2 g	Tube	500
L/Qxx04DyRP	L/Qxx04Dy	0.3 g	Embossed Carrier	2500
L/Qxx04DyTP	L/Qxx04Dy	0.3 g	Tube Pack	750
L/Qxx04VyTP	L/Qxx04Vy	0.4 g	Tube Pack	750

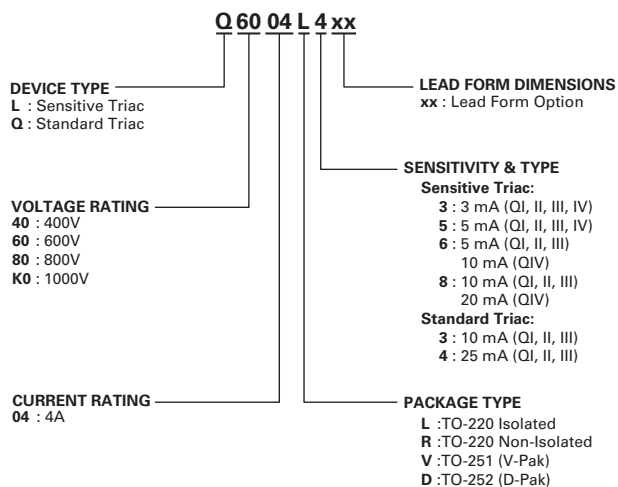
Note: xx = Voltage; y = Sensitivity

TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

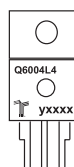


Part Numbering System

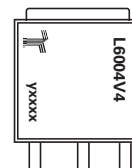


Part Marking System

TO-220 AB
(R & L Packages)

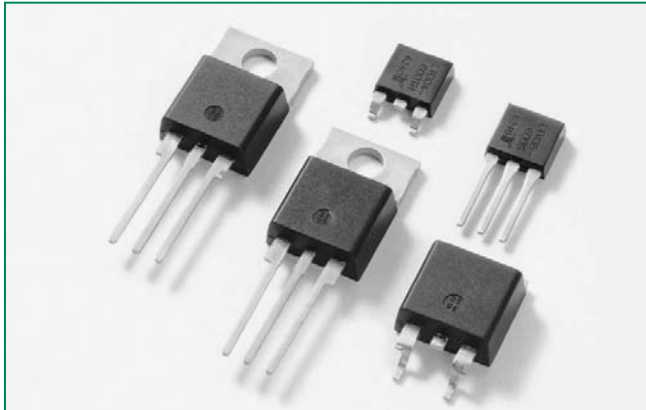


TO-251AA &
TO-252AA
(V and D Packages)



RoHS

Lxx06xx & Qxx06xx & Qxx06xHx Series



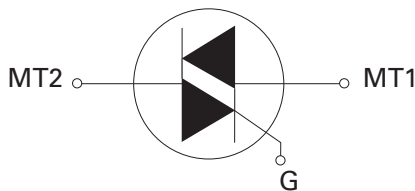
Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	5 to 50	mA

Schematic Symbol



Description

6 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 85 A
- Electrically isolated “L - Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Sensitive Triac (4 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Lxx06Ly	$T_C = 80^\circ\text{C}$	6	A
		Lxx06Vy / Lxx06Dy/ Lxx06Ry	$T_C = 85^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	$f = 50\text{ Hz}$	$t = 20\text{ ms}$	50	A
		$f = 60\text{ Hz}$	$t = 16.7\text{ ms}$	60	
I^2t	I^2t Value for fusing	$t_p = 8.3\text{ ms}$		15	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 50\text{mA}$ with $0.1\mu\text{s}$ rise time	$f = 120\text{ Hz}$	$T_J = 110^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10\mu\text{s}$	$T_J = 110^\circ\text{C}$	1.6	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 110^\circ\text{C}$	0.4	W
T_{stg}	Storage temperature range				-40 to 150 $^\circ\text{C}$
T_J	Operating junction temperature range				-40 to 110 $^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triac

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx06Ry / Qxx06Ny	$T_C = 95^\circ\text{C}$	6	A
		Qxx06Ly	$T_C = 90^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	65	A
		f = 60 Hz	t = 16.7 ms	80	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		26.5	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 200\text{mA}$ with $0.1\mu\text{s}$ rise time	f = 120 Hz	$T_J = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}; I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	1.6	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter				Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	Qxx06LHy		T _c = 95°C	6	A
		Qxx06RHy / Qxx06NHy Qxx06VHy / Qxx06DHy		T _c = 100°C		
I _{TSM}	Non repetitive surge peak on-state current (full cycle, T _j initial = 25°C)	f = 50 Hz	t = 20 ms	Qxx06VHy Qxx06DHy	55	A
				Qxx06LHy Qxx06RHy Qxx06NHy	80	
		f = 60 Hz	t = 16.7 ms	Qxx06VHy Qxx06DHy	65	
				Qxx06LHy Qxx06RHy Qxx06NHy	85	
I ² t	I ² t Value for fusing	t _p = 8.3 ms		Qxx06VHy Qxx06DHy	17.5	A ² s
				Qxx06LHy Qxx06RHy Qxx06NHy	30	
di/dt	Critical rate of rise of on-state current	f = 120 Hz		T _j = 125°C	70	A/μs
I _{GTM}	Peak gate trigger current	t _p ≤ 10 μs; I _{GT} ≤ I _{GTM}		T _j = 125°C	1.6	A
P _{G(AV)}	Average gate power dissipation			T _j = 125°C	0.5	W
T _{stg}	Storage temperature range				-40 to 150	°C
T _j	Operating junction temperature range				-40 to 125	°C

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		Value			Unit
				Lxx06x5	Lxx06x6	Lxx06x8	
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III IV	MAX.	5 5	5 10	10 20	mA
V_{GT}		ALL	MAX.	1.3			V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2			V
I_H	$I_T = 100\text{mA}$		MAX.	10	10	20	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	400V	TYP.	30	30	40	V/ μs
		600V		20	20	30	
$(dv/dt)_c$	$(di/dt)_c = 3.2\ \text{A/ms}$ $T_J = 110^\circ\text{C}$		TYP.	1	2	2	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\ \mu\text{s}$ $I_T = 8.5\ \text{A(pk)}$		TYP.	3.0	3.0	3.2	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Value		Unit
				Qxx06x4	Qxx06x5	
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III IV	MAX. TYP.	25 50	50 75	mA
V_{GT}		I – II – III	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$	ALL	MIN.	0.2		V
I_H	$I_T = 200\text{mA}$		MAX.	50	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	120		V/ μs
		600V			100	
		800V			85	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V			100	
$(dv/dt)_c$	$(di/dt)_c = 3.2\ \text{A/ms}$ $T_J = 125^\circ\text{C}$		TYP.	4	4	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\ \mu\text{s}$ $I_T = 8.5\ \text{A(pk)}$		TYP.	3.0	3.0	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant			Value		Unit	
					Qxx06xH3	Qxx06xH4		
I _{GT}	V _D = 12V R _L = 60 Ω	I – II – III	MAX.		10	35	mA	
V _{GT}		I – II – III	MAX.		1.3		V	
V _{GD}	V _D = V _{DRM} R _L = 3.3 kΩ T _J = 125°C	I – II – III	MIN.		0.2		V	
I _H	I _T = 100mA		MAX.		15	35	mA	
dv/dt	V _D = V _{DRM} Gate Open T _J = 125°C	Qxx06VHy / Qxx06DHy	MIN.	400V	75	400	V/μs	
				600V	50	300		
				800V		200		
		Qxx06LHy / Qxx06RH _y / Qxx06NH _y		400V	75	450		
				600V	50	350		
				800V		250		
	V _D = V _{DRM} Gate Open T _J = 100°C	ALL		1000V		150		
(dv/dt) _c	(di/dt) _c = 3.2 A/ms T _J = 125°C		MIN.		20	25	V/μs	
t _{gt}	I _G = 2 × I _{GT} PW = 15μs I _T = 8.5 A(pk)		TYP.		4.0	4.0	μs	

Note: xx = voltage, x = package, y = sensitivity

Static Characteristics

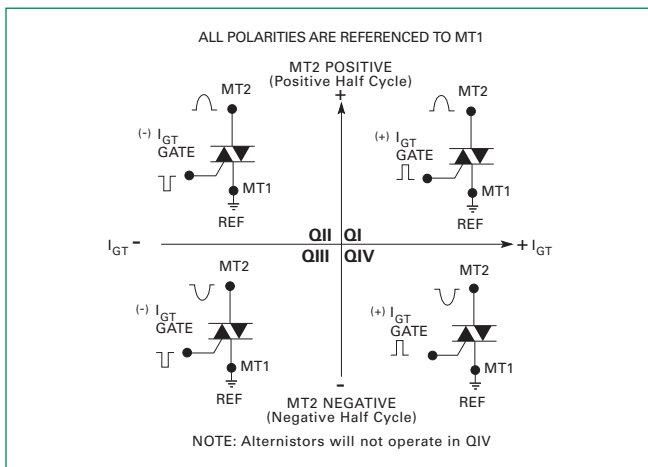
Symbol	Test Conditions					Value	Unit
V _{TM}	I _{TM} = 11.3A t _p = 380 μs				MAX.	1.60	V
I _{DRM} / I _{RRM}	V _{DRM} = V _{RRM}	Lxx06xy	T _J = 25°C	400 - 600V	MAX.	20	μA
			T _J = 110°C	400 - 600V		0.5	mA
		Qxx06xy	T _J = 25°C	400 - 1000V		50	μA
			T _J = 125°C	400 - 800V		2	mA
			T _J = 100°C	1000V		3	
		Qxx06xHy	T _J = 25°C	400 - 800V		10	μA
				1000V		20	
			T _J = 125°C	400 - 800V		3	mA
			T _J = 100°C	1000V		2	

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	L/Qxx06Ryy / L/Qxx06Nyy	1.8
		L/Qxx06Lyy	3.3
		L/Qxx06Vyy / L/Qxx06Dyy	3.2
$R_{\theta(J-A)}$	Junction to ambient	L/Qxx06Ryy	45
		L/Qxx06Lyy	50
		L/Qxx06Vyy	70

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

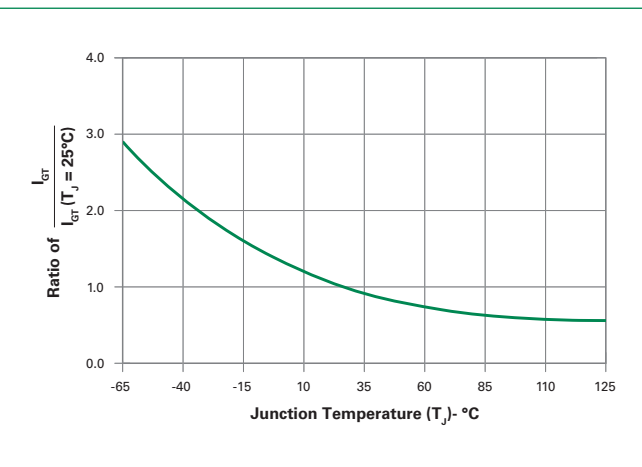


Figure 3: Normalized DC Holding Current vs. Junction Temperature

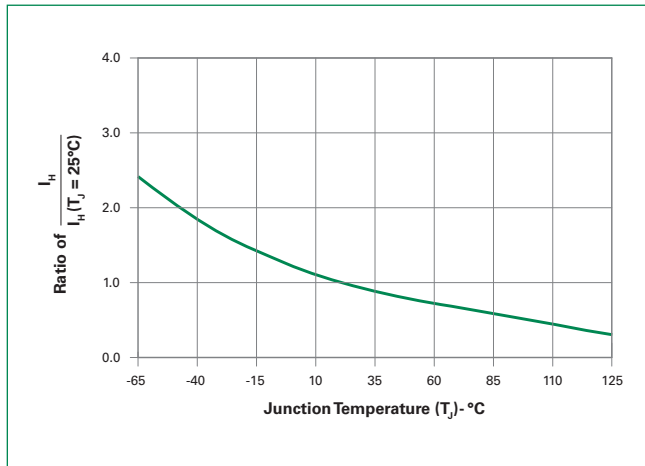


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

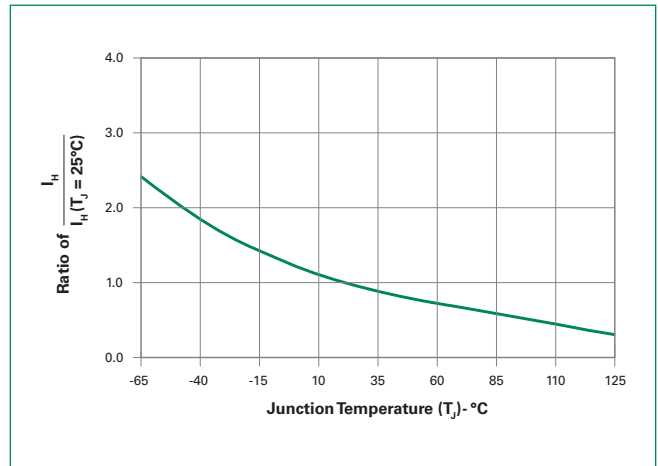


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

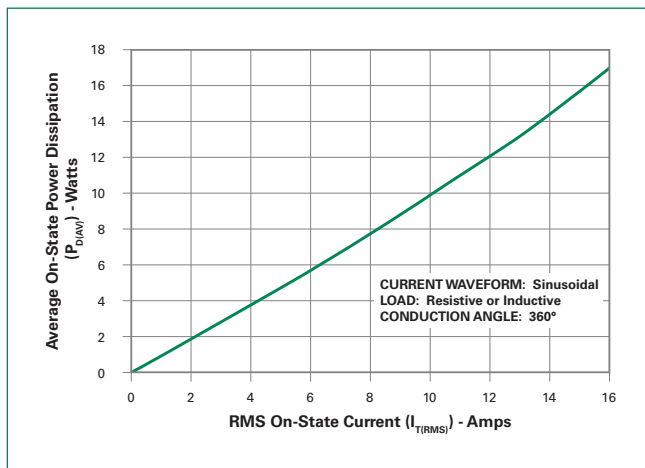


Figure 6: Maximum Allowable Case Temperature vs. On-State Current (Sensitive Triac)

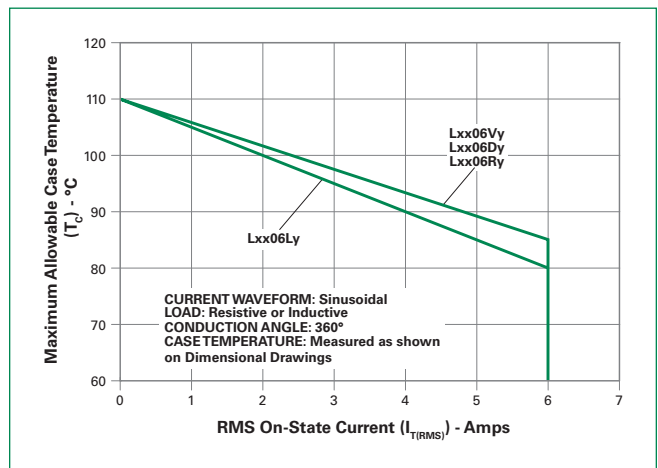


Figure 7: Maximum Allowable Case Temperature vs. On-State Current (Standard Triac)

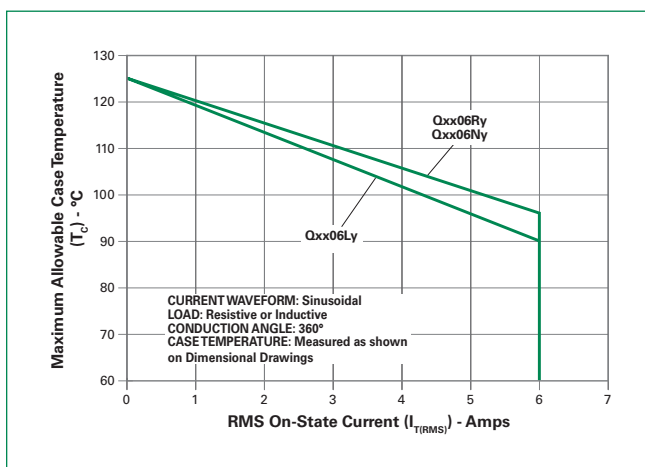


Figure 8: Maximum Allowable Case Temperature vs. On-State Current (Alternistor Triac)

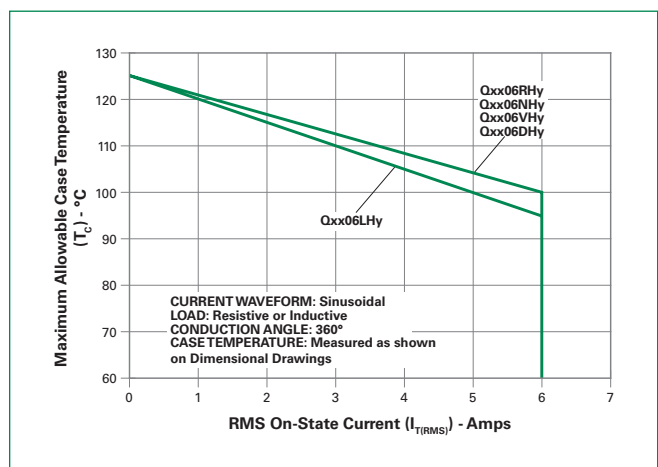


Figure 9: Maximum Allowable Ambient Temperature vs. On-State Current (Sensitive / Standard Triac)

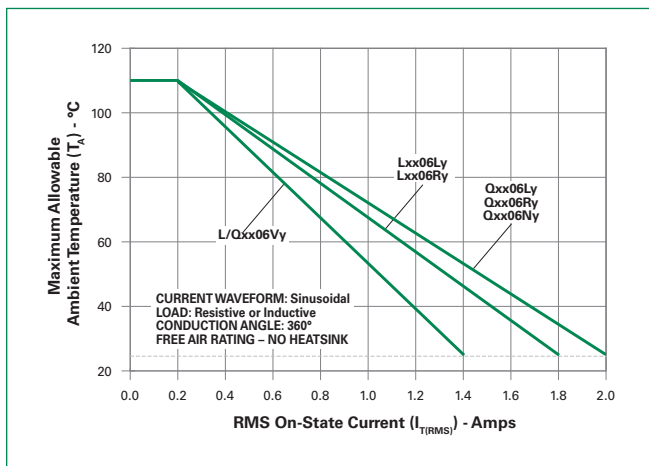


Figure 10: Maximum Allowable Ambient Temperature vs. On-State Current (Alternistor Triac)

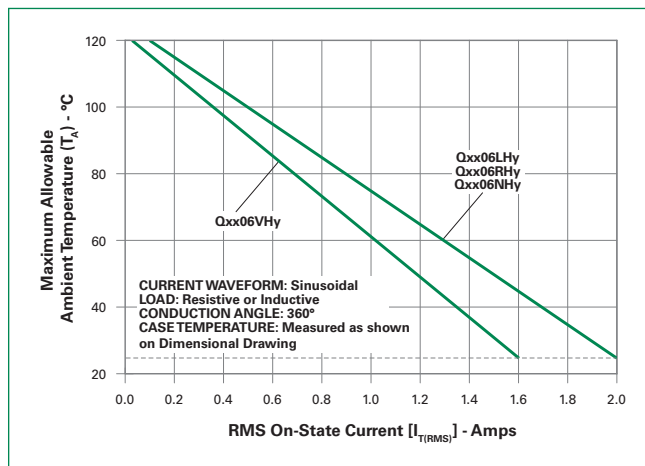


Figure 11: On-State Current vs. On-State Voltage (Typical)

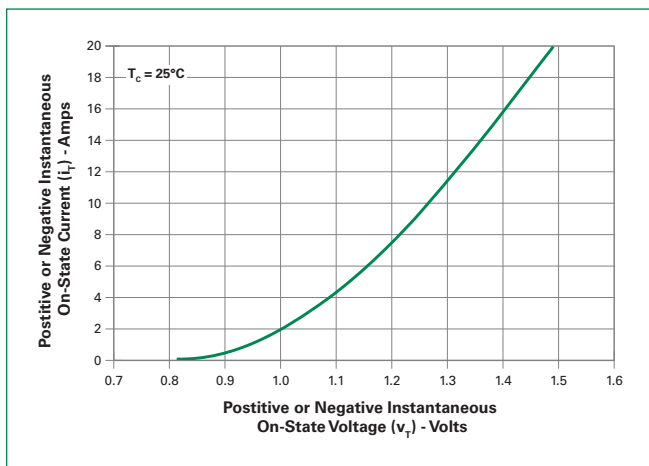


Figure 12: Surge Peak On-State Current vs. Number of Cycles (Sensitive / Standard Triac)

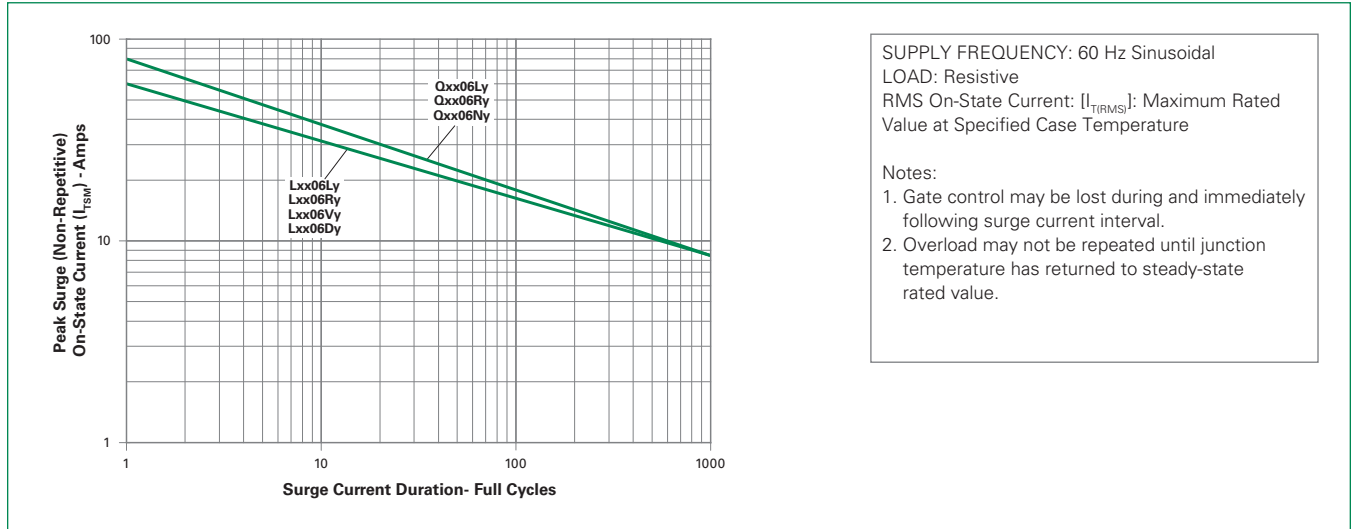
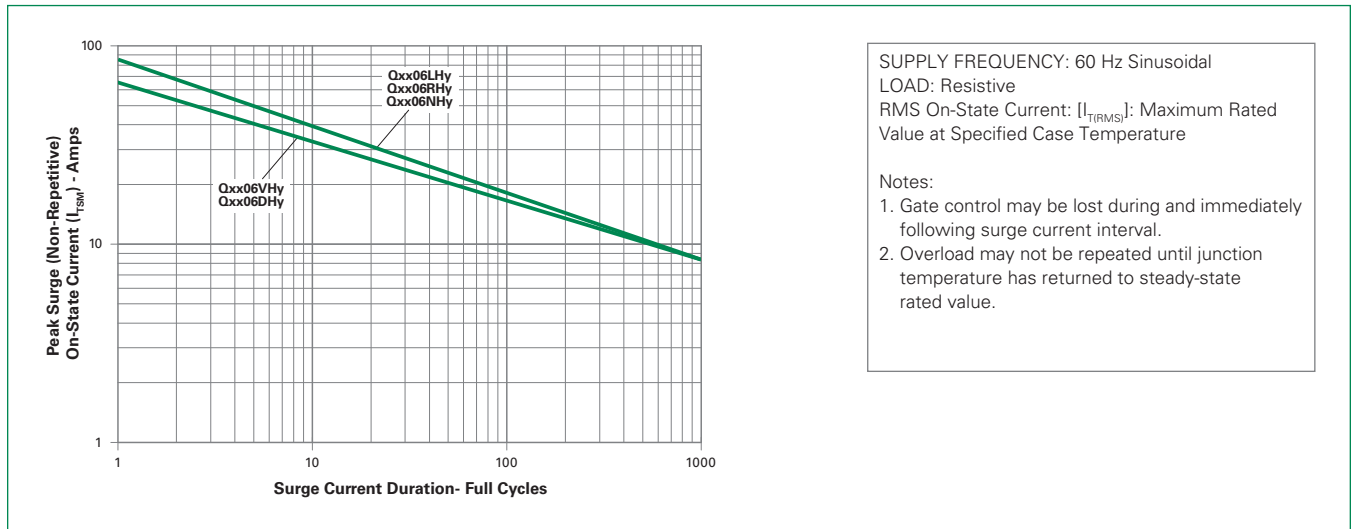


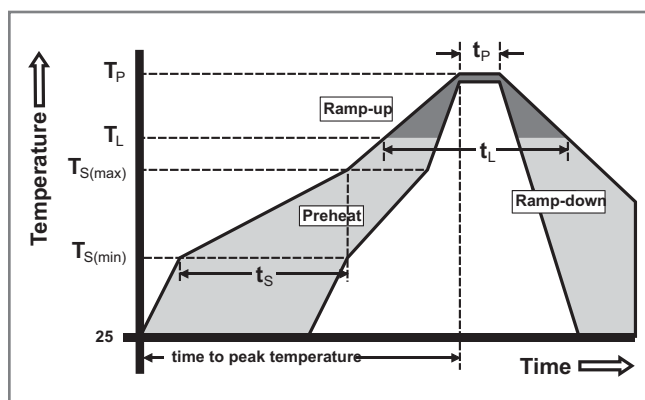
Figure 13: Surge Peak On-State Current vs. Number of Cycles (Alternistor Triac)



Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

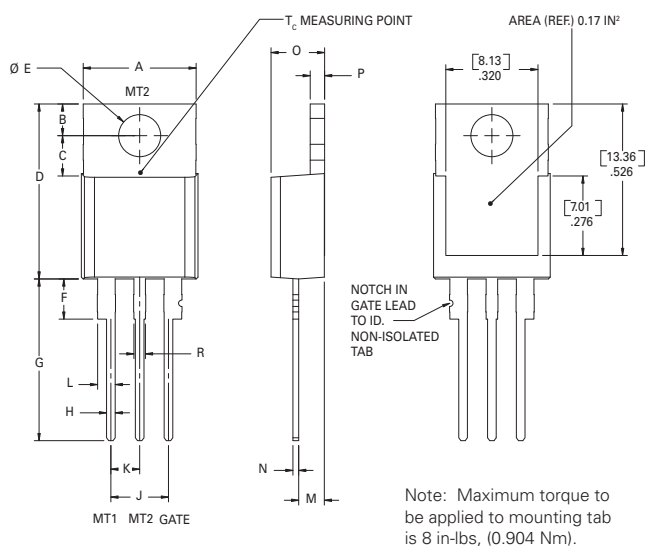
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking (V_{DRM})	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

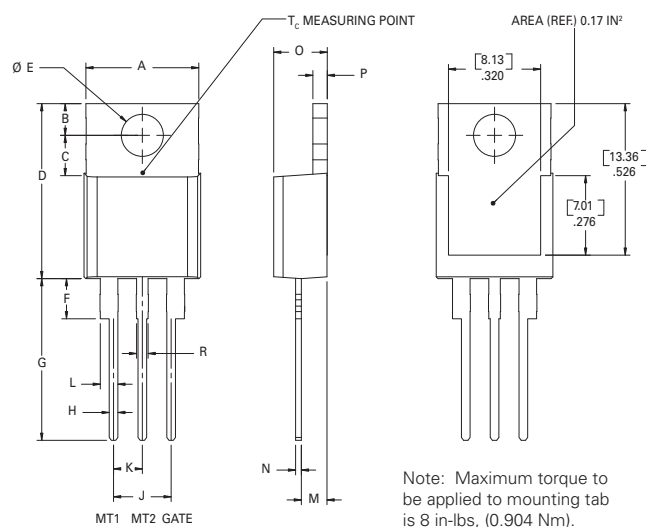
Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

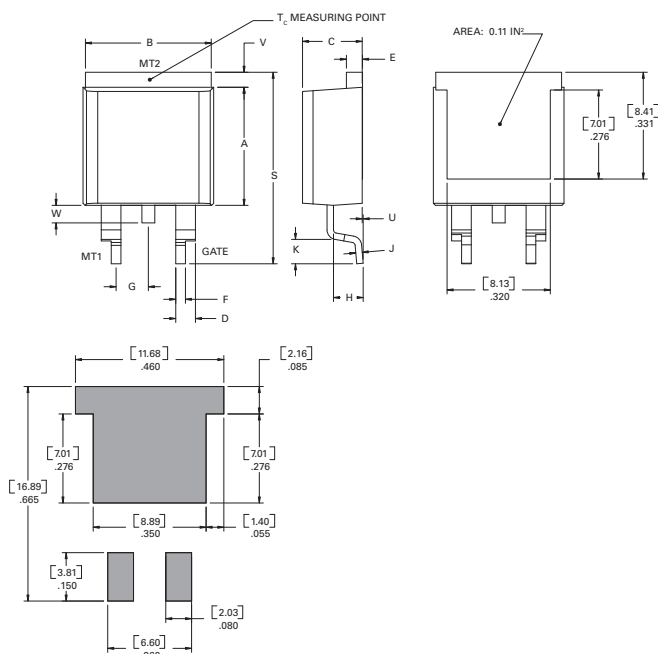
6.0A TRIACS

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



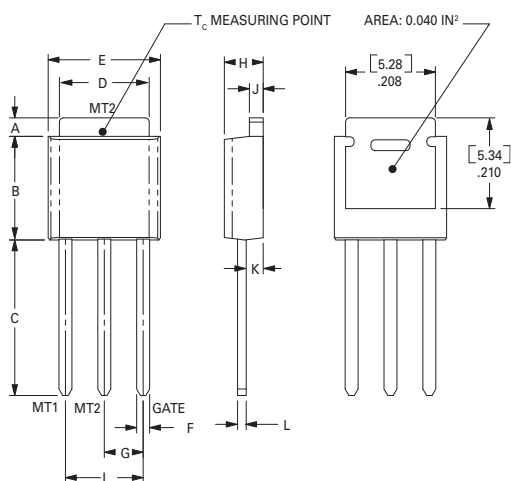
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-263AB (N-Package) — D²-PAK Surface Mount



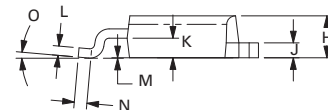
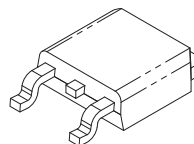
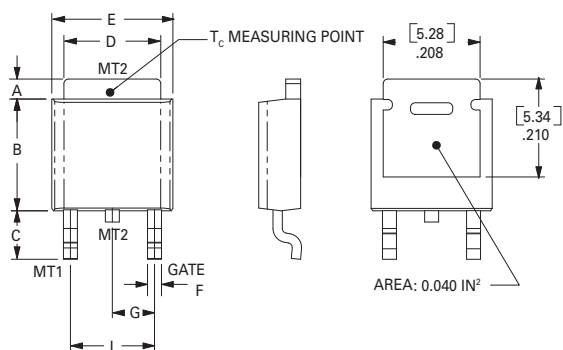
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Dimensions — TO-251AA (V-Package) — V-PAK Through Hole

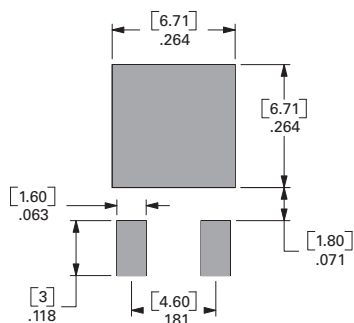


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface mount



Pad Layout for TO-252AA (D-Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Product Selector

Part Number	Voltage				Gate Sensitivity Quadrants		Type	Package
	400V	600V	800V	1000V	I - II - III	IV		
Lxx06L5	X	X			5 mA	5 mA	Sensitive Triac	TO-220L
Lxx06D5	X	X			5 mA	5 mA	Sensitive Triac	TO-252 D-PAK
Lxx06R5	X	X			5mA	5mA	Sensitive Triac	TO-220R
Lxx06V5	X	X			5 mA	5 mA	Sensitive Triac	TO-251 V-PAK
Lxx06L6	X	X			5 mA	10 mA	Sensitive Triac	TO-220L
Lxx06D6	X	X			5 mA	10 mA	Sensitive Triac	TO-252 D-PAK
Lxx06R6	X	X			5mA	10mA	Sensitive Triac	TO-220R
Lxx06V6	X	X			5 mA	10 mA	Sensitive Triac	TO-251 V-PAK
Lxx06L8	X	X			10 mA	20 mA	Sensitive Triac	TO-220L
Lxx06D8	X	X			10 mA	20 mA	Sensitive Triac	TO-252 D-PAK
Lxx06R8	X	X			10mA	20mA	Sensitive Triac	TO-220R
Lxx06V8	X	X			10 mA	20 mA	Sensitive Triac	TO-251 V-PAK
Qxx06VH3	X	X			10 mA		Alternistor Triac	TO-251 V-PAK
Qxx06DH3	X	X			10 mA		Alternistor Triac	TO-252 D-PAK
Qxx06L4	X				25 mA		Standard Triac	TO-220L
Qxx06R4	X				25 mA		Standard Triac	TO-220R
Qxx06N4	X				25 mA		Standard Triac	TO-263 D ² -PAK
Qxx06RH3	X	X			10mA		Alternistor Triac	TO-220R
Qxx06LH4	X	X	X	X	35 mA		Alternistor Triac	TO-220L
Qxx06RH4	X	X	X	X	35 mA		Alternistor Triac	TO-220R
Qxx06VH4	X	X	X	X	35 mA		Alternistor Triac	TO-251 V-PAK
Qxx06DH4	X	X	X	X	35 mA		Alternistor Triac	TO-252 D-PAK
Qxx06NH4	X	X	X	X	35 mA		Alternistor Triac	TO-263 D ² -PAK
Qxx06L5		X	X	X	50 mA		Standard Triac	TO-220L
Qxx06R5		X	X	X	50 mA		Standard Triac	TO-220R
Qxx06N5		X	X	X	50 mA		Standard Triac	TO-263 D ² -PAK

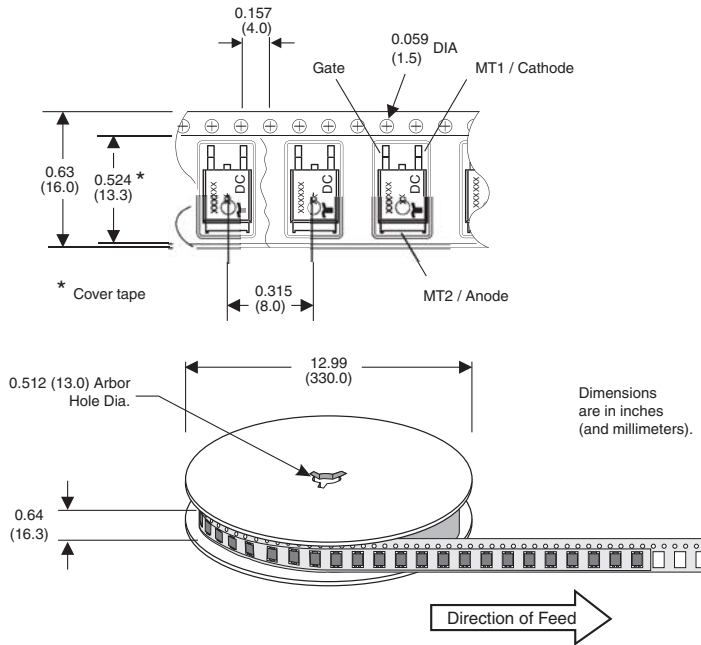
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Lxx06L/Ry	Lxx06L/Ry	2.2 g	Bulk	500
Lxx06L/RyTP	Lxx06L/Ry	2.2 g	Tube Pack	500
Lxx06DyTP	Lxx06Dy	0.3 g	Tube	750
Lxx06DyRP	Lxx06Dy	0.3 g	Embossed Carrier	2500
Lxx06VyTP	Lxx06Vy	0.4 g	Tube	750
Qxx06L/Ryy	Qxx06L/Ryy	2.2 g	Bulk	500
Qxx06L/RyyTP	Qxx06L/Ryy	2.2 g	Tube Pack	500
Qxx06NyyTP	Qxx06Nyy	1.6 g	Tube	500
Qxx06NyyRP	Qxx06Nyy	1.6 g	Embossed Carrier	500
Qxx06DyyTP	Qxx06Dyy	0.3 g	Tube	750
Qxx06DyyRP	Qxx06Dyy	0.3 g	Embossed Carrier	2500
Qxx06VyyTP	Qxx06Vyy	0.4 g	Tube	750

Note: xx = voltage; yy = sensitivity

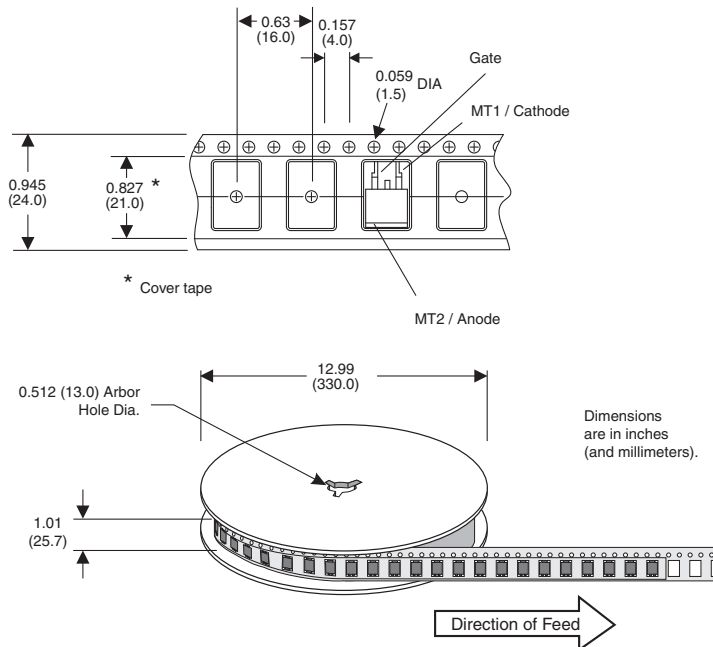
TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

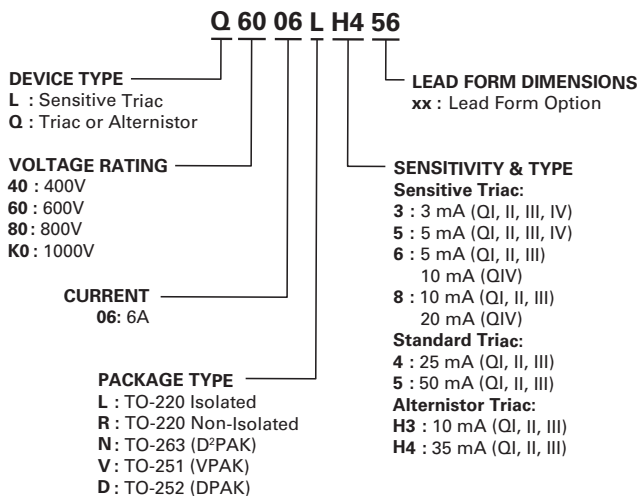


TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

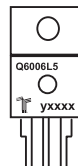


Part Numbering System

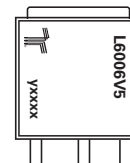


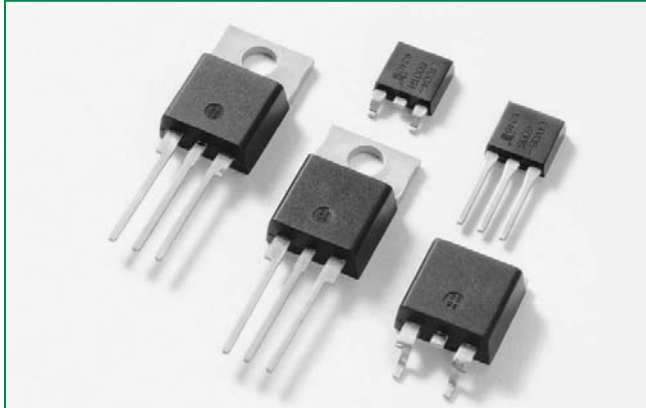
Part Marking System

TO-220 AB – (R & L Packages)
TO-263 AA – (N Package)



TO-252AA – (D Package)
TO-251AA – (V Package)





Description


8 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

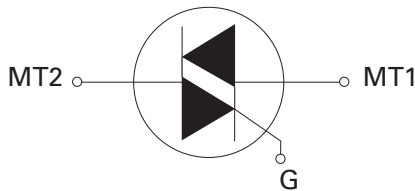
Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	5 to 50	mA

Schematic Symbol



Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 100 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Sensitive Triac (4 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Lxx08Ly	$T_c = 80^\circ\text{C}$	8	A
		Lxx08Ry / Lxx08Vy / Lxx08Dy	$T_c = 85^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	f = 50 Hz	t = 20 ms	65	A
		f = 60 Hz	t = 16.7 ms	85	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		26.5	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 50\text{mA}$ with $0.1\mu\text{s}$ rise time	f = 120 Hz	$T_j = 110^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$	$T_j = 110^\circ\text{C}$	1.6	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 110^\circ\text{C}$	0.4	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range			-40 to 110	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triac

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx08Ry / Qxx08Ny	$T_c = 95^\circ\text{C}$	8	A
		Qxx08Ly	$T_c = 90^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25°C)	f = 50 Hz	t = 20 ms	83	A
		f = 60 Hz	t = 16.7 ms	100	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		41	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time	f = 120 Hz	$T_j = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s};$ $I_{GT} \leq T_{GTM}$	$T_j = 125^\circ\text{C}$	1.8	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Alternistor (3 Quadrants)

Symbol	Parameter				Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	Qxx08LHy		T _C = 90°C	8	A
		Qxx08RHy / Qxx08NHy Qxx08VHy / Qxx08DHy		T _C = 95°C		
I _{TSM}	Non repetitive surge peak on-state current (full cycle, T _J initial = 25°C)	f = 50 Hz	t = 20 ms	Qxx08VHy / Qxx08DHy	80	A
				Qxx08LHy / Qxx08RHy / Qxx08NHy	83	
		f = 60 Hz	t = 16.7 ms	Qxx08VHy / Qxx08DHy	85	
				Qxx08LHy / Qxx08RHy / Qxx08NHy	100	
I ² t	I ² t Value for fusing	t _p = 8.3 ms		Qxx08VHy / Qxx08DHy	30	A ² s
				Qxx08LHy / Qxx08RHy / Qxx08NHy	41	
di/dt	Critical rate of rise of on-state current	f = 120 Hz		T _J = 125°C	70	A/μs
I _{GTM}	Peak gate trigger current	t _p ≤ 10 μs; I _{GT} ≤ I _{GTM}	T _J = 125°C	Qxx08VHy / Qxx08DHy	1.6	A
				Qxx08LHy / Qxx08RHy / Qxx08NHy	2.0	
P _{G(AV)}	Average gate power dissipation	T _J = 125°C	I _{GT} = 10mA	Qxx08VHy / Qxx08DHy	0.4	W
			I _{GT} = 35mA	Qxx08LHy / Qxx08RHy / Qxx08NHy	0.5	
T _{stg}	Storage temperature range				-40 to 150	°C
T _J	Operating junction temperature range				-40 to 125	°C

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		Lxx08x6	Lxx08x8	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III IV	MAX.	5 10	10 20	mA
V_{GT}		ALL	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2		V
I_H	$I_T = 100\text{mA}$		MAX.	10	20	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	400V	TYP.	30	40	V/ μs
		600V		20	30	
(dv/dt)c	(di/dt)c = 4.3 A/ms $T_J = 110^\circ\text{C}$		TYP.	2	2	V/ μs
t_{gt}	$I_G = 100\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 11.3 \text{ A(pk)}$		TYP.	3.0	3.2	μs

Note: xx = voltage, x = package, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Qxx80x4	Qxx80x5	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III IV	MAX. TYP.	25 50	50 75	mA
V_{GT}		I – II – III	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$	ALL	MIN.	0.2		V
I_H	$I_T = 200\text{mA}$		MAX.	50	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	150		V/ μs
		600V			125	
		800V			100	
		1000V			80	
(dv/dt)c	(di/dt)c = 4.3 A/ms $T_J = 125^\circ\text{C}$		TYP.	4	4	V/ μs
t_{gt}	$I_G = 100\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 11.3\ \text{A(pk)}$		TYP.	3.0	3.0	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant			Qxx08xH3	Qxx08xH4	Unit
I _{GT}	V _D = 12V R _L = 60 Ω	I – II – III	MAX.		10	35	mA
V _{GT}		I – II – III	MAX.		1.3		V
V _{GD}	V _D = V _{DRM} R _L = 3.3 kΩ T _J = 125°C	I – II – III	MIN.		0.2		V
I _H	I _T = 100mA		MAX.		15	35	mA
dv/dt	V _D = V _{DRM} Gate Open T _J = 125°C	Qxx08LHy / Qxx08RHy / Qxx08NHy	MIN.	400V	75	400	V/μs
				600V	50	300	
				800V		200	
				1000V		100	
		Qxx08VHy / Qxx08DHy		400V	75	450	
				600V	50	350	
				800V		250	
				1000V		150	
(dv/dt)c	(di/dt)c = 4.3 A/ms T _J = 125°C		MIN.		20	25	V/μs
t _{gt}	I _G = 100mA PW = 15μs I _T = 11.3 A(pk)		TYP.		4.0	4.0	μs

Note : xx = voltage, x = package, y = sensitivity

Static Characteristics

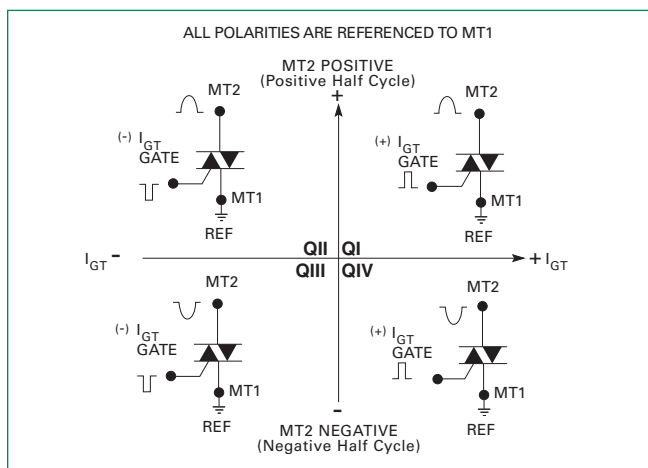
Symbol	Test Conditions					Value	Unit
V _{TM}	I _{TM} = 11.3A t _p = 380 μs				MAX.	1.60	V
I _{DRM} I _{RRM}	V _{DRM} = V _{RRM}	Lxx08xy	T _J = 25°C	400 - 600V	MAX.	20	μA
			T _J = 110°C	400 - 600V		0.5	mA
		Qxx08xy	T _J = 25°C	400 - 1000V		50	μA
			T _J = 125°C	400 - 800V		2	mA
			T _J = 100°C	1000V		3	
		Qxx08xHy	T _J = 25°C	400 - 800V		10	μA
				1000V		20	
			T _J = 125°C	400 - 800V		2	mA
			T _J = 100°C	1000V		3	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	L/Qxx08Ryy / L/Qxx08Nyy	1.5	$^\circ C/W$
		L/Qxx08Lyy	2.8	
		L/Qxx08Vyy	2.1	
$R_{\theta(J-A)}$	Junction to ambient	L/Qxx08Ryy	45	$^\circ C/W$
		L/Qxx08Lyy	50	
		L/Qxx08Vyy	64	

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

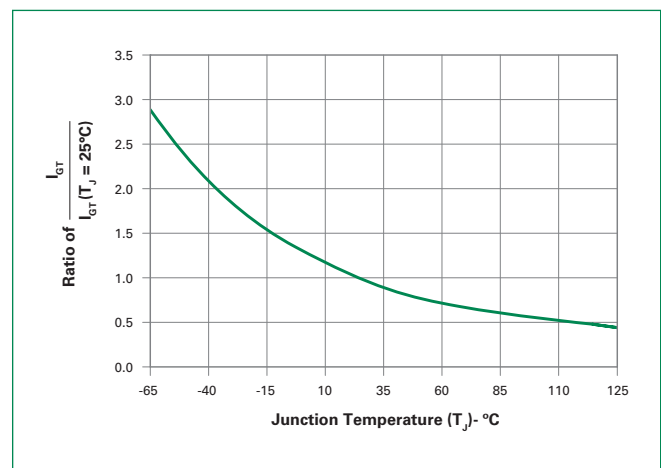


Figure 3: Normalized DC Holding Current vs. Junction Temperature

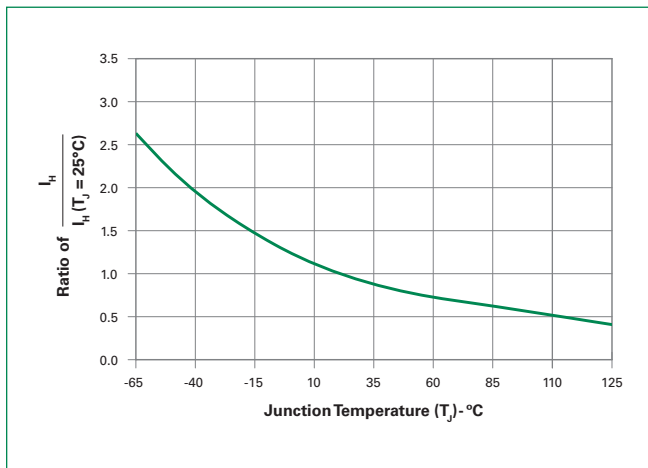


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

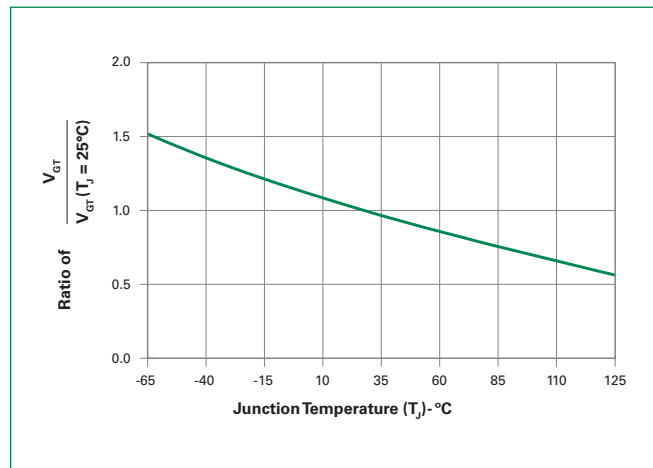


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

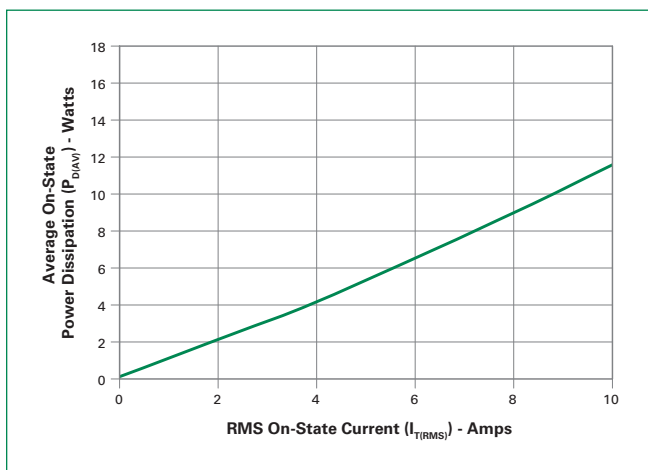


Figure 6: Maximum Allowable Case Temperature vs. On-State Current (Sensitive Triac)

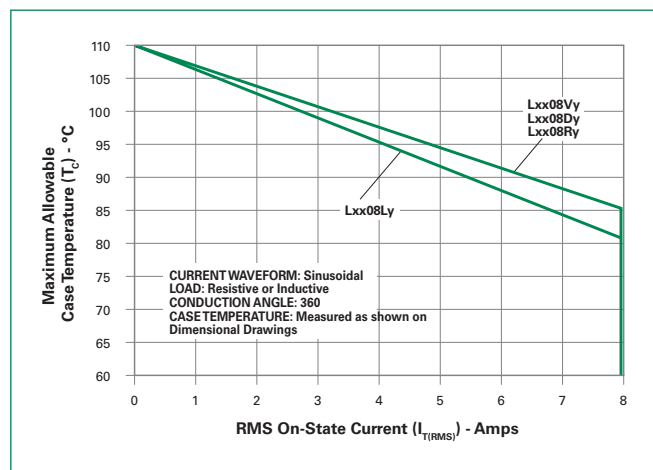


Figure 7: Maximum Allowable Case Temperature vs. On-State Current (Standard / Alternistor Triac)

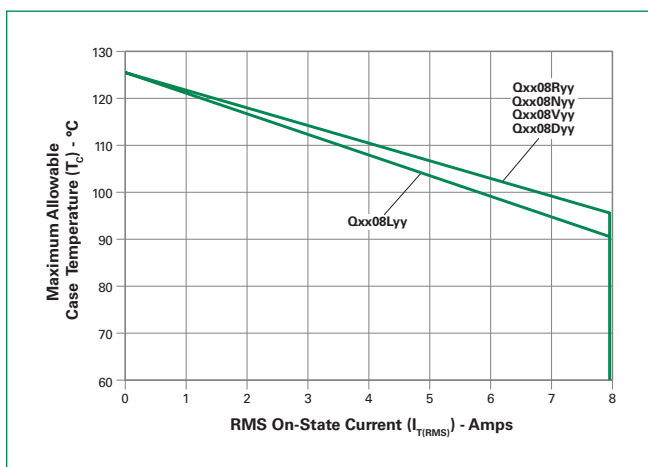
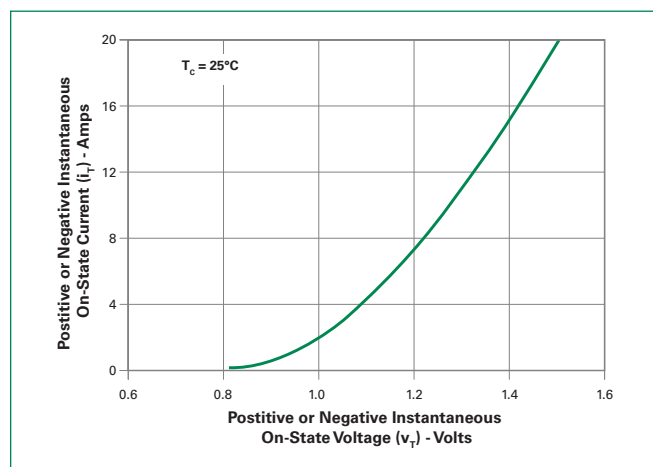


Figure 8: On-State Current vs. On-State Voltage (Typical)



Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Figure 9: Maximum Allowable Ambient Temperature vs. On-State Current

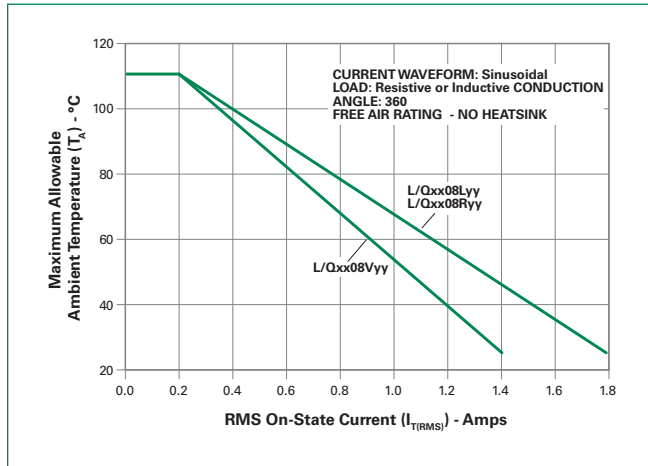
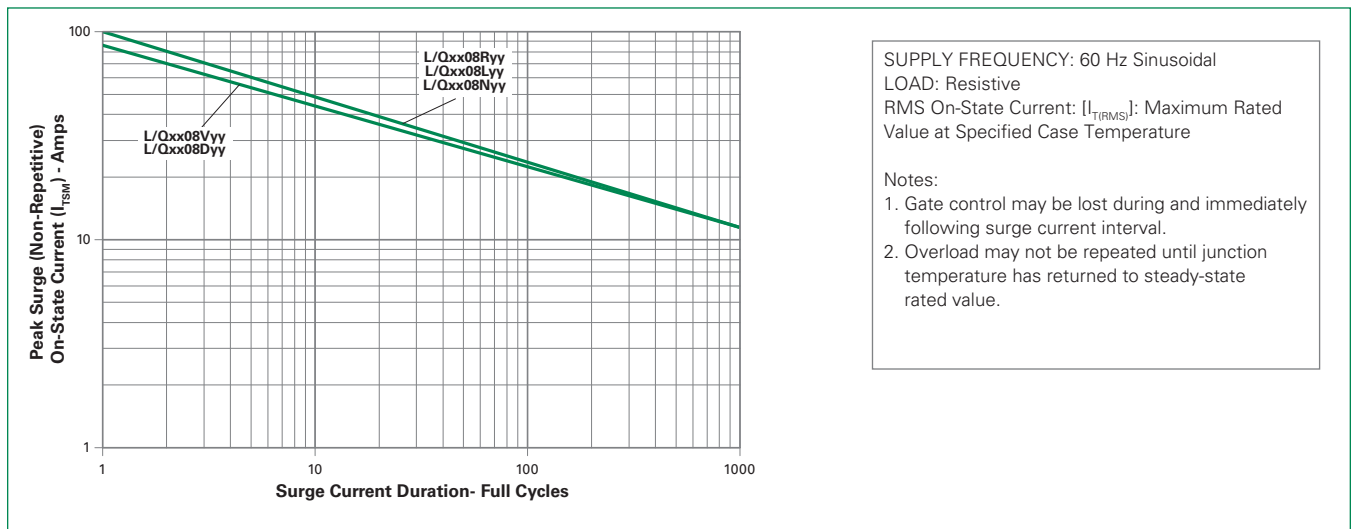


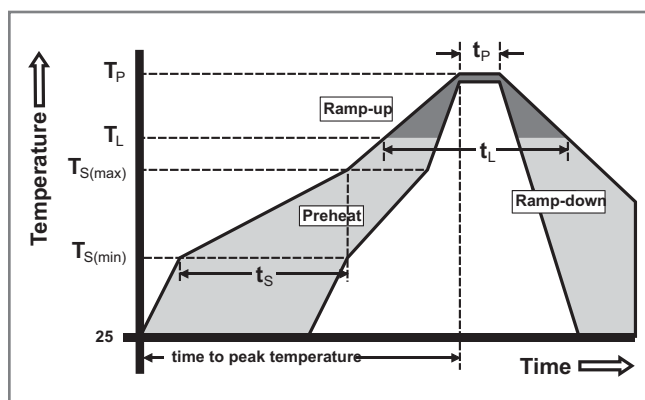
Figure 10: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

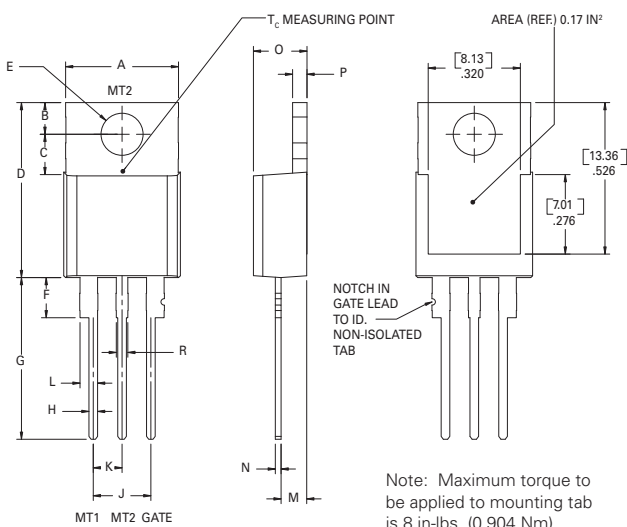
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

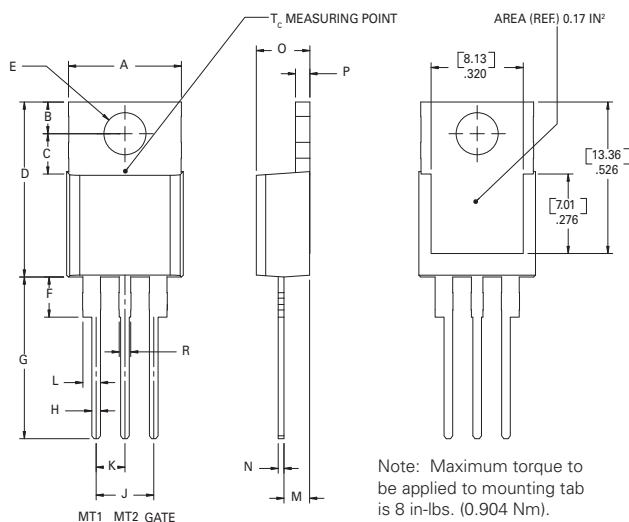
Test	Specifications and Conditions
AC Blocking (V_{DRM})	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



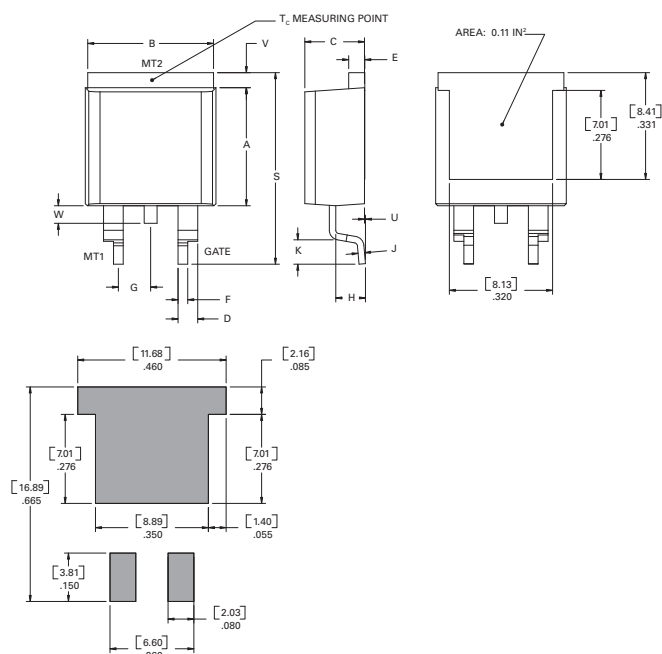
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



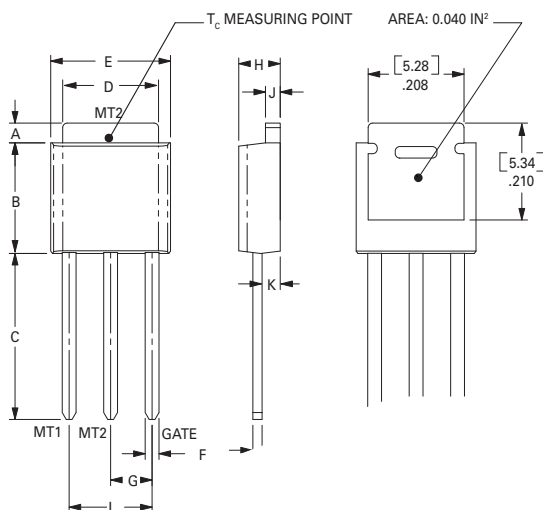
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-263AA (N-Package) — D²-PAK Surface Mount



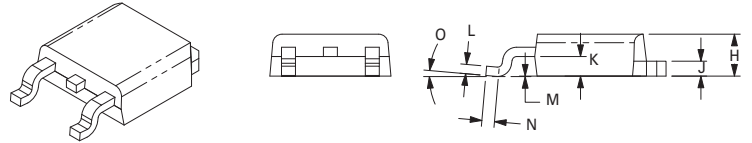
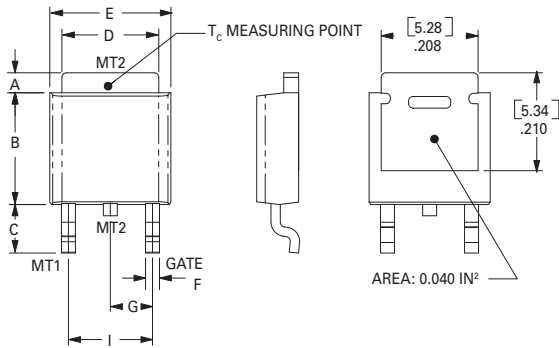
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Dimensions — TO-251AA (V-Package) — V-PAK Through Hole

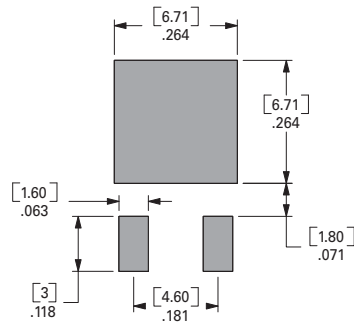


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



Pad Layout for TO-252AA (D-Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Product Selector

Part Number	Voltage (xx)				Gate Sensitivity Quadrants		Type	Package
	400V	600V	800V	1000V	I – II – III	IV		
Lxx08L6	X	X			5 mA	10 mA	Sensitive Triac	TO-220L
Lxx08D6	X	X			5 mA	10 mA	Sensitive Triac	TO-252 D-PAK
Lxx08R6	X	X			5mA	10mA	Sensitive Triac	TO-220R
Lxx08V6	X	X			5 mA	10 mA	Sensitive Triac	TO-251 V-PAK
Lxx08L8	X	X			10 mA	20 mA	Sensitive Triac	TO-220L
Lxx08D8	X	X			10 mA	20 mA	Sensitive Triac	TO-252 D-PAK
Lxx08R8	X	X			10mA	20mA	Sensitive Triac	TO-220R
Lxx08V8	X	X			10 mA	20 mA	Sensitive Triac	TO-251 V-PAK
Qxx08RH3	X	X			10 mA		Alternistor Triac	TO-220R
Qxx08VH3	X	X			10 mA		Alternistor Triac	TO-251 V-PAK
Qxx08DH3	X	X			10 mA		Alternistor Triac	TO-252 D-PAK
Qxx08L4	X				25 mA		Triac	TO-220L
Qxx08R4	X				25 mA		Triac	TO-220R
Qxx08N4	X				25 mA		Triac	TO-263 D ² -PAK
Qxx08LH4	X	X	X	X	35 mA		Alternistor Triac	TO-220L
Qxx08RH4	X	X	X	X	35 mA		Alternistor Triac	TO-220R
Qxx08VH4	X	X	X	X	35 mA		Alternistor Triac	TO-251 V-PAK
Qxx08DH4	X	X	X	X	35 mA		Alternistor Triac	TO-252 D-PAK
Qxx08NH4	X	X	X	X	35 mA		Alternistor Triac	TO-263 D ² -PAK
Qxx08L5		X	X	X	50 mA		Triac	TO-220L
Qxx08R5		X	X	X	50 mA		Triac	TO-220R
Qxx08N5		X	X	X	50 mA		Triac	TO-263 D ² -PAK

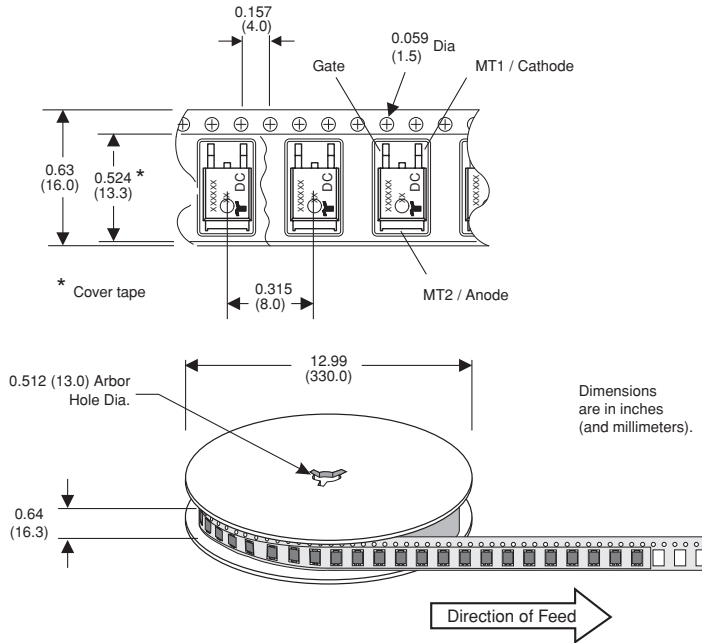
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
L/Qxx08L/Ryy	L/Qxx08L/Ryy	2.2 g	Bulk	500
L/Qxx08L/RyyTP	L/Qxx08L/Ryy	2.2 g	Tube Pack	500
Qxx08NyyTP	Qxx08Nyy	1.6 g	Tube	500
Qxx08NyyRP	Qxx08Nyy	1.6 g	Embossed Carrier	500
L/Qxx08DyyTP	L/Qxx08Dyy	0.3 g	Tube	750
L/Qxx08DyyRP	L/Qxx08Dyy	0.3 g	Embossed Carrier	2500
L/Qxx08VyyTP	L/Qxx08Vyy	0.4 g	Tube	750

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

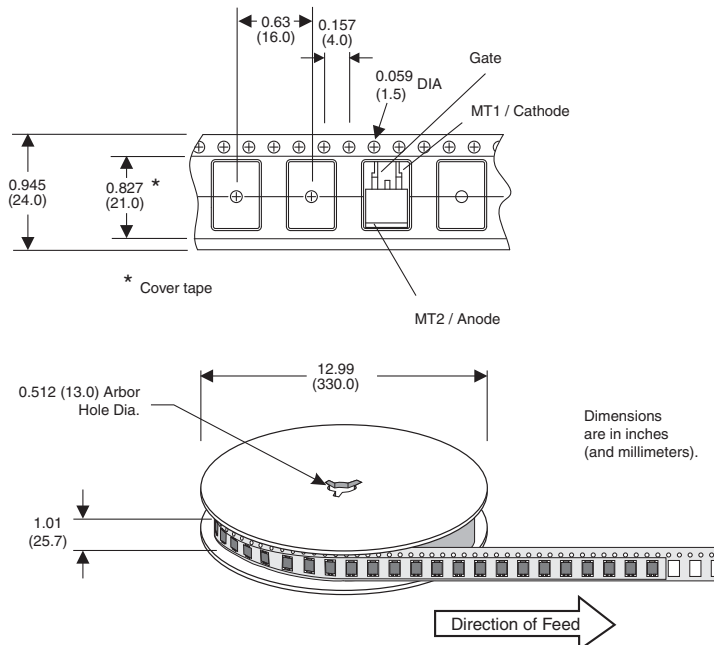
TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

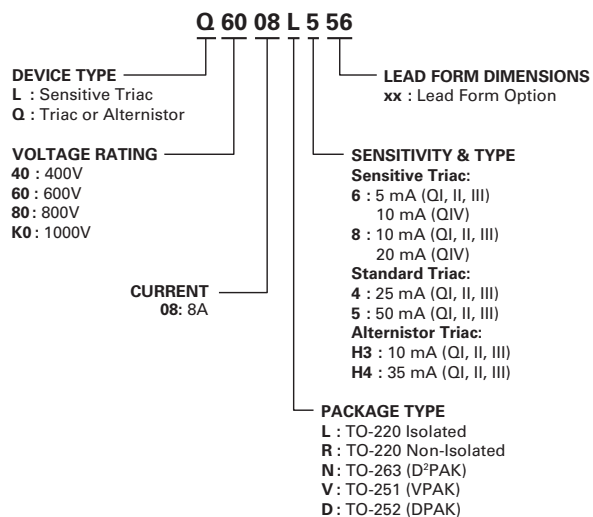


TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

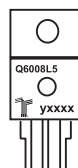


Part Numbering System

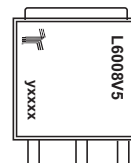


Part Marking System

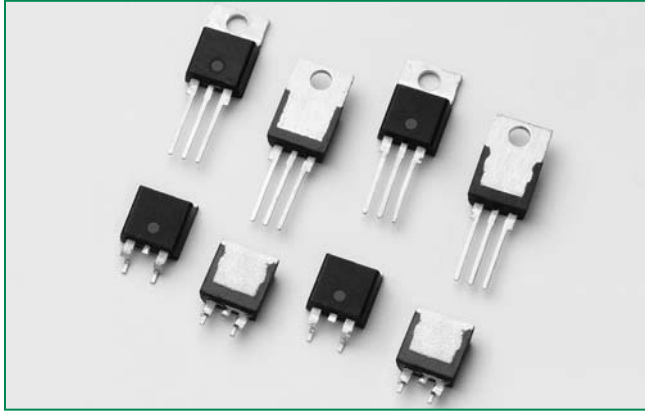
TO-220 AB – (R & L Packages)
TO-263 AA – (N Package)




TO-252AA – (D Package)
TO-251AA – (V Package)



RoHS Qxx10xx & Qxx10xHx Series



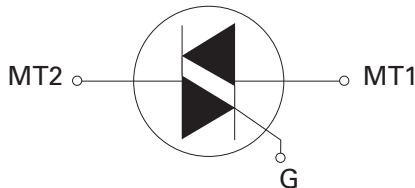
Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	10	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	25 to 50	mA

Schematic Symbol



Description

10 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 120 A
- Electrically isolated package "L - Package" and UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point sine wave

Applications

Alternistor type devices are used in applications requiring high commutation performance such as controlling inductive loads. Isolated packages are offered with internal construction, having the case or mounting tab electrically isolated from the semiconductor chip.

Absolute Maximum Ratings — Standard Triac

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx10Ry/ Qxx10Ny	$T_c = 95^\circ\text{C}$	10	A
		Qxx10Ly	$T_c = 90^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	100	A
		f = 60 Hz	t = 16.7 ms	120	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		60	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time	f = 120 Hz	$T_J = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	1.8	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx10LHy	$T_c = 90^\circ\text{C}$	10	A
		Qxx10RHy/ Qxx10NHx	$T_c = 95^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	110	A
		f = 60 Hz	t = 16.7 ms	120	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		60	A^2s
di/dt	Critical rate of rise of on-state current	f = 120 Hz	$T_J = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	2.0	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Qxx10x4	Qxx10x5	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III IV	MAX.	25 50	50 75 (TYP)	mA
V_{GT}		I – II – III	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$	ALL	MIN.	0.2		V
I_H	$I_T = 200\text{mA}$		MAX.	35	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	150	225	$\text{V}/\mu\text{s}$
		600V		100	200	
		800V		75	175	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V		50	150	
(dv/dt)c	(di/dt)c = 5.4 A/ms $T_J = 125^\circ\text{C}$		TYP.	2	4	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 14.1 \text{ A(pk)}$		TYP.	3.0	3.0	μs

Note: xx = voltage, x = package, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant		Value	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III	MAX.	50	mA
V_{GT}		I – II – III	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2	V
I_H	$I_T = 100\text{mA}$		MAX.	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	750	V/ μs
		600V		650	
		800V		500	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V		300	
$(dv/dt)c$	$(di/dt)c = 5.4\ \text{A/ms}$ $T_J = 125^\circ\text{C}$		TYP.	30	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}$ $P_W = 15\ \mu\text{s}$ $I_T = 14.1\ \text{A(pk)}$		TYP.	4.0	μs

Static Characteristics

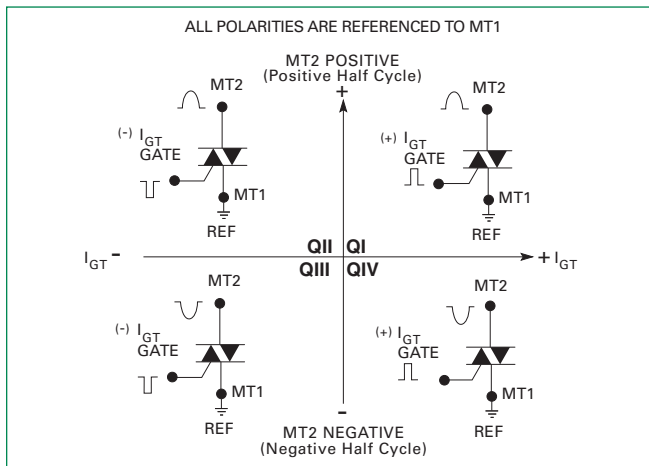
Symbol	Test Conditions			Value	Unit	
V_{TM}	$I_{TM} = 14.1A$ $t_p = 380\ \mu s$			MAX.	1.60	V
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$	$T_J = 25^{\circ}C$	400 - 600V	MAX.	10	μA
		$T_J = 125^{\circ}C$	400 - 800V		2	mA
		$T_J = 100^{\circ}C$	1000V		3	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx10Ryy/ Qxx10Nyy	1.3	$^\circ\text{C/W}$
		Qxx10Lyy	2.6	
$R_{\theta(J-A)}$	Junction to ambient (AC)	Qxx10Ryy	45	$^\circ\text{C/W}$
		Qxx10Lyy	50	

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

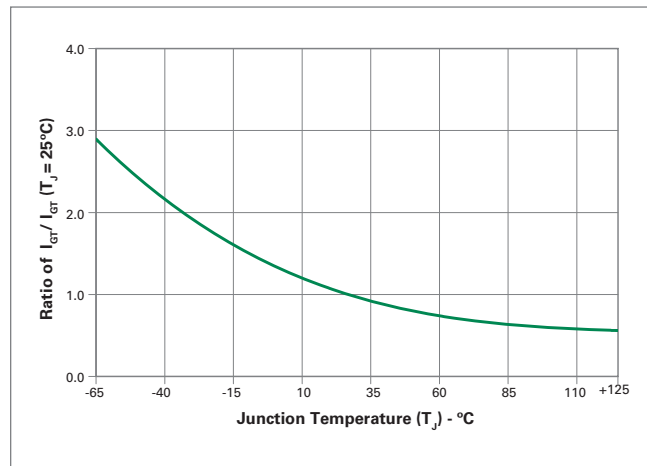


Figure 3: Normalized DC Holding Current vs. Junction Temperature

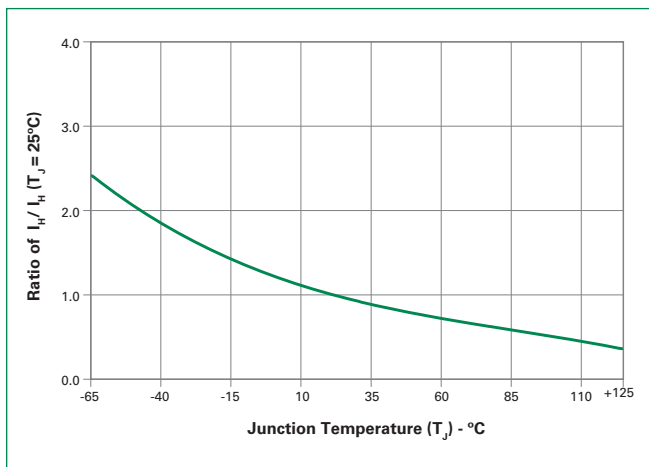


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

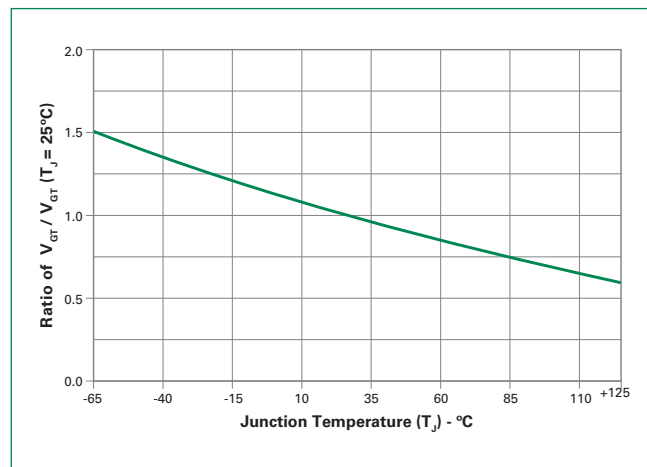


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

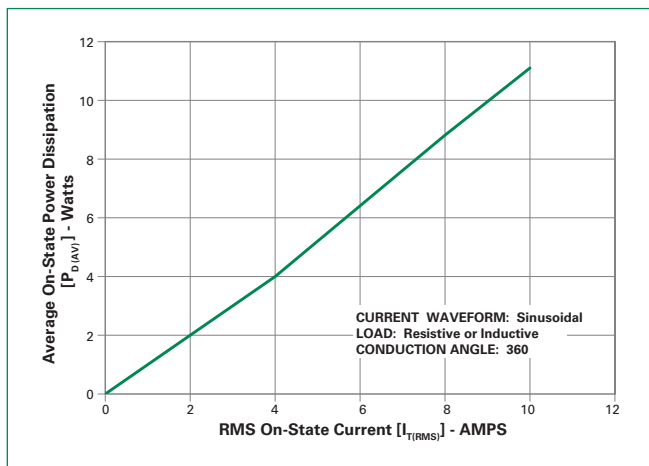


Figure 6: Maximum Allowable Case Temperature vs. On-State Current (Sensitive Triac)

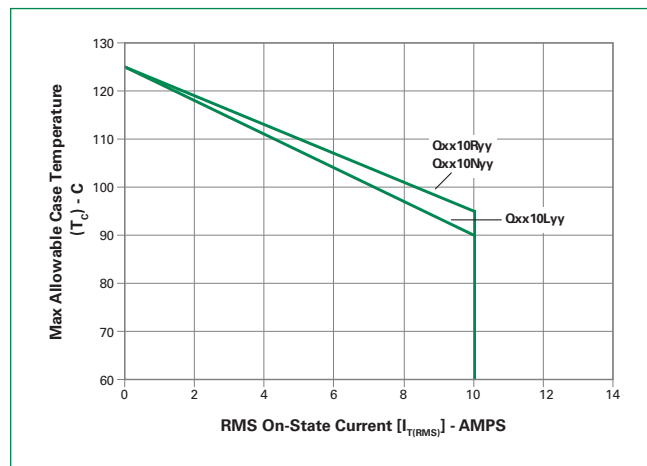


Figure 7: Maximum Allowable Ambient Temperature vs. On-State Current

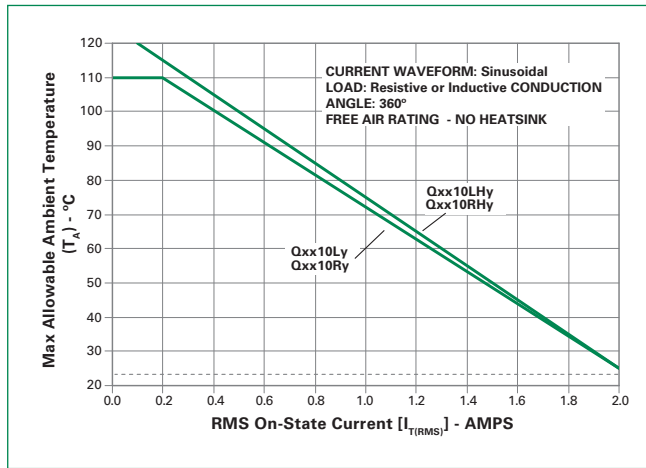


Figure 8: On-State Current vs. On-State Voltage (Typical)

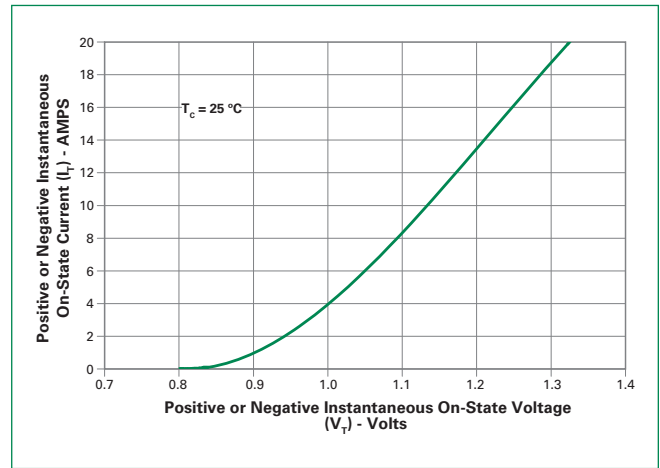
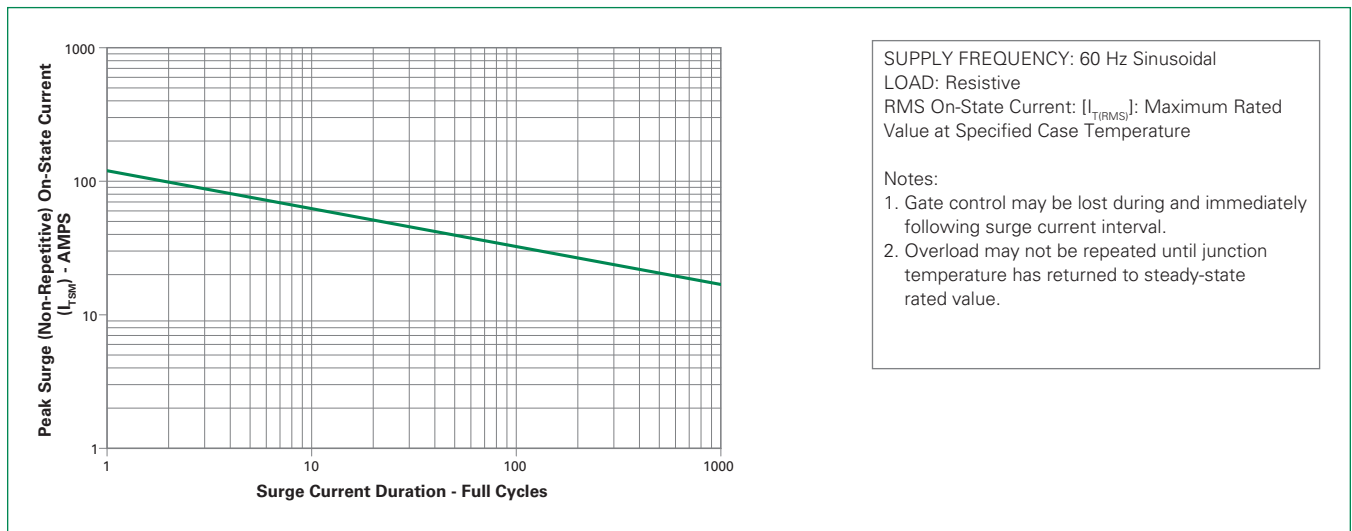
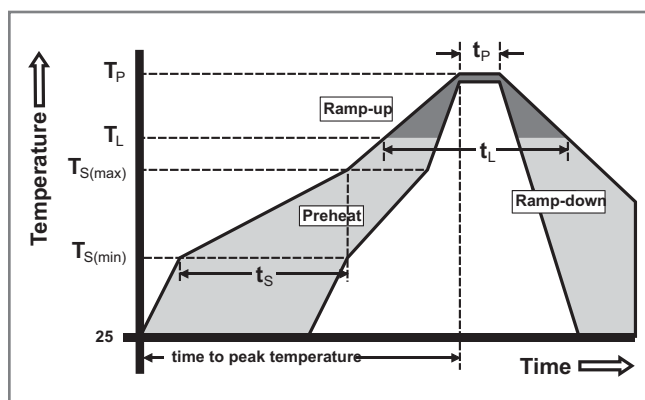


Figure 9: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Terminal Material	Copper Alloy

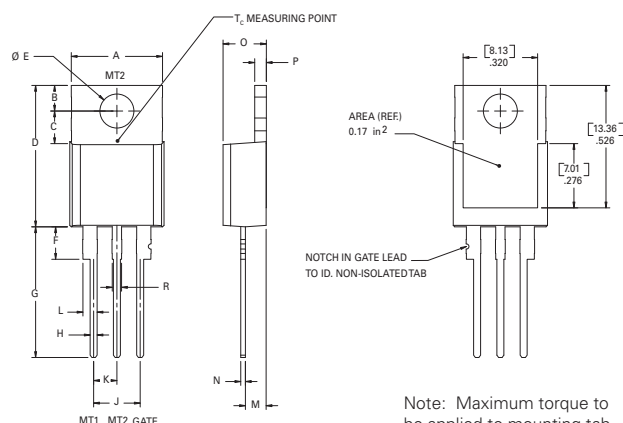
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C, 15-min dwell-time
Temperature/Humidity	EIA/JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA/JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3 Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead

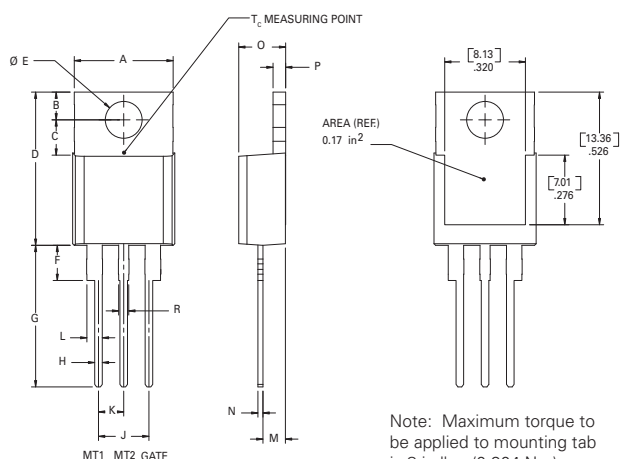


Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.965	1.22

10.0 A TRIACS

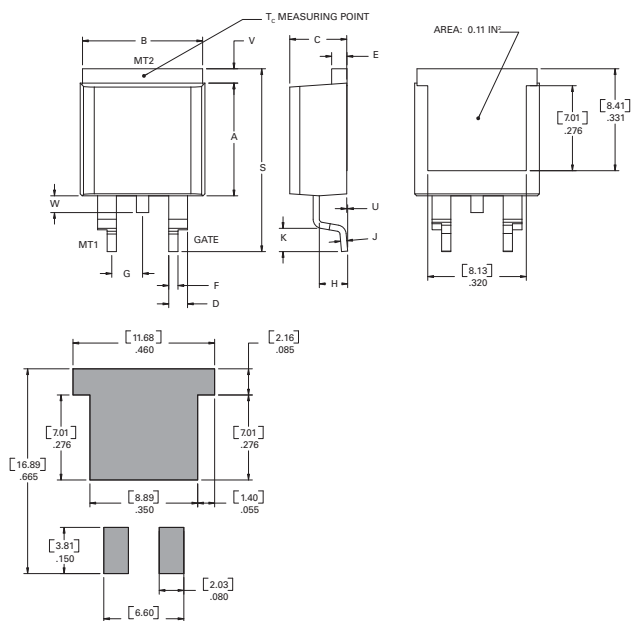
Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.965	1.22

Dimensions — TO-263AA (N-Package) — D²-PAK Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.016	1.78

Product Selector

Part Number	Voltage (xx)				Gate Sensitivity Quadrants		Type	Package
	400V	600V	800V	1000V	I – II – III	IV		
Qxx10L4	X	X	X	X	25 mA	50 mA	Standard Triac	TO-220L
Qxx10R4	X	X	X	X	25 mA	50 mA	Standard Triac	TO-220R
Qxx10N4	X	X	X	X	25 mA	50 mA	Standard Triac	TO-263 D ² -PAK
Qxx10L5	X	X	X	X	50 mA		Standard Triac	TO-220L
Qxx10R5	X	X	X	X	50 mA		Standard Triac	TO-220R
Qxx10N5	X	X	X	X	50 mA		Standard Triac	TO-263 D ² -PAK
Qxx10LH5	X	X	X	X	50 mA		Alternistor Triac	TO-220L
Qxx10RH5	X	X	X	X	50 mA		Alternistor Triac	TO-220R
Qxx10NH5	X	X	X	X	50 mA		Alternistor Triac	TO-263 D ² -PAK

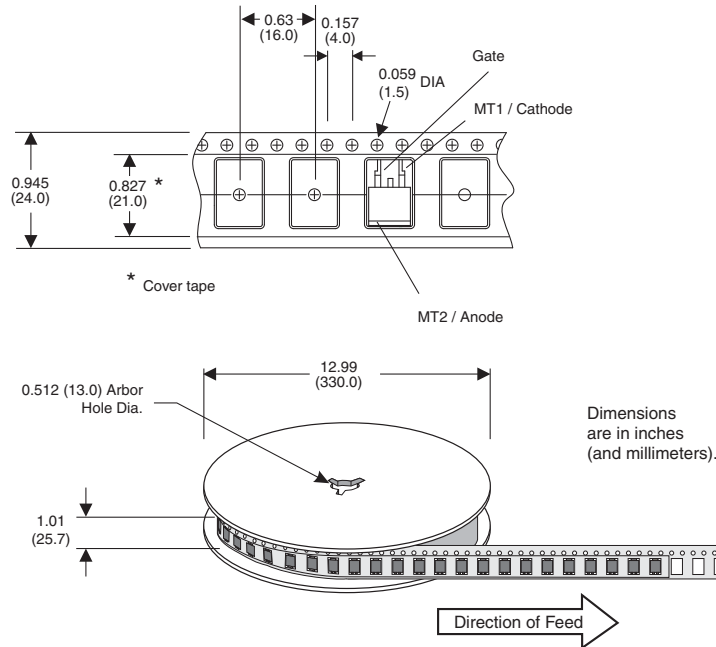
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx10L/Ryy	Qxx10L/Ryy	2.2 g	Bulk	500
Qxx10L/RyyTP	Qxx10L/Ryy	2.2 g	Tube Pack	500
Qxx10NyyTP	Qxx10Nyy	1.6 g	Tube	500
Qxx10NyyRP	Qxx10Nyy	1.6 g	Embossed Carrier	500

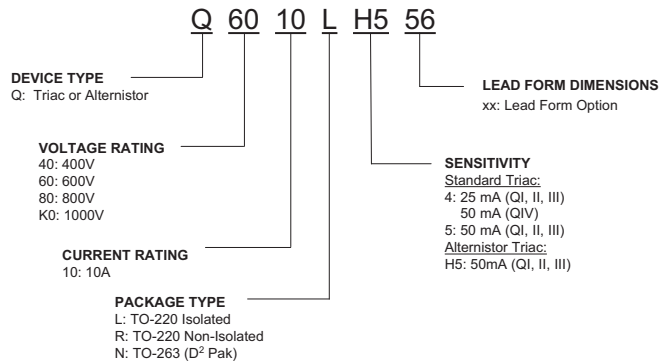
Note: xx = voltage, yy = type & sensitivity

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

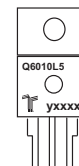


Part Numbering System

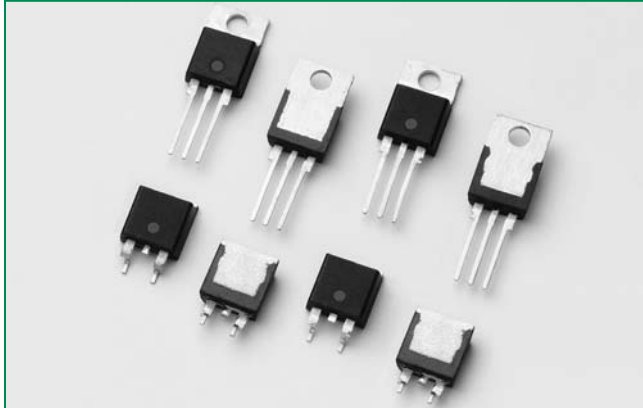


Part Marking System


TO-220 AB & TO-263AA
(R, L and N Packages)







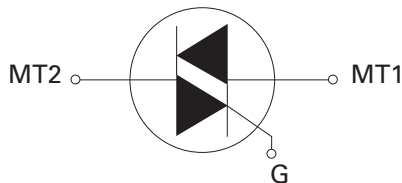
Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	10 to 50	mA

Schematic Symbol



Description

12 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 120 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Alternistor (3 Quadrants)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx12LHy $T_C = 90^\circ\text{C}$	12
		Qxx12RH Qxx12NH $T_C = 105^\circ\text{C}$	
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz t = 20 ms	A
		f = 60 Hz t = 16.7 ms	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms	A^2s
di/dt	Critical rate of rise of on-state current	f = 120 Hz $T_J = 125^\circ\text{C}$	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s};$ $I_{GT} \leq I_{GTM}$ $T_J = 125^\circ\text{C}$	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$	W
T_{stg}	Storage temperature range	-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range	-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant	Qxx12xH2	Qxx12xH5	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	10	mA
V_{GT}		I – II – III	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2	V
I_H	$I_T = 100\text{mA}$	MAX.	15	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	300	$\text{V}/\mu\text{s}$
		600V		200	
		800V		150	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V		150	
(dv/dt)c	(di/dt)c = 6.5 A/ms $T_J = 125^\circ\text{C}$	MIN.	2	30	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\mu\text{s}$ $I_T = 17.0 \text{ A(pk)}$	TYP.	4	4	μs

Static Characteristics

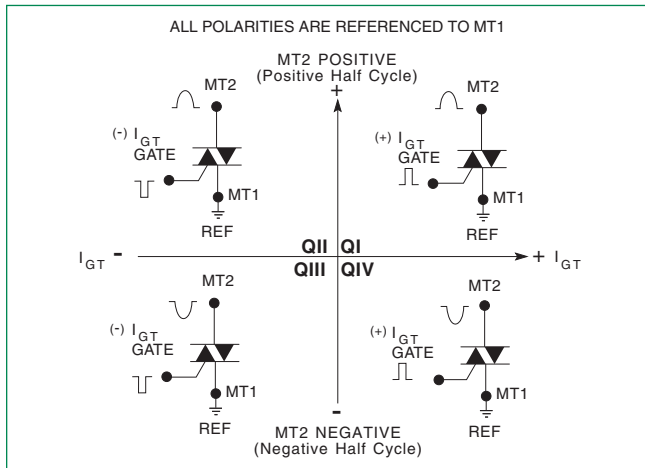
Symbol	Test Conditions	Value	Unit
V_{TM}	$I_{TM} = 17.0\text{A}$ $t_p = 380 \mu\text{s}$	MAX.	1.60
I_{DRM} I_{RRM}	$V_D = V_{DRM} / V_{RRM}$	$T_J = 25^\circ\text{C}$ 400-1000V	10
		$T_J = 125^\circ\text{C}$ 400-800V	2
		$T_J = 100^\circ\text{C}$ 1000V	3

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx12RH Qxx12NH	$^\circ\text{C}/\text{W}$
		Qxx12LH	
$R_{\theta(J-A)}$	Junction to ambient (AC)	Qxx12RH	$^\circ\text{C}/\text{W}$
		Qxx12LH	

Note: xx = voltage, y = sensitivity

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

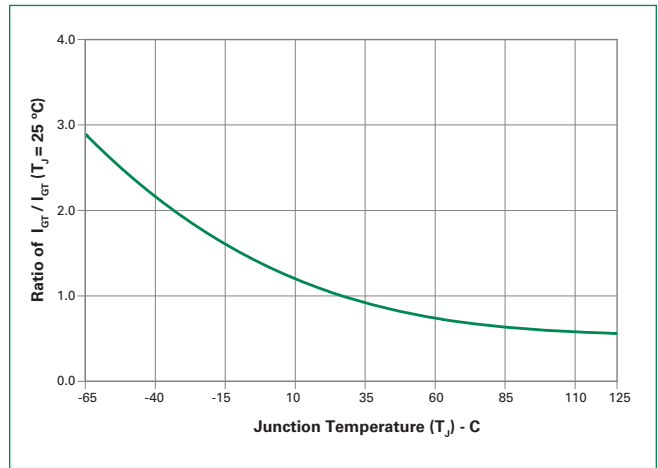


Figure 3: Normalized DC Holding Current vs. Junction Temperature

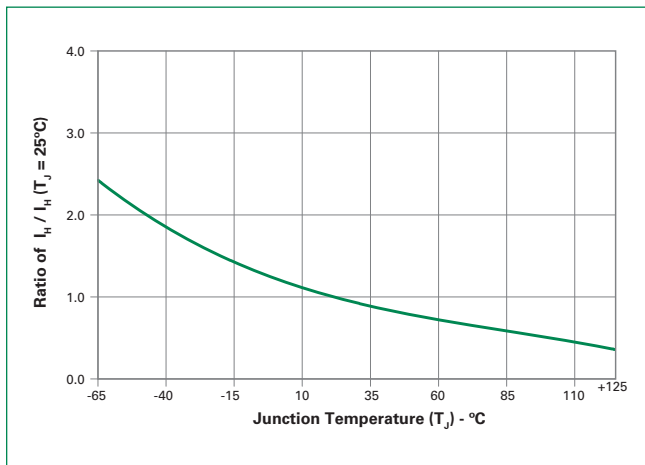


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

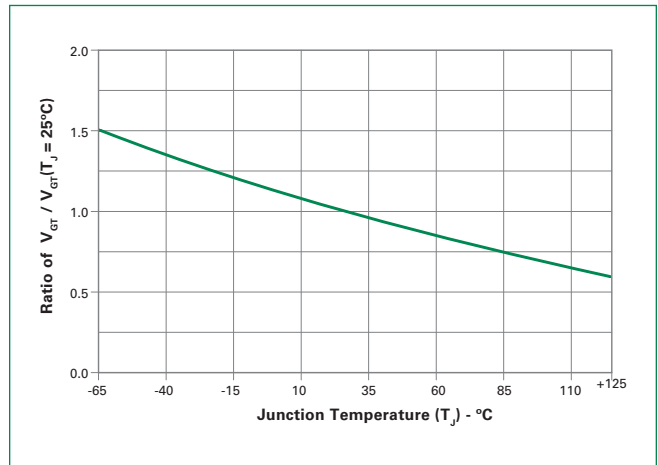


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

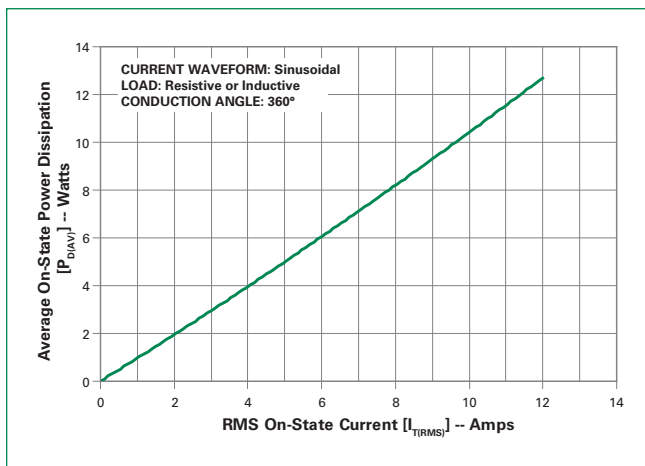


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

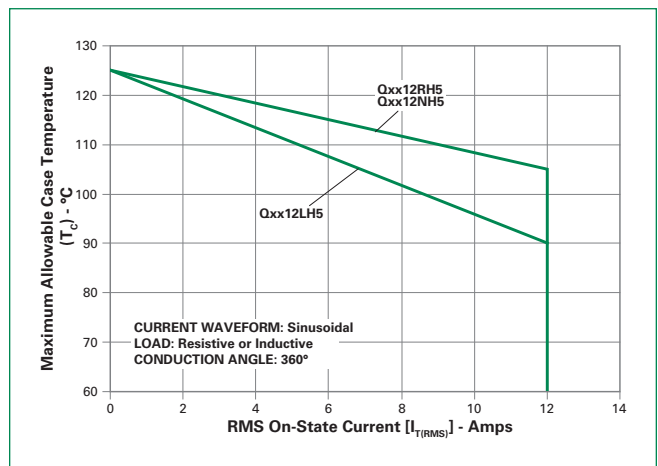


Figure 7: Maximum Allowable Ambient Temperature vs. On-State Current

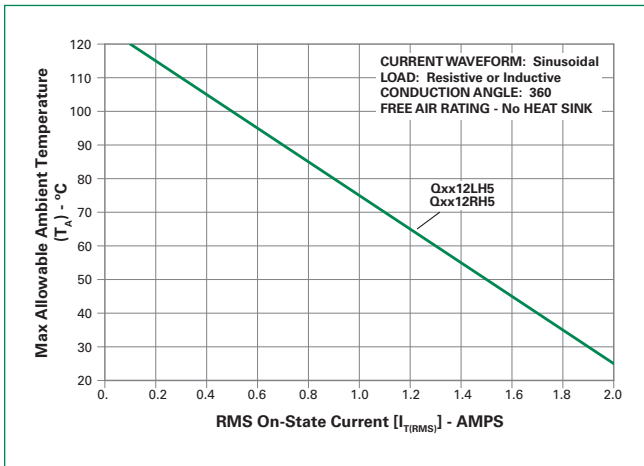


Figure 8: On-State Current vs. On-State Voltage (Typical)

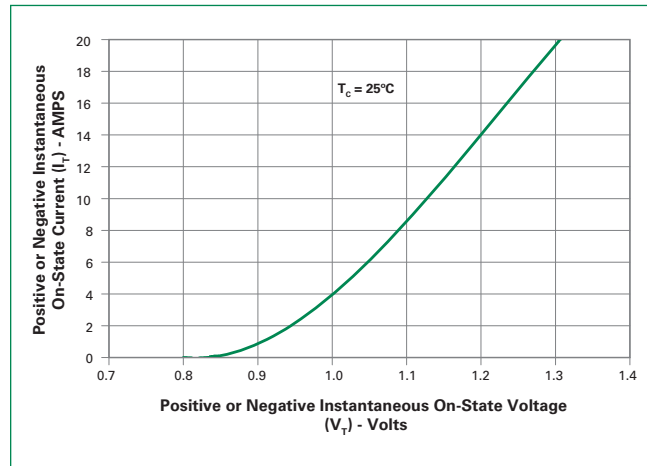
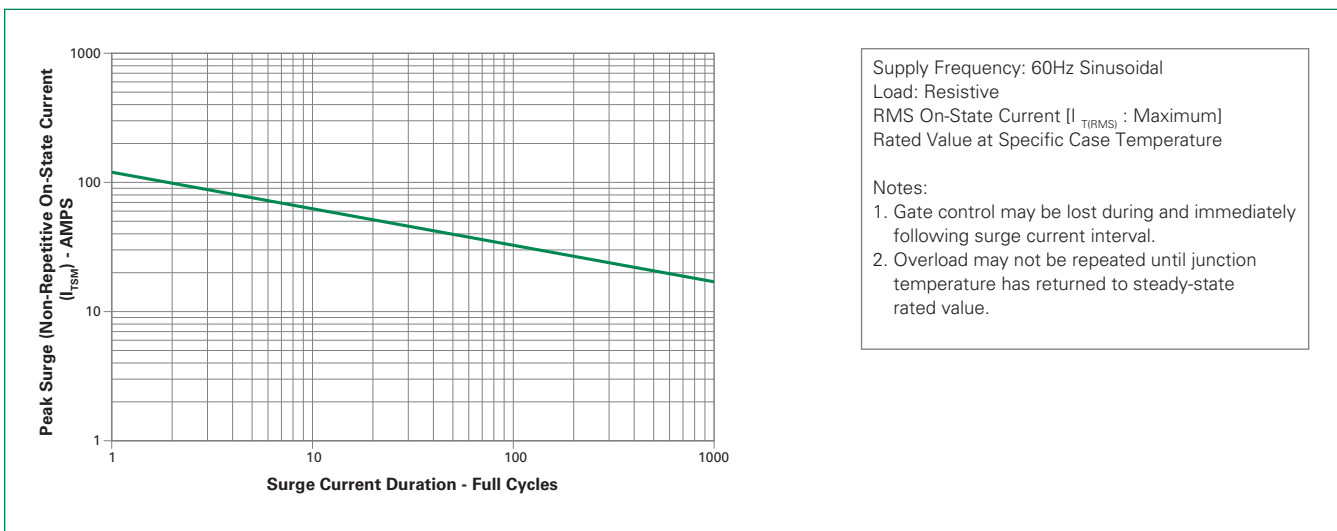
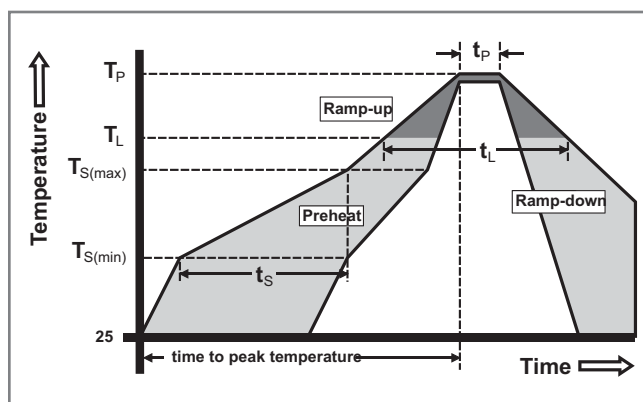


Figure 9: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

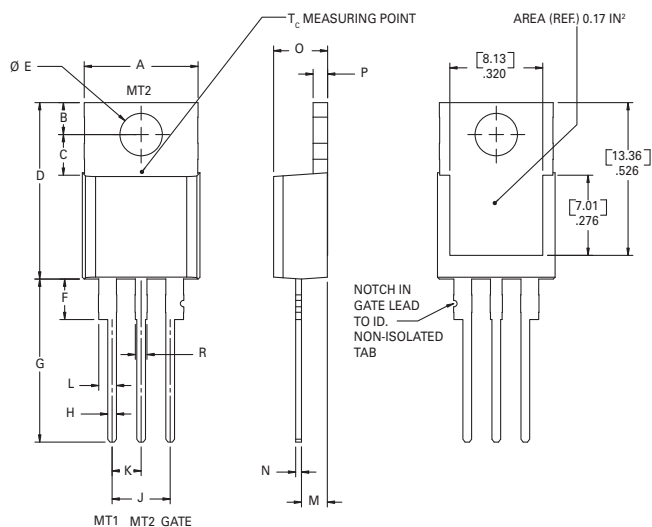
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

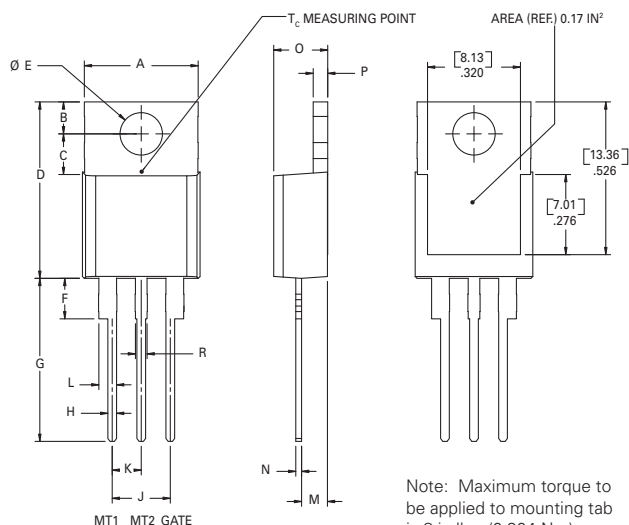
Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

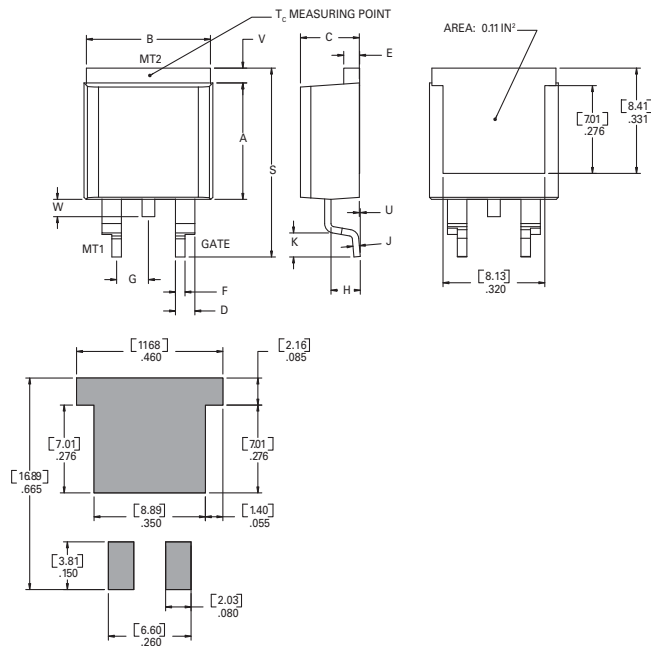
Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-263AB (N-Package) — D²Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

12.0 A TRIACS

Product Selector

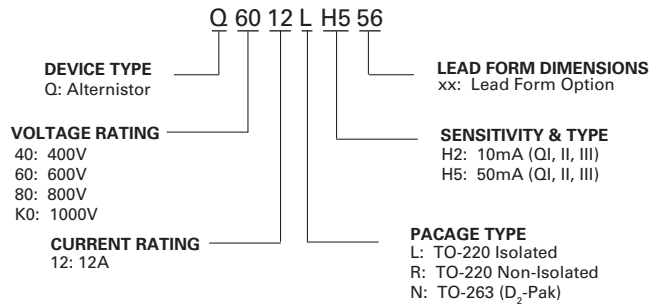
Part Number	Voltage				Gate Sensitivity Quadrants I – II – III	Type	Package
	400V	600V	800V	1000V			
Qxx12LH2	X	X	X		10 mA	Alternistor Triac	TO-220L
Qxx12RH2	X	X	X		10 mA	Alternistor Triac	TO-220R
Qxx12NH2	X	X	X		10 mA	Alternistor Triac	TO-263 D ² PAK
Qxx12LH5	X	X	X	X	50 mA	Alternistor Triac	TO-220L
Qxx12RH5	X	X	X	X	50 mA	Alternistor Triac	TO-220R
Qxx12NH5	X	X	X	X	50 mA	Alternistor Triac	TO-263 D ² PAK

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx12L/RHy	Qxx12L/RHy	2.2 g	Bulk	500
Qxx12L/RHyTP	Qxx12L/RHy	2.2 g	Tube Pack	500
Qxx12NHyTP	Qxx12NHy	1.6 g	Tube	500
Qxx12NHyRP	Qxx12NHy	1.6 g	Embossed Carrier	500

Note: xx = Voltage; y = Sensitivity

Part Numbering System

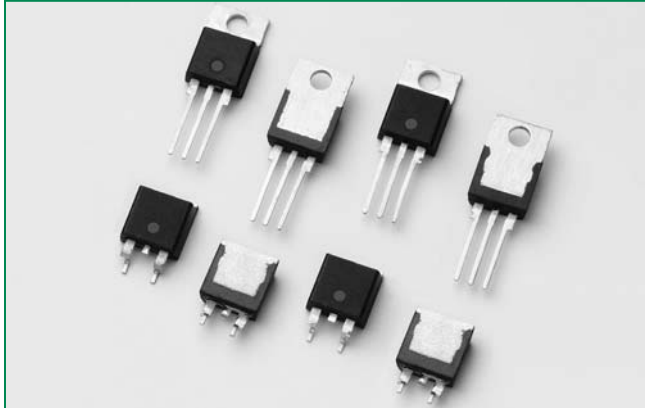


Part Marking System


TO-220 AB & TO-263
(R, L and N Packages)



RoHS Qxx15xx & Qxx16xHx Series



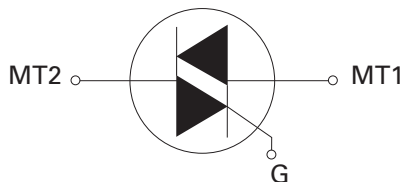
Agency Approval

Agency	Agency File Number
	L Package : E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	15 & 16	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	10 to 80	mA

Schematic Symbol



Description

15 Amp and 16 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 200 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point in sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Standard Triac

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx15Ly	$T_C = 80^\circ\text{C}$	15	A
		Qxx15Ry Qxx15Ny	$T_C = 90^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	167	A
		f = 60 Hz	t = 16.7 ms	200	
I^2t	I^2t Value for fusing		$t_p = 8.3$ ms	166	A^2s
di/dt	Critical rate of rise of on-state current	f = 120 Hz	$T_J = 125^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	2.0	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx16LHy	$T_C = 80^\circ\text{C}$	16	A
		Qxx16RHy Qxx16NH y	$T_C = 90^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	167	A
		f = 60 Hz	t = 16.7 ms	200	
I^2t	I^2t Value for fusing		$t_p = 8.3$ ms	166	A^2s
di/dt	Critical rate of rise of on-state current	f = 120 Hz	$T_J = 125^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$; $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	2.0	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Value	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	50	mA
V_{GT}		I – II – III	MAX.	2.0	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2	V
I_H	$I_T = 100\text{mA}$		MAX.	70	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	275	$\text{V}/\mu\text{s}$
		600V		225	
		800V		200	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V		200	
(dv/dt)c	(di/dt)c = 8.1 A/ms $T_J = 125^\circ\text{C}$		MIN.	4	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 22.6 \text{ A(pk)}$		TYP.	4	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant		Qxx16xH2	Qxx16xH3	Qxx16xH4	Qxx16xH6	Unit
I _{GT}	V _D = 12V R _L = 60 Ω	I – II – III	MAX.	10	20	35	80	mA
V _{GT}		I – II – III	MAX.	1.3				V
V _{GD}	V _D = V _{DRM} R _L = 3.3 kΩ T _J = 125°C	I – II – III	MIN.	0.2				V
I _H	I _T = 100mA		MAX.	15	35	50	70	mA
dv/dt	V _D = V _{DRM} Gate Open T _J = 125°C	400V	MIN.	200	350	475	925	V/μs
		600V		150	250	400	850	
		800V		100	200	350	475	
	V _D = V _{DRM} Gate Open T _J = 100°C	1000V		100	200	300	350	
(dv/dt) _c	(di/dt) _c = 8.6 A/ms T _J = 125°C		MIN.	2	20	25	30	V/μs
t _{gt}	I _G = 2 × I _{GT} PW = 15μs I _T = 22.6 A(pk)		TYP.	3	3	3	5	μs

Static Characteristics

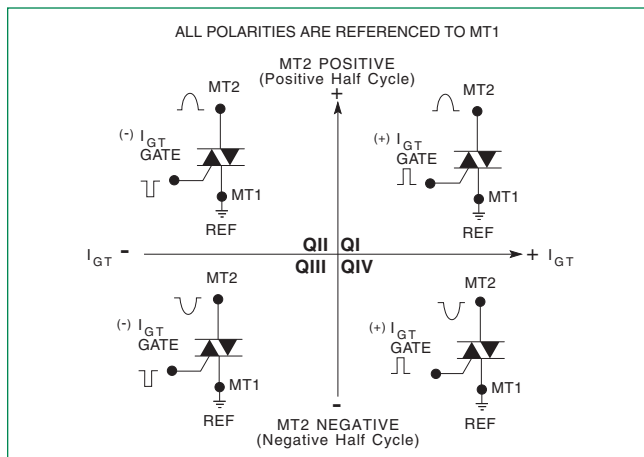
Symbol	Test Conditions				Value	Unit
V _{TM}	15A Device I _T = 21.2A t _p = 380µs			MAX	1.60	V
	16A Device I _T = 22.6A t _p = 380µs					
I _{DRM} I _{RRM}	V _D = V _{DRM} / V _{RRM}	T _J = 25°C	400-1000V	MAX	5	µA
		T _J = 125°C	400-800V		2	mA
		T _J = 100°C	1000V		3	

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx15Ry Qxx15Ny Qxx16RHy Qxx16NHy	$^\circ\text{C/W}$
		Qxx15Ly Qxx16LHy	
$R_{\theta(J-A)}$	Junction to ambient	Qxx15Ry Qxx16RHy	$^\circ\text{C/W}$
		Qxx15Ly Qxx16LHy	

Note: xx = voltage; y = sensitivity

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

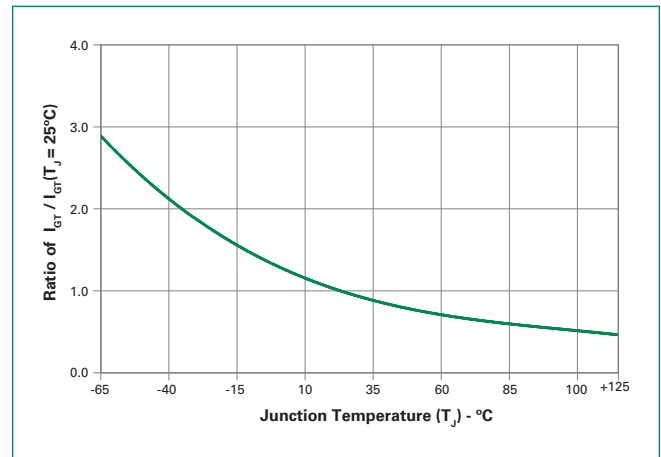


Figure 3: Normalized DC Holding Current vs. Junction Temperature

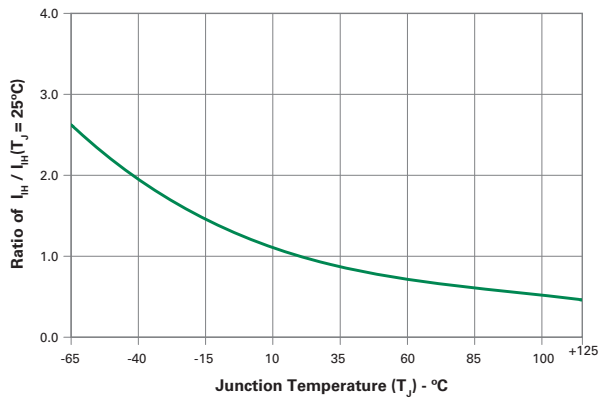


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

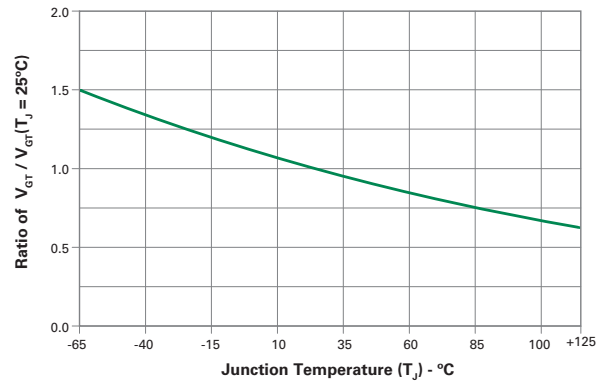


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

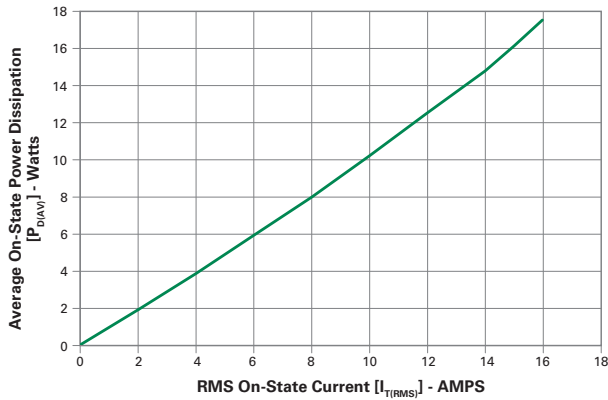


Figure 6: Maximum Allowable Case Temperature vs. On-State Current (15A devices)

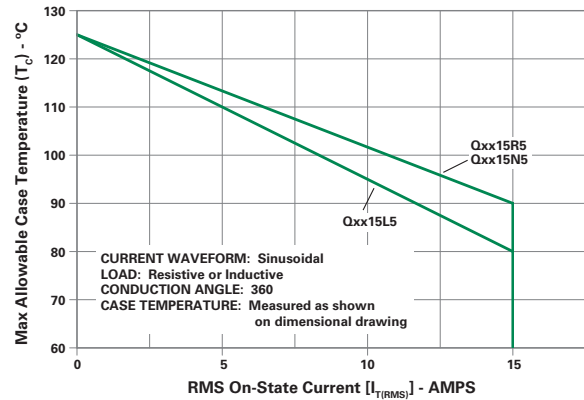


Figure 7: Maximum Allowable Case Temperature vs. On-State Current (16A devices)

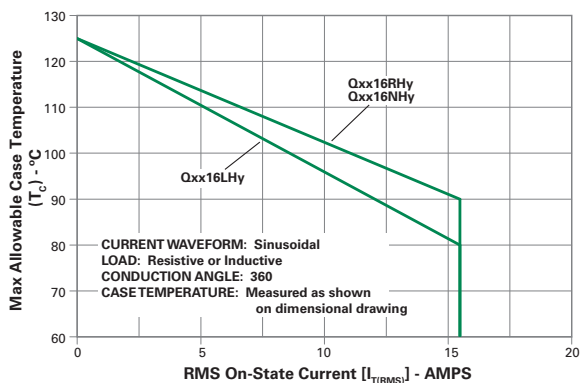


Figure 8: Maximum Allowable Ambient Temperature vs. On-State Current

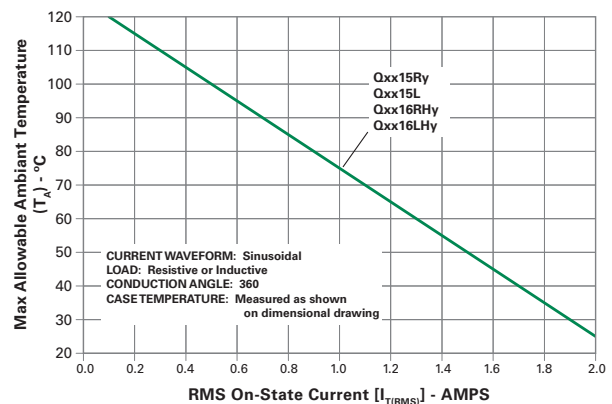


Figure 9: On-State Current vs. On-State Voltage (Typical)

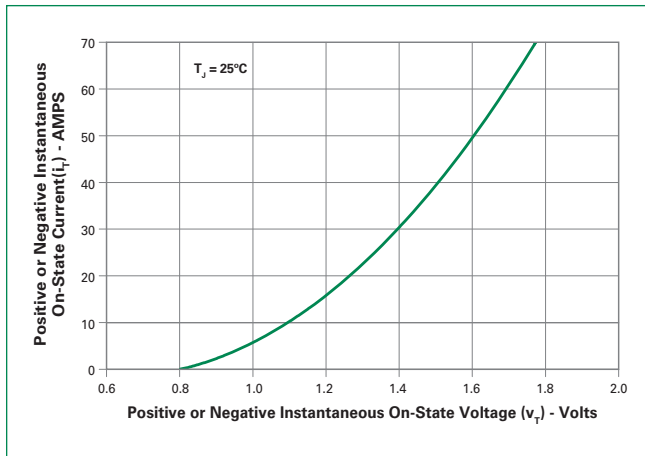
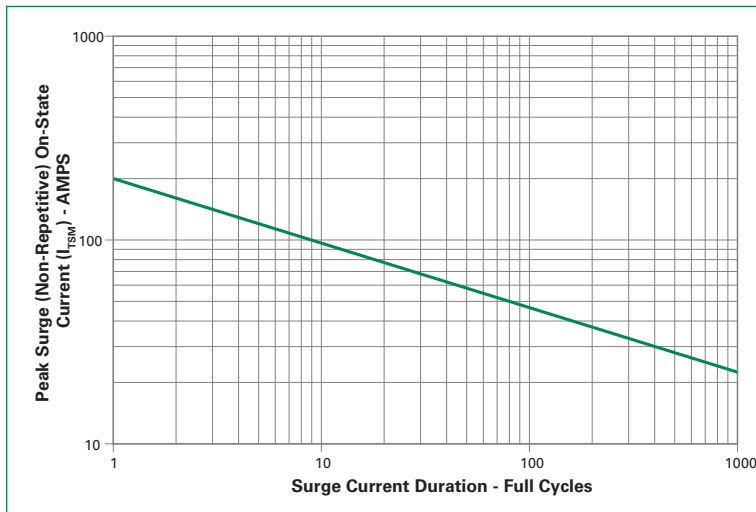


Figure 10: Surge Peak On-State Current vs. Number of Cycles



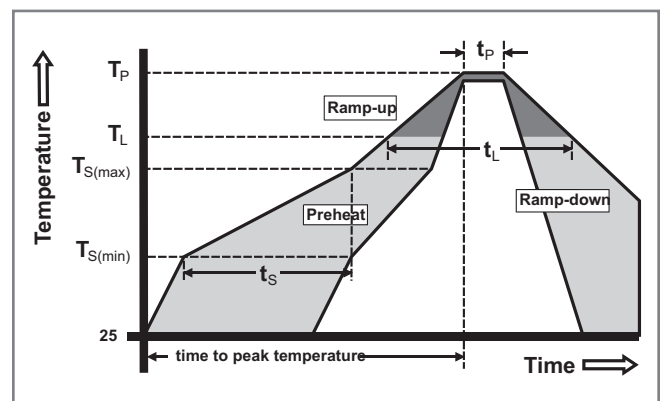
Supply Frequency: 60Hz Sinusoidal
Load: Resistive
RMS On-State [$I_{T(RMS)}$]: Max Rated Value at Specific Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 $^{+0/-50}$ °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

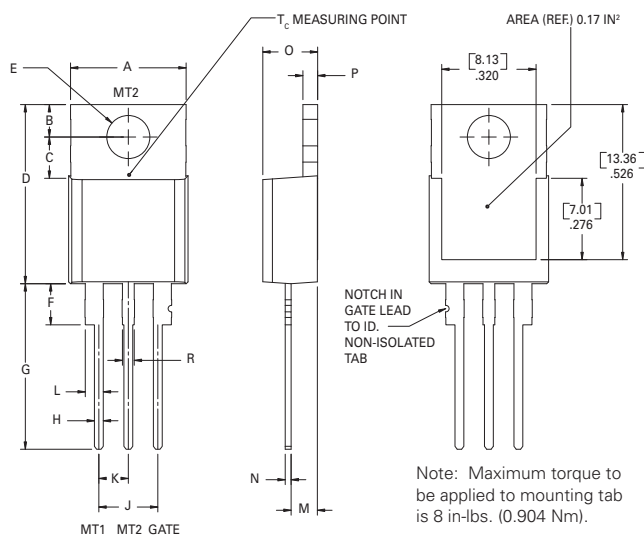
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

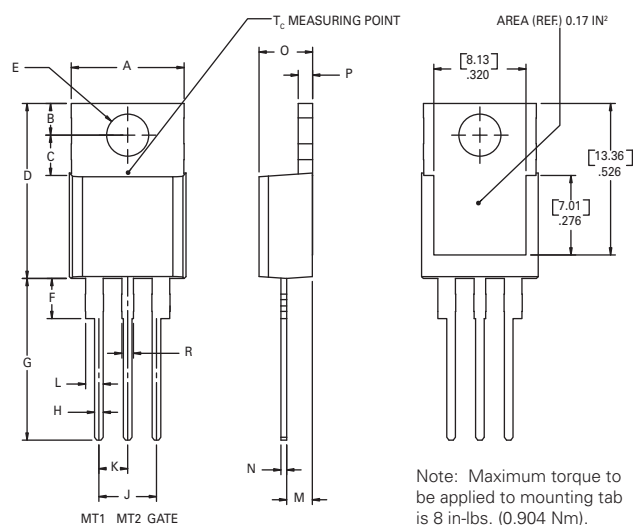
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.66	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

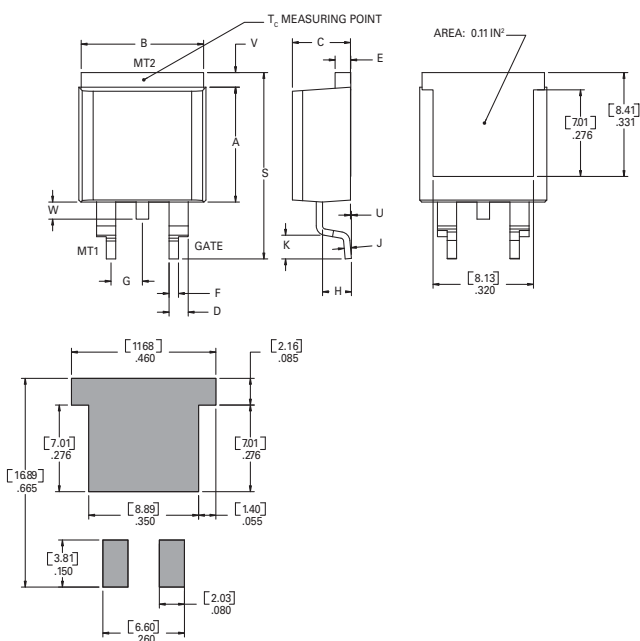
Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.60
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

15/16 A TRIACS

Dimensions — TO-263AB (N-Package) — D²Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Product Selector

Part Number	Voltage				Gate Sensitivity Quadrants	Type	Package
	400V	600V	800V	1000V	I – II – III		
Qxx15L5	X	X	X	X	50 mA	Standard Triac	TO-220L
Qxx15R5	X	X	X	X	50 mA	Standard Triac	TO-220R
Qxx15N5	X	X	X	X	50 mA	Standard Triac	TO-263 D ² -PAK
Qxx16LH2	X	X	X	X	10 mA	Alternistor Triac	TO-220L
Qxx16RH2	X	X	X	X	10 mA	Alternistor Triac	TO-220R
Qxx16NH2	X	X	X	X	10 mA	Alternistor Triac	TO-263 D ² -PAK
Qxx16LH3	X	X	X	X	20 mA	Alternistor Triac	TO-220L
Qxx16RH3	X	X	X	X	20 mA	Alternistor Triac	TO-220R
Qxx16NH3	X	X	X	X	20 mA	Alternistor Triac	TO-263 D ² -PAK
Qxx16LH4	X	X	X	X	35 mA	Alternistor Triac	TO-220L
Qxx16RH4	X	X	X	X	35 mA	Alternistor Triac	TO-220R
Qxx16NH4	X	X	X	X	35 mA	Alternistor Triac	TO-263 D ² -PAK
Qxx16LH6	X	X	X	X	80 mA	Alternistor Triac	TO-220L
Qxx16RH6	X	X	X	X	80 mA	Alternistor Triac	TO-220R
Qxx16NH6	X	X	X	X	80 mA	Alternistor Triac	TO-263 D ² -PAK

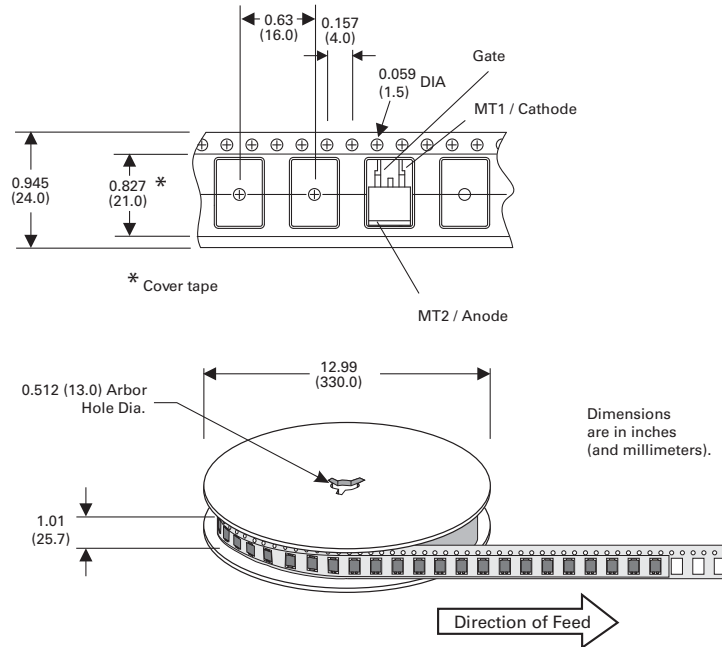
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx15L/Ry	Qxx15L/Ry	2.2 g	Bulk	500
Qxx15L/RyTP	Qxx15L/Ry	2.2 g	Tube Pack	500
Qxx15NyTP	Qxx15Ny	1.6 g	Tube	500
Qxx15NyRP	Qxx15Ny	1.6 g	Embossed Carrier	500
Qxx16L/RHy	Qxx16L/RHy	2.2 g	Bulk	500
Qxx16L/RHyTP	Qxx16L/RHy	2.2 g	Tube Pack	500
Qxx16NHyTP	Qxx16NHy	1.6 g	Tube	500
Qxx16NHyRP	Qxx16NHy	1.6 g	Embossed Carrier	500

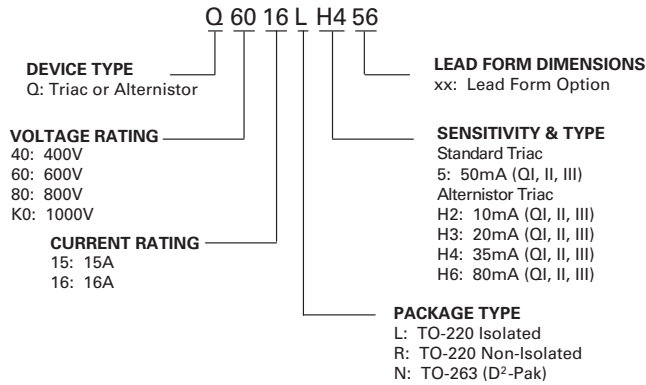
Note: xx = Voltage; y = Sensitivity

TO-263 Embossed Carrier Reel Pack (RP)

Meets all EIA-481-2 Standards

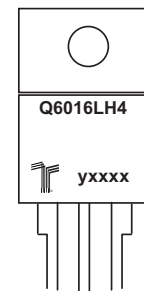


Part Numbering System



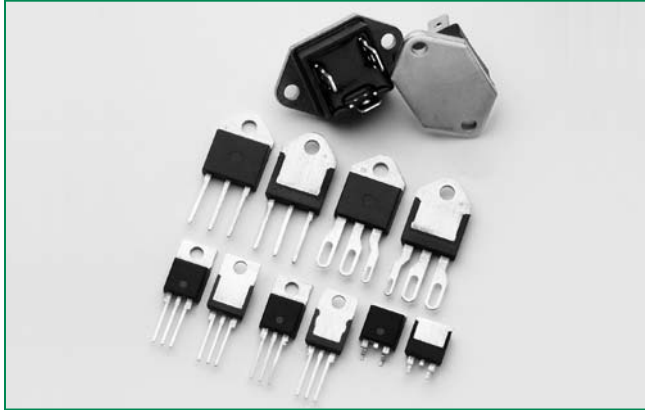
Part Marking System

TO-220AB & TO-263AA (R, L and N Packages)





RoHS Qxx25xx & Qxx25xHx Series



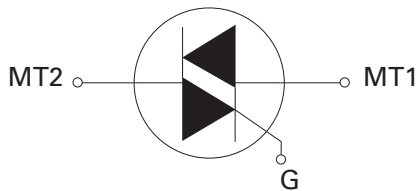
Agency Approval

Agency	Agency File Number
	TO-220L, TO-218K, TO-218J & Fastpak Packages: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	1000	V
I_{GT}	50 to 80	mA

Schematic Symbol



Description

25 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 250 A

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings – Standard Triac

Symbol	Parameter	Test Conditions		Value	Unit	
$I_{T(RMS)}$	RMS on-state current	Qxx25R5 Qxx25N5	$T_c = 85^{\circ}\text{C}$	25	A	
		Qxx25P5	$T_c = 57^{\circ}\text{C}$			
I_{TSM}	Peak non-repetitive surge current	Qxx25R5 Qxx25N5	single half cycle; $f = 50\text{Hz}$; T_J (initial) = 25°C	167	A	
			single half cycle; $f = 60\text{Hz}$; T_J (initial) = 25°C	200		
		Qxx25P5	single half cycle; $f = 50\text{Hz}$; T_J (initial) = 25°C	220		250
			single half cycle; $f = 60\text{Hz}$; T_J (initial) = 25°C			
I^2t	I^2t Value for fusing	Qxx25R5 Qxx25N5	$t_p = 8.3\text{ms}$	166	A^2s	
		Qxx25P5		260		
di/dt	Critical rate-of-rise of on-state current	$f = 60\text{Hz}$; $T_J = 125^{\circ}\text{C}$		100	$\text{A}/\mu\text{s}$	
I_{GTM}	Peak gate current	$T_J = 125^{\circ}\text{C}$		2	A	
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^{\circ}\text{C}$		0.5	W	
T_{stg}	Storage temperature range			-40 to 125	$^{\circ}\text{C}$	
T_J	Operating junction temperature range	Qxx25R5 Qxx25N5		-40 to 125	$^{\circ}\text{C}$	
		Qxx25P5		-25 to 125		

Absolute Maximum Ratings – Alternistor Triac

Symbol	Parameter	Test Conditions		Value	Unit
$I_{T(RMS)}$	RMS on-state current	Qxx25LH5 Qxx25L6	$T_C = 65^{\circ}\text{C}$	25	A
		Qxx25K6 Qxx25J6	$T_C = 85^{\circ}\text{C}$		
		Qxx25RH5 Qxx25NH5 Qxx25R6 Qxx25NH6	$T_C = 95^{\circ}\text{C}$		
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_J (\text{initial}) = 25^{\circ}\text{C}$		208	A
		single half cycle; $f = 60\text{Hz}$; $T_J (\text{initial}) = 25^{\circ}\text{C}$		250	
I^2t	I^2t Value for fusing	$t_p = 8.3\text{ms}$		260	A^2s
di/dt	Critical rate-of-rise of on-state current	$f = 60\text{Hz}$; $T_J = 125^{\circ}\text{C}$		100	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate current	$T_J = 125^{\circ}\text{C}$		2	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^{\circ}\text{C}$		0.5	W
T_{stg}	Storage temperature range			-40 to 125	$^{\circ}\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^{\circ}\text{C}$

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Value		Unit
				Qxx25R5 Qxx25N5	Qxx25P5	
I _{GT}	V _D = 12V; R _L = 60 Ω	I – II – III	MAX.	50		mA
		IV	TYP.	120		
V _{GT}		I – II – III	MAX.	1.3		V
		IV	TYP.	2.5		
V _{GD}	V _D = V _{DRM} ; R _L = 3.3 kΩ ; T _J = 125°C	ALL	MIN.	0.2		V
I _H	I _T = 400mA (initial)		MAX.	100	50	mA
dv/dt	V _D = V _{DRM} ; Gate Open; T _J = 125°C	400V	MIN.	275	—	V/μs
		600V		225	475	
		800V		200	400	
	V _D = V _{DRM} ; Gate Open; T _J = 100°C	1000V		200	—	
(dv/dt) _c	(di/dt) _c = 13.3 A/ms; T _J = 125°C		MIN.	5		V/μs
t _{gt}	I _G = 2 × I _{GT} ; PW = 15μs; I _T = 35.4 A		TYP.	4	3	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac

Symbol	Test Conditions	Quadrant		Value		Unit
				Qxx25RH5 Qxx25LH5 Qxx25NH5	Qxx25R6 Qxx25L6 Qxx25NH6 Qxx25K6 Qxx25J6	
I_{GT}	$V_D = 12\text{V}; R_L = 60\ \Omega$	I – II – III	MAX.	50	80	mA
V_{GT}		I – II – III	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}; R_L = 3.3\ \text{k}\Omega; T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2		V
I_H	$I_T = 400\text{mA}$ (initial)		MAX.	50	100	mA
dv/dt	$V_D = V_{DRM};$ Gate Open; $T_J = 125^\circ\text{C}$	400V	MIN.	575	600	V/ μs
		600V		500	600	
		800V		400	475	
	$V_D = V_{DRM};$ Gate Open; $T_J = 100^\circ\text{C}$	1000V		—	400	
$(dv/dt)_c$	$(di/dt)_c = 13.3\ \text{A/ms}; T_J = 125^\circ\text{C}$		MIN.	20	30	V/ μs
t_{gt}	$I_G = 2 \times I_{GT}; PW = 15\ \mu\text{s}; I_T = 35.4\ \text{A}$		TYP.	3	5	μs

Static Characteristics

Symbol	Test Conditions				Value		Unit
					Qxx25R5 Qxx25N5 Qxx25xH5 Qxx25x6 Qxx25NH6	Qxx25P5	
V _{TM}	I _T = 35.4A; t _p = 380 μs			MAX.	1.8	1.4	V
I _{DRM} /I _{RRM}	V _{DRM} /V _{RRM}	T _J = 25°C	600 – 800V	MAX.	10	100	μA
			1000V		20	—	
		T _J = 100°C	600 – 800V		500	—	
			1000V		1000	—	
		T _J = 125°C	600 – 800V		2000	5000	

Note: xx = voltage, x = package

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx25R5 / Qxx25N5 Qxx25R6 / Qxx25NH6 Qxx25RH5 / Qxx25NH5	0.89	°C/W
		Qxx25P5	1.6	
		Qxx25L6 / Qxx25LH5	2.0	
		Qxx25K6 / Qxx25J6	1.32	
$R_{\theta(J-A)}$	Junction to ambient	Qxx25Ry	45	°C/W
		Qxx25L6 / Qxx25LH5	50	

Note: xx = voltage, y = sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

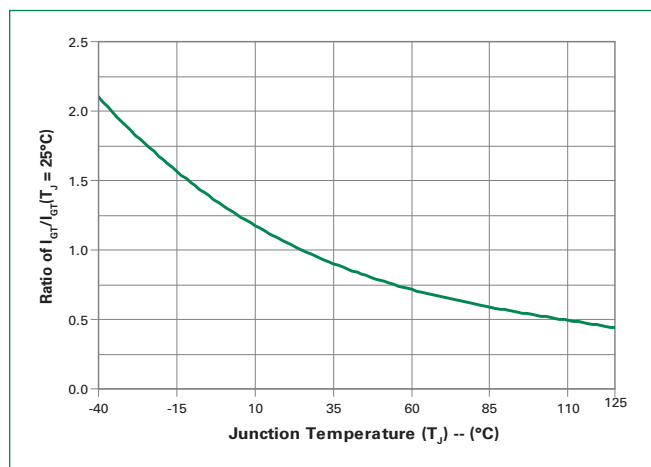


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

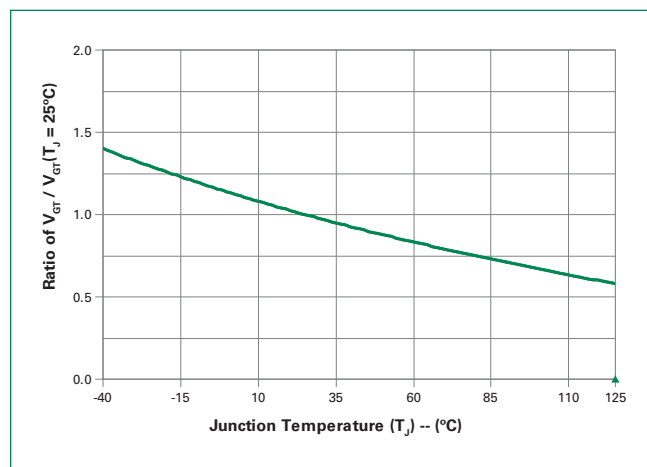


Figure 3: Normalized DC Holding Current vs. Junction Temperature

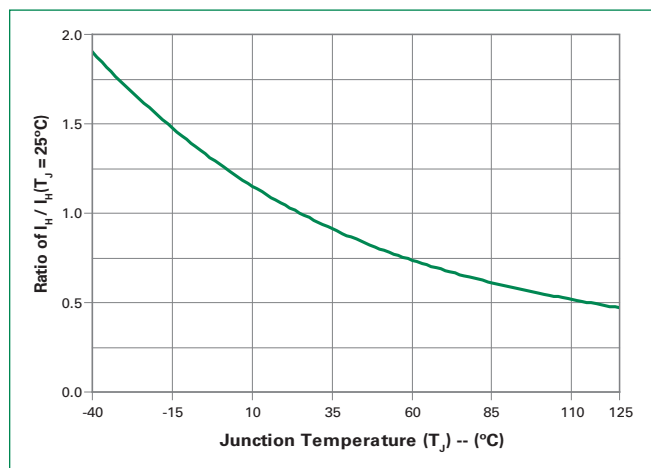


Figure 4: On-State Current vs. On-State Voltage (Typical)

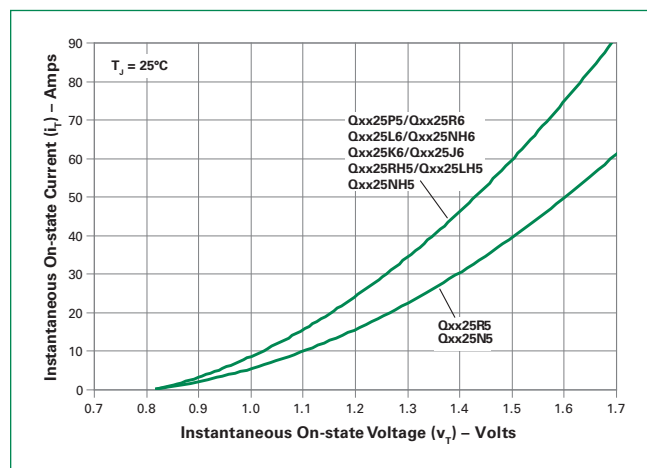


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

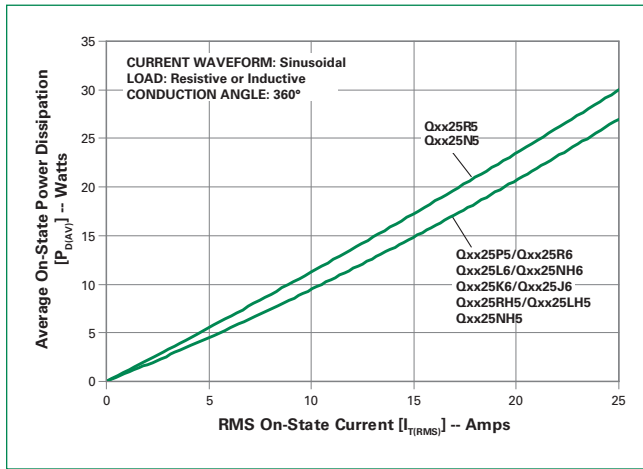


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

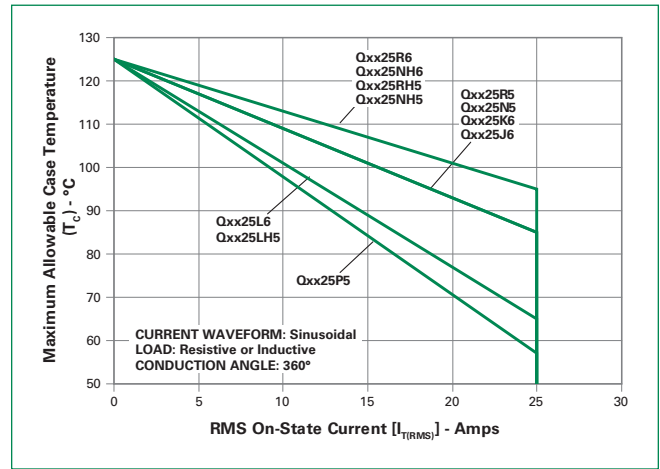


Figure 7: Maximum Allowable Ambient Temperature vs. RMS On-State Current (TO-220 packages only)

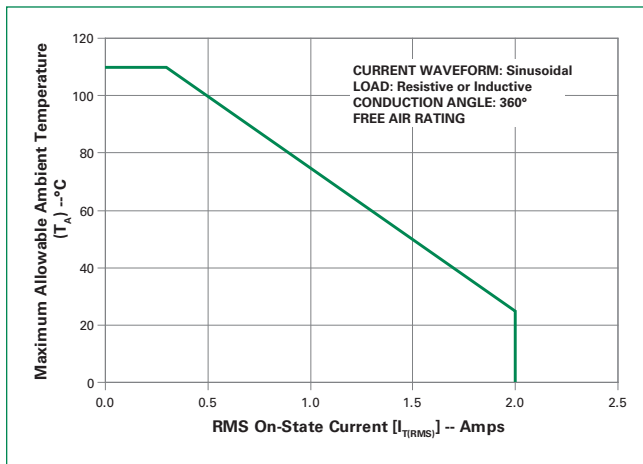
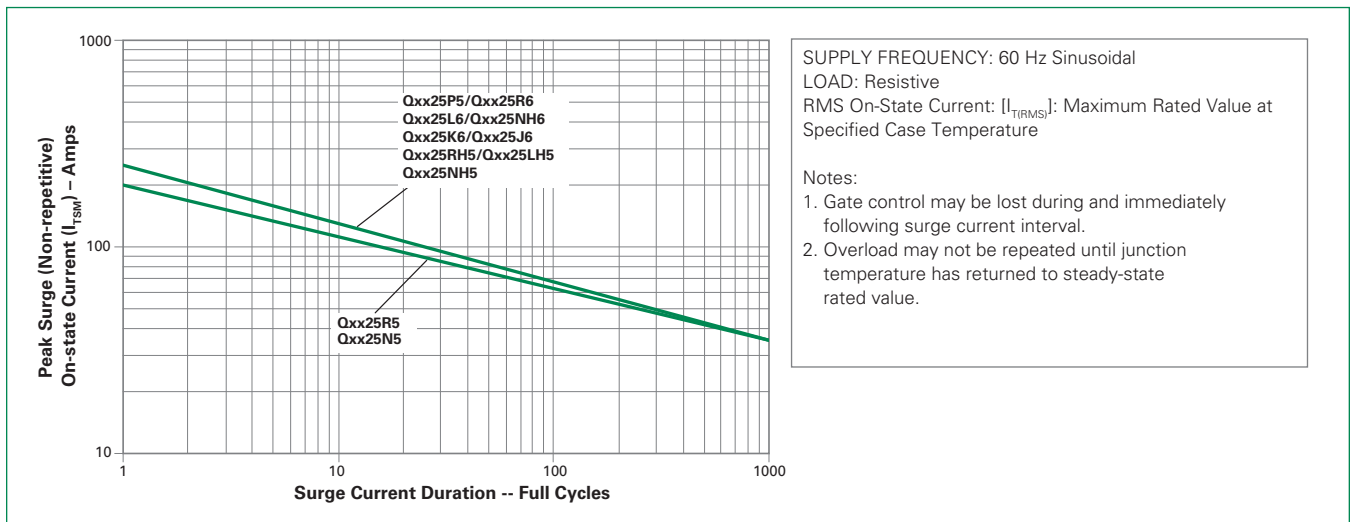
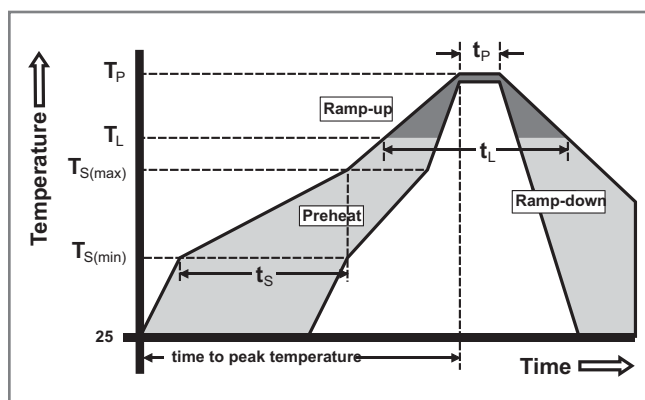


Figure 8: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

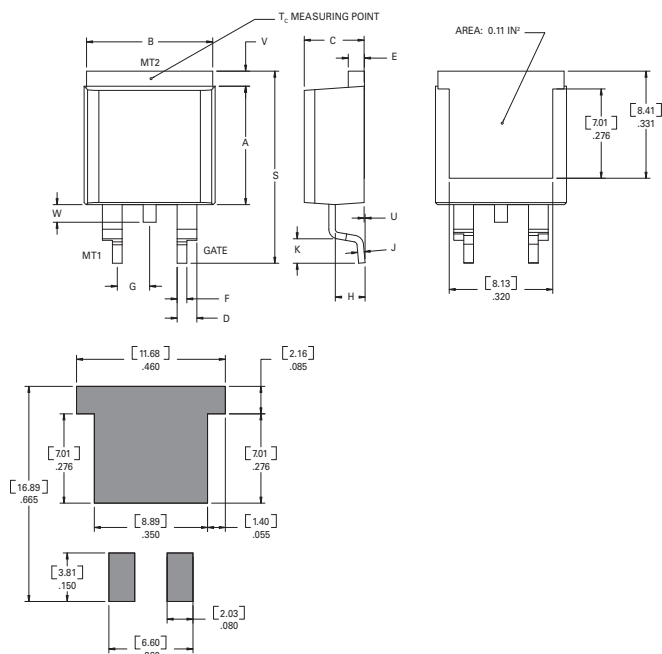
Environmental Specifications

Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{RRM} , 125°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051 -40°C to 125°C, 15-minute dwell, 100 cycles
Biased Temp & Humidity	EIA/JEDEC: JESD22-A101 320VDC, 85°C, 85%RH, 1008 hours
High Temp. Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	-40°C, 1008 hours
Thermal Shock	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002, Category 3, Test A
Lead Bend	MIL-STD-750: Method 2036, Condition E

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

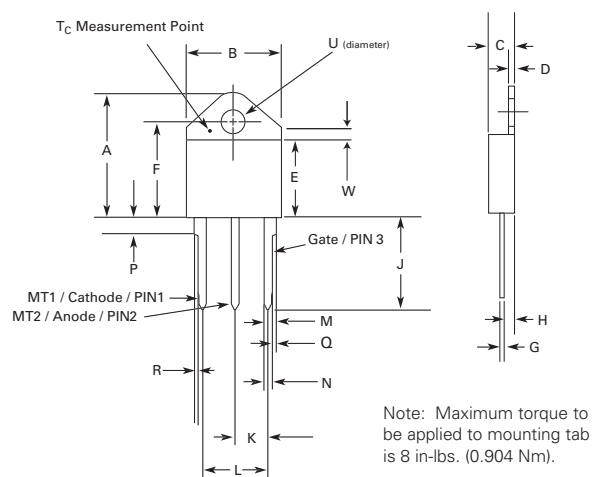
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.66	2.92
C	0.230	0.250	5.85	6.35
D	0.590	0.620	14.98	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.80	3.30
G	0.540	0.575	13.71	14.60
H	0.025	0.035	0.63	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	1.78	2.16
N	0.018	0.024	0.45	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.53
R	0.038	0.048	0.97	1.22

Dimensions — TO-263 (N Package) — D²Pak Surface Mount



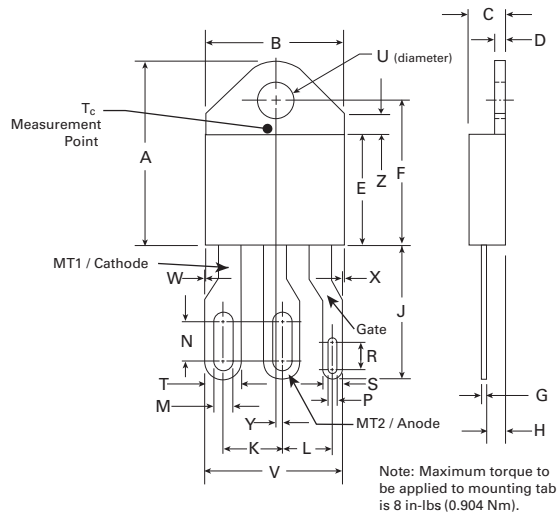
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Dimensions — TO-218AC (K Package) — Isolated Mounting Tab



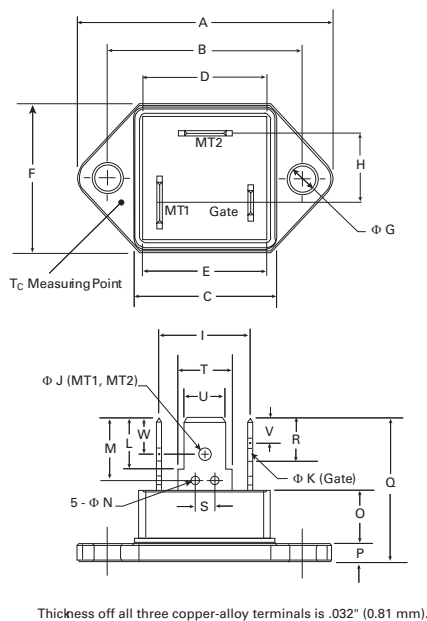
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.164	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

Dimensions — TO-218X (J Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	0.410	0.420
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Dimensions — TO-3 (P Package) Fastpak — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	1.531	1.543	38.90	39.20
B	1.177	1.185	29.90	30.10
C	0.843	0.850	21.40	21.60
D	0.780	0.795	19.80	20.20
E	0.783	0.791	19.90	20.10
F	0.874	0.906	22.20	23.00
G	0.161	0.169	4.10	4.30
H	0.386	0.465	9.80	11.80
I	0.508	0.587	12.90	14.90
J	0.079	0.087	2.00	2.20
K	0.047	0.055	1.20	1.40
L	0.307	0.319	7.80	8.10
M	0.372	0.396	9.45	10.05
N	0.043	0.059	1.10	1.50
O	0.315	0.331	8.00	8.40
P	0.098	0.106	2.50	2.70
Q	0.846	0.886	21.50	22.50
R	0.244	0.256	6.20	6.50
S	0.106	0.130	2.70	3.30
T (MT1)	0.321	0.329	8.15	8.35
T (MT2)	0.321	0.329	8.15	8.35
T (Gate)	0.220	0.228	5.60	5.80
U (MT1)	0.246	0.254	6.25	6.45
U (MT2)	0.246	0.254	6.25	6.45
U (Gate)	0.183	0.191	4.65	4.85
V	0.120	0.130	3.05	3.30
W	0.175	0.185	4.45	4.70

Maximum torque to be applied to mounting tab is 8 in-lbs (0.904Nm).

Product Selector

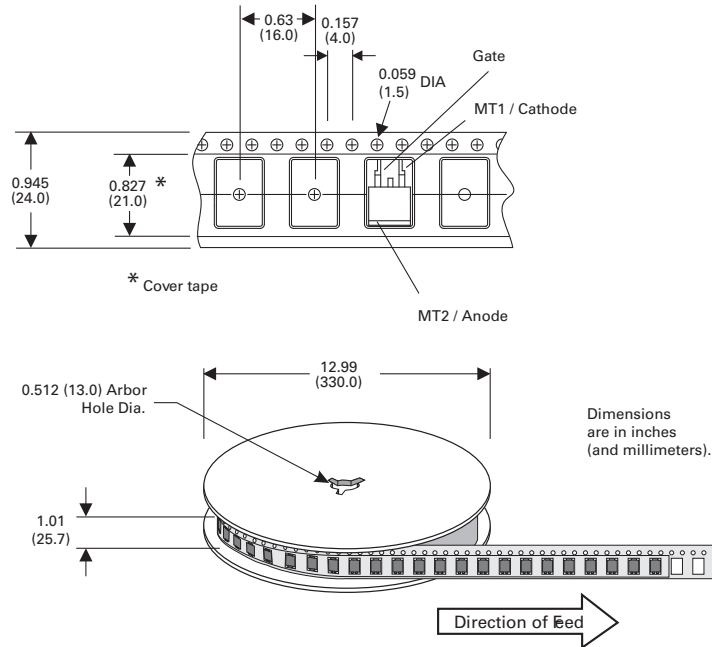
Part Number	Voltage				Gate Sensitivity Quadrants		Package
	400V	600V	800V	1000V	I - II - III	IV	
Qxx25R5	X	X	X	X	50 mA	120 mA (TYP)	TO-220R
Qxx25N5	X	X	X	X	50 mA	120 mA (TYP)	TO-263 D ² -Pak
Qxx25P5		X	X		50 mA	120 mA (TYP)	Fastpak
Qxx25RH5	X	X	X		50 mA		TO-220R
Qxx25LH5	X	X	X		50 mA		TO-220L
Qxx25NH5	X	X	X		50 mA		TO-263 D ² -Pak
Qxx25R6	X	X	X	X	80 mA		TO-220R
Qxx25L6	X	X	X	X	80 mA		TO-220L
Qxx25NH6	X	X	X	X	80 mA		TO-263 D ² -Pak
Qxx25J6	X	X	X		80 mA		TO-218X
Qxx25K6	X	X	X	X	80 mA		TO-218AC

Packing Options

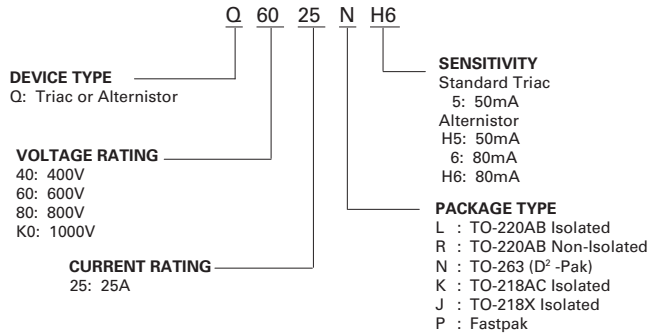
Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx25R5	Qxx25R5	2.20g	Bulk	500
Qxx25R5TP	Qxx25R5	2.20g	Tube	500
Qxx25N5TP	Qxx25N5	1.60g	Tube	500
Qxx25N5RP	Qxx25N5	1.60g	Embossed Carrier	500
Qxx25RH5	Qxx25RH5	2.20g	Bulk	500
Qxx25RH5TP	Qxx25RH5	2.20g	Tube	500
Qxx25LH5	Qxx25LH5	2.20g	Bulk	500
Qxx25LH5TP	Qxx25LH5	2.20g	Tube	500
Qxx25NH5TP	Qxx25NH5	1.60g	Tube	500
Qxx25NH5RP	Qxx25NH5	1.60g	Embossed Carrier	500
Qxx25P5	Qxx25P5	21.4g	Bulk	200
Qxx25R6	Qxx25R6	2.20g	Bulk	500
Qxx25R6TP	Qxx25R6	2.20g	Tube	500
Qxx25L6	Qxx25L6	2.20g	Bulk	500
Qxx25L6TP	Qxx25L6	2.20g	Tube	500
Qxx25NH6TP	Qxx25NH6	1.60g	Tube	500
Qxx25NH6RP	Qxx25NH6	1.60g	Embossed Carrier	500
Qxx25J6	Qxx25J6	5.23g	Bulk	250
Qxx25J6TP	Qxx25J6	5.23g	Tube	500
Qxx25K6	Qxx25K6	4.40g	Bulk	250
Qxx25K6TP	Qxx25K6	4.40g	Tube	500

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



Part Numbering System

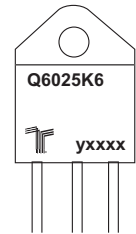


Part Marking System

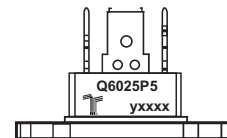
TO-220AB (R & L Packages)
TO-263 (N Package)



TO-218AC (K Package)
TO-218X (J Package)

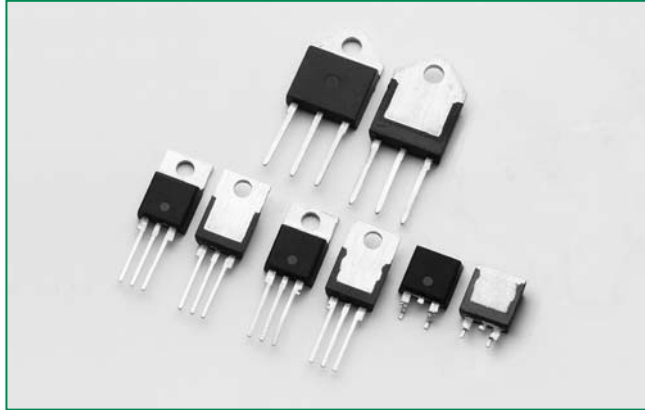


Fastpak (P Package)





RoHS HQ6025xH5 Series



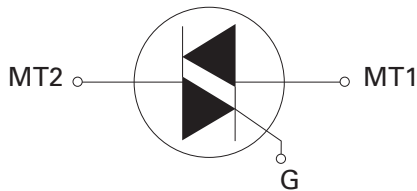
Agency Approval

Agency	Agency File Number
	L and K Packages: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	50	mA

Schematic Symbol



Description

25Amp bi-directional Alternistor Triac is designed for AC switching and phase control applications requiring a higher temperature environment.

Alternistor type devices only operate in quadrants I, II, & and are used in circuits requiring high dv/dt capability.

Features & Benefits

- 150°C maximum junction temperature
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 300 A

Applications

Typically used in high-temperature environments where available heat-sinking is minimal such as heating and white goods applications.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions		Value	Unit
I _{T(RMS)}	RMS on-state current	HQ6025LH5	T _C = 95°C	25	A
		HQ6025RH5	T _C = 102°C		
		HQ6025NH5			
		HQ6025KH5			
I _{TSM}	Peak non-repetitive surge current		single half cycle; f = 50Hz; T _J (initial) = 25°C	250	A
			single half cycle; f = 60Hz; T _J (initial) = 25°C	300	
I ² t	I ² t Value for fusing	t _p = 8.3ms		373	A ² s
di/dt	Critical rate-of-rise of on-state current	f = 60Hz; T _J = 150°C		100	A/μs
I _{GTM}	Peak gate current	T _J = 150°C		2	A
P _{G(AV)}	Average gate power dissipation	T _J = 150°C		0.5	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 150	°C

Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Quadrant		Value	Unit
I_{GT}	$V_D = 12\text{V}$; $R_L = 60\ \Omega$	I – II – III	MAX.	50	mA
V_{GT}		I – II – III	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$; $R_L = 3.3\ \text{k}\Omega$; $T_j = 150^\circ\text{C}$	I – II – III	MIN.	0.2	V
I_H	$I_T = 400\text{mA}$ (initial)		MAX.	80	mA
dv/dt	$V_D = V_{DRM}$; Gate Open; $T_j = 150^\circ\text{C}$		MIN.	350	$\text{V}/\mu\text{s}$
$(dv/dt)_c$	$(di/dt)_c = 13.3\ \text{A/ms}$; $T_j = 150^\circ\text{C}$		MIN.	20	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$; $PW = 15\mu\text{s}$; $I_T = 35.4\ \text{A}$		TYP.	3	μs

Static Characteristics

Symbol	Test Conditions			Value	Unit
V_{TM}	$I_T = 35.4\text{A}$; $t_p = 380\ \mu\text{s}$		MAX.	1.4	V
I_{DRM}/I_{RRM}	V_{DRM}/V_{RRM}	$T_j = 25^\circ\text{C}$	MAX.	5	μA
		$T_j = 150^\circ\text{C}$		6000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	HQ6025LH5	2.0	$^\circ\text{C}/\text{W}$
		HQ6025RH5 HQ6025NH5	0.86	
		HQ6025KH5	1.35	
$R_{\theta(J-A)}$	Junction to ambient	HQ6025LH5	50	$^\circ\text{C}/\text{W}$
		HQ6025RH5	45	

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

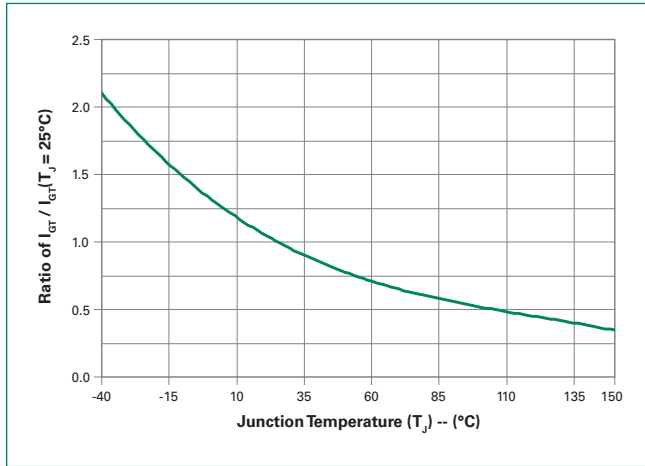


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

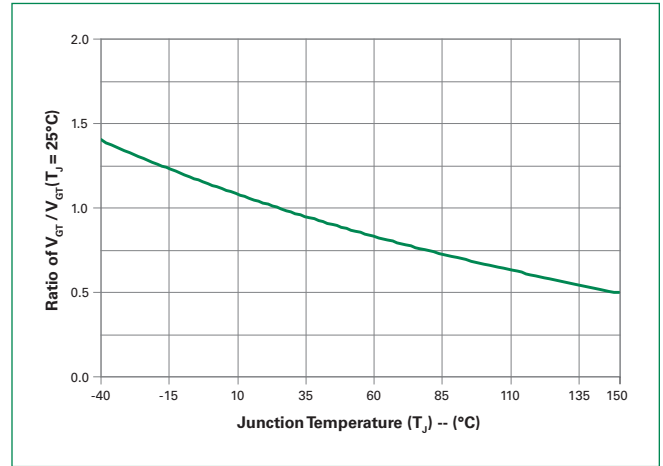


Figure 3: Normalized DC Holding Current vs. Junction Temperature

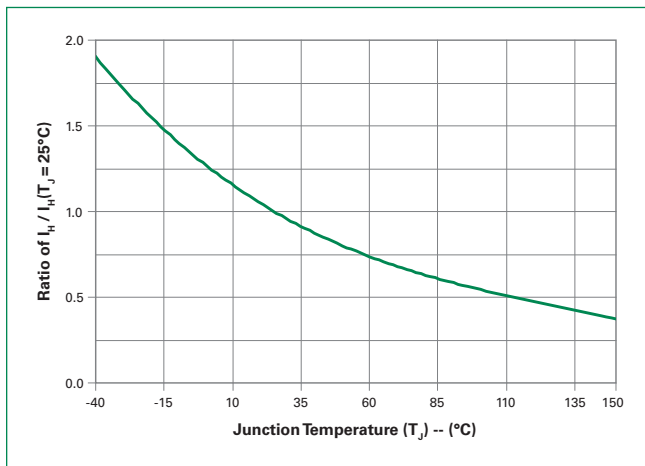


Figure 4: On-State Current vs. On-State Voltage (Typical)

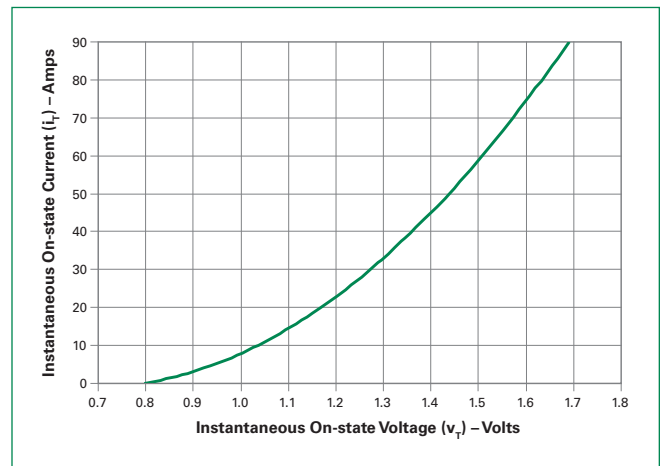


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

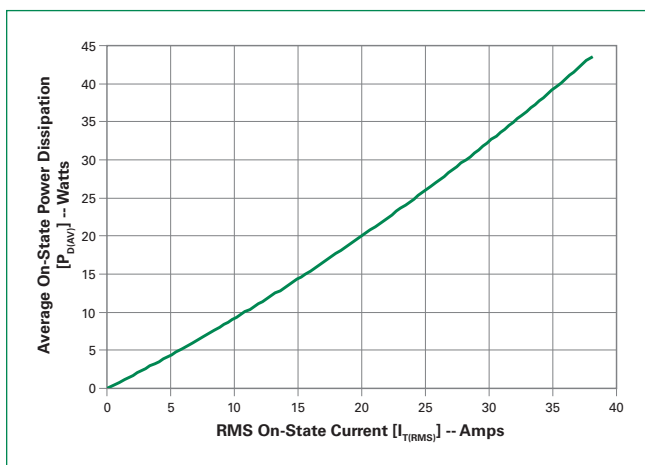


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

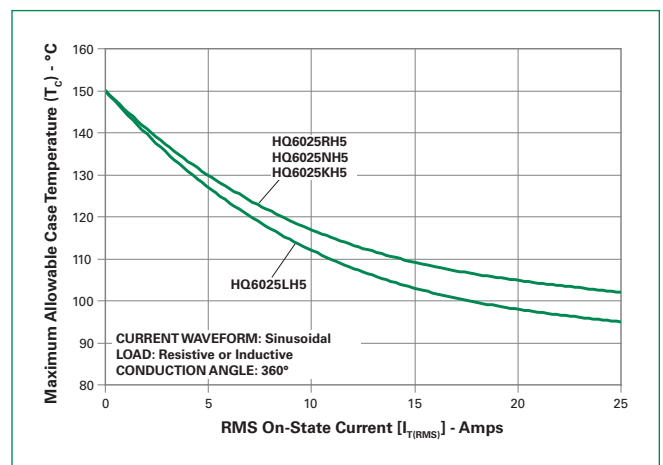


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

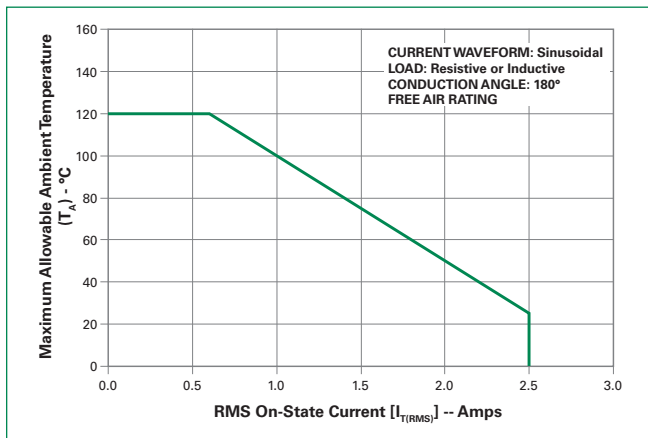
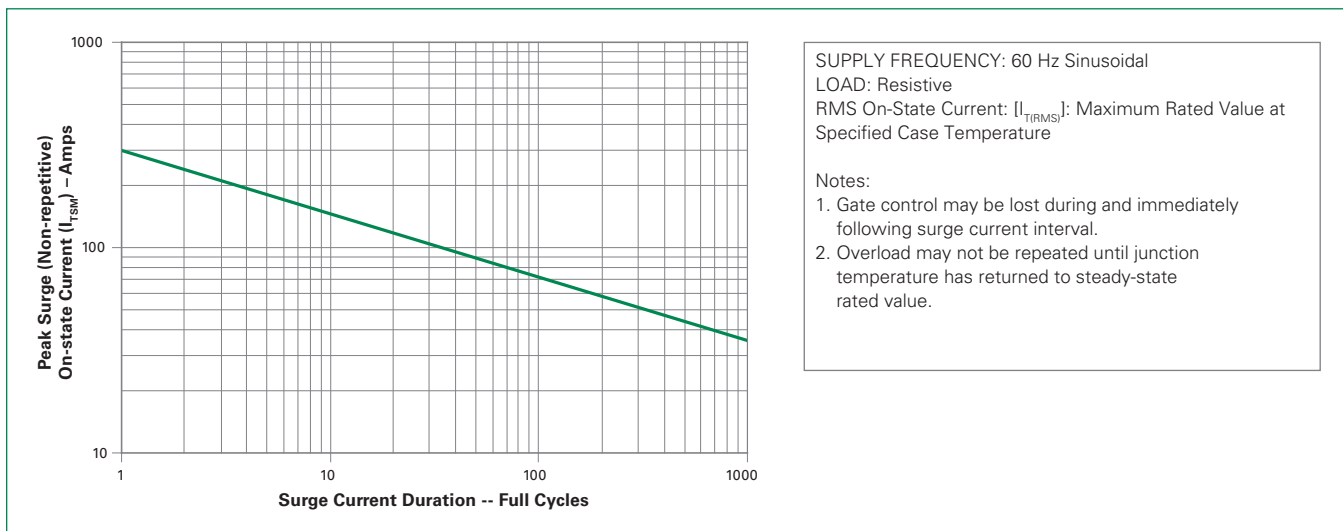
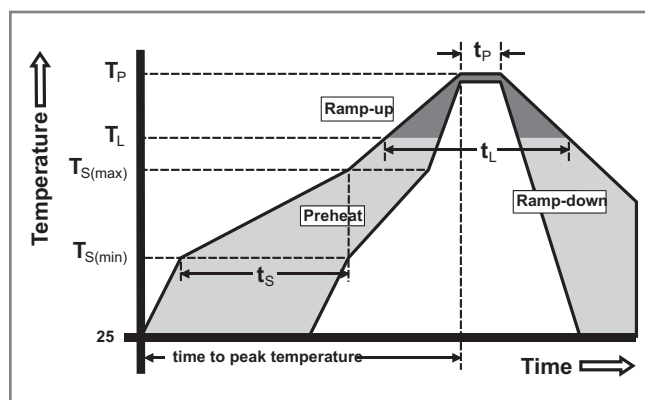


Figure 8: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Material	Copper Alloy
Terminal Finish	100% Matte Tin Plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0

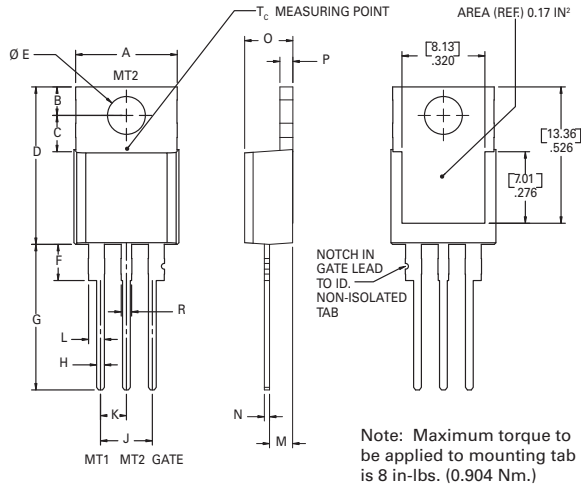
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

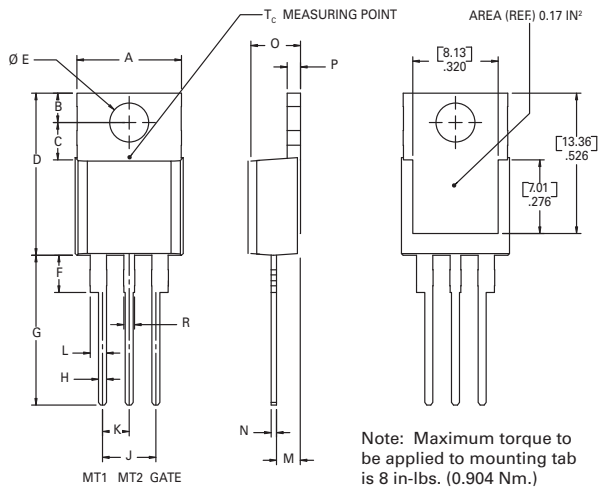
Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{RRM} , 150°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
Biased Temp & Humidity	EIA/JEDEC: JESD22-A101 320VDC, 85°C, 85%RH, 1008 hours
High Temp. Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	-40°C, 1008 hours
Thermal Shock	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002, Category 3, Test A
Lead Bend	MIL-STD-750: Method 2036, Condition E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



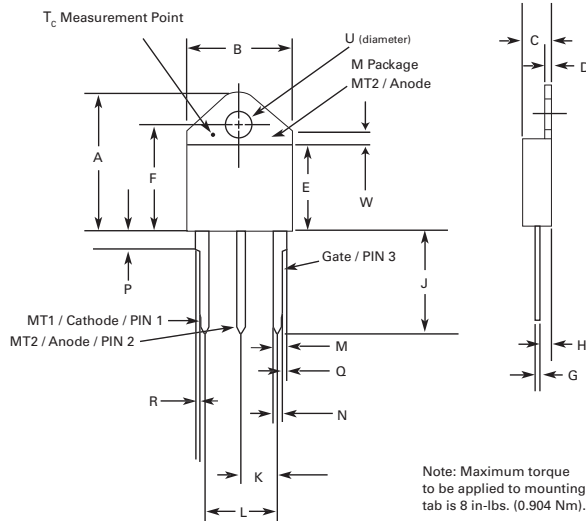
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO- 220AB (L Package) — Isolated Mounting Tab



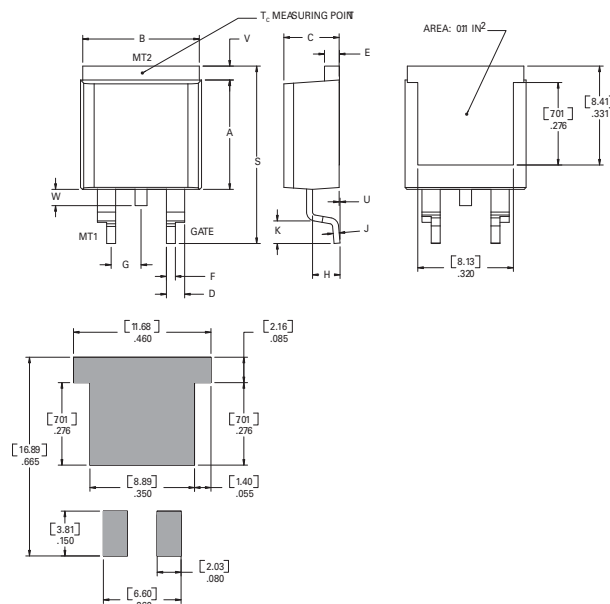
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-218AC (K Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.159	0.163	4.04	4.14
W	0.085	0.095	2.17	2.42

Dimensions — TO-263AB (N-Package) — D² -PAK Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Product Selector

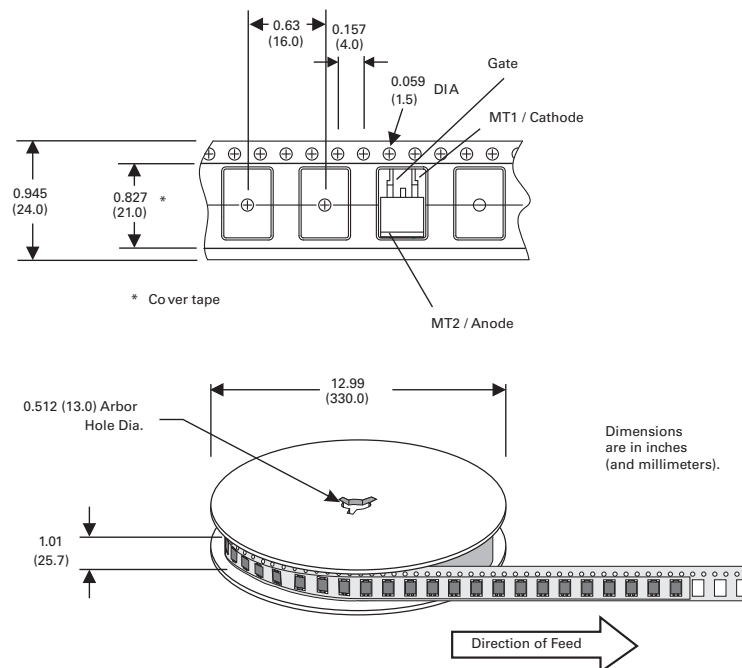
Part Number	Voltage				Gate Sensitivity	Package
	400V	600V	800V	1000V		
HQ6025RH5		X			50 mA	TO-220R
HQ6025NH5		X			50 mA	TO-263
HQ6025LH5		X			50 mA	TO-220L
HQ6025KH5		X			50 mA	TO-218K

Packing Options

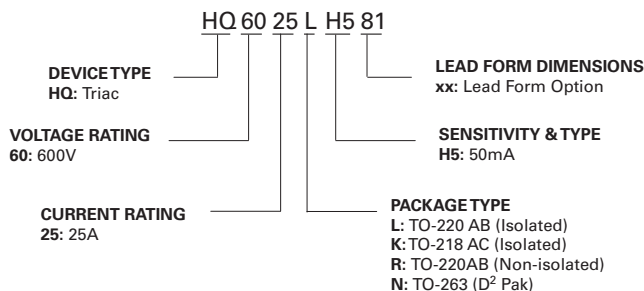
Part Number	Marking	Weight	Packing Mode	Base Quantity
HQ6025RH5	HQ6025RH5	2.2g	Bulk	500
HQ6025RH5TP	HQ6025RH5	2.2g	Tube	500
HQ6025NH5TP	HQ6025NH5	1.6g	Tube	500
HQ6025NH5RP	HQ6025NH5	1.6g	Embossed Carrier	500
HQ6025LH5	HQ6025LH5	2.2g	Bulk	500
HQ6025LH5TP	HQ6025LH5	2.2g	Tube	500
HQ6025KH5	HQ6025KH5	4.4g	Bulk	250
HQ6025KH5TP	HQ6025KH5	4.4g	Tube	500

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



Part Numbering System



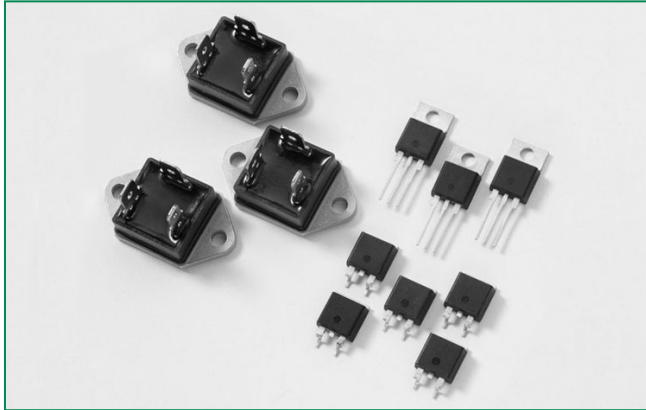
Part Marking System

TO-220AB (R and L Packages) TO-218AC (K Package)
TO-263 (N Package)



RoHS

Qxx30xHx & Qxx35xx & Qxx35xHx Series



Description

30 Amp / 35 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 800V
- Surge capability up to 350A
- Electrically isolated package “FASTPAK” & “L - Package” are UL recognized for 2500Vrms

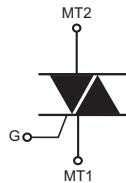
Agency Approval

Agency	Agency File Number
	FASTPAK & L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	30 & 35	A
V_{DRM}/V_{RRM}	400 to 800	V
$I_{GT(Q1)}$	50	mA

Schematic Symbol



Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings – Standard Triac

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	Qxx35P5	T _c = 55°C	35	A
I _{TSM}	Non repetitive surge peak on-state current (full cycle, T _J initial = 25°C)	f = 50 Hz	t = 20 ms	300	A
		f = 60 Hz	t = 16.7 ms	350	
I ² t	I ² t Value for fusing		t _p = 8.3 ms	508	A ² s
di/dt	Critical rate of rise of on-state current (I _G = 200mA with ≤ 0.1μs rise time)	f = 120 Hz	T _J = 125°C	100	A/μs
I _{GTM}	Peak gate trigger current	t _p ≤ 10 μs I _{GT} ≤ I _{GTM}	T _J = 125°C	2	A
P _{G(AV)}	Average gate power dissipation		T _J = 125°C	0.5	W
T _{stg}	Storage temperature range			-40 to 125	°C
T _J	Operating junction temperature range			-25 to 125	°C

Note: xx = voltage

Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx35RH5/Qxx35NH5	$T_C = 90^\circ\text{C}$	35	A
		Qxx30LH5	$T_C = 50^\circ\text{C}$	30	
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	290	A
		f = 60 Hz	t = 16.7 ms	350	
I^2t	I^2t Value for fusing		$t_p = 8.3$ ms	508	A^2s
di/dt	Critical rate of rise of on-state current ($I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_J = 125^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	2	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-25 to 125	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Qxx35P5	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 30 \Omega$	I – II – III	MAX.	50	mA
		IV	TYP.	120	
V_{GT}		I – II – III	MAX.	2.75	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2	V
I_H	$I_T = 400\text{mA}$		MAX.	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	600V	MIN.	475	$\text{V}/\mu\text{s}$
		800V		400	
(dv/dt)c	(di/dt)c = 18.9 A/ms $T_J = 125^\circ\text{C}$		TYP.	5	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 49.5\text{A(pk)}$		TYP.	3	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant		Qxx35RH5 Qxx35NH5 Qxx30LH5	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 30 \Omega$	I – II – III	MAX.	50	mA
		I – II – III	MAX.	2	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2	V
I_H	$I_T = 400\text{mA}$		MAX.	75	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	475	$\text{V}/\mu\text{s}$
		600V		400	
(dv/dt)c	(di/dt)c = 18.9 A/ms $T_J = 125^\circ\text{C}$		MIN.	20	$\text{V}/\mu\text{s}$
t_{gt}	35A device $I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 49.5\text{A(pk)}$		TYP.	3	μs
	30A device $I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 42.4\text{A(pk)}$				

Note: xx = voltage

Static Characteristics

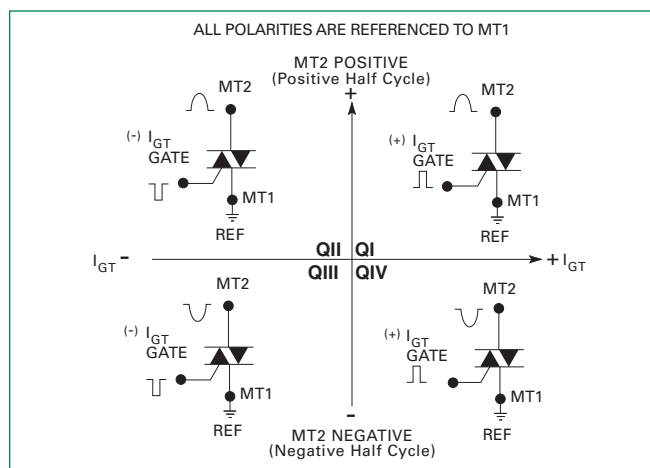
Symbol	Test Conditions					Value	Unit
V _{TM}	35A device I _{TM} = 49.5A t _p = 380 μs				MAX.	1.5	V
	30A device I _{TM} = 42.4A t _p = 380 μs					1.4	
I _{DRM} I _{RRM}	V _D = V _{DRM} /V _{RRM}	Qxx35P5	T _J = 25°C	600 - 800V	MAX.	100	μA
			T _J = 125°C	600 - 800V		5	mA
		Qxx35R/NH5 Qxx30LH5	T _J = 25°C	400 - 600V	MAX.	10	μA
			T _J = 125°C	400 - 600V		2	mA

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx35P5	1.50	$^\circ C/W$
		Qxx35RH5 / Qxx35NH5	0.85	
		Qxx30LH5	2.30	
$R_{\theta(J-A)}$	Junction to ambient	Qxx35RH5	45	$^\circ C/W$
		Qxx30LH5	50	

Note: xx = voltage

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

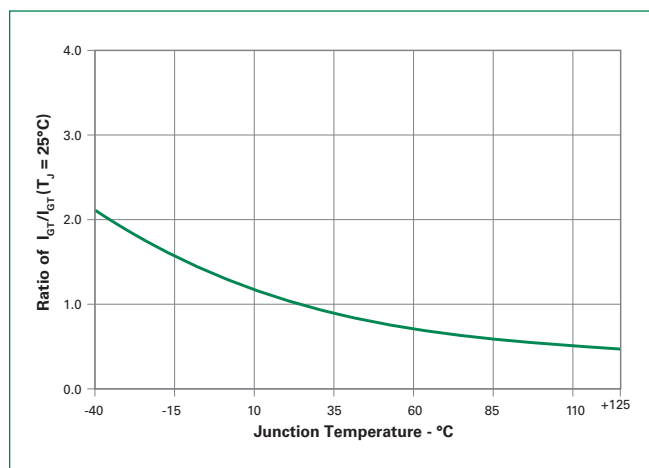


Figure 3: Normalized DC Holding Current vs. Junction Temperature

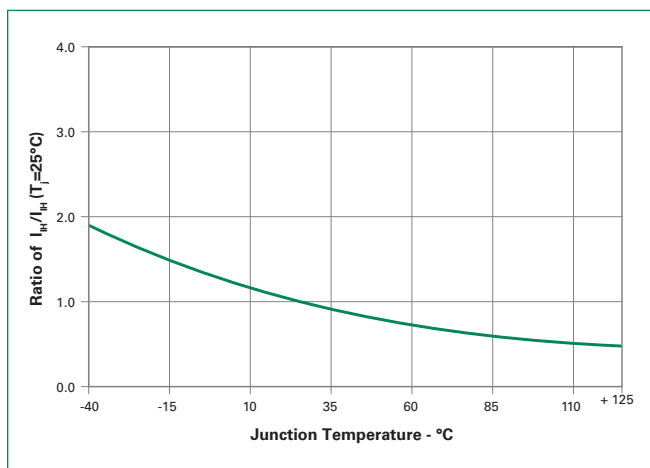


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

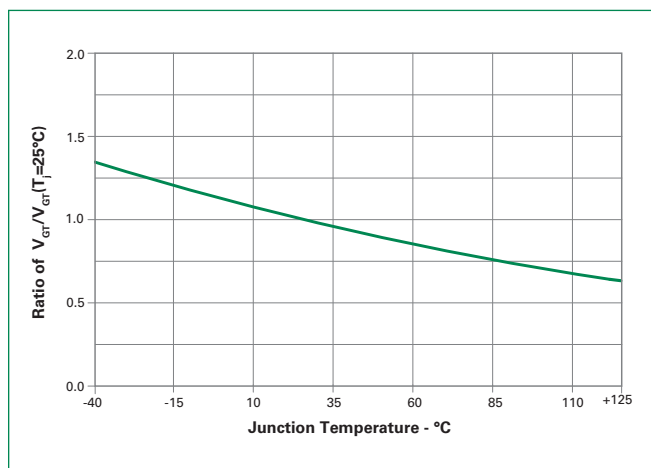


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

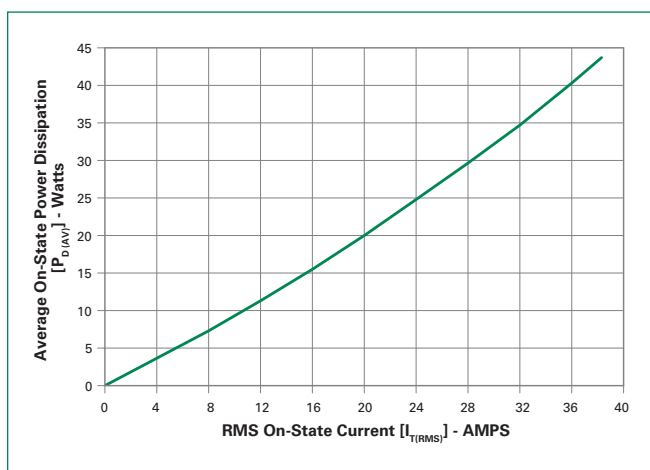
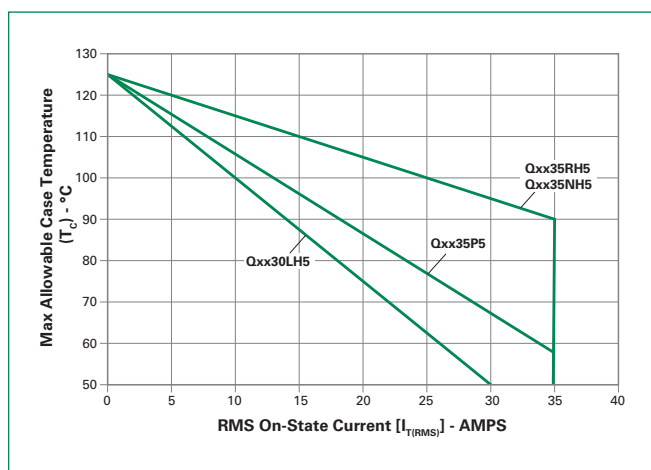


Figure 6: Maximum Allowable Case Temperature vs. On-State Current



Note: xx = voltage

Figure 7: On-State Current vs. On-State Voltage (Typical)

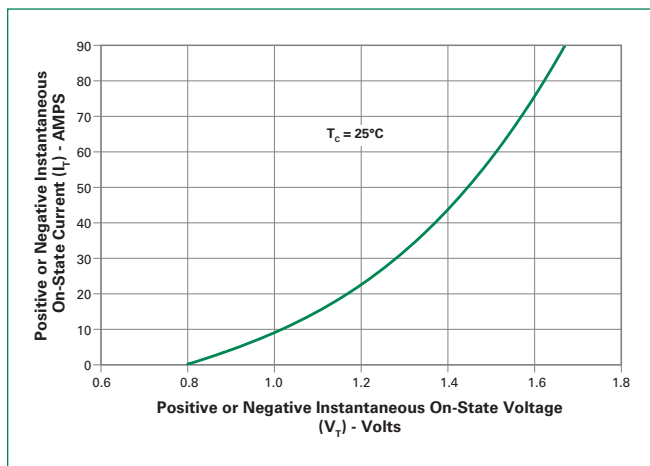
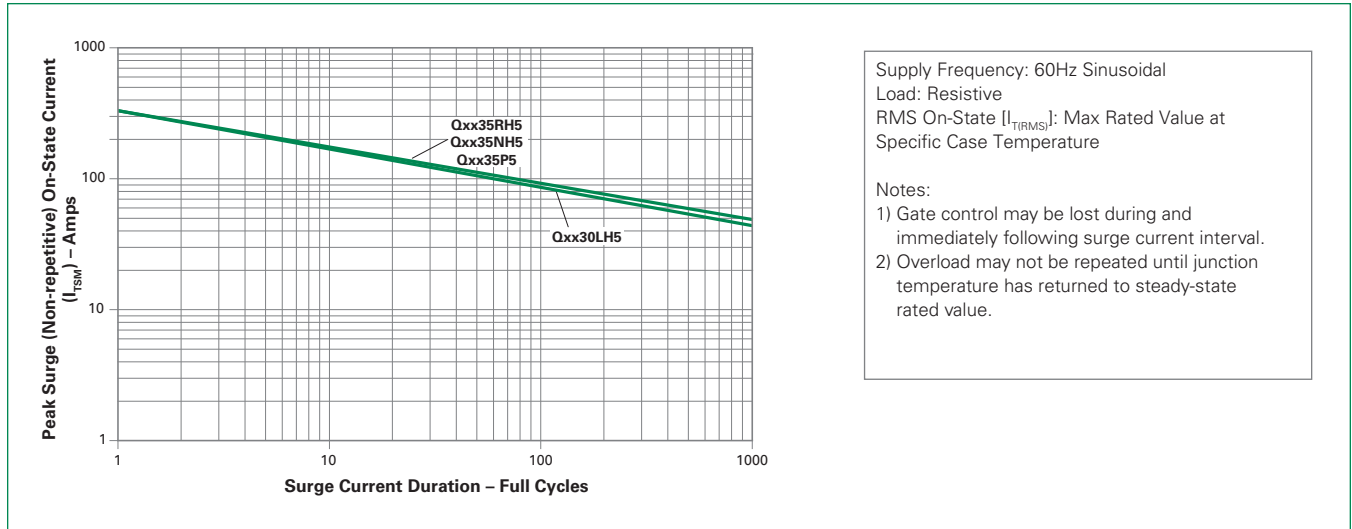


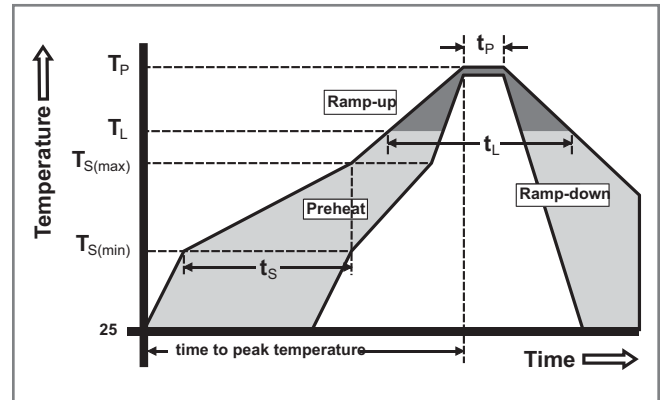
Figure 8: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Terminal Material	Copper Alloy

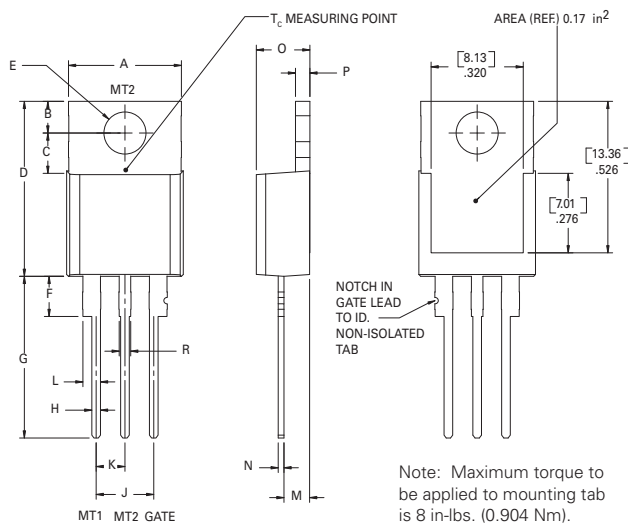
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

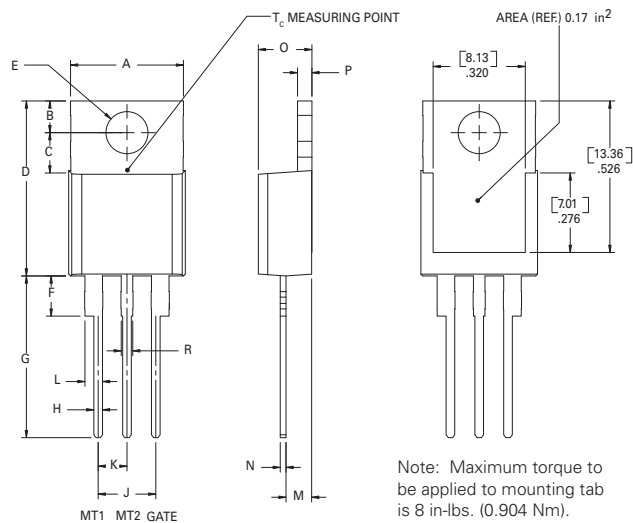
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

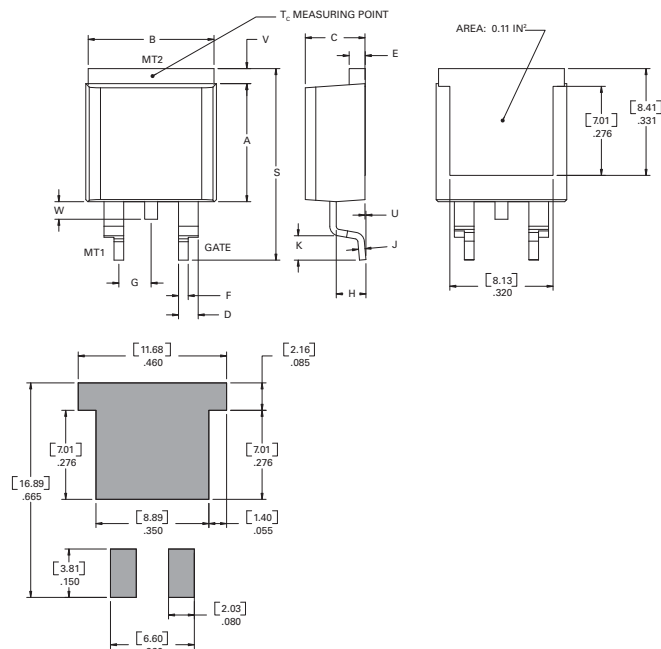
Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

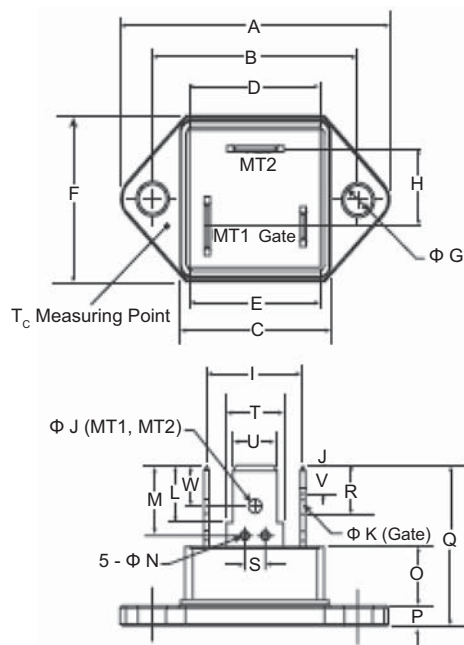
30/35 A TRIACS

Dimensions — TO-263 (N-Package) — D² Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.016	1.78

Dimensions — TO-3 Fastpak (P Package) — Isolated Mounting Tab



Thickness of all three copper-alloy terminals is .032" (0.81mm)

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	1.531	1.543	38.90	39.20
B	1.177	1.185	29.90	30.10
C	0.843	0.850	21.40	21.60
D	0.780	0.795	19.80	20.20
E	0.783	0.791	19.90	20.10
F	0.874	0.906	22.20	23.00
G	0.161	0.169	4.10	4.30
H	0.386	0.465	9.80	11.80
I	0.508	0.587	12.90	14.90
J	0.079	0.087	2.00	2.20
K	0.047	0.055	1.20	1.40
L	0.307	0.319	7.80	8.10
M	0.372	0.396	9.45	10.05
N	0.043	0.059	1.10	1.50
O	0.315	0.331	8.00	8.40
P	0.098	0.106	2.50	2.70
Q	0.846	0.886	21.50	22.50
R	0.244	0.256	6.20	6.50
S	0.106	0.130	2.70	3.30
T(MT1)	0.321	0.329	8.15	8.35
T(MT2)	0.321	0.329	8.15	8.35
T(Gate)	0.220	0.228	5.60	5.80
U(MT1)	0.246	0.254	6.25	6.45
U(MT2)	0.246	0.254	6.25	6.45
U(Gate)	0.183	0.191	4.65	4.85
V	0.120	0.130	3.05	3.30
W	0.175	0.185	4.45	4.70

Maximum torque to be applied to mounting tab is 8 in-lbs (0.904 Nm)

Product Selector

Part Number	Voltage			Gate Sensitivity Quadrants		$I_{T(RMS)}$	Type	Package
	400V	600V	800V	I – II – III	IV			
Qxx35P5		X	X	50 mA	120 mA (TYP)	35A	Standard Triac	FASTPACK
Qxx35RH5	X	X		50 mA		35A	Alternistor Triac	TO-220R
Qxx35NH5	X	X		50 mA		35A	Alternistor Triac	TO-263 D ² -PAK
Qxx30LH5	X	X		50 mA		30A	Alternistor Triac	TO-220L

Note: xx = Voltage

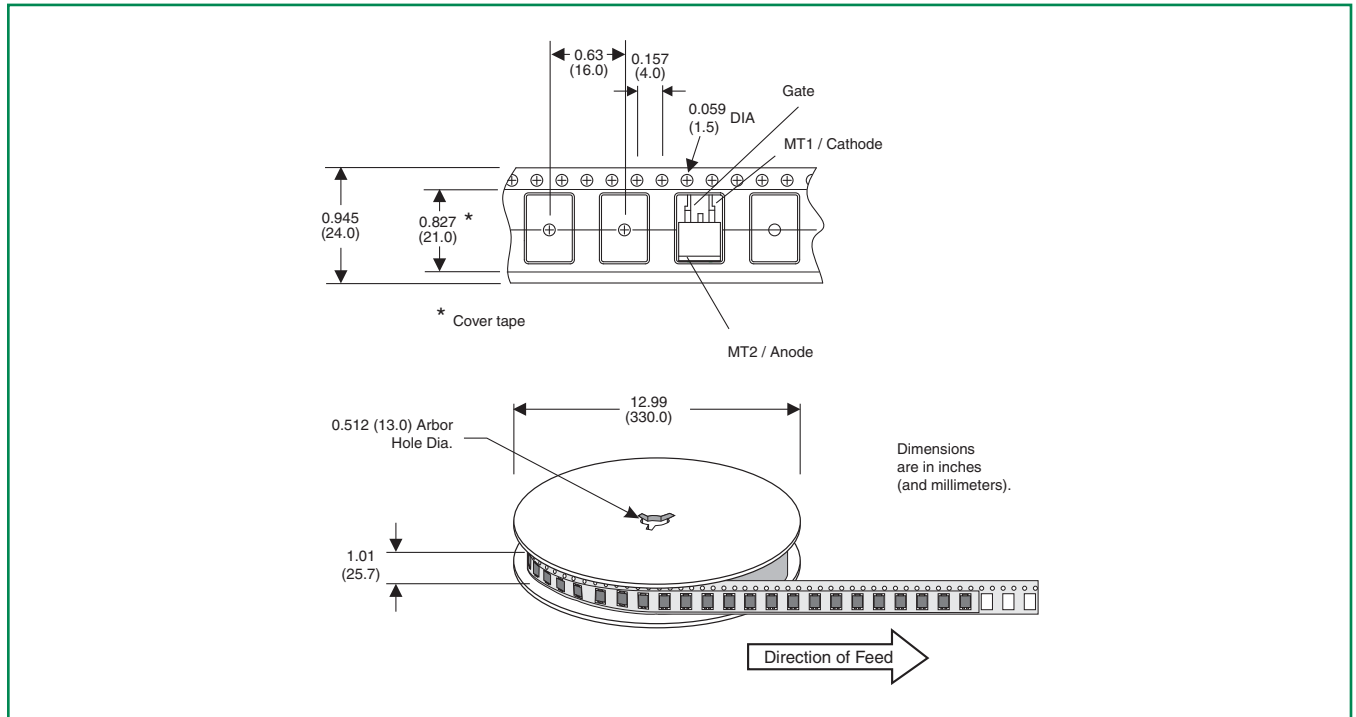
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx30LH5	Qxx30LH5	2.20 g	Bulk	500
Qxx30LH5TP	Qxx30LH5	2.20 g	Tube	500
Qxx35RH5	Qxx35LH5	2.20 g	Bulk	500
Qxx35RH5TP	Qxx35LH5	2.20 g	Tube	500
Qxx35NH5TP	Qxx35LH5	1.60 g	Tube	500
Qxx35NH5RP	Qxx35LH5	1.60 g	Embossed Carrier	500
Qxx35P5	Qxx35P5	21.4 g	Bulk	200

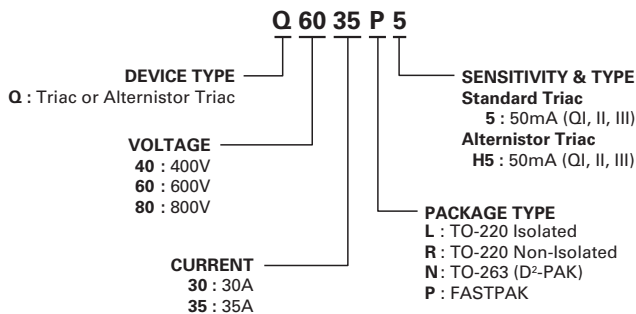
Note: xx = Voltage

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



Part Numbering System

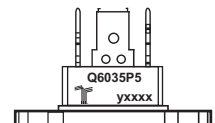


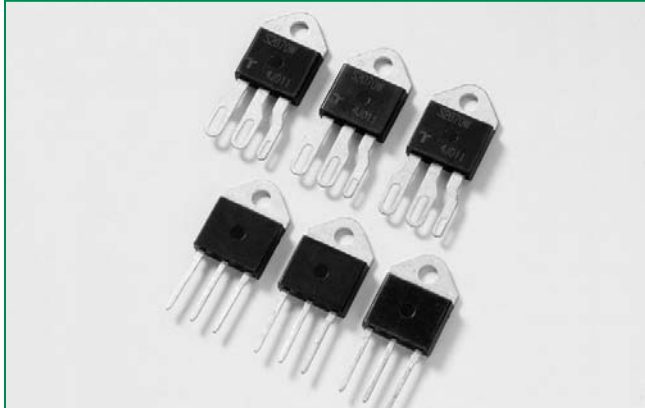
Part Marking System

TO-220 AB (R and L Packages)
TO-263 (N Package)



FASTPAK (P Package)





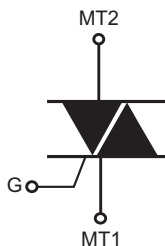
Agency Approval

Agency	Agency File Number
	K & J Packages: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	80 to 100	mA

Schematic Symbol



Description

40 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000V
- Surge capability up to 400A
- Electrically isolated K & J -Packages are UL recognized for 2500Vrms

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx40x7 Qxx40xH6	$T_c = 75^\circ\text{C}$	40	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	335	A
		f = 60 Hz	t = 16.7 ms	400	
I^2t	I^2t Value for fusing		$t_p = 8.3$ ms	664	A^2s
di/dt	Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$, tr ≤ 100 ns)	f = 120 Hz	$T_J = 125^\circ\text{C}$	150	A/μs
I_{GTM}	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.8	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, x = package

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant		Value		Unit
				Qxx40xH6	Qxx40x7	
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	80	100	mA
V_{GT}		I – II – III	MAX.	1.3	2.0	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2		V
I_H	$I_T = 400\text{mA}$		MAX.	80	100	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	600	700	V/μs
		600V		500	625	
		800V		475	575	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V			500	
(dv/dt)c	(di/dt)c = 21.6 A/μs $T_J = 125^\circ\text{C}$		MIN.	30	50	V/μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15μs $I_T = 56.6\text{A(pk)}$		TYP.	5		μs

Static Characteristics

Symbol	Test Conditions			Value	Unit
V_{TM}	$I_{TM} = 56.6\text{A}$ $t_p = 380 \mu\text{s}$	$T_J = 25^\circ\text{C}$	MAX.	1.8	V
I_{DRM} / I_{RRM}	$V_D = V_{DRM} / V_{RRM}$	$T_J = 25^\circ\text{C}$	400 – 1000V	20	μA
		$T_J = 125^\circ\text{C}$	400 – 800V	5	mA
		$T_J = 100^\circ\text{C}$	1000V	5	mA

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx40KH6 Qxx40K7	0.97	$^\circ\text{C/W}$
		Qxx40JH6 Qxx40J7	0.95	

Note: xx = voltage

Figure 1: Definition of Quadrants

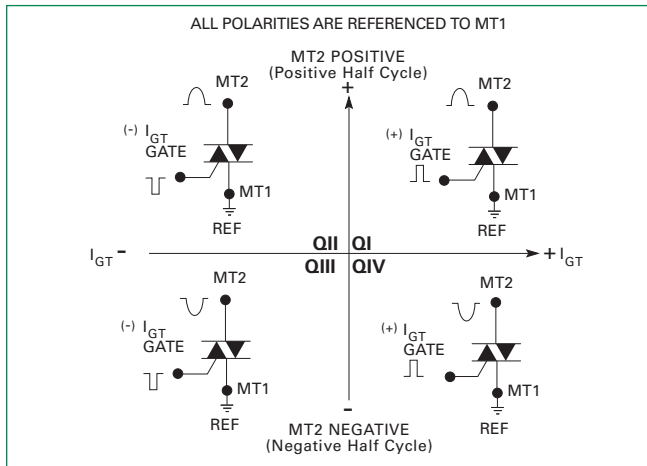


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

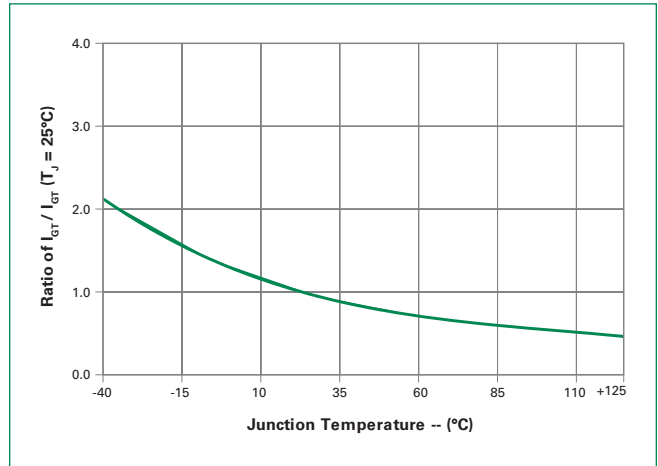


Figure 3: Normalized DC Holding Current vs. Junction Temperature

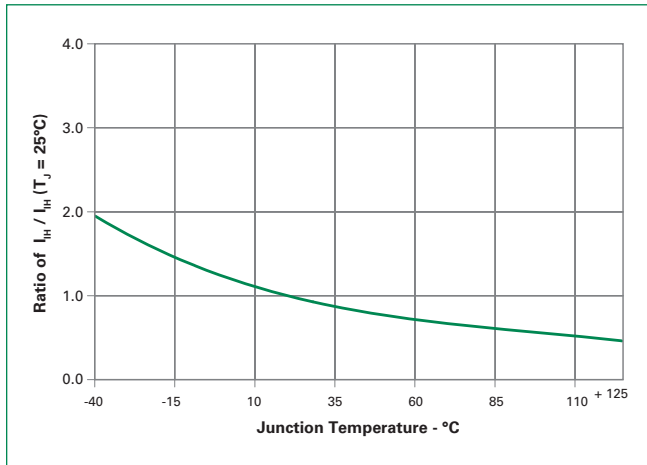


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

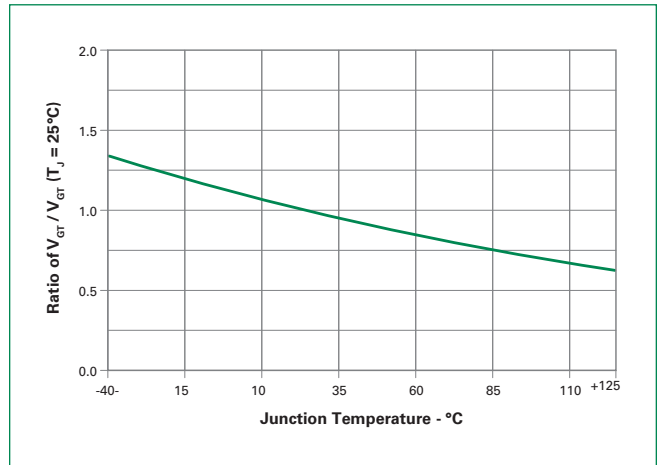


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

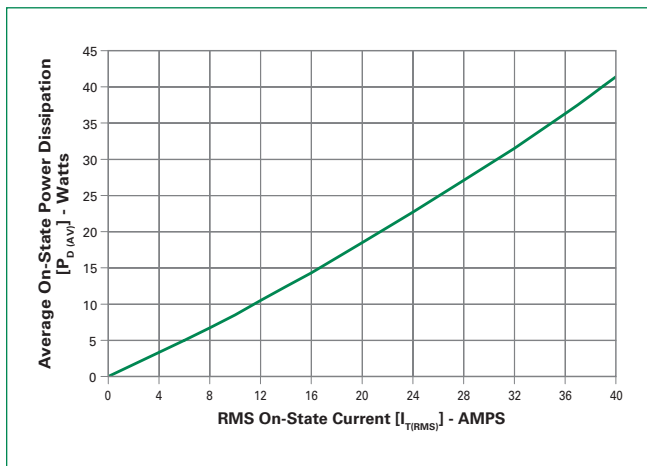


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

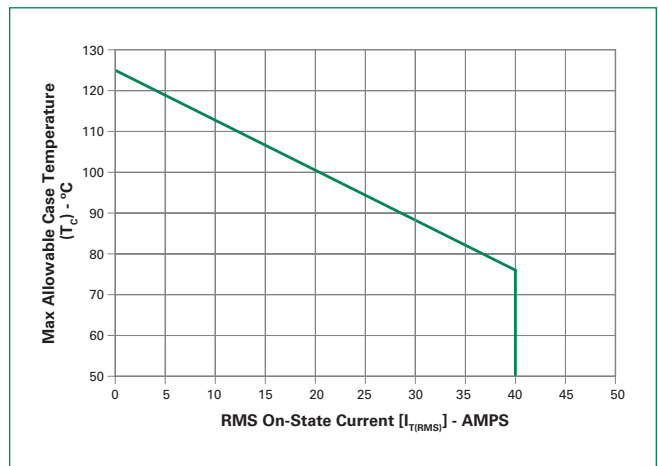


Figure 7: On-State Current vs. On-State Voltage (Typical)

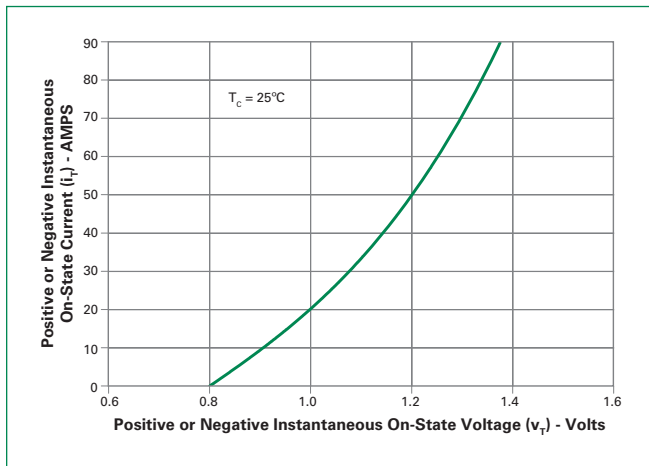
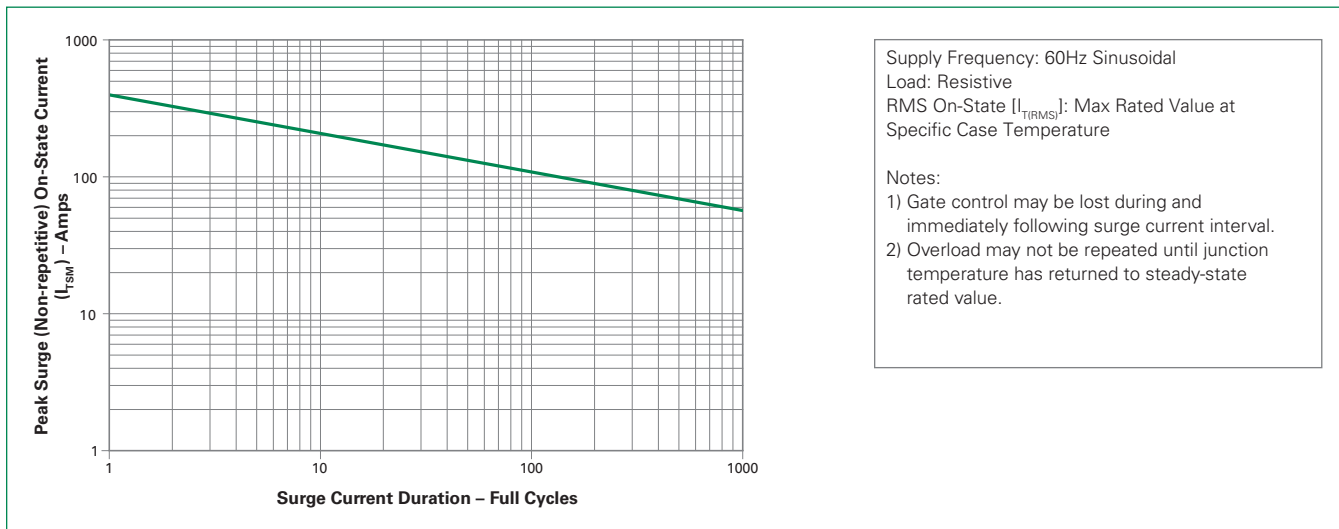


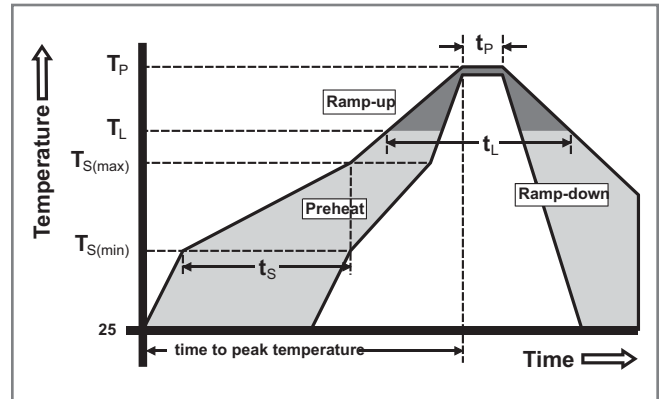
Figure 8: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Lead Material	Copper Alloy

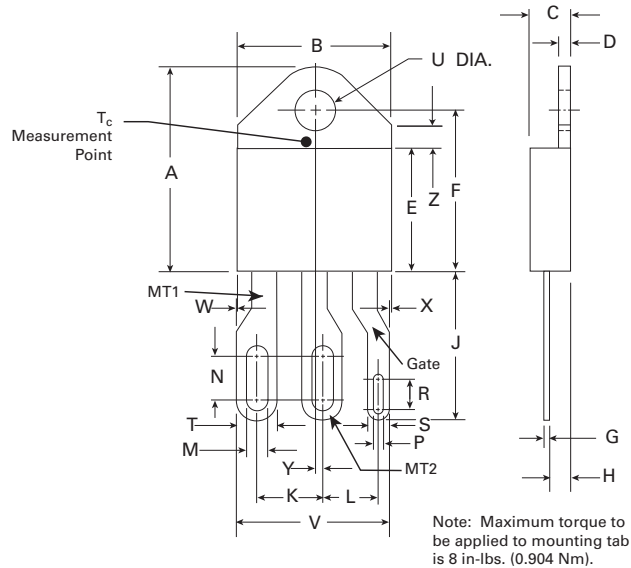
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

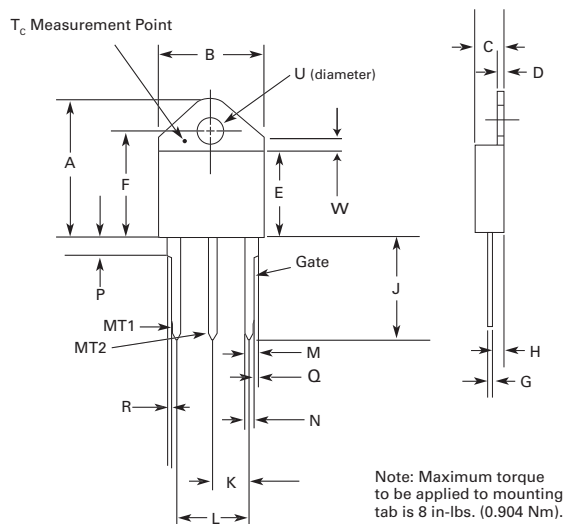
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-218X (J Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Dimensions — TO-218AC (K Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.164	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

Product Selector

Part Number	Voltage				Gate Sensitivity Quadrants		$I_{T(RMS)}$	Type	Package
	400V	600V	800V	1000V	I – II – III	IV			
Qxx40KH6	X	X	X	X	80mA		40A	Alternistor Triac	TO-218AC
Qxx40JH6	X	X	X		80mA		40A	Alternistor Triac	TO-218X
Qxx40K7	X	X	X	X	100 mA		40A	Alternistor Triac	TO-218AC
Qxx40J7	X	X	X		100 mA		40A	Alternistor Triac	TO-218X

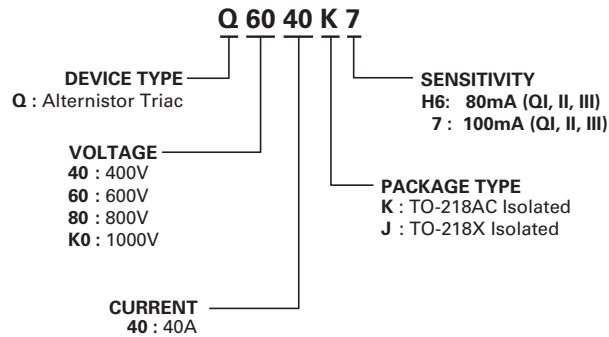
Note: xx = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx40KH6	Qxx40KH6	4.40g	Bulk	250
Qxx40KH6TP	Qxx40KH6	4.40g	Tube	500
Qxx40JH6	Qxx40JH6	5.23g	Bulk	250
Qxx40JH6TP	Qxx40JH6	5.23g	Tube	500
Qxx40K7	Qxx40K7	4.40g	Bulk	250
Qxx40K7TP	Qxx40K7	4.40g	Tube	500
Qxx40J7	Qxx40J7	5.23g	Bulk	250
Qxx40J7TP	Qxx40J7	5.23g	Tube	500

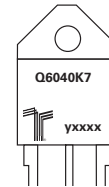
Note: xx = Voltage

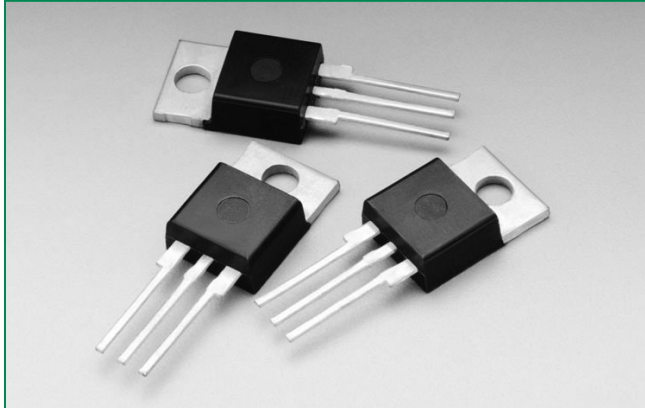
Part Numbering System




Part Marking System

TO-218 AC (K Package)
TO-218 X – (J Package)

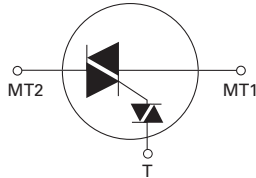




Agency Approval

Agency	Agency File Number
	L Package : E71639

Schematic Symbol



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	4 to 15	A
V_{DRM} / V_{RRM}	400 to 600	V
DIAC V_{BO}	33 to 43	V

Description

The Quadrac is an internally triggered Triac designed for AC switching and phase control applications. It is a Triac and DIAC in a single package, which saves user expense by eliminating the need for separate Triac and DIAC components.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type Quadacs are used in circuits requiring high dv/dt capability.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 200 A

Applications

Excellent for AC switching and phase control applications such as lighting and heating. Typical applications are AC solid-state switches, light dimmers, power tools, home/ brown goods and white goods appliances.

Alternistor Quadacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated package is offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings

Symbol	Parameter		Value					Unit
			Qxx04LT	Qxx06LT / Qxx06LTH	Qxx08LT / Qxx08LTH	Qxx10LT / Qxx10LTH	Qxx15LT / Qxx15LTH	
I _{T(RMS)}	RMS forward current	Qxx04LT: T _C = 95°C Qxx06LT/Qxx08LT/Qxx10LT: T _C = 90°C Qxx15LT: T _C = 80°C	4	6	8	10	15	A
I _{TSM}	Peak non-repetitive surge current	single half cycle; f = 50Hz; T _J (initial) = 25°C	46	65	83	100	167	A
		single half cycle; f = 60Hz; T _J (initial) = 25°C	55	80	100	120	200	
I ² t	I ² t value for fusing	t _p = 8.3ms	12.5	26.5	41	60	166	A²s
di/dt	Critical rate-of-rise of on-state current	f = 60Hz; T _J =125°C	50	70			100	A/μs
I _{GM}	Peak gate current	T _J = 125°C	1.5					A
T _{stg}	Storage temperature range		-40 to 150					°C
T _J	Operating junction temperature range		-40 to 125					°C

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) – Standard Quadrac

Symbol	Test Conditions		Value					Unit
			Qxx04LT	Qxx06LT	Qxx08LT	Qxx10LT	Qxx15LT	
I _H	I _T = 200mA (initial)	MAX.	40	50	60	60	70	mA
dv/dt	V _D = V _{DRM} ; gate open; T _J =100°C	MIN.	400V	75	150	175	200	V/μs
			600V	50	125	150	175	
	V _D = V _{DRM} ; gate open; T _J =125°C	MIN.	400V	50	100	120	150	
			600V	50	85	100	120	
dv/dt(c)	di/dt(c) = 0.54 x I _{T(rms)} / ms; T _J = 125°C	MIN.	3	4				V/μs
t _{gt}	(note 1)	TYP.	3					μs

(1) Reference test circuit in figure 10 and waveform in figure 11; $C_T = 0.1\mu\text{F}$ with 0.1 μs rise time.

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) – Alternistor Quadrac

Symbol	Test Conditions		Value				Unit
			Qxx06LTH	Qxx08LTH	Qxx10LTH	Qxx15LTH	
I_H	$I_T = 20\text{mA}$ (initial)	MAX.	50	50	60	70	mA
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^\circ\text{C}$	MIN.	400V	575	925		$\text{V}/\mu\text{s}$
			600V	425	775		
	$V_D = V_{DRM}$; gate open; $T_J = 125^\circ\text{C}$	MIN.	400V	450	700		
			600V	350	600		
$dv/dt(c)$	$di/dt(c) = 0.54 \times I_{T(rms)} / \text{ms}$; $T_J = 125^\circ\text{C}$	MIN.	25		30		$\text{V}/\mu\text{s}$
t_{gt}	(note 1)	TYP.	3				μs

(1) Reference test circuit in figure 10 and waveform in figure 11; $C_T = 0.1\mu\text{F}$ with 0.1 μs rise time.

Note: xx = voltage

Trigger DIAC Specifications

Symbol	Test Conditions		Value	Unit
ΔV_{BO}	Breakover Voltage Symmetry	MAX.	3	V
V_{BO}	Breakover Voltage, forward and reverse	MIN.	33	V
		MAX.	43	
$[\Delta V_{\pm}]$	Dynamic Breakback Voltage, forward and reverse (note 1)	MIN.	5	V
I_{BO}	Peak Breakover Current	MAX.	25	uA
C_T	Trigger Firing Capacitance	MAX.	0.1	μF

(1) Reference test circuit in figure 10 and waveform in figure 11.

Static Characteristics

Symbol	Test Conditions		Value	Unit
V_{TM}	$I_T = 1.41 \times I_{T(rms)}$ A; $t_p = 380\mu s$	MAX.	1.6	V
I_{DRM} / I_{RRM}	V_{DRM} / V_{RRM}	$T_J = 25^\circ C$	10	μA
		$T_J = 100^\circ C$	500	
		$T_J = 125^\circ C$	2000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx04LT	3.6	°C/W
		Qxx06LT / Qxx06LTH	3.3	
		Qxx08LT / Qxx08LTH	2.8	
		Qxx10LT / Qxx10LTH	2.6	
		Qxx15LT / Qxx15LTH	2.1	
$R_{\theta(J-A)}$	Junction to ambient		50	°C/W

Note : xx = voltage

Figure 1: Normalized DC Holding Current vs. Junction Temperature

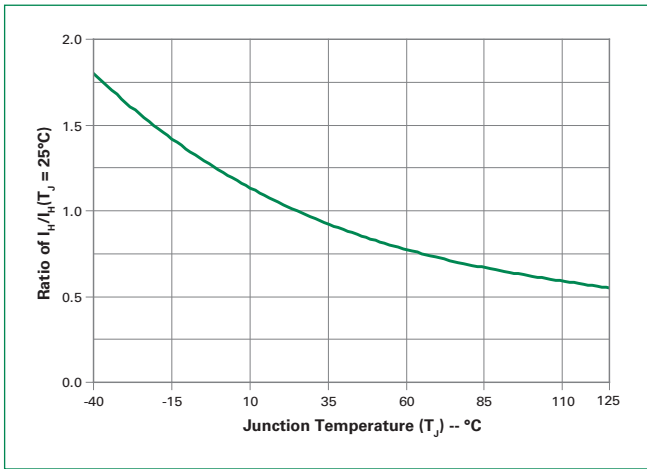


Figure 2: On-State Current vs. On-State Voltage (Typical) (4A)

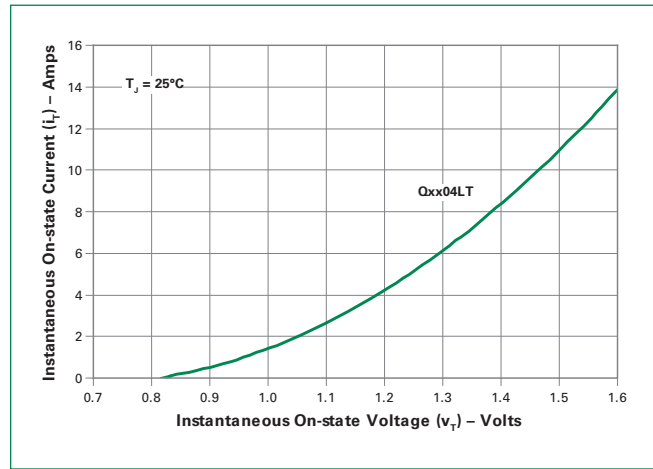


Figure 3: On-State Current vs. On-State Voltage (Typical) (6A to 15A)

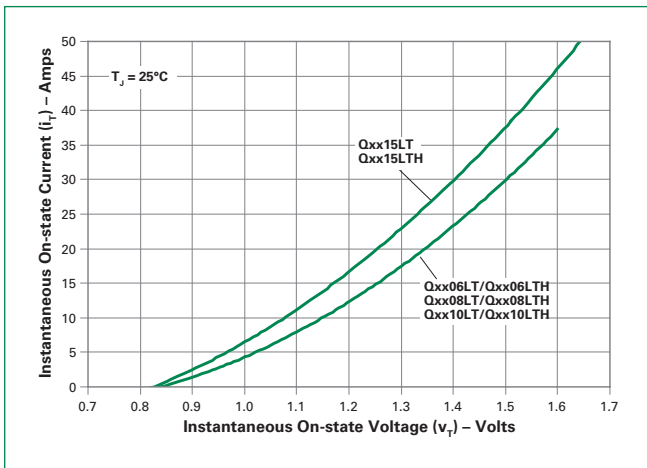


Figure 4: Power Dissipation vs. RMS On-State Current (Typical) (4A)

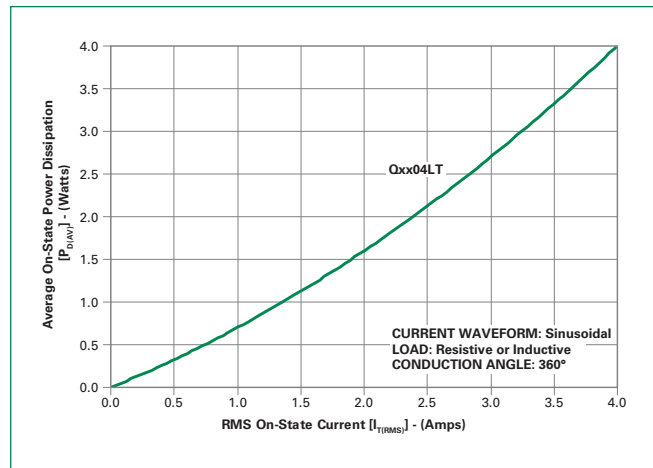


Figure 5: Power Dissipation vs. RMS On-State Current (Typical) (6A to 15A)

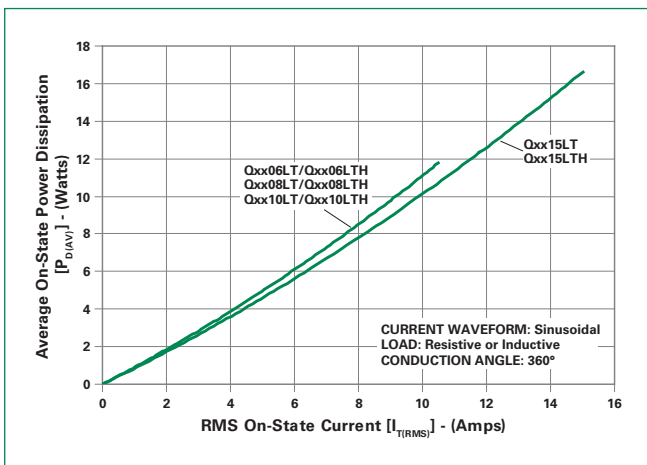


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

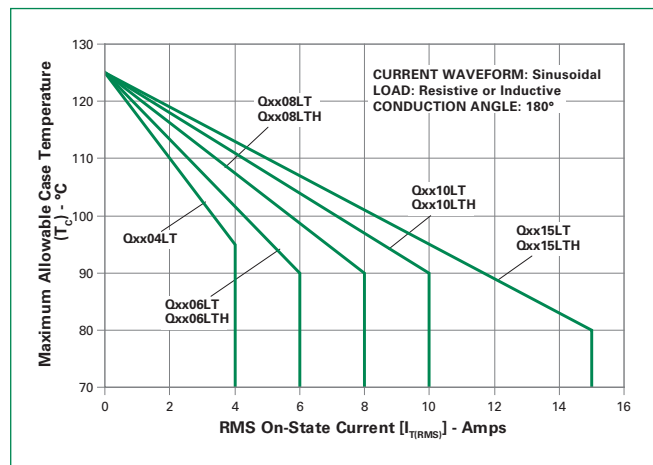
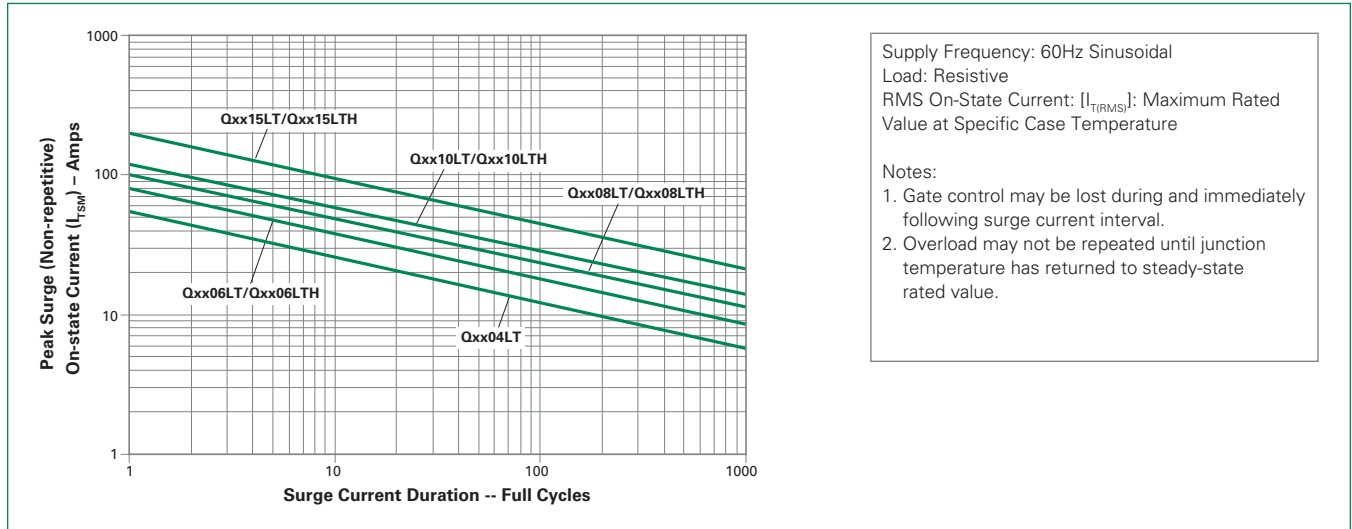


Figure 7: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage

Figure 8: DIAC V_{BO} Change vs. Junction Temperature

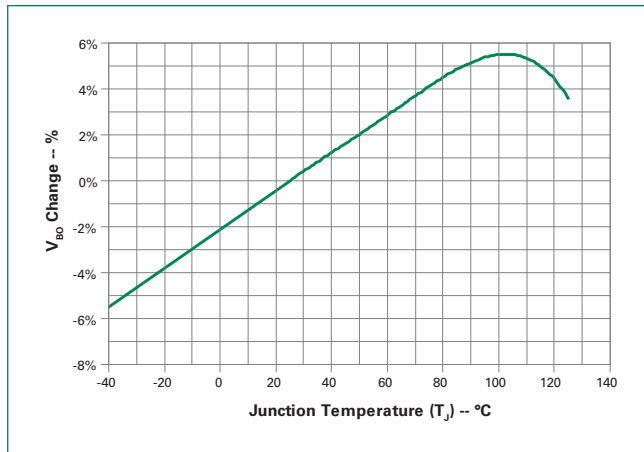


Figure 9: Test Circuit

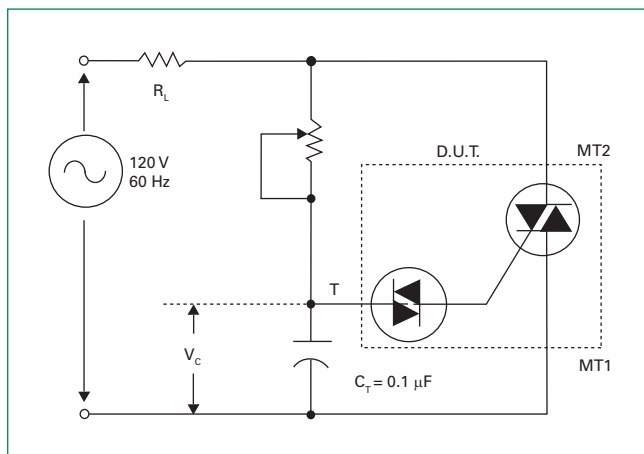
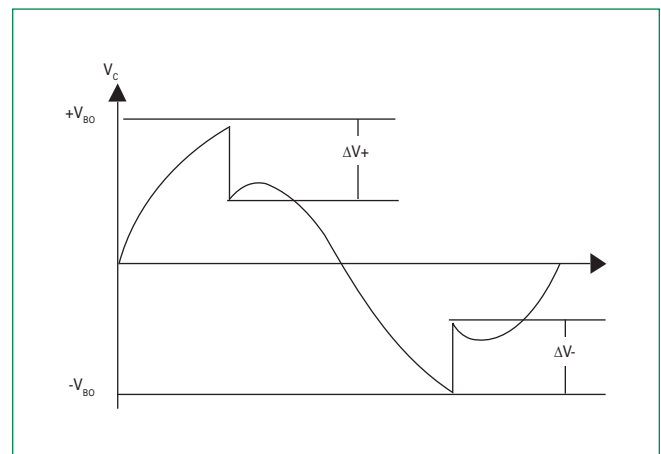
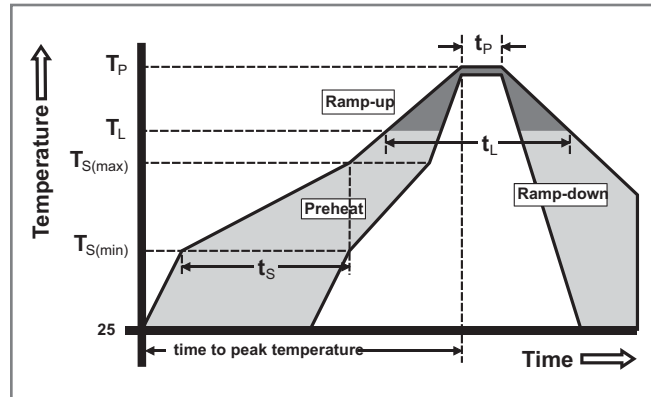


Figure 10: Test Circuit Waveform



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260°C $+0/-5$
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	1005 Matte Tin-plated
Body Material	UL Recognized epoxy meeting flammability classification 94-0
Lead Material	Copper Alloy

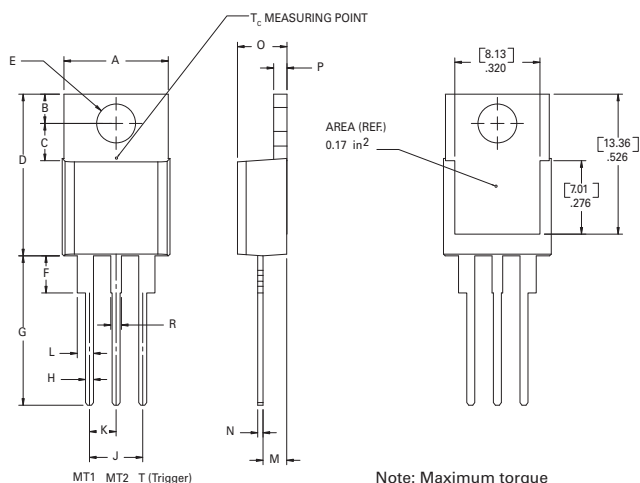
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{DRM} (VAC-peak), 125°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
Biased Temperature & Humidity	EIA/JEDEC: JESD22-A101 320VDC, 85°C, 85%RH, 1008 hours
High Temp Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	-40°C, 1008 hours
Thermal Shock	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002, Category 3, Test A
Lead Bend	MIL-STD-750: Method 2036, Condition E

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Product Selector

Part Number	Voltage				Type	Package
	400V	600V	800V	1000V		
Qxx04LT	X	X			Quadrac	TO-220L
Qxx06LT	X	X			Quadrac	TO-220L
Qxx06LTH	X	X			Alternistor Quadrac	TO-220L
Qxx08LT	X	X			Quadrac	TO-220L
Qxx08LTH	X	X			Alternistor Quadrac	TO-220L
Qxx10LT	X	X			Quadrac	TO-220L
Qxx10LTH	X	X			Alternistor Quadrac	TO-220L
Qxx15LT	X	X			Quadrac	TO-220L
Qxx15LTH	X	X			Alternistor Quadrac	TO-220L

Note: xx = Voltage

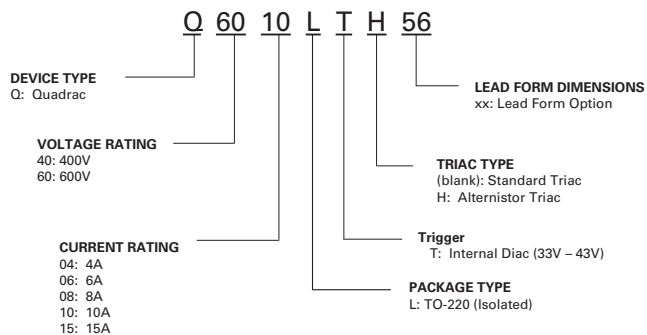
4/6/8/10/15 A QUADRACS

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx04LT	Qxx04LT	2.2 g	Bulk	500
Qxx04LTTP	Qxx04LT	2.2 g	Tube	500
Qxx06LT	Qxx06LT	2.2 g	Bulk	500
Qxx06LTTP	Qxx06LT	2.2 g	Tube	500
Qxx06LTH	Qxx06LTH	2.2 g	Bulk	500
Qxx06LTHTP	Qxx06LTH	2.2 g	Tube	500
Qxx08LT	Qxx08LT	2.2 g	Bulk	500
Qxx08LTTP	Qxx08LT	2.2 g	Tube	500
Qxx08LTH	Qxx08LTH	2.2 g	Bulk	500
Qxx08LTHTP	Qxx08LTH	2.2 g	Tube	500
Qxx10LT	Qxx10LT	2.2 g	Bulk	500
Qxx10LTTP	Qxx10LT	2.2 g	Tube	500
Qxx10LTH	Qxx10LTH	2.2 g	Bulk	500
Qxx10LTHTP	Qxx10LTH	2.2 g	Tube	500
Qxx15LT	Qxx15LT	2.2 g	Bulk	500
Qxx15LTTP	Qxx15LT	2.2 g	Tube	500
Qxx15LTH	Qxx15LTH	2.2 g	Bulk	500
Qxx15LTHTP	Qxx15LTH	2.2 g	Tube	500

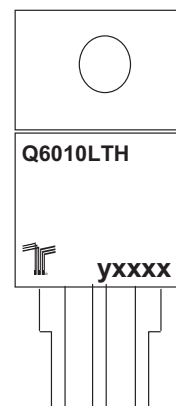
Note: xx = Voltage

Part Numbering System

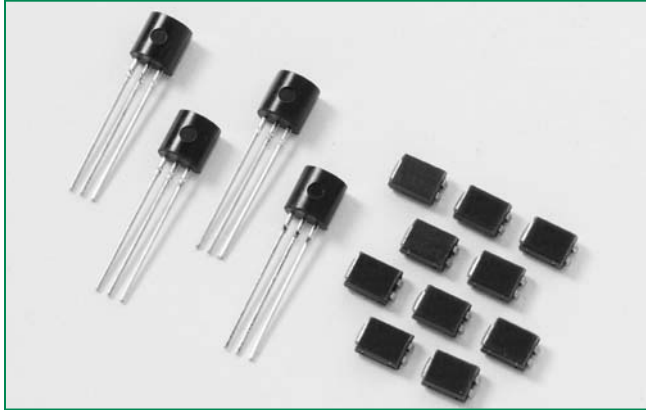


Part Marking System

TO-220AB (L Package)



RoHS EC103xx & SxSx Series



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Sensitive gate SCRs are easily triggered with microAmps of current as furnished by sense coils, proximity switches, and microprocessors.

Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 20 A

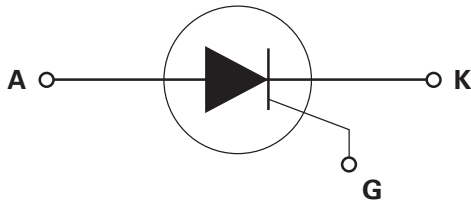
Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	400 to 600	V
I_{GT}	12 to 500	μA

Applications

Typical applications are capacitive discharge systems for strobe lights and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Schematic Symbol



Absolute Maximum Ratings – Sensitive SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 75^\circ C$	0.8	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j(\text{initial}) = 25^\circ C$	16	A
		single half cycle; $f = 60\text{Hz}$; $T_j(\text{initial}) = 25^\circ C$	20	
I^2t	I^2t Value for fusing	$t_p = 8.3\text{ ms}$	1.6	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{ Hz}$; $T_j = 110^\circ C$	50	$A/\mu s$
I_{GM}	Peak gate current	$T_j = 110^\circ C$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 110^\circ C$	0.1	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ C$
T_j	Operating junction temperature range		-40 to 110	$^\circ C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value				Unit
				SxS1 EC103X1	SxS2 EC103X2	SxS EC103X	SxS3 EC103X3	
I_{GT}	$V_D = 12\text{V}; R_L = 60\ \Omega$		MAX.	12	50	200	500	μA
V_{GT}			MAX.	0.8				V
dv/dt	$V_D = V_{DRM}; R_{GK} = 1\text{k}\Omega$	400V	MIN.	20	25	30	40	$\text{V}/\mu\text{s}$
		600V		10	10	15	20	
V_{GD}	$V_D = V_{DRM}; R_L = 3.3\text{k}\Omega; T_J = 110^\circ\text{C}$		MIN.	0.2	0.25			V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	5			8	mA
t_q	(1)		MAX.	60		50	45	μs
t_{gt}	$I_G = 2 \times I_{GT}; PW = 15\mu\text{s}; I_T = 1.6\text{A}$		TYP.	2	3	4	5	μs

(1) $I_T = 1\text{A}; t_p = 50\mu\text{s}; dv/dt = 5\text{V}/\mu\text{s}; di/dt = 5\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions		Value	Unit
V_{TM}	$I_T = 1.2\text{A}; t_p = 380\ \mu\text{s}$		MAX.	V
I_{DRM} / I_{RRM}	$V_{DRM} = V_{RRM}$	$T_J = 25^\circ\text{C}$	MAX.	1
		$T_J = 100^\circ\text{C}$		50
		$T_J = 110^\circ\text{C}$		100

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	EC103xy	75	$^\circ\text{C}/\text{W}$
		SxSy	60*	
$R_{\theta(J-A)}$	Junction to ambient	EC103xy	160	$^\circ\text{C}/\text{W}$

Notes: x = voltage, y = sensitivity

* = Mounted on 1 cm² copper (two-ounce) foil surface

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

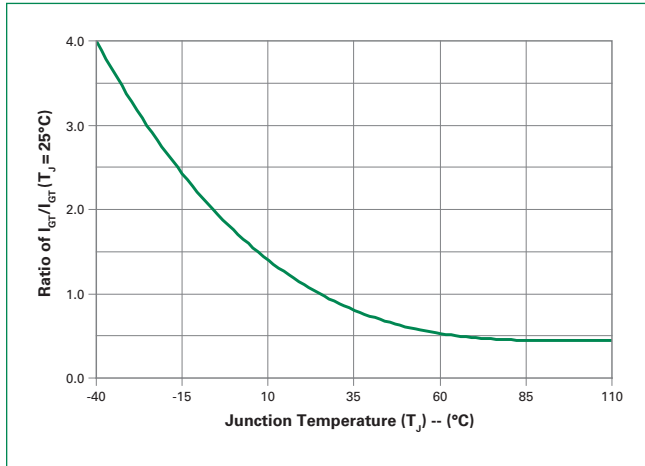


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

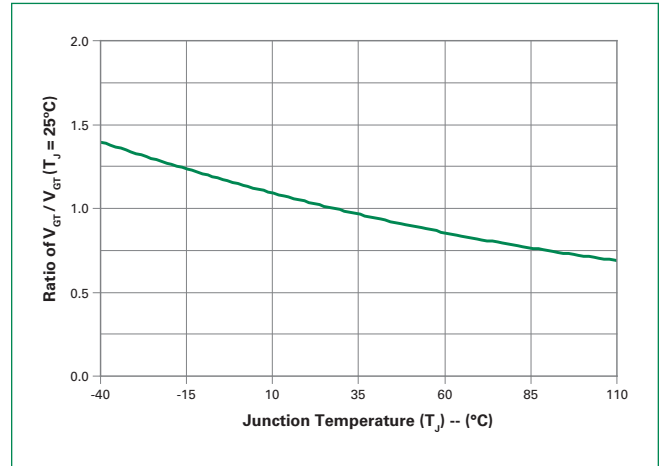


Figure 3: Normalized DC Holding Current vs. Junction Temperature

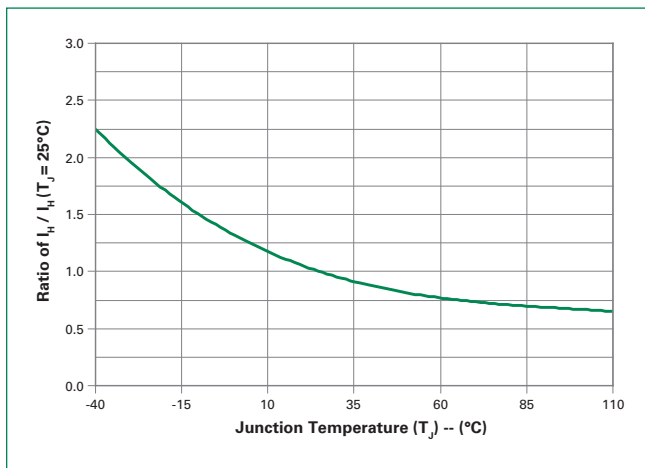


Figure 4: On-State Current vs. On-State Voltage (Typical)

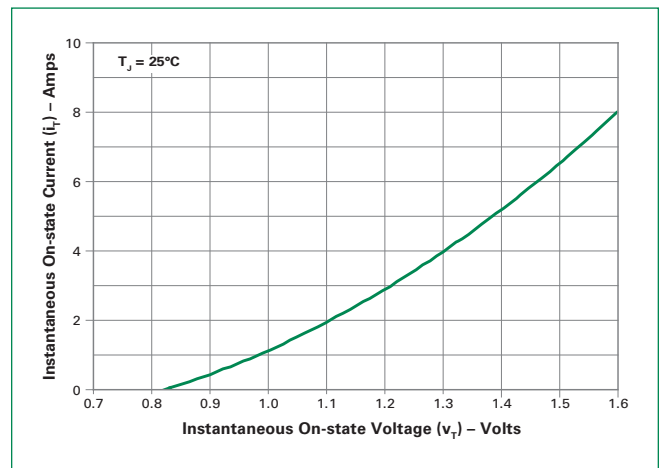


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

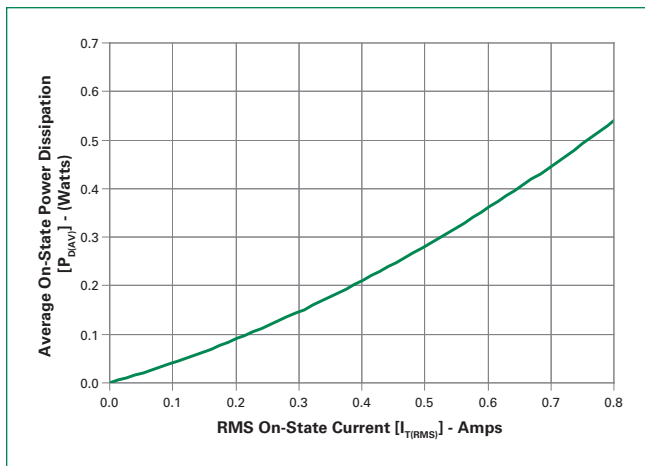


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

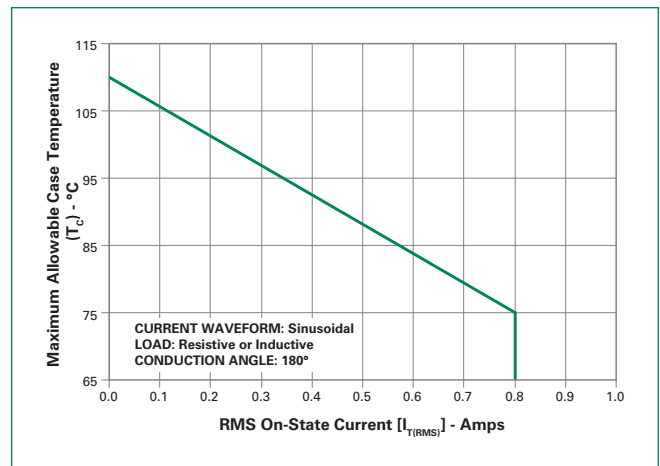


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

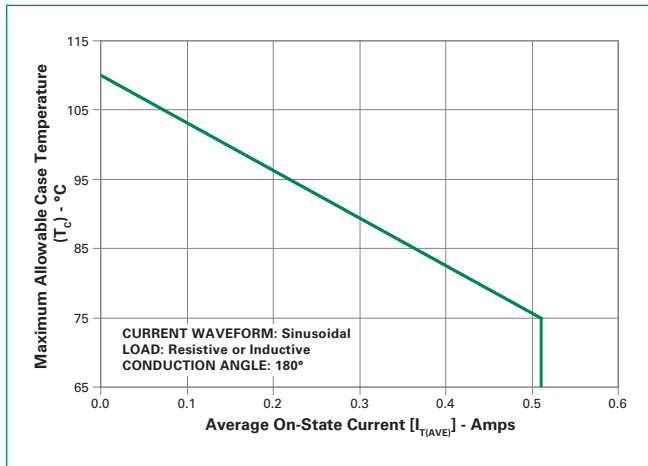


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current

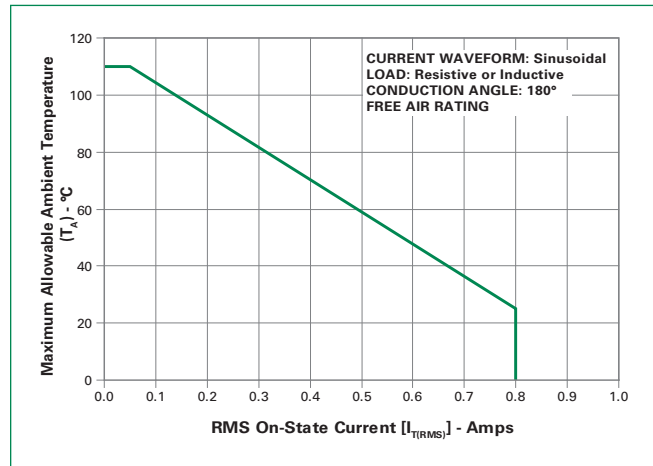


Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current

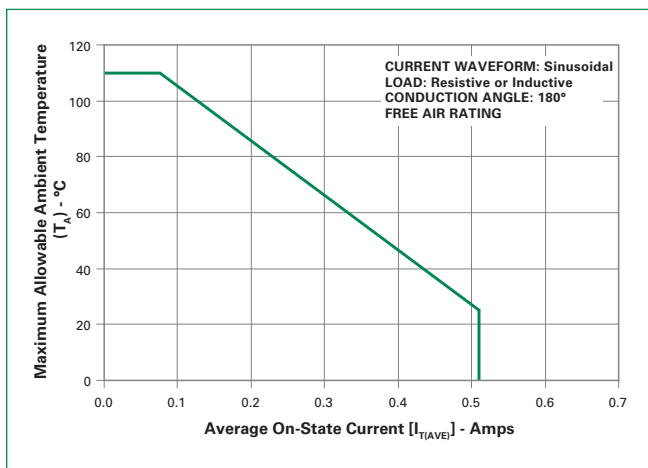


Figure 10: Peak Capacitor Discharge Current

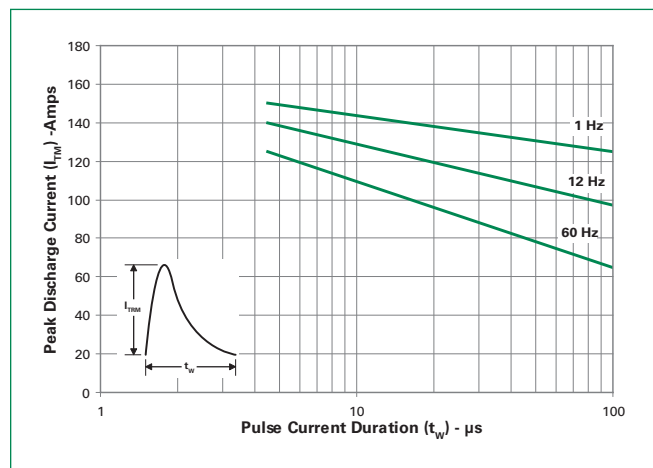


Figure 11: Peak Repetitive Sinusoidal Pulse Current

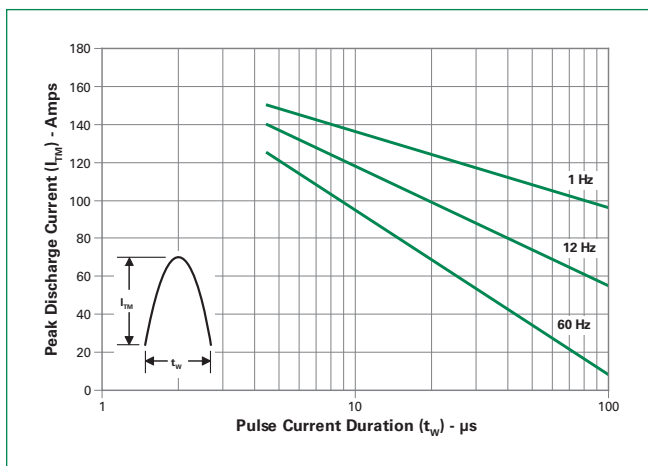


Figure 12: Surge Peak On-State Current vs. Number of Cycles

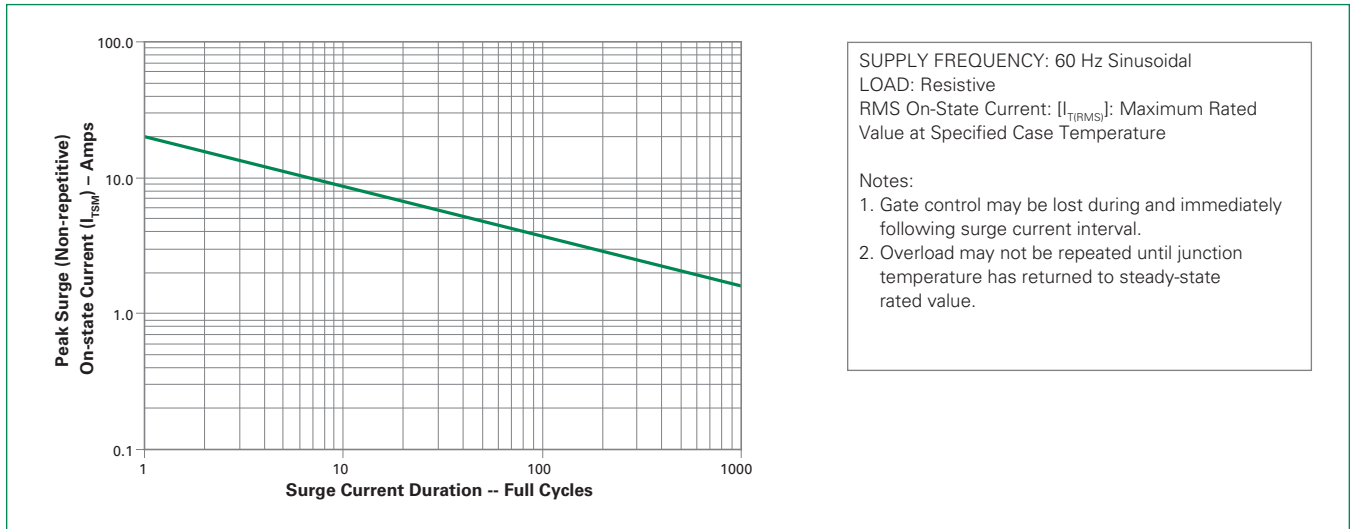
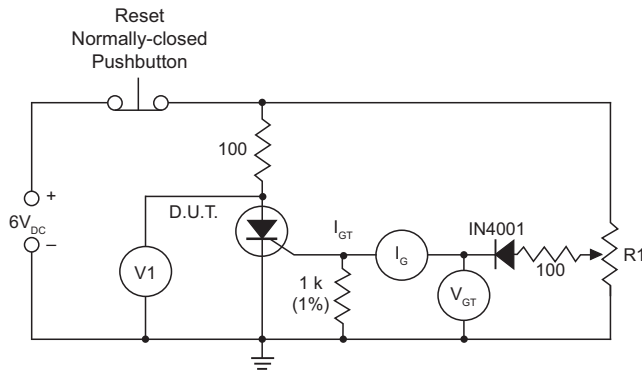


Figure 13: Simple Test Circuit for Gate Trigger Voltage and Current



Note: V1 — 0 V to 10 V dc meter

V_{GT} — 0 V to 1 V dc meter

I_G — 0 mA to 1 mA dc milliammeter

R1 — 1 k potentiometer

To measure gate trigger voltage and current, raise gate voltage (V_{GT}) until meter reading V1 drops from 6 V to 1 V. Gate trigger voltage is the reading on V_{GT} just prior to V1 dropping. Gate trigger current I_{GT} can be computed from the relationship

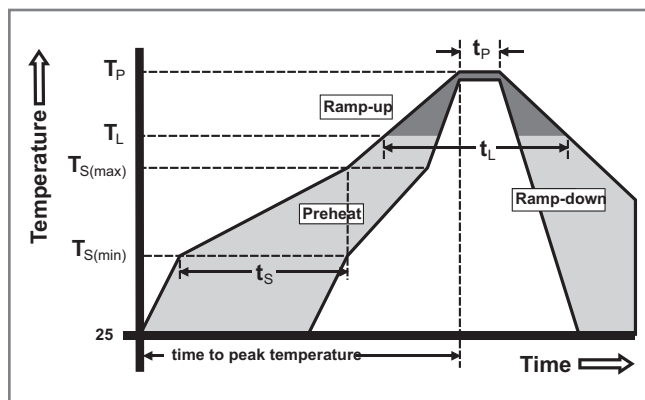
$$I_{GT} = I_G - \frac{V_{GT}}{1000} \text{ Amps}$$

where I_G is reading (in amperes) on meter just prior to V1 dropping

Note: I_{GT} may turn out to be a negative quantity (trigger current flows out from gate lead). If negative current occurs, I_{GT} value is not a valid reading. Remove 1 k resistor and use I_G as the more correct I_{GT} value. This will occur on 12 μ A gate products.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated/Pb-free Solder Dipped
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

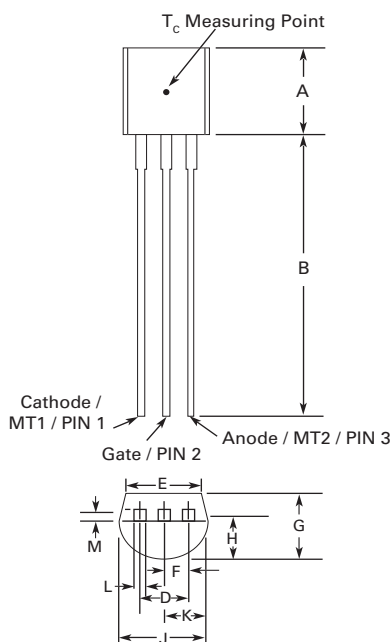
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 110°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

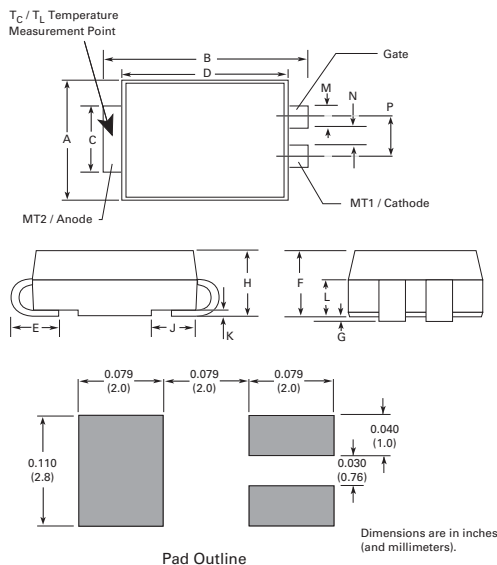
Dimensions – TO-92 (E Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500	-	12.70	-
D	0.095	0.105	2.41	2.67
E	0.150	-	3.81	-
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43

All leads insulated from case. Case is electrically nonconductive.

Dimensions — Compak (C Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.140	0.155	3.56	3.94
B	0.205	0.220	5.21	5.59
C	0.077	0.083	1.96	2.11
D	0.166	0.180	4.22	4.57
E	0.036	0.063	0.91	1.60
F	0.066	0.083	1.67	2.11
G	0.004	0.008	0.10	0.20
H	0.077	0.086	1.96	2.18
J	0.043	0.053	1.09	1.35
K	0.008	0.012	0.20	0.30
L	0.039	0.049	0.99	1.24
M	0.022	0.028	0.56	0.71
N	0.027	0.033	0.69	0.84
P	0.052	0.058	1.32	1.47

0.8 A SCRs

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
EC103 x 1	X	X			12 μ A	Sensitive SCR	TO-92
EC103 x 2	X	X			50 μ A	Sensitive SCR	TO-92
EC103 x	X	X			200 μ A	Sensitive SCR	TO-92
EC103 x 3	X	X			500 μ A	Sensitive SCR	TO-92
S x S1	X	X			12 μ A	Sensitive SCR	Compak
S x S2	X	X			50 μ A	Sensitive SCR	Compak
S x S	X	X			200 μ A	Sensitive SCR	Compak
S x S3	X	X			500 μ A	Sensitive SCR	Compak

Note: x = Voltage

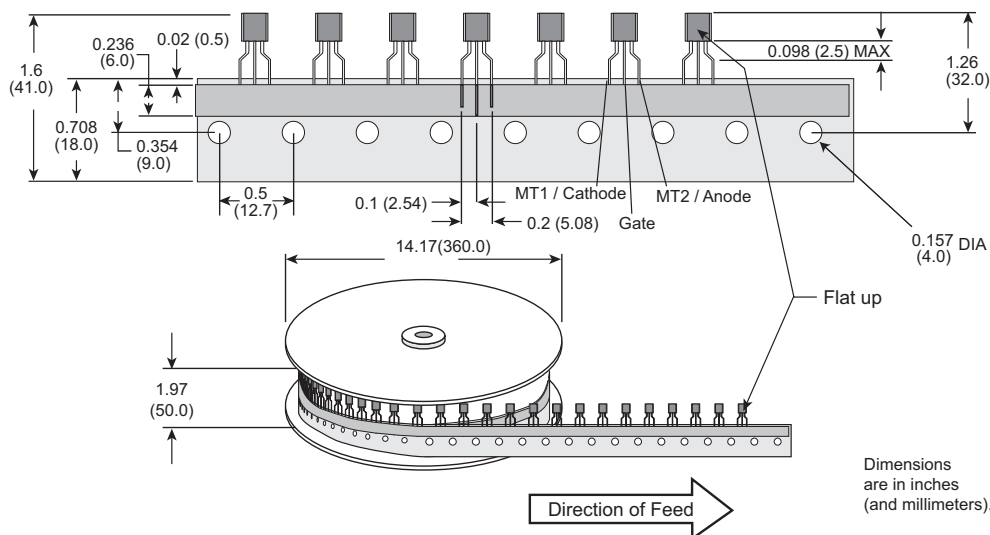
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
EC103xy	EC103xy	0.19 g	Bulk	2000
EC103xyRP	EC103xy	0.19 g	Reel Pack	2000
EC103xyAP	EC103xy	0.19 g	Ammo Pack	2000
SxSyRP	SxSy	0.08 g	Embossed Carrier	2500

Note: x = Voltage, y = sensitivity

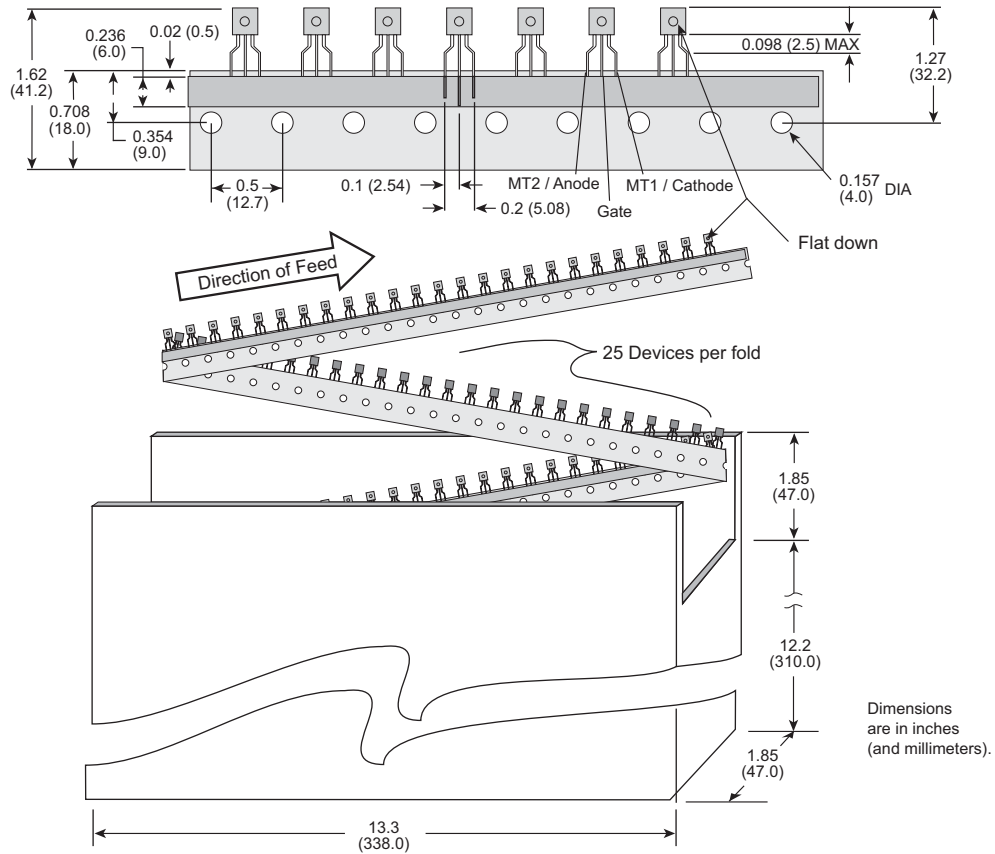
TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards



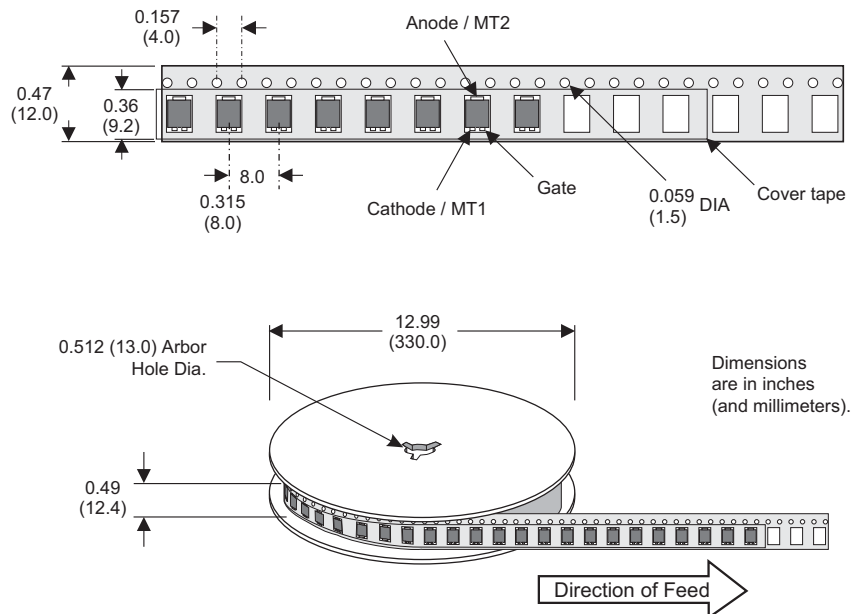
TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards

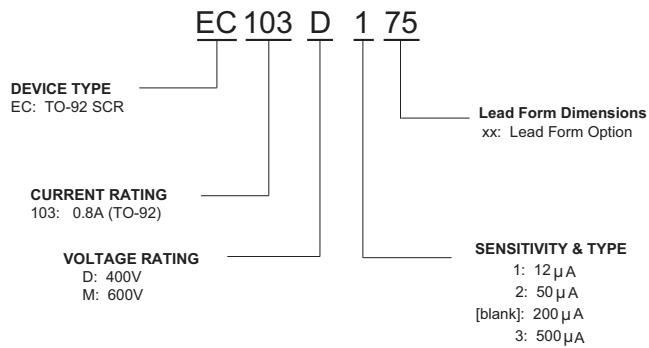


Compak Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-1 Standards

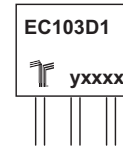


Part Numbering System (TO-92)

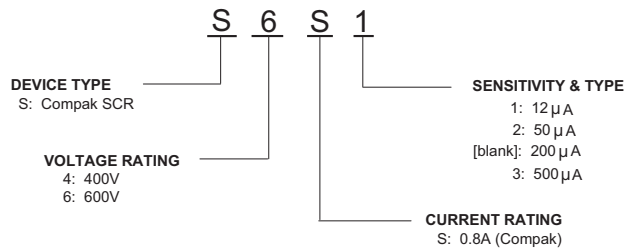


Part Marking System

TO-92 (E Package)

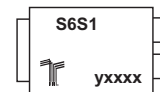


Part Numbering System (Compak)



Part Marking System (Compak)

Compak (C Package)



RoHS **SxX8xSx Series**



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	400 to 800	V
I_{GT}	5 to 200	μA

Applications

The SxX8xSx EV series is specifically designed for GFCI (Ground Fault Circuit Interrupter) and gas ignition applications.

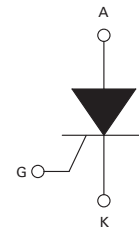
Description

New device series offers high static dv/dt and lower turn off (t_q) sensitive SCR with its small die planar construction design. It is specifically designed for GFCI (Ground Fault Circuit Interrupter) and Gas Ignition applications. All SCRs junctions are glass-passivated to ensure long term reliability and parametric stability.

Features

- RoHS compliant
- Thru-hole and surface mount packages
- Surge current capability > 10Amps
- Blocking voltage (V_{DRM}/V_{RRM}) capability - up to 800V
- High dv/dt noise immunity
- Improved turn-off time (t_q) < 25 μsec
- Sensitive gate for direct microprocessor interface

Schematic Symbol



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-92 $T_c = 55^\circ C$	0.8 A
		SOT-89 $T_c = 60^\circ C$	0.8 A
		SOT-223 $T_L = 60^\circ C$	0.8 A
$I_{T(AV)}$	Average on-state current	TO-92 $T_c = 55^\circ C$	0.51 A
		SOT-89 $T_c = 60^\circ C$	0.51 A
		SOT-223 $T_L = 60^\circ C$	0.51 A
I_{TSM}	Non repetitive surge peak on-state current (Single cycle, T_j initial = $25^\circ C$)	TO-92 SOT-89 SOT-223 $F = 50 Hz$	8 A
		$F = 60 Hz$	10 A
I^2t	I^2t Value for fusing	$t_p = 10 ms$ $F = 50 Hz$	0.32 A^2s
		$t_p = 8.3 ms$ $F = 60 Hz$	0.41 A^2s
di/dt	Critical rate of rise of on-state current $I_G = 10mA$	TO-92 SOT-89 SOT-223 $T_j = 125^\circ C$	50 $A/\mu s$
I_{GM}	Peak Gate Current	$t_p = 10 \mu s$ $T_j = 125^\circ C$	1.0 A
$P_{G(AV)}$	Average gate power dissipation	— $T_j = 125^\circ C$	0.1 W
T_{stg}	Storage junction temperature range	—	-40 to 150 $^\circ C$
T_j	Operating junction temperature range	—	-40 to 125 $^\circ C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value			Unit
				SxX8yS1	SxX8yS2	SxX8yS	
I_{GT}	DC Gate Trigger Current	$V_D = 6\text{V}$ $R_L = 100\ \Omega$	MIN.	0.5	1	15	μA
			MAX.	5	50	200	μA
V_{GT}	DC Gate Trigger Voltage	$V_D = 6\text{V}$ $R_L = 100\ \Omega$	MAX.	0.8			V
V_{GRM}	Peak Reverse Gate Voltage	$I_{RG} = 10\ \mu\text{A}$	MIN.	5			V
I_H	Holding Current	$R_{GK} = 1\ \text{k}\Omega$	MAX.	5			mA
(dv/dt)s	Critical Rate-of-Rise of Off-State Voltage	$T_J = 125^\circ\text{C}$ $V_D = V_{DRM}/V_{RRM}$ Exp. Waveform $R_{GK} = 1\ \text{k}\Omega$	MIN.	75			V/ μs
t_q	Turn-Off Time	$T_J = 25^\circ\text{C} @ 600\text{V}$ $R_{GK} = 1\ \text{k}\Omega$	MAX.	30	25	25	μs
t_{gt}	Turn-On Time	$I_G = 10\text{mA}$ $PW = 15\ \mu\text{sec}$ $I_T = 1.6\text{A(pk)}$	MAX.	2.0	2.0	2.0	μs

Note: x = voltage, y = package

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Limit	Value	Unit
V_{TM}	Peak On-State Voltage	$I_{TM} = 1.6\text{A (pk)}$	MAX.	1.70	V
I_{DRM}	Off-State Current, Peak Repetitive	$T_J = 25^\circ\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$	MAX.	3	μA
		$T_J = 125^\circ\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$	MAX.	500	μA

Thermal Resistances

Symbol	Description	Test Conditions		Value	Unit
R _{th(j-c)}	Junction to case (AC)	I _T = 0.8A _(RMS) ¹	TO-92	75	°C/W
			SOT-223	30	°C/W
			SOT-89	50	°C/W
R _{th(j-a)}	Junction to ambient	I _T = 0.8A _(RMS) ¹	TO-92	150	°C/W
			SOT-223	60	°C/W
			SOT-89	90	°C/W

¹ 60Hz AC resistive load condition, 100% conduction.

Figure 1: Normalized DC Gate Trigger Current For All Quadrants vs. Junction Temperature

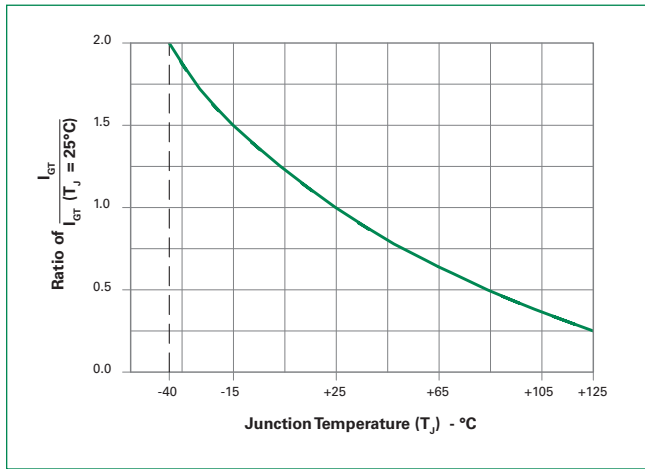


Figure 2: Normalized DC Holding Current vs. Junction Temperature

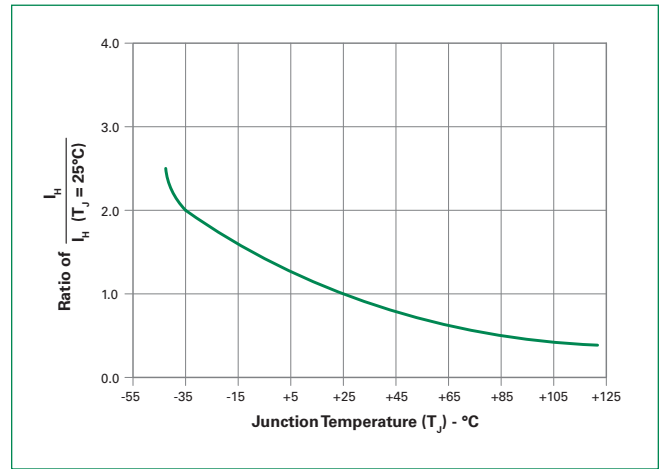


Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

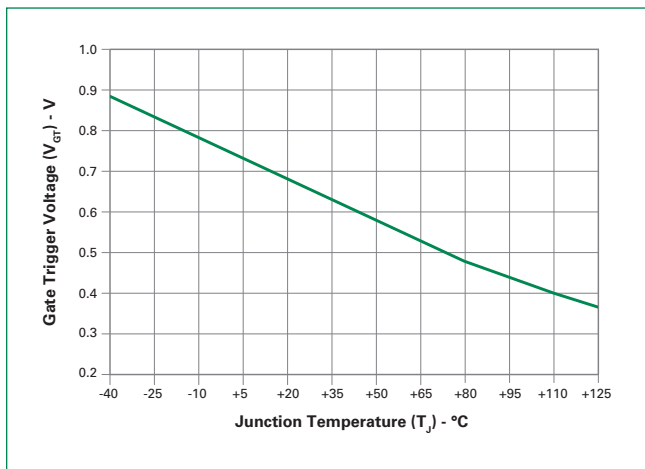


Figure 4: Power Dissipation (Typical) vs. RMS On-State Current

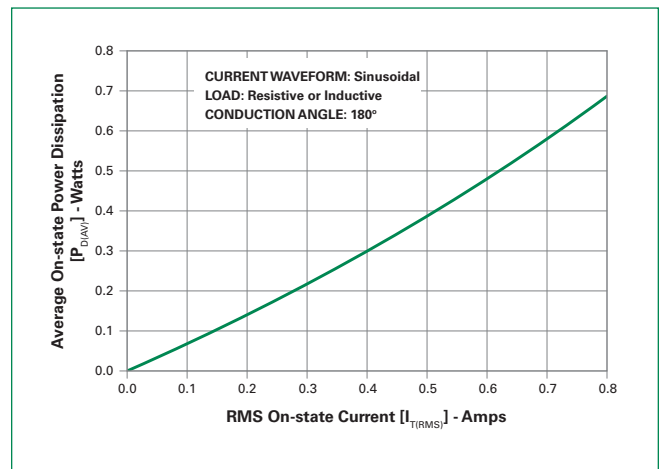


Figure 5: Maximum Allowable Case Temperature vs. On-State Current

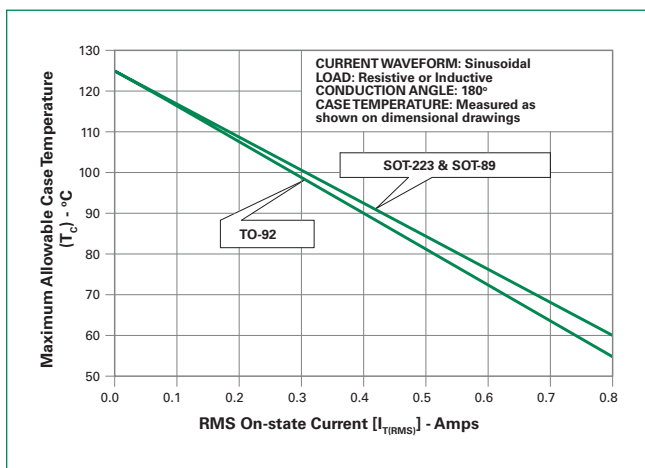
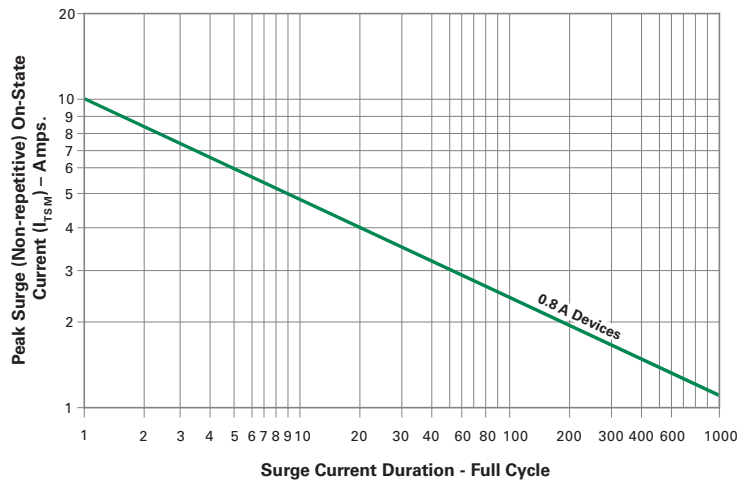


Figure 6: Surge Peak On-State Current vs. Number of Cycles



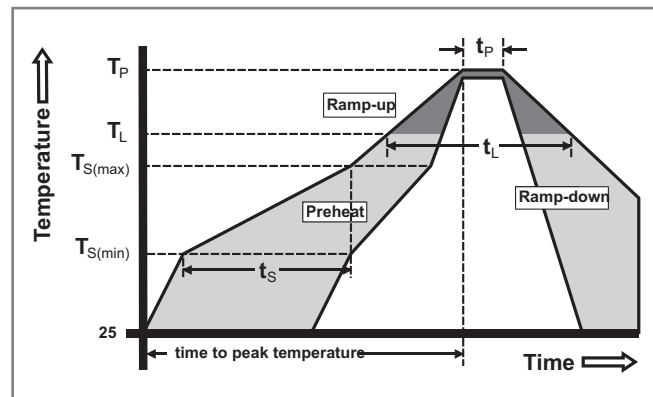
Supply Frequency: 60Hz Sinusoidal
Load: Resistive
RMS On-State Current ($I_{T(RMS)}$): Max Rated Value at Specific Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Lead Material	Copper Alloy

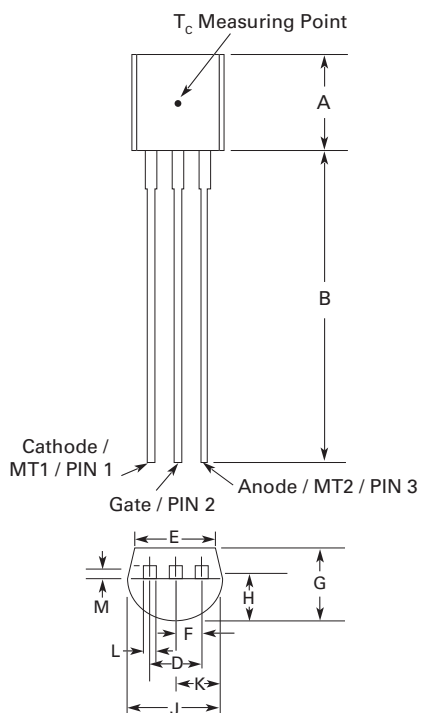
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Reliability/Environmental Tests

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 110°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

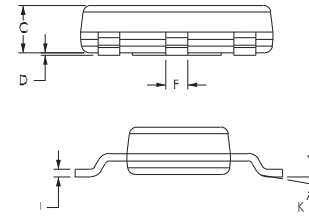
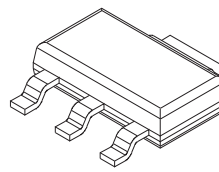
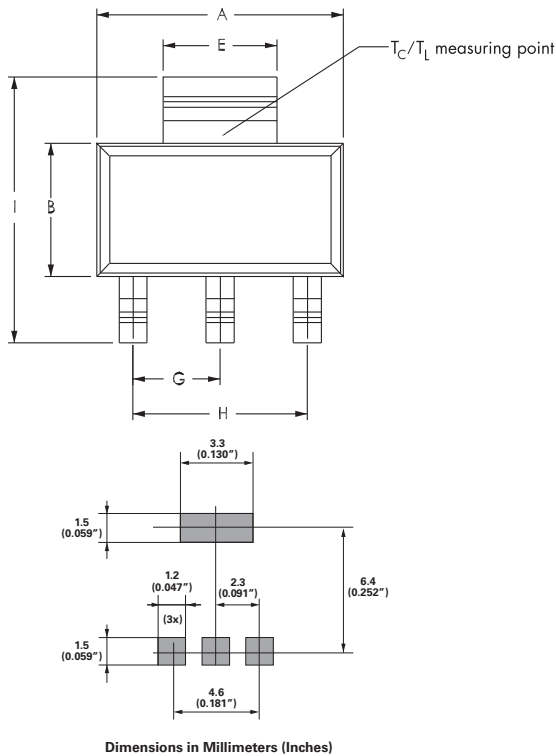
Dimensions – TO-92 (E Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500		12.70	
D	0.095	0.105	2.41	2.67
E	0.150		3.81	
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43

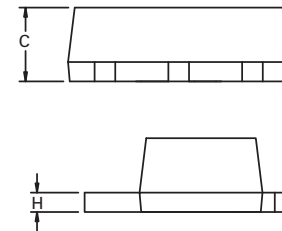
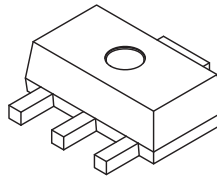
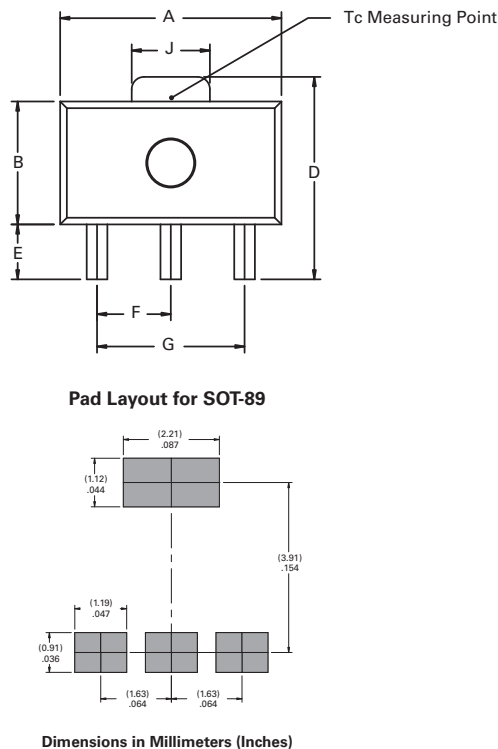
All leads insulated from case. Case is electrically nonconductive.

Dimensions – SOT-223



Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.248	0.256	0.264	6.30	6.50	6.70
B	0.130	0.138	0.146	3.30	3.50	3.70
C	—	—	0.071	—	—	1.80
D	0.001	—	0.004	0.02	—	0.10
E	0.114	0.118	0.124	2.90	3.00	3.15
F	0.024	0.027	0.034	0.60	0.70	0.85
G	—	0.090	—	—	2.30	—
H	—	0.181	—	—	4.60	—
I	0.264	0.276	0.287	6.70	7.00	7.30
J	0.009	0.010	0.014	0.24	0.26	0.35
K	10° MAX					

Dimensions – SOT-89



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.173	—	0.181	4.40	—	4.60
B	0.090	—	0.102	2.29	—	2.60
C	0.055	—	0.063	1.40	—	1.60
D	0.155	—	0.167	3.94	—	4.25
E	0.035	—	0.047	0.89	—	1.20
F	0.056	—	0.062	1.42	—	1.57
G	0.115	—	0.121	2.92	—	3.07
H	0.014	—	0.017	0.35	—	0.44
I	0.014	—	0.019	0.36	—	0.48
J	0.064	—	0.072	1.62	—	1.83

Product Selector

Part Number	Voltage			Gate Sensitivity	Package
	400V	600V	800V		
S4X8ES	X	—	—	200 μ A	TO-92
S6X8ES	—	X	—	200 μ A	TO-92
S8X8ES	—	—	X	200 μ A	TO-92
S4X8TS	X	—	—	200 μ A	SOT-223
S6X8TS	—	X	—	200 μ A	SOT-223
S8X8TS	—	—	X	200 μ A	SOT-223
S4X8BS	X	—	—	200 μ A	SOT-89
S6X8BS	—	X	—	200 μ A	SOT-89
S4X8ES1	X	—	—	5 μ A	TO-92
S6X8ES1	—	X	—	5 μ A	TO-92
S8X8ES1	—	—	X	5 μ A	TO-92
S4X8TS1	X	—	—	5 μ A	SOT-223
S6X8TS1	—	X	—	5 μ A	SOT-223
S8X8TS1	—	—	X	5 μ A	SOT-223
S4X8ES2	X	—	—	50 μ A	TO-92
S6X8ES2	—	X	—	50 μ A	TO-92
S8X8ES2	—	—	X	50 μ A	TO-92
S4X8TS2	X	—	—	50 μ A	SOT-223
S6X8TS2	—	X	—	50 μ A	SOT-223
S8X8TS2	—	—	X	50 μ A	SOT-223

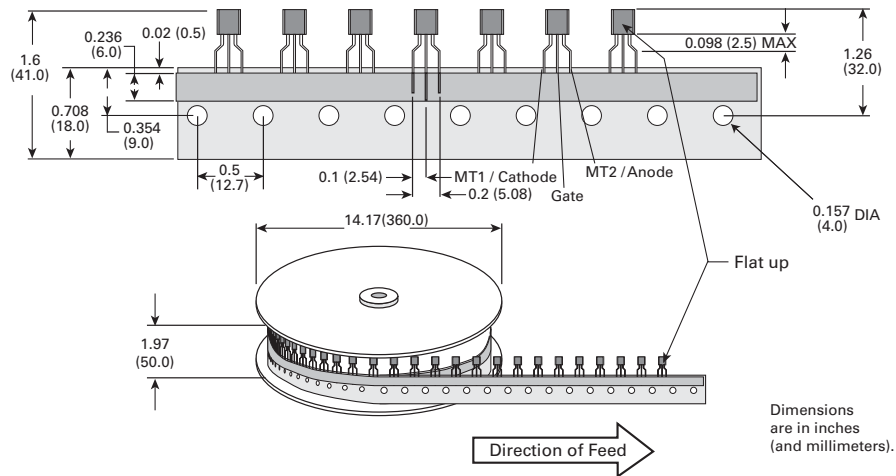
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
SxX8ESy	SxX8ESy	0.170g	Bulk	2500
SxX8ESyAP	SxX8ESy	0.170g	Ammo Pack	2000
SxX8ESyRP	SxX8ESy	0.170g	Tape & Reel	2000
SxX8TSyRP	SxX8TSy	0.120g	Tape & Reel	1000
SxX8BSRP	xX8	0.053g	Tape & Reel	1000

Note: x = voltage, y = gate sensitivity

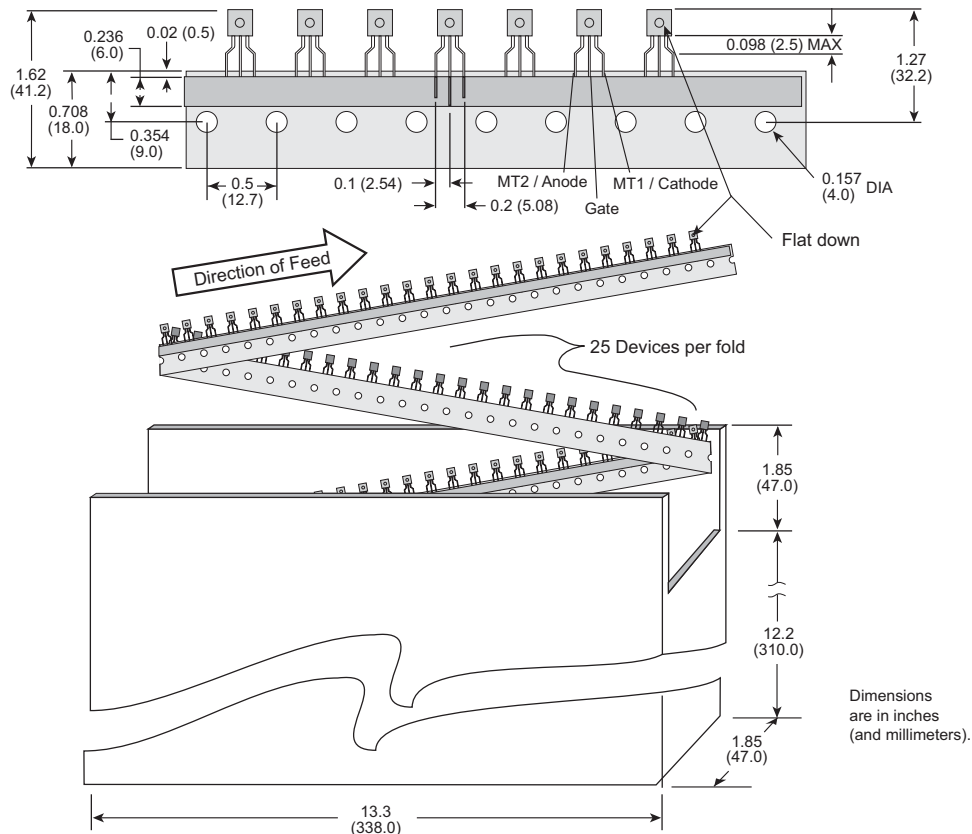
TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards

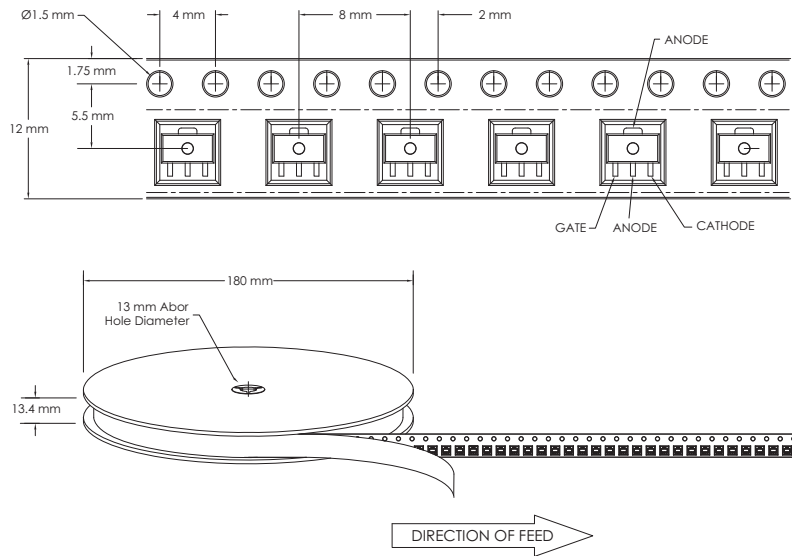


TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

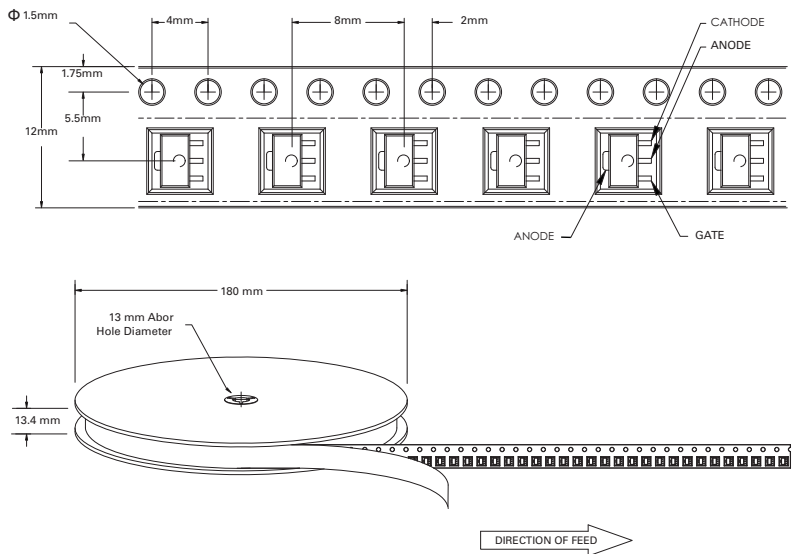
Meets all EIA-468-B 1994 Standards



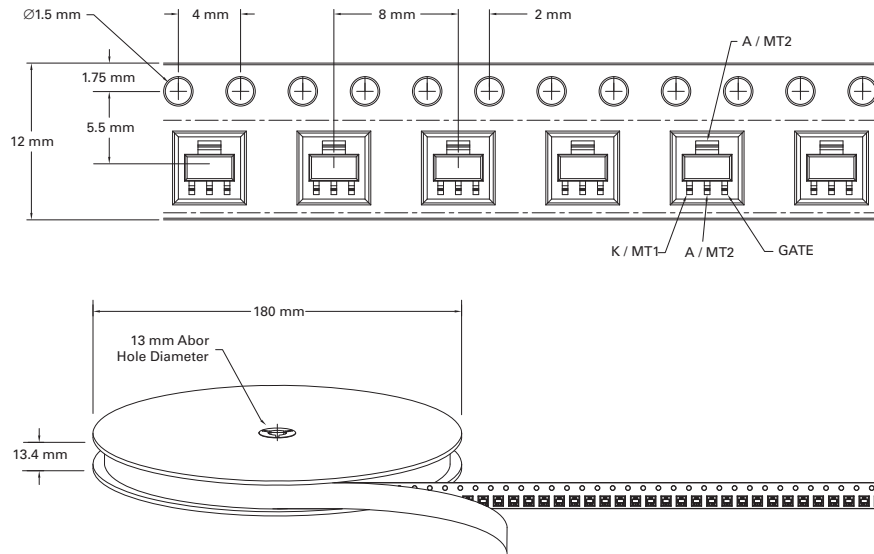
SOT-89 Reel Pack (RP) Specifications



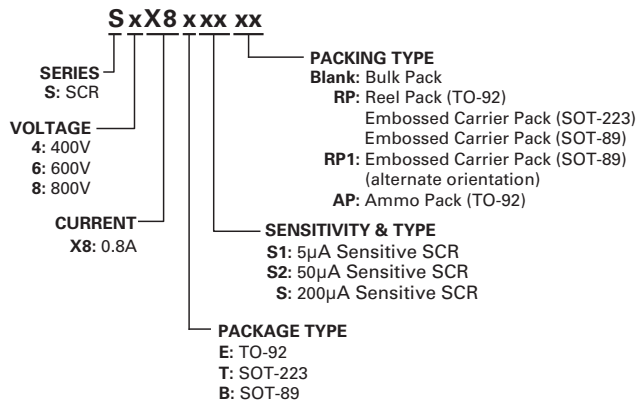
SOT-89 Reel Pack (RP1) Specifications



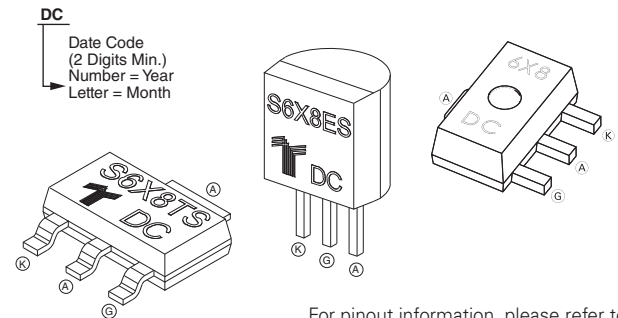
SOT-223 Reel Pack (RP) Specifications



Part Numbering System

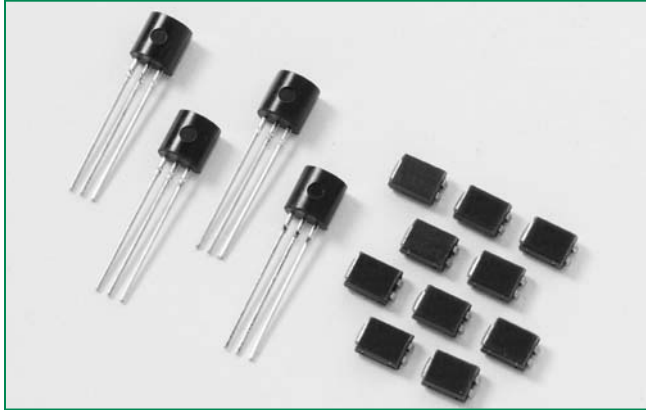


Part Marking System



For pinout information, please refer to Schematic Symbol section of this document.

RoHS Sx01E & SxN1 Series



Description

Excellent for lower current heat, lamp, and audible alarm controls for home goods.

Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 30 A

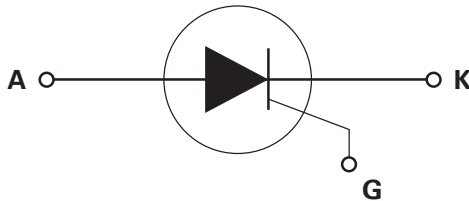
Applications

Typical applications are AC solid-state switches, fluidlevel sensors, strobes, and capacitive-discharge ignition systems.

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	400 to 600	V
I_{GT}	10	mA

Schematic Symbol



Absolute Maximum Ratings — Standard SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 90^\circ\text{C}$	1	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	25	A
		single half cycle; $f = 60\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	30	
I^2t	I_2t Value for fusing	$t_p = 8.3\text{ ms}$	3.7	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_j = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_j = 125^\circ\text{C}$	1.5	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.3	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions		Value	Unit
I_{GT}	$V_D = 12V$; $R_L = 60\ \Omega$	MAX.	10	mA
		MIN.	1	
V_{GT}		MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^\circ\text{C}$	MIN.	20	V/ μs
	$V_D = V_{DRM}$; gate open; $T_J = 125^\circ\text{C}$		40	
V_{GD}	$V_D = V_{DRM}$; $R_L = 3.3\ \text{k}\Omega$; $T_J = 125^\circ\text{C}$	MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)	MAX.	30	mA
t_q	(1)	MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$; $PW = 15\mu\text{s}$; $I_T = 2\text{A}$	TYP.	2	μs

(1) $I_T = 1\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 20\text{V}/\mu\text{s}$; $di/dt = -10\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions		Value	Unit
V_{TM}	$I_T = 2\text{A}$; $t_p = 380\ \mu\text{s}$	MAX.	1.6	V
I_{DRM} / I_{RRM}	$V_{DRM} = V_{RRM}$	$T_J = 25^\circ\text{C}$	10	μA
		$T_J = 100^\circ\text{C}$	200	
		$T_J = 125^\circ\text{C}$	500	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sx01E	50	$^\circ\text{C}/\text{W}$
		SxN1	35*	
$R_{\theta(J-A)}$	Junction to ambient	Sx01E	145	$^\circ\text{C}/\text{W}$

Notes : x = voltage

* = Mounted on 1 cm² copper (two-ounce) foil surface

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

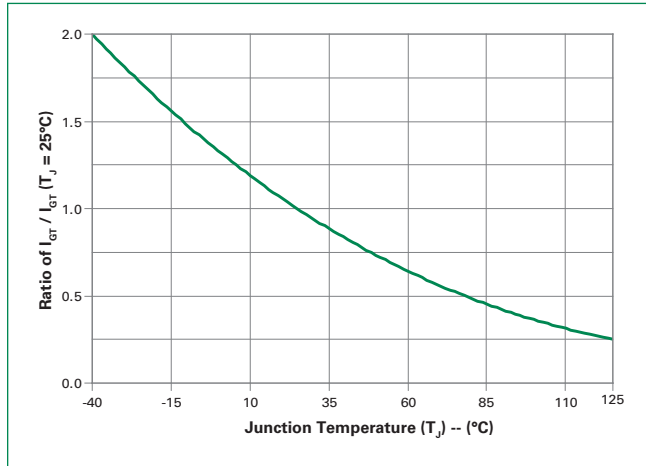


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

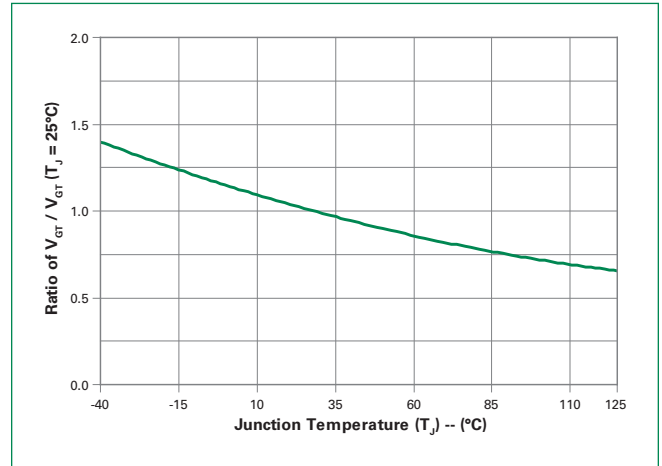


Figure 3: Normalized DC Holding Current vs. Junction Temperature

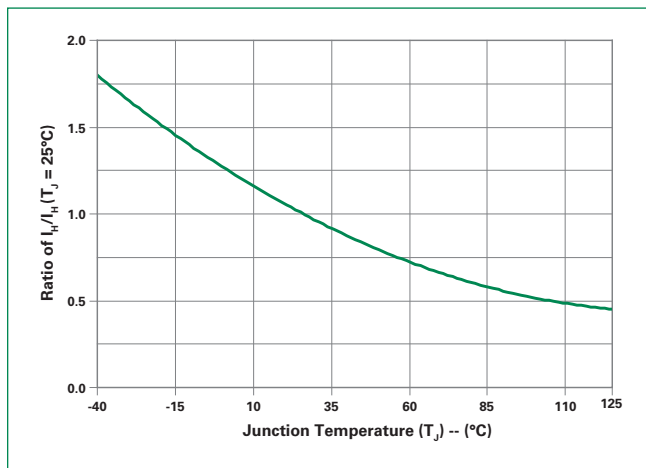


Figure 4: On-State Current vs. On-State Voltage (Typical)

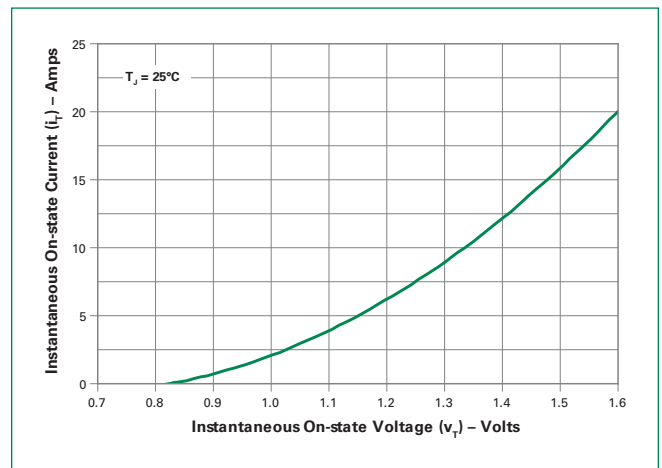


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

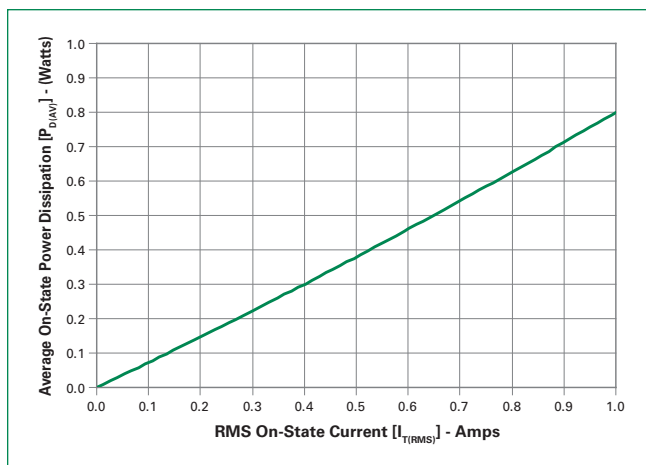


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

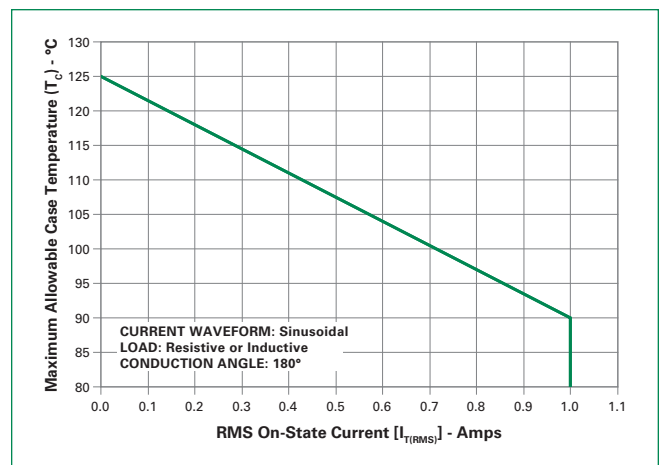


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

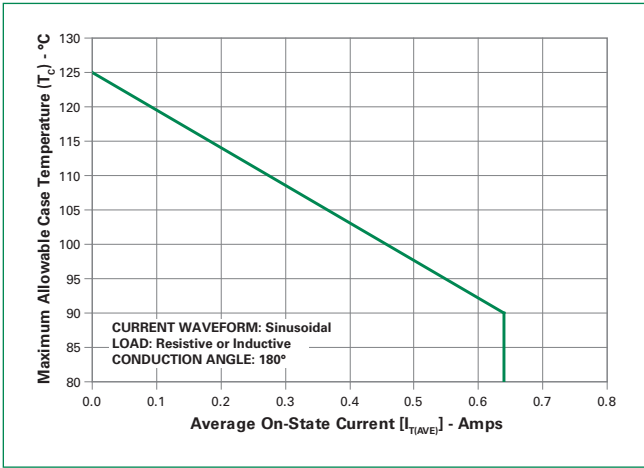


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current

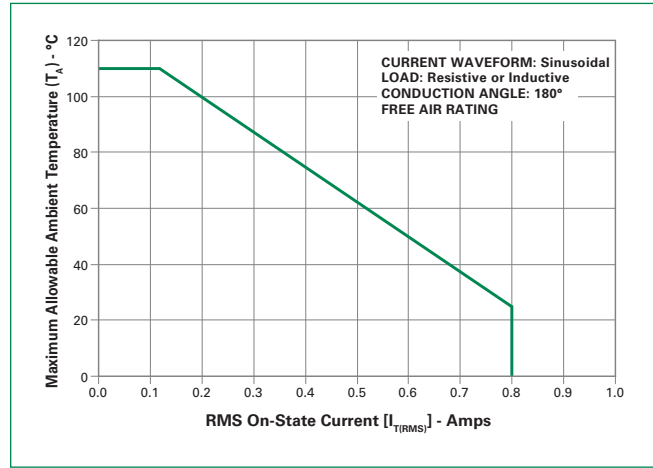


Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current

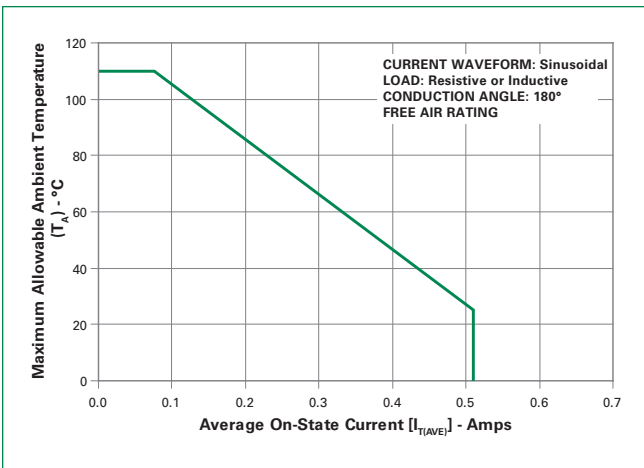


Figure 10: Peak Capacitor Discharge Current

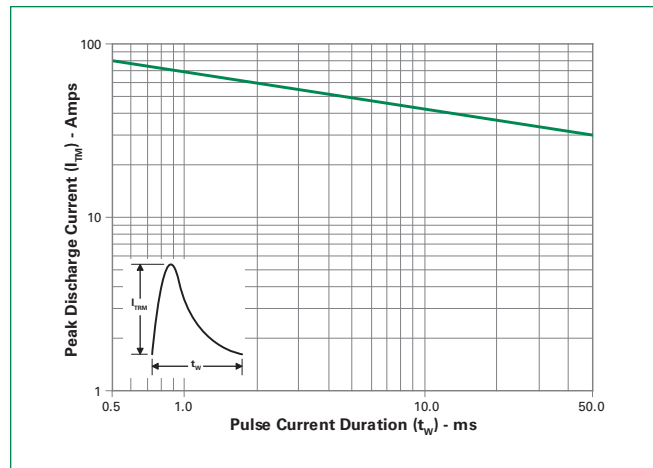


Figure 11: Peak Capacitor Discharge Current Derating

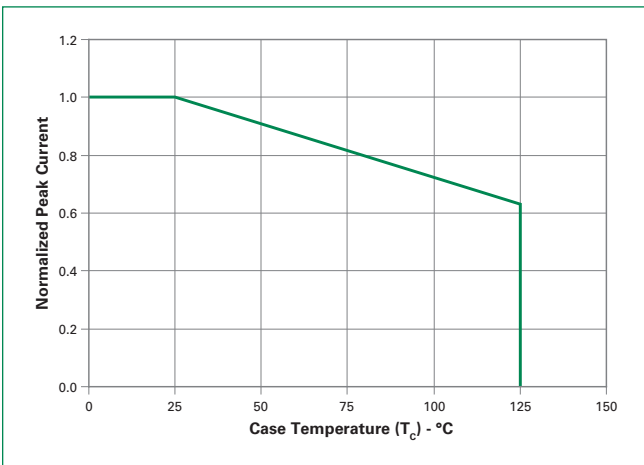
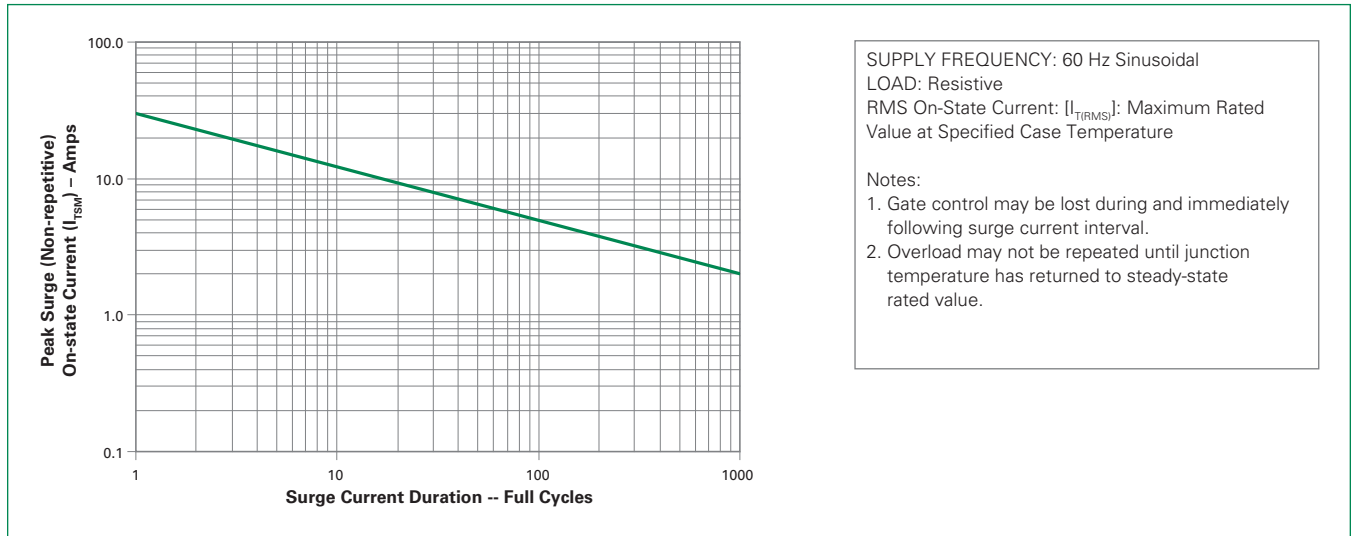
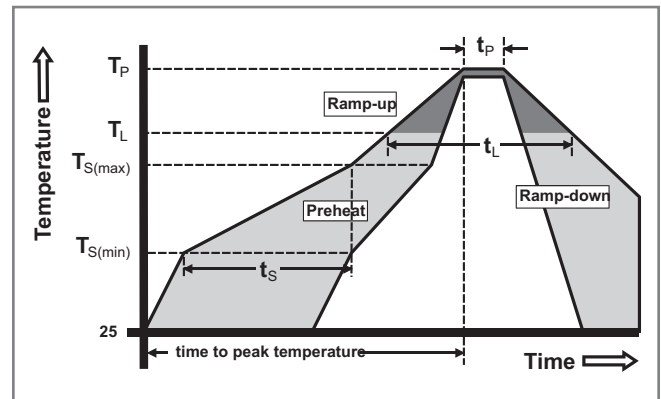


Figure 12: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

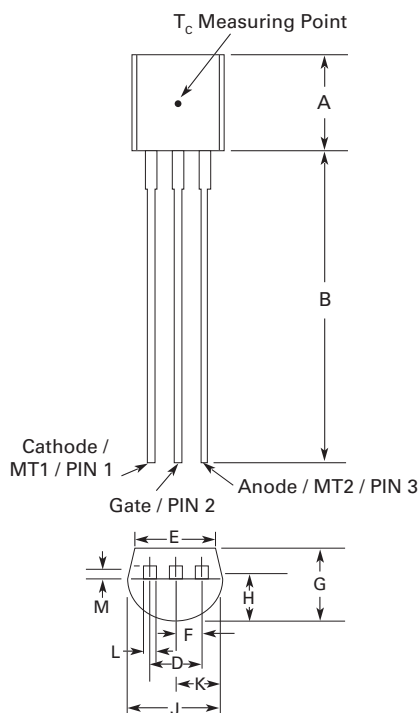
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

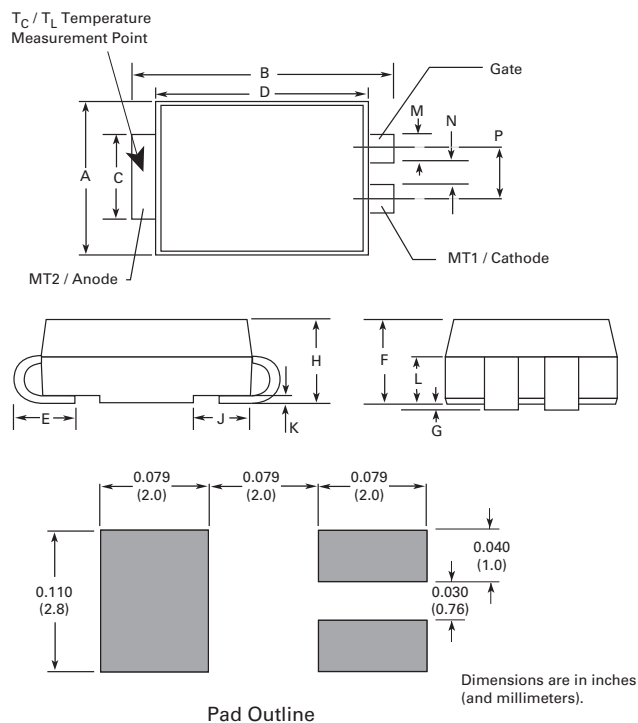
Dimensions – TO-92 (E Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500		12.70	
D	0.095	0.105	2.41	2.67
E	0.150		3.81	
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43

All leads insulated from case. Case is electrically nonconductive.

Dimensions - Compak (C Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.140	0.155	3.56	3.94
B	0.205	0.220	5.21	5.59
C	0.077	0.083	1.96	2.11
D	0.166	0.180	4.22	4.57
E	0.036	0.063	0.91	1.60
F	0.066	0.083	1.67	2.11
G	0.004	0.008	0.10	0.20
H	0.077	0.086	1.96	2.18
J	0.043	0.053	1.09	1.35
K	0.008	0.012	0.20	0.30
L	0.039	0.049	0.99	1.24
M	0.022	0.028	0.56	0.71
N	0.027	0.033	0.69	0.84
P	0.052	0.058	1.32	1.47

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sx01E	X	X			10mA	Standard SCR	TO-92
SxN1	X	X			10mA	Standard SCR	Compak

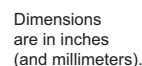
Note: x = Voltage

Packing Options

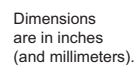
Part Number	Marking	Weight	Packing Mode	Base Quantity
Sx01E	Sx01E	0.19 g	Bulk	2000
Sx01ERP	Sx01E	0.19 g	Reel Pack	2000
Sx01EAP	Sx01E	0.19 g	Ammo Pack	2000
SxN1RP	SxN1	0.08 g	Embossed Carrier	2500

Note: x = Voltage

Meets all EIA-468-B 1994 Standards

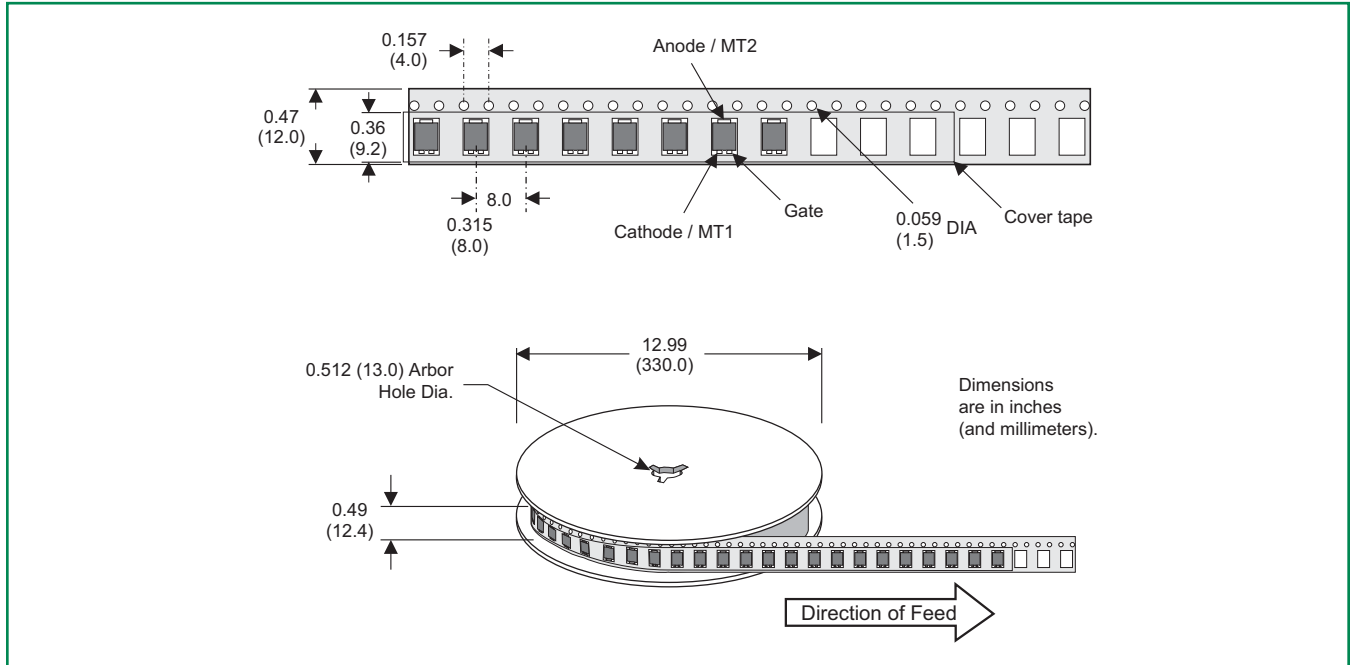


Meets all EIA-468-B 1994 Standards

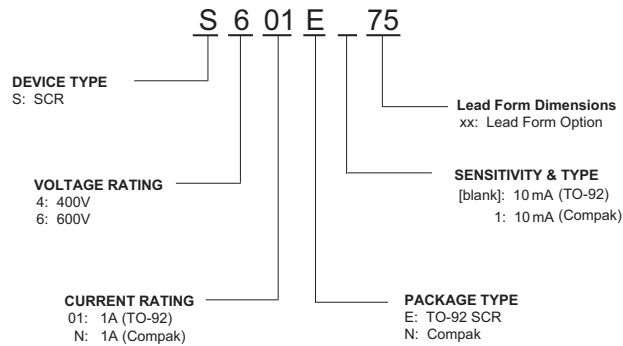


Compak Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-1 Standards



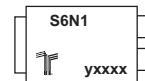
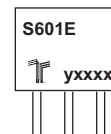
Part Numbering System



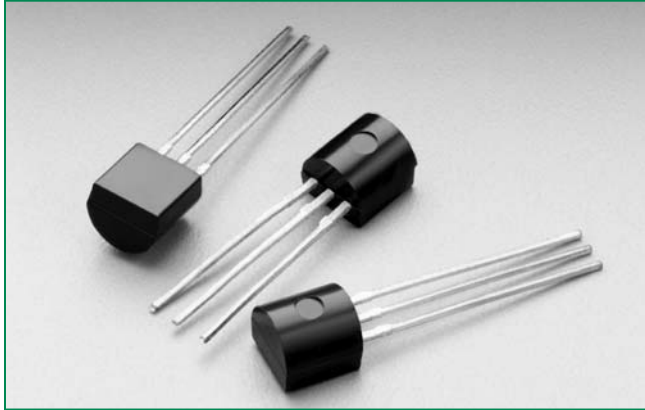
Part Marking System

TO-92 (E Package)

Compak (C Package)



RoHS **TCR22-x Series**



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Sensitive gate SCRs are easily triggered with microAmps of current as furnished by sense coils, proximity switches, and microprocessors.

Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 20 A

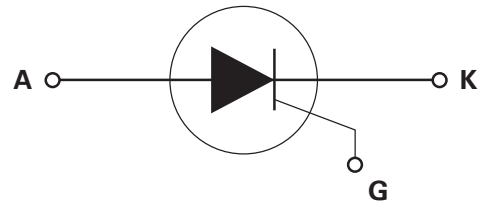
Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	1.5	A
V_{DRM}/V_{RRM}	400 to 600	V
I_{GT}	200	μA

Applications

Typical applications are capacitive discharge systems for strobe lights and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Schematic Symbol



Absolute Maximum Ratings – Sensitive SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 40^\circ C$	1.5	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50Hz$; T_j (initial) = $25^\circ C$	16	A
		single half cycle; $f = 60Hz$; T_j (initial) = $25^\circ C$	20	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms	1.6	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60$ Hz ; $T_j = 110^\circ C$	50	$A/\mu s$
I_{GM}	Peak gate current	$T_j = 110^\circ C$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 110^\circ C$	0.1	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ C$
T_j	Operating junction temperature range		-40 to 110	$^\circ C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value	Unit
I_{GT}	$V_D = 6V; R_L = 100\ \Omega$		MAX.	200	μA
V_{GT}			MAX.	0.8	V
dv/dt	$V_D = V_{DRM}; R_{GK} = 1k\Omega$	400V	MIN.	40	$V/\mu\text{s}$
		600V		30	
V_{GD}	$V_D = V_{DRM}; R_L = 3.3\ k\Omega; T_J = 110^\circ\text{C}$		MIN.	0.25	V
V_{GRM}	$I_{GR} = 10\mu\text{A}$		MIN.	6	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	5	mA
t_q	(1)		MAX.	50	μs
t_{gt}	$I_G = 2 \times I_{GT}; PW = 15\mu\text{s}; I_T = 3A$		TYP.	3.5	μs

(1) $I_T = 1A; t_p = 50\mu\text{s}; dv/dt = 5V/\mu\text{s}; di/dt = 10A/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions			Value	Unit	
V _{TM}	I _T = 3A; t _p = 380 μs			MAX.	1.5	V
I _{DRM} / I _{RRM}	V _{DRM} = V _{RRM}	T _J = 25°C	400V	MAX.	1	μA
			600V		2	
		T _J = 110°C			100	

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	50	$^\circ\text{C}/W$
$R_{\theta(J-A)}$	Junction to ambient	160	$^\circ\text{C}/W$

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

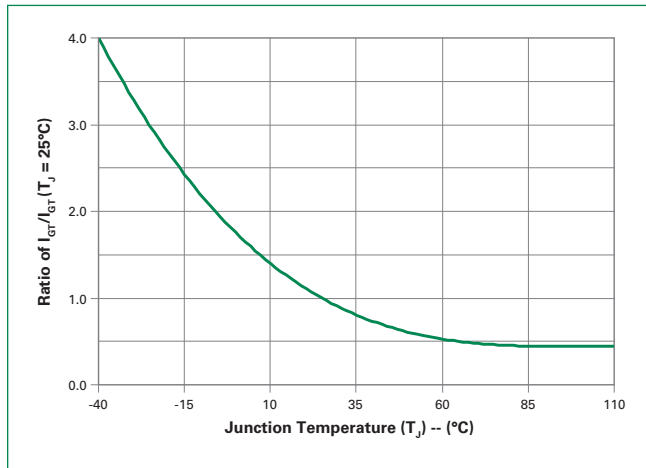


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

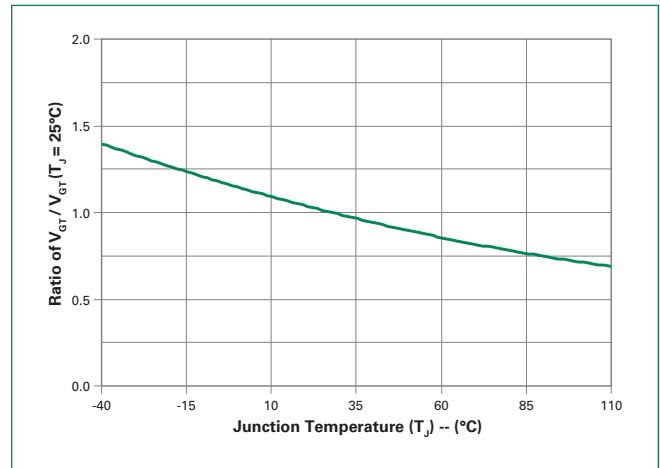


Figure 3: Normalized DC Holding Current vs. Junction Temperature

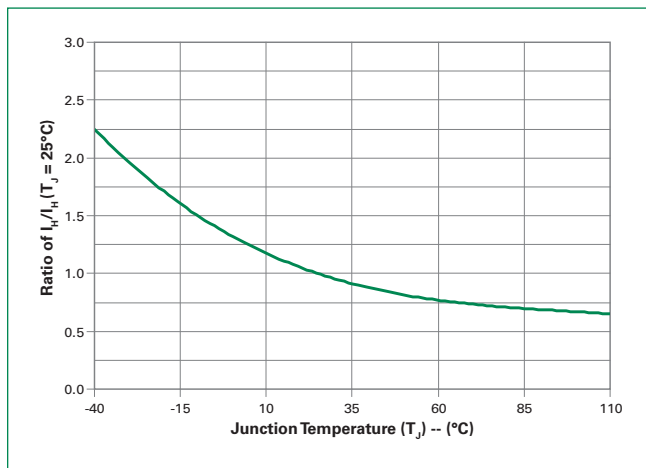


Figure 4: Normalized DC Latching Current vs. Junction Temperature

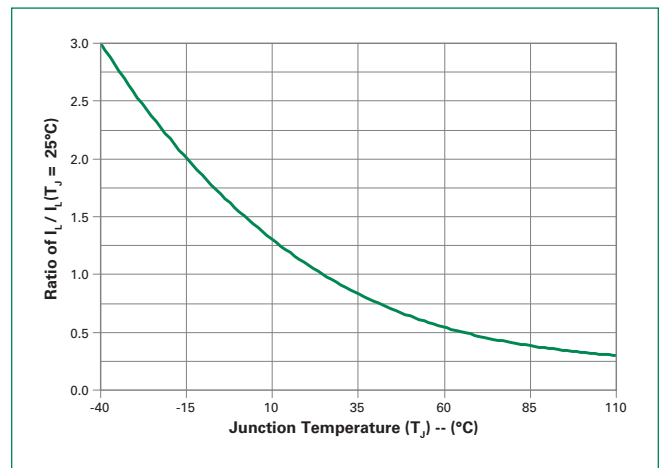


Figure 5: On-State Current vs. On-State Voltage (Typical)

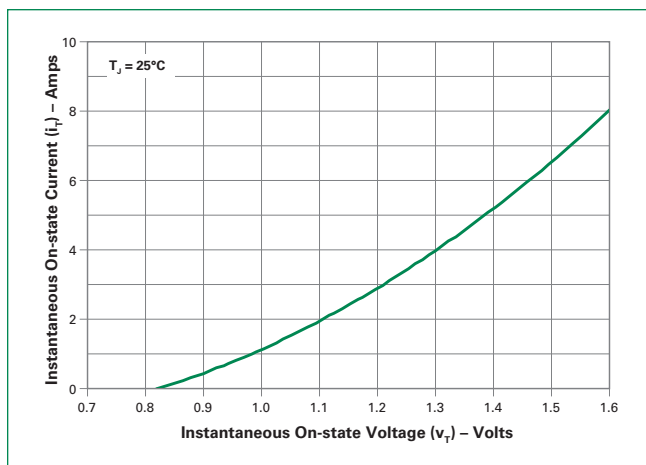


Figure 6: Power Dissipation (Typical) vs. RMS On-State Current

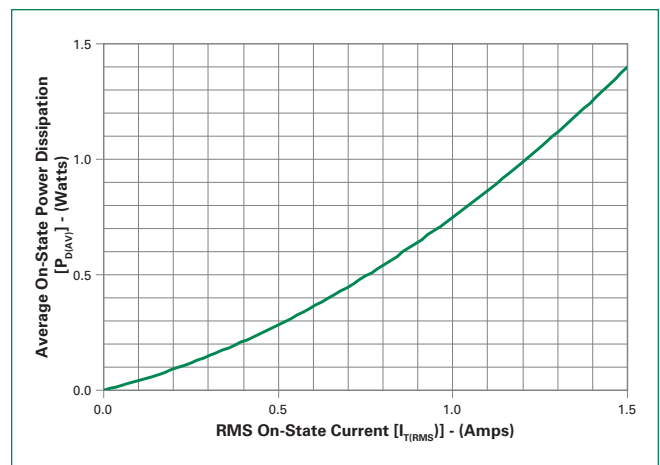


Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current

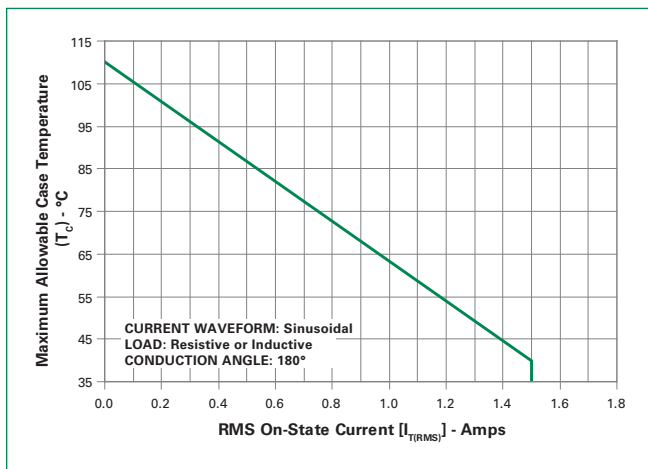


Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current

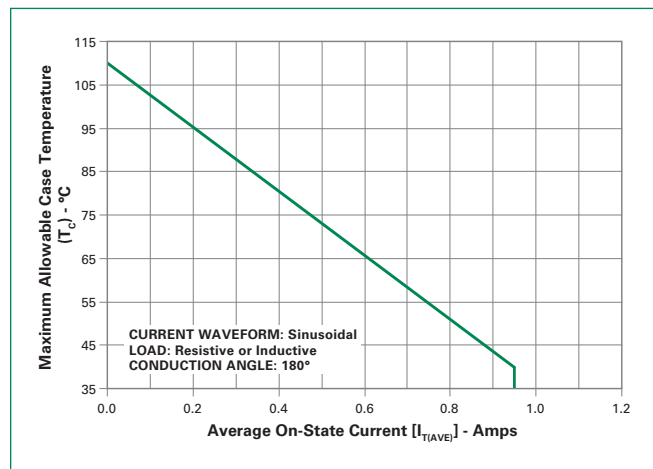


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

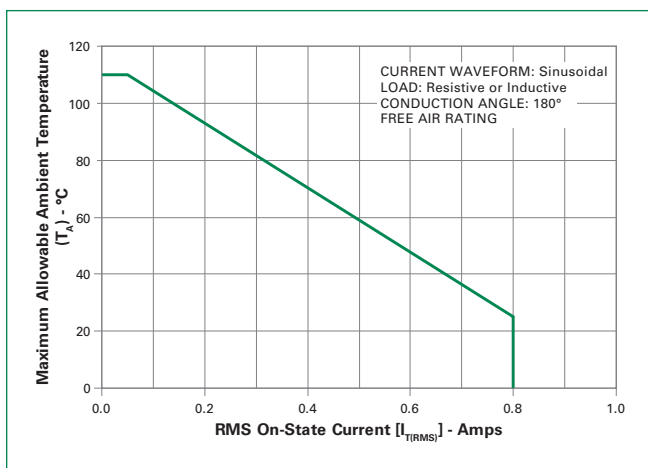


Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current

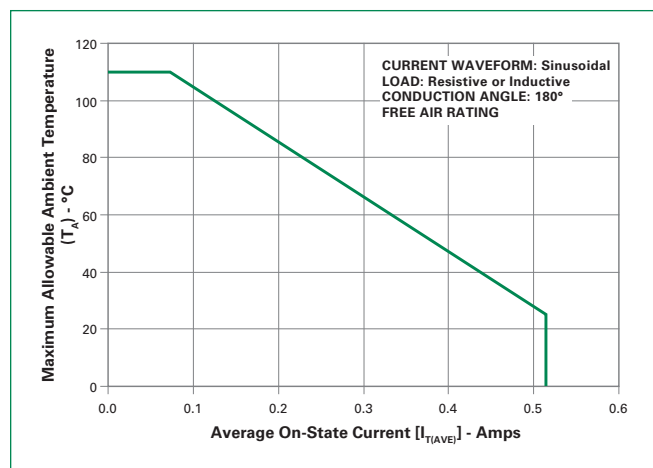


Figure 11: Peak Repetitive Capacitor Discharge Current

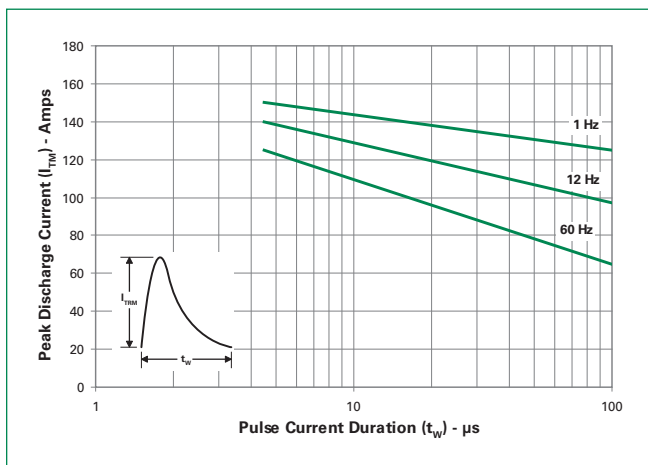


Figure 12: Peak Repetitive Sinusoidal Pulse Current

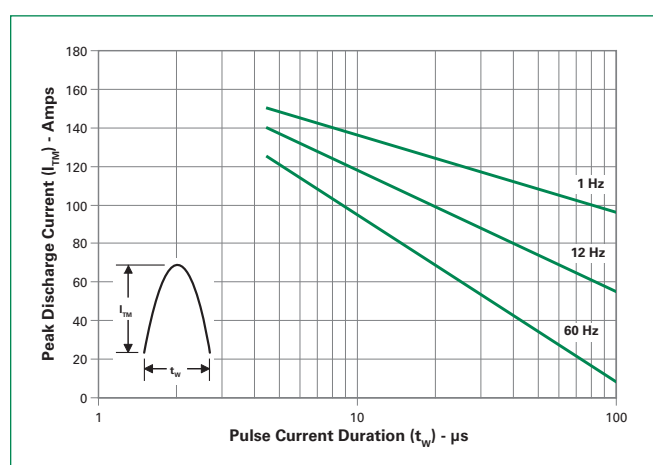


Figure 13: Surge Peak On-State Current vs. Number of Cycles

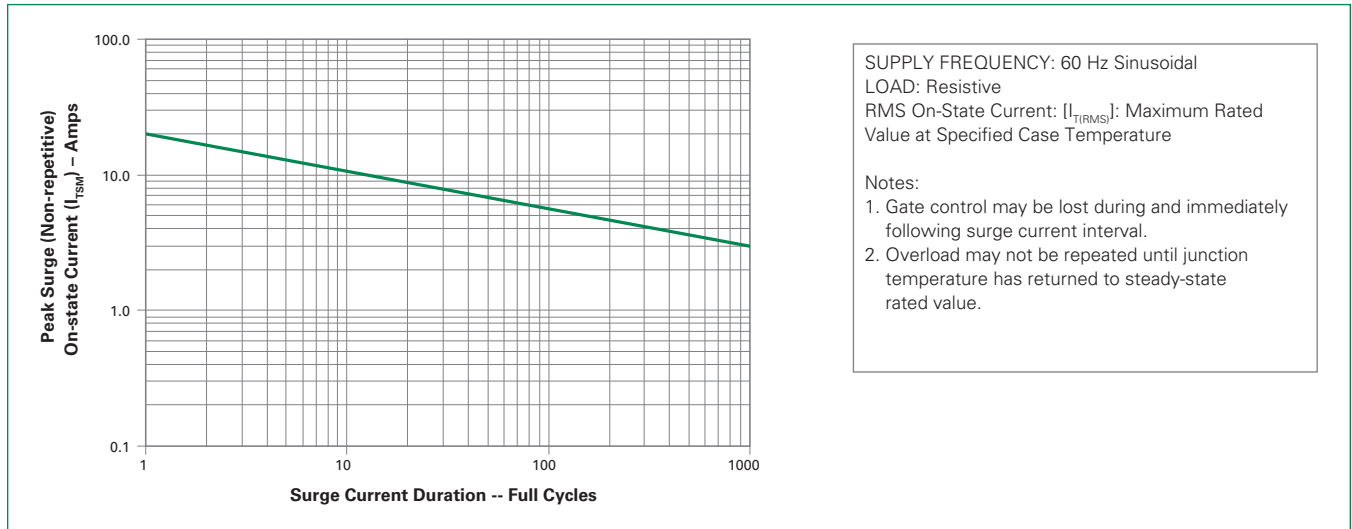
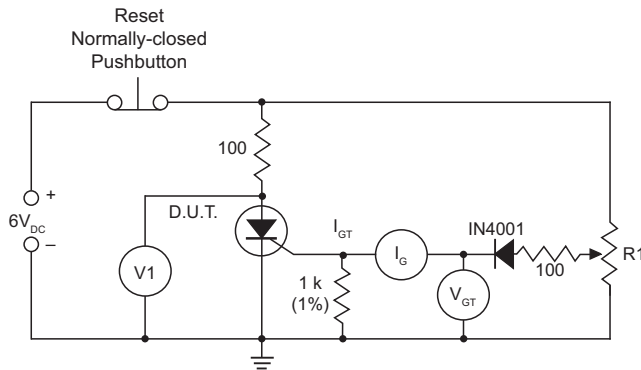


Figure 14: Simple Test Circuit for Gate Trigger Voltage and Current



Note: V1 — 0 V to 10 V dc meter
 V_{GT} — 0 V to 1 V dc meter
 I_G — 0 mA to 1 mA dc milliammeter
R1 — 1 k potentiometer

To measure gate trigger voltage and current, raise gate voltage (V_{GT}) until meter reading V1 drops from 6 V to 1 V. Gate trigger voltage is the reading on V_{GT} just prior to V1 dropping. Gate trigger current I_{GT} Can be computed from the relationship

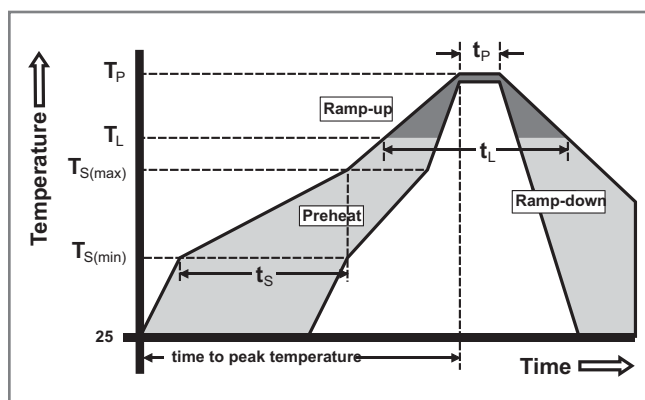
$$I_{GT} = I_G - \frac{V_{GT}}{1000} \text{ Amps}$$

where I_G is reading (in amperes) on meter just prior to V1 dropping

Note: I_{GT} may turn out to be a negative quantity (trigger current flows out from gate lead). If negative current occurs, I_{GT} value is not a valid reading. Remove 1 k resistor and use I_G as the more correct I_{GT} value. This will occur on 12 μ A gate products.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matt Tin-plated/Pb-free Solder Dipped
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

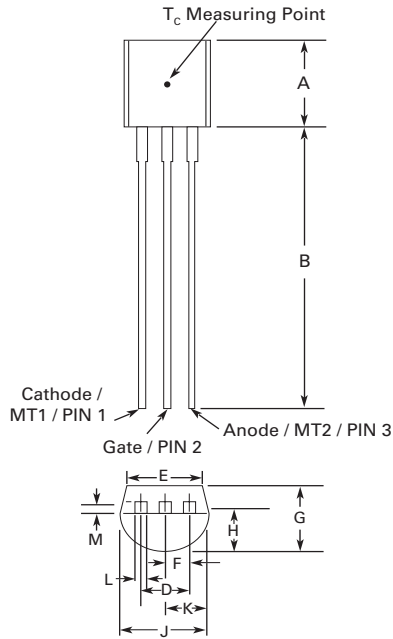
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 110°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions – TO-92 (E Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500		12.70	
D	0.095	0.105	2.41	2.67
E	0.150		3.81	
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43

All leads insulated from case. Case is electrically nonconductive.

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
TCR22-6	X				200μA	Sensitive SCR	TO-92
TCR22-8		X			200μA	Sensitive SCR	TO-92

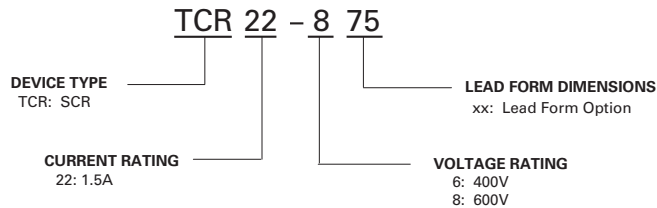
Note: x = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
TCR22-x	TCR22-x	0.19 g	Bulk	2000
TCR22-xRP	TCR22-x	0.19 g	Reel Pack	2000
TCR22-xAP	TCR22-x	0.19 g	Ammo Pack	2000

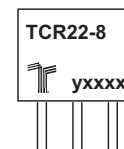
Note: x = Voltage

Part Numbering System



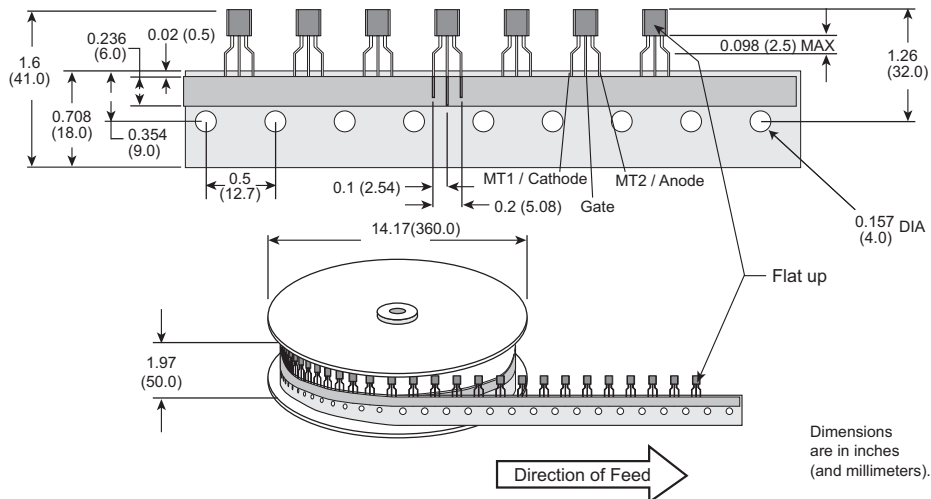
Part Marking System

TO-92 (E Package)



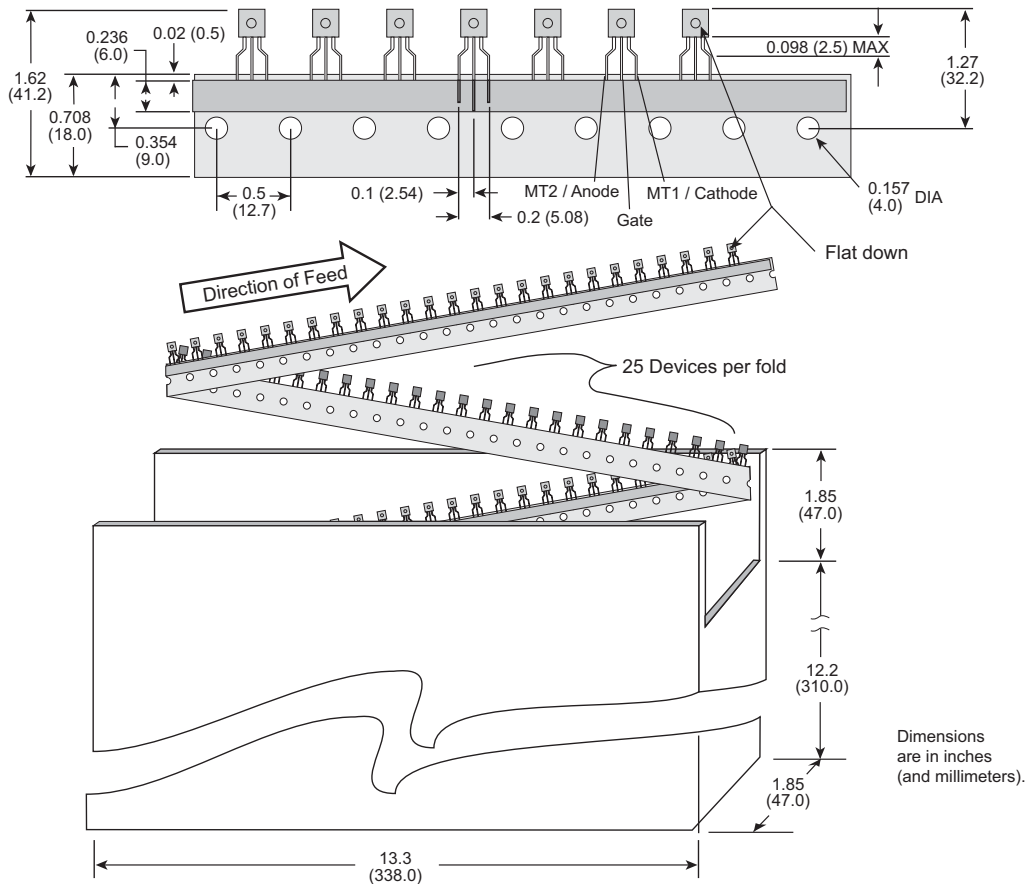
TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards

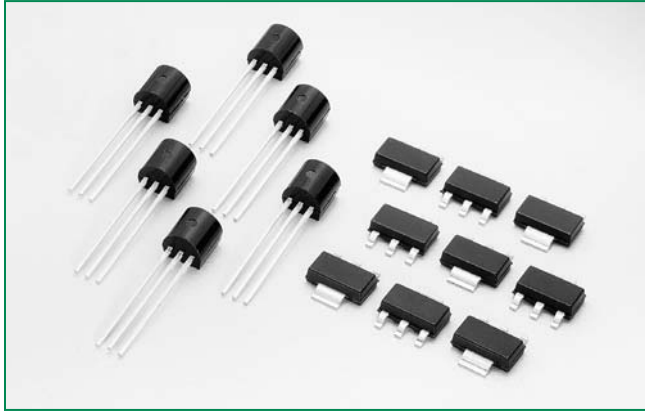


TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards



RoHS Sx02xS Series



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	1.5	A
V_{DRM}/V_{RRM}	400 to 600	V
I_{GT}	200	μA

Applications

The Sx02xS EV series is specifically designed for Gas Ignition applications that require high pulse surge current capability.

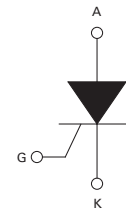
Description

New 1.5 Amp sensitive gate SCR series offers high static dv/dt with low turn off time (t_q) through small die planar construction design. All SCR's junctions are glass-passivated to ensure long term reliability and parametric stability.

Features

- RoHS compliant
- Thru hole and surface mount packages
- Surge capability > 15Amps
- Blocking voltage (V_{DRM}/V_{RRM}) capability — up to 600V
- High dv/dt noise immunity
- Improved turn-off time (t_q) < 35 μsec .
- Sensitive gate for direct microprocessor interface

Schematic Symbol



Absolute Maximum Ratings

Symbol	Parameter			Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-92	$T_c = 65^{\circ}C$	1.5	A	
		SOT-223	$T_L = 95^{\circ}C$			
$I_{T(AV)}$	Average on-state current	TO-92	$T_c = 65^{\circ}C$	0.95	A	
		SOT-223	$T_c = 95^{\circ}C$			
I_{TSM}	Non repetitive surge peak on-state current (Single cycle, T_J initial = $25^{\circ}C$)	TO-92 SOT-223	$F = 50$ Hz	12.5	A	
			$F = 60$ Hz	15.0		
I^2t	I^2t Value for fusing	$t_p = 10$ ms	$F = 50$ Hz	0.78	A^2s	
		$t_p = 8.3$ ms	$F = 60$ Hz	0.93		
di/dt	Critical rate of rise of on-state current $I_G = 10mA$	TO-92 SOT-223	$T_J = 125^{\circ}C$	50	$A/\mu s$	
I_{GM}	Peak gate current	$t_p = 10 \mu s$	$T_J = 125^{\circ}C$	1.0	A	
$P_{G(AV)}$	Average gate power dissipation			$T_J = 125^{\circ}C$	0.1	W
T_{stg}	Storage junction temperature range				-40 to 150	$^{\circ}C$
T_J	Operating junction temperature range				-40 to 125	$^{\circ}C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Sx02xS		Unit
			Min	Max	
I_{GT}	DC Gate Trigger Current	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	15	200	μA
V_{GT}	DC Gate Trigger Voltage		—	0.8	V
V_{GRM}	Peak Reverse Gate Voltage	$I_{RG} = 10\mu\text{A}$	5	—	V
I_H	Holding Current	$R_{GK} = 1\ \text{k}\Omega$	—	5	mA
$(dv/dt)_s$	Critical Rate-of-Rise of Off-State Voltage	$T_J = 125^\circ\text{C}$ $V_D = V_{DRM} / V_{RRM}$ Exponential Waveform $R_{GK} = 1\ \text{k}\Omega$	25	—	V/ μs
t_q	Turn-Off Time	$T_J = 125^\circ\text{C} @ 600\text{V}$ $R_{GK} = 1\ \text{k}\Omega$	—	35	μs
t_{gt}	Turn-On Time	$I_G = 10\text{mA}$ PW = 15 μsec $I_T = 3.0\text{A}$ (pk)	—	3	μs

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Value		Unit
			Min	Max	
V_{TM}	Peak On-State Voltage	$I_{TM} = 3.0\text{A}$ (pk)	—	1.70	V
I_{DRM}	Off-State Current, Peak Repetitive	$T_J = 25^\circ\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$	—	5	μA
		$T_J = 125^\circ\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$	—	500	μA

Thermal Resistances

Symbol	Description	Test Conditions		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	$I_T = 1.5\text{A}_{(RMS)}$ ¹	TO-92	50	$^\circ\text{C/W}$
			SOT-223	25	
$R_{th(j-a)}$	Junction to ambient	$I_T = 1.5\text{A}_{(RMS)}$ ¹	TO-92	160	$^\circ\text{C/W}$
			SOT-223	60	

¹ 60Hz AC resistive load condition, 100% conduction.

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

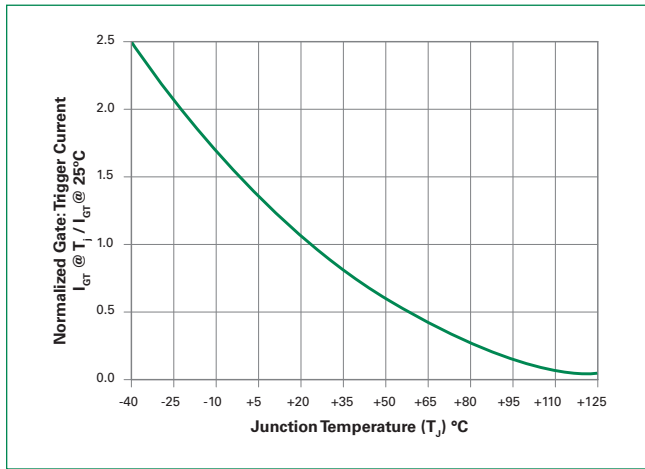


Figure 2: Normalized DC Holding Current vs. Junction Temperature

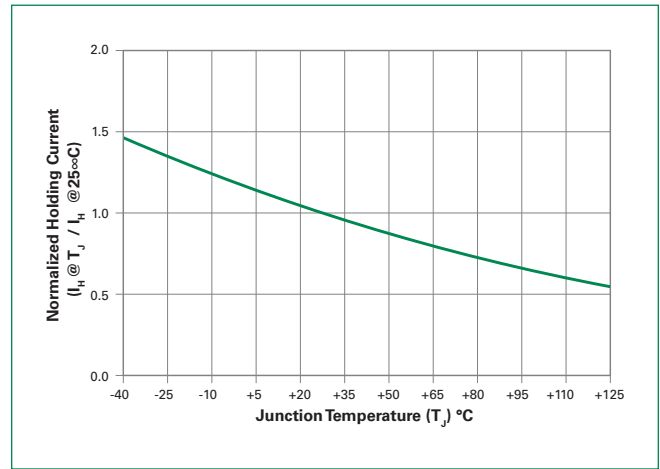


Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

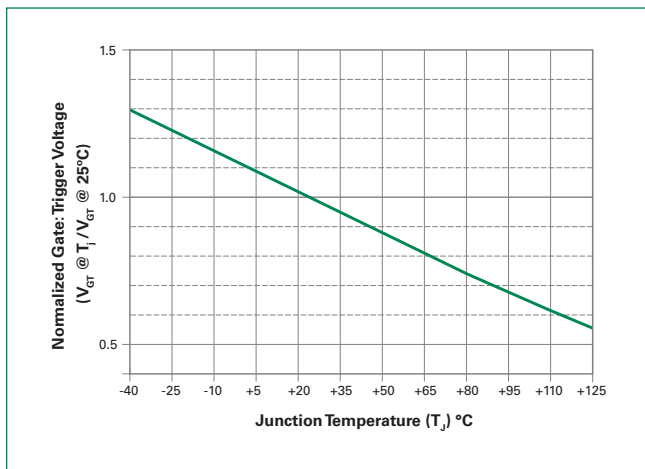


Figure 4: Power Dissipation (Typical) vs. RMS On-State Current

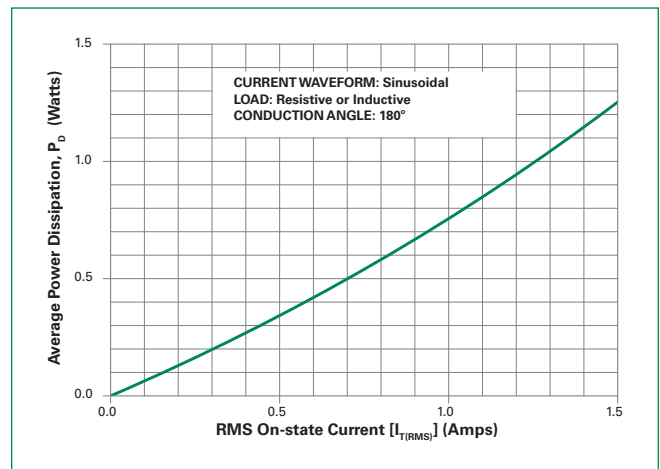


Figure 5: Maximum Allowable Case Temperature vs. On-State Current

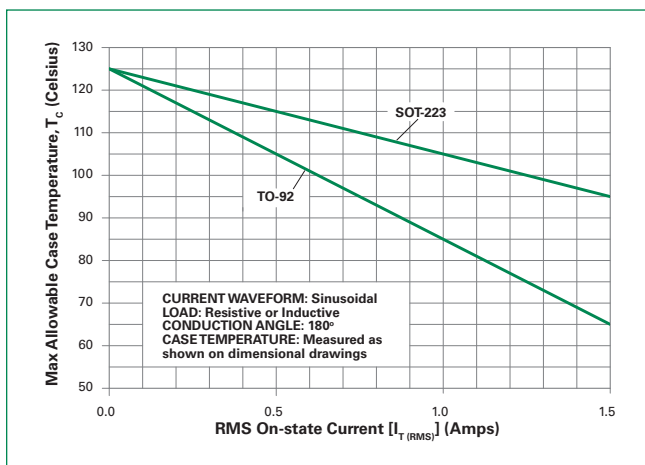
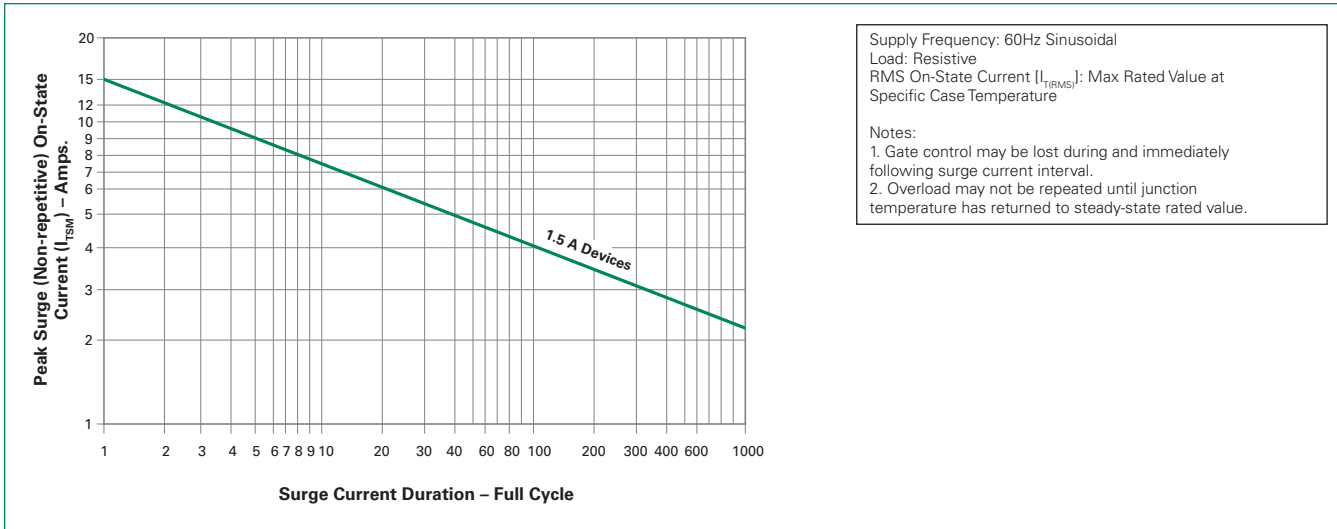
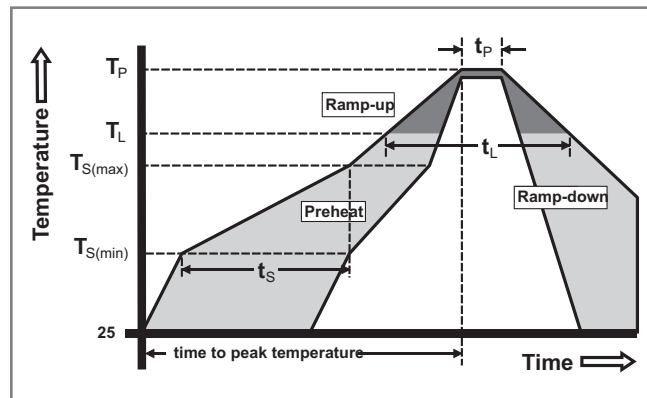


Figure 6: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{S(min)}$)	150°C
	- Temperature Max ($T_{S(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{S(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.
Lead Material	Copper Alloy

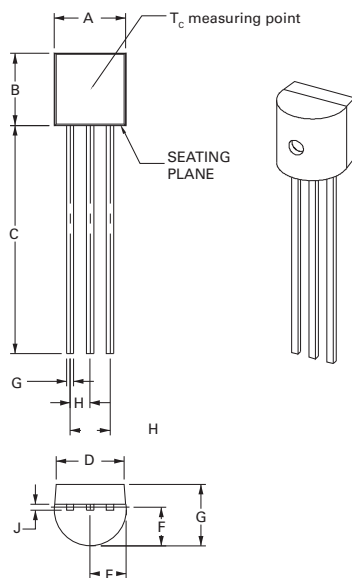
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

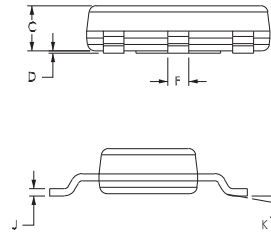
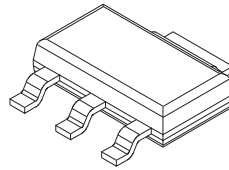
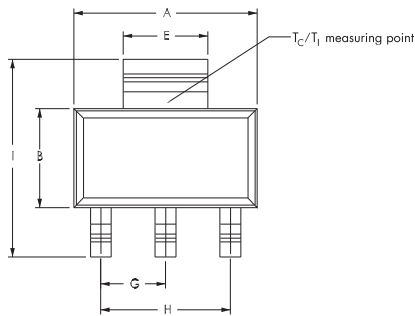
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-92 (E Package)

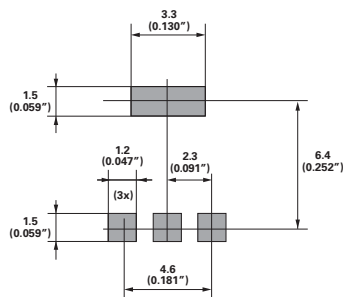


Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.175	—	0.205	4.450	—	5.200
B	0.170	—	0.210	4.320	—	5.330
C	0.500	—	—	12.700	—	—
D	0.135	0.165	—	3.430	4.190	—
E	0.125	—	0.165	3.180	—	4.190
F	0.080	0.095	0.105	2.040	2.400	2.660
G	0.016	—	0.021	0.407	—	0.533
H	0.045	0.050	0.055	1.150	1.270	1.390
I	0.095	0.100	0.105	2.420	2.540	2.660
J	0.015	—	0.020	0.380	—	0.500

Dimensions – SOT-223



Pad Layout for SOT-223



Dimensions in Millimeters (Inches)

Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.248	0.256	0.264	6.30	6.50	6.70
B	0.130	0.138	0.146	3.30	3.50	3.70
C	—	—	0.071	—	—	1.80
D	0.001	—	0.004	0.02	—	0.10
E	0.114	0.118	0.124	2.90	3.00	3.15
F	0.024	0.027	0.034	0.60	0.70	0.85
G	—	0.090	—	—	2.30	—
H	—	0.181	—	—	4.60	—
I	0.264	0.276	0.287	6.70	7.00	7.30
J	0.009	0.010	0.014	0.24	0.26	0.35
K	10° MAX					

Product Selector

Part Number	Voltage		Gate Sensitivity	Package
	400V	600V		
S402ES	X	—	200μA	TO-92
S602ES	—	X	200μA	TO-92
S402TS	X	—	200μA	SOT-223
S602TS	—	X	200μA	SOT-223

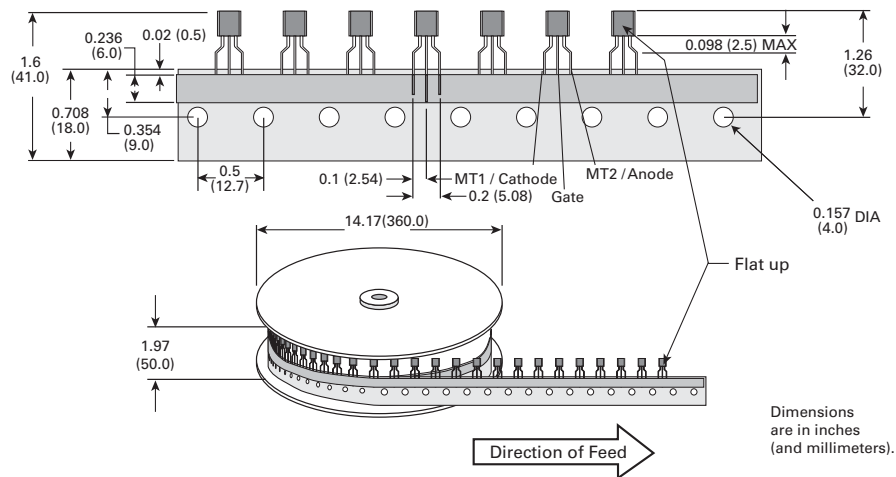
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sx02ES	Sx02ES	0.170 g	Bulk	2500
Sx02ESAP	Sx02ES	0.170 g	Ammo Pack	2000
Sx02ESRP	Sx02ES	0.170 g	Tape & Reel	2000
Sx02TSRP	Sx02TS	0.120 g	Tape & Reel	1000

Note: x = voltage

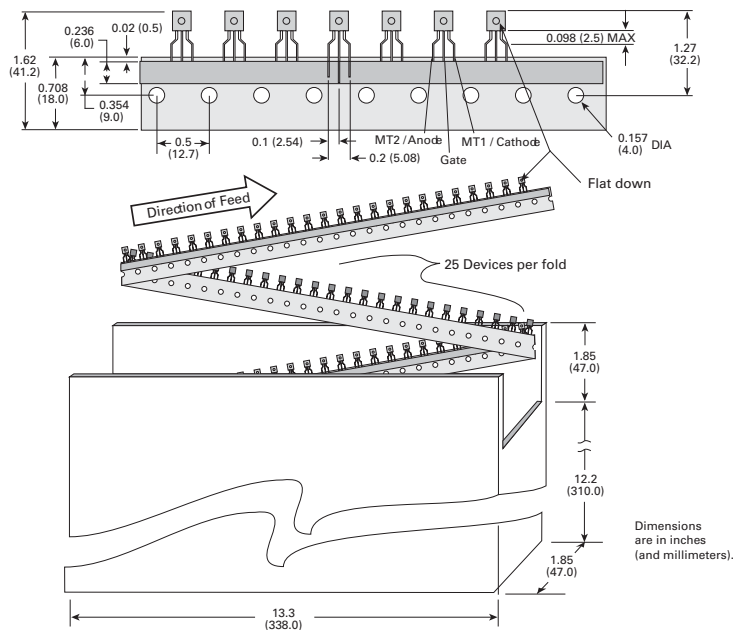
TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-B 1994 Standards

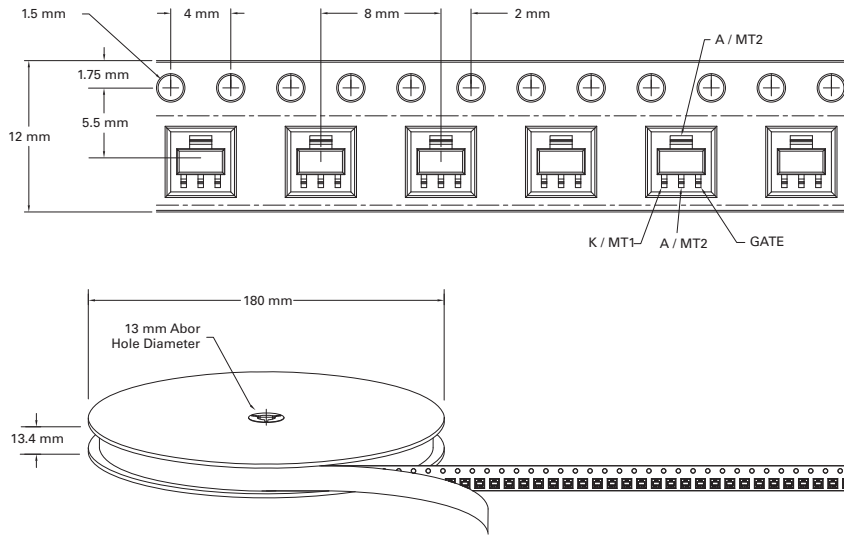


TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

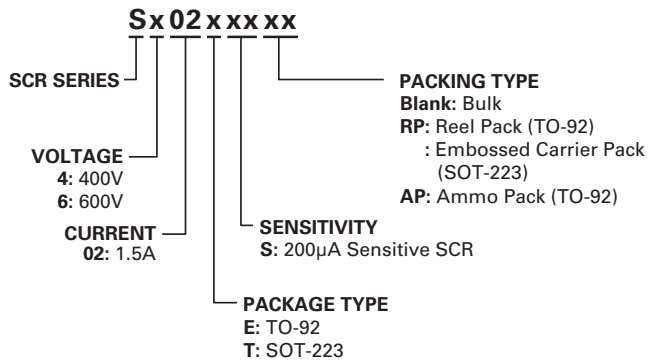
Meets all EIA-468-B 1994 Standards



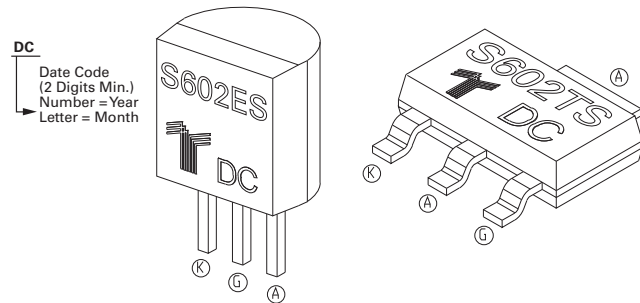
SOT-223 Reel Pack (RP) Specifications



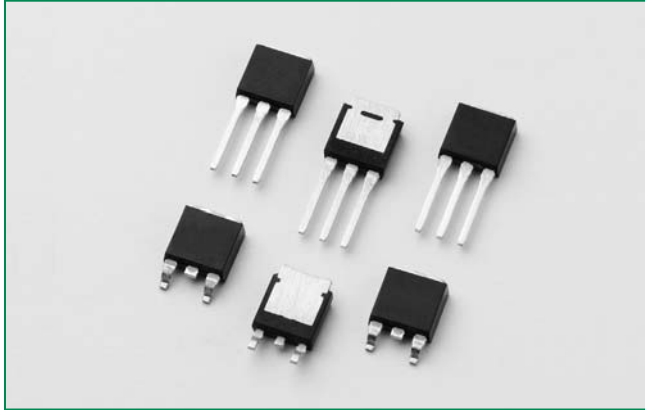
Part Numbering System



Part Marking System



RoHS **Sxx04xSx Series**



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Sensitive gate SCRs are easily triggered with microAmps of current as furnished by sense coils, proximity switches, and microprocessors.

Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 30 A

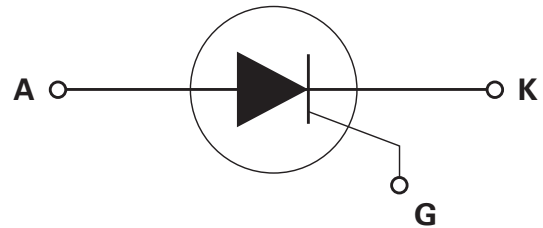
Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	400 to 600	V
I_{GT}	50 to 500	μA

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Schematic Symbol



Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 75^\circ C$	4	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50Hz$; T_J (initial) = $25^\circ C$	16	A
		single half cycle; $f = 60Hz$; T_J (initial) = $25^\circ C$	20	
I^2t	I^2t Value for fusing	$t_p = 8.3 ms$	1.6	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60Hz$; $T_J = 110^\circ C$	50	$A/\mu s$
I_{GM}	Peak gate current	$T_J = 110^\circ C$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 110^\circ C$	0.1	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ C$
T_J	Operating junction temperature range		-40 to 110	$^\circ C$

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_C = 95^\circ\text{C}$	4	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_J(\text{initial}) = 25^\circ\text{C}$	25	A
		single half cycle; $f = 60\text{Hz}$; $T_J(\text{initial}) = 25^\circ\text{C}$	30	
I^2t	I^2t Value for fusing	$t_p = 8.3\text{ ms}$	3.7	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_J = 110^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_J = 110^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 110^\circ\text{C}$	0.1	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		-40 to 110	$^\circ\text{C}$

Electrical Characteristics — ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions		Value		Unit
			Sxx04xS1	Sxx04xS2	
I_{GT}	$V_D = 6\text{V}$; $R_L = 100\ \Omega$; $R_{GK} = 1\text{kohm}$	MAX.	50	200	μA
V_{GT}		MAX.	0.8		V
dv/dt	$V_D = V_{DRM}$; $R_{GK} = 1\text{k}\Omega$	TYP.	8		$\text{V}/\mu\text{s}$
V_{GD}	$V_D = V_{DRM}$; $R_L = 3.3\text{ k}\Omega$; $T_J = 110^\circ\text{C}$	MIN.	0.2		V
V_{GRM}	$I_{GR} = 10\mu\text{A}$	MIN.	6		V
I_H	$I_T = 20\text{mA}$ (initial); $R_{GK} = 1\text{kohm}$	MAX.	4	6	mA
t_q	(1)	MAX.	50		μs
t_{gt}	$I_G = 2 \times I_{GT}$; $PW = 15\mu\text{s}$; $I_T = 8\text{A}$	TYP.	3	4	μs

Notes :

xx = voltage, x = package

(1) $I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = 10\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions		Value	Unit	
V_{TM}	Sxx04xSy $I_T = 8A$; $t_p = 380\ \mu s$		MAX.	1.6	V
I_{DRM} / I_{RRM}	$V_{DRM} / V_{RRM} - R_{GK} = 1kohm$	$T_J = 25^{\circ}C$	MAX.	2	μA
		$T_J = 110^{\circ}C$		100	

Note : xx or z = voltage, x = package, y = sensitivity

Thermal Resistances

Symbol	Parameter		Value	Unit
R _{θ(J-C)}	Junction to case (AC)	Sxx04VSy	3.8	°C/W
		Sxx04DSy	3.0	
R _{θ(J-A)}	Junction to ambient	Sxx04VSy	85	°C/W

Notes: xx = voltage, y = sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

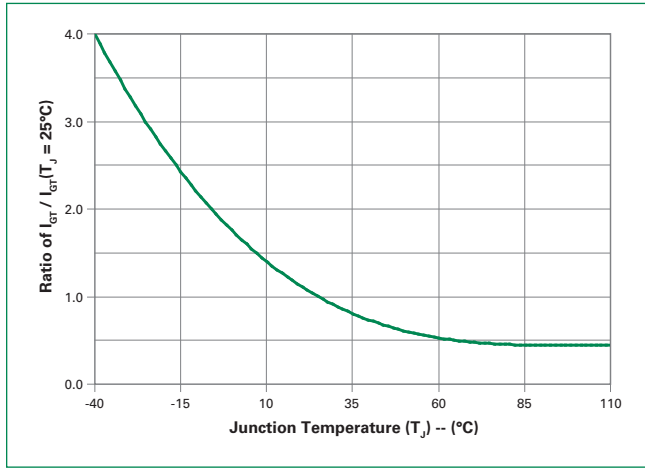


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

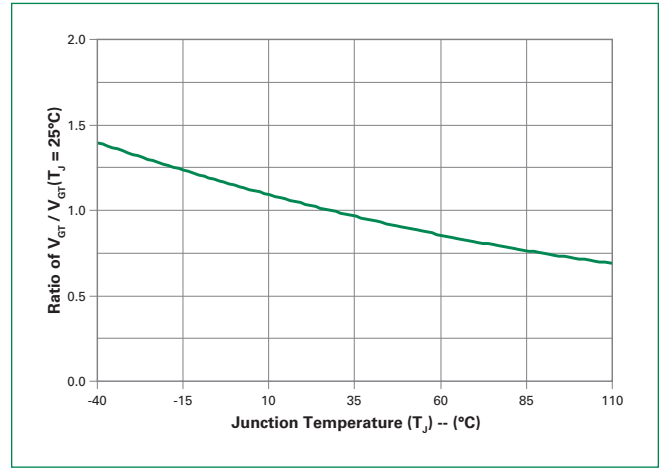


Figure 3: Normalized DC Holding Current vs. Junction Temperature

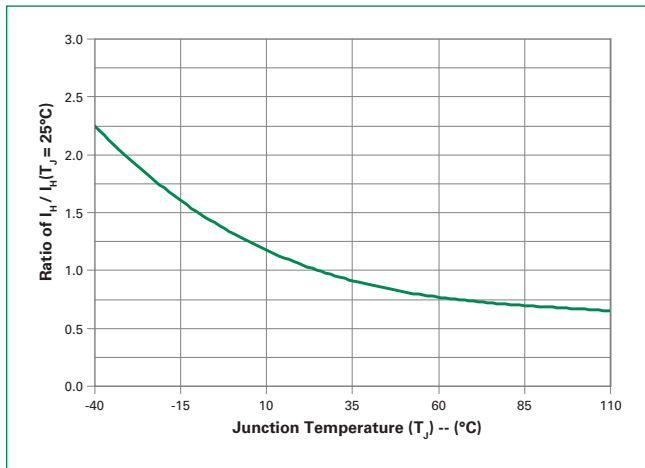


Figure 4: Normalized DC Latching Current vs. Junction Temperature

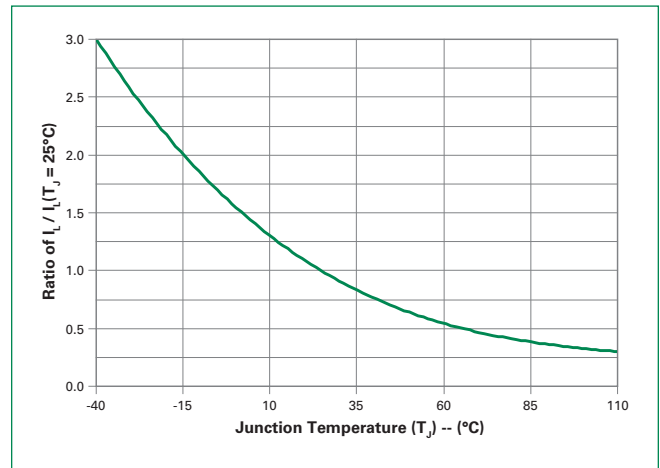


Figure 5: On-State Current vs. On-State Voltage (Typical)

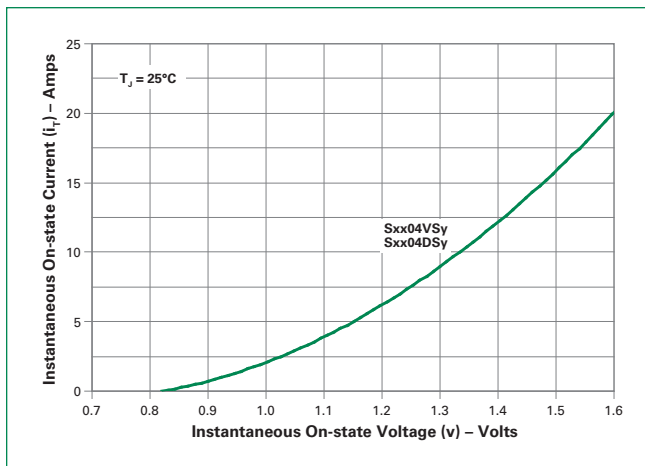
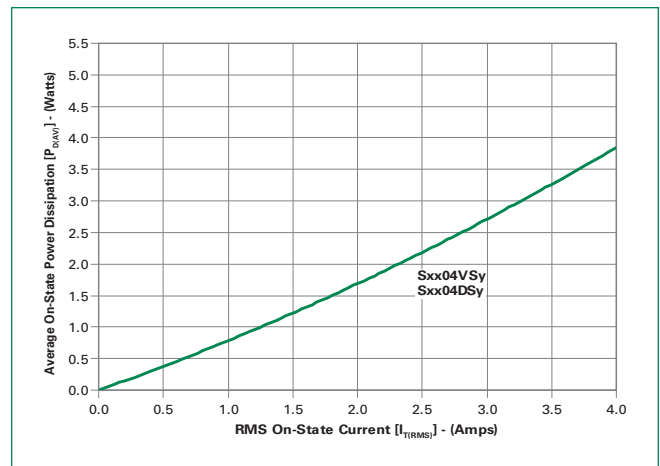


Figure 6: Power Dissipation (Typical) vs. RMS On-State Current



Note: xx or z = voltage, y = sensitivity

Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current

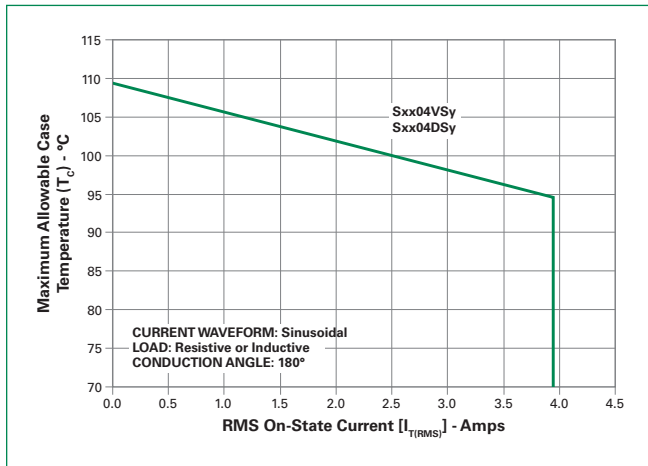


Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current

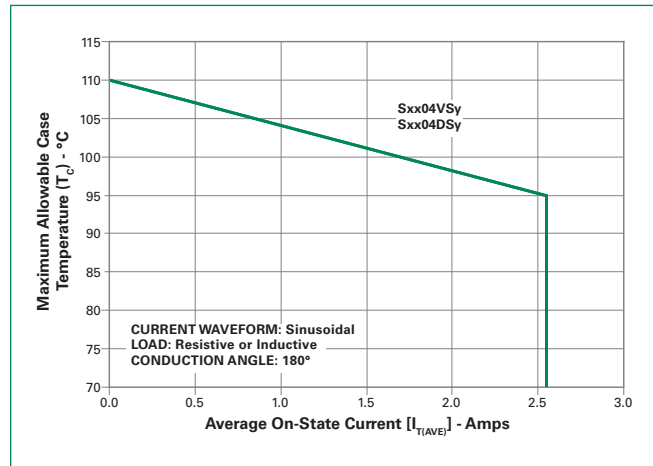


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

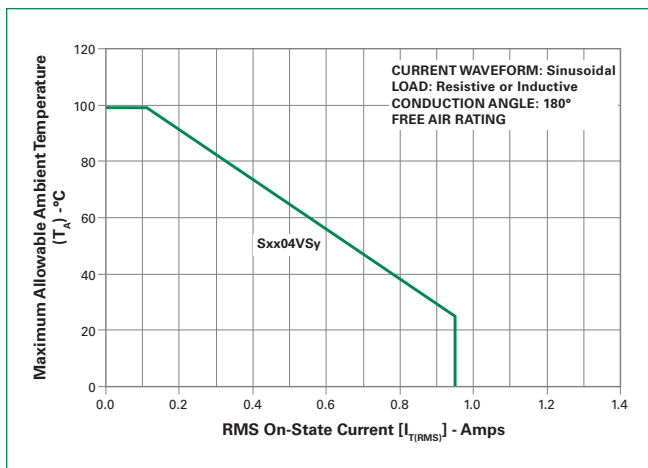


Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current

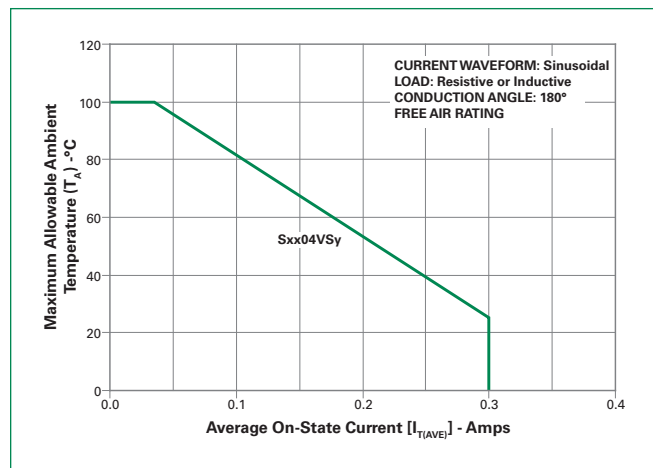


Figure 11: Peak Repetitive Capacitor Discharge Current

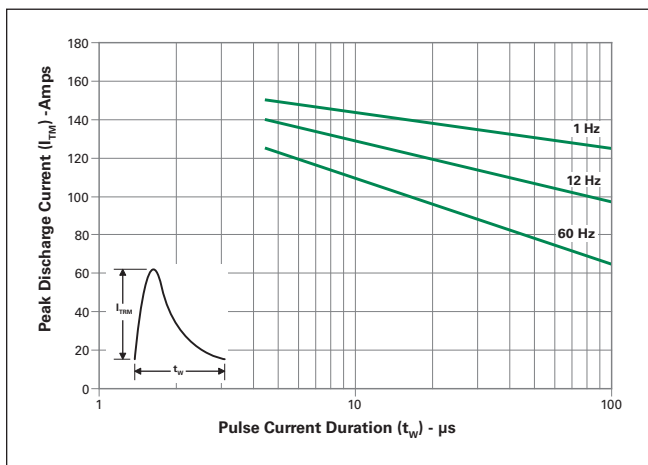
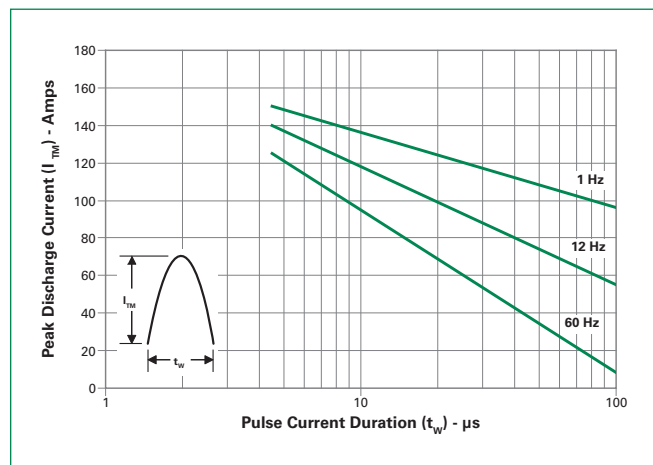
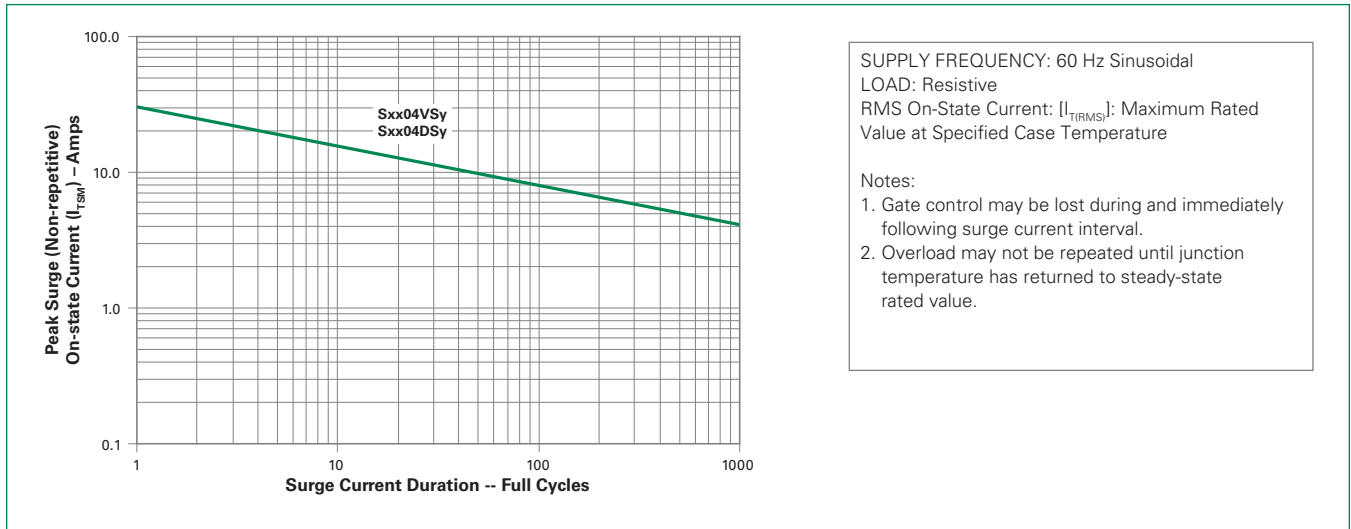


Figure 12: Peak Repetitive Sinusoidal Pulse Current



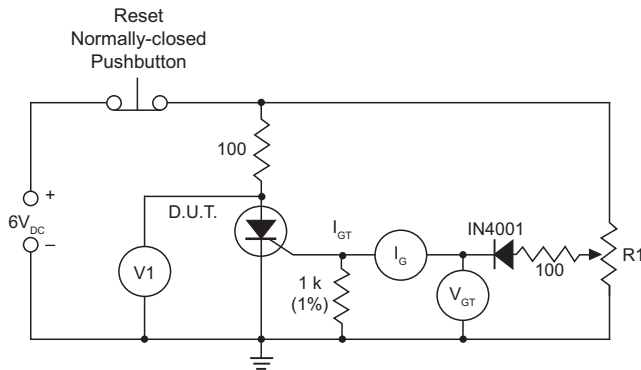
Note: xx = voltage, y = sensitivity

Figure 13: Surge Peak On-State Current vs. Number of Cycles



Note: xx or z - voltage, y = sensitivity

Figure 14: Simple Test Circuit for Gate Trigger Voltage and Current



Note: V1 — 0 V to 10 V dc meter
V_{GT} — 0 V to 1 V dc meter
I_G — 0 mA to 1 mA dc milliammeter
R1 — 1 k potentiometer

To measure gate trigger voltage and current, raise gate voltage (V_{GT}) until meter reading V1 drops from 6 V to 1 V. Gate trigger voltage is the reading on V_{GT} just prior to V1 dropping. Gate trigger current I_{GT} can be computed from the relationship

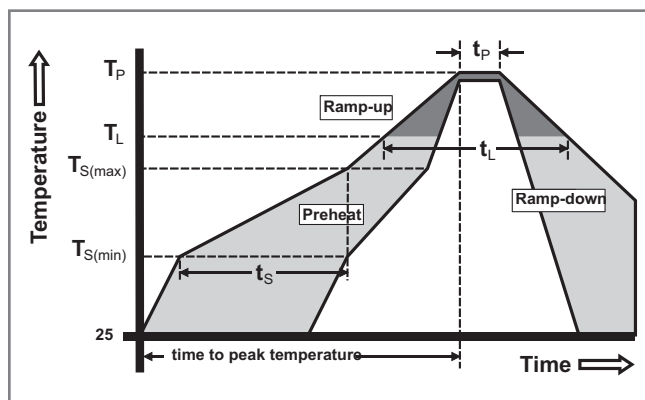
$$I_{GT} = I_G - \frac{V_{GT}}{1000} \text{ Amps}$$

where I_G is reading (in amperes) on meter just prior to V1 dropping

Note: I_{GT} may turn out to be a negative quantity (trigger current flows out from gate lead). If negative current occurs, I_{GT} value is not a valid reading. Remove 1 k resistor and use I_G as the more correct I_{GT} value. This will occur on 12 μ A gate products.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

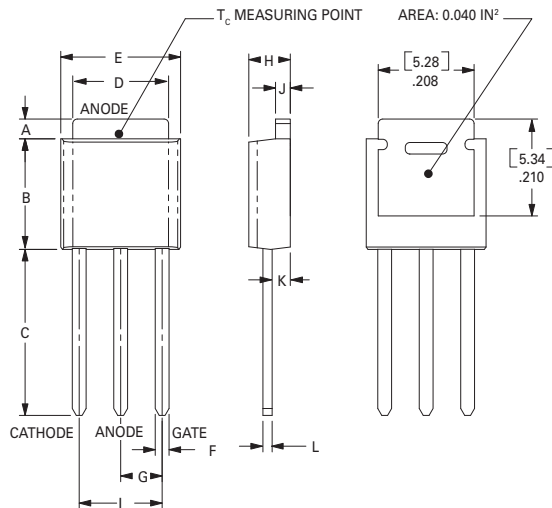
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

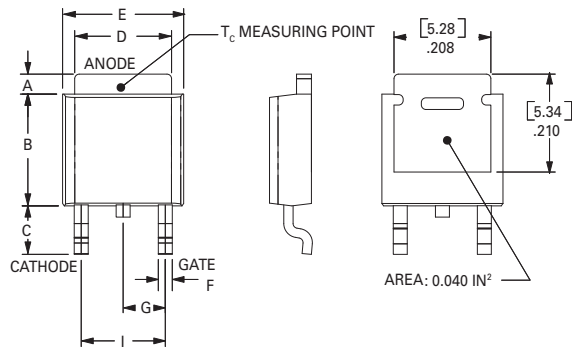
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours , $R_{gk} = 1\text{ kohms}$
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwelltime at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole

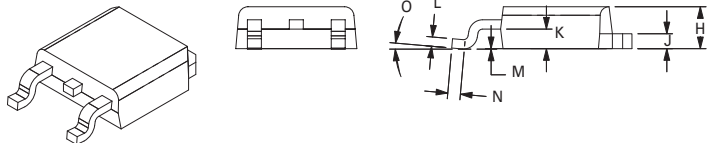
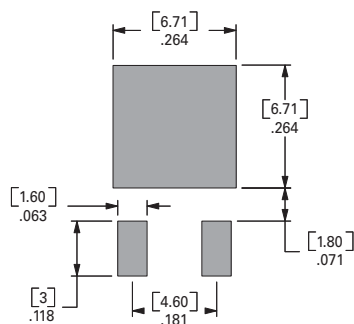


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



Pad Layout for TO-252AA (D-Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx04DS1	X	X			50μA	Sensitive SCR	TO-252
Sxx04DS2	X	X			200μA	Sensitive SCR	TO-252
Sxx04VS1	X	X			50μA	Sensitive SCR	TO-251
Sxx04VS2	X	X			200μA	Sensitive SCR	TO-251

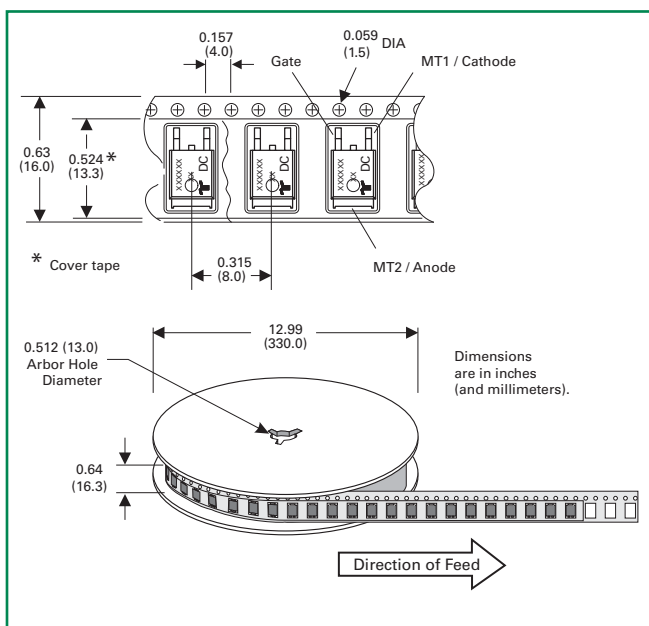
Note: xx = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx04DSyTP	Sxx04DSy	0.3g	Tube	750
Sxx04DSyRP	Sxx04DSy	0.3g	Embossed Carrier	2500
Sxx04VSyTP	Sxx04VSy	0.4g	Tube	750

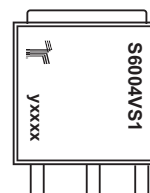
Note: xx = voltage, y = sensitivity

TO-252 Embossed Carrier Reel Pack (RP) Specs

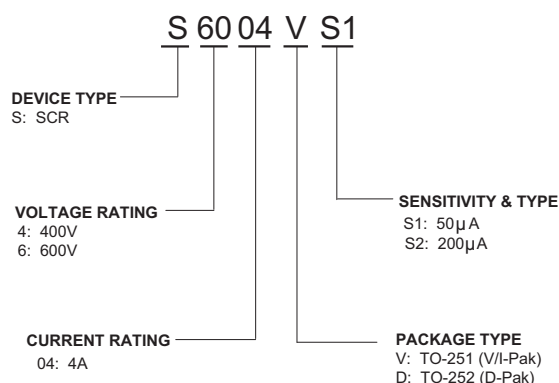


Part Marking System

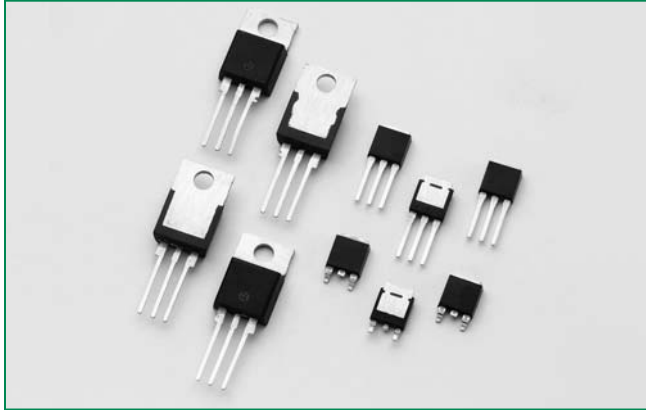
TO-252AA – (D Package)
TO-251AA – (V Package)



Part Numbering System



RoHS Sxx06xSx & Sxx06x Series



Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	0.2 to 15	mA

Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Sensitive gate SCRs are easily triggered with microAmps of current as furnished by sense coils, proximity switches, and microprocessors. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

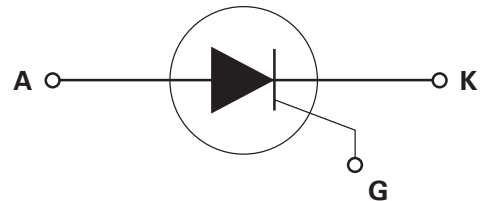
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 100 A

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Absolute Maximum Ratings — Sensitive SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx06LSy $T_c = 80^\circ\text{C}$	6	A
		Sxx06RSy $T_c = 95^\circ\text{C}$		
		Sxx06DSy Sxx06VSY		
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j (\text{initial}) = 25^\circ\text{C}$	83	A
		single half cycle; $f = 60\text{Hz}$; $T_j (\text{initial}) = 25^\circ\text{C}$	100	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	41	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_j = 110^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate current	$T_j = 110^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 110^\circ\text{C}$	0.1	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 110	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard SCRs

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current	Sxx06L	T _C = 100°C	6	A
		Sxx06R	T _C = 110°C		
		Sxx06D Sxx06V			
I _{TSM}	Peak non-repetitive surge current	single half cycle; f = 50Hz; T _J (initial) = 25°C		83	A
		single half cycle; f = 60Hz; T _J (initial) = 25°C		100	
I ² t	I ² t value for fusing	t _p = 8.3 ms		41	A ² s
di/dt	Critical rate-of-rise of on-state current	f = 60Hz; T _J =125°C		100	A/μs
I _{GTM}	Peak gate current	T _J = 125°C		2	A
P _{G(AV)}	Average gate power dissipation	T _J = 125°C		0.5	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 125	°C

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive SCRs

Symbol	Test Conditions		Value		Unit
			Sxx06xS2	Sxx06xS3	
I_{GT}	$V_D = 6\text{V}$ $R_L = 100 \Omega$	MAX.	200	500	μA
V_{GT}		MAX.	0.8		V
dv/dt	$V_D = V_{DRM}$; $R_{GK} = 1\text{k}\Omega$; $T_J = 110^\circ\text{C}$	TYP.	8		$\text{V}/\mu\text{s}$
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 110^\circ\text{C}$	MIN.	0.2		V
V_{GRM}	$I_{GR} = 10\mu\text{A}$	MIN.	6		V
I_H	$I_T = 20\text{mA}$ (initial)	MAX.	6	8	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = -30\text{A}/\mu\text{s}$	MAX.	50	45	μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\mu\text{s}$ $I_T = 12\text{A}$	TYP.	4	5	μs

Note: xx = voltage, x = package

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard SCRs

Symbol	Test Conditions			Value	Unit
				Sxx06x	
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$		MAX.	15	mA
V_{GT}			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^\circ\text{C}$	400V	MIN.	350	$\text{V}/\mu\text{s}$
		600V		300	
		800V		250	
		1000V		100	
	$V_D = V_{DRM}$; gate open; $T_J = 125^\circ\text{C}$	400V		250	
		600V		225	
		800V		200	
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	30	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = -30\text{A}/\mu\text{s}$		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\mu\text{s}$ $I_T = 12\text{A}$		TYP.	2	μs

Note: xx = voltage, x = package

Static Characteristics

Symbol	Test Conditions					Value	Unit
V _{TM}	I _T = 12A; t _p = 380 μs				MAX.	1.6	V
I _{DRM} / I _{RRM}	V _{DRM} = V _{RRM}	Sxx06xyy	T _J = 25°C	400 – 600V	MAX.	5	μA
			T _J = 110°C	400 – 600V		250	
		Sxx06x	T _J = 25°C	400 – 800V		10	
				1000V		20	
			T _J = 100°C	400 – 800V		200	
				1000V		3000	
			T _J = 125°C	400 – 800V		500	

Note: xx = voltage, x = package, yy = sensitivity

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx06RSy	2.6	$^\circ C/W$
		Sxx06LSy	4.3	
		Sxx06VSy	2.4	
		Sxx06DSy	1.8	
		Sxx06R	2.5	
		Sxx06L	4.0	
		Sxx06V	2.3	
		Sxx06D	1.7	
$R_{\theta(J-A)}$	Junction to ambient	Sxx06RSy	40	$^\circ C/W$
		Sxx06LSy	65	
		Sxx06VSy	85	
		Sxx06R	40	
		Sxx06L	50	
		Sxx06V	70	

Note: xx = voltage, y = sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature (Sensitive SCR)

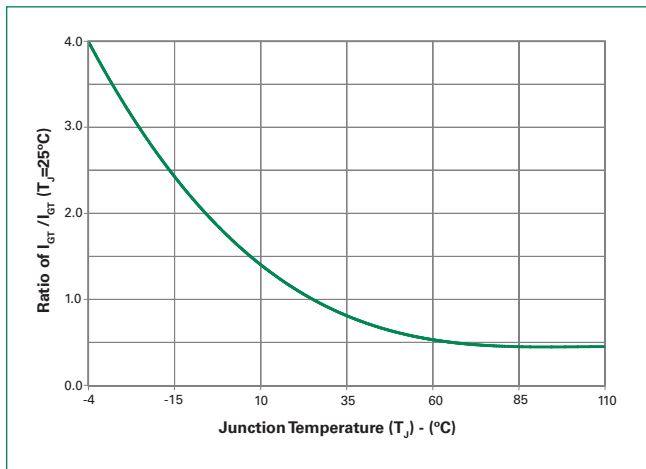


Figure 2: Normalized DC Gate Trigger Current vs. Junction Temperature (Standard SCR)

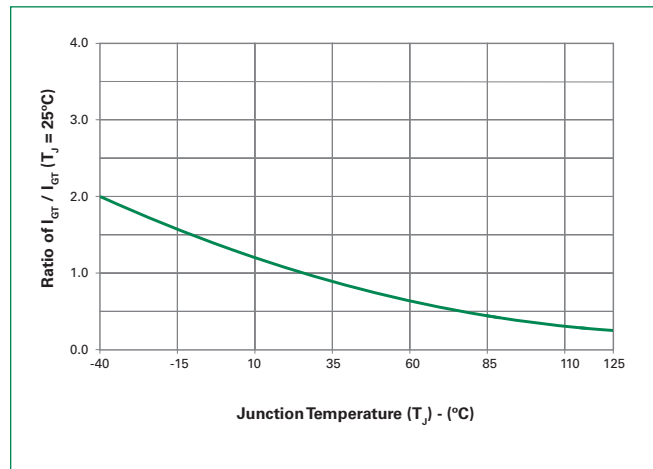


Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

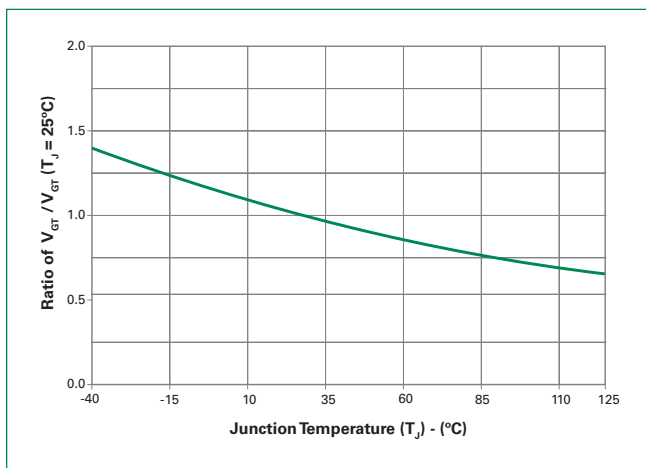


Figure 4: Normalized DC Holding Current vs. Junction Temperature

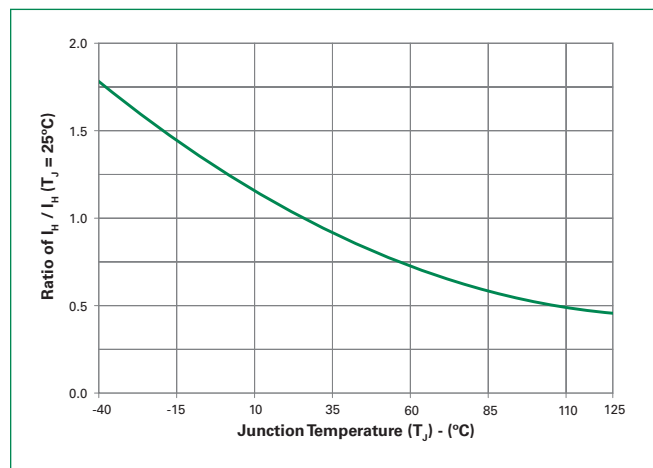


Figure 5: On-State Current vs. On-State Voltage (Typical)

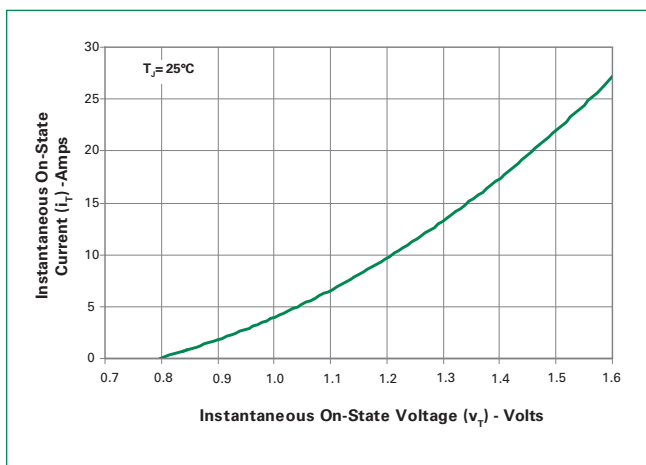


Figure 6: Power Dissipation (Typical) vs. RMS On-State Current

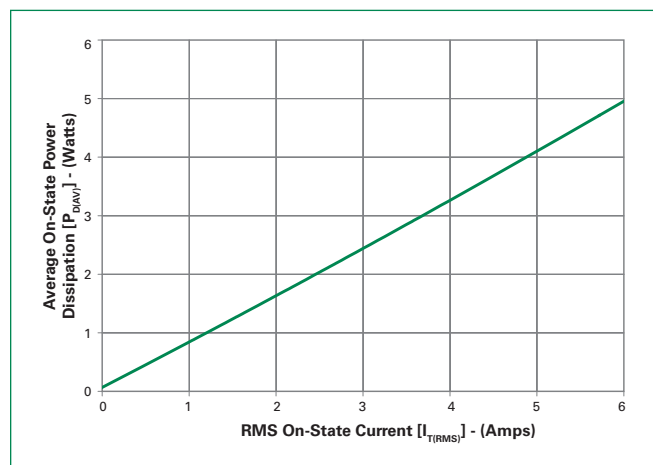


Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current

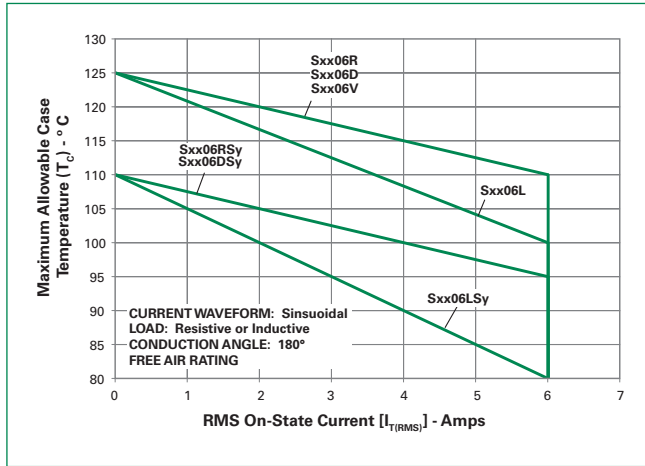


Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current

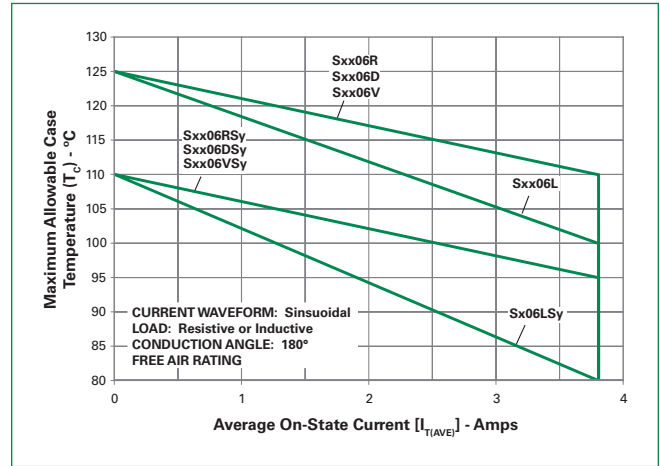


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

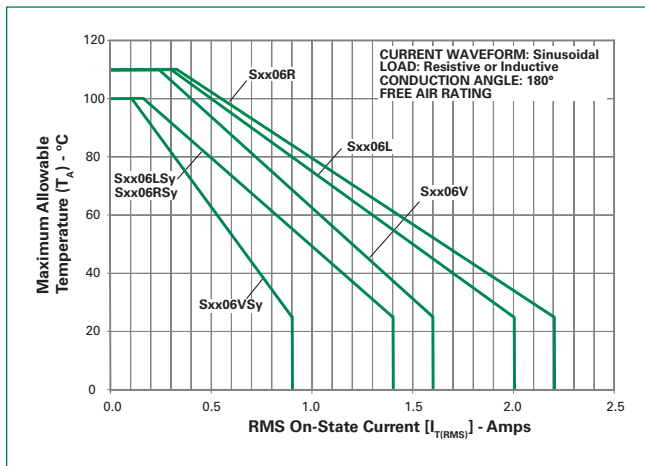
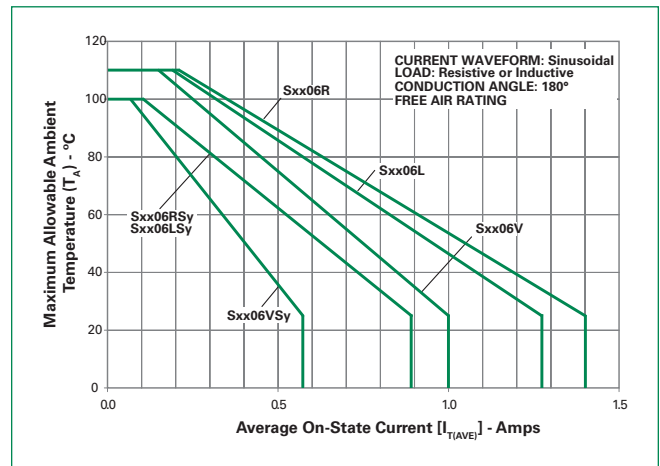


Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current



Note: xx = voltage, y = sensitivity

Figure 11: Peak Capacitor Discharge Current

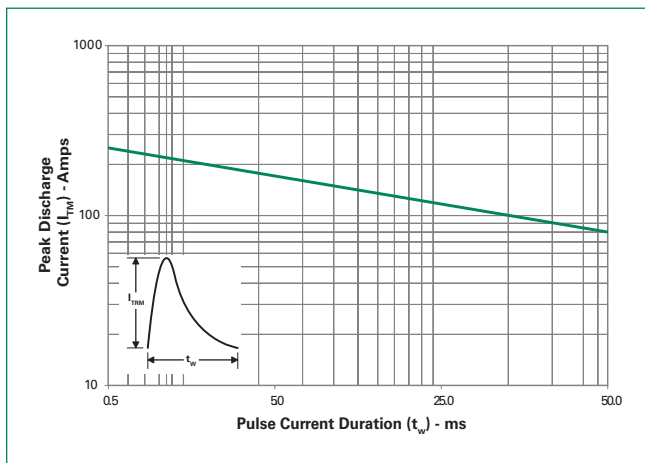


Figure 12: Peak Capacitor Discharge Current Derating

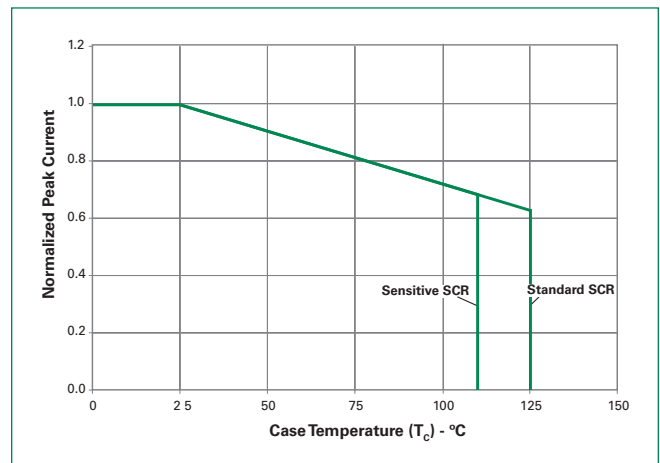
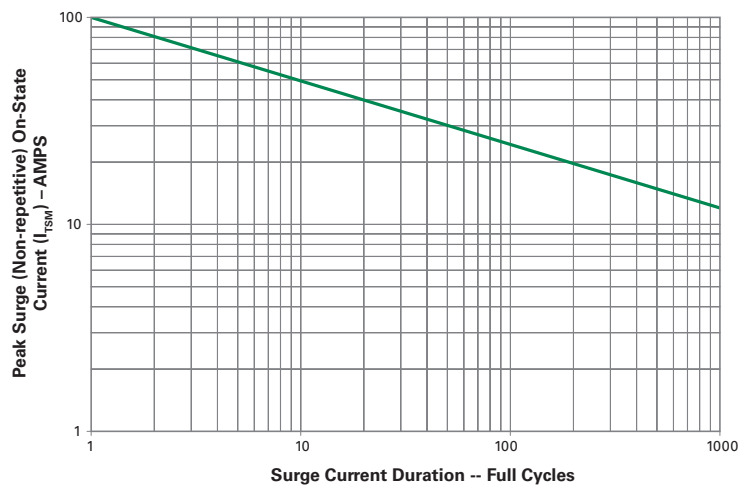


Figure 13: Surge Peak On-State Current vs. Number of Cycles



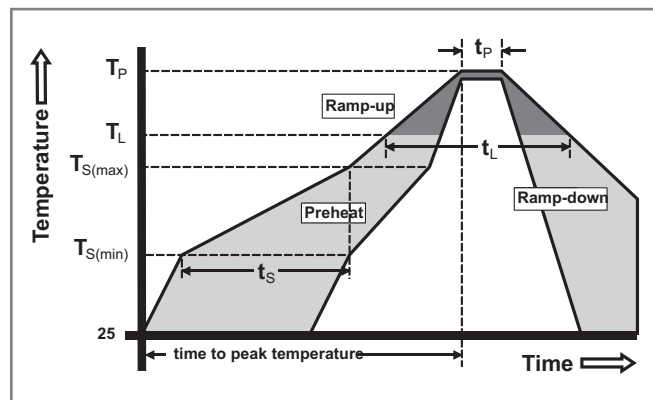
SUPPLY FREQUENCY: 60 Hz Sinusoidal
LOAD: Resistive
RMS On-State Current: [$I_{T(RMS)}$]: Maximum Rated Value at Specified Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	-Temperature Min ($T_{s(min)}$)	150°C
	-Temperature Max ($T_{s(max)}$)	200°C
	-Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	-Temperature (T_L) (Liquidus)	217°C
	-Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

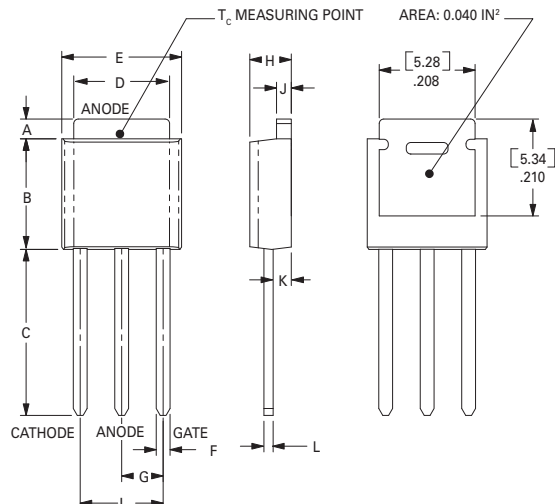
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx06RS2	X	X			0.2mA	Sensitive SCR	TO-220R
Sxx06LS2	X	X			0.2mA	Sensitive SCR	TO-220L
Sxx06VS2	X	X			0.2mA	Sensitive SCR	TO-251
Sxx06DS2	X	X			0.2mA	Sensitive SCR	TO-252
Sxx06RS3	X	X			0.5mA	Sensitive SCR	TO-220R
Sxx06LS3	X	X			0.5mA	Sensitive SCR	TO-220L
Sxx06VS3	X	X			0.5mA	Sensitive SCR	TO-251
Sxx06DS3	X	X			0.5mA	Sensitive SCR	TO-252
Sxx06R	X	X	X	X	15mA	Standard SCR	TO-220R
Sxx06L	X	X	X	X	15mA	Standard SCR	TO-220L
Sxx06V	X	X	X	X	15mA	Standard SCR	TO-251
Sxx06D	X	X	X	X	15mA	Standard SCR	TO-252

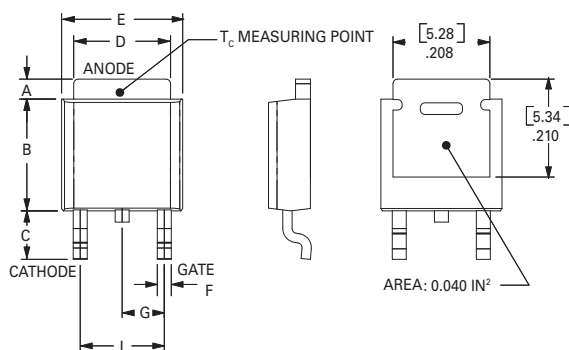
Note: xx = voltage

Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole

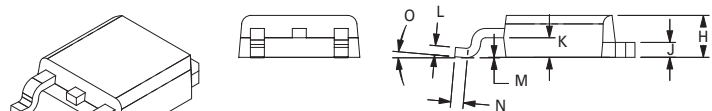
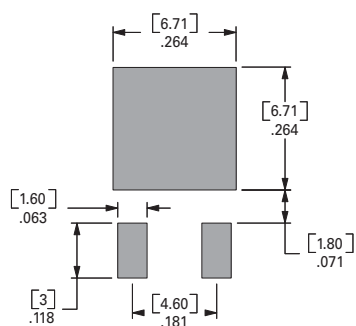


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount

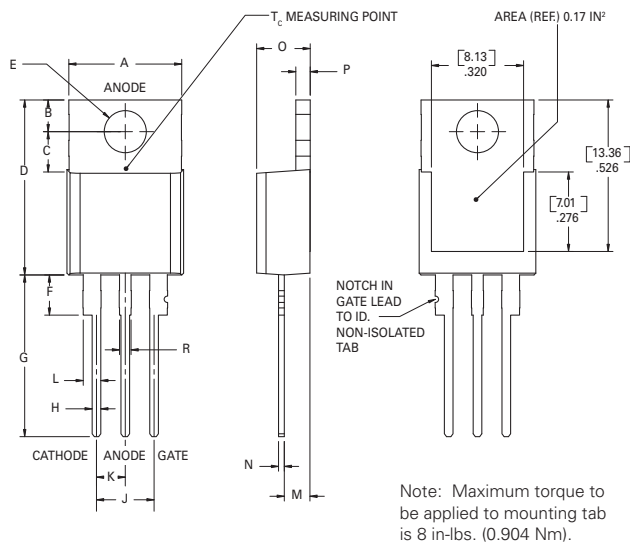


Pad Layout for TO-252AA (D-Package)



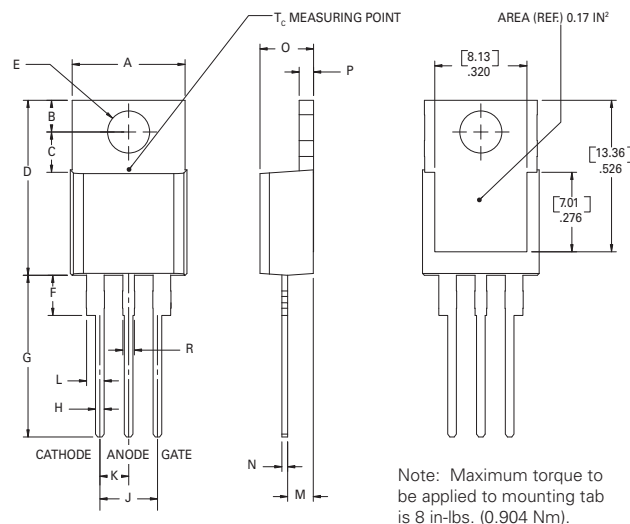
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
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O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

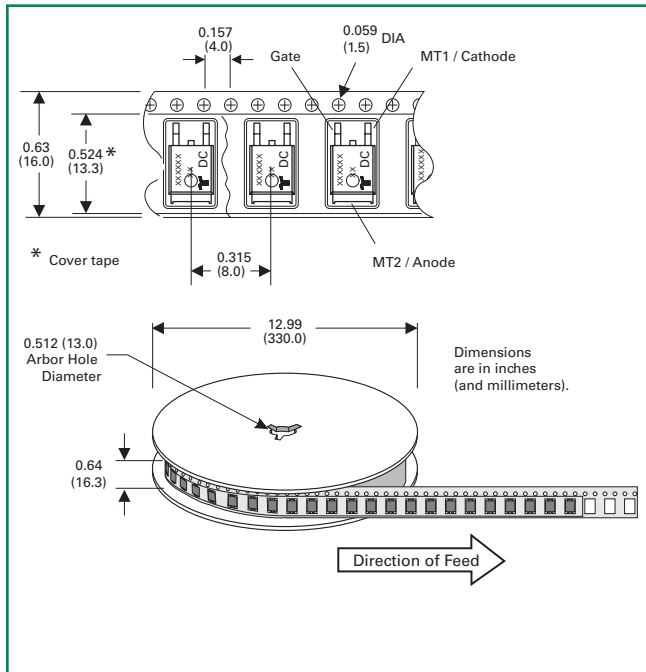
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx06L/Ryy	Sxx06L/Ryy	2.2 g	Bulk	500
Sxx06L/RyyTP	Sxx06L/Ryy	2.2 g	Tube	500
Sxx06DyyTP	Sxx06Dyy	0.3 g	Tube	750
Sxx06DyyRP	Sxx06Dyy	0.3 g	Embossed Carrier	2500
Sxx06VyyTP	Sxx06Vyy	0.4 g	Tube	750
Sxx06VyyRP	Sxx06Vyy	0.4 g	Embossed Carrier	2500
Sxx06L/R	Sxx06L/R	2.2 g	Bulk	500
Sxx06L/RTP	Sxx06L/R	2.2 g	Tube	500
Sxx06DTP	Sxx06D	0.3 g	Tube	750
Sxx06DRP	Sxx06D	0.3 g	Embossed Carrier	2500
Sxx06VTP	Sxx06V	0.4 g	Tube	750
Sxx06VRP	Sxx06V	0.4 g	Embossed Carrier	2500

Note: xx = Voltage; yy = Sensitivity

TO-252 Embossed Carrier Reel Pack (RP) Specs

Meets all EIA-481-2 Standards



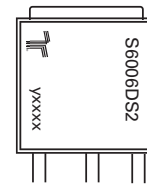
Part Marking System

TO-220AB (R and L Packages)

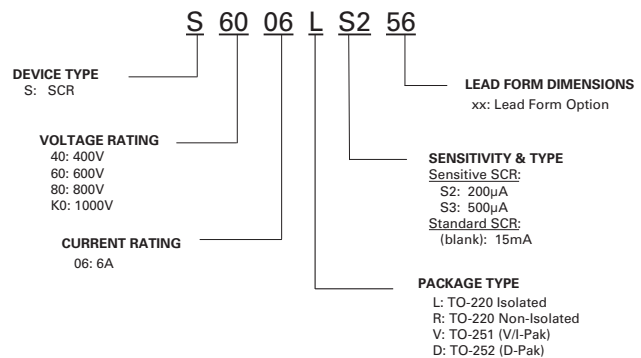


TO-251AA – (V Package)

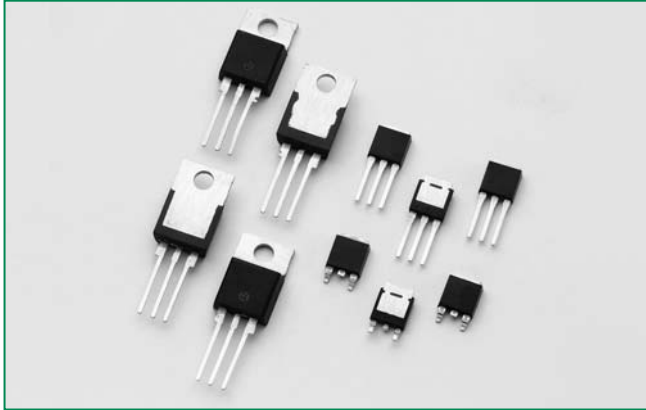
TO-252AA – (D Package)



Part Numbering System



RoHS Sxx08xSx & Sxx08x Series



Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	0.2 to 15	mA

Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Sensitive gate SCRs are easily triggered with microAmps of current as furnished by sense coils, proximity switches, and microprocessors. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

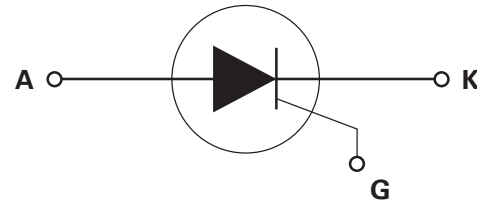
Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 100 A

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances. Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Absolute Maximum Ratings — Sensitive SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx08LSy $T_c = 80^\circ\text{C}$	8	A
		Sxx08RSy Sxx08DSy Sxx08VSy $T_c = 95^\circ\text{C}$		
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	83	A
		single half cycle; $f = 60\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	100	
I^2t	I^2t Value for fusing	$t_p = 8.3\text{ ms}$	41	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{ Hz}$; $T_j = 110^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate current	$T_j = 110^\circ\text{C}$	1.6	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 110^\circ\text{C}$	0.4	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 110	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard SCRs

Symbol	Parameter	Test Conditions		Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx08L	$T_c = 110^\circ\text{C}$	8	A
		Sxx08R	$T_c = 110^\circ\text{C}$		
		Sxx08D	$T_c = 110^\circ\text{C}$		
		Sxx08V	$T_c = 110^\circ\text{C}$		
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_J (\text{initial}) = 25^\circ\text{C}$		83	A
		single half cycle; $f = 60\text{Hz}$; $T_J (\text{initial}) = 25^\circ\text{C}$		100	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$		41	A^2s
di/dt	Critical rate-of-rise of on-state current	$f = 60 \text{ Hz } T_J = 125^\circ\text{C}$		100	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_J = 125^\circ\text{C}$		2	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$		0.5	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) – Sensitive SCRs

Symbol	Test Conditions		Value		Unit
			Sxx08xS2	Sxx08xS3	
I_{GT}	$V_D = 6\text{V } R_L = 60 \Omega$	MAX.	200	500	μA
V_{GT}		MAX.	0.8		V
dv/dt	$V_D = V_{DRM}$; $R_{GK} = 1\text{k}\Omega$; $T_J = 110^\circ\text{C}$	TYP.	8		$\text{V}/\mu\text{s}$
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 110^\circ\text{C}$	MIN.	0.2		V
V_{GRM}	$I_{GR} = 10\mu\text{A}$	MIN.	6		V
I_H	$I_T = 20\text{mA}$ (initial)	MAX.	6	8	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = -30\text{A}/\mu\text{s}$	MAX.	50	45	μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\mu\text{s}$ $I_T = 12\text{A}$	TYP.	4	5	μs

Note: xx = voltage x = package

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) – Standard SCRs

Symbol	Test Conditions			Value	Unit
				Sxx08x	
I_{GT}	$V_D = 12\text{V } R_L = 60 \Omega$		MAX.	15	mA
V_{GT}			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^\circ\text{C}$	400V	MIN.	350	$\text{V}/\mu\text{s}$
		600V		300	
		800V		250	
		1000V		100	
	$V_D = V_{DRM}$; gate open; $T_J = 125^\circ\text{C}$	400V		250	
		600V		225	
		800V		200	
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^\circ\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	30	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = -30\text{A}/\mu\text{s}$		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\mu\text{s}$ $I_T = 16\text{A}$		TYP.	2	μs

Note: xx = voltage x = package

Static Characteristics

Symbol	Test Conditions				Value	Unit	
V _{TM}	I _T = 16A; t _p = 380 μs				MAX.	1.6	V
I _{DRM} / I _{RRM}	V _{DRM} = V _{RRM}	Sxx08xyy	T _J = 25°C	400 - 600V	MAX.	5	μA
			T _J = 110°C	400 - 600V		250	
		Sxx08x	T _J = 25°C	400 - 800V		10	
				1000V		20	
			T _J = 100°C	400 - 800V		200	
				1000V		3000	
			T _J = 125°C	400 - 800V		500	

Note: xx = voltage, x = package, yy = sensitivity

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx08RSy	1.8	$^\circ C/W$
		Sxx08LSy	3.4	
		Sxx08VSy	2.1	
		Sxx08DSy	1.5	
		Sxx08R	1.8	
		Sxx08L	3.4	
		Sxx08V	2.0	
		Sxx08D	1.5	
$R_{\theta(J-A)}$	Junction to ambient	Sxx08RSy	40	$^\circ C/W$
		Sxx08LSy	65	
		Sxx08VSy	85	
		Sxx08R	40	
		Sxx08L	50	
		Sxx08V	70	

Note: xx = voltage, y = sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature (Sensitive SCR)

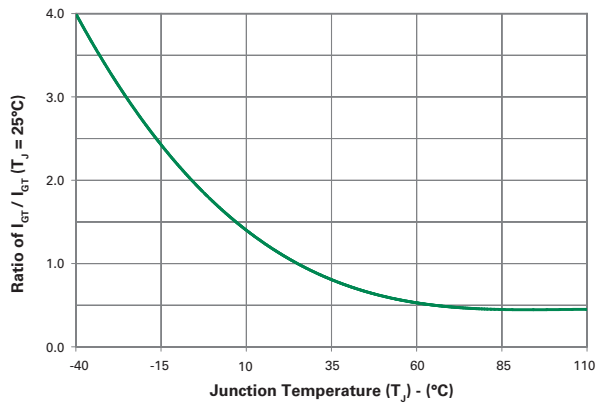


Figure 2: Normalized DC Gate Trigger Current vs. Junction Temperature (Standard SCR)

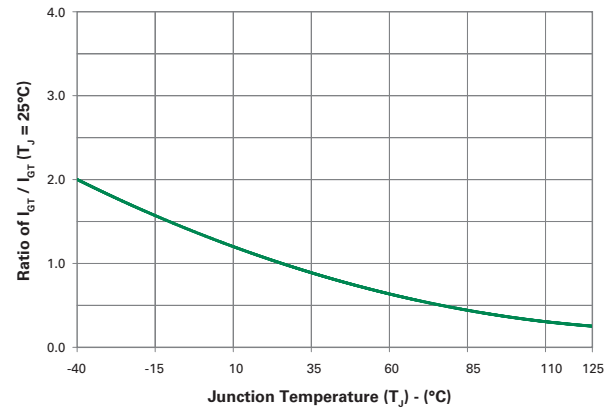


Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

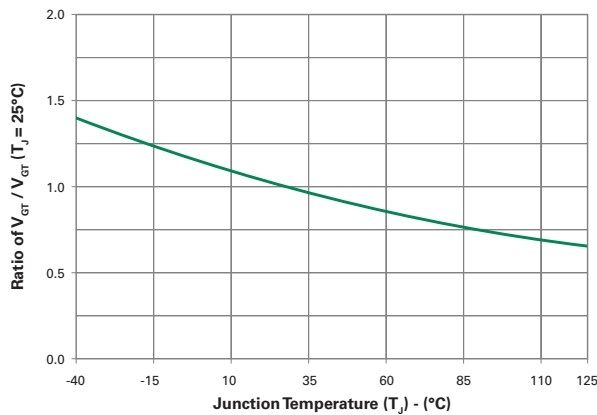


Figure 4: Normalized DC Holding Current vs. Junction Temperature

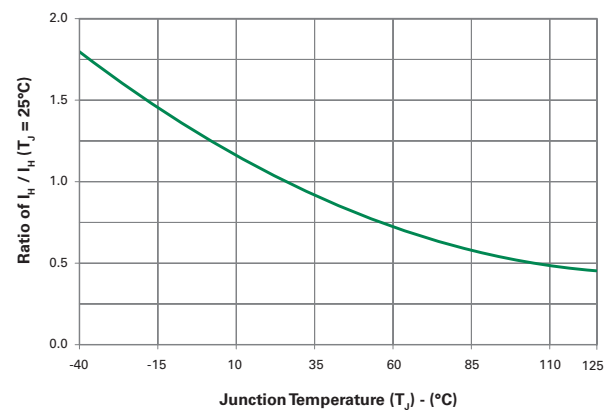


Figure 5: On-State Current vs. On-State Voltage (Typical)

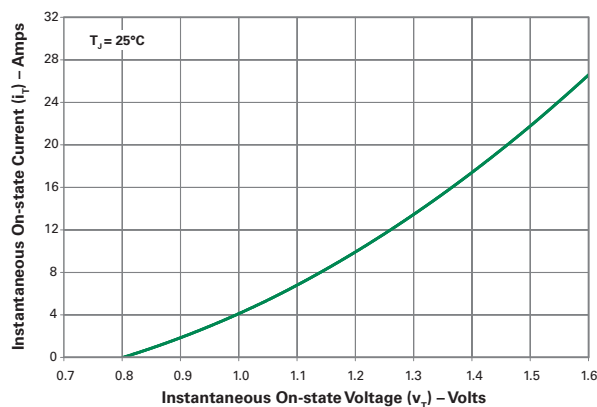


Figure 6: Power Dissipation (Typical) vs. RMS On-State Current

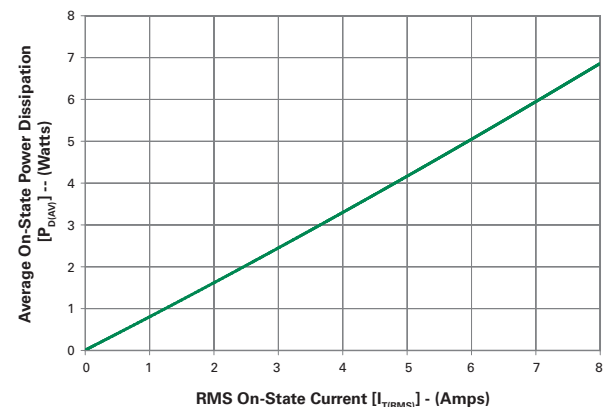


Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current

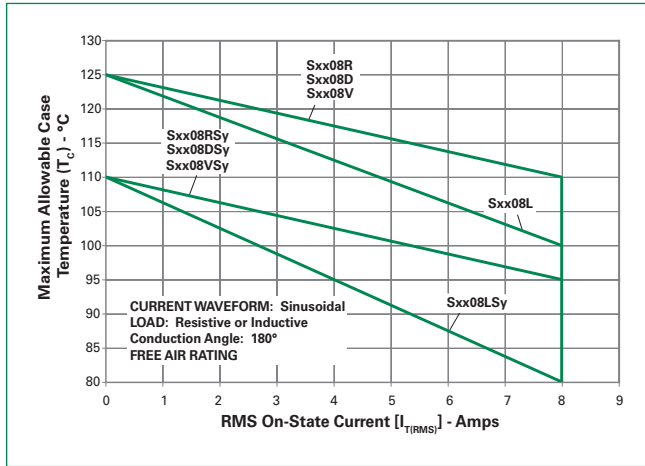


Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current

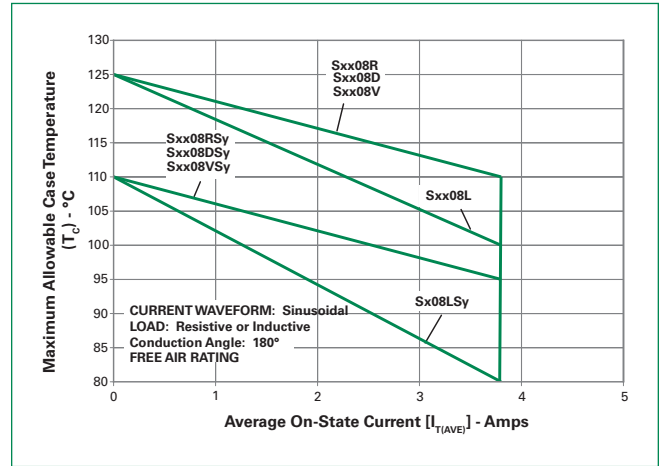


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

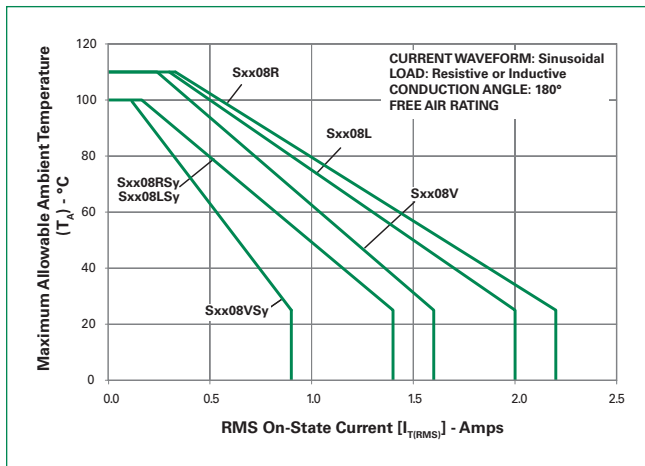
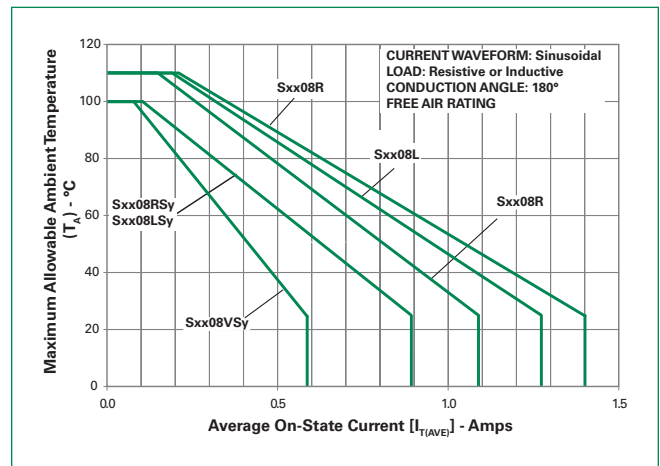


Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current



Note: xx = voltage, y = sensitivity

Figure 11: Peak Capacitor Discharge Current

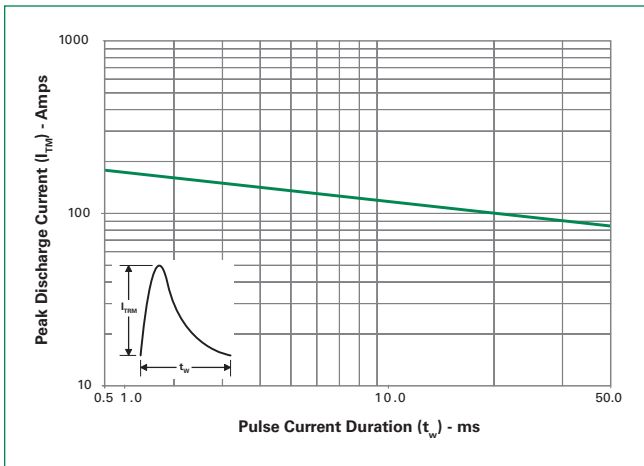


Figure 12: Peak Capacitor Discharge Current Derating

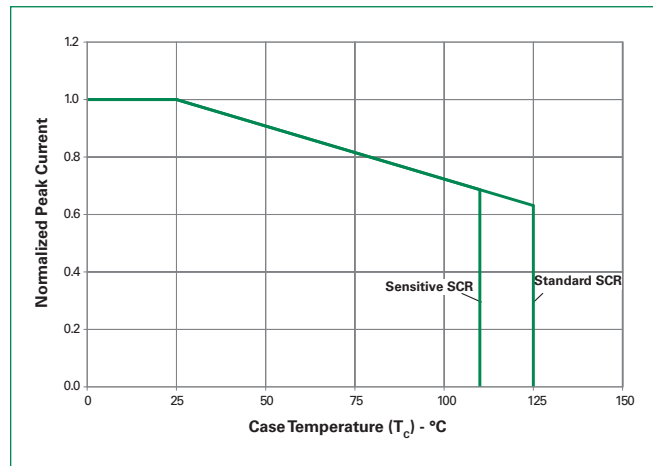
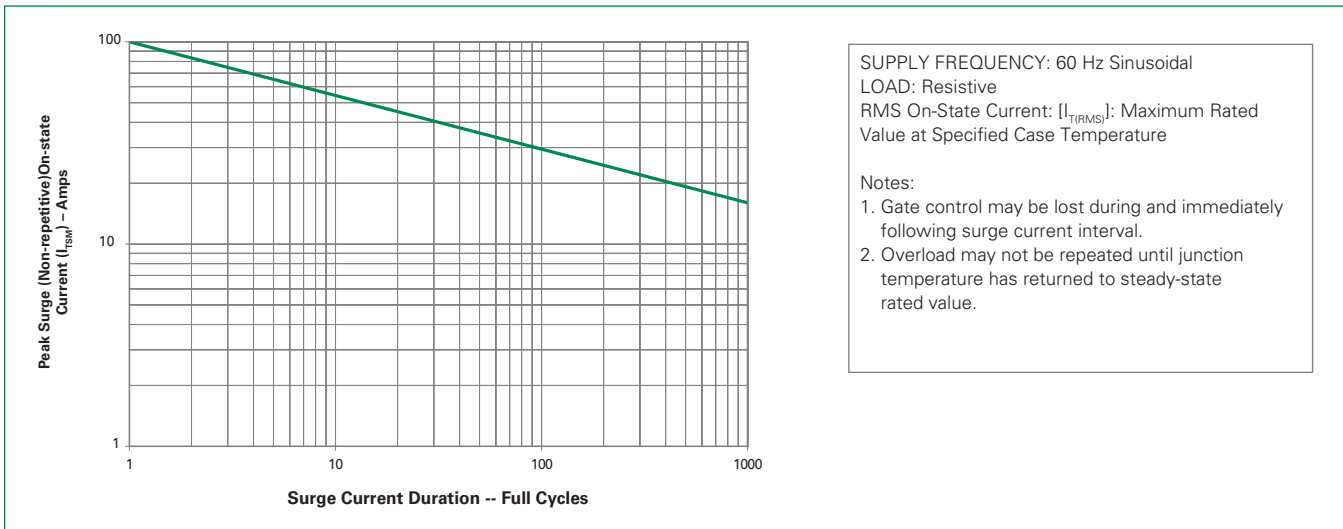
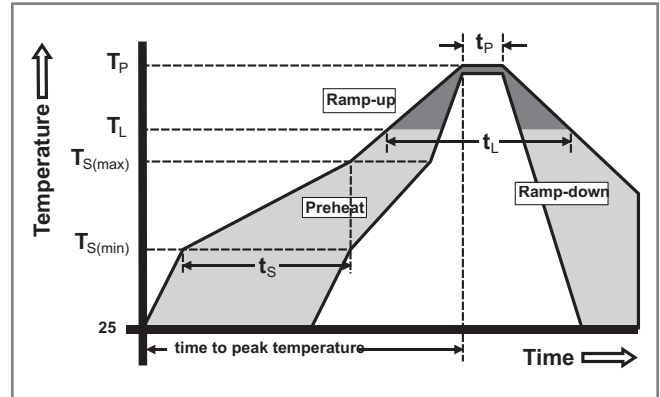


Figure 13: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

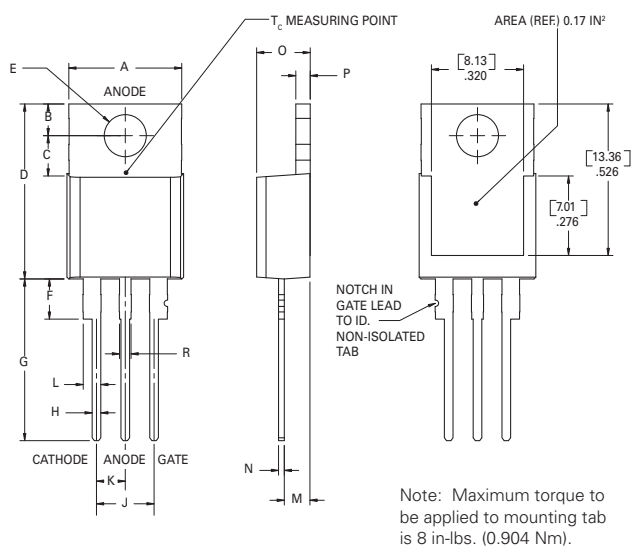
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

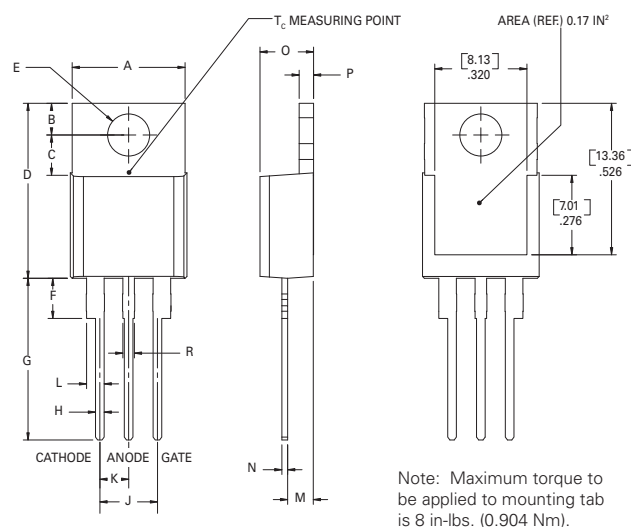
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



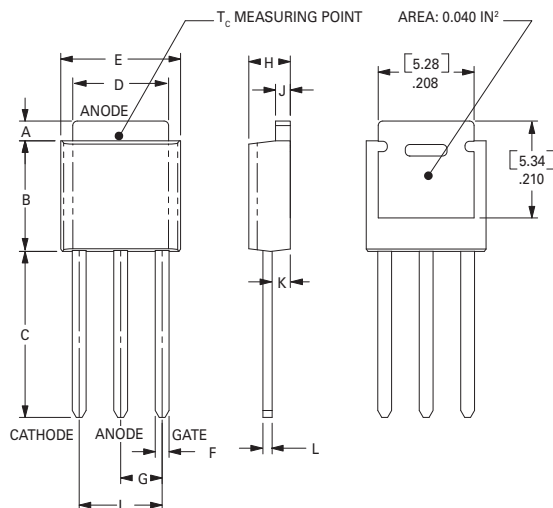
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
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J	0.195	0.205	4.95	5.21
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L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



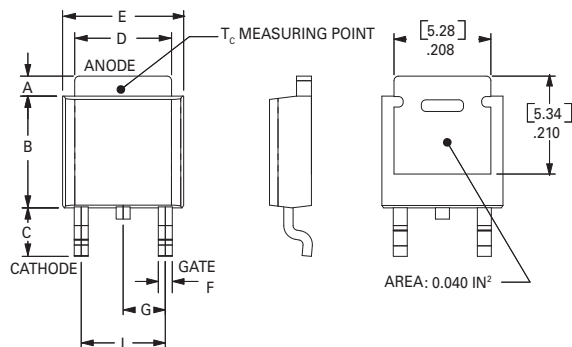
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	Min	Max	Min	Max
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N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole

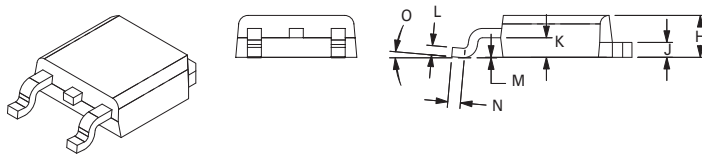
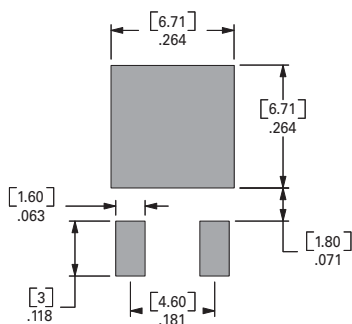


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



Pad Layout for TO-252AA (D-Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx08RS2	X	X			0.2mA	Sensitive SCR	TO-220R
Sxx08LS2	X	X			0.2mA	Sensitive SCR	TO-220L
Sxx08VS2	X	X			0.2mA	Sensitive SCR	TO-251
Sxx08DS2	X	X			0.2mA	Sensitive SCR	TO-252
Sxx08RS3	X	X			0.5mA	Sensitive SCR	TO-220R
Sxx08LS3	X	X			0.5mA	Sensitive SCR	TO-220L
Sxx08VS3	X	X			0.5mA	Sensitive SCR	TO-251
Sxx08DS3	X	X			0.5mA	Sensitive SCR	TO-252
Sxx08R	X	X	X	X	15mA	Standard SCR	TO-220R
Sxx08L	X	X	X	X	15mA	Standard SCR	TO-220L
Sxx08V	X	X	X	X	15mA	Standard SCR	TO-251
Sxx08D	X	X	X	X	15mA	Standard SCR	TO-252

Note: xx = Voltage

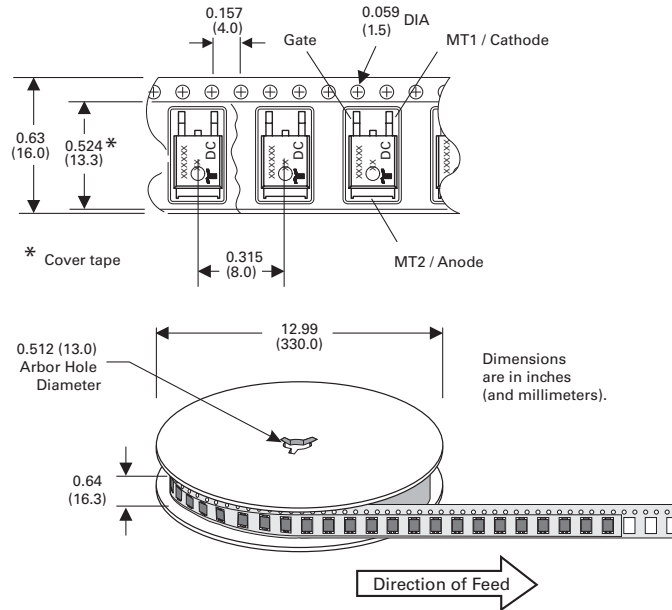
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx08L/Ryy	Sxx08L/Ryy	2.2 g	Bulk	500
Sxx08L/RyyTP	Sxx08L/Ryy	2.2 g	Tube	500
Sxx08DyyTP	Sxx08Dyy	0.3 g	Tube	750
Sxx08DyyRP	Sxx08Dyy	0.3 g	Embossed Carrier	2500
Sxx08VyyTP	Sxx08Vyy	0.4 g	Tube	750
Sxx08VyyRP	Sxx08Vyy	0.4 g	Embossed Carrier	2500
Sxx08L/R	Sxx08L/R	2.2 g	Bulk	500
Sxx08L/RTP	Sxx08L/R	2.2 g	Tube	500
Sxx08DTP	Sxx08D	0.3 g	Tube	750
Sxx08DRP	Sxx08D	0.3 g	Embossed Carrier	2500
Sxx08VTP	Sxx08V	0.4 g	Tube	750
Sxx08VRP	Sxx08V	0.4 g	Embossed Carrier	2500

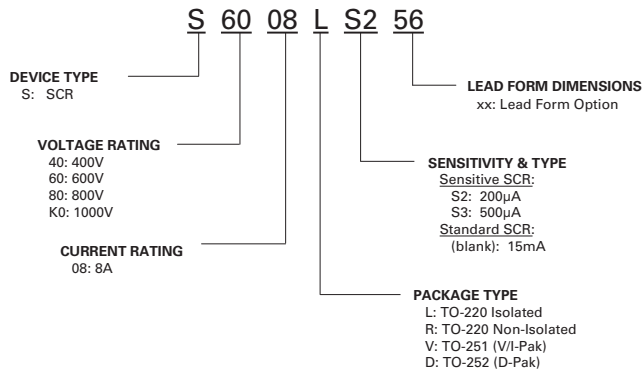
Note: xx = Voltage; yy = Sensitivity

TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

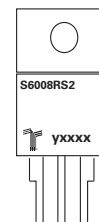


Part Numbering System

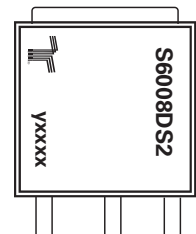


Part Marking System

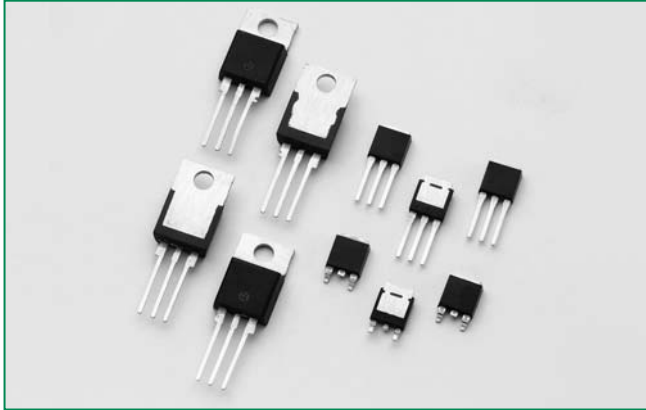
TO-220AB (R and L Packages)




TO-251AA – (V Package)
TO-252AA – (D Package)



RoHS Sxx10xSx & Sxx10x Series



Agency Approval

Agency	Agency File Number
	TO-220L Package : E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	10	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	0.2 to 15	mA

Description

Excellent unidirectional switches for phase control and general switching applications such as heating and motor speed controls.

Sensitive gate SCRs are easily triggered with microAmps of current as furnished by sense coils, proximity switches, and microprocessors.

Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

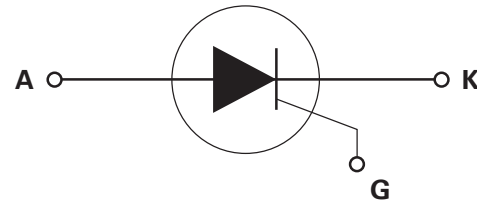
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 100 A

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Absolute Maximum Ratings — Sensitive SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx10LSy $T_c = 80^\circ\text{C}$	10	A
		Sxx10RSy Sxx10DSy Sxx10VSY $T_c = 95^\circ\text{C}$		
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j (\text{initial}) = 25^\circ\text{C}$	83	A
		single half cycle; $f = 60\text{Hz}$; $T_j (\text{initial}) = 25^\circ\text{C}$	100	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	41	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60 \text{ Hz}$; $T_j = 110^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_j = 110^\circ\text{C}$	1	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 110^\circ\text{C}$	0.1	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 110	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard SCRs

Symbol	Parameter	Test Conditions		Value	Unit
I _{T(RMS)}	RMS on-state current	Sxx10L	T _C = 100°C	10	A
		Sxx10R	T _C = 110°C		
		Sxx10D Sxx10V			
I _{TSM}	Peak non-repetitive surge current	single half cycle; f = 50Hz; T _J (initial) = 25°C		83	A
		single half cycle; f = 60Hz; T _J (initial) = 25°C		100	
I ² t	I ² t Value for fusing	t _p = 8.3 ms		41	A ² s
di/dt	Critical rate-of-rise of on-state current	f = 60 Hz T _J = 125°C		100	A/μs
I _{GM}	Peak gate current	T _J = 125°C		2	A
P _{G(AV)}	Average gate power dissipation	T _J = 125°C		0.5	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 125	°C

Note: xx = voltage

Electrical Characteristics ($T_J = 25^{\circ}\text{C}$, unless otherwise specified) – Sensitive SCRs

Symbol	Test Conditions		Value		Unit
			Sxx10xS2	Sxx10xS3	
I_{GT}	$V_D = 6\text{V}$ $R_L = 100\ \Omega$	MAX.	200	500	μA
V_{GT}		MAX.	0.8		V
dv/dt	$V_D = V_{DRM}$; $R_{GK} = 1\text{k}\Omega$; $T_J = 110^{\circ}\text{C}$	TYP.	8		$\text{V}/\mu\text{s}$
V_{GD}	$V_D = V_{DRM}$; $R_L = 3.3\text{ k}\Omega$; $T_J = 110^{\circ}\text{C}$	MIN.	0.2		V
V_{GRM}	$I_{GR} = 10\mu\text{A}$	MIN.	6		V
I_H	$I_T = 20\text{mA}$ (initial)	MAX.	6	8	mA
t_q	(1)	MAX.	50	45	μs
t_{gt}	$I_G = 2 \times I_{GT}$; $PW = 15\mu\text{s}$; $I_T = 12\text{A}$	TYP.	4	5	μs

NOTE: xx = voltage, x = package

(1) $I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = 30\text{A}/\mu\text{s}$

Electrical Characteristics ($T_J = 25^{\circ}\text{C}$, unless otherwise specified) – Standard SCRs

Symbol	Test Conditions			Value	Unit
				Sxx10x	
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\ \Omega$		MAX.	15	mA
V_{GT}			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^{\circ}\text{C}$	400V	MIN.	350	$\text{V}/\mu\text{s}$
		600V		300	
		800V		250	
		1000V		100	
	$V_D = V_{DRM}$; gate open; $T_J = 125^{\circ}\text{C}$	400V		250	
		600V		225	
		800V		200	
V_{GD}	$V_D = V_{DRM}$; $R_L = 3.3\text{ k}\Omega$; $T_J = 125^{\circ}\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	30	mA
t_q	(1)		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$; $PW = 15\mu\text{s}$; $I_T = 20\text{A}$		TYP.	2	μs

NOTE: xx = voltage, x = package

(1) $I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; $dv/dt = 5\text{V}/\mu\text{s}$; $di/dt = 30\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions					Value	Unit
V _{TM}	I _T = 20A; t _p = 380 μs				MAX.	1.6	V
I _{DRM} / I _{RRM}	V _{DRM} / V _{RRM}	Sxx10xyy	T _J = 25°C	400 - 600V	MAX.	5	μA
			T _J = 110°C	400 - 600V		250	
		Sxx10x	T _J = 25°C	400 - 800V		10	
				1000V		20	
			T _J = 100°C	400 - 800V		200	
				1000V		3000	
			T _J = 125°C	400 - 800V		500	

Note: xx = voltage, x = package, yy = sensitivity

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx10RSy	1.6	$^\circ C/W$
		Sxx10LSy	3.0	
		Sxx10Vsy	1.7	
		Sxx10DSy	1.45	
		Sxx10R	1.6	
		Sxx10L	3.0	
		Sxx10V	1.7	
		Sxx10D	1.45	
$R_{\theta(J-A)}$	Junction to ambient	Sxx10RSy	40	$^\circ C/W$
		Sxx10LSy	65	
		Sxx10Vsy	85	
		Sxx10R	40	
		Sxx10L	50	
		Sxx10V	70	

Note: xx = voltage, y = sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature (Sensitive SCR)

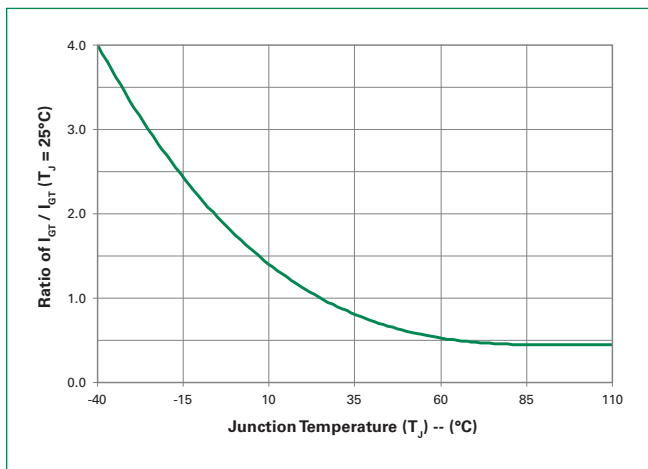


Figure 2: Normalized DC Gate Trigger Current vs. Junction Temperature (Standard SCR)

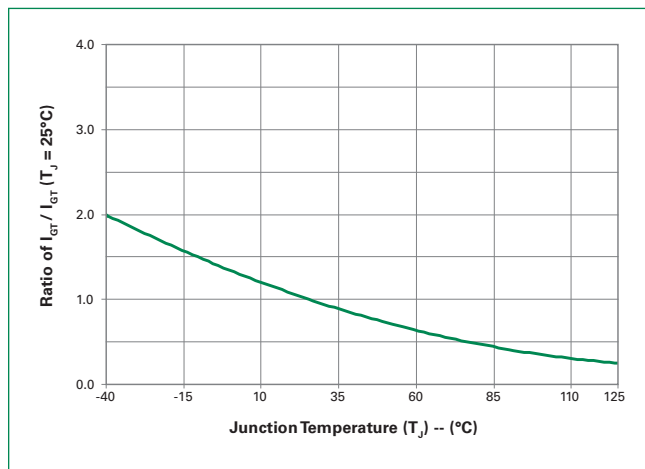


Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

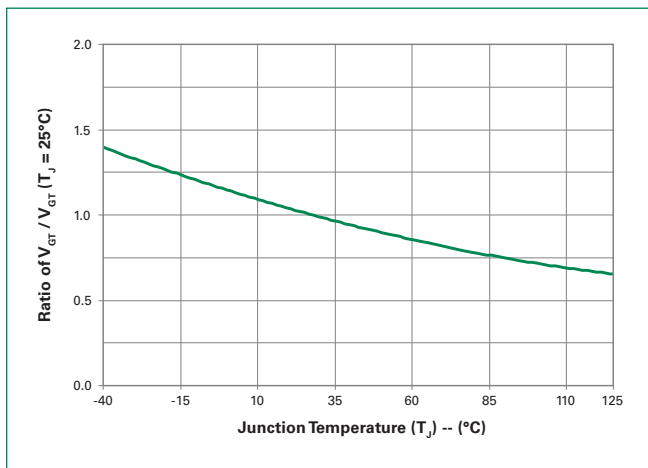


Figure 4: Normalized DC Holding Current vs. Junction Temperature

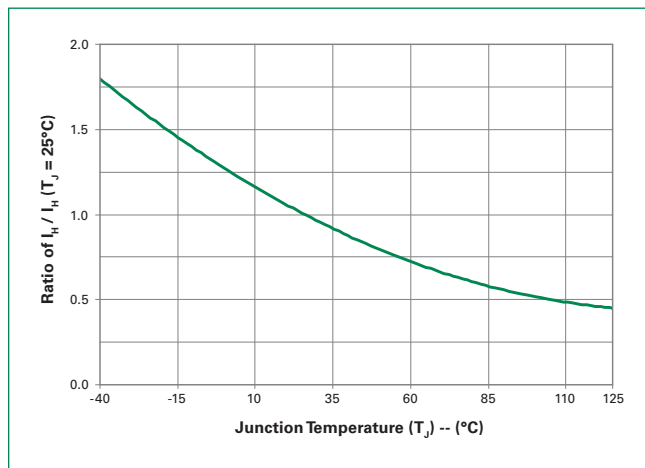


Figure 5: On-State Current vs. On-State Voltage (Typical)

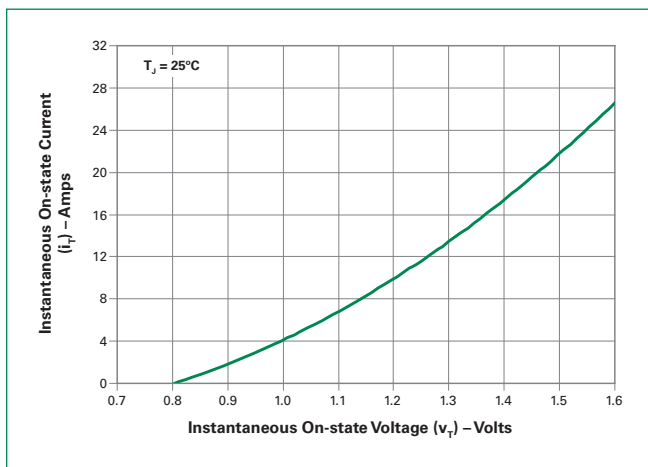


Figure 6: Power Dissipation (Typical) vs. RMS On-State Current

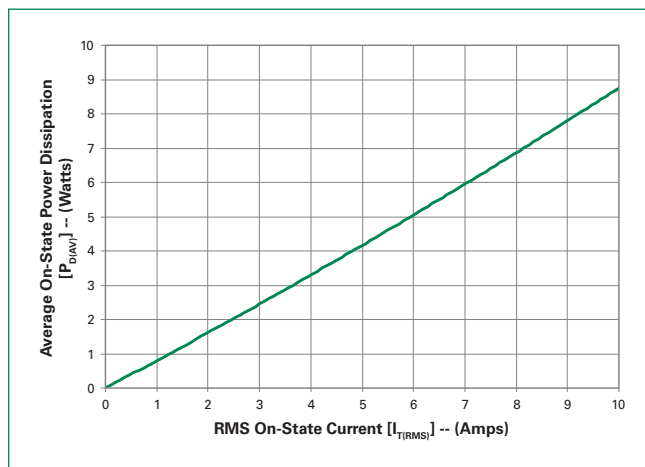


Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current

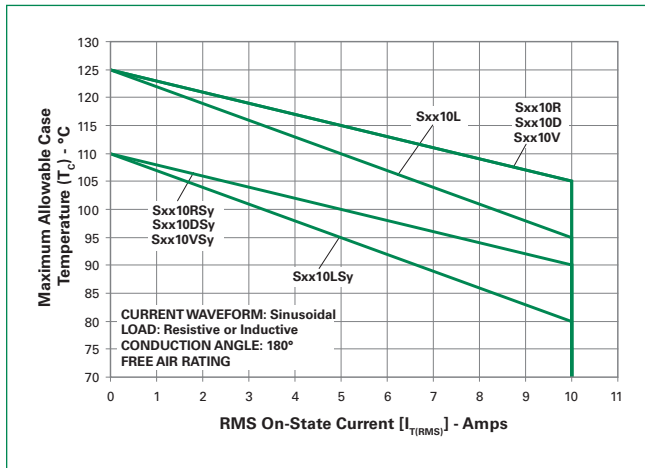


Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current

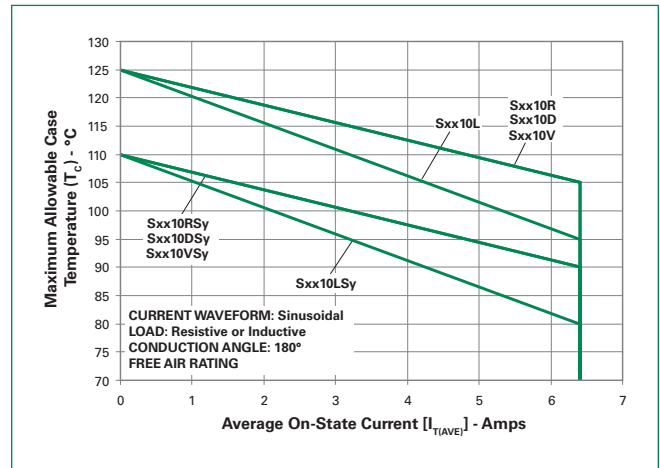


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

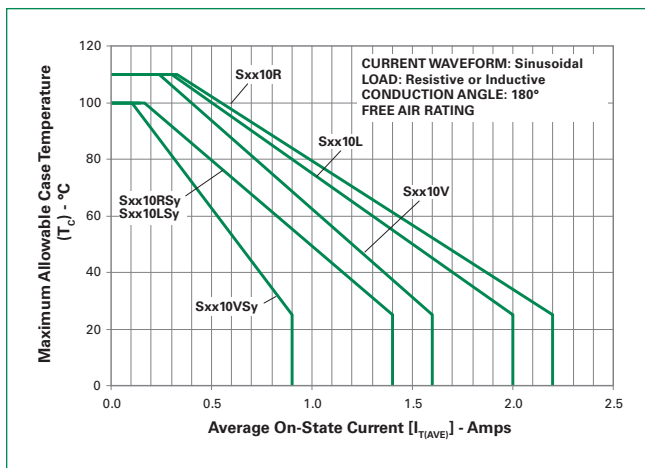
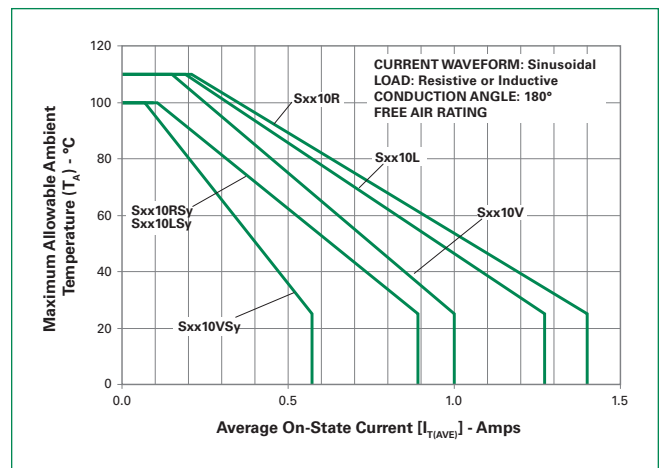


Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current



Note: xx = voltage, y = sensitivity

Figure 11: Peak Capacitor Discharge Current

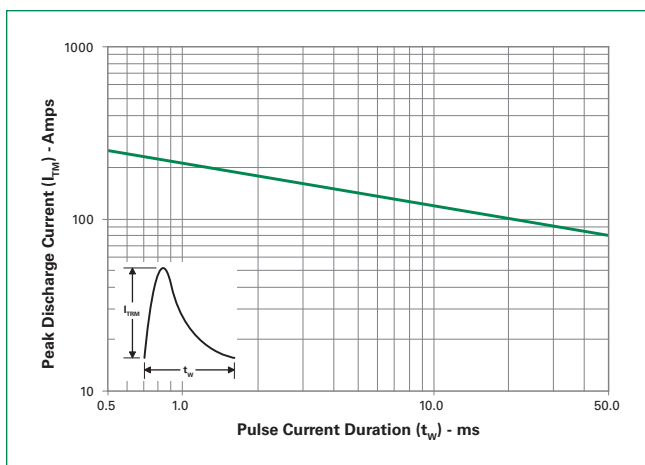


Figure 12: Peak Capacitor Discharge Current Derating

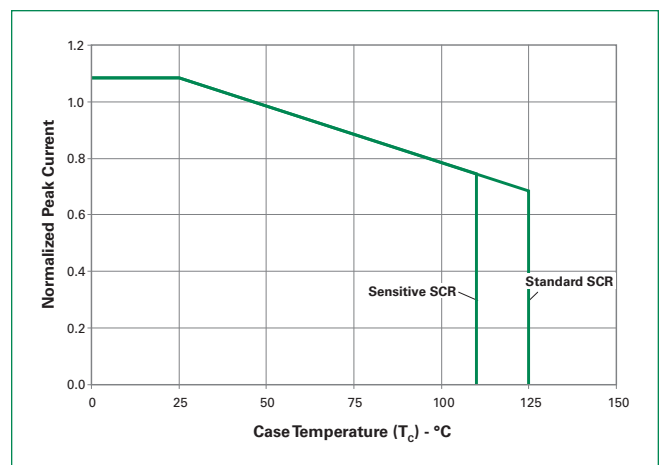
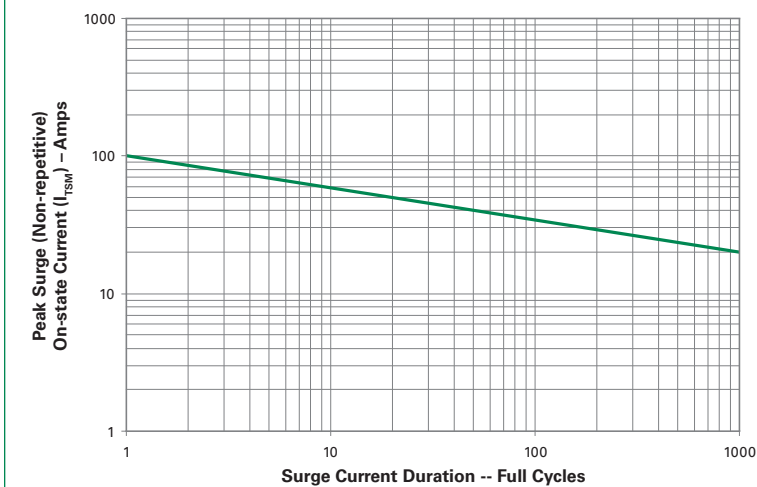


Figure 13: Surge Peak On-State Current vs. Number of Cycles



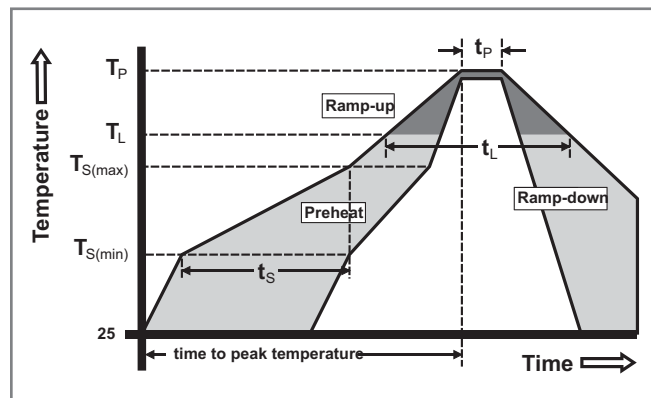
SUPPLY FREQUENCY: 60 Hz Sinusoidal
LOAD: Resistive
RMS On-State Current: [$I_{T(RMS)}$]: Maximum Rated Value at Specified Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

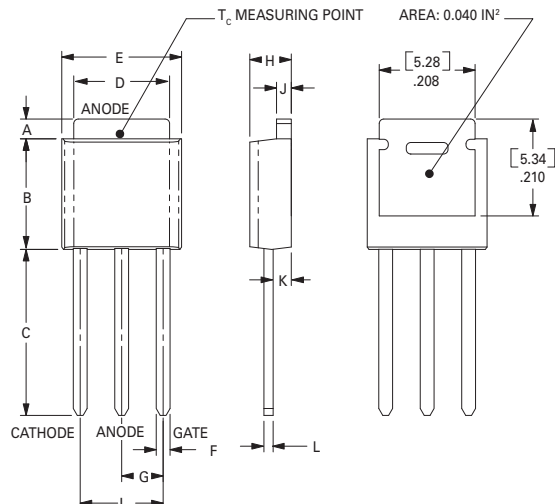
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx10RS2	X	X			0.2mA	Sensitive SCR	TO-220R
Sxx10LS2	X	X			0.2mA	Sensitive SCR	TO-220L
Sxx10VS2	X	X			0.2mA	Sensitive SCR	TO-251
Sxx10DS2	X	X			0.2mA	Sensitive SCR	TO-252
Sxx10RS3	X	X			0.5mA	Sensitive SCR	TO-220R
Sxx10LS3	X	X			0.5mA	Sensitive SCR	TO-220L
Sxx10VS3	X	X			0.5mA	Sensitive SCR	TO-251
Sxx10DS3	X	X			0.5mA	Sensitive SCR	TO-252
Sxx10R	X	X	X	X	15mA	Standard SCR	TO-220R
Sxx10L	X	X	X	X	15mA	Standard SCR	TO-220L
Sxx10V	X	X	X	X	15mA	Standard SCR	TO-251
Sxx10D	X	X	X	X	15mA	Standard SCR	TO-252

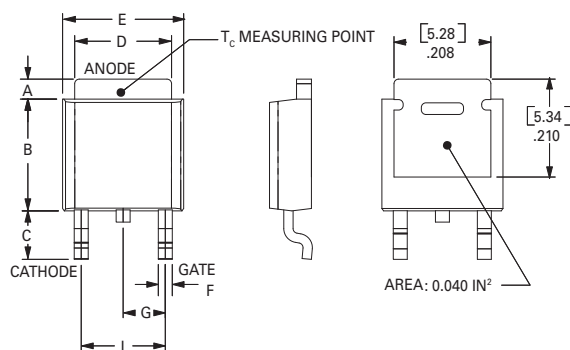
Note: xx = Voltage

Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole

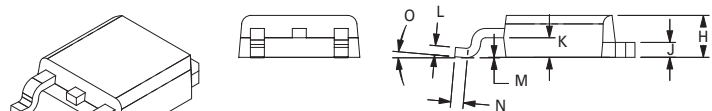
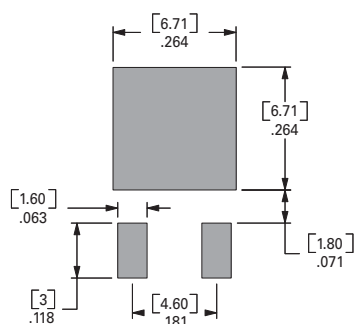


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
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B	0.235	0.245	5.97	6.22
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J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount

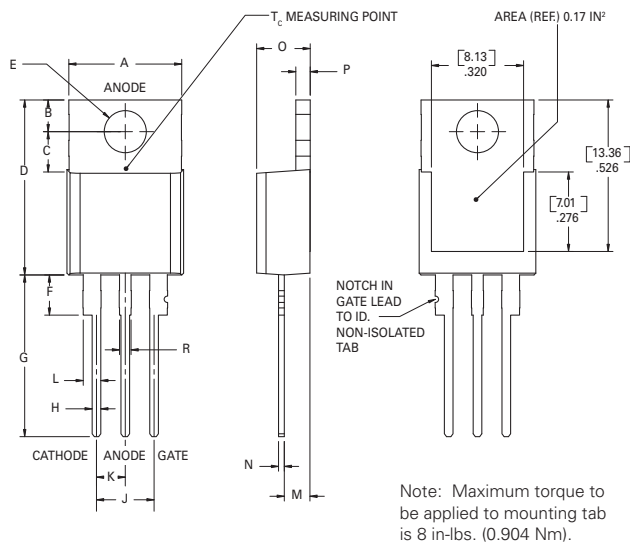


Pad Layout for TO-252AA (D-Package)



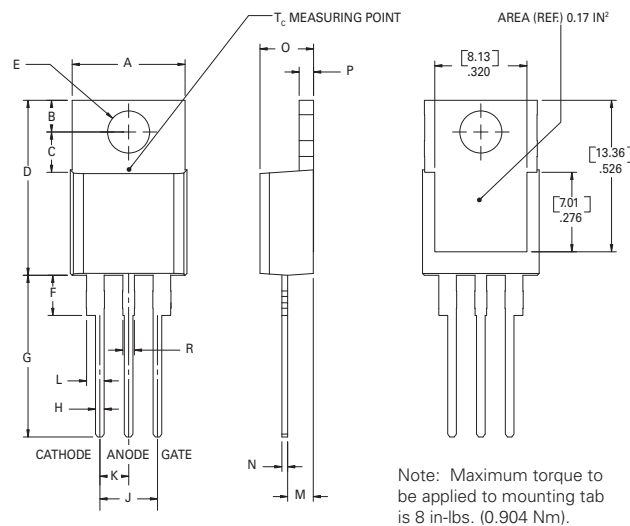
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
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L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

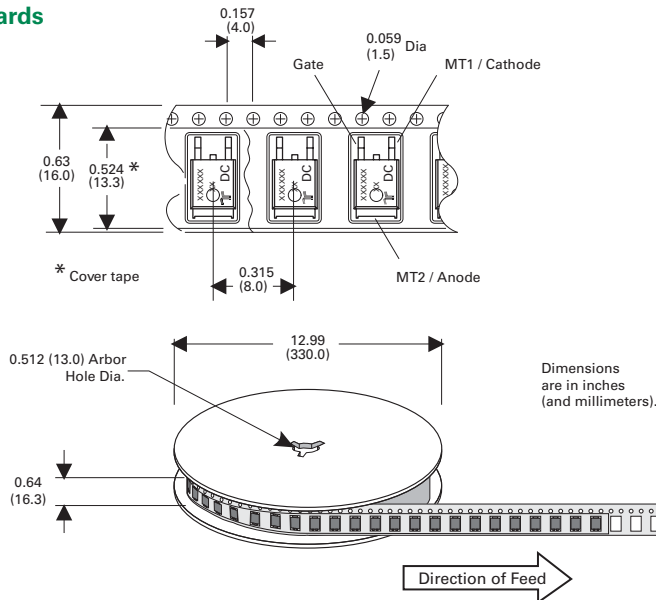
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx10L/Ryy	Sxx10L/Ryy	2.2 g	Bulk	500
Sxx10L/RyyTP	Sxx10L/Ryy	2.2 g	Tube	500
Sxx10DyyTP	Sxx10Dyy	0.3 g	Tube	750
Sxx10DyyRP	Sxx10Dyy	0.3 g	Embossed Carrier	2500
Sxx10VyyTP	Sxx10Vyy	0.4 g	Tube	750
Sxx10VyyRP	Sxx10Vyy	0.4 g	Embossed Carrier	2500
Sxx10L/R	Sxx10L/R	2.2 g	Bulk	500
Sxx10L/RTP	Sxx10L/R	2.2 g	Tube	500
Sxx10DTP	Sxx10D	0.3 g	Tube	750
Sxx10DRP	Sxx10D	0.3 g	Embossed Carrier	2500
Sxx10VTP	Sxx10V	0.4 g	Tube	750
Sxx10VRP	Sxx10V	0.4 g	Embossed Carrier	2500

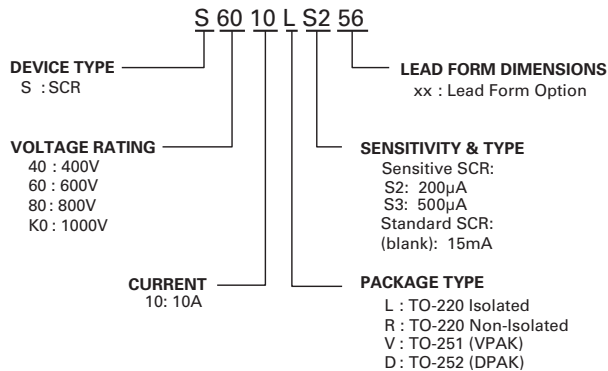
Note: xx = Voltage; yy = Sensitivity

TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



Part Numbering System



Part Marking System

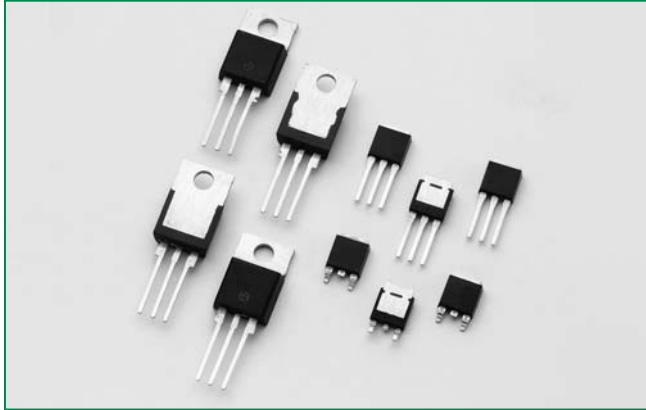
TO-220AB - (R & L Packages)



TO-251AA - (V Package)
TO-252AA - (D Package)



RoHS **Sxx12x Series**



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

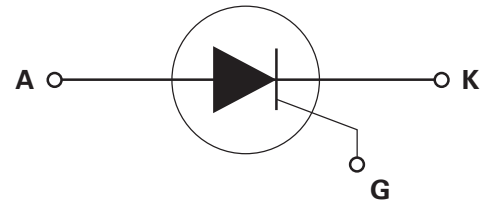
Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 120 A

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Schematic Symbol



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	20	mA

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx12R Sxx12D Sxx12V $T_c = 105^\circ\text{C}$	12	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	100	A
		single half cycle; $f = 60\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	120	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	60	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_j = 125^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_j = 125^\circ\text{C}$	2	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 125	

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value	Unit
I_{GT}	$V_D = 12V$ $R_L = 60\ \Omega$		MAX.	20	mA
V_{GT}			MIN.	1	
			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^\circ\text{C}$	400V	MIN.	350	V/ μs
		600V		300	
		800V		250	
		1000V		100	
	$V_D = V_{DRM}$; gate open; $T_J = 125^\circ\text{C}$	400V		250	
		600V		225	
		800V		200	
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	40	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; dv/dt = 5V/ μs ; di/dt = 30A/ μs		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 20\text{A}$		TYP.	2	μs

Static Characteristics

Symbol	Test Conditions			Value	Unit	
V _{TM}	I _T = 24A; t _p = 380 μs			MAX.	1.6	V
I _{DRM} / I _{RRM}	V _{DRM} = V _{RRM}	T _J = 25°C	400 – 600V	MAX.	10	μA
			800 – 1000V		20	
		T _J = 100°C	400 – 800V		500	
			1000V		3000	
		T _J = 125°C	400 – 800V		1000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx12R	1.5	$^\circ\text{C/W}$
		Sxx12V	1.6	
		Sxx12D	1.4	
$R_{\theta(J-A)}$	Junction to ambient	Sxx12R	40	$^\circ\text{C/W}$
		Sxx12V	70	

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

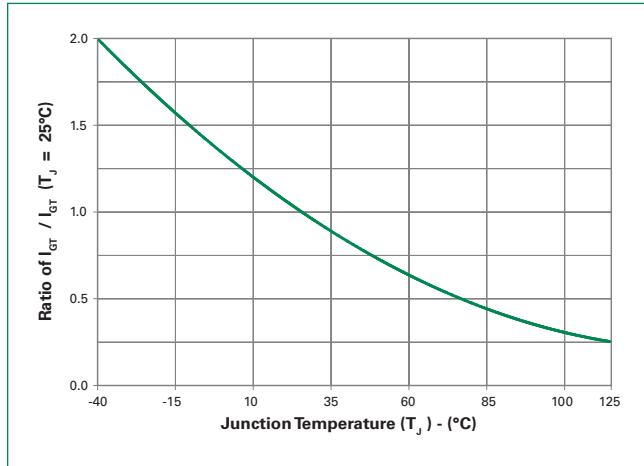


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

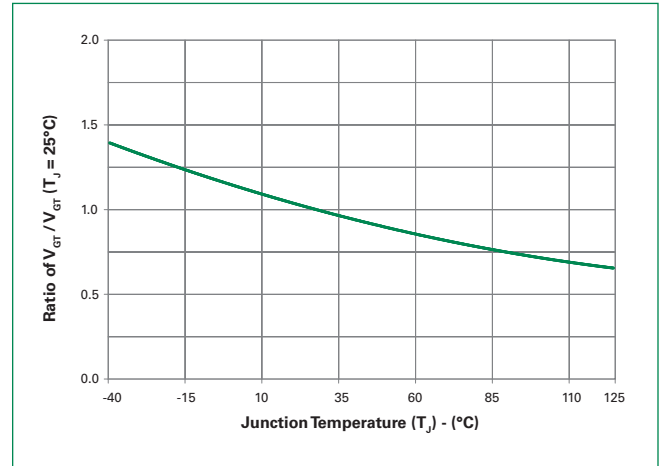


Figure 3: Normalized DC Holding Current vs. Junction Temperature

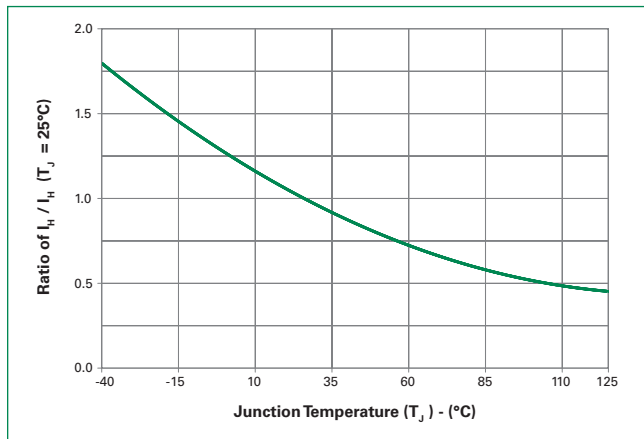


Figure 4: On-State Current vs. On-State Voltage (Typical)

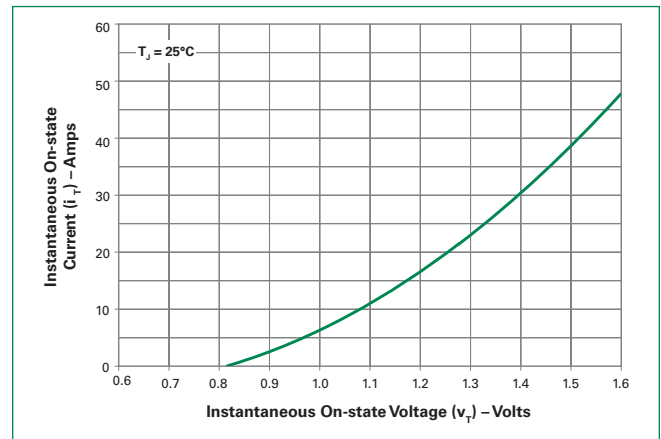


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

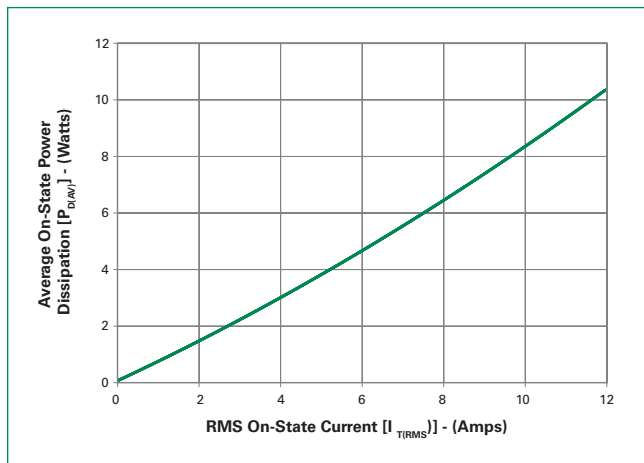


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

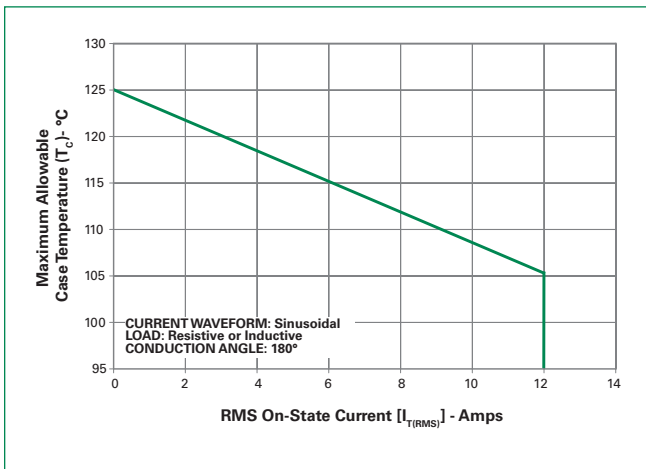


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

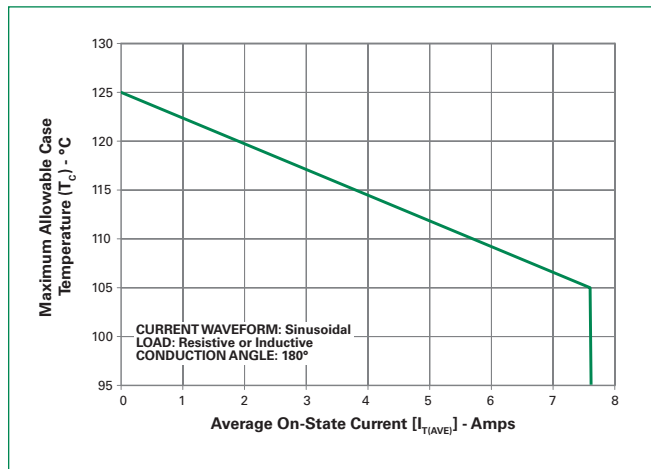
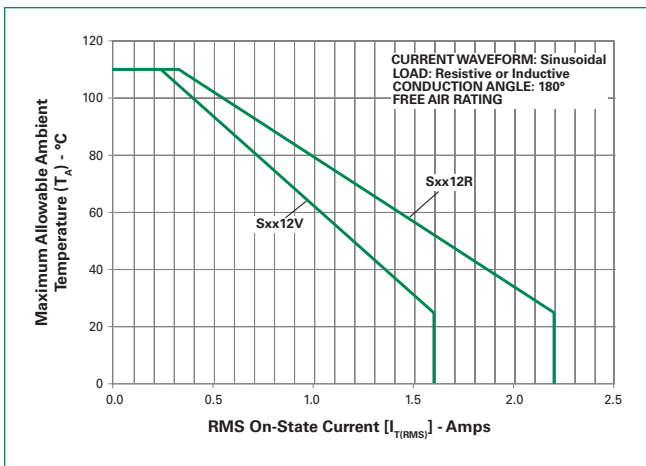


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current



Note: xx = voltage

Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current

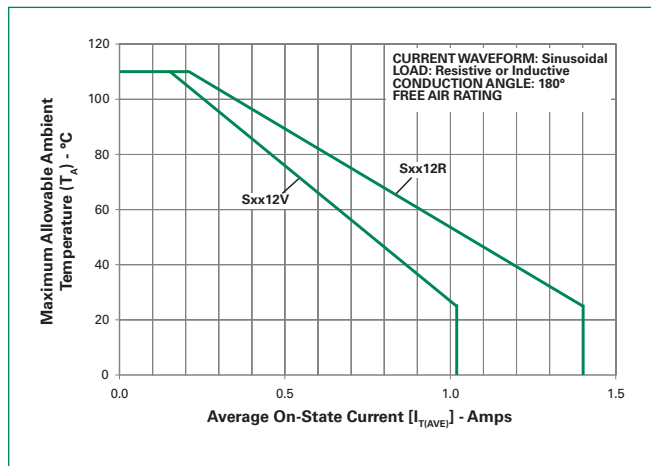


Figure 10: Peak Capacitor Discharge Current

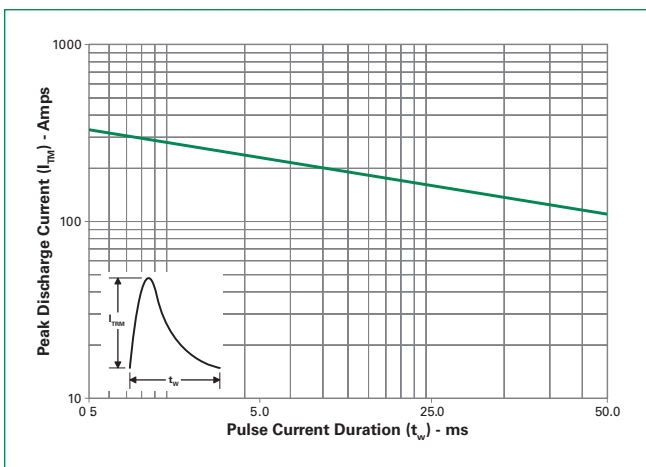


Figure 11: Peak Capacitor Discharge Current Derating

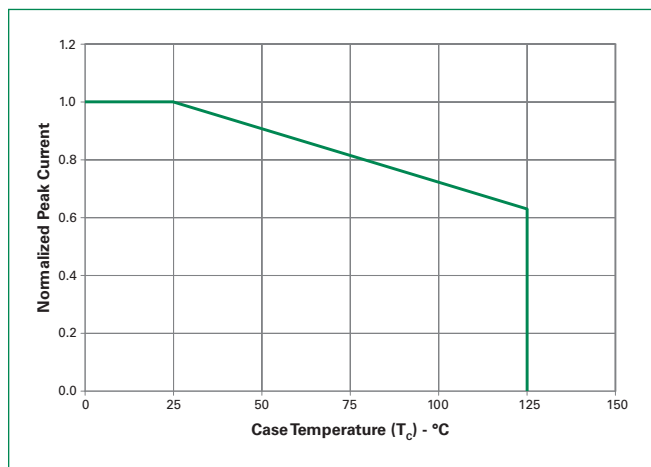
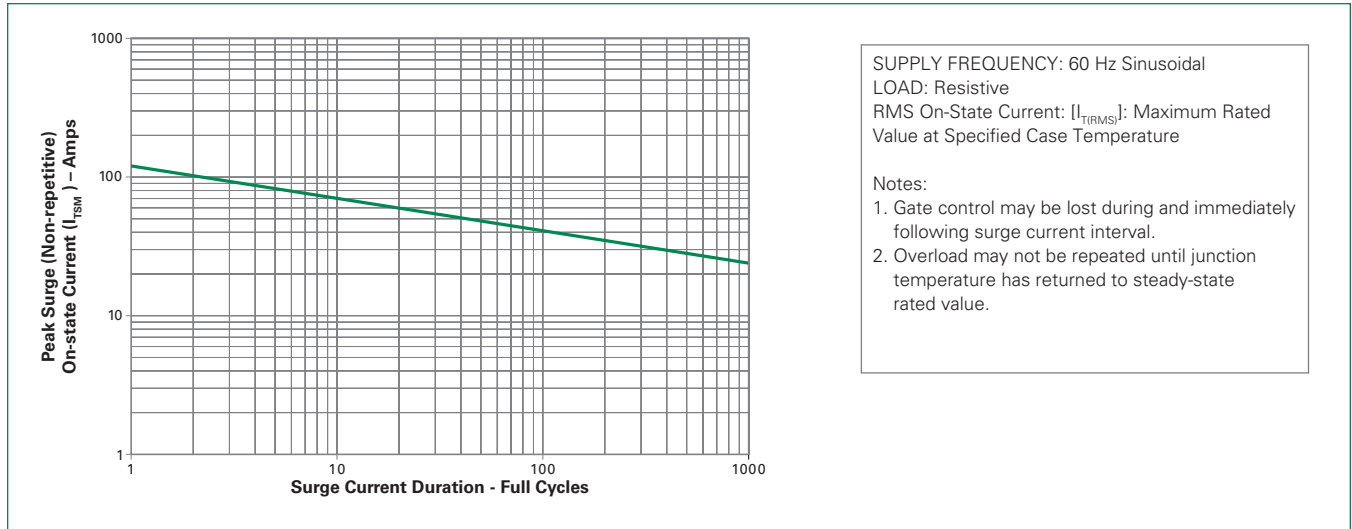
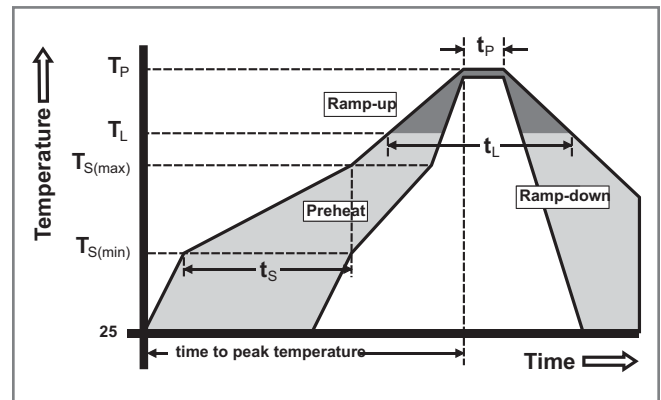


Figure 12: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

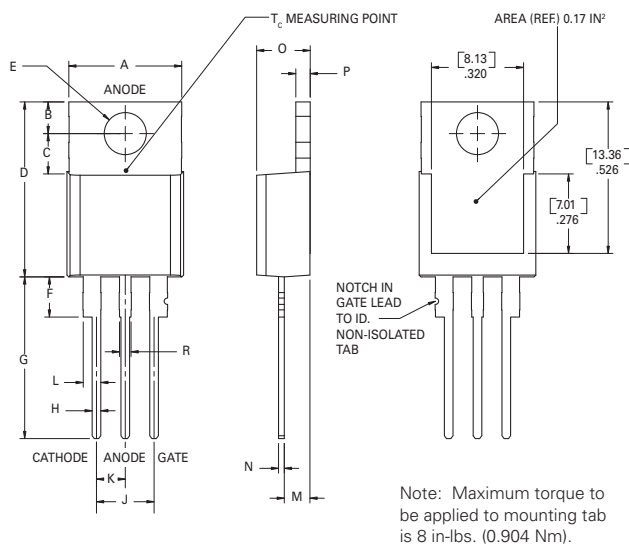
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

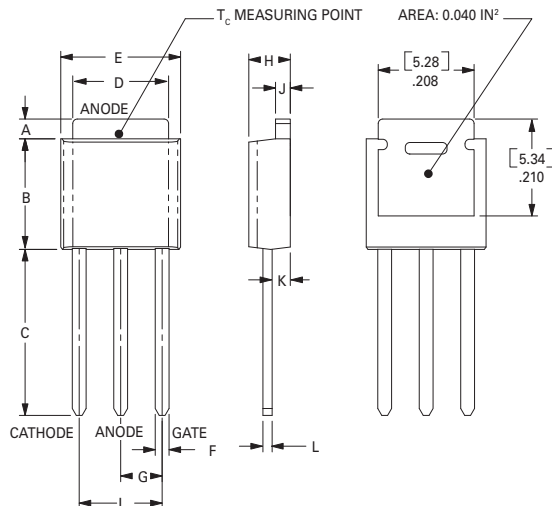
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



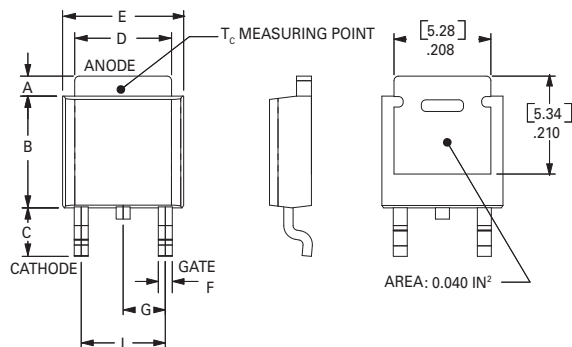
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole

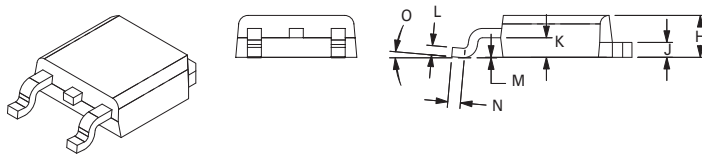
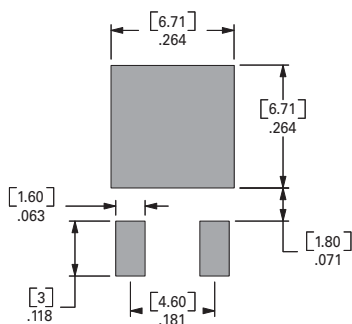


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.350	0.375	8.89	9.53
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



Pad Layout for TO-252AA (D-Package)



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.050	1.02	1.27
B	0.235	0.245	5.97	6.22
C	0.106	0.113	2.69	2.87
D	0.205	0.213	5.21	5.41
E	0.255	0.265	6.48	6.73
F	0.027	0.033	0.69	0.84
G	0.087	0.093	2.21	2.36
H	0.085	0.095	2.16	2.41
I	0.176	0.184	4.47	4.67
J	0.018	0.023	0.46	0.58
K	0.038	0.044	0.97	1.12
L	0.018	0.023	0.46	0.58
M	0.000	0.004	0.00	0.10
N	0.021	0.027	0.53	0.69
O	0°	5°	0°	5°

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx12R	X	X	X	X	20mA	Sensitive SCR	TO-220R
Sxx12V	X	X	X	X	20mA	Standard SCR	TO-251
Sxx12D	X	X	X	X	20mA	Standard SCR	TO-252

Note: xx = voltage

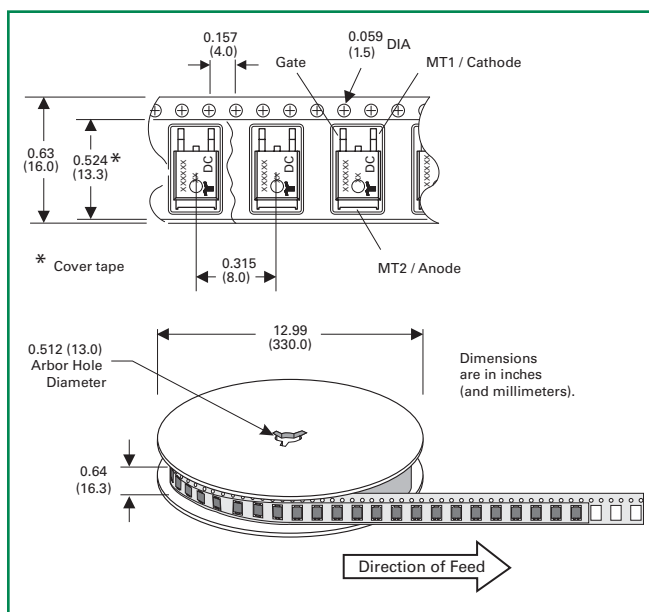
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx12R	Sxx12R	2.2 g	Bulk	500
Sxx12RTP	Sxx12R	2.2 g	Tube	500
Sxx12DTP	Sxx12D	0.3 g	Tube	750
Sxx12DRP	Sxx12D	0.3 g	Embossed Carrier	2500
Sxx12VTP	Sxx12V	0.4 g	Tube	750

Note: xx = Voltage

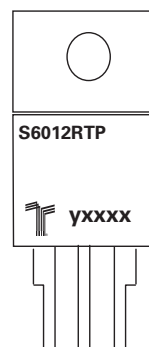
TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



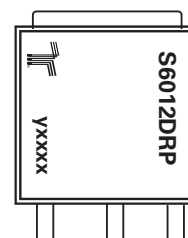
Part Marking System

TO-220AB (R Package)

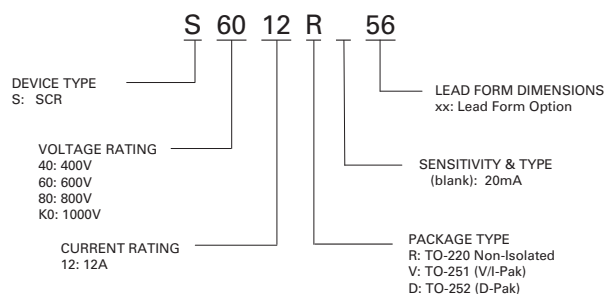


TO-251AA – (V Package)

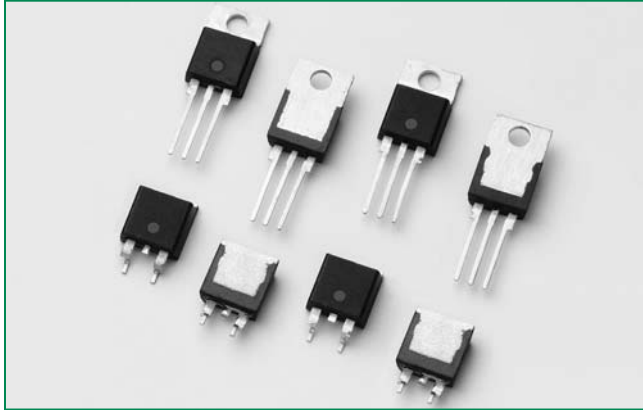
TO-252AA – (D Package)



Part Numbering System



RoHS Sxx15x & Sxx16x Series



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

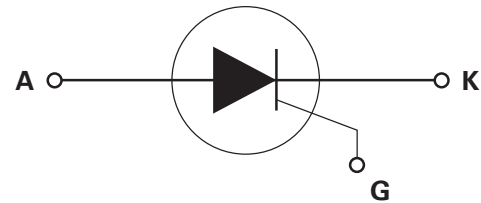
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 225 A

Applications


Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also controls for power tools, home/brown goods and white goods appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	15 & 16	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	30	mA

Absolute Maximum Ratings — Standard SCRs

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx15L $T_c = 90^\circ\text{C}$	15	A
		Sxx16R Sxx16N $T_c = 110^\circ\text{C}$	16	
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	188	A
		single half cycle; $f = 60\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	225	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	210	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60 \text{ Hz}$; $T_j = 125^\circ\text{C}$	125	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_j = 125^\circ\text{C}$	3	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.6	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Value		Unit
		Sxx15x	Sxx16x	
I_{GT}	$V_D = 12\text{V}; R_L = 60\ \Omega$	MAX.	30	mA
		MIN.	1	
V_{GT}		MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 100^\circ\text{C}$	400V	450	V/ μs
		600V	425	
		800V	400	
		1000V	200	
	$V_D = V_{DRM}$; gate open; $T_J = 125^\circ\text{C}$	400V	350	
		600V	325	
		800V	300	
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 110^\circ\text{C}$	MIN.	0.2	V
I_H	$I_T = 20\text{mA}$ (initial)	MAX.	40	mA
t_q	$I_T = 2\text{A}; t_p = 50\mu\text{s}; dv/dt = 5\text{V}/\mu\text{s}; di/dt = -30\text{A}/\mu\text{s}$	MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$ $PW = 15\mu\text{s}$ $I_T = 12\text{A}$	TYP.	2	μs

Note: xx = voltage, x = package

(1) $I_T = 2\text{A}; t_p = 50\mu\text{s}; dv/dt = 5\text{V}/\mu\text{s}; di/dt = -30\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions				Value	Unit
V_{TM}	15A Device $I_T = 30A$; $t_p = 380\ \mu s$			MAX.	1.6	V
	16A Device $I_T = 32A$; $t_p = 380\ \mu s$					
I_{DRM} / I_{RRM}	$V_{DRM} = V_{RRM}$	$T_J = 25^{\circ}C$	400 - 600V	MAX.	10	μA
			800 - 1000V		20	
		$T_J = 100^{\circ}C$	400 - 600V		500	
			800V		1000	
			1000V		3000	
		$T_J = 125^{\circ}C$	400 - 600V		1000	
			800V		2000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx16R/ Sxx16N	1.1	$^\circ\text{C}/\text{W}$
		Sxx15L	2.5	
$R_{\theta(J-A)}$	Junction to ambient	Sxx16R	40	$^\circ\text{C}/\text{W}$
		Sxx15L	50	

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

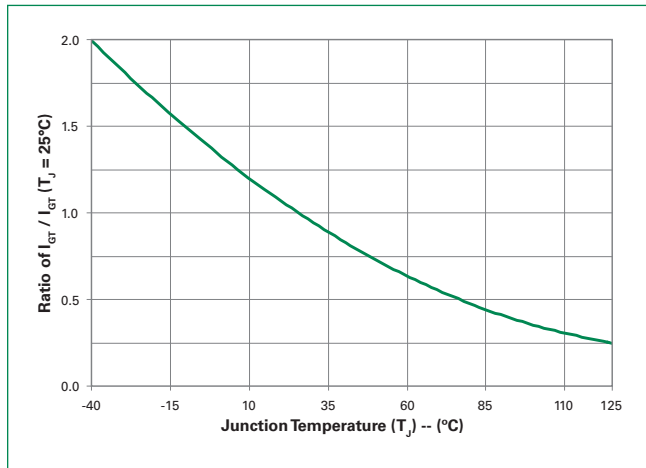


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

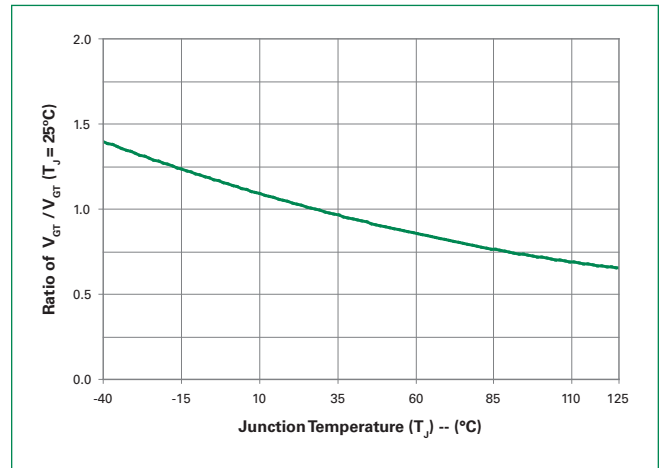


Figure 3: Normalized DC Holding Current vs. Junction Temperature

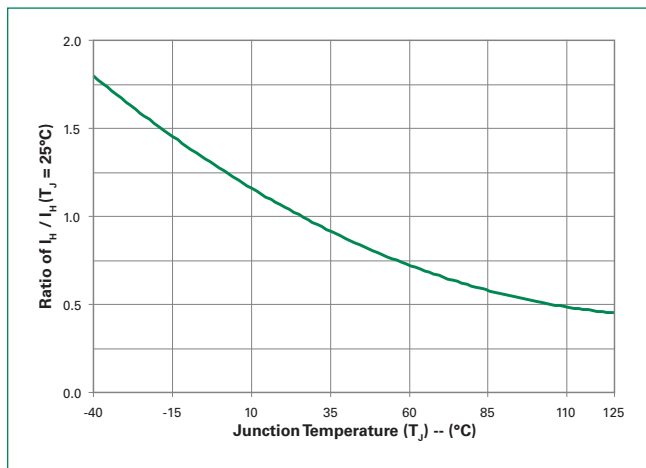


Figure 4: On-State Current vs. On-State Voltage (Typical)

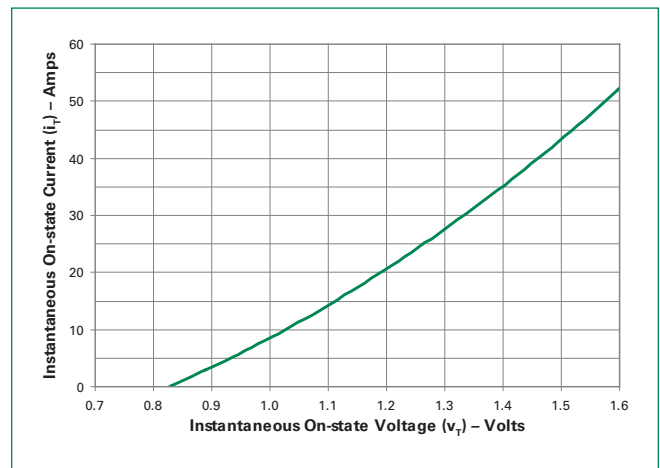


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

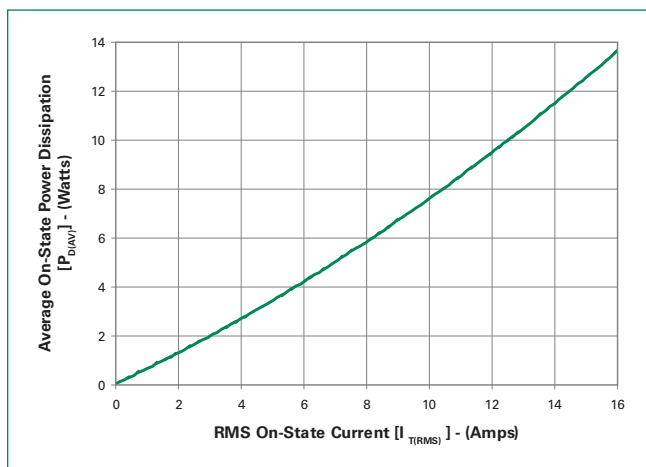


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

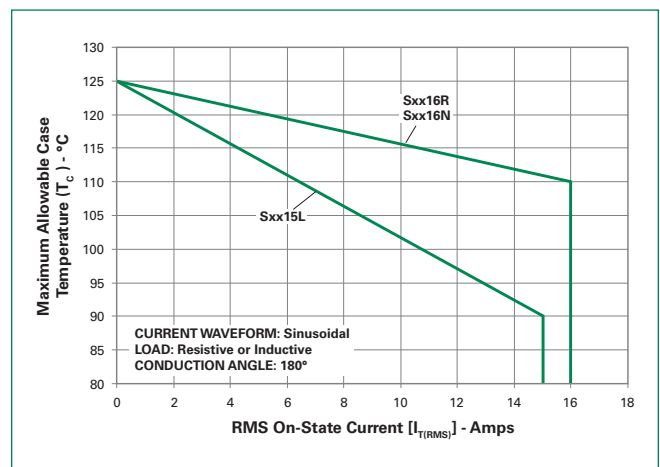


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

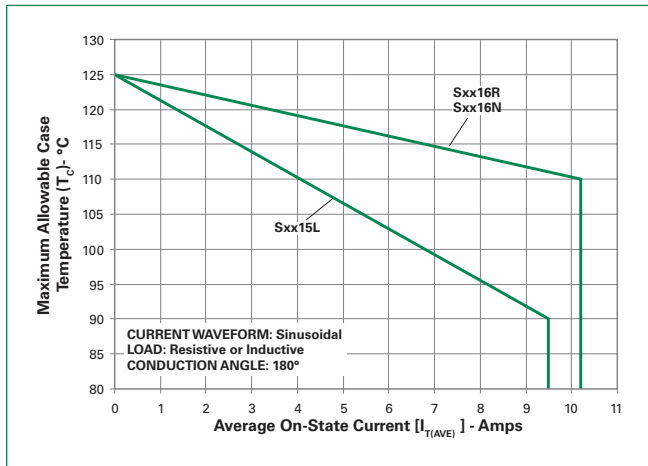


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current

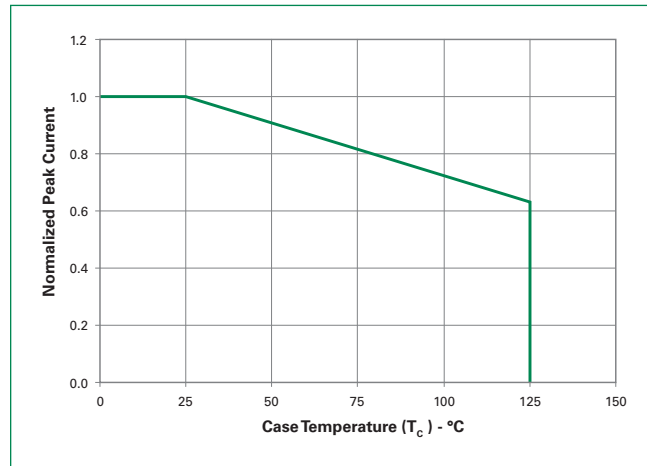
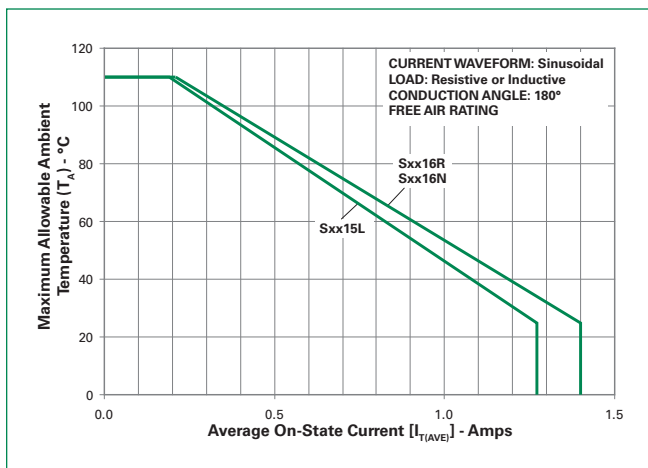


Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current



Note: xx = voltage

Figure 10: Peak Capacitor Discharge Current

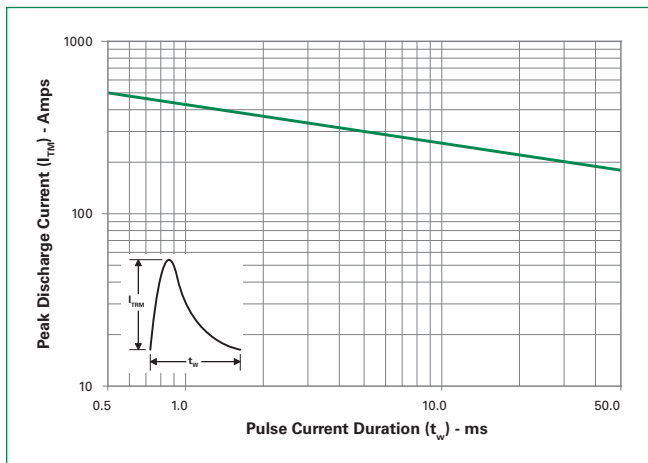


Figure 11: Peak Capacitor Discharge Current Derating

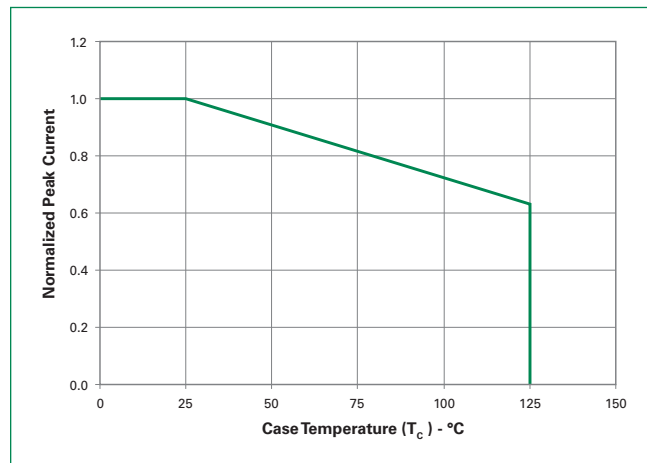
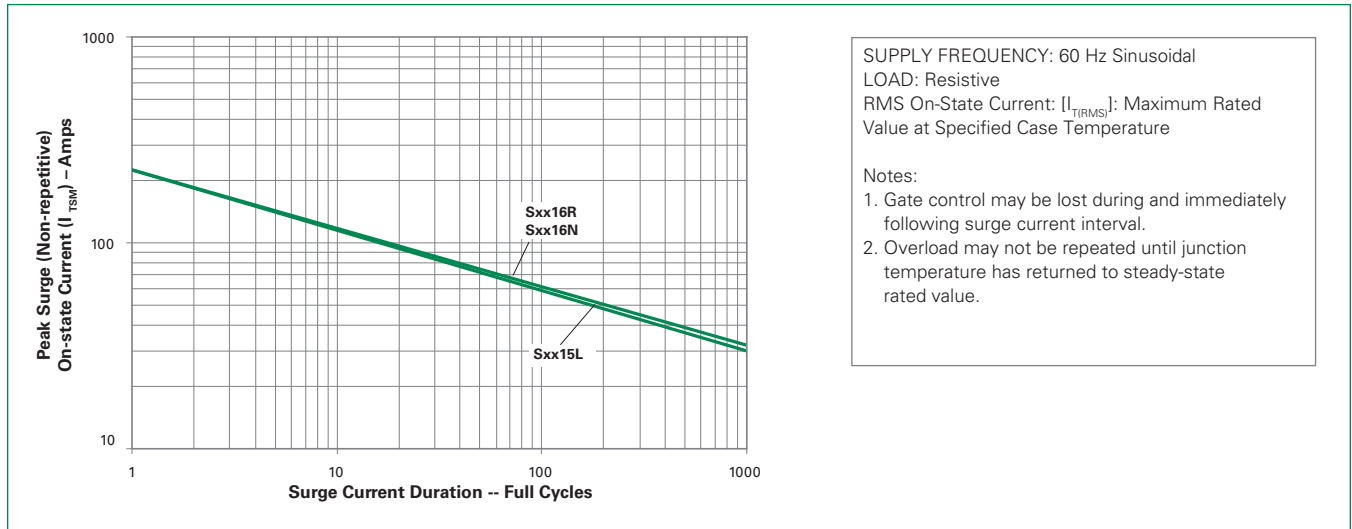
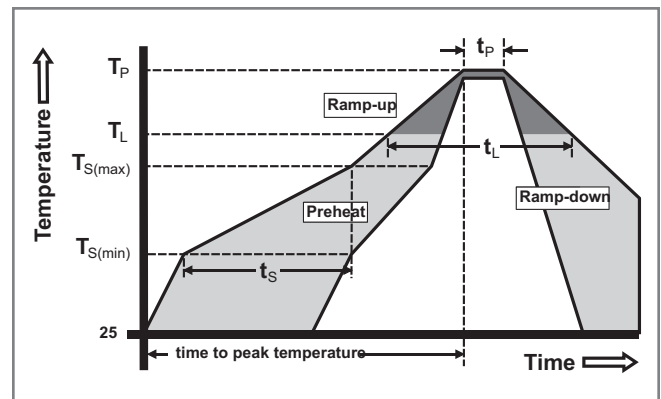


Figure 12: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

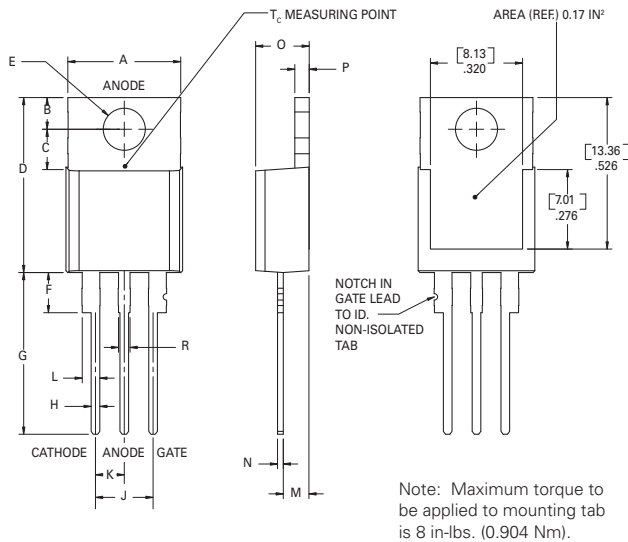
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

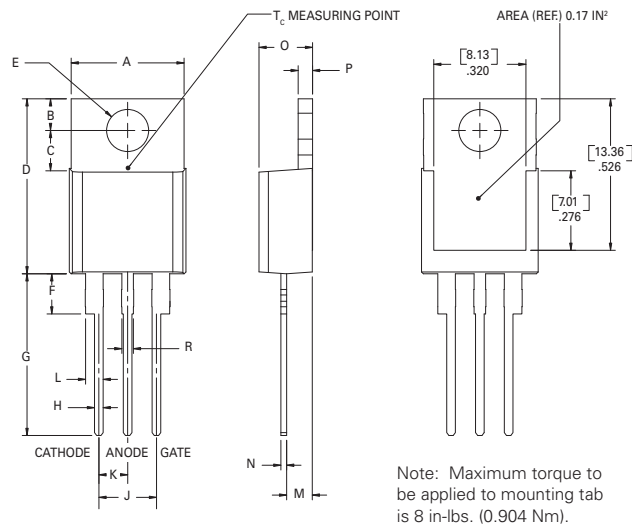
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



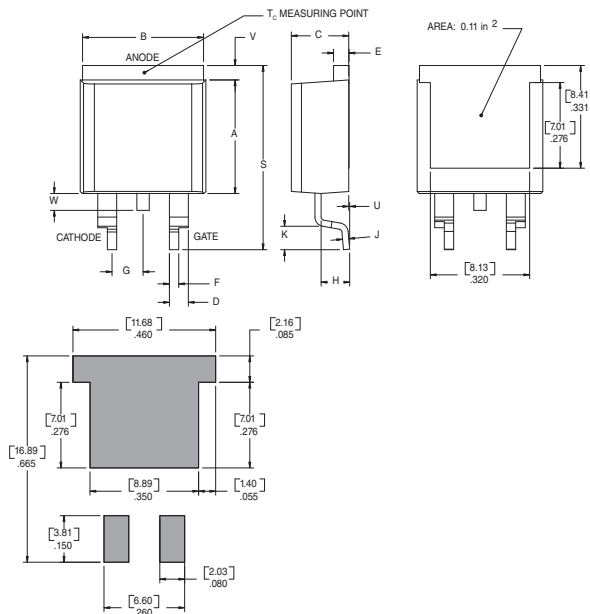
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO- 263AA (N-package) — D²-Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx15L	X	X	X	X	30mA	Standard SCR	TO-220L
Sxx16R	X	X	X	X	30mA	Standard SCR	TO-220R
Sxx16N	X	X	X	X	30mA	Standard SCR	TO-263

Note: xx = Voltage

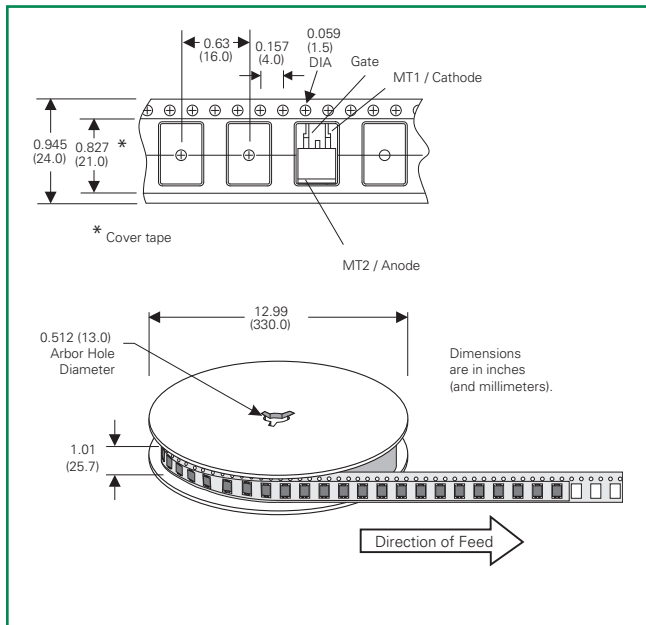
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx15L	Sxx15L	2.2 g	Bulk	500
Sxx15LTP	Sxx15L	2.2 g	Tube	500
Sxx16R	Sxx16R	2.2 g	Bulk	500
Sxx16RTP	Sxx16R	2.2 g	Tube	500
Sxx16NTP	Sxx16N	1.6 g	Tube	500
Sxx16NRP	Sxx16N	1.6 g	Embossed Carrier	500

Note: xx = Voltage

TO-263 Embossed Carrier Reel Pack (RP) Specs

Meets all EIA-481-2 Standards

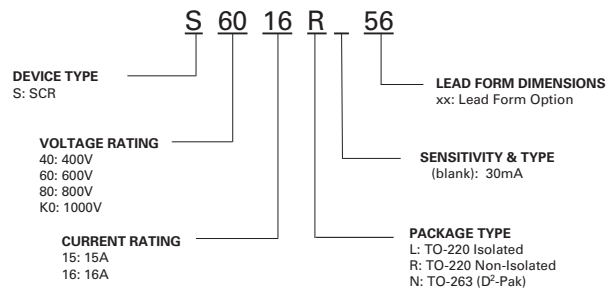


Part Marking System

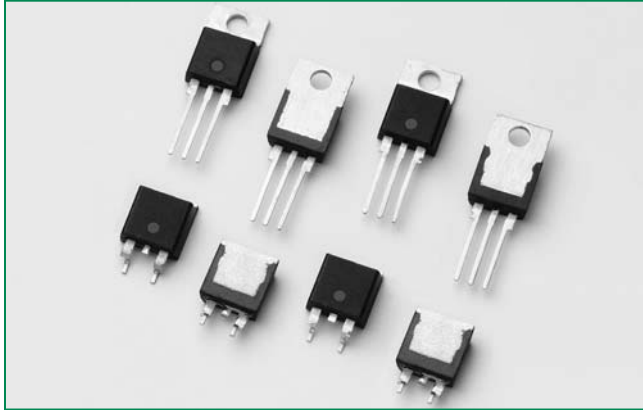
TO-220 AB (R, and L Packages)
TO-263 AA (N Package)



Part Numbering System



RoHS Sxx20x & Sxx25x Series



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

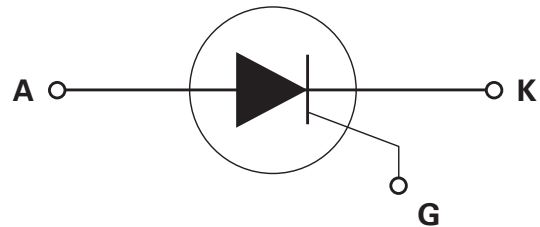
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 350 A

Applications


Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Agency Approval

Agency	Agency File Number
	L Package: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	20 & 25	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	30 to 35	mA

Absolute Maximum Ratings — 20A SCR

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 80^\circ\text{C}$	20	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	255	A
		single half cycle; $f = 60\text{Hz}$; $T_j(\text{initial}) = 25^\circ\text{C}$	300	
I^2t	I^2t Value for fusing	$t_p = 8.3\text{ ms}$	374	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_j = 125^\circ\text{C}$	125	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_j = 125^\circ\text{C}$	3	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.6	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Absolute Maximum Ratings — 25A SCR

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx25L: $T_c=75^\circ\text{C}$ Sxx25R/Sxx25N: $T_c=100^\circ\text{C}$	25	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; T_J (initial) = 25°C	300	A
		single half cycle; $f = 60\text{Hz}$; T_J (initial) = 25°C	350	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	510	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_J = 125^\circ\text{C}$	150	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_J = 125^\circ\text{C}$	3.5	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$	0.8	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value		Unit
				Sxx20L	Sxx25x	
I _{GT}	V _D = 12V; R _L = 60Ω		MAX.	30	35	mA
V _{GT}			MIN.	1	1	
			MAX.	1.5		V
dv/dt	V _D = V _{DRM} ; gate open; T _J = 100°C	400V	MIN.	450		V/μs
		600V		425		
		800V		400		
		1000V		200		
	V _D = V _{DRM} ; gate open; T _J = 125°C	400V		350		
		600V		325		
		800V		300		
V _{GD}	V _D = V _{DRM} ; R _L = 3.3 kΩ; T _J = 125°C		MIN.	0.2		V
I _H	I _T = 200mA (initial)		MAX.	40	50	mA
t _q	(1)		MAX.	35		μs
t _{gt}	I _G = 2 x I _{GT} ; PW = 15μs; I _T = 40A		TYP.	2		μs

Notes :

xx = voltage, x = package

(1) $I_T=2\text{A}$; $t_p=50\mu\text{s}$; $dv/dt=5\text{V}/\mu\text{s}$; $di/dt=30\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions			Value	Unit	
V _{TM}	20A Device I _T = 40A; t _p = 380μs		MAX.	1.6	V	
	25A Device I _T = 50A; t _p = 380μs					
I _{DRM} / I _{RRM}	V _{DRM} / V _{RRM}	T _J = 25°C	400 – 600V	MAX.	10	μA
			800 – 1000V		20	
		T _J = 100°C	400 – 600V		500	
			800V		1000	
			1000V		3000	
		T _J = 125°C	400 – 600V		1000	
			800V		2000	

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx25R / Sxx25N	1.0
		Sxx20L	2.4
		Sxx25L	2.35
$R_{\theta(J-A)}$	Junction to ambient	Sxx25R	40
		Sxx20L Sxx25R / Sxx25L	50

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

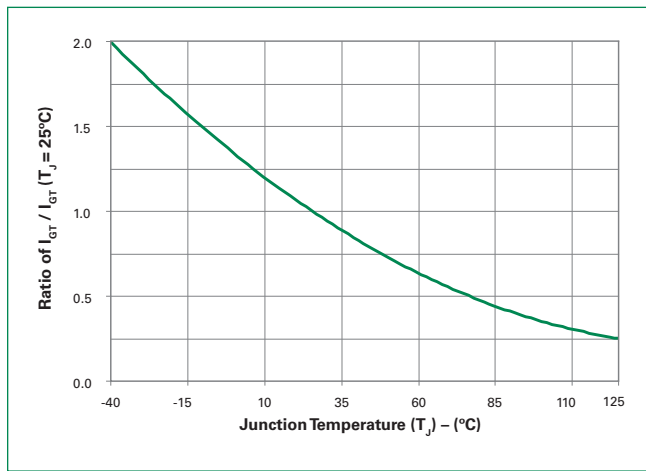


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

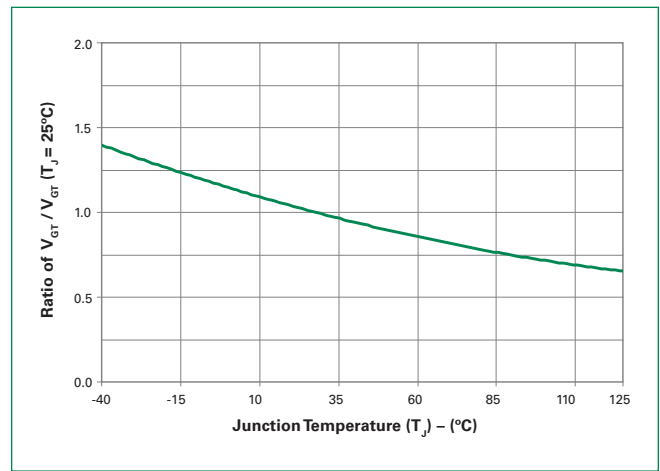


Figure 3: Normalized DC Holding Current vs. Junction Temperature

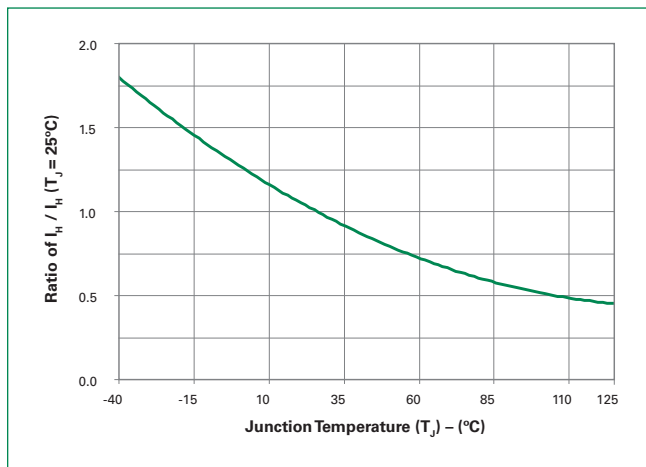


Figure 4: On-State Current vs. On-State Voltage (Typical)

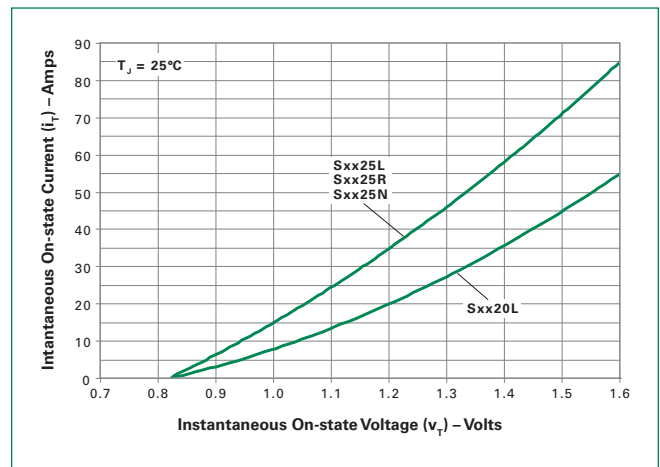


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

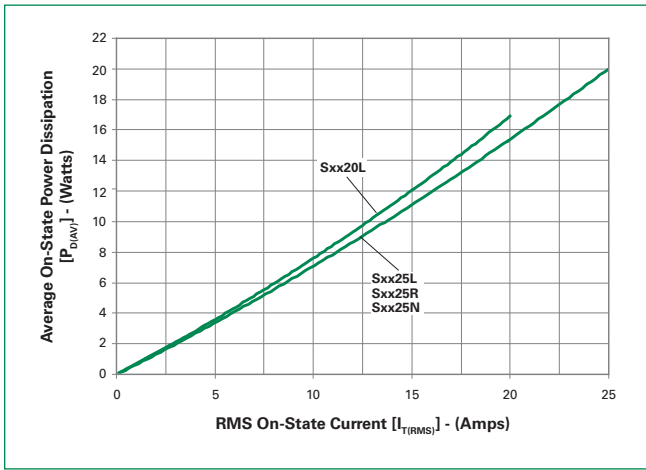


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

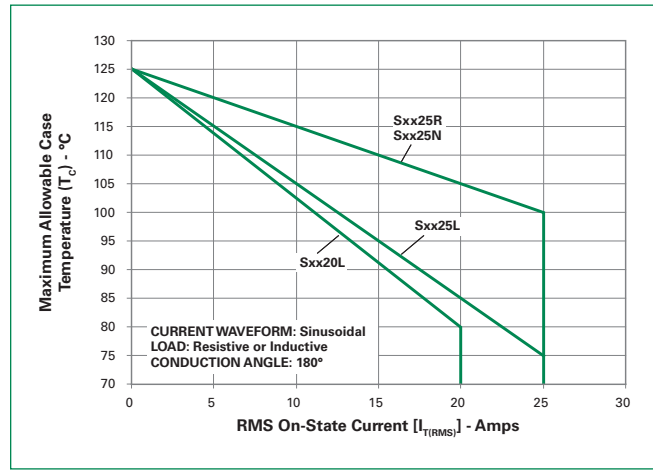


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

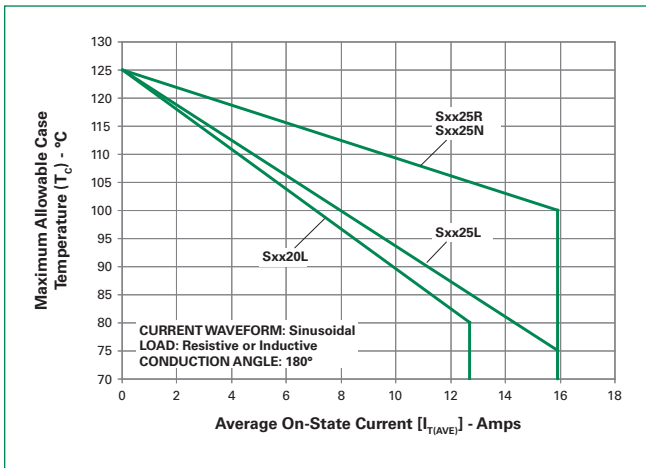


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current

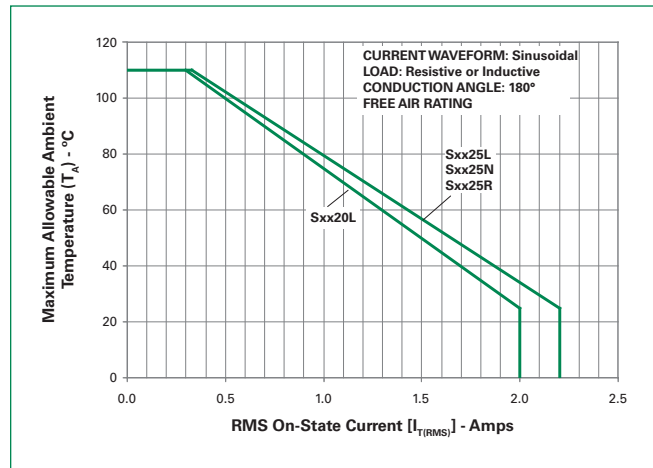
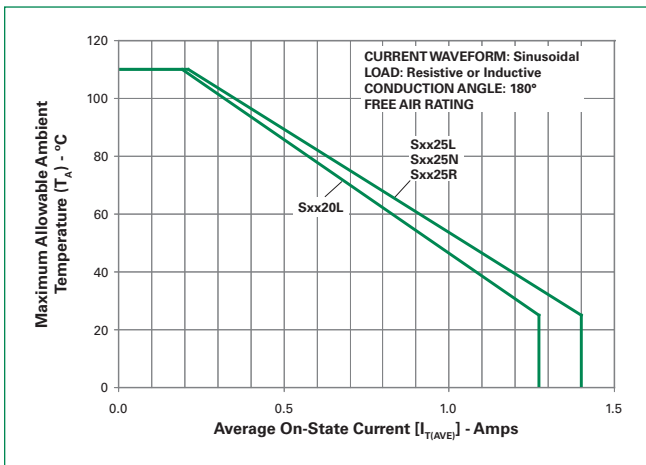


Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current



Note: xx = voltage

Figure 10: Peak Capacitor Discharge Current

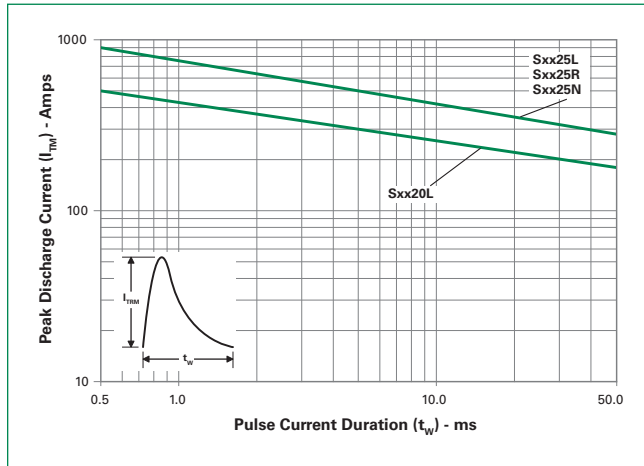


Figure 11: Peak Capacitor Discharge Current Derating

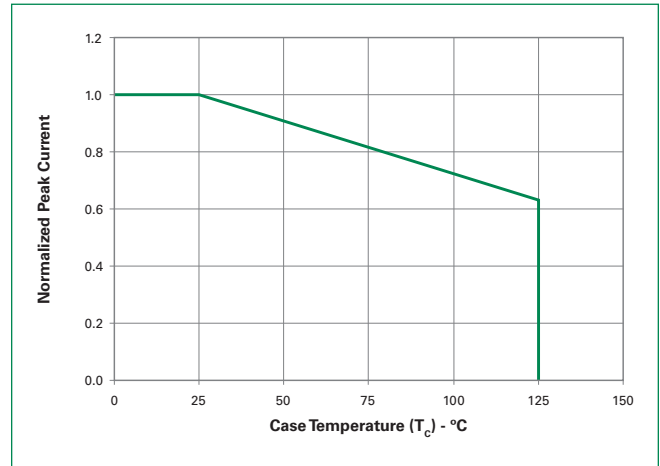
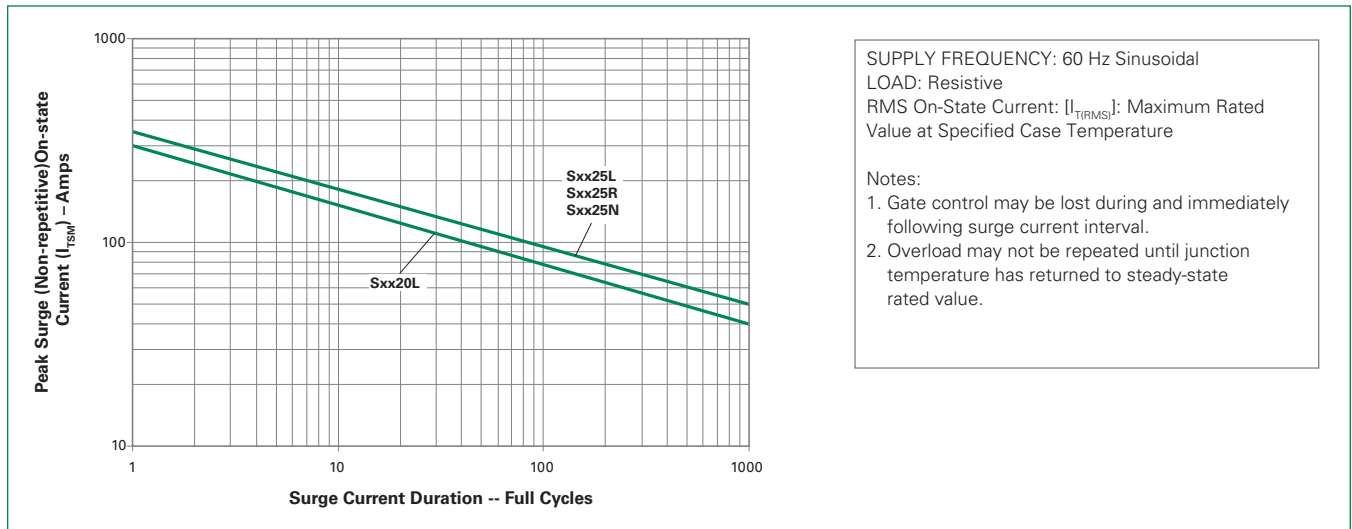
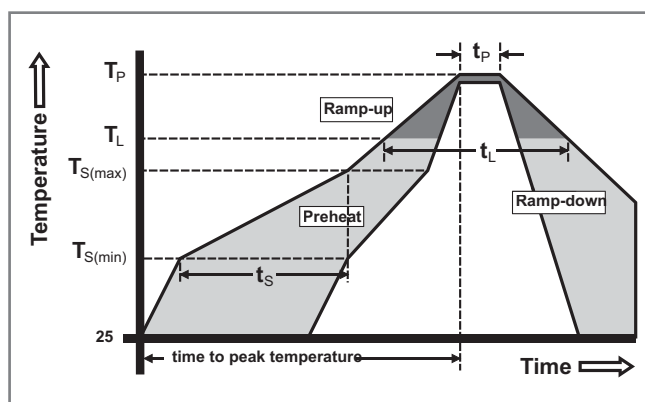


Figure 12: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

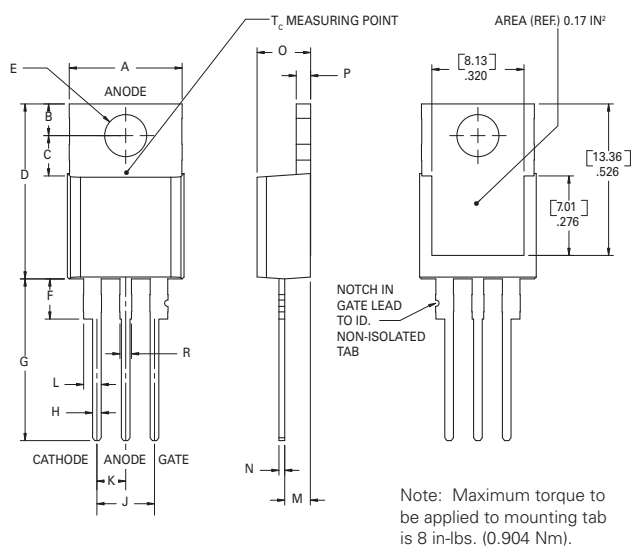
Design Considerations

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Environmental Specifications

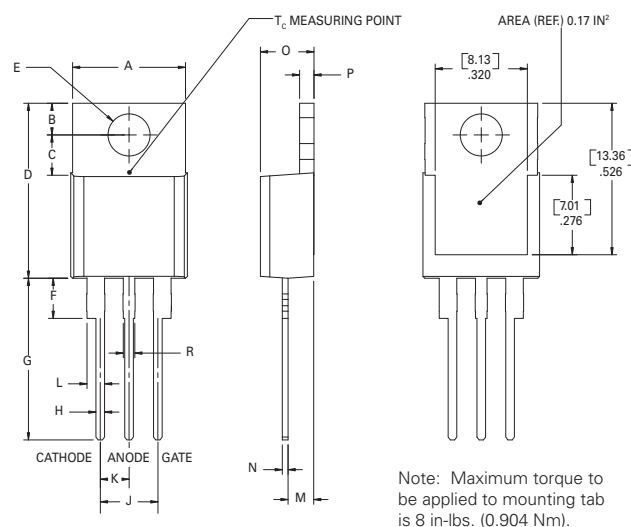
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwelltime at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



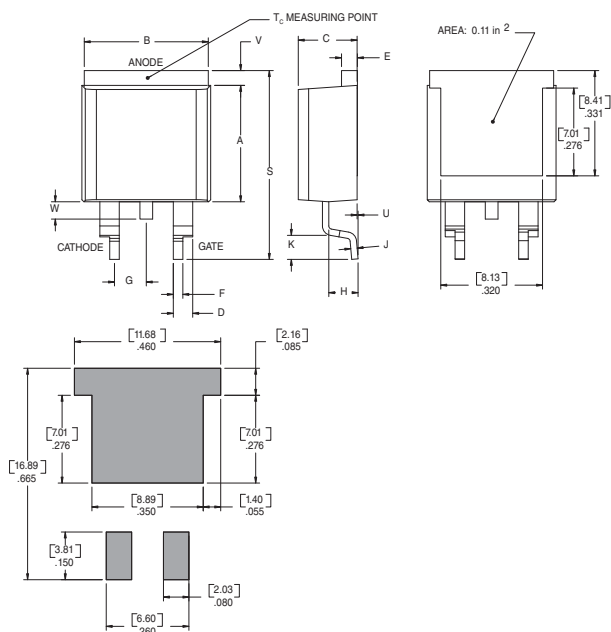
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions –TO- 263AA (N-package) — D²-Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.016	1.78

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx20L	X	X	X	X	30mA	Standard SCR	TO-220L
Sxx25L	X	X	X	X	35mA	Standard SCR	TO-220L
Sxx25R	X	X	X	X	35mA	Standard SCR	TO-220R
Sxx25N	X	X	X	X	35mA	Standard SCR	TO-263

Note: xx = Voltage

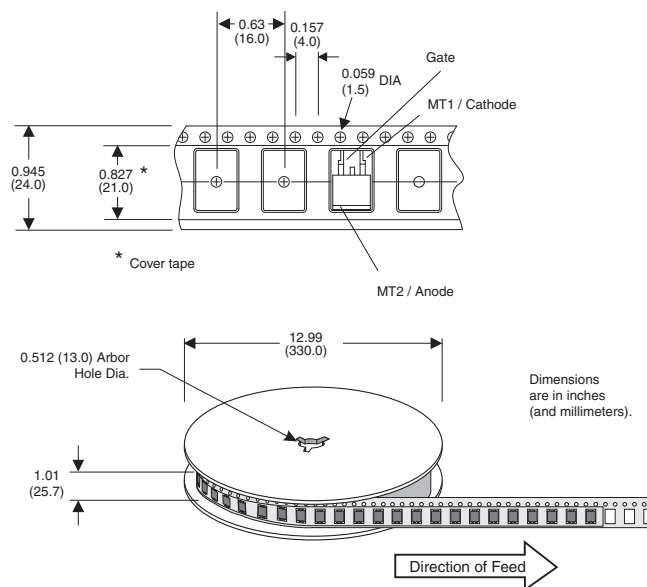
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx20L	Sxx20L	2.2g	Bulk	500
Sxx20LTP	Sxx20L	2.2g	Tube	500
Sxx25L	Sxx25L	2.2g	Bulk	500
Sxx25LTP	Sxx25L	2.2g	Tube	500
Sxx25R	Sxx25R	2.2g	Bulk	500
Sxx25RTP	Sxx25R	2.2g	Tube	500
Sxx25NTP	Sxx25N	1.6g	Tube	500
Sxx25NRP	Sxx25N	1.6g	Embossed Carrier	500

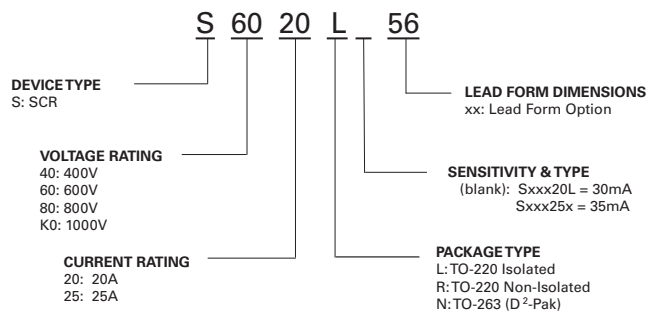
Note: xx = Voltage

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

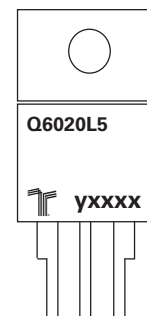


Part Numbering System



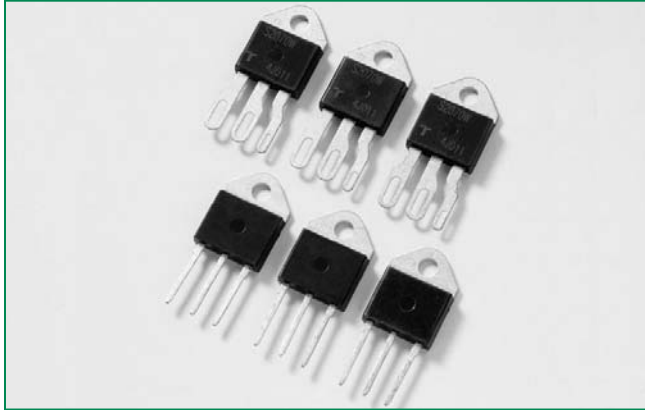
Part Marking System

TO-220 AB (R, and L Packages)
TO-263 AA (N Package)





RoHS Sxx35x Series



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits


- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 500 A

Applications

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

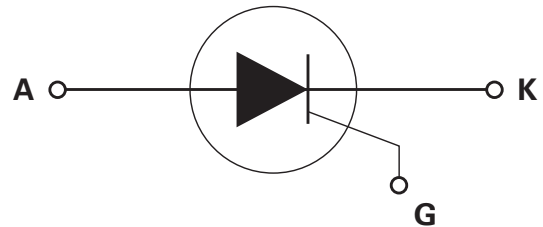
Agency Approval

Agency	Agency File Number
	J & K Packages: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	35	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	40	mA

Schematic Symbol



Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 95^\circ\text{C}$	35	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_j (\text{initial}) = 25^\circ\text{C}$	425	A
		single half cycle; $f = 60\text{Hz}$; $T_j (\text{initial}) = 25^\circ\text{C}$	500	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	1035	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_j = 125^\circ\text{C}$	150	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_j = 125^\circ\text{C}$	3.5	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.8	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value	Unit
I_{GT}	$V_D = 12\text{V}; R_L = 60\Omega$		MAX.	40	mA
			MIN.	5	
V_{GT}			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}; \text{gate open}; T_J = 100^\circ\text{C}$	400V	MIN.	450	V/ μs
		600V		425	
		800V		400	
		1000V		200	
	$V_D = V_{DRM}; \text{gate open}; T_J = 125^\circ\text{C}$	400V		350	
		600V		325	
		800V		300	
V_{GD}	$V_D = V_{DRM}; R_L = 3.3\text{ k}\Omega; T_J = 125^\circ\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	50	mA
t_q	(1)		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}; \text{PW} = 15\mu\text{s}; I_T = 70\text{A}$		TYP.	2	μs

Notes :

(1) $I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; dv/dt=5V/ μs ; di/dt=-30A/ μs

Static Characteristics

Symbol	Test Conditions			Value	Unit
V_{TM}	$I_T = 70\text{A}; t_p = 380\mu\text{s}$		MAX.	1.8	V
I_{DRM} / I_{RRM}	V_{DRM} / V_{RRM}	$T_J = 25^\circ\text{C}$	400 – 600V	10	μA
			800 – 1000V	20	
		$T_J = 100^\circ\text{C}$	400 – 600V	1000	
			800V	1500	
			1000V	3000	
		$T_J = 125^\circ\text{C}$	400 – 600V	2000	
			800V	3000	

Thermal Resistance

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	0.7	$^\circ\text{C/W}$

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

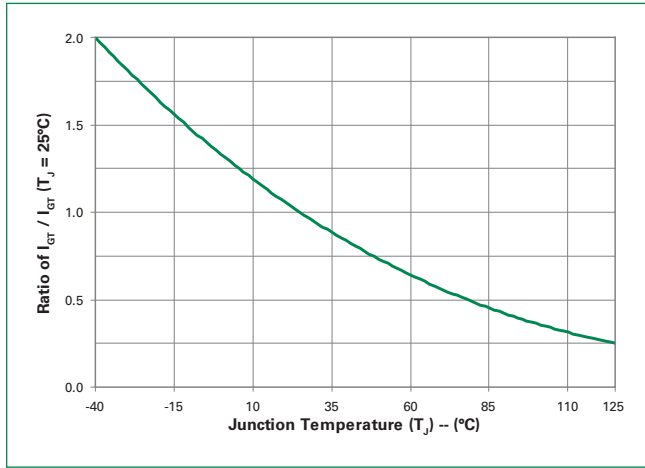


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

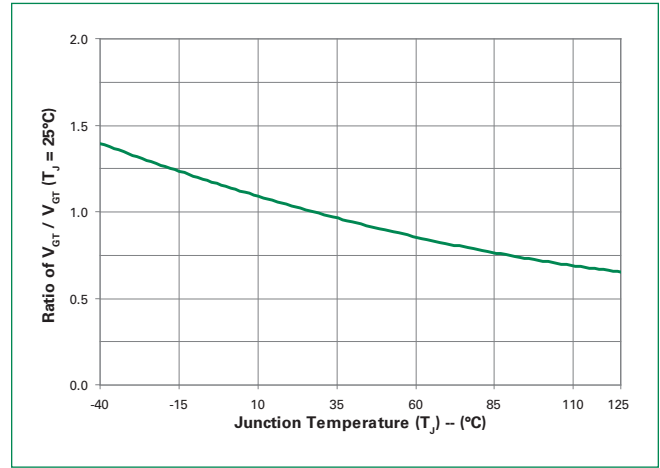


Figure 3: Normalized DC Holding Current vs. Junction Temperature

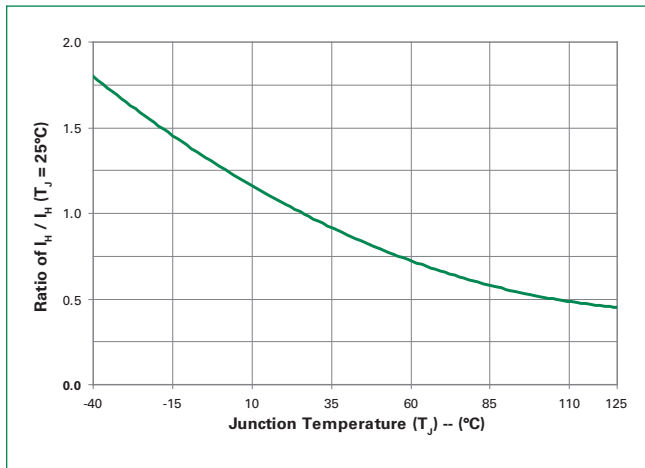


Figure 4: On-State Current vs. On-State Voltage (Typical)

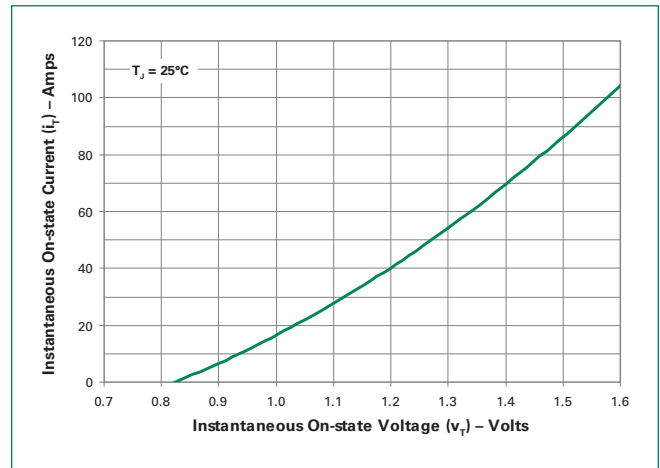


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

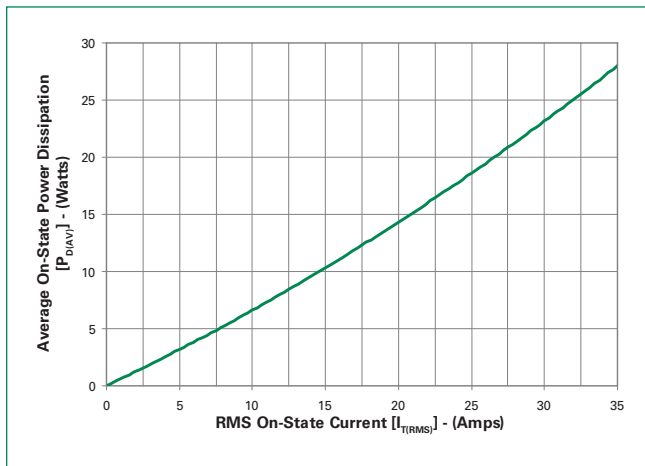


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

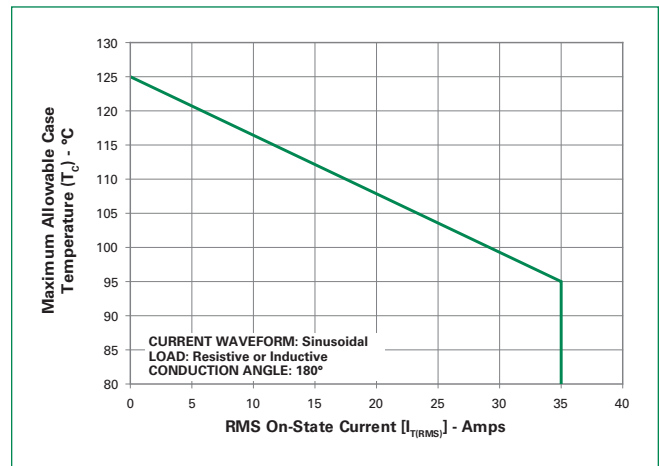


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

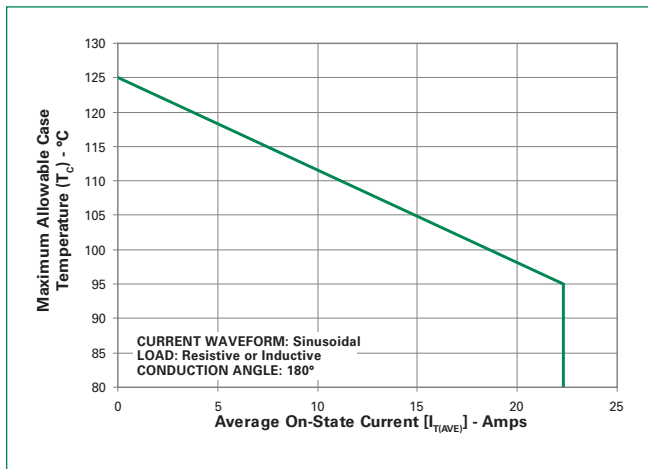


Figure 8: Peak Capacitor Discharge Current

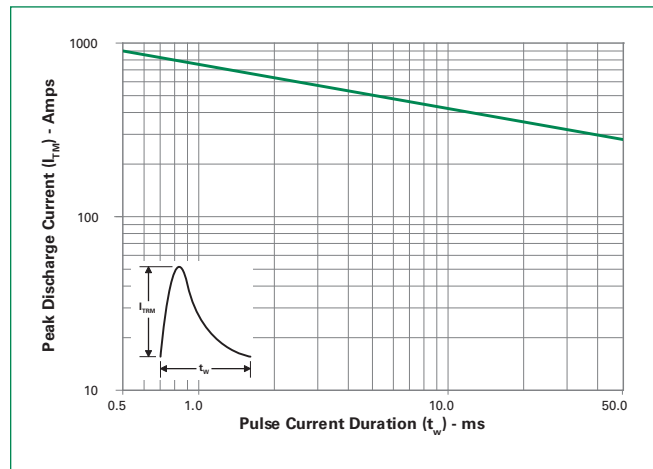


Figure 9: Peak Capacitor Discharge Current Derating

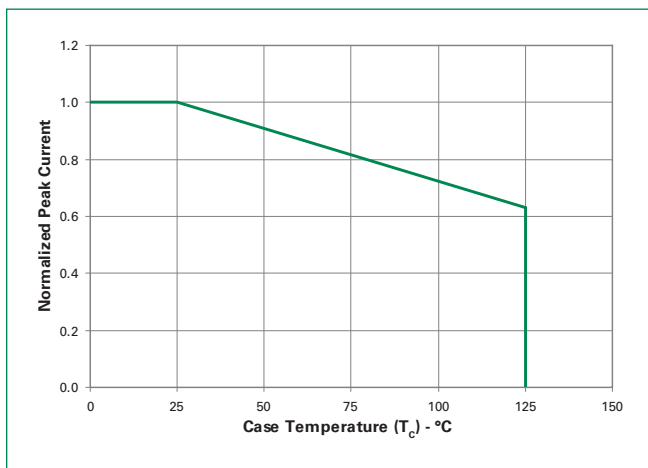
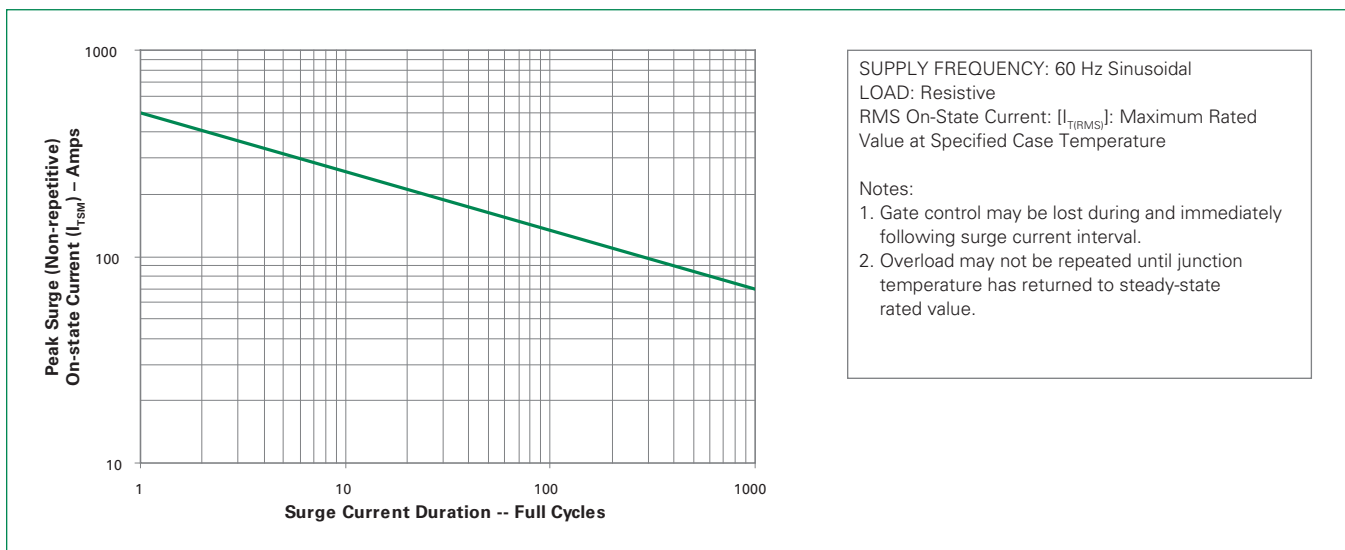
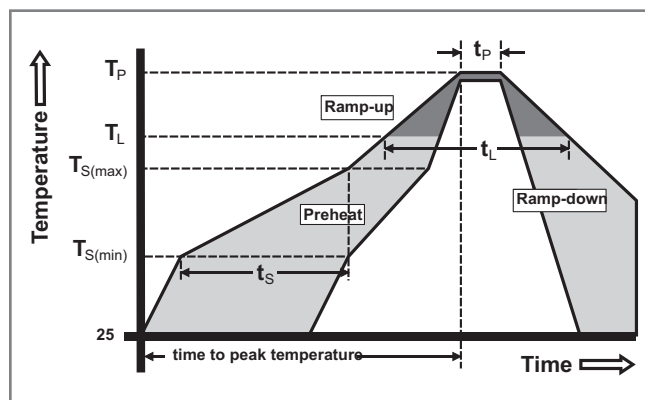


Figure 10: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

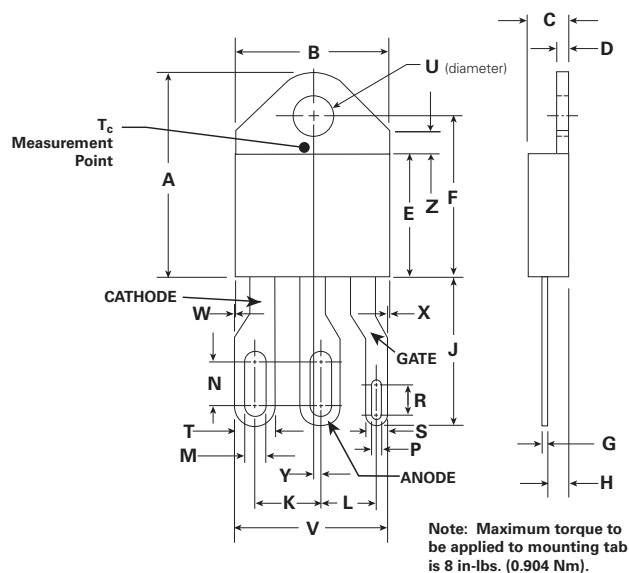
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

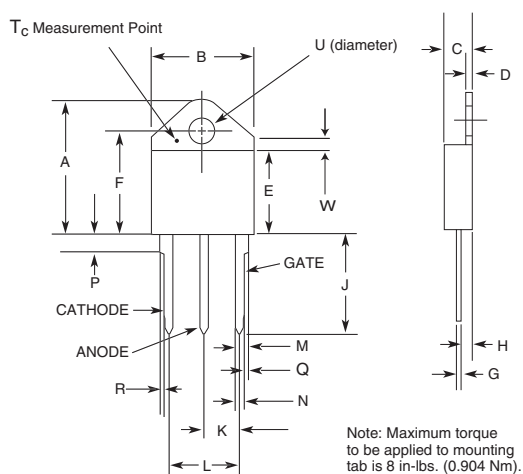
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwelltime at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions –TO- 218X (J Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Dimensions –TO- 218AC (K Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.164	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx35K	X	X	X	X	40mA	Standard SCR	TO-218AC
Sxx35J	X	X	X		40mA	Standard SCR	TO-218X

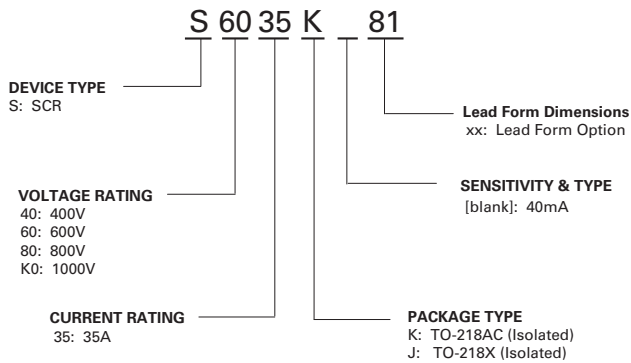
Note: xx = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx35K	Sxx35K	4.40g	Bulk	250
Sxx35KTP	Sxx35K	4.40g	Tube	500
Sxx35J	Sxx35J	5.23g	Bulk	250
Sxx35JTP	Sxx35J	5.23g	Tube	500

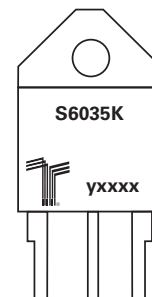
Note: xx = Voltage

Part Numbering System

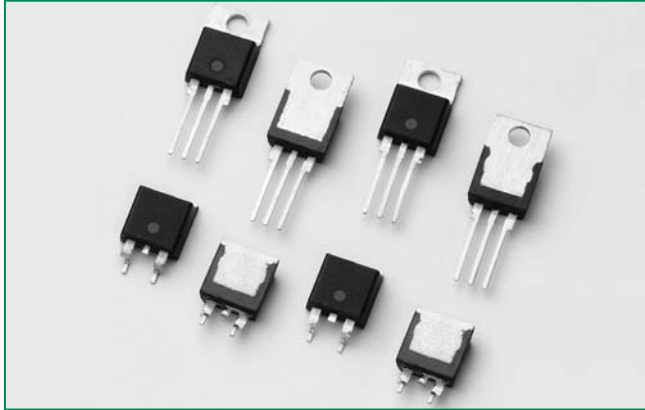


Part Marking System

TO-218 AC (K Package)
TO-218 X – (J Package)



RoHS **Sxx40x Series**



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

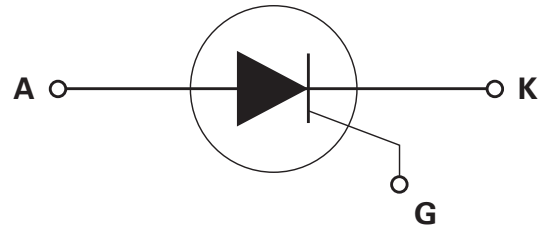
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 520 A

Applications

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	40	μA

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 100^\circ C$	40	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50Hz$; T_j (initial) = $25^\circ C$	430	A
		single half cycle; $f = 60Hz$; T_j (initial) = $25^\circ C$	520	
I^2t	I^2t Value for fusing	$t_p = 8.3 ms$	1122	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60Hz$; $T_j = 125^\circ C$	175	$A/\mu s$
I_{GM}	Peak gate current	$T_j = 125^\circ C$	3.5	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ C$	0.8	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ C$
T_j	Operating junction temperature range		-40 to 125	$^\circ C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value	Unit
I_{GT}	$V_D = 12\text{V}; R_L = 60\ \Omega$		MAX.	40	mA
			MIN.	5	
V_{GT}			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}; \text{gate open}; T_J = 100^\circ\text{C}$	400V	MIN.	650	V/ μs
		600V		600	
		800V		500	
		1000V		250	
	$V_D = V_{DRM}; \text{gate open}; T_J = 125^\circ\text{C}$	400V		550	
		600V		500	
		800V		475	
V_{GD}	$V_D = V_{DRM}; R_L = 3.3\ \text{k}\Omega; T_J = 125^\circ\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	60	mA
t_q	(1)		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}; \text{PW} = 15\mu\text{s}; I_T = 80\text{A}$		TYP.	2.5	μs

Note :

(1) $I_T = 2\text{A}; t_p = 50\mu\text{s}; dv/dt = 5\text{V}/\mu\text{s}; di/dt = 30\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions			Value	Unit
V_{TM}	$I_T = 80\text{A}; t_p = 380\mu\text{s}$		MAX.	1.8	V
I_{DRM} / I_{RRM}	V_{DRM} / V_{RRM}	$T_J = 25^\circ\text{C}$	400 – 600V	10	μA
			800 V	20	
			1000 V	30	
		$T_J = 100^\circ\text{C}$	400 – 600V	1000	
			800V	1500	
			1000V	5000	
		$T_J = 125^\circ\text{C}$	400 – 600V	2000	
			800V	3000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx40R / Sxx40N	0.6	$^\circ\text{C}/\text{W}$
$R_{\theta(J-A)}$	Junction to ambient	Sxx40R	40	$^\circ\text{C}/\text{W}$

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

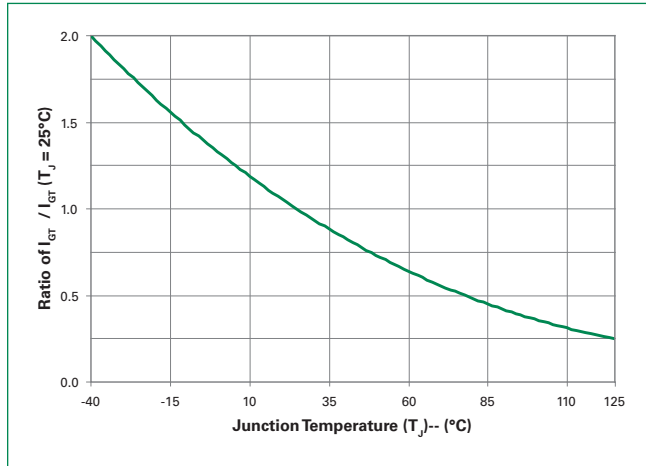


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

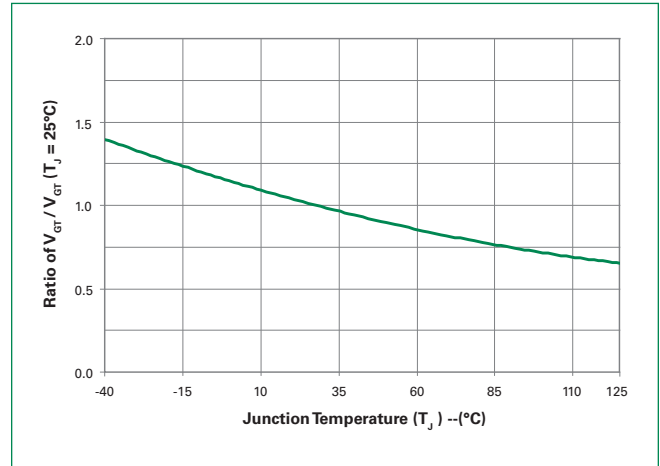


Figure 3: Normalized DC Holding Current vs. Junction Temperature

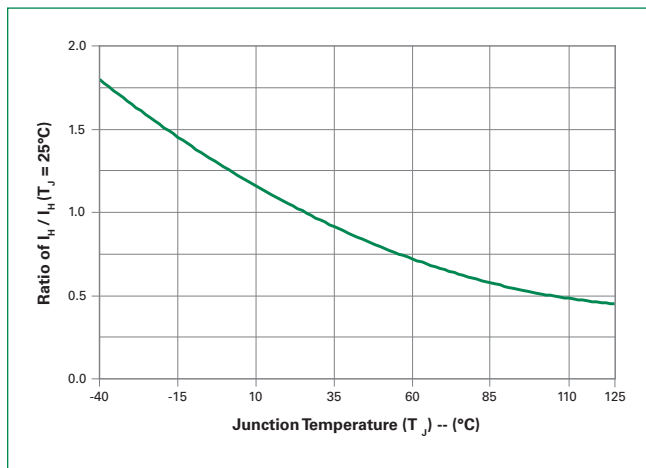


Figure 4: On-State Current vs. On-State Voltage (Typical)

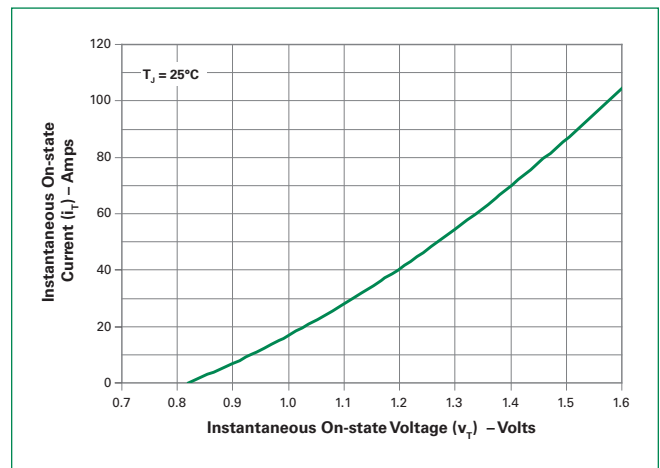


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

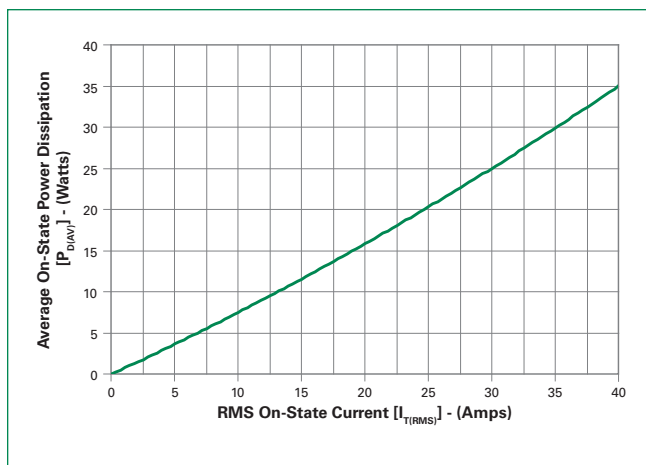


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

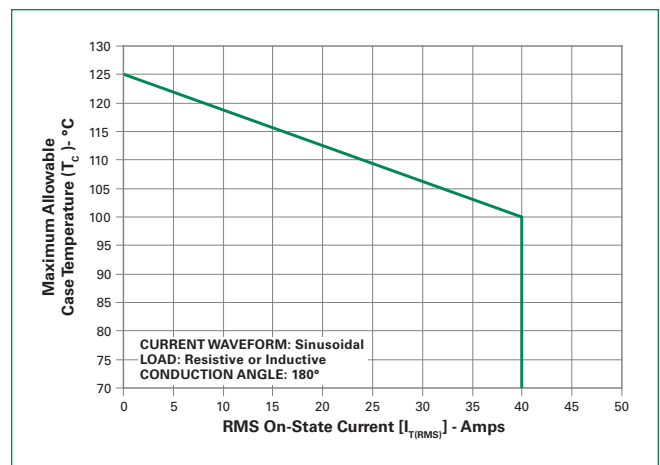


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

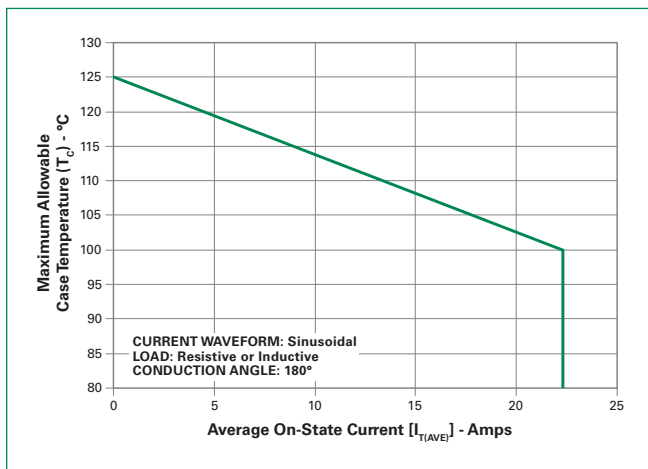


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current

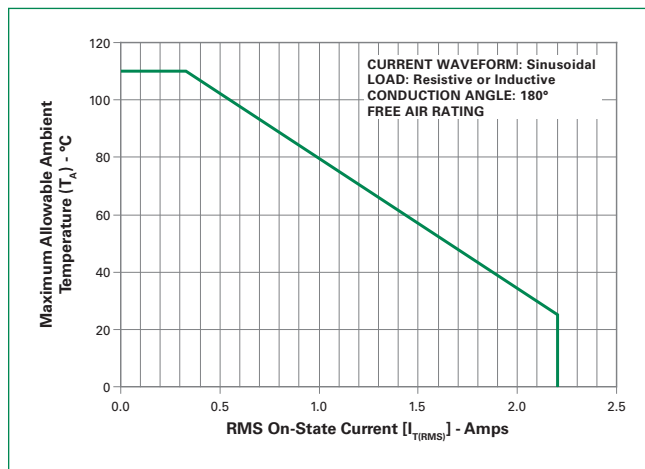


Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current

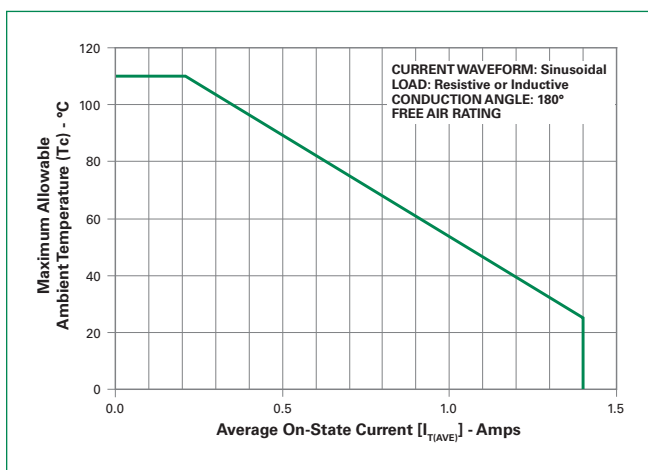


Figure 10: Peak Capacitor Discharge Current

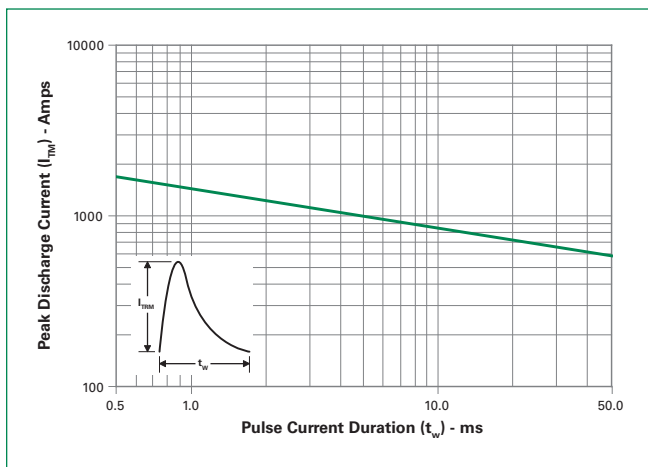


Figure 11: Peak Capacitor Discharge Current Derating

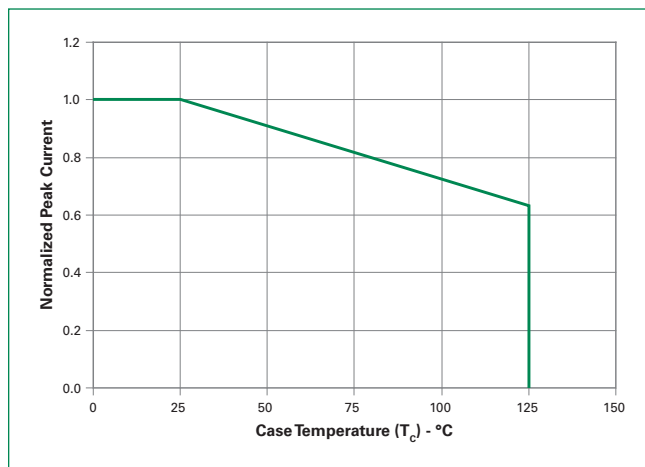
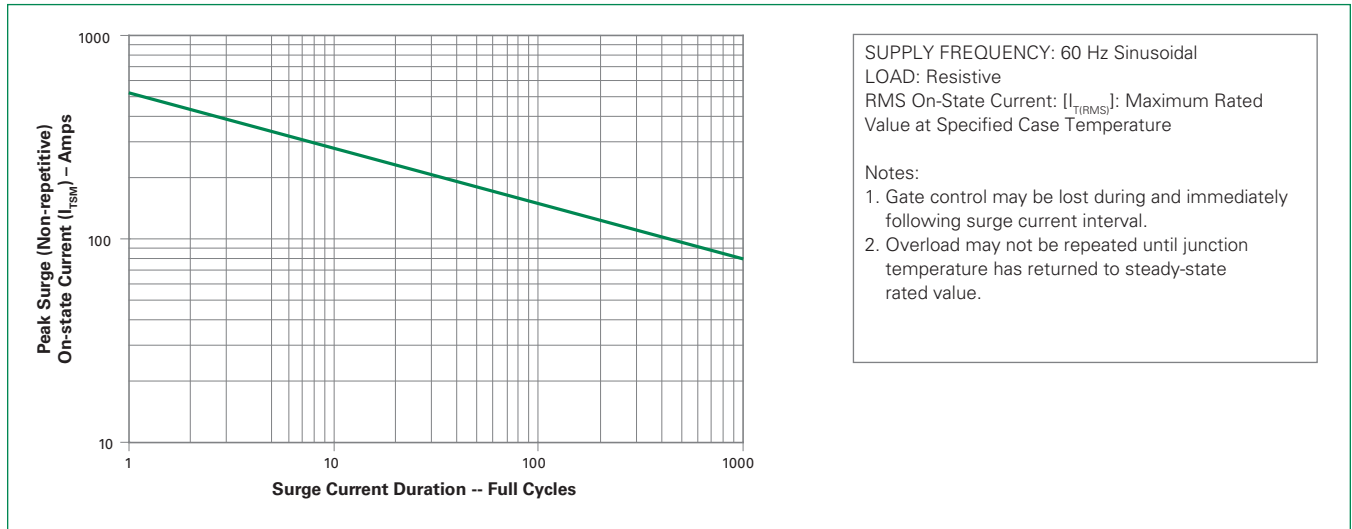
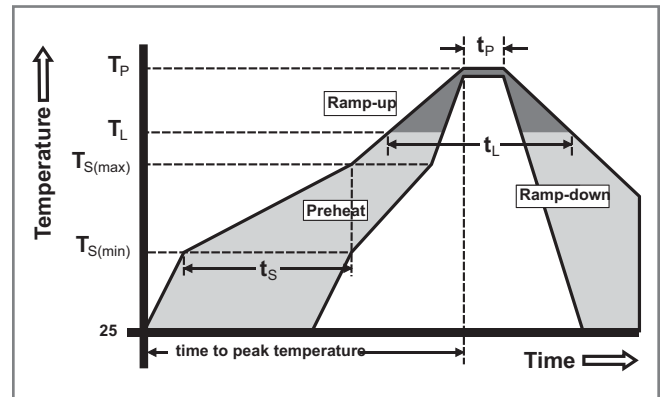


Figure 12: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

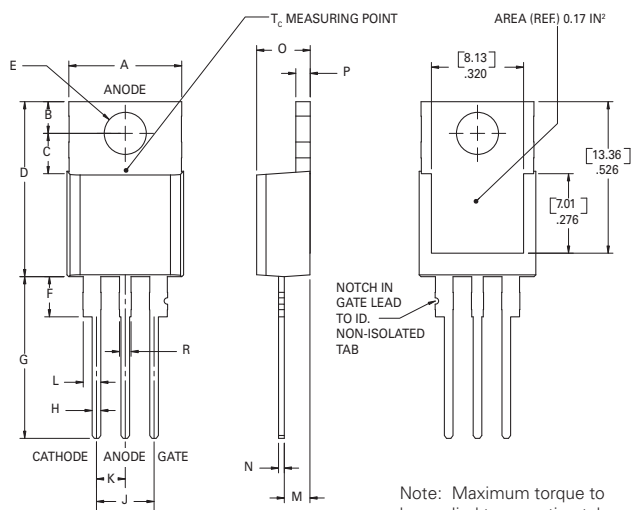
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

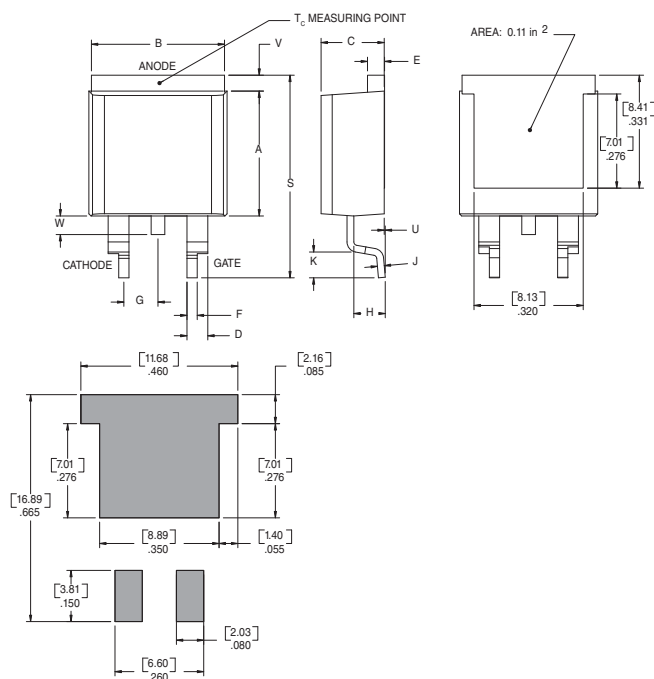
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwelltime at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



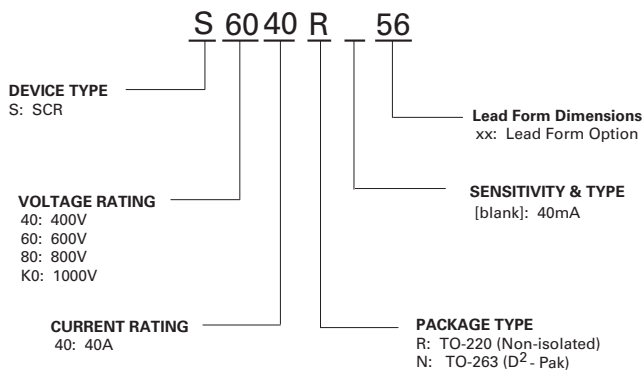
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions – TO- 263 (N-package) — D²-Pak Surface Mount



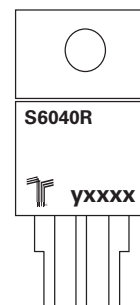
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.63	0.89
E	0.048	0.055	1.22	1.40
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.083	0.093	2.11	2.36
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.87
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Part Numbering System



Part Marking System

TO-220 AB (R Package)
TO-263 (N Package)



Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx40R	X	X	X	X	40mA	Standard SCR	TO-220R
Sxx40N	X	X	X	X	40mA	Standard SCR	TO-263

Note: xx = Voltage

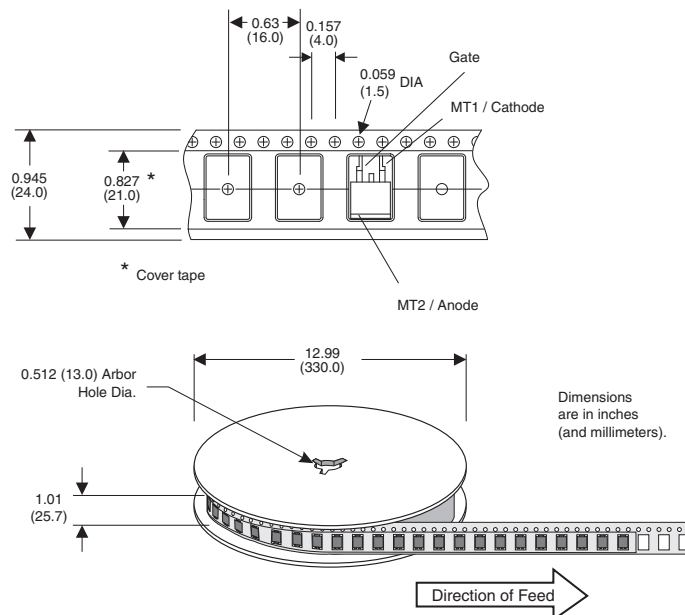
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx40R	Sxx40R	2.2g	Bulk	500
Sxx40RTP	Sxx40R	2.2g	Tube	500
Sxx40NTP	Sxx40N	1.6g	Tube	500
Sxx40NRP	Sxx40N	1.6g	Embossed Carrier	500

Note: xx = Voltage

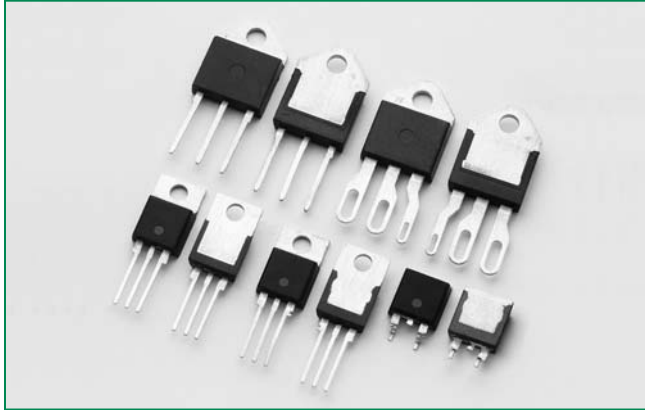
Reel Pack (RP) for TO-263 Embossed Carrier Specifications

Meets all EIA-481-2 Standards



RoHS

Sxx55x Series



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

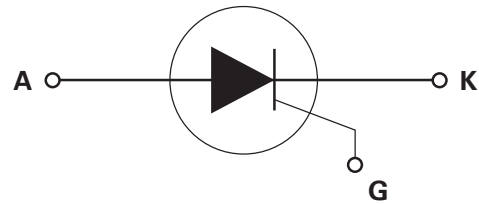
Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 650 A

Applications

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Schematic Symbol



Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	55	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	40	mA

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 90^\circ\text{C}$	55	A
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_J (\text{initial}) = 25^\circ\text{C}$	550	A
		single half cycle; $f = 60\text{Hz}$; $T_J (\text{initial}) = 25^\circ\text{C}$	650	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	1750	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_J = 125^\circ\text{C}$	175	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_J = 125^\circ\text{C}$ $P_w = 10\mu\text{S}$	4.0	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$	0.8	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

55 A SCRs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value	Unit
I _{GT}	V _D = 12V; R _L = 60 Ω		MAX.	40	mA
			MIN.	5	
V _{GT}			MAX.	1.5	V
dv/dt	V _D = V _{DRM} ; gate open; T _J = 100°C	400V	MIN.	650	V/μs
		600V		600	
		800V		500	
		1000V		250	
	V _D = V _{DRM} ; gate open; T _J = 125°C	400V		550	
		600V		500	
		800V		475	
V _{GD}	V _D = V _{DRM} ; R _L = 3.3 kΩ; T _J = 125°C		MIN.	0.2	V
I _H	I _T = 200mA (initial)		MAX.	60	mA
t _q	(1)		MAX.	35	μs
t _{gt}	I _G = 2 × I _{GT} ; PW = 15μs; I _T = 110A		TYP.	2.5	μs

Note :

(1) $I_T=2\text{A}$; $t_p=50\mu\text{s}$; $dv/dt=5\text{V}/\mu\text{s}$; $di/dt=30\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions				Value	Unit
V _{TM}	I _T = 110A; t _p = 380μs			MAX.	1.8	V
I _{DRM} / I _{RRM}	V _{DRM} / V _{RRM}	T _J = 25°C	400 – 600V	MAX.	10	μA
			800 V		20	
			1000 V		30	
		T _J = 100°C	400 – 600V		1000	
			800V		1500	
			1000V		5000	
		T _J = 125°C	400 – 600V		2000	
			800V		3000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx55R	0.5	$^\circ\text{C}/\text{W}$
		Sxx55N		
		Sxx55W Sxx55M	0.53	
$R_{\theta(J-A)}$	Junction to ambient	Sxx55R	40	$^\circ\text{C}/\text{W}$

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

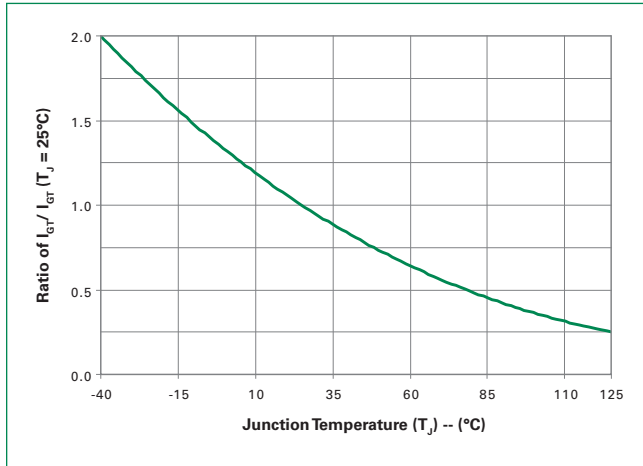


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

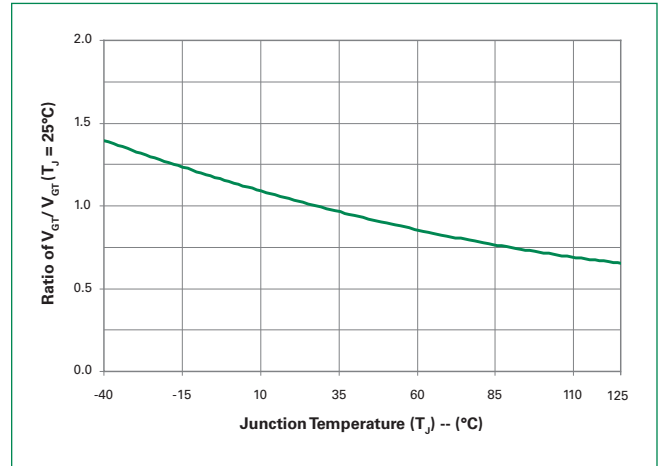


Figure 3: Normalized DC Holding Current vs. Junction Temperature

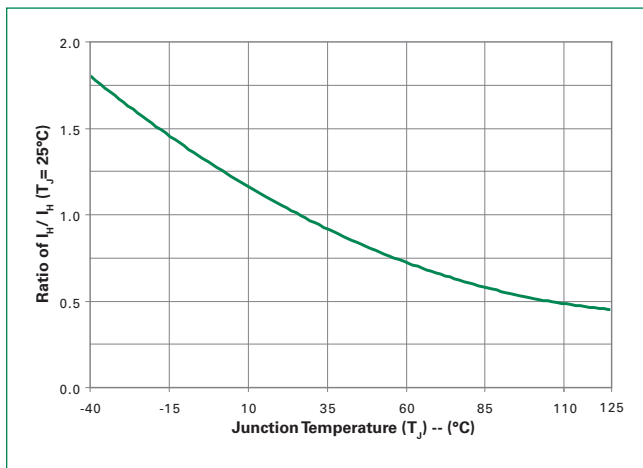


Figure 4: On-State Current vs. On-State Voltage (Typical)

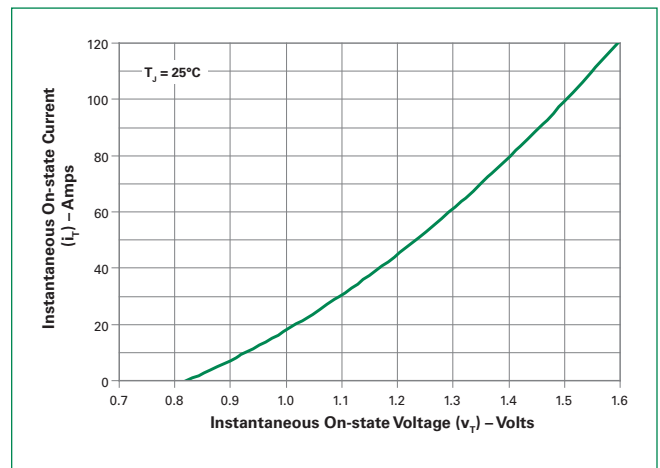


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

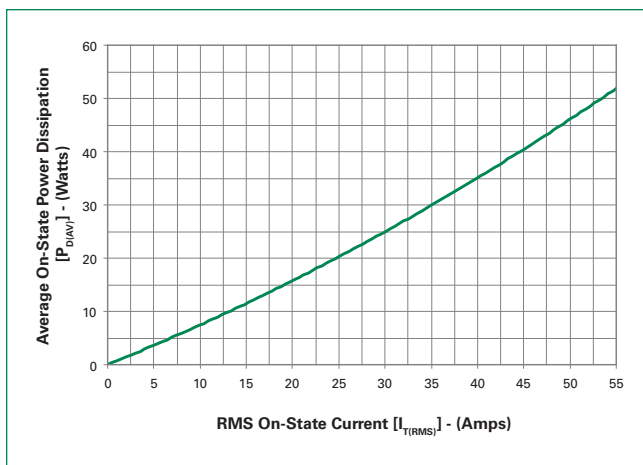
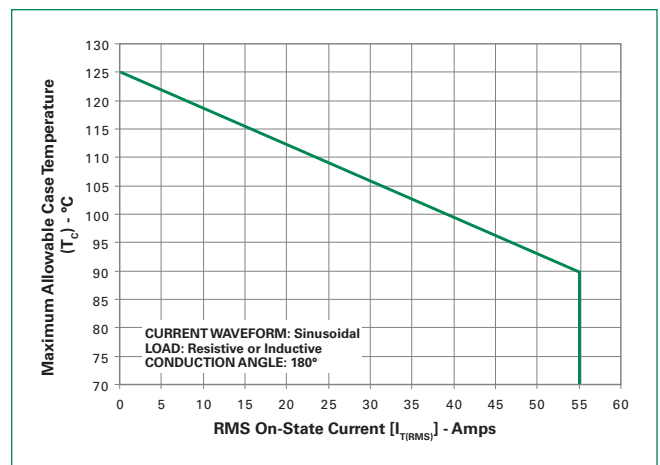


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current



Note: xx = voltage

Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

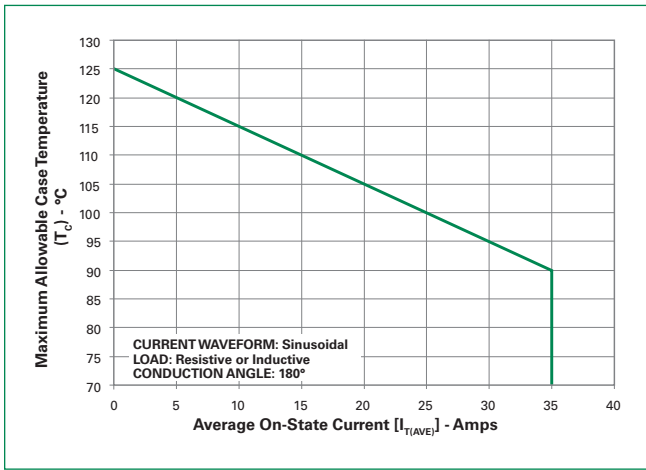


Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current

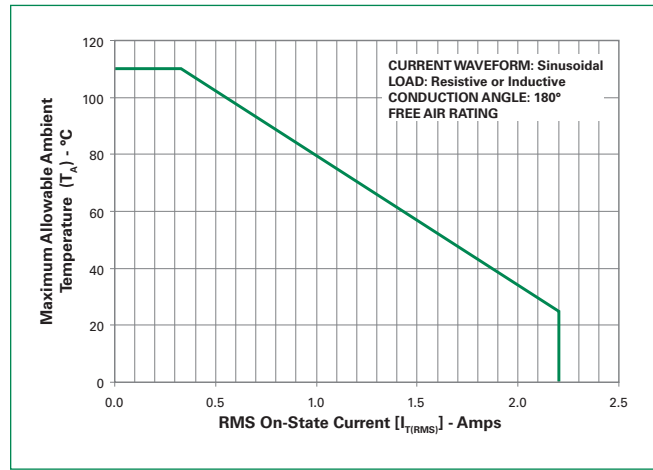


Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current

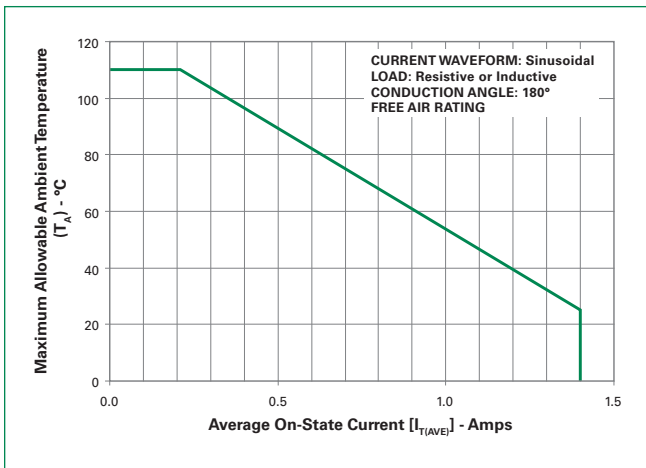


Figure 10: Peak Capacitor Discharge Current

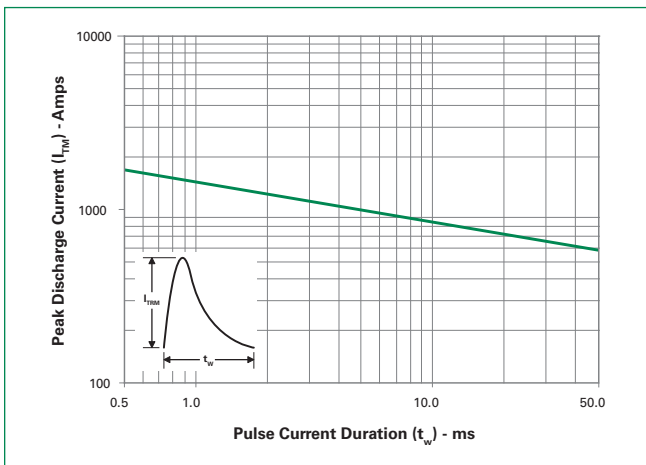
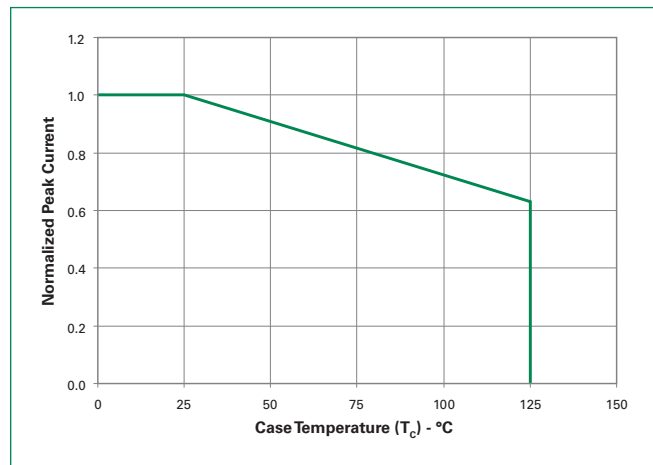
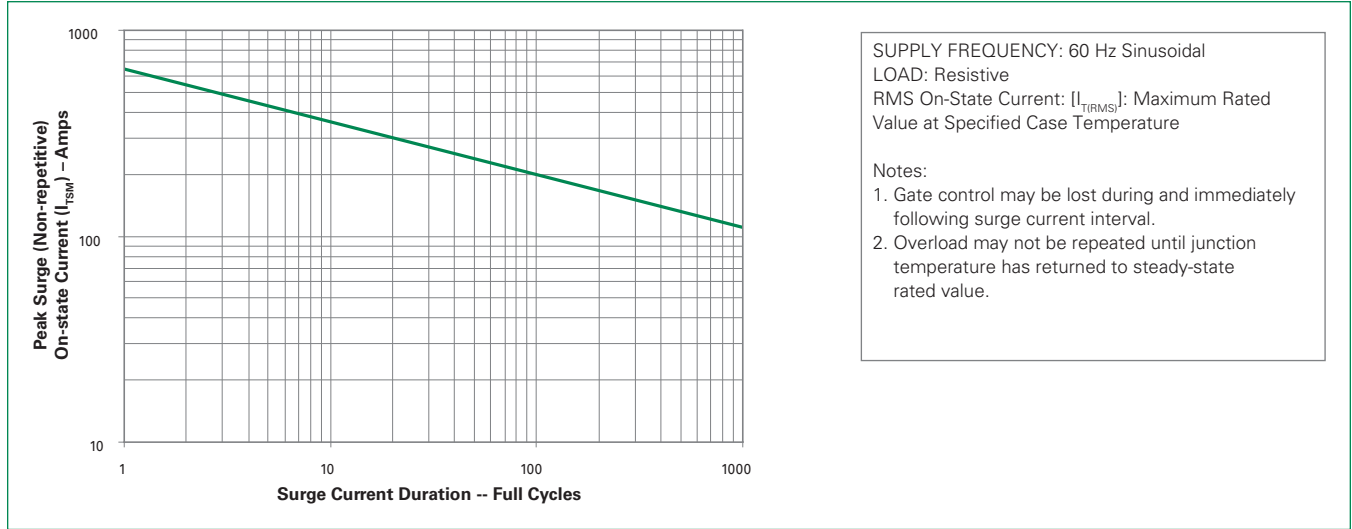


Figure 11: Peak Capacitor Discharge Current Derating



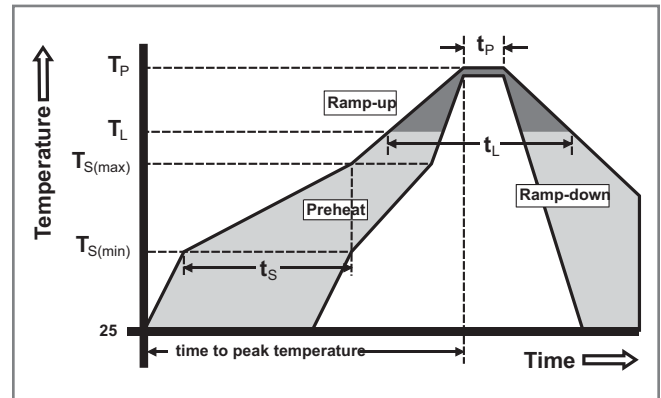
Note: xx = voltage

Figure 12: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

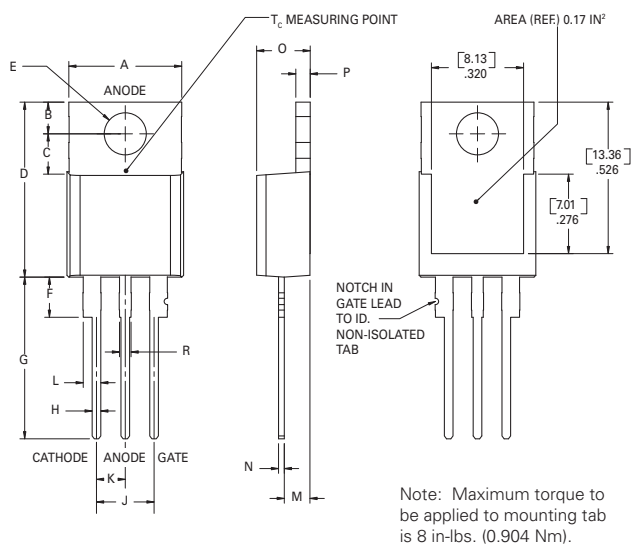
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

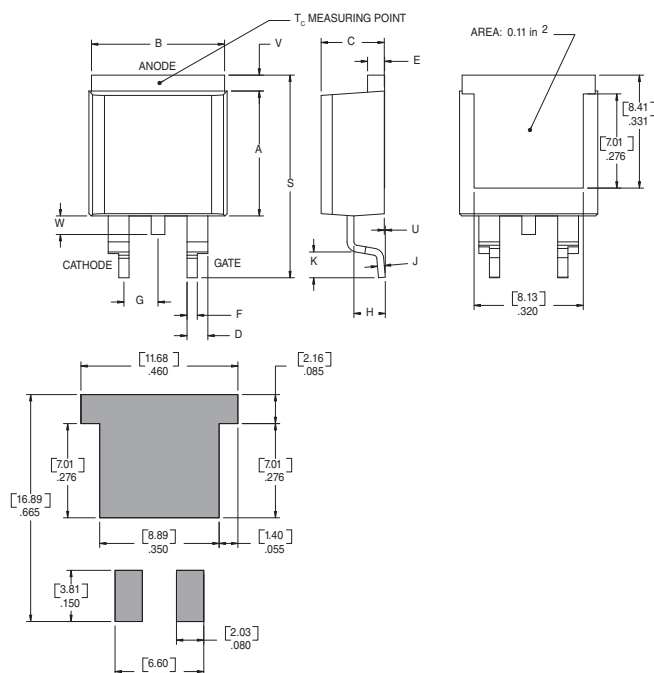
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwelltime at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



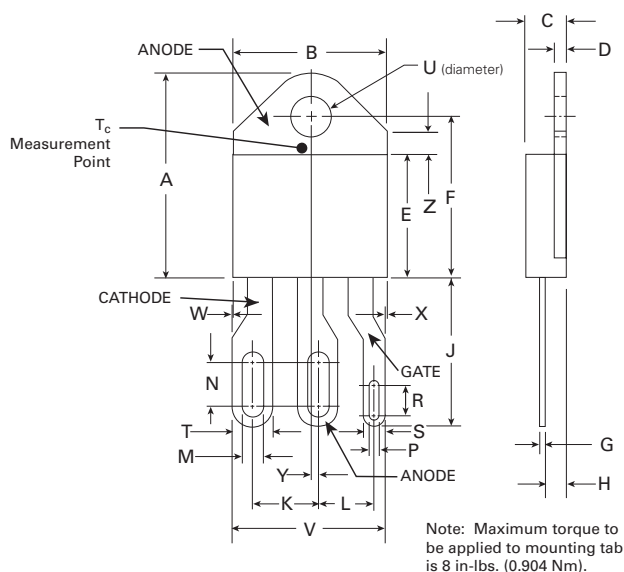
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions – TO-263AA (N-package) — D²-Pak Surface Mount



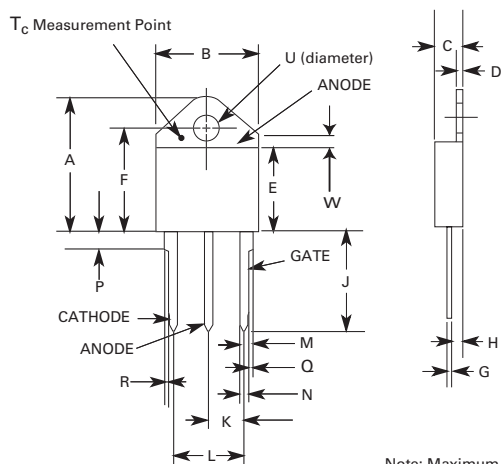
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.63	0.89
E	0.048	0.055	1.22	1.40
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.083	0.093	2.11	2.36
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.87
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Dimensions – TO-218X (W Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Dimensions – TO-218AC (M Package) — Non-isolated Mounting Tab Common with Center Lead



Note: Maximum torque to be applied to mounting tab is 8 in.-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.164	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx55R	X	X	X	X	40mA	Standard SCR	TO-220R
Sxx55N	X	X	X	X	40mA	Standard SCR	TO-263
Sxx55W	X	X	X		40mA	Standard SCR	TO-218X
Sxx55M	X	X	X	X	40mA	Standard SCR	TO-218AC

Note: xx = Voltage

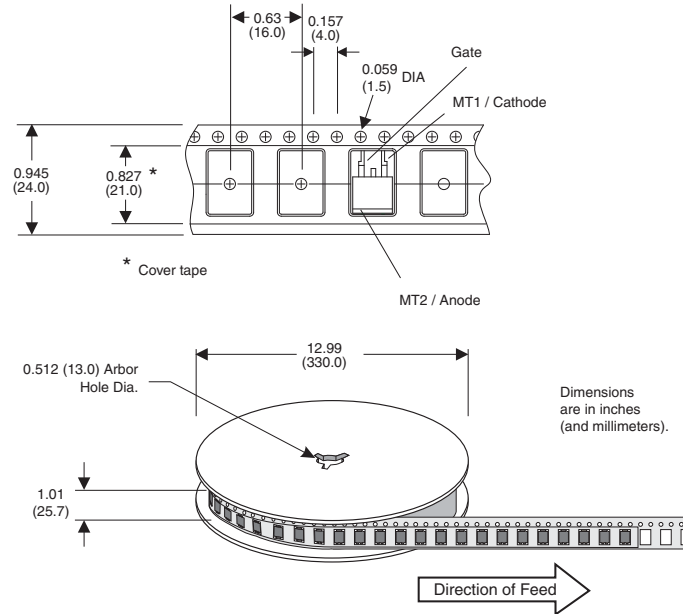
Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx55R	Sxx55R	2.2g	Bulk	500
Sxx55RTP	Sxx55R	2.2g	Tube	500
Sxx55NTP	Sxx55N	1.6g	Tube	500
Sxx55NRP	Sxx55N	1.6g	Embossed Carrier	500
Sxx55W	Sxx55W	5.23g	Bulk	250
Sxx55WTP	Sxx55W	5.23g	Tube	500
Sxx40M	Sxx40M	4.40g	Bulk	250
Sxx55MTP	Sxx55M	4.40g	Tube	500

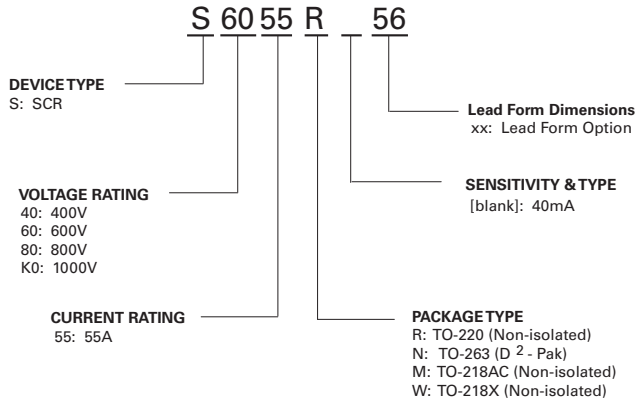
Note: xx = Voltage

TO-263 Embossed Carrier Reel Pack (RP) Specification

Meets all EIA-481-2 Standards

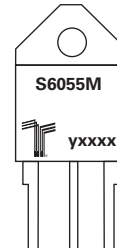


Part Numbering System

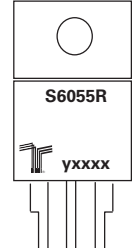


Part Marking System

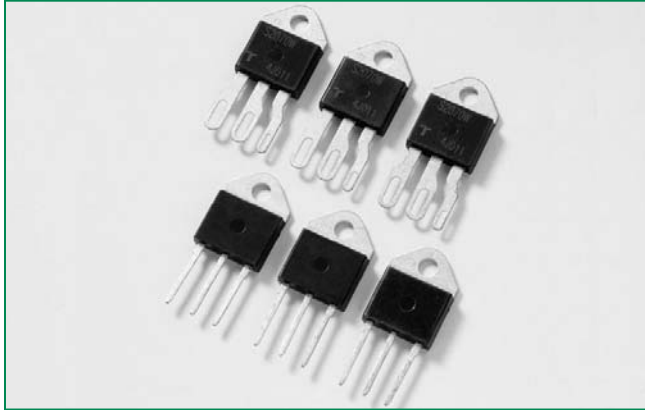
TO-218AC - (M Package)
TO-218X - (W Package)



TO-220 AB (R Package)
TO-263 (N Package)



RoHS **Sxx65x & Sxx70x Series**



Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls. Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

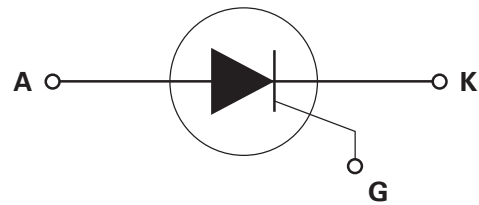
- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 950 A

Applications


Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Agency Approval

Agency	Agency File Number
	J & K Packages: E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	65 & 70	A
V_{DRM}/V_{RRM}	400 to 1000	V
I_{GT}	50	mA

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx65J Sxx65K $T_C = 75^\circ\text{C}$	65	A
		Sxx70W $T_C = 80^\circ\text{C}$	70	
I_{TSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_J (\text{initial}) = 25^\circ\text{C}$	800	A
		single half cycle; $f = 60\text{Hz}$; $T_J (\text{initial}) = 25^\circ\text{C}$	950	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	3745	A^2s
di/dt	Critical rate of rise of on-state current	$f = 60\text{Hz}$; $T_J = 125^\circ\text{C}$	200	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$T_J = 125^\circ\text{C}$ $P_w = \mu\text{S}$	5.0	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$	1.0	W
T_{stg}	Storage temperature range		-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			Value	Unit
I_{GT}	$V_D = 12\text{V}; R_L = 60\ \Omega$		MAX.	50	mA
			MIN.	5	
V_{GT}			MAX.	2.0	V
dv/dt	$V_D = V_{DRM}; \text{gate open}; T_J = 100^\circ\text{C}$	400V	MIN.	650	V/ μs
		600V		600	
		800V		500	
		1000V		250	
	$V_D = V_{DRM}; \text{gate open}; T_J = 125^\circ\text{C}$	400V		550	
		600V		500	
		800V		475	
V_{GD}	$V_D = V_{DRM}; R_L = 3.3\ \text{k}\Omega; T_J = 125^\circ\text{C}$		MIN.	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)		MAX.	80	mA
t_q	(1)		MAX.	35	μs
t_{gt}	$I_G = 2 \times I_{GT}; \text{PW} = 15\mu\text{s}; I_T = 140\text{A}$		TYP.	2.5	μs

Note :

(1) $I_T = 2\text{A}; t_p = 50\mu\text{s}; dv/dt = 5\text{V}/\mu\text{s}; di/dt = 30\text{A}/\mu\text{s}$

Static Characteristics

Symbol	Test Conditions			Value	Unit	
V _{TM}	65A Device I _T = 130A; t _p = 380μs			MAX.	1.8	V
	70A Device I _T = 140A; t _p = 380μs					
I _{DRM} / I _{RRM}	V _{DRM} / V _{RRM}	T _J = 25°C	400 – 800V	MAX.	20	μA
			1000 V		30	
		T _J = 100°C	400 – 600V		1500	
			800V		2000	
			1000V		5000	
		T _J = 125°C	400V – 600V		3000	
			800V		5000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx65J Sxx65K	0.86	$^\circ\text{C}/\text{W}$
		Sxx70W	0.6	

Note: xx = voltage

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

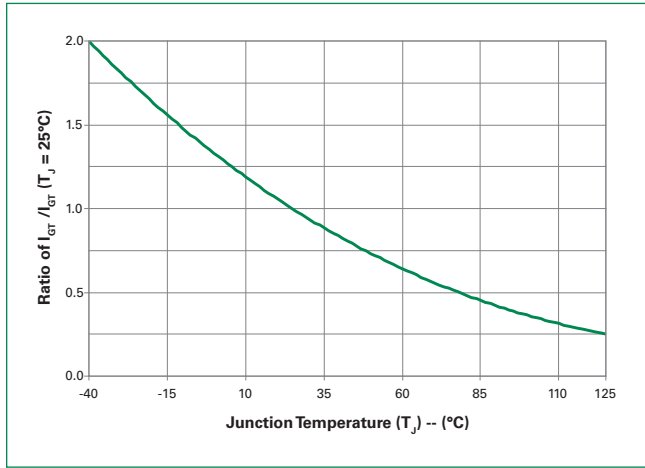


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

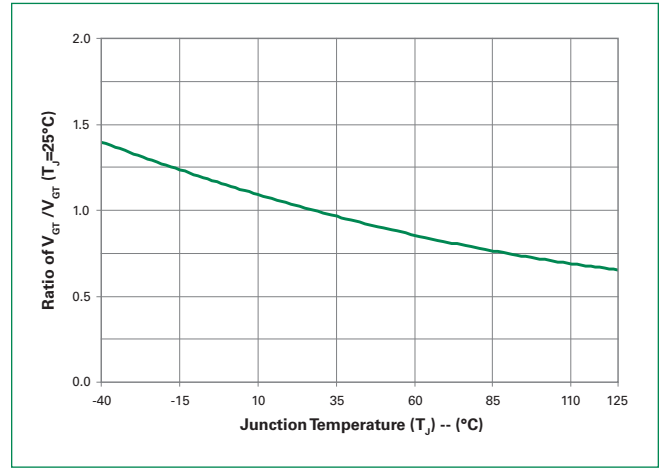


Figure 3: Normalized DC Holding Current vs. Junction Temperature

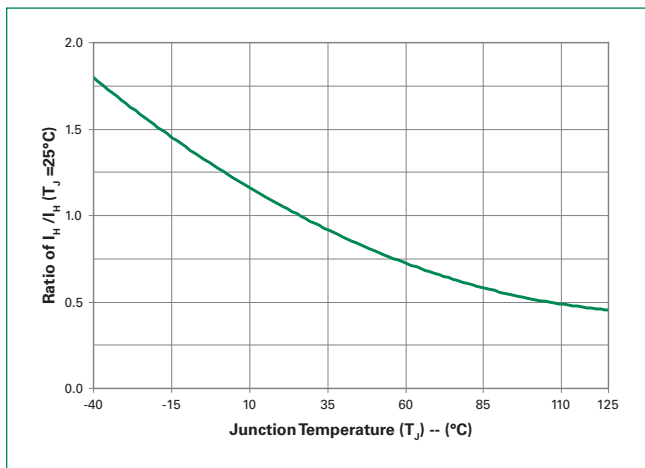


Figure 4: On-State Current vs. On-State Voltage (Typical)

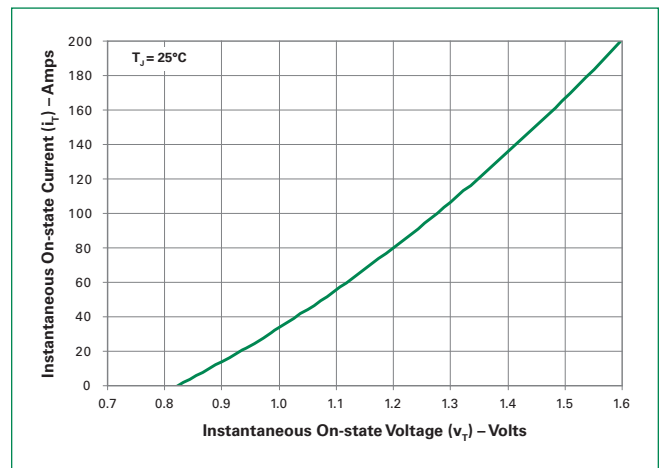


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

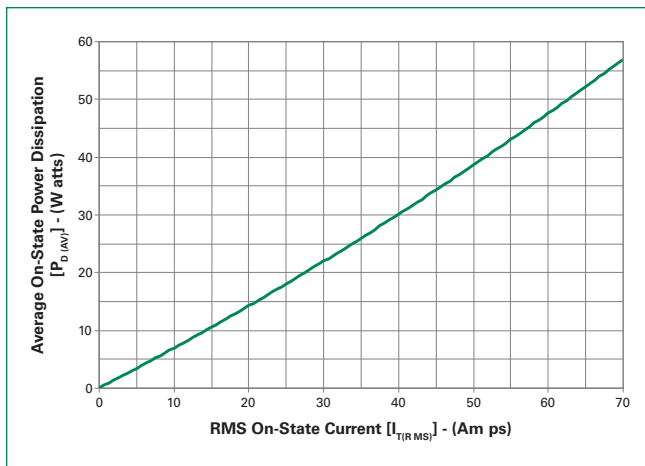
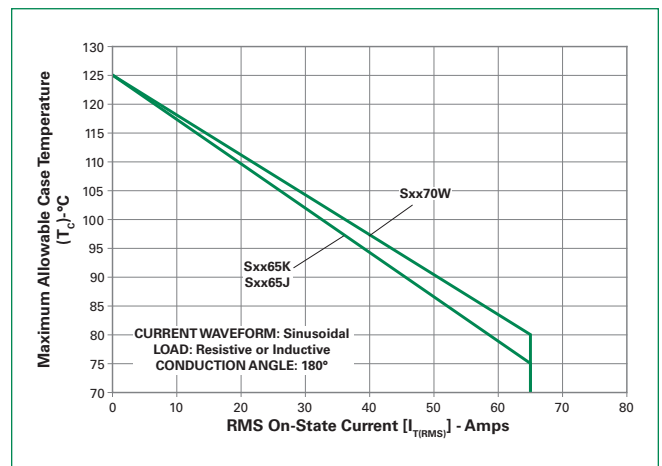


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current



Note: xx = voltage

Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

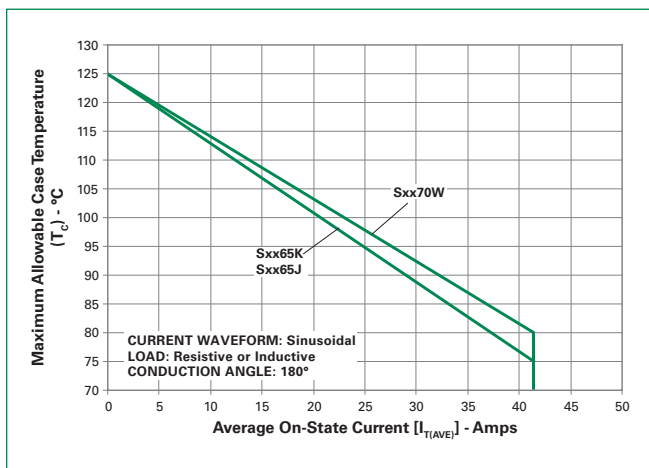


Figure 8: Peak Capacitor Discharge Current

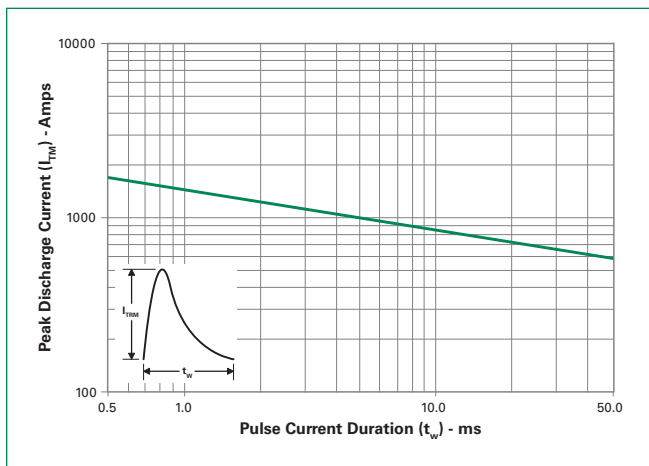


Figure 9: Peak Capacitor Discharge Current Derating

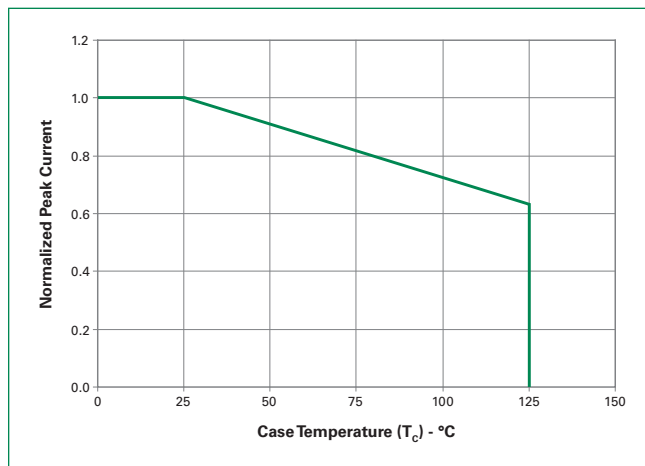
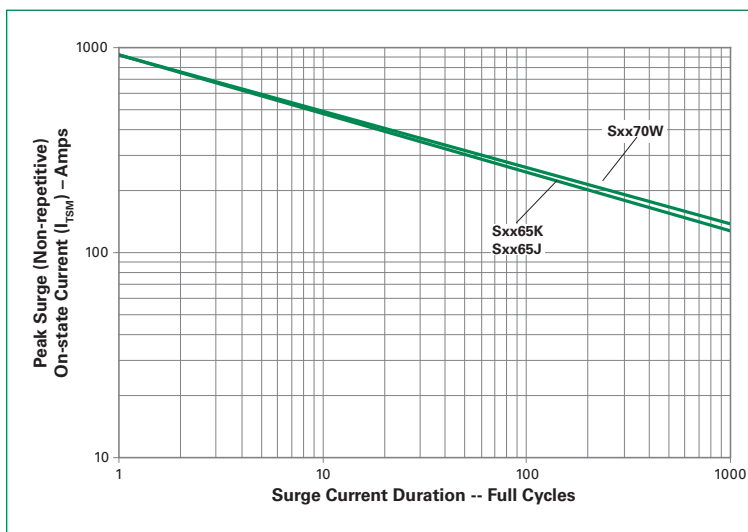


Figure 10: Surge Peak On-State Current vs. Number of Cycles



SUPPLY FREQUENCY: 60 Hz Sinusoidal
LOAD: Resistive
RMS On-State Current: [$I_{T(RMS)}$]: Maximum Rated Value at Specified Case Temperature

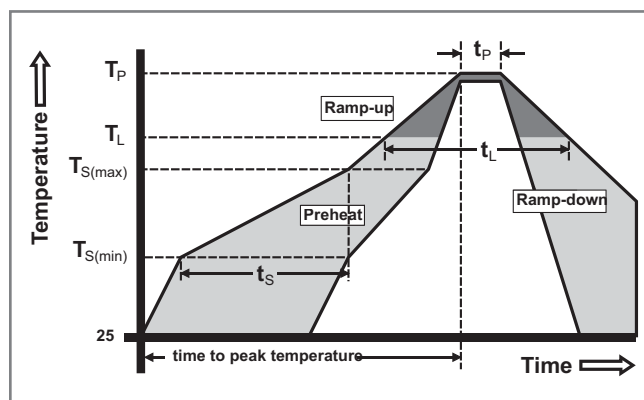
Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Note: xx = Voltage

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

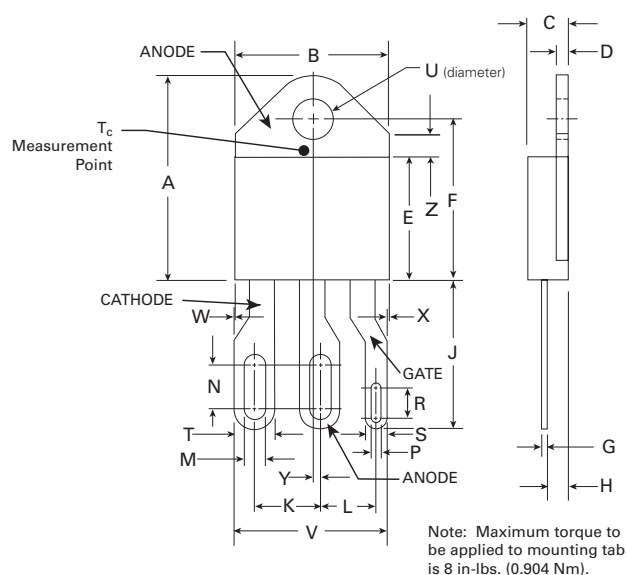
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

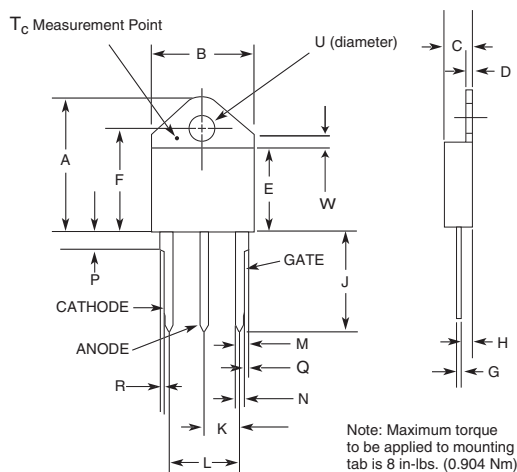
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC; 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwelltime at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions – TO-218X (W Package) — Non-Isolated Mounting Tab



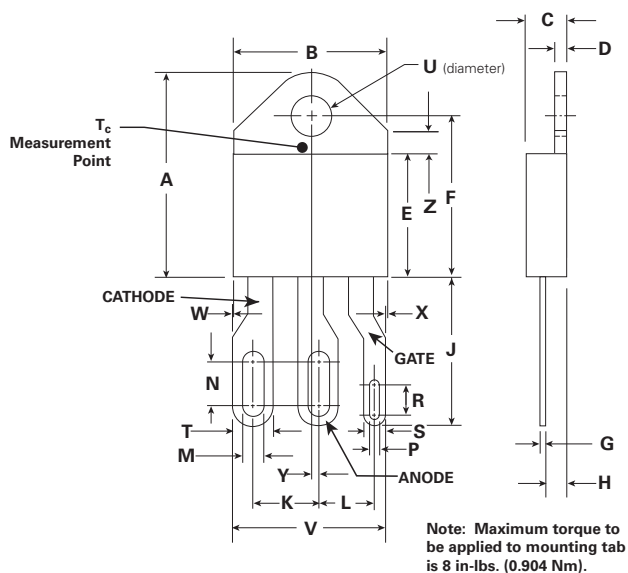
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Dimensions – TO-218AC (K Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.164	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

Dimensions – TO-218X (J Package) — Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx65K	X	X	X	X	50mA	Standard SCR	TO-218AC
Sxx65J	X	X	X		50mA	Standard SCR	TO-218X
Sxx70W	X	X	X		50mA	Standard SCR	TO-218X

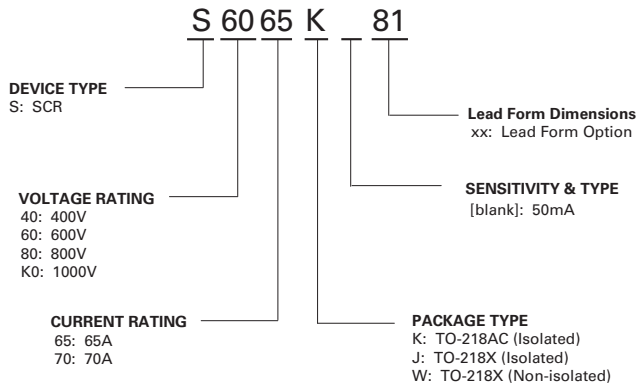
Note: xx = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx65K	Sxx65K	4.40g	Bulk	250
Sxx65KTP	Sxx65K	4.40g	Tube	500
Sxx65J	Sxx65J	5.23g	Bulk	250
Sxx65JTP	Sxx65J	5.23g	Tube	500
Sxx70W	Sxx70W	5.23g	Bulk	250
Sxx70WTP	Sxx70W	5.23g	Tube	500

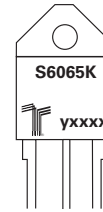
Note: xx = Voltage

Part Numbering System



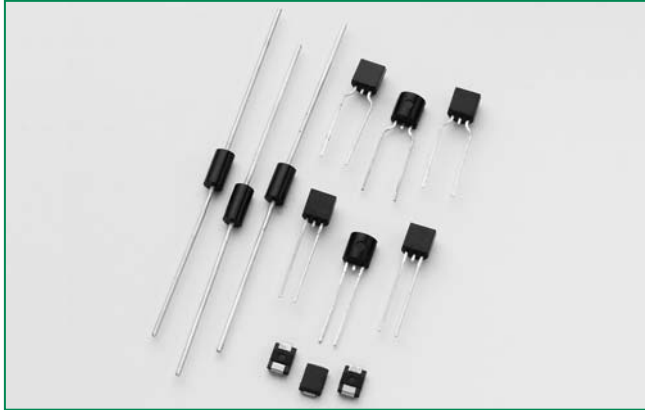
Part Marking System

TO-218AC - (K Package)
TO-218X - (J Package)
TO-218X - (W Package)

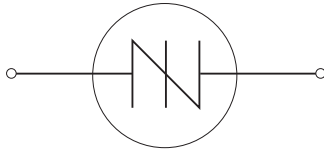


RoHS

Kxxxzy SIDAC



Schematic Symbol



Description

The SIDAC is a silicon bilateral voltage triggered switch. Upon application of a voltage exceeding the SIDAC breakover voltage point, the SIDAC switches on through a negative resistance region to a low on-state voltage. Conduction continues until the current is interrupted or drops below the minimum holding current of the device.

SIDACs feature glass-passivated junctions to ensure a rugged and dependable device capable of withstanding harsh environments.

Features

- AC Circuit Oriented
- RoHS Compliant
- Triggering Voltage of 79V to 330V

Applications

Suitable for high voltage power supplies, natural gas igniters, high-pressure Sodium lamps, and Xenon flash ignition.

Electrical Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Max	Unit
V_{BO}	Breakover/Trigger Voltage	K0900y	79	97	V
		K1050y	95	113	
		K1100y	104	118	
		K1200y	110	125	
		K1300y	120	138	
		K1400y	130	146	
		K1500y	140	170	
		K200zy	190	215	
		K220zy	205	230	
		K240zy	220	250	
		K250zy	240	280	
		K300zy	270	330	
V_{DRM}	Repetitive Peak Off-state Voltage	K0900y	70		V
		K1050y	90		
		K1100y	90		
		K1200y	90		
		K1300y	90		
		K1400y	90		
		K1500y	90		
		K200zy	180		
		K220zy	180		
		K240zy	190		
		K250zy	200		
		K300zy	200		

Note: xxx = voltage, z = circuit function, y = package

Electrical Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Max	Unit
$I_{T(RMS)}$	On-state RMS Current	50/60Hz, $T_J < 125^\circ\text{C}$		1	A
I_{DRM}	Repetitive Peak Off-state Current	$V = V_{DRM}$ 50/60Hz Sine Wave		5	μA
V_{TM}	Peak On-state Voltage	$I_T = 1\text{A}$ Kxxx0y Kxxx2y		1.5 3.0	V
I_H	Dynamic Holding Current	$R_L = 100\Omega$ 50/60Hz Sine Wave		150	mA
R_S	Switching Resistance, $R_S = \frac{(V_{BO} - V_S)}{(I_S - I_{BO})}$	50/60Hz Sine Wave		100	Ω
I_{BO}	Breakover Current	50/60Hz Sine Wave		10	μA
I_{TRM}	Peak Repetitive Pulse Current (refer to figure 4)	$t_p = 10\mu\text{s}$ 60Hz 5Hz		80 160	A
I_{TSM}	Peak Non-repetitive Surge Current (refer to figure 5)	Single Cycle 60Hz 50Hz		20 16.7	A
di/dt	Critical Rate of Rise of On-state Current			150	A/ μs
dv/dt	Critical Rate of Rise of Off-state Voltage		1500		V/ μs
T_S	Storage Temperature Range		-40	150	$^\circ\text{C}$
T_J	Junction Temperature Range		-40	125	$^\circ\text{C}$
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	DO-15 DO-214 (1)		18 30	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	TO-92		35	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	DO-15 TO-92		75 95	$^\circ\text{C/W}$

Notes: xxx = voltage, z = circuit function, y = package

(1) Mounted on 1 cm² copper foil surface; two-ounce copper foil

Figure 1: V-I Characteristics

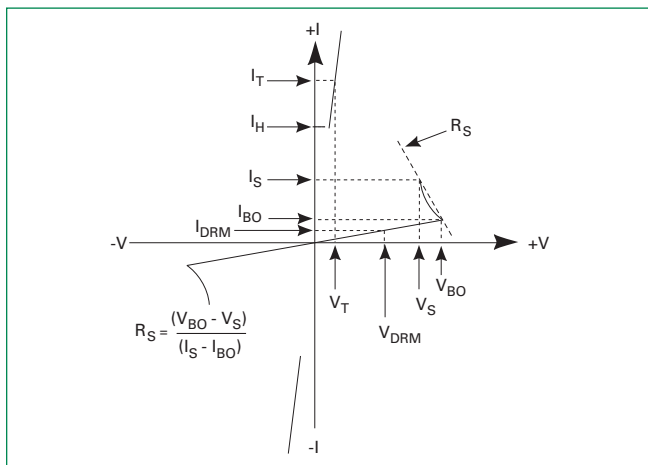


Figure 2: On-state Current vs. On-state Voltage (Typical)

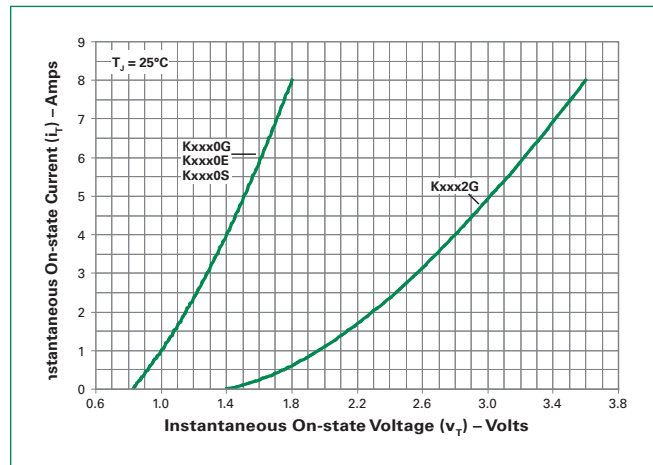


Figure 3: Power Dissipation vs. On-state Current (Typical)

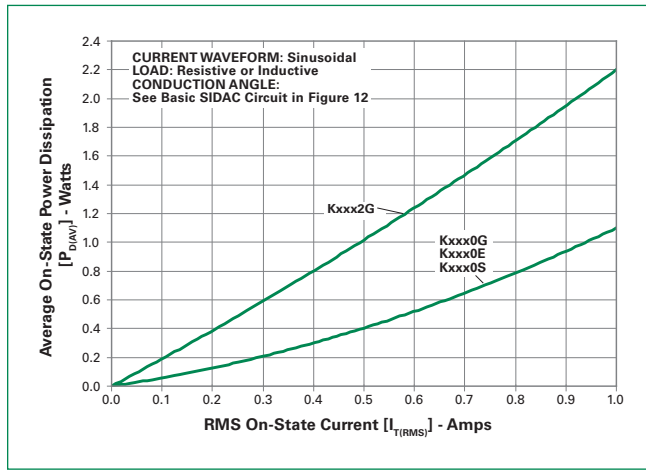


Figure 4: Repetitive Peak On-state Current (I_{TRM}) vs. Pulse Width at Various Frequencies

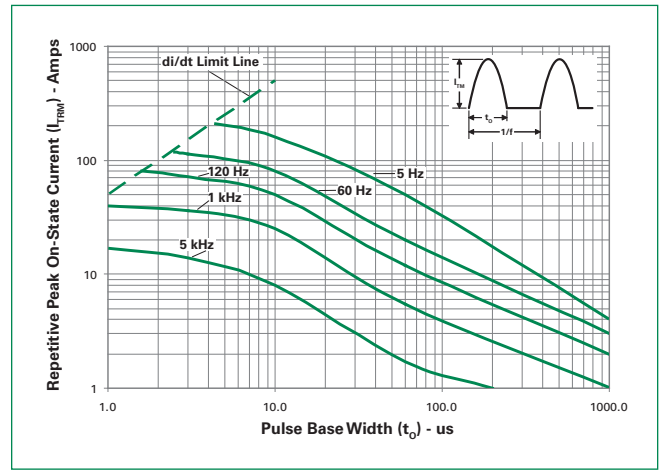


Figure 5: Peak Non-repetitive Surge Current (I_{TSM}) vs. Number of Cycles

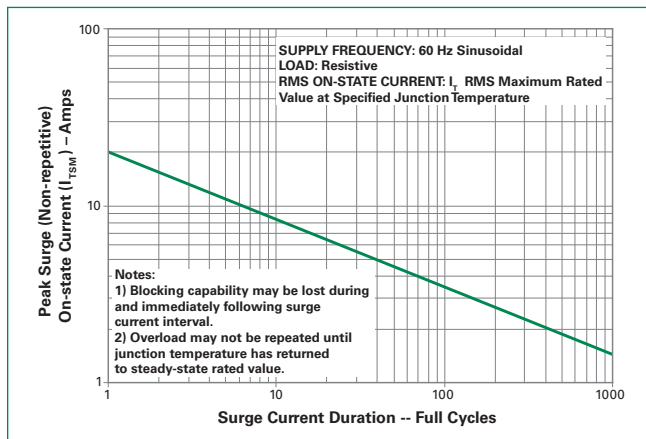


Figure 6: Normalized V_{BO} Change vs. Junction Temperature

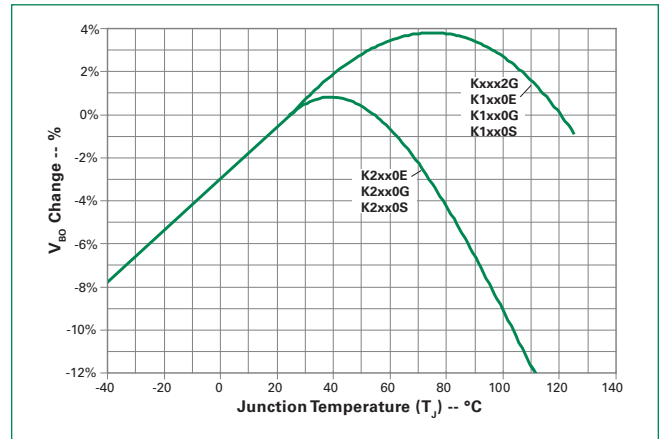


Figure 7: Normalized DC Holding Current vs. Junction Temperature

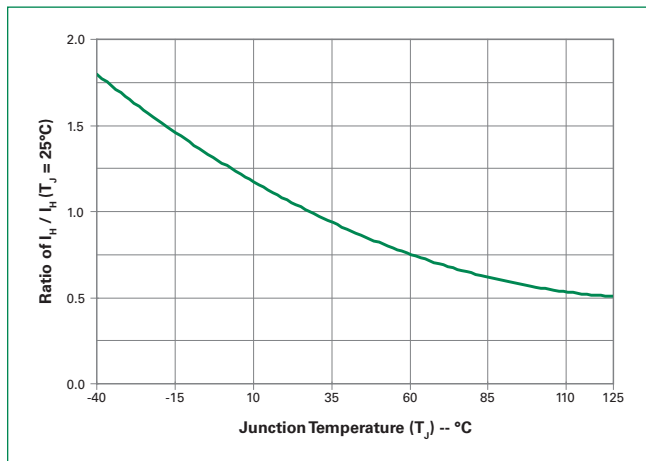


Figure 8: Maximum Allowable Case Temperature vs. RMS On-state Current

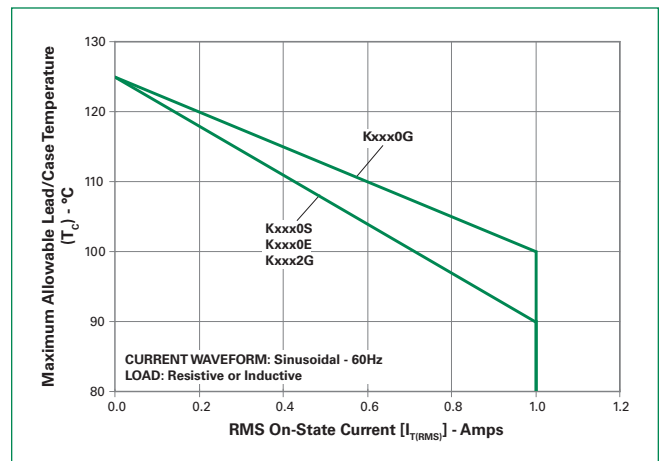


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

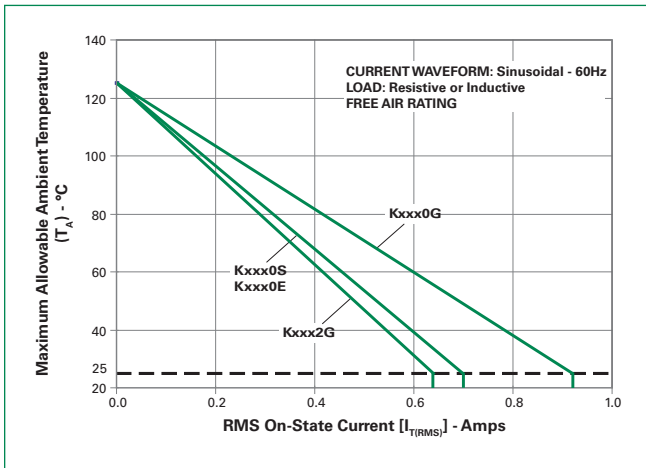


Figure 10: Normalized Repetitive Peak Breakover Current (I_{BO}) vs. Junction Temperature

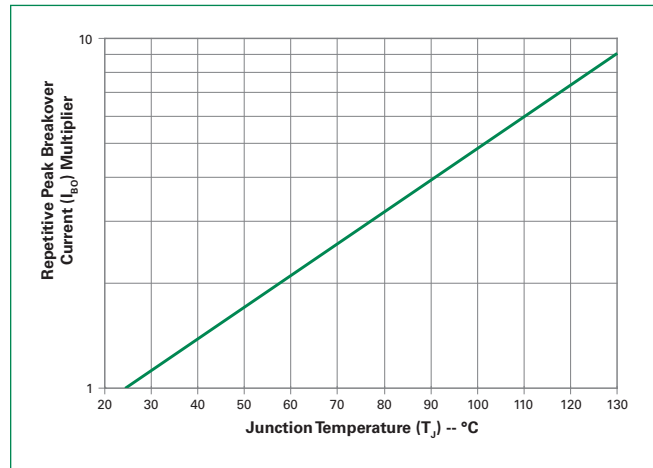


Figure 11: Dynamic Holding Current Test Circuit for SIDACs

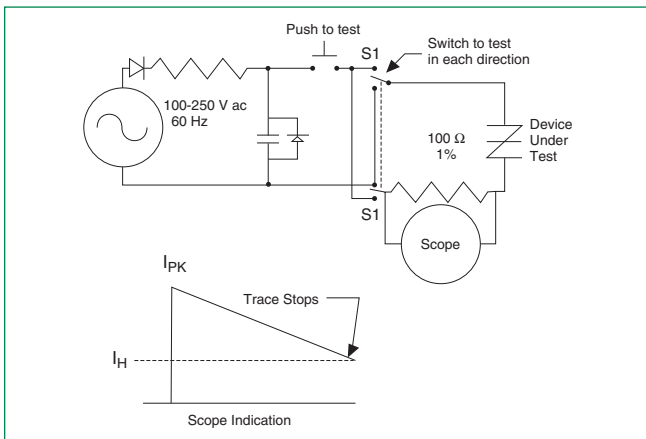


Figure 12: Basic SIDAC Circuit

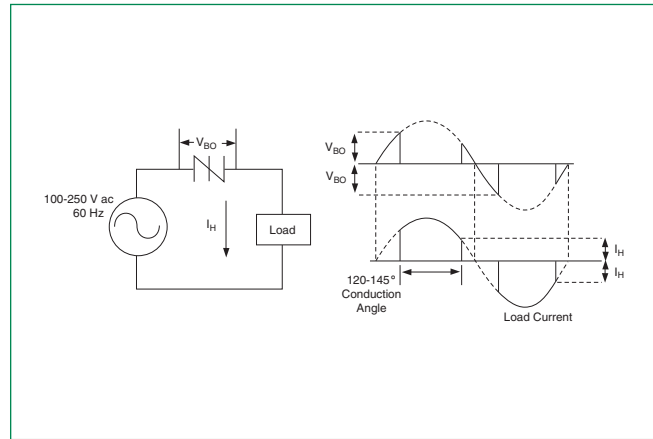


Figure 13: Relaxation Oscillator Using a SIDAC

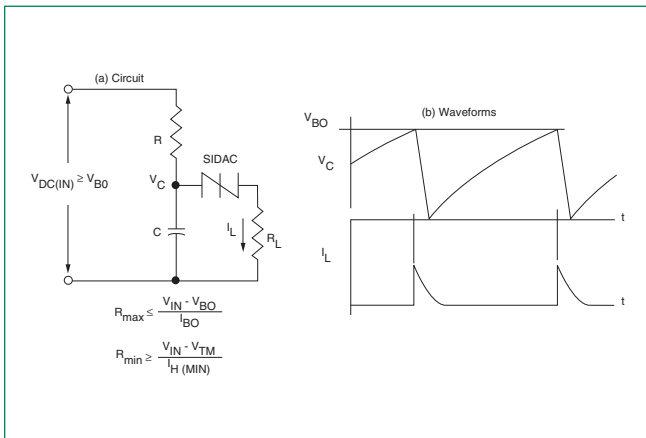


Figure 14: Low-voltage Input Circuit for Gas Ignition

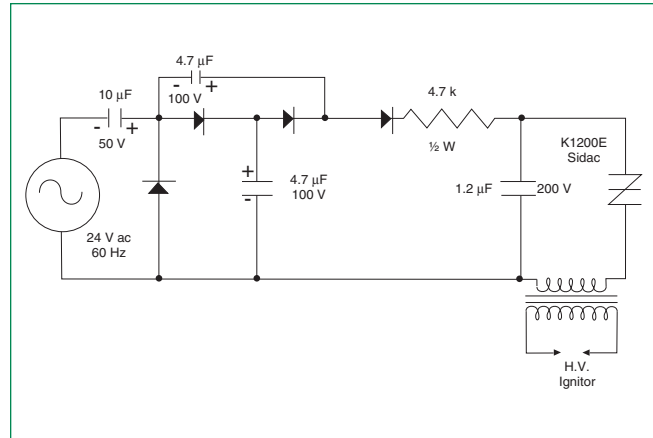


Figure 15: Comparison of SIDAC versus SCR for Gas Ignitor Circuit

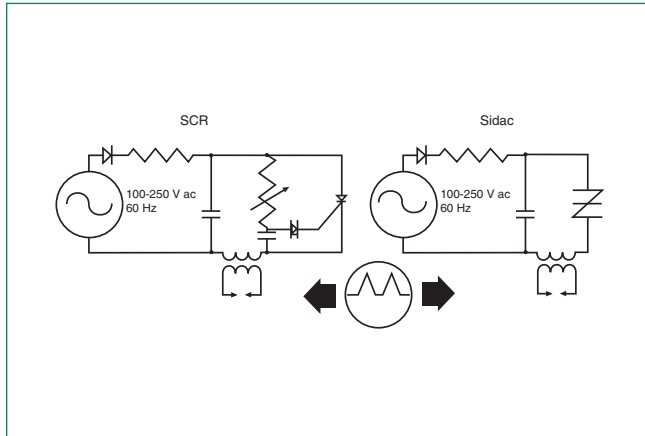


Figure 16: Xenon Lamp Flashing Circuit

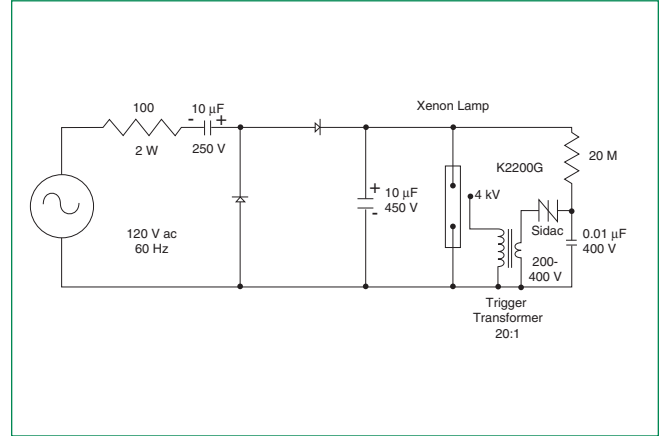
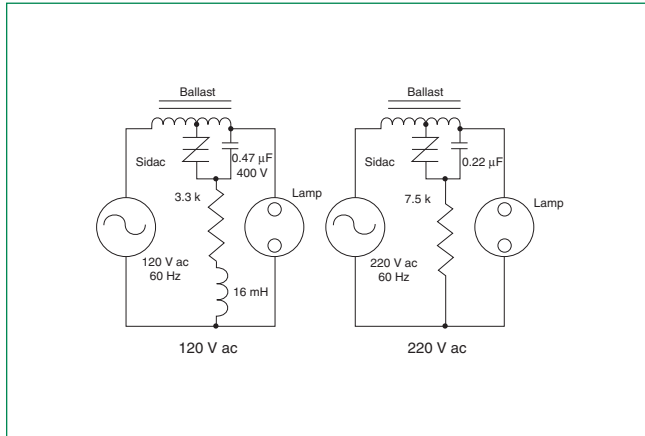
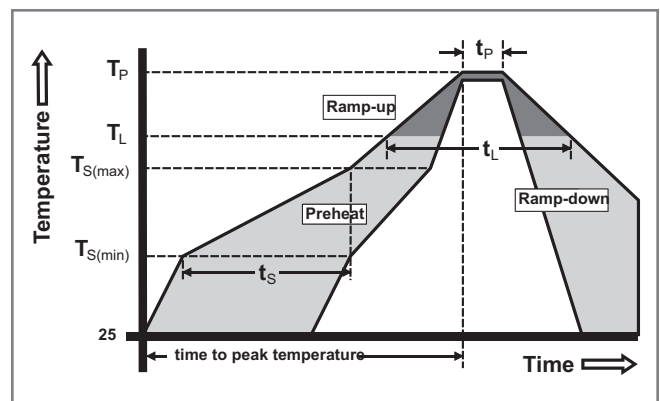


Figure 17: Typical High-pressure Sodium Lamp Firing Circuit



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_P)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin Plated / Pb-free Solder Dipped
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

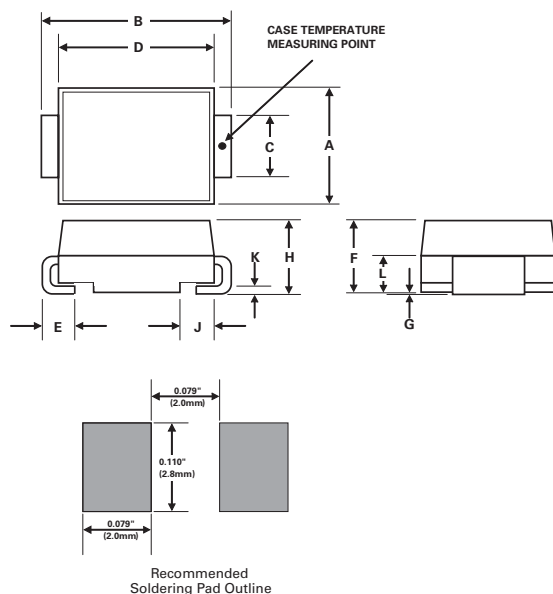
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Overheating and surge currents are the main killers of SIDACs. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Reliability/Environmental Tests

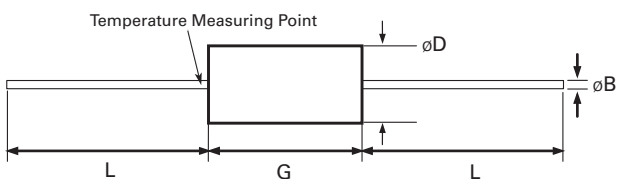
Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{DRM} (VAC-peak), 125°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
Biased Temperature & Humidity	EIA/JEDEC: JESD22-A101 80% min V_{BO} (V_{DC}), 85°C, 85%RH, 1008 hours
High Temp Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	-40°C, 1008 hours
Thermal Shock	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002: Category 3
Lead Bend	MIL-STD-750: Method 2036, Condition E

Dimensions — DO-214



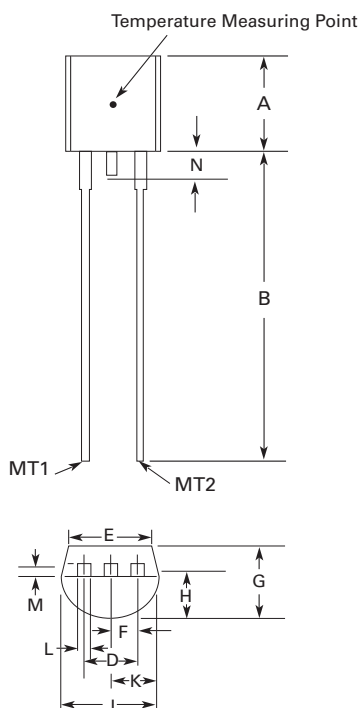
Dimension	Inches		Millimeters	
	Max	Max	Min	Max
A	0.140	0.155	3.56	3.94
B	0.205	0.220	5.21	5.59
C	0.077	0.083	1.96	2.11
D	0.166	0.180	4.22	4.57
E	0.036	0.063	0.91	1.60
F	0.066	0.083	1.67	2.11
G	0.004	0.008	0.10	0.20
H	0.077	0.086	1.95	2.18
J	0.043	0.053	1.09	1.35
K	0.008	0.012	0.20	0.30
L	0.039	0.049	0.99	1.24

Dimensions — DO-15



Dimension	Inches		Millimeters	
	Max	Max	Min	Max
øB	0.028	0.034	0.711	0.864
øD	0.120	0.140	3.048	3.556
G	0.235	0.270	5.969	6.858
L	1.000		25.400	

Dimensions — TO-92 with Type 70 Lead Form



Dimension	Inches		Millimeters	
	Max	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500		12.70	
D	0.095	0.105	2.41	2.67
E	0.150		3.81	
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43
N		0.060		1.52

Notes:

1. Type 70 lead form as shown is standard for the E package.
2. All leads are insulated from case. Case is electrically nonconductive (rated at 16000V ac rms for one minute from leads to case over the operating temperature range.)
3. Mold flash shall not exceed 0.13 mm per side.

Product Selector

Part Number	Switching Voltage Range		Blocking Voltage	Packages		
	V _{BO} Minimum	V _{BO} Maximum	V _{DRM}	DO-15	DO-214	TO-92
K0900y	79V	97V	70V	K0900G	K0900S	K0900E70
K1050y	95V	113V	90V	K1050G	K1050S	K1050E70
K1100y	104V	118V	90V	K1100G	K1100S	K1100E70
K1200y	110V	125V	90V	K1200G	K1200S	K1200E70
K1300y	120V	138V	90V	K1300G	K1300S	K1300E70
K1400y	130V	146V	90V	K1400G	K1400S	K1400E70
K1500y	140V	170V	90V	K1500G	K1500S	K1500E70
K2000y	190V	215V	180V	K2000G	K2000S	K2000E70
K2002y	190V	215V	180V	K2002G		
K2200y	205V	230V	180V	K2200G	K2200S	K2200E70
K2202y	205V	230V	180V	K2202G		
K2400y	220V	250V	190V	K2400G	K2400S	K2400E70
K2402y	220V	250V	190V	K2402G		
K2500y	240V	280V	200V	K2500G	K2500S	K2500E70
K2502y	240V	280V	200V	K2502G		
K3002y	270V	330V	200V	K3002G		

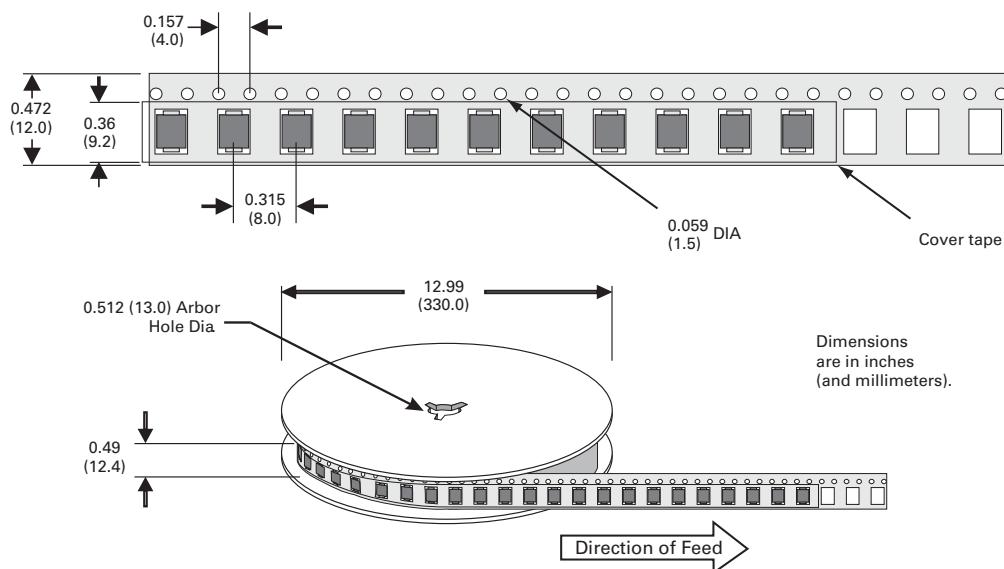
Note: y = package

Packing Options

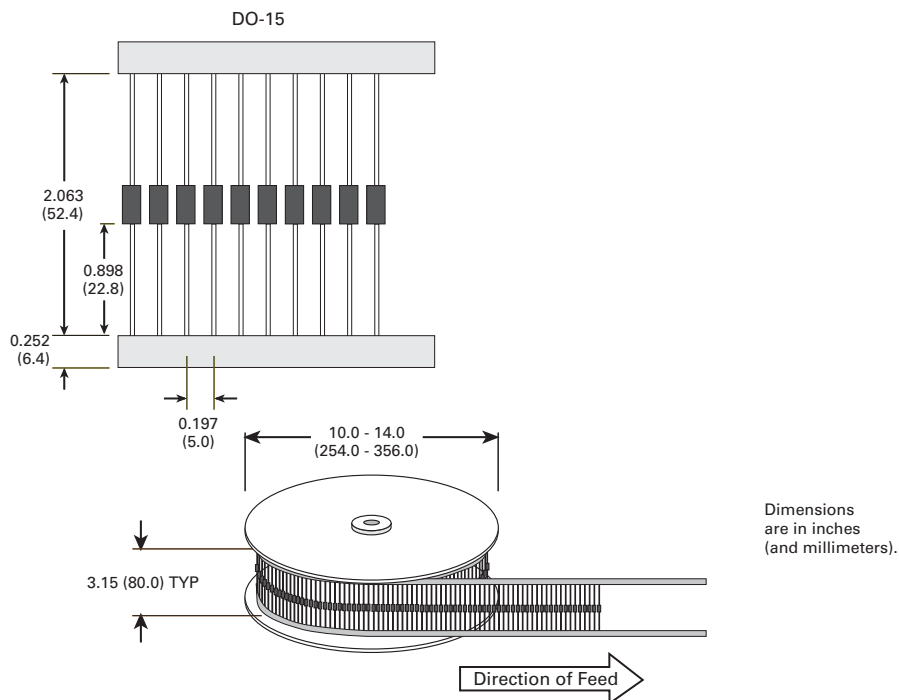
Part Number	Marking	Weight	Packaging Mode	Base Quantity
Kxxx0G	Kxxx0G	0.38g	Bulk	1000
Kxxx0GRP	Kxxx0G	0.38g	Reel Pack	5000
Kxxx2G	Kxxx2G	0.38g	Bulk	1000
Kxxx2GRP	Kxxx2G	0.38g	Reel Pack	5000
Kxxx0SRP	KxxS	0.1g	Reel Pack	2500
Kxxx0E70	Kxxx0E	0.17g	Bulk	2000
Kxxx0E70AP	Kxxx0E	0.17g	Ammo Pack	2000
Kxxx0E70RP2	Kxxx0E	0.17g	Reel Pack	2000
Kxxx0E70RP3	Kxxx0E	0.17g	Reel Pack	2000

Note: xxx or xx = voltage

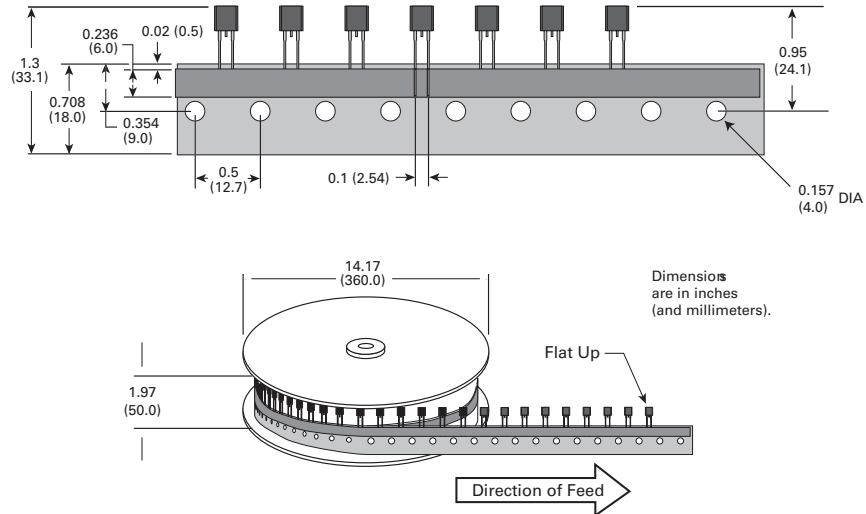
DO-214 Embossed Carrier Reel Pack (RP) Specifications



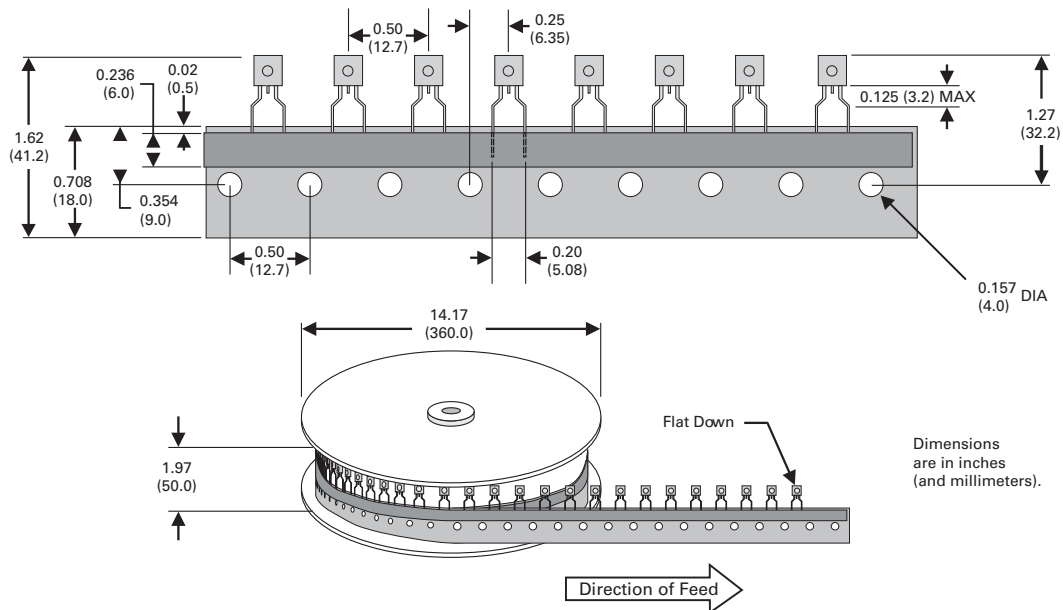
DO-15 Reel Pack (RP) Specifications



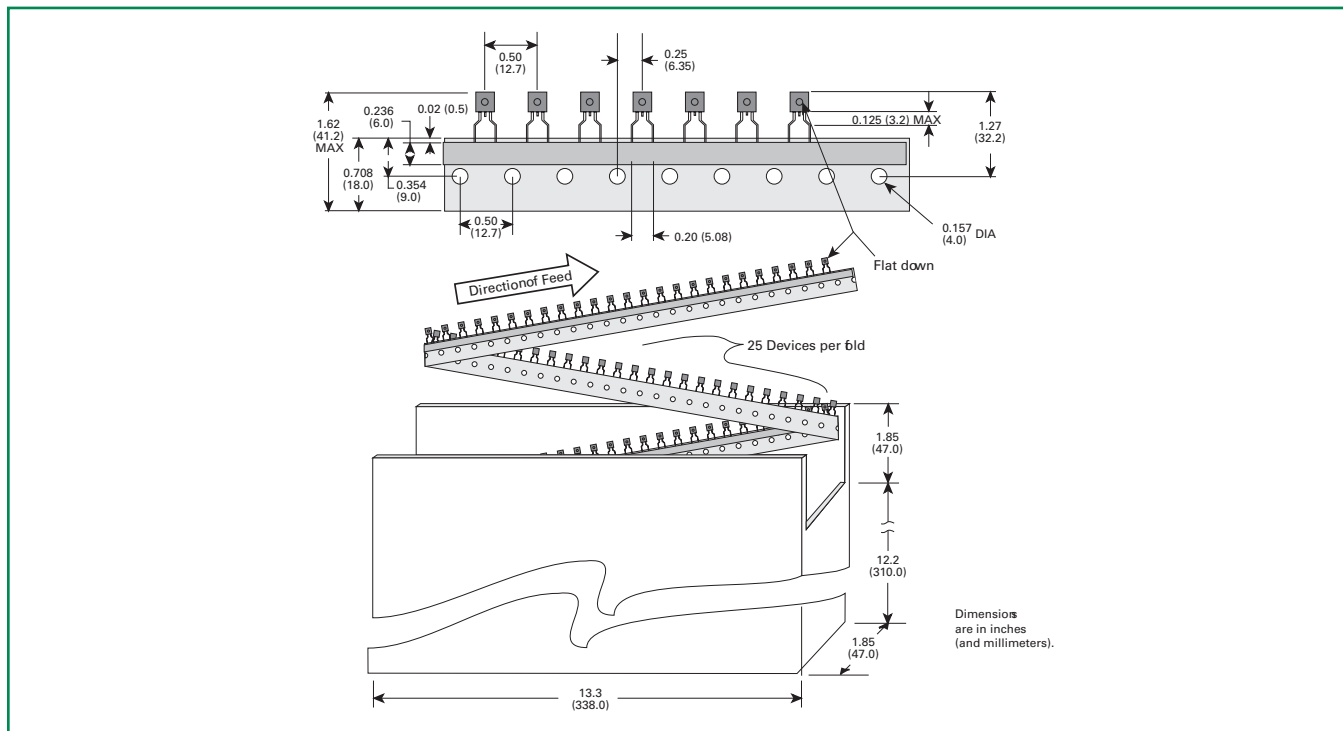
TO-92 Type 70 Reel Pack (RP3) Radial Leaded Specifications



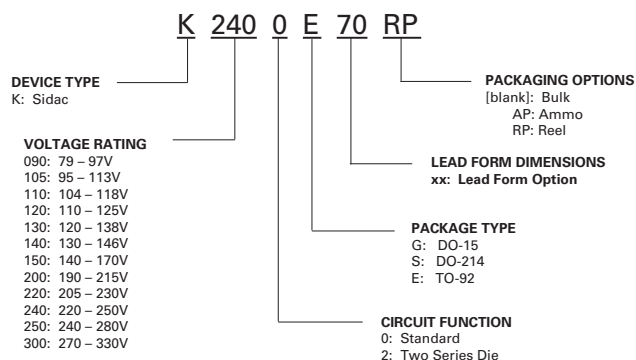
TO-92 Type 70 Reel Pack (RP2) Radial Leaded Specifications



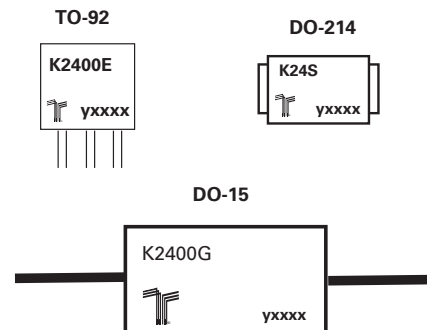
TO-92 Type 70 Ammo Pack (AP) Radial Leaded Specifications



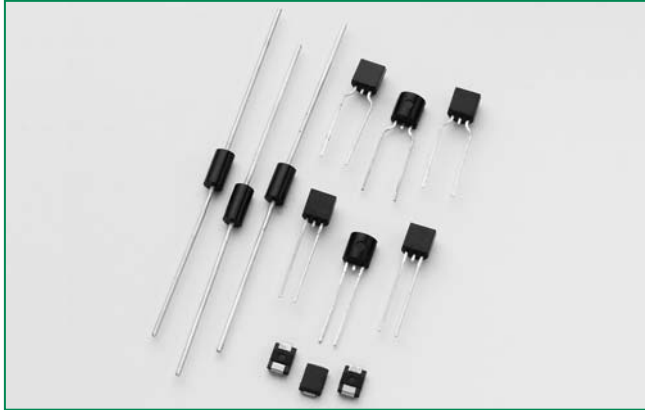
Part Numbering System



Part Marking System



RoHS Kxxx0yH Series



Schematic Symbol



Description

The new Kxxx0yH is a higher energy SIDAC switch for gas ignition applications requiring higher current pulse current especially at low repetition rate. It is offered in a DO-15 and TO-92 leaded packages as well as DO-214 surface mount package. Voltage activation of this solid state switch is accomplished with peak voltage level of 190 to 280Volts. The SIDAC is a silicon bilateral voltage triggered Thyristor switch that switches on through a negative resistance region to a low on-state voltage. Conduction will continue until current is interrupted or lowered below minimum holding current of the device.

Features

- AC Circuit Oriented
- Triggering Voltage of 190 to 280V
- 280A Pulse Current Capability
- RoHS Compliant

Applications

Suitable for high voltage power supplies, natural gas igniters, and Xenon flash ignition.

Electrical Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Max	Unit
V_{BO}	Breakover/Trigger Voltage	K2000yH	190	215	V
		K2200yH	205	230	
		K2400yH	220	250	
		K2500yH	240	280	
V_{DRM}	Repetitive Peak Off-state Voltage	K2000yH	180		V
		K2200yH	180		
		K2400yH	190		
		K2500yH	200		
$I_{T(RMS)}$	On-state RMS Current	50/60Hz, $T_J < 125^\circ\text{C}$		1	A
V_{TM}	Peak On-state Voltage	$I_T = 1\text{A}$		1.5	V
I_H	Dynamic Holding Current	$R_T = 100\Omega$ 50/60Hz Sine Wave		150	mA
R_S	Switching Resistance, $R_S = \frac{(V_{BO} - V_S)}{(I_S - I_{BO})}$	50/60Hz Sine Wave		100	Ω
I_{BO}	Breakover Current	50/60Hz Sine Wave		50	μA
I_{TRM}	Peak Repetitive Pulse Current (refer to figure 4)	$t_p = 10\mu\text{s}$	60Hz	120	A
			5Hz	280	
di/dt	Critical Rate of Rise of On-State Current			150	A/ μs
dv/dt	Critical Rate of Rise of Off-State Voltage		1500		V/ μs
T_S	Storage Temperature Range		-40	150	$^\circ\text{C}$
T_J	Junction Temperature Range		-40	125	$^\circ\text{C}$
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	DO-15		18	$^\circ\text{C/W}$
		DO-214		30	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	DO-92		35	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	DO-15		75	$^\circ\text{C/W}$
		DO-92		95	

Note: xxx - voltage, y = package

Figure 1: V-I Characteristics

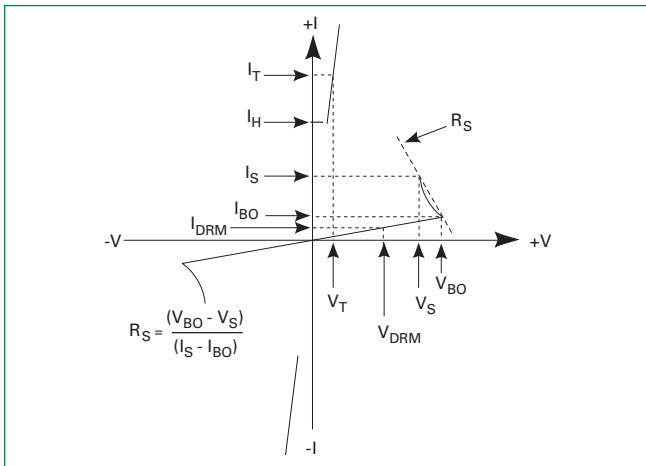


Figure 2: On-state Current vs. On-state Voltage (Typical)

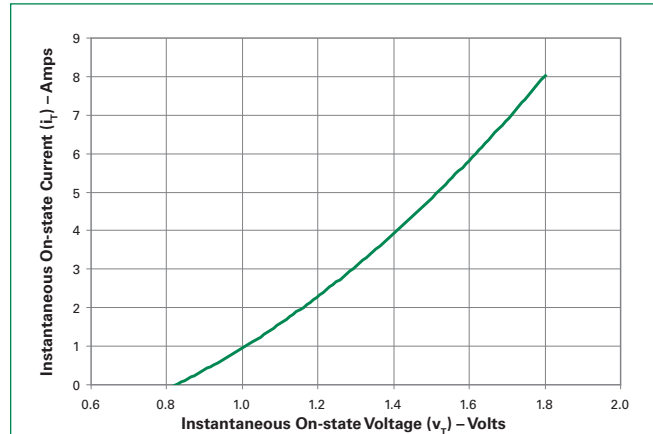


Figure 3: Power Dissipation vs. On-state Current (Typical)

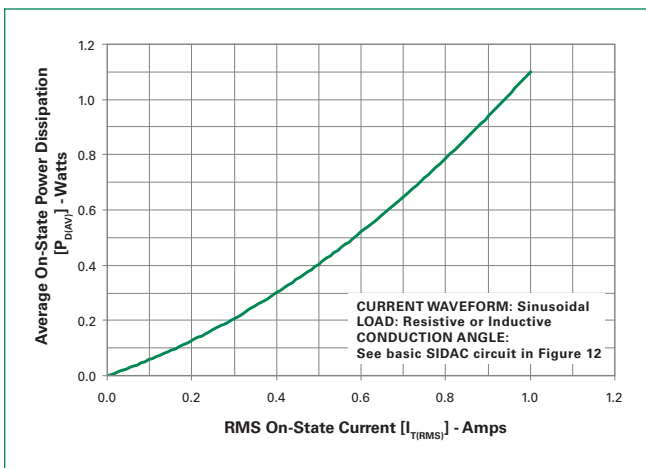


Figure 4: Repetitive Peak On-state Current (I_{TRM}) vs. Pulse Width at Various Frequencies

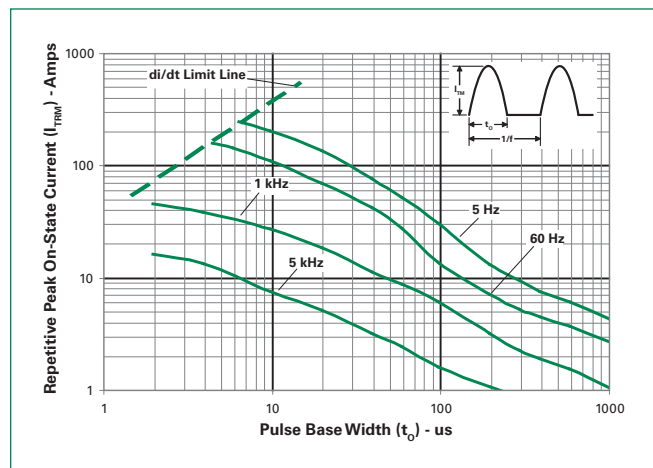


Figure 5: Surge Peak On-state Current vs. Number of Cycles

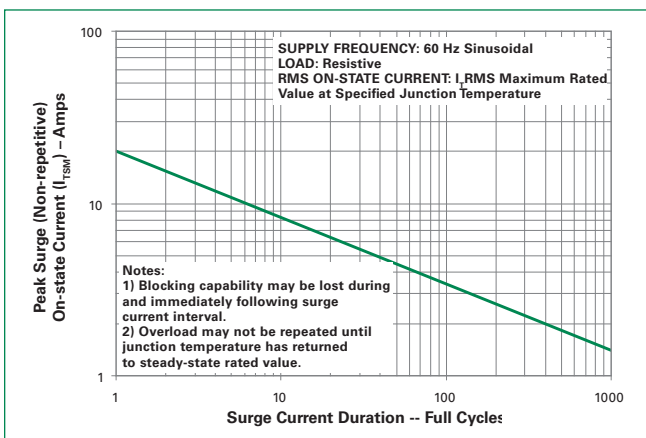


Figure 6: Normalized V_{BO} Change vs. Junction Temperature

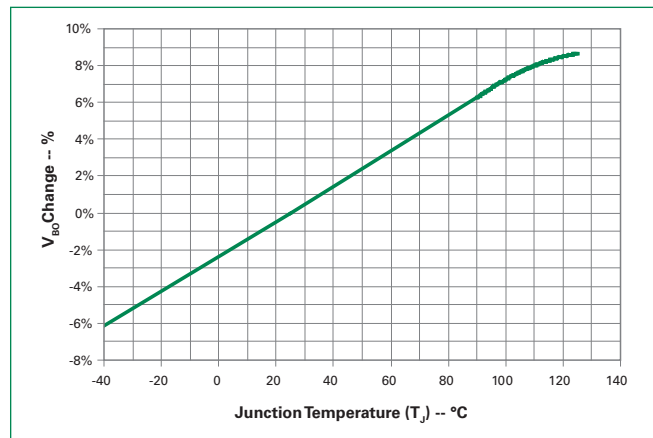


Figure 7: Normalized DC Holding Current vs. Junction Temperature

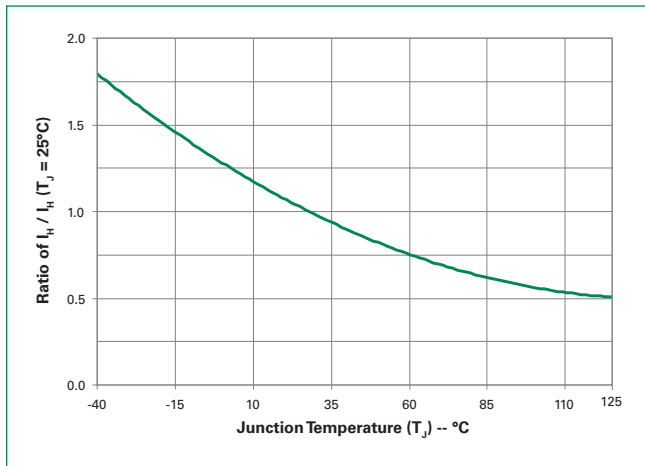


Figure 8: Maximum Allowable Case Temperature vs. RMS On-State Current

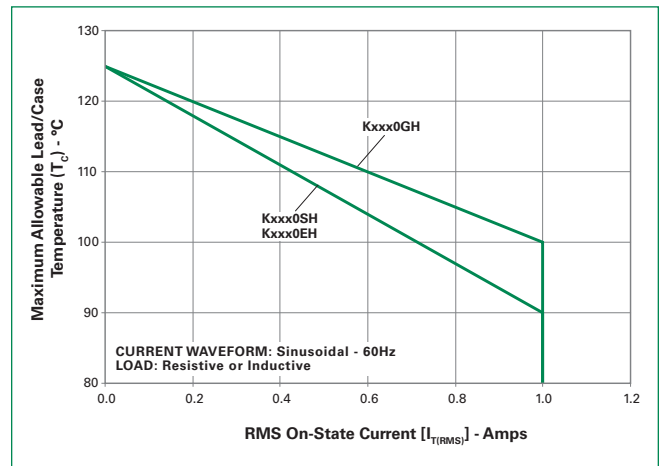


Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current

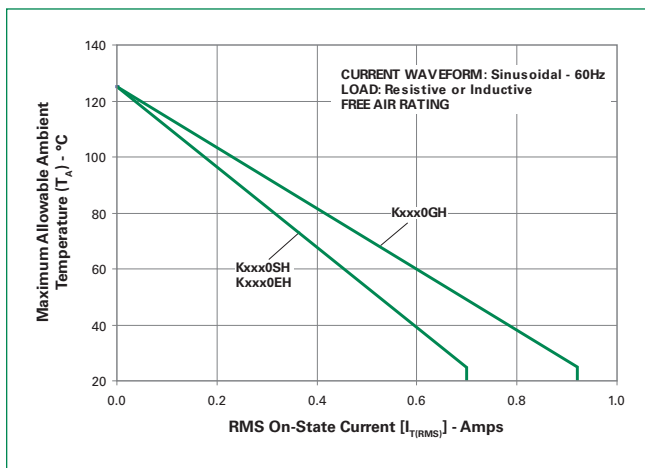


Figure 10: Normalized Repetitive Peak Breakover Current (I_{BO}) vs. Junction Temperature

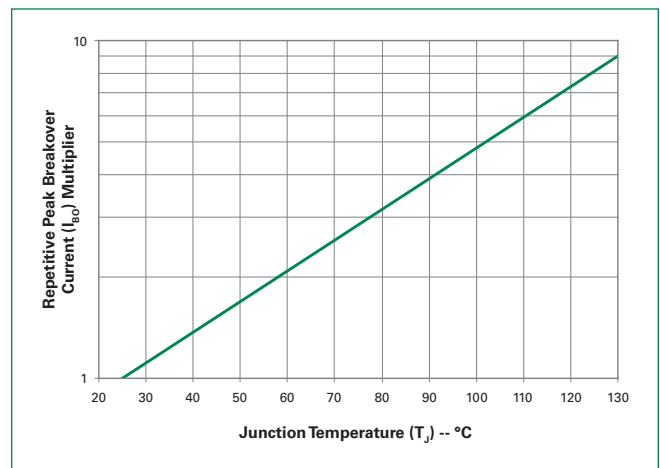


Figure 11: Dynamic Holding Current Test Circuit for SIDACs

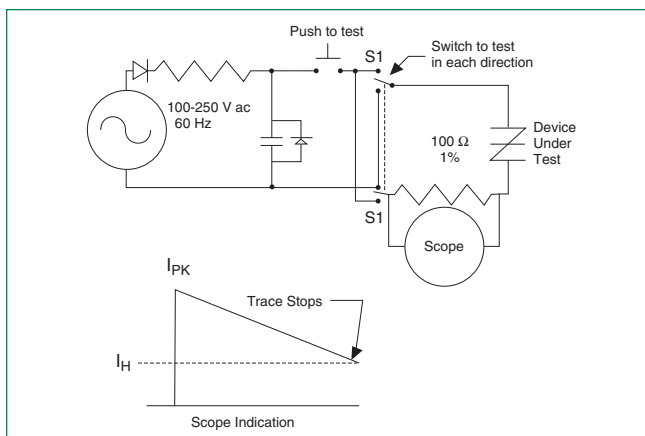


Figure 12: Basic SIDAC Circuit

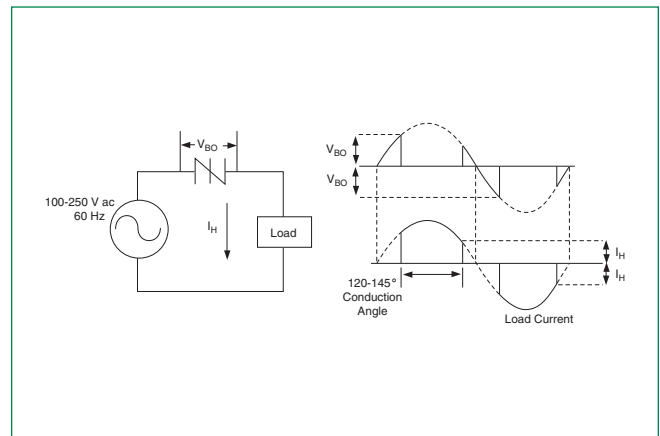


Figure 13: Relaxation Oscillator Using a SIDAC

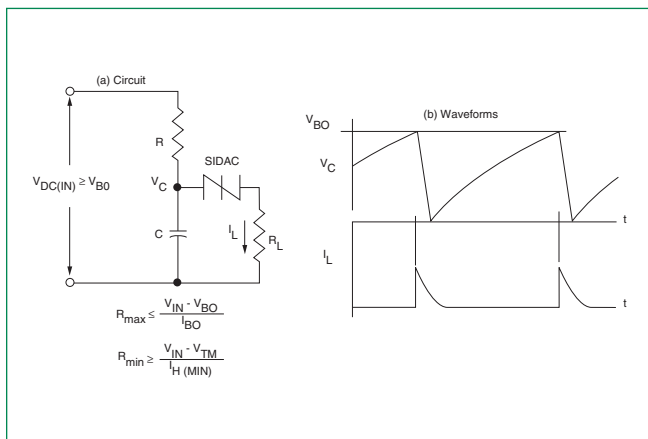
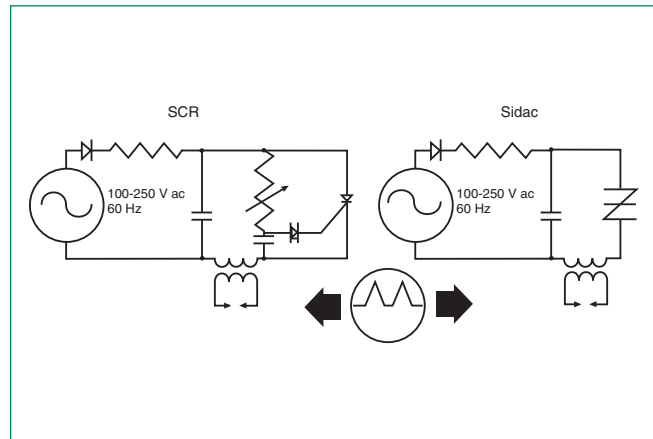
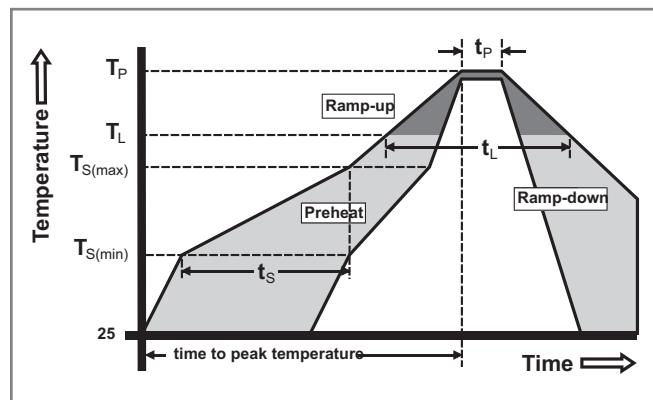


Figure 14: General Gas Ignitor Circuit



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Material	Copper Alloy
Terminal Finish	100% Matte Tin-plated /Pb Free solder dipped.
Body Material	UL recognized epoxy meeting flammability classification 94V-0.

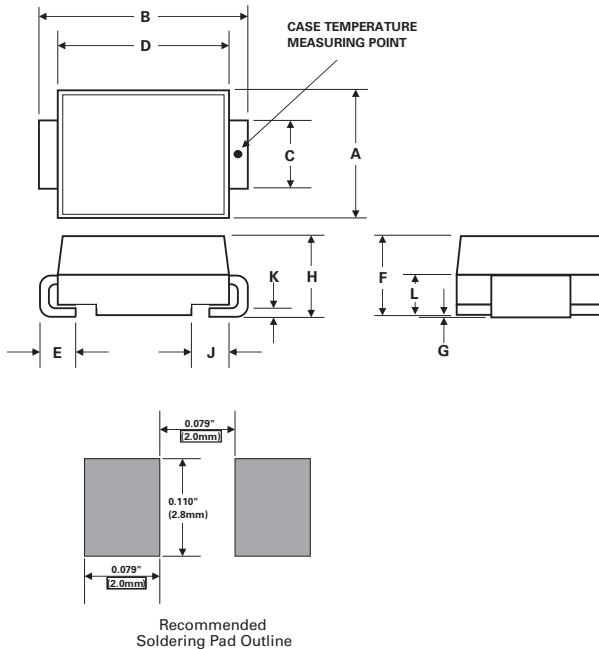
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Overheating and surge currents are the main killers of SIDACs. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Reliability/Environmental Tests

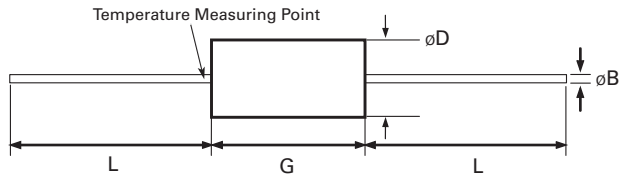
Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{DRM} (VAC-peak), 125°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
Biased Temperature & Humidity	EIA/JEDEC: JESD22-A101 (VDC), 85°C, 85%RH, 1008 hours
High Temp Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	-40°C, 1008 hours
Thermal Shock	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002: Category 3
Repetitive Surge Life Testing	MIL-STD-750: Method 2036, Condition E

Dimensions — DO-214



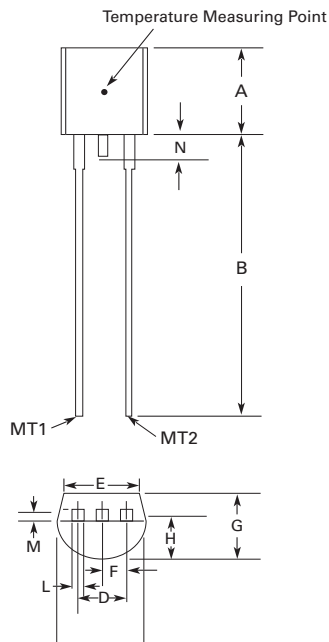
Dimension	Inches		Millimeters	
	Max	Max	Min	Max
A	0.130	0.156	3.30	3.95
B	0.201	0.220	5.10	5.60
C	0.077	0.087	1.95	2.20
D	0.159	0.181	4.05	4.60
E	0.030	0.063	0.75	1.60
F	0.075	0.096	1.90	2.45
G	0.002	0.008	0.05	0.20
H	0.077	0.104	1.95	2.65
J	0.043	0.053	1.09	1.35
K	0.006	0.016	0.15	0.41
L	0.030	0.055	0.76	1.40

Dimensions — DO-15



Dimension	Inches		Millimeters	
	Max	Max	Min	Max
øB	0.028	0.034	0.711	0.864
øD	0.120	0.140	3.048	3.556
G	0.235	0.270	5.969	6.858
L	1.000		25.400	

Dimensions - TO-92 with Type 70 Lead Form



Dimension	Inches		Millimeters	
	Max	Max	Min	Max
A	0.176	0.196	4.47	4.98
B	0.500		12.70	
D	0.095	0.105	2.41	2.67
E	0.150		3.81	
F	0.046	0.054	1.16	1.37
G	0.135	0.145	3.43	3.68
H	0.088	0.096	2.23	2.44
J	0.176	0.186	4.47	4.73
K	0.088	0.096	2.23	2.44
L	0.013	0.019	0.33	0.48
M	0.013	0.017	0.33	0.43
N		0.060		1.52

Notes:

1. Type 70 lead form as shown is standard for the E package.
2. All leads are insulated from case. Case is electrically nonconductive (rated at 16000V ac rms for one minute from leads to case over the operating temperature range.)
3. Mold flash shall not exceed 0.13 mm per side.

Product Selector

Part Number	Switching Voltage Range		Blocking Voltage	Packages		
	V _{BO} Minimum	V _{BO} Maximum	V _{DRM}	DO-15	DO-214	TO-92
K2000yH	190V	215V	180V	K2000GH	K2000SH	K2000EH70
K2200yH	205V	230V	180V	K2200GH	K2200SH	K2200EH70
K2400yH	220V	250V	190V	K2400GH	K2400SH	K2400EH70
K2500yH	240V	280V	200V	K2500GH	K2500SH	K2500EH70

Note: y = package

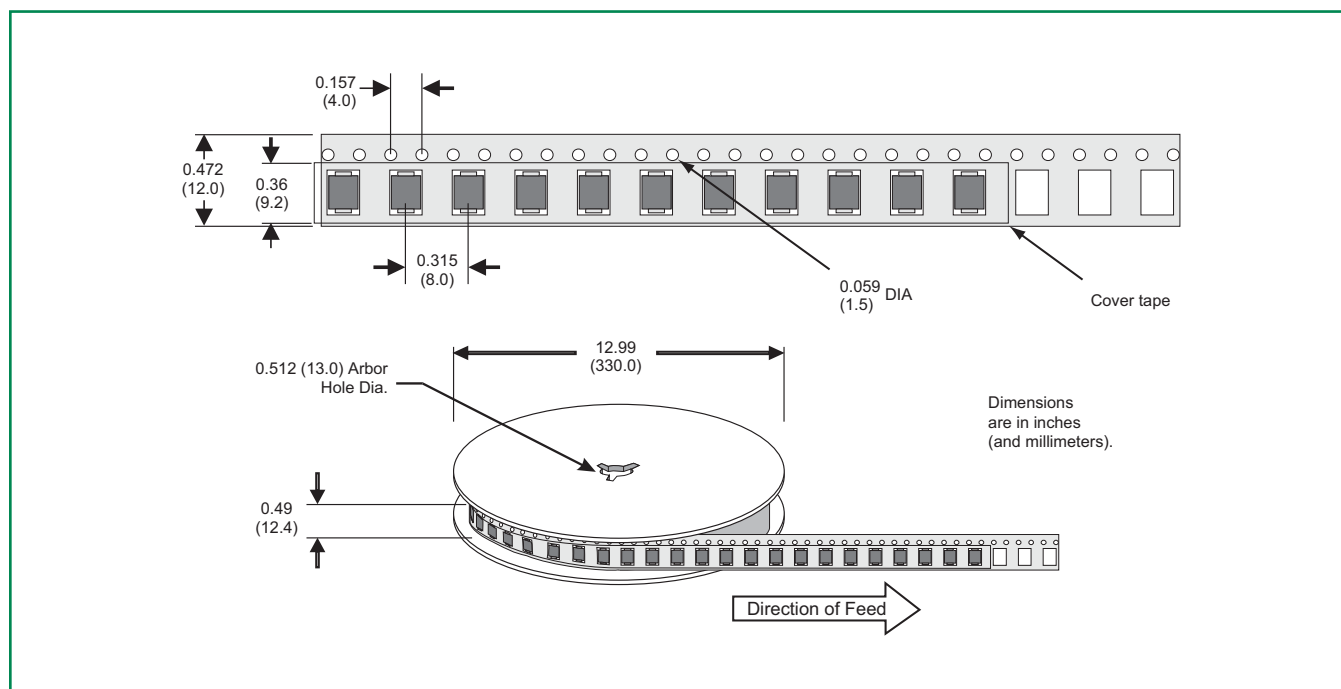
Packing Options

Part Number	Marking	Weight	Packaging Mode	Base Quantity
Kxxx0GH	Kxxx0GH	0.38g	Bulk	1000
Kxxx0GHRP	Kxxx0GH	0.38g	Reel Pack	5000
Kxxx0SHRP	KxxSH	0.1g	Reel Pack	2500
Kxxx0EH70	Kxxx0EH	0.17g	Bulk	2000
Kxxx0EH70AP	Kxxx0EH	0.17g	Ammo Pack	2000
Kxxx0EH70RP2	Kxxx0EH	0.17g	Reel Pack	2000
Kxxx0EH70RP3	Kxxx0EH	0.17g	Reel Pack	2000

Note: xxx or xx = voltage

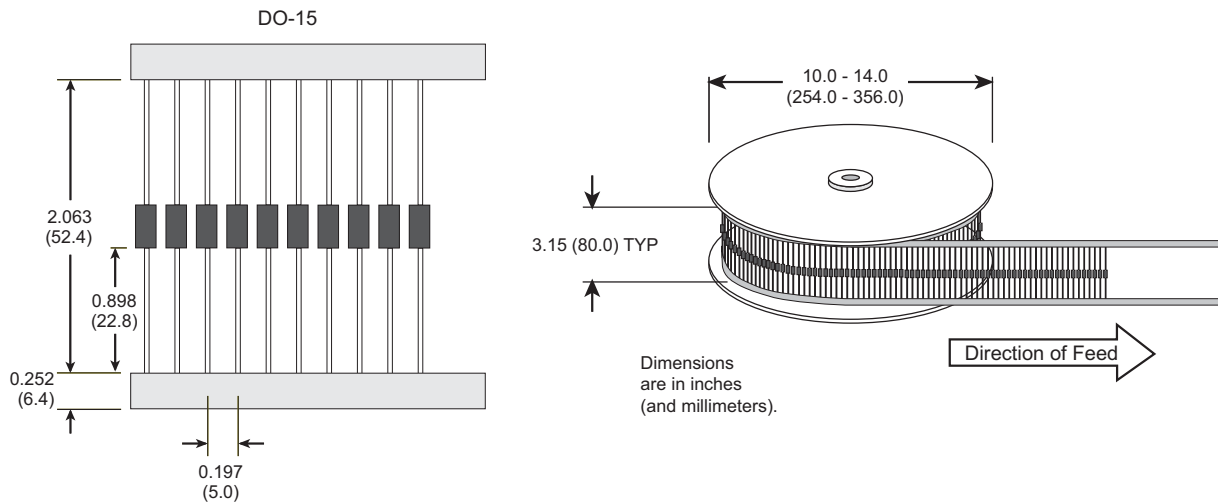
DO-214 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-1 Standards



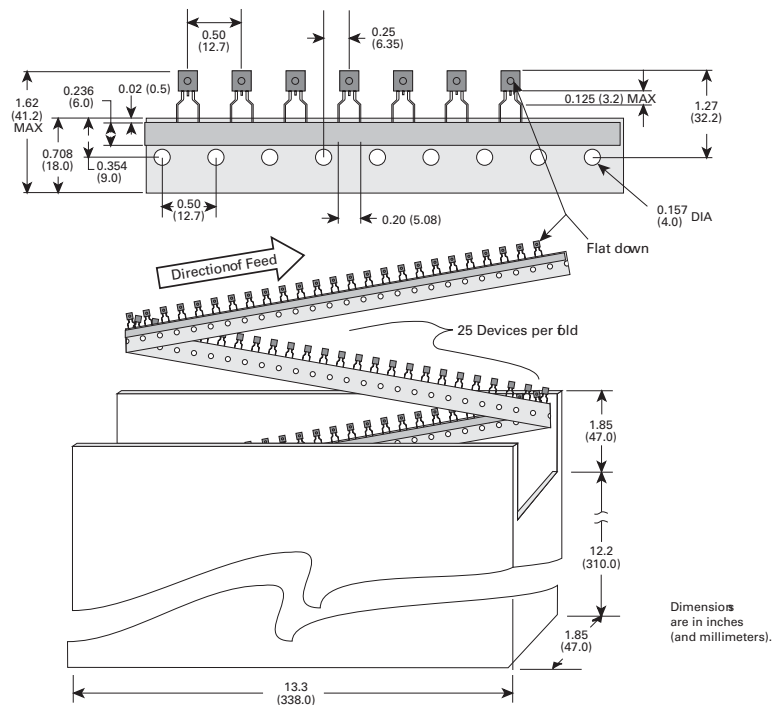
DO-15 Reel Pack (RP) Specifications

Meets all EIA RS-296 Standards

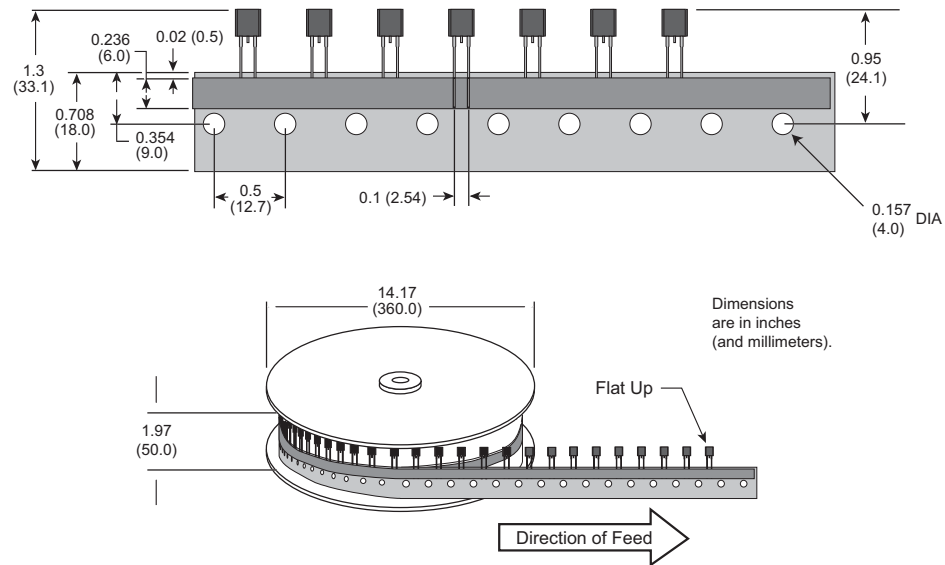


TO-92 Type 70 Ammo Pack (AP) Radial Leaded Specifications

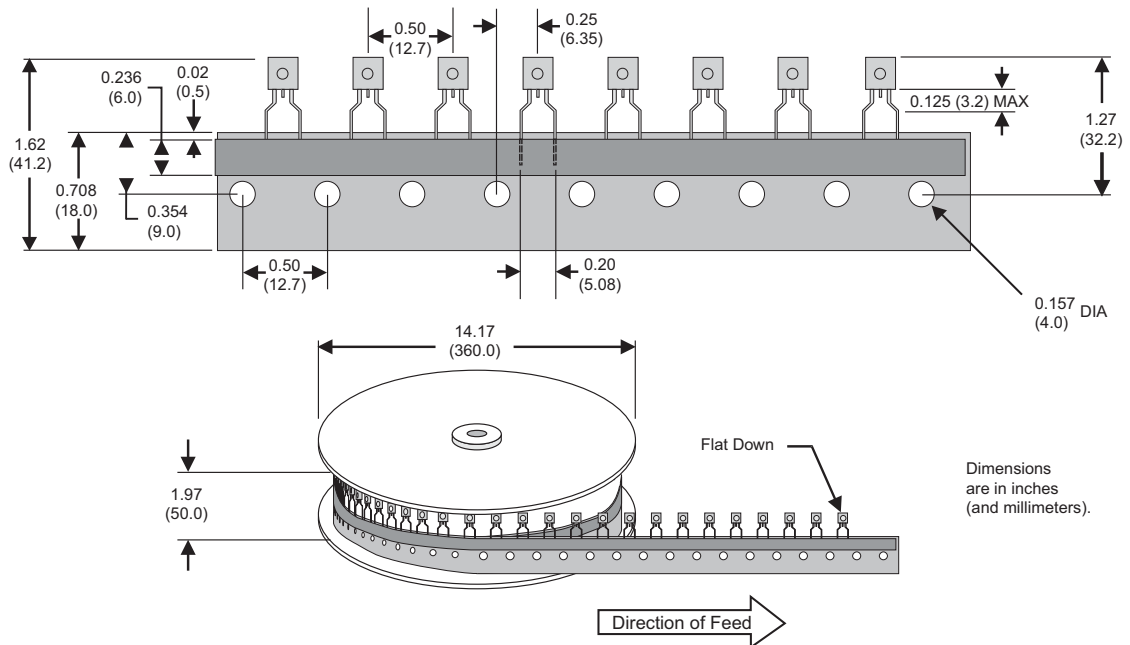
Meets all EIA-468-B 1994 Standards



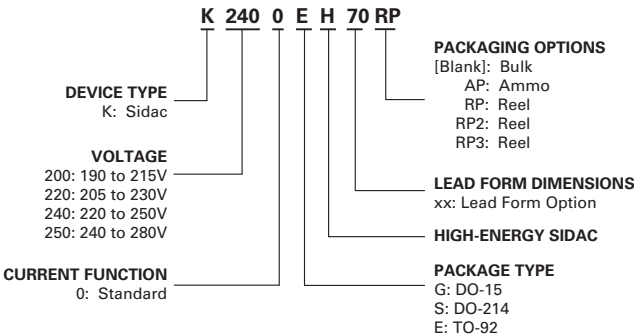
TO-92 Type 70 Reel Pack (RP3) Optional Specifications



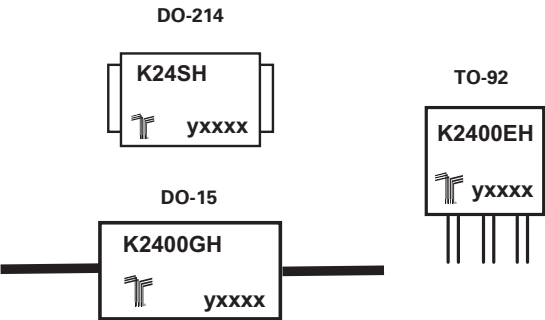
TO-92 Type 70 Reel Pack (RP2) Standard Specifications



Part Numbering System

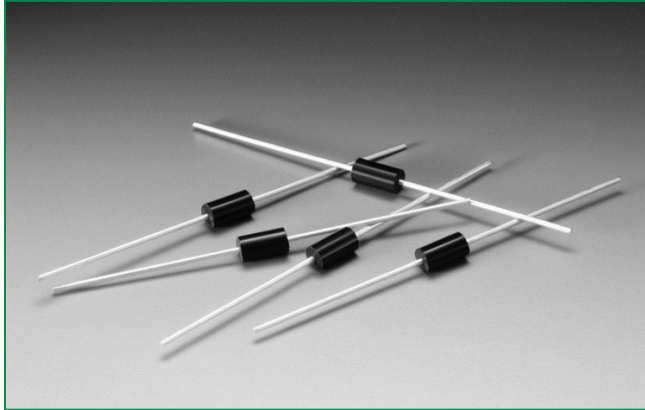


Part Marking System

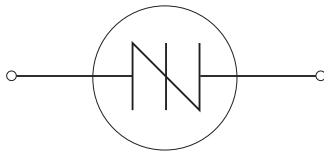


RoHS

Kxxx1G Series



Schematic Symbol



Applications

Typical application circuit presented in Figure 10 of this data sheet (Typical Metal Halide Ignitor Circuit).

Description

The Multipulse™ SIDAC is a voltage switch used in Metal-Halide lamp ignition circuits as well as High Pressure Sodium lamp ignition circuits for outdoor street and area lighting. This robust solid state switch is designed to handle lamp igniter applications requiring operation at ambient temperatures up to 90°C where igniter circuit components can raise SIDAC junction temperature up to 125°C, especially when the lamp element is removed or ruptured. Its excellent commutation time (t_{COMM}) makes this robust product best suited for producing multiple pulses in each half cycle of 50/60 Hz line voltage. The Multipulse™ SIDAC is offered in DO-15 axial leaded package.

Kxxx1G SIDAC has a repetitive off-state blocking voltage (V_{DRM}) of 180V to 270V minimum depending actual device type. Blocking capability is ensured by glass passivated junctions for best reliability. Package is epoxy encapsulation with tin-plated copper alloy leads.

Features

- AC circuit oriented
- **RoHS** Compliant
- Triggering Voltage of 200 to 380V

Electrical Specifications

Symbol	Parameters	Test Conditions	Min	Max	Unit
V_{BO}	Breakover/Trigger Voltage	K2201G K2401G K2501G K3601G	200 220 240 340	230 250 280 380	V
V_{DRM}	Repetitive Peak Off-State Voltage	K2201G K2401G K2501G K3601G	180 190 200 270		V
$I_{T(RMS)}$	On-State RMS Current, $T_J < 125^\circ\text{C}$	50/60Hz Sine Wave		1	A
I_H	Dynamic Holding Current, $R=100\ \Omega$	50/60Hz Sine Wave		160 TYP	mA
R_s	Switching Resistance, $R_s = \frac{(V_{BO} - V_s)}{(I_s - I_{BO})}$	50/60Hz Sine Wave		100	Ω
t_{COMM}	Commutation Time $T_J < 125^\circ\text{C}$	See test circuit and waveform in Figure 9		100	μsec
I_{BO}	Breakover Current	50/60Hz Sine Wave		10	μA
I_{TSM}	Non-repetitive 1 cycle On-State peak value	60Hz 50Hz		20.0 16.7	A
di/dt	Critical Rate of Rise of On-State Current			150	A/ μsec
dv/dt	Critical Rate of Rise of Off-State Voltage			1500	V/ μsec
T_s	Storage Temperature Range		-40	+125	$^\circ\text{C}$
T_J	Max Operating Junction Temperature		-40	+125	$^\circ\text{C}$
$R_{\theta JL}$	Thermal Resistance	Junction to lead		18	$^\circ\text{C/W}$

Figure 1: Characteristics

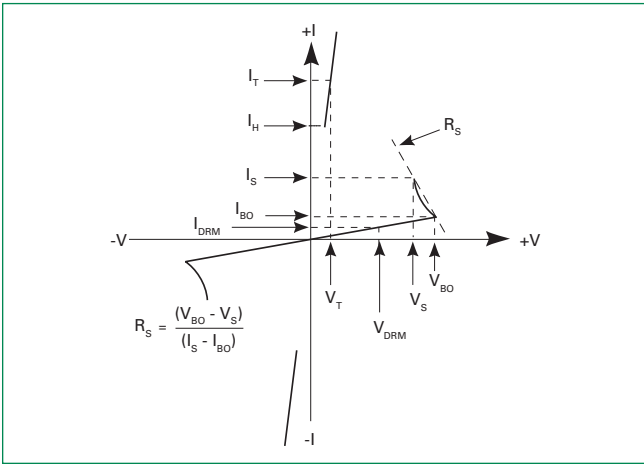


Figure 2: Maximum Allowable Lead/Tab Temperature vs. On-State Current

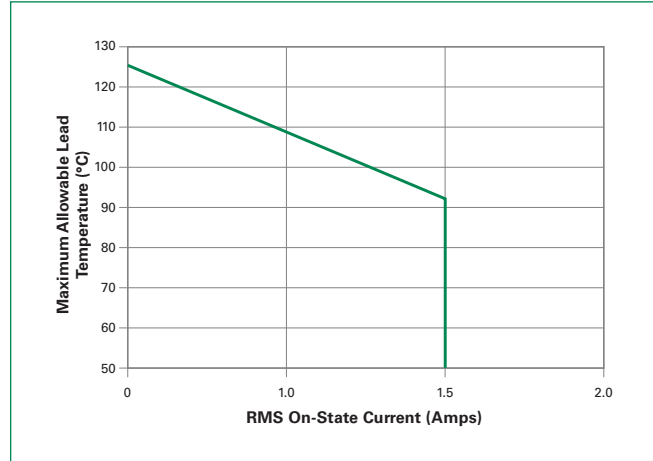


Figure 3: Power Dissipation (Typical) vs. On-State Current

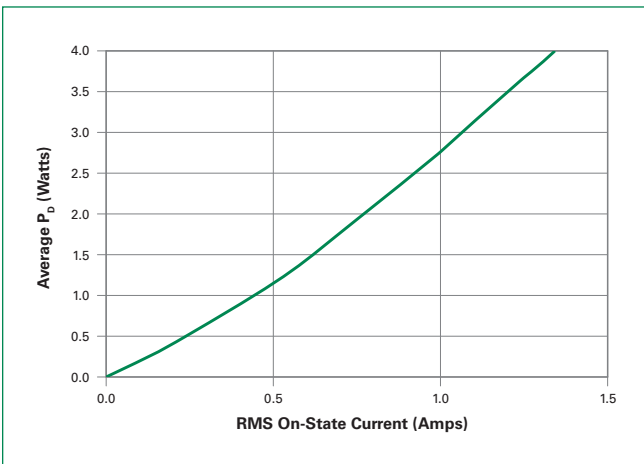


Figure 4: V_{BO} Change vs. Junction Temperature

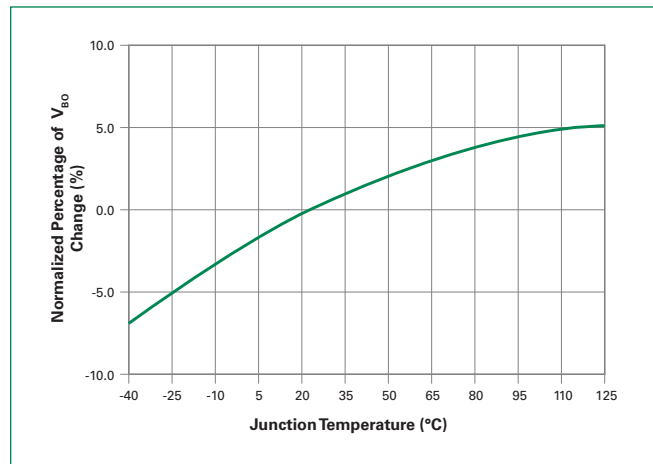


Figure 5: Pulse On-State Current Rating

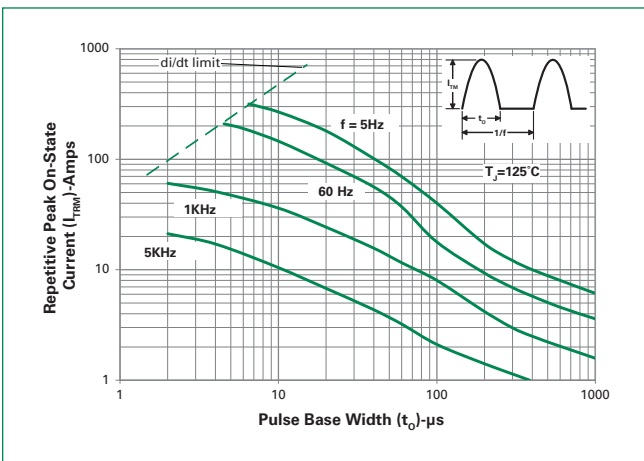


Figure 6: Maximum Allowable Ambient Temperature vs. On-State Current

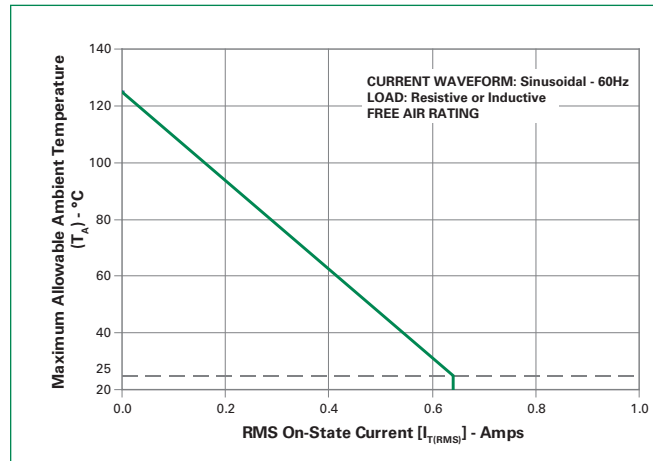


Figure 7: Peak Surge Current vs Surge Current Duration

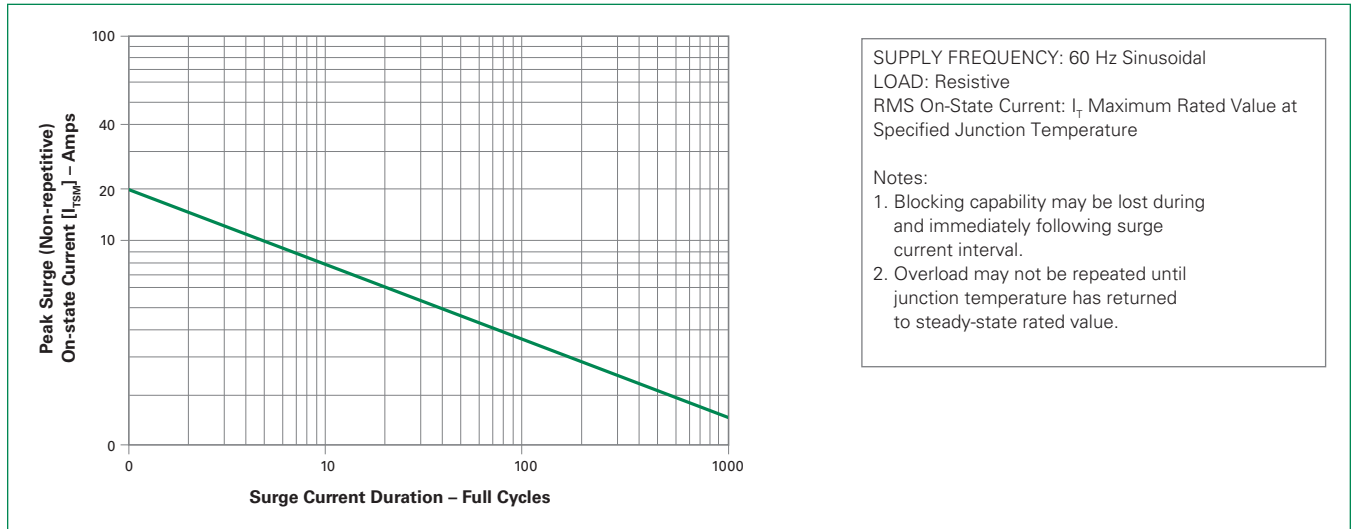


Figure 8: Typical On-State Voltage vs On-State Current

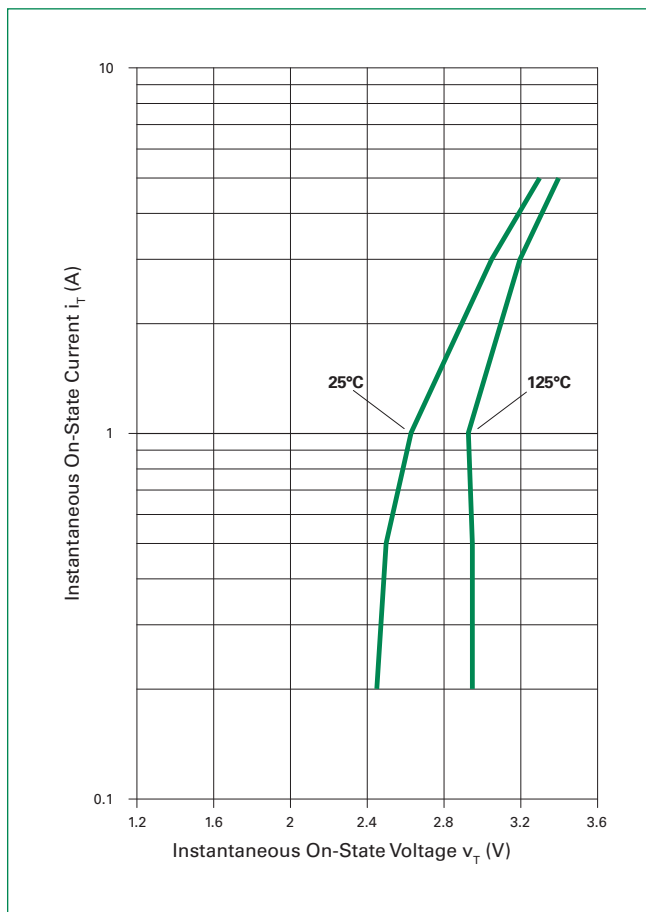


Figure 9: Multipulse™ SIDAC t_{COMM} , Commutation Time

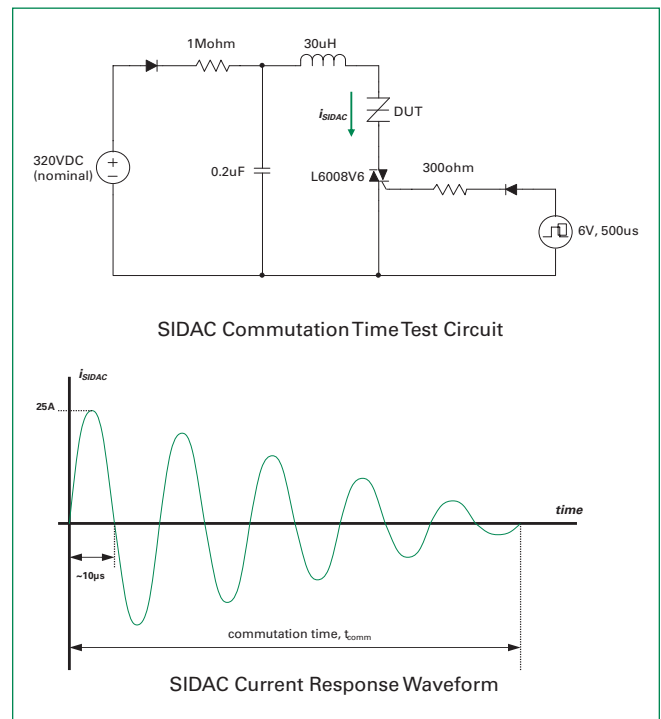
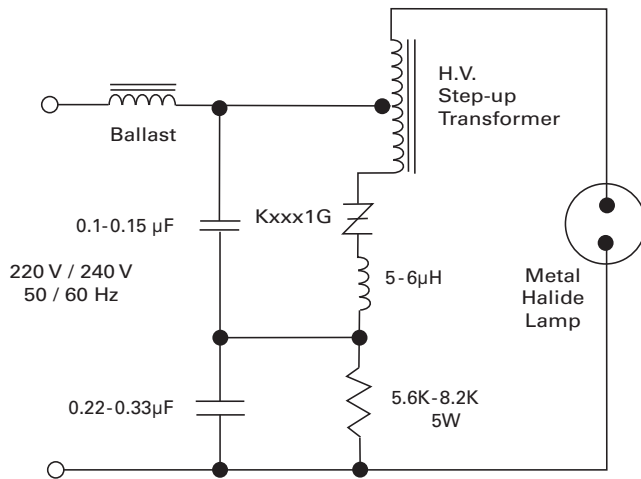


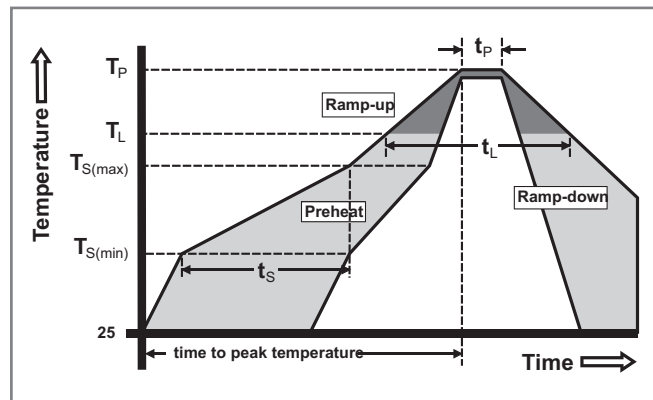
Figure 10: Typical Metal Halide Ignitor Circuit



Note: With proper component selection, this circuit will produce three pulses for ignition of metal halide lamp that requires a minimum of three pulses at 4kV magnitude and >1uSec duration each at a minimum repetition rate of 3.3kHz.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin Plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

Package	Weight / unit (mg)
DO-15	385

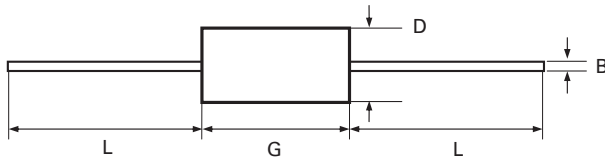
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Overheating and surge currents are the main killers of SIDACs. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Reliability/Environmental Tests

Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{DRM} (VAC-peak), 125°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051, 100 cycles; -40°C to 150°C, 15-minute dwell time
Temperature / Humidity	EIA/JEDEC: JESD22-A101 1008 hours; 160V - DC: 85°C; 85% relative humidity
High Temp Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	-40°C, 1008 hours
Thermal Shock	MIL-STD-750: Method 1056 10 cycles; 0°C to 100°C; 5-minute dwell-time at each temperature; 10-sec (max) transfer time between temperature
Autoclave	EIA/JEDEC: JESD22-A102 168 hours (121°C at 2 ATMs) and 100% RH
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002: Category 3, Test A
Repetitive Surge Life Testing	Multi firings per half cycle at 60Hz in application circuit for 168 hours minimum

Dimensions — DO-15 (G Package)



Dimension	Inches		Millimeters	
	Max	Max	Min	Max
B	0.028	0.034	0.711	0.864
D	0.120	0.140	3.048	3.556
G	0.235	0.270	5.969	6.858
L	1.000		25.400	

Product Selector

Part Number	Switching Voltage Range		Blocking Voltage	Packages
	V_{BO} Minimum	V_{BO} Maximum	V_{DRM}	
K2201G	200V	230V	180V	DO-15
K2401G	220V	250V	190V	DO-15
K2501G	240V	280V	200V	DO-15
K3601G	340V	380V	270V	DO-15

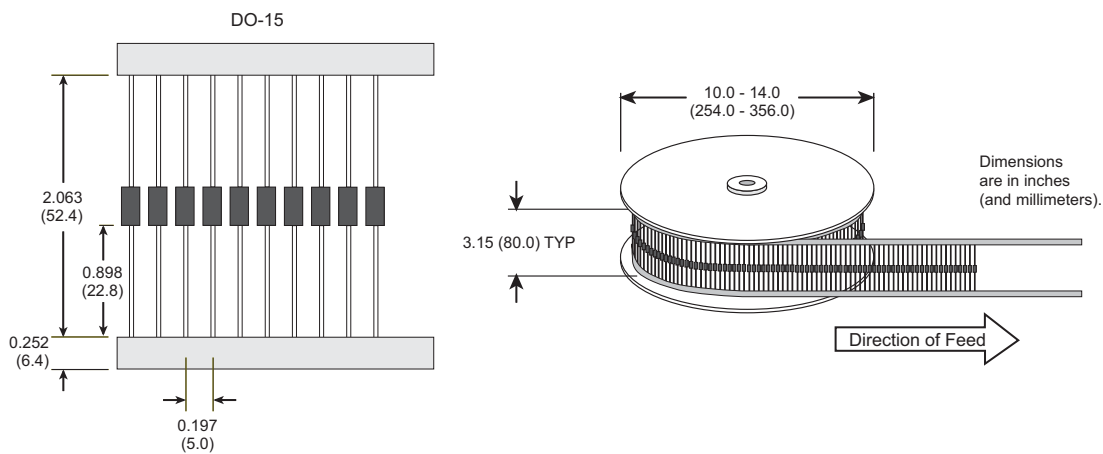
Packing Options

Part Number	Package	Packing Mode	Base Quantity
Kxxx1G	DO-15	Bulk	1000
Kxxx1GRP		Tape & Reel	5000

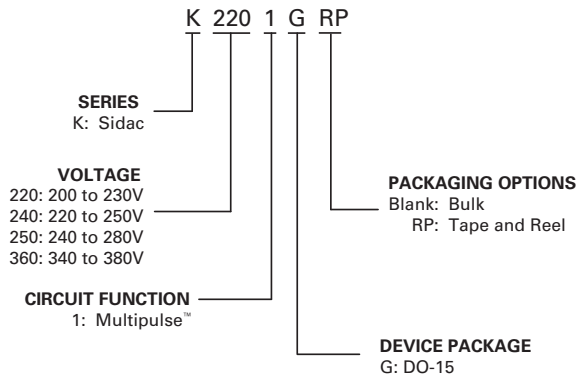
Note: xxx = voltage

DO-15 Embossed Carrier RP Specifications

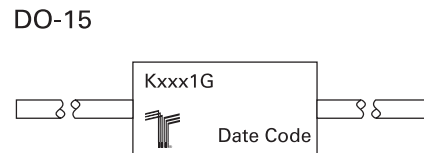
Meets all EIA RS-29-6 Standards



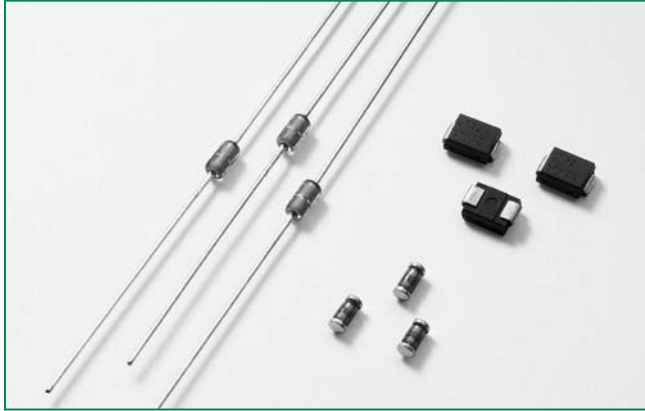
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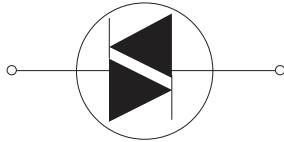
Part Marking System



RoHS HTxxx & HTMxxx & STxxx Series



Schematic Symbol



Applications

DIACs are used to trigger Triacs and SCRs in phase control circuits for lamp dimming, universal motor speed control, and heat control. They are used also for triggering transistors in solid state ballast lighting controls.

Description

The HTM, HT, and ST series of bilateral trigger DIACs offer a range of voltage characteristics from 27V to 70V. A DIAC semiconductor is a full-wave or bidirectional Thyristor. It is triggered from a blocking state to a conduction state for either polarity of applied voltage whenever the amplitude of applied voltage exceeds the breakover voltage of the DIAC.

Features & Benefits

- **RoHS** compliant
 - Bilateral triggering device
 - Glass-passivated junctions
 - Wide voltage range selections
 - Long-term reliability
 - Parameter stability
 - Reliable barrier against junction contamination
- ST Series:**
- Epoxy SM package (DO-214)
 - High-temperature, solder bonded die attachment
- HTM/HT Series:**
- MINIMELF/DO-35 trigger package

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Min	Max	Unit
I_{TRM}	Pulse On-State Current	120PPS, $T_A \leq 40^\circ\text{C}$ pulse width = 10 μs		2 1.5 ^(*)	A
T_S	Storage Temperature Range		-40	+125	$^\circ\text{C}$
T_J	Operating Junction Temperature		-40	+125	$^\circ\text{C}$
$P_{D(AV)}$	Device Power Dissipation	$T_A = -40^\circ\text{C}$ to $+40^\circ\text{C}$		See Product Selector Table	mW

(*)Only Applies to HT-60

Notes:

1. Service Dissipation (at $T_A = -40^\circ\text{C}$ to $+40^\circ\text{C}$): 250mW for DO-35 and MINIMELF/SOD-80 and 300mW for DO214
2. Above $+40^\circ\text{C}$, Derate: 3.6mW/ $^\circ\text{C}$ for DO-35 and MINIMELF/SOD-80 and 3mW/ $^\circ\text{C}$ for DO214

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Description	Test Conditions	Min	Max	Unit
V_{BO}	Breakover/Trigger Voltage	50/60Hz Sine Wave	See Product Selector Table	See Product Selector Table	V
ΔV_{BO}	Breakover Voltage Symmetry	$+V_{BO}$ to $-V_{BO}$		2 ^(Note 1)	V
V_{BB}	Δ Breakback Voltage ^(Note 4)	V_{BO} to V_{10mA}	5		V
		V_{BO} to V_{6mA} ^(*)	15		V
$V_{BB(DYN)}$	Dynamic Δ Breakback Voltage ^(Notes 2 & 3)	120 PPS	10		V
I_{BO}	Breakover Current	50/60Hz Sine Wave		15	μA

(*) Only Applies to HT-60

Electrical Characteristic Notes:

1. Breakover voltage symmetry as close as 1V is available from the factory for these products.

2. See Figure 4 and Figure 5 for test circuit and waveforms.

3. Typical switching time is 900 nano-seconds measured at I_{PK} (Figure 4) across a 20 Ω resistor (Figure 5). Switching time is defined as rise time of I_{PK} between the 10% to 90% points

4. See V-I Characteristics

Static Characteristics - Not Applicable

Product Selector

Part Number	Package Availability			V_{BO}	
	MINIMELF	DO-35	DO-214	MIN	MAX
XX-32	—	HT-32	ST-32	27V	37V
XX-32A/ 5761	—	HT-32A	—	28V	36V
XX-32B/ 5761A	HTM-32B	HT-32B	ST-32B	30V	34V
XX-34B	—	HT-34B	ST-34B	32V	36V
XX-35	—	HT-35	ST-35	30V	40V
XX-36A/ 5762	—	HT-36A	ST-36A	32V	40V
XX-36B	—	HT-36B	ST-36B	34V	38V
XX-40	—	HT-40	ST-40	35V	45V
XX-60	—	HT-60	—	56V	70V

"XX" = HTM for MINIMELF

HT for DO-35

ST for DO-214

Thermal Resistances

Symbol	Description	Test Conditions		Value	Unit
$R_{\theta(J-L)}$	Junction to Lead	Maximum Lead Temperature: 85°C	DO-35	100	°C/W
		Maximum Lead Temperature: 90°C	DO-214	65*	°C/W
		Maximum Lead Temperature: 87°C	MINIMELF	75	°C/W
$R_{\theta(J-A)}$	Junction to Ambient	Free-Air	DO-35	278	°C/W

* Mounted on 1 cm² copper foil surface; two-ounce copper foil

Figure 1: V-I Characteristics

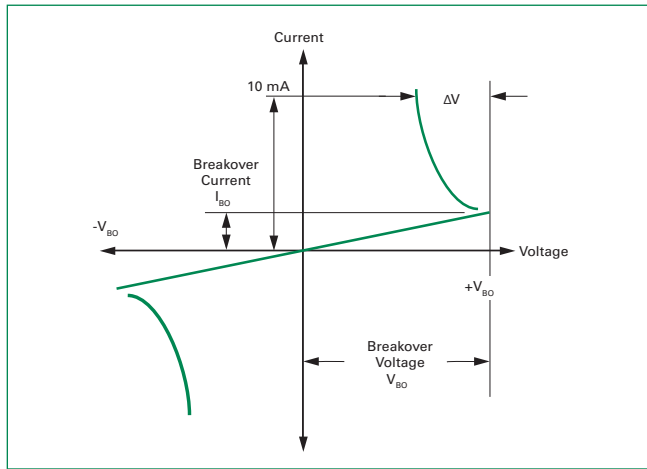


Figure 2: Typical DIAC/Triac Full-wave Phase Control Circuit

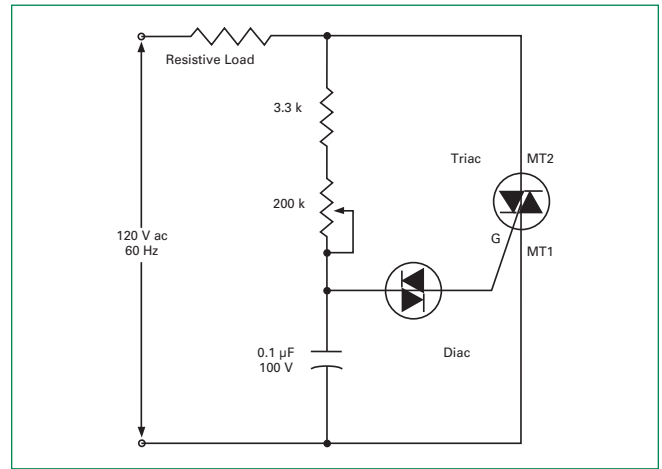


Figure 3: Repetitive Peak On-state Current vs. Pulse Duration

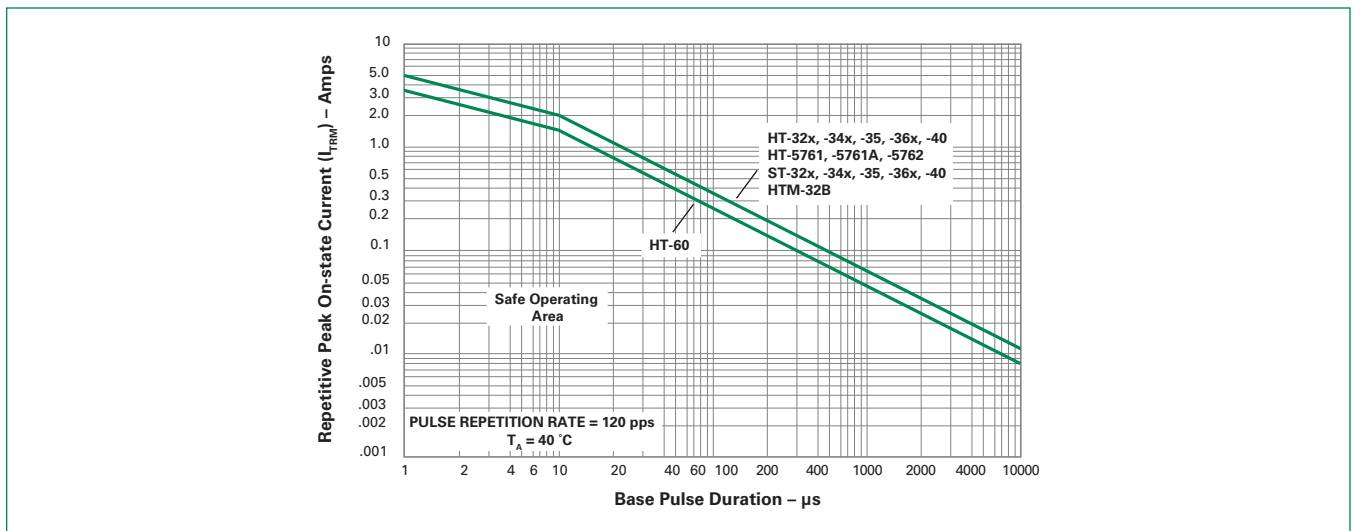


Figure 4: Normalized V_{BO} Change vs. Junction Temperature

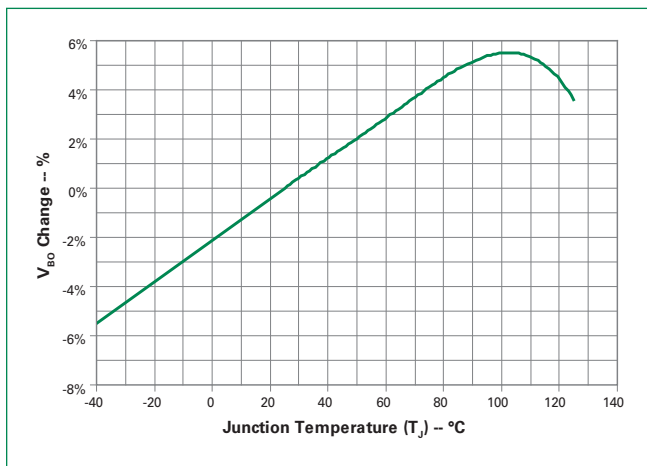


Figure 5: Test Circuit Waveforms (Refer to Figure 5)

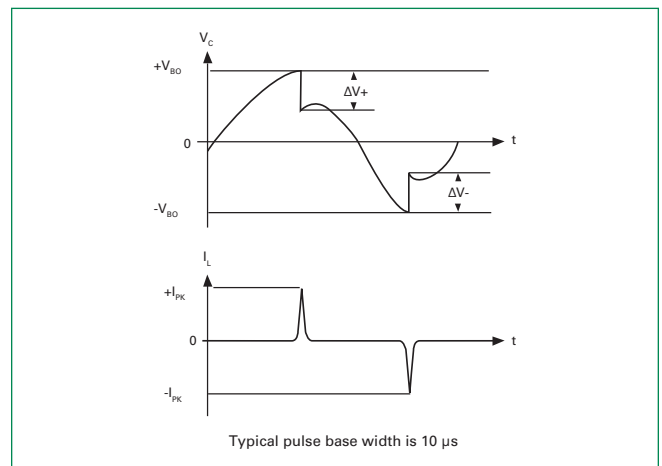
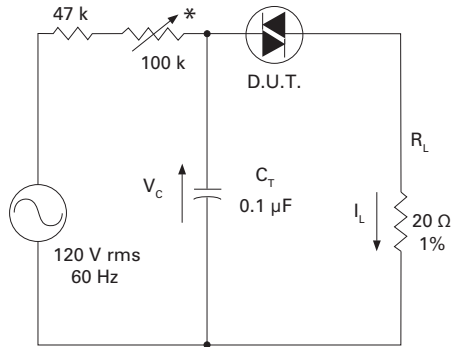
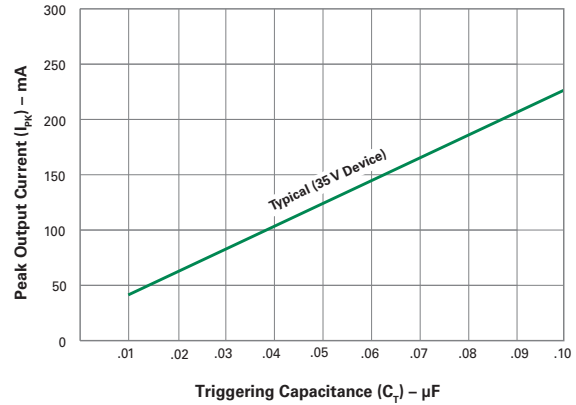


Figure 6: Circuit Used to Measure DIAC Characteristics (Refer to Figure 4)



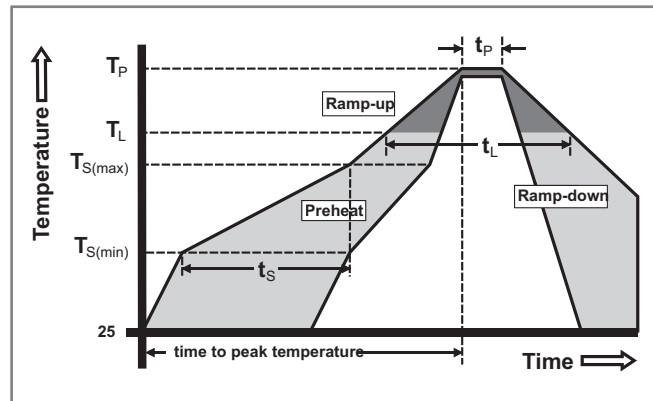
* Adjust for one firing in each half cycle. D.U.T. = Diac

Figure 7: Peak Output Current vs. Triggering Capacitance (Per Figure 5 with R_L of 20 Ω)



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp (T_L) to peak)		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte-Tin Plated/ Pb-Free Solder Dipped
Body Material	DO-214: UL recognized epoxy meeting flammability classification 94V-0. DO-35/MINIMELF: Glass case body
Lead Material	DO-214: Copper Alloy DO-35/MINIMELF: Copper Clad Iron

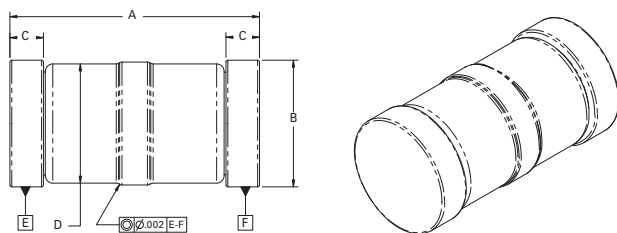
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Overheating and surge currents are the main killers of DIACs. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Reliability/Environmental Tests

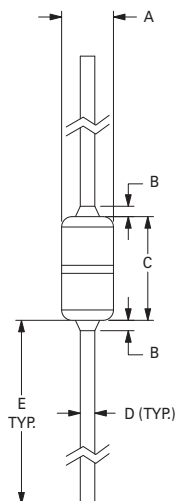
Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750, M-1040, Cond A Applied 80% of Rated Min V_{BO} (VAC-peak) @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 80% of Rated Min V_{BO} (V_{DC}): 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E
Burn-in	1 firing per 1/2 cycle, 168 hours

Dimensions – MINIMELF / SOD-80 (MM Package)



Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.125	0.134	0.142	3.18	3.40	3.61
B	0.066	0.068	0.070	1.68	1.73	1.78
C	0.012	0.018	0.020	0.30	0.46	0.51
D	—	0.063	—	—	1.60	—

Dimensions – DO-35 (Y Package)

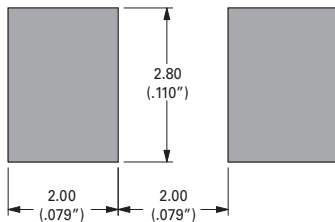
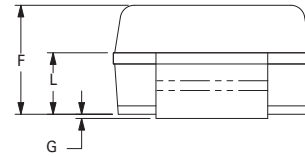
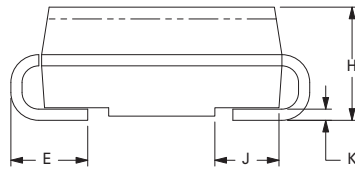
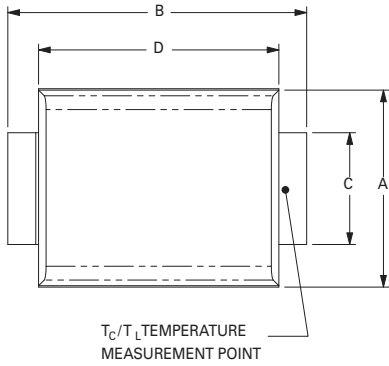


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A (Note 1)	0.060	0.090	1.530	2.280
B (Note 2)		0.015		0.381
C (Note 1)	0.135	0.165	3.430	4.190
D	0.018	0.022	0.458	0.558
E	1.000		25.400	

Notes:

- Package contour optional within dimensions A and C. Slugs, if any, shall be included within this cylinder but shall not be subject to the minimum limit of Dimension A.
- Lead diameter is not controlled in this zone to allow for flash, lead finish build-up and minor irregularities other than slugs.

Dimensions – DO-214 (S Package)



Recommended Soldering Pad Outline
(Reference Only)

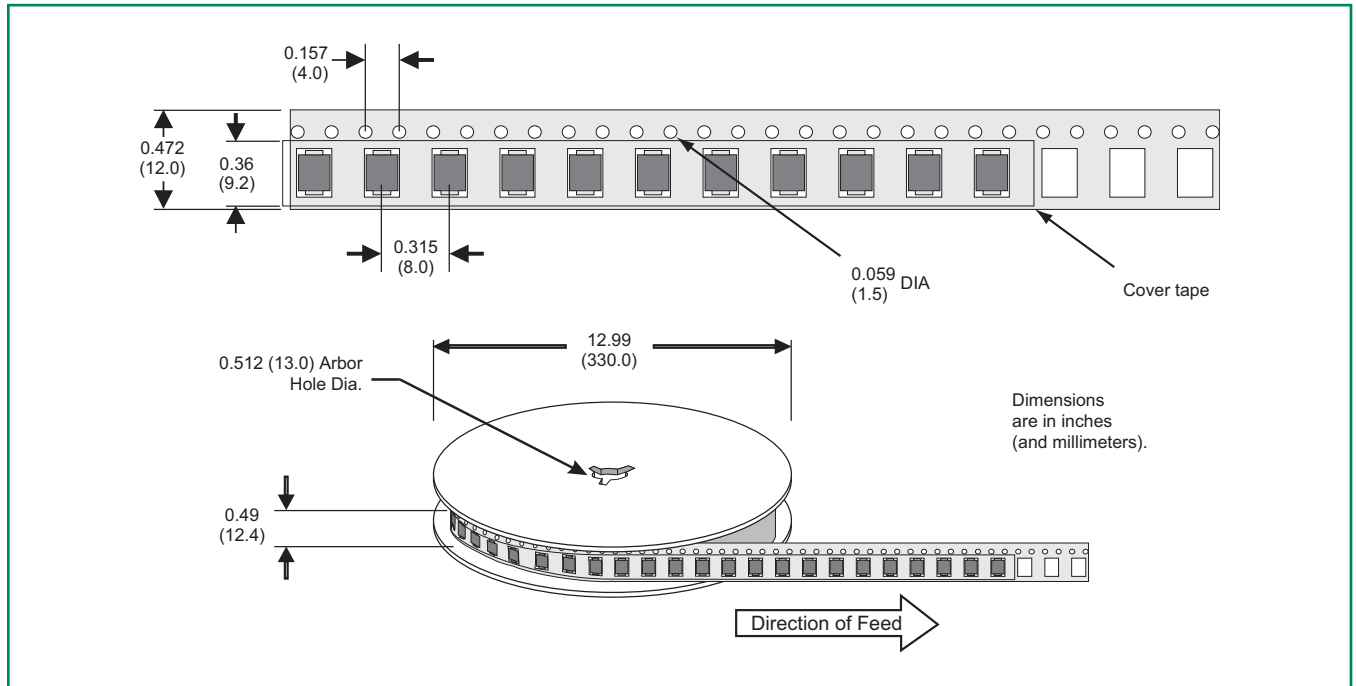
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.140	0.155	3.56	3.94
B	0.205	0.220	5.21	5.59
C	0.077	0.083	1.96	2.11
D	0.166	0.180	4.22	4.57
E	0.036	0.063	0.91	1.60
F	0.066	0.083	1.67	2.11
G	0.004	0.008	0.10	0.20
H	0.077	0.086	1.96	2.18
J	0.043	0.053	1.09	1.35
K	0.008	0.012	0.20	0.30
L	0.039	0.049	0.99	1.24

Packing Options

Part Number	Marking	Package	Weight/ Unit	Packing Mode	Base Quantity	Quantity	
						Reel	Box
HTM-xxxRP	—	MINIMELF	0.040g	Tape & Reel	5000	2500	—
HT-xxxRP	—	DO35	0.150g	Tape & Reel	5000	5000	—
HT-xxx	—	DO35	0.150g	Bulk	5000	—	5000
ST-xxxRP	STxxx	DO214	0.075g	Tape & Reel	2500	2500	—

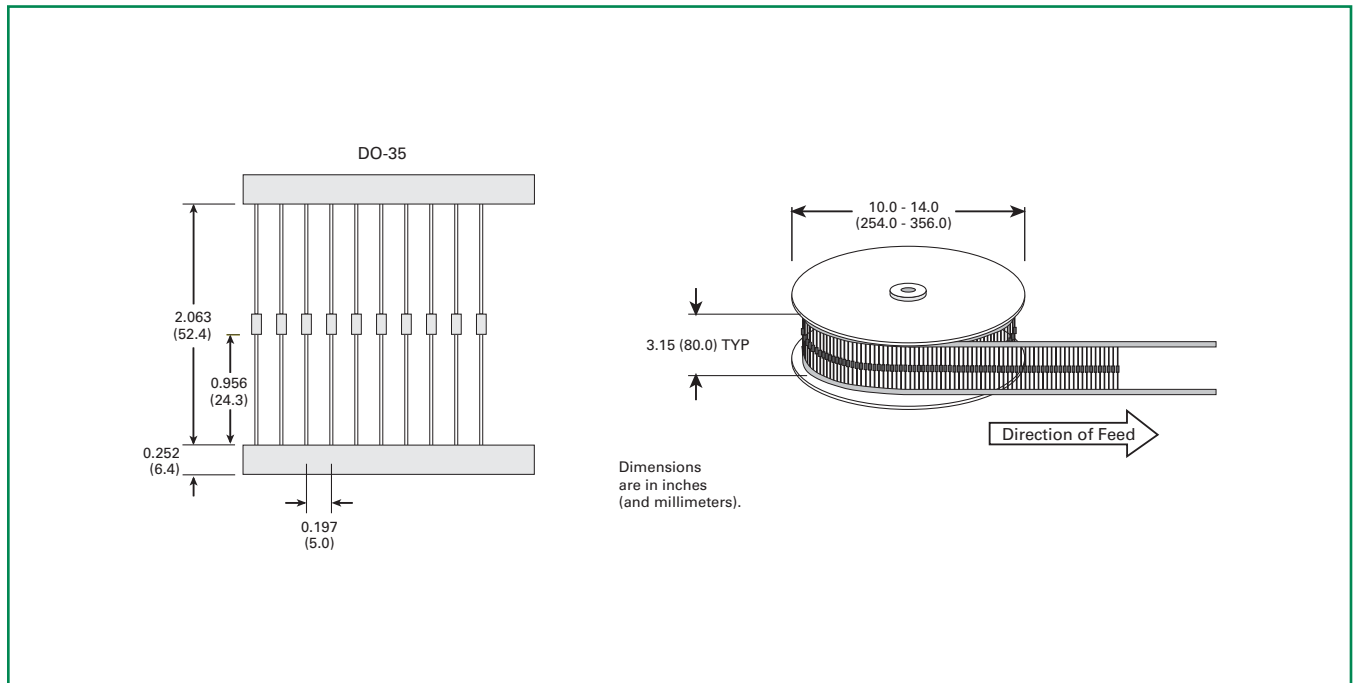
DO-214 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-1 Standards

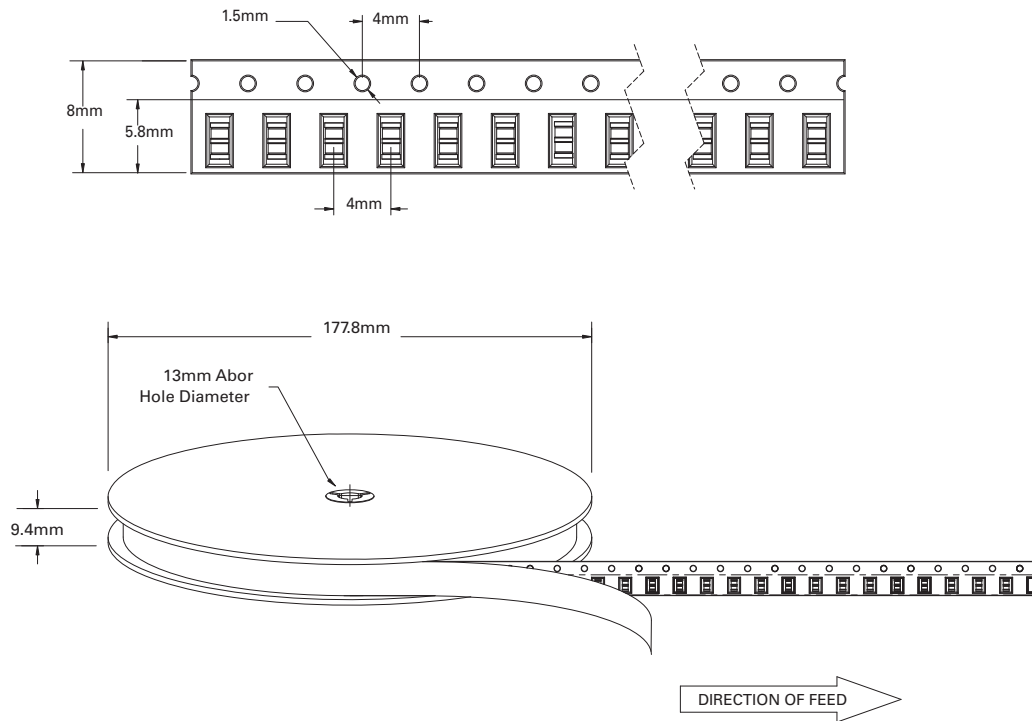


DO-35 Reel Pack (RP) Specifications

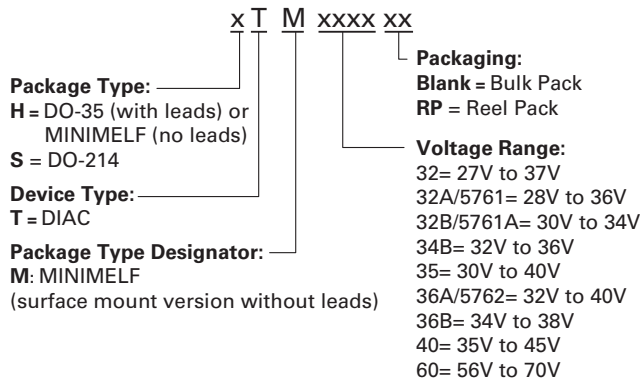
Meets all EIA-296 Standards



MINIMELF Reel Pack (RP) Specifications



Part Numbering System



Part Marking System

DO-35 & MINIMELF: No marking

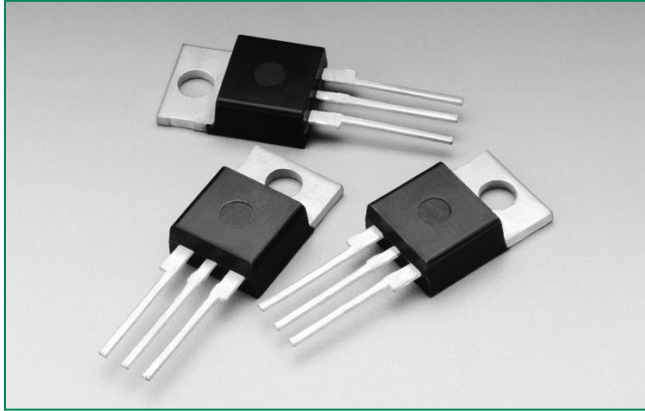
DO-214:




First Line: Part Number
Second Line: Date Code

RoHS

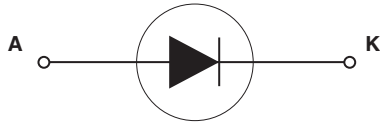
Dxx15L & Dxx20L & Dxx25L Series



Agency Approval

Agency	Agency File Number
	L Package : E71639

Schematic Symbol



Description

Silicon rectifiers that are excellent for DC phase control applications with motor loads.

Isolated mounting tab allows for use in circuits with common anode or common cathode connections.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 350 A

Applications

Typical applications are AC to DC solid-state switches for industrial power tools, exercise equipment, white goods, and commercial appliances.

Internally constructed isolated package is offered for ease of heat sinking with highest isolation voltage.

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	15 / 20 / 25	A
V_{RRM}	400 to 1000	V

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value			Unit
			Dxx15L	Dxx20L	Dxx25L	
$I_{F(RMS)}$	RMS forward current	Dxx15L: $T_C = 85^\circ\text{C}$	15	20	25	A
$I_{F(AV)}$	Average forward current	Dxx20L/Dxx25L: $T_C = 80^\circ\text{C}$	9.5	12.7	15.9	A
I_{FSM}	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$; $T_J(\text{initial}) = 25^\circ\text{C}$	188	255	300	A
		single half cycle; $f = 60\text{Hz}$; $T_J(\text{initial}) = 25^\circ\text{C}$	225	300	350	
I^2t	I^2t Value for fusing	$t_p = 8.3 \text{ ms}$	210	374	508	A^2s
T_{stg}	Storage temperature range		-40 to 150			$^\circ\text{C}$
T_J	Operating junction temperature range		-40 to 125			$^\circ\text{C}$

Note: xx = voltage

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test Conditions		Value	Unit
t_{rr}	Reverse-recovery Time	$I_F = 0.9A$, $I_R = 1.5A$	TYP.	4	μs

Static Characteristics

Symbol	Test Conditions				Value	Unit	
V _{FM}	15A Device I _T = 30A; t _p = 380μs			MAX.	1.6	V	
	20A Device I _T = 40A; t _p = 380μs						
	25A Device I _T = 50A; t _p = 380μs						
I _{RM}	V _{RRM}		T _J = 25°C	400-600V	MAX.	10	μA
				800-1000V		20	
			T _J = 100°C	400-800V		500	
				1000V		3000	
			T _J = 125°C	400-800V		1000	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)		Dxx15L	2.85
			Dxx20L	2.55
			Dxx25L	2.50

Note: xx = voltage

Figure 1: On-State Current vs. On-State Voltage (Typical)

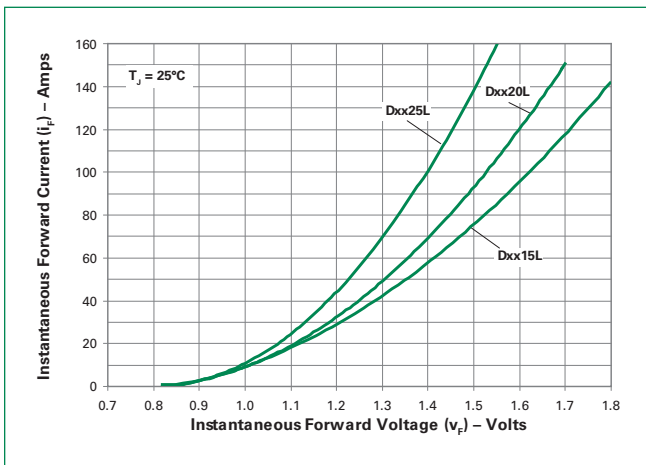


Figure 2: Power Dissipation vs. RMS On-State Current (Typical)

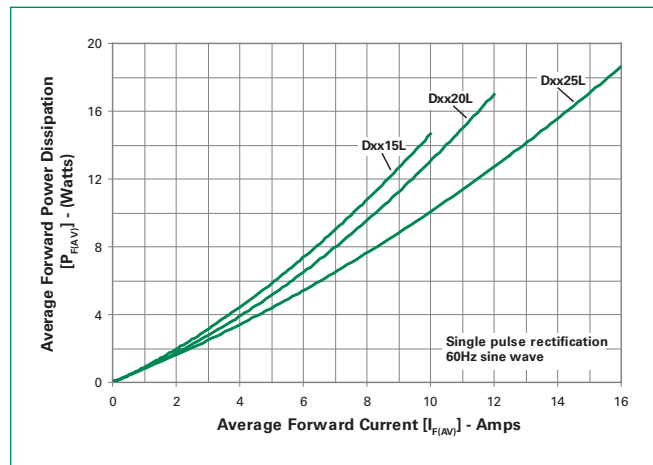


Figure 3: Maximum Allowable Case Temperature vs. Average On-State Current

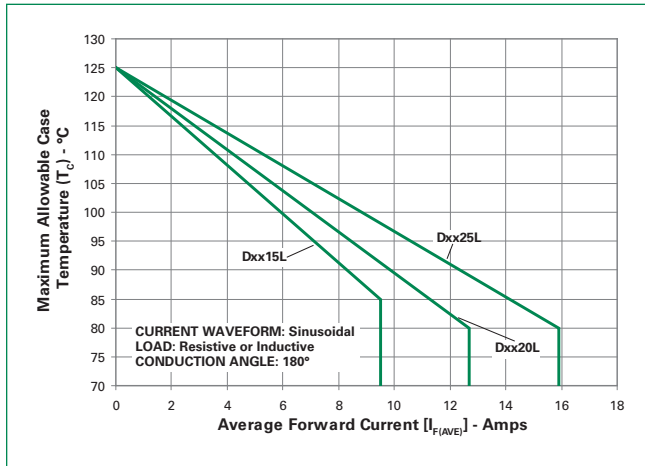
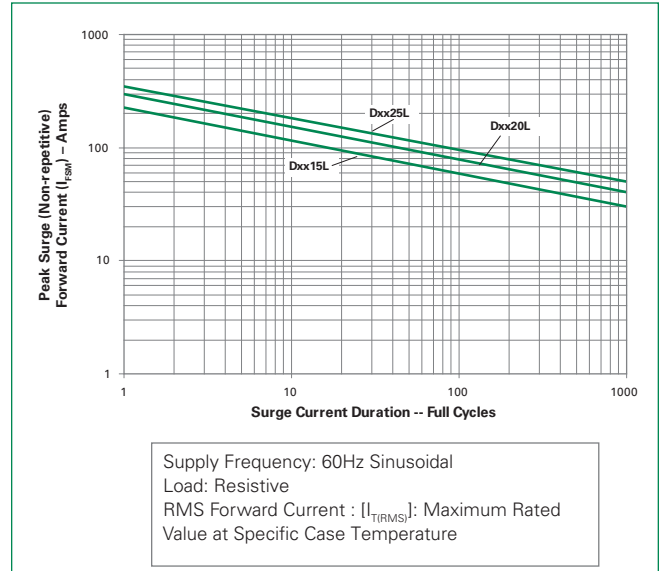
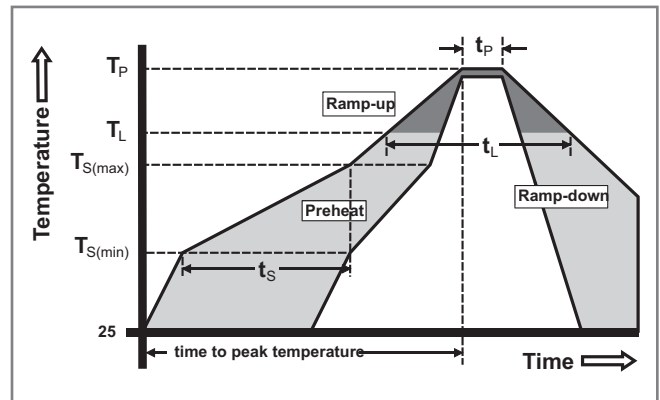


Figure 4: Surge Peak On-State Current vs. Number of Cycles



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260°C $\pm 0/-5$
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin Plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Lead Material	Copper Alloy

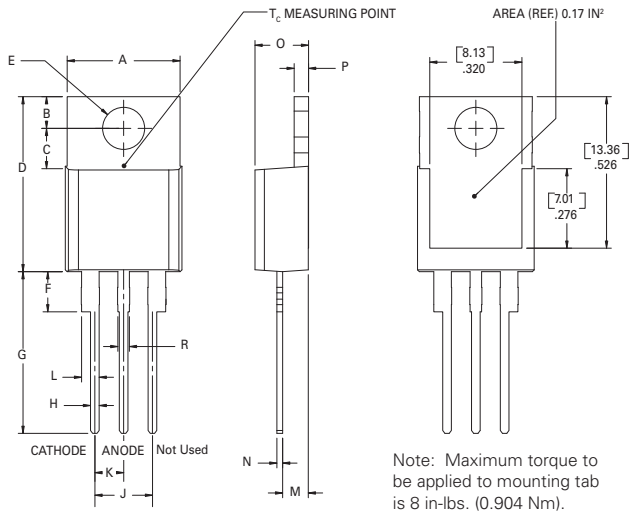
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the rectifier. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
High Temperature Voltage Blocking	MIL-STD-750: Method 1040, Condition A Rated V_{RRM} , 125°C, 1008 hours
Temperature Cycling	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
Biased Temperature & Humidity	EIA/JEDEC: JESD22-A101 320VDC, 85°C, 85%RH, 1008 hours
High Temp Storage	MIL-STD-750: Method 1031 150°C, 1008 hours
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
Resistance to Solder Heat	MIL-STD-750: Method 2031 260°C, 10 seconds
Solderability	ANSI/J-STD-002, Category 3, Test A
Lead Bend	MIL-STD-750: Method 2036, Condition E

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Product Selector

Part Number	Voltage				Type	Package
	400V	600V	800V	1000V		
Dxx15L	X	X	X	X	Rectifier	TO-220L
Dxx20L	X	X	X	X	Rectifier	TO-220L
Dxx25L	X	X	X	X	Rectifier	TO-220L

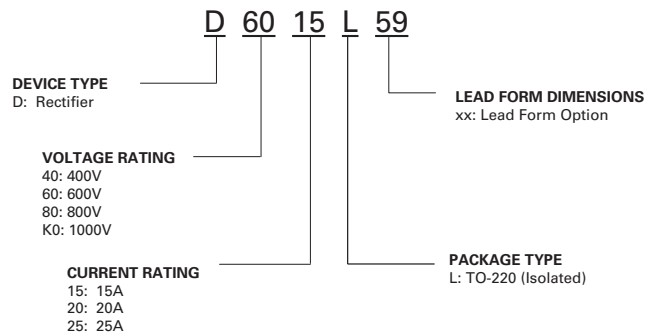
Note: xx = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Dxx15L	Dxx15L	2.2 g	Bulk	500
Dxx15LTP	Dxx15L	2.2 g	Tube	500
Dxx20L	Dxx20L	2.2 g	Bulk	500
Dxx20LTP	Dxx20L	2.2 g	Tube	500
Dxx25L	Dxx25L	2.2 g	Bulk	500
Dxx25LTP	Dxx25L	2.2 g	Tube	500

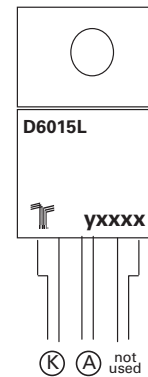
Note: xx = Voltage

Part Numbering System



Part Marking System

TO-220AB (L Package)



Lead Form Dimensions

The TO-218, TO-220AB, and TO-92 package configurations, because of their unique design, can be mounted in a variety of methods, depending upon heat sink requirements and circuit packaging methods. Any of the derived types shown in this section are available as standard parts direct from the factory. Custom package variations are available. Consult the factory for more information.

To designate lead form options, simply indicate the type number at the end of the Teccor standard part number.

Example: Q4008L465 (Signifies Type 65)

See "Description of Part Numbers" in the Product Selection Guide of this catalog for a complete description of Teccor part numbers.

Lead Bending Specifications

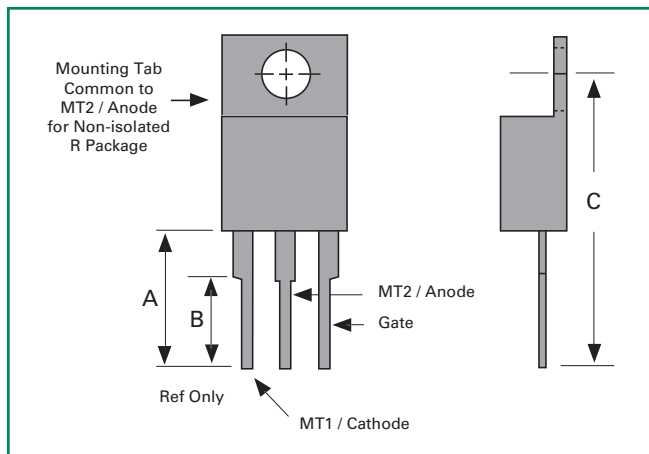
Leads may be bent easily and may be bent to any desired angle, provided that the bend is made at a minimum 0.063" (0.1 for TO-218) away from the package body with a minimum radius of 0.032". DO-15 device leads may be bent with a minimum radius of 0.050"; and DO-35 device leads may be bent with a minimum radius of 0.028". Leads should be held firmly between the package body and the bend, so that strain on the leads is not transmitted to the package body.

When bending leads in the plane of the leads (spreading), bend only the narrow part.

Sharp angle bends should be done only once, as repetitive bending will fatigue and break the leads.

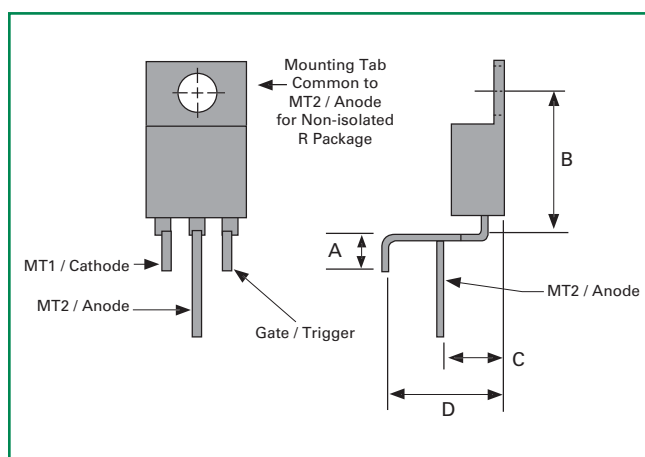
TO-220 Type 51 — R or L Package

Replaces RCA 6249



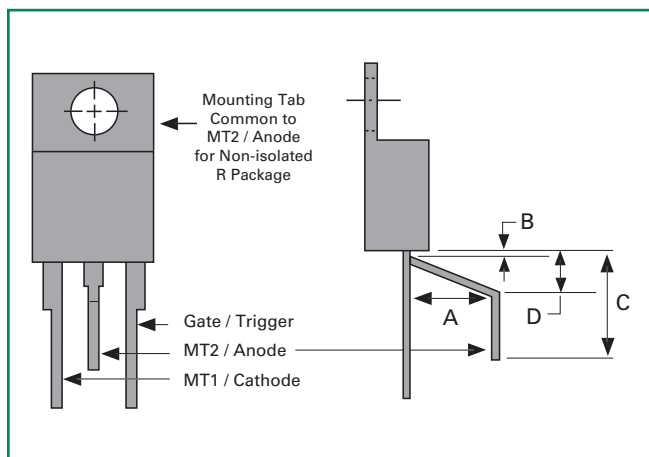
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.320	0.340	8.13	8.64
B	0.190		4.83	
C	0.795	0.850	20.19	21.59

TO-220 Type 53 — R or L Package



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.175		4.45	
B	0.542	0.582	13.77	14.78
C	0.167	0.207	4.24	5.26
D	0.355	0.395	9.02	10.03

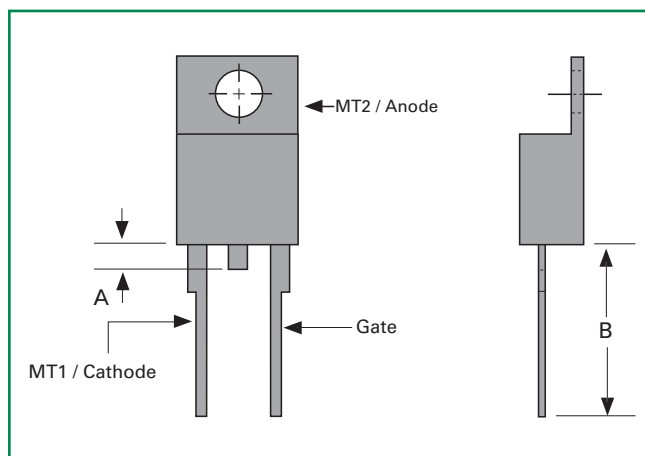
TO-220 Type 52 — R or L Package



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.169	0.189	4.29	4.80
B	0.040	0.060	1.02	1.52
C	0.250		6.35	
D	0.110	0.170	2.79	4.32

TO-220 Type 54 — R Package

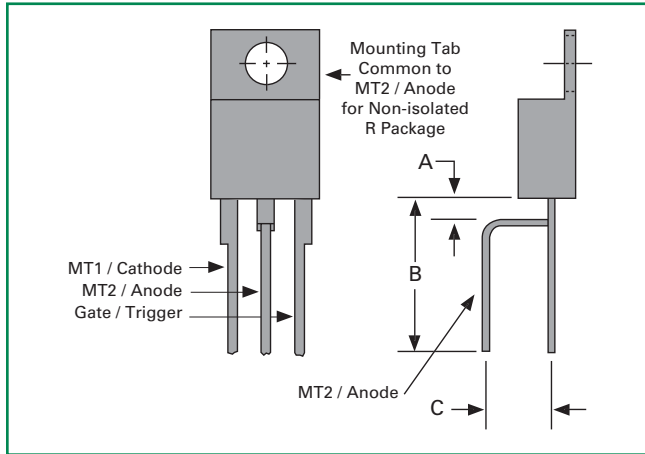
Replaces Motorola Form 4, G.E. Type 4, RCA 6206



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.070	1.02	1.78
B	0.500		12.70	

TO-220 Type 55 — R or L Package

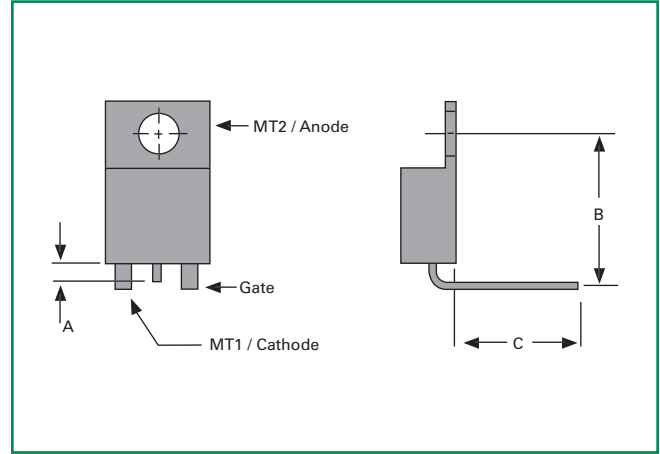
Replaces G.E. Type 5



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.065	0.095	1.65	2.41
B	0.353	0.433	8.97	11.00
C	0.115	0.130	2.92	3.30

TO-220 Type 57 — R Package

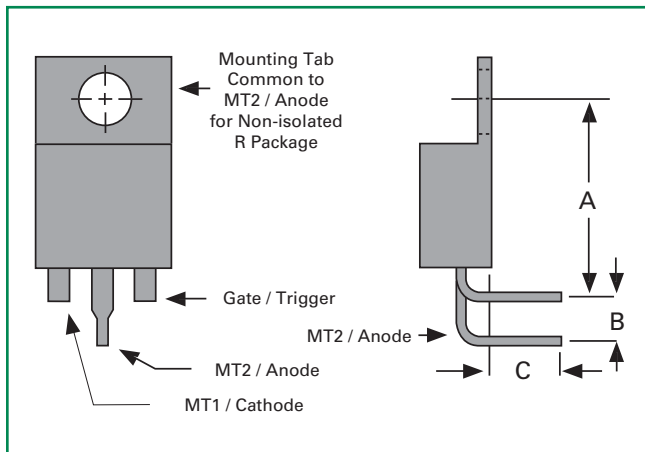
Similar to TO-66, Gate-Cathode Reversed



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.040	0.070	1.02	1.78
B	0.570	0.590	14.48	14.99
C	0.340	0.422	8.64	10.72

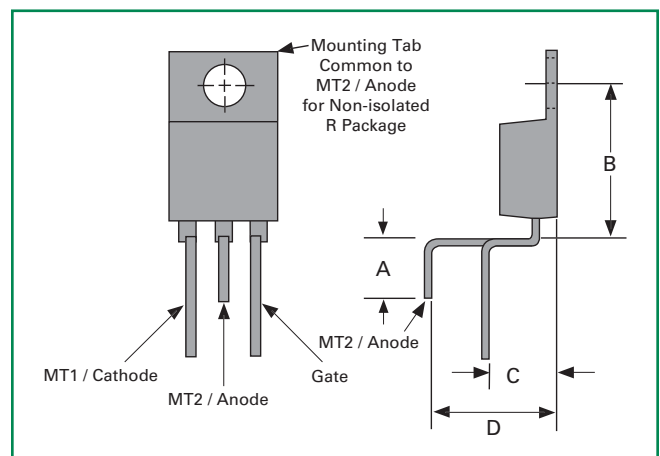
TO-220 Type 56 — R or L Package

Replaces G.E. Type 6, Motorola Lead Form 3, RCA 6221



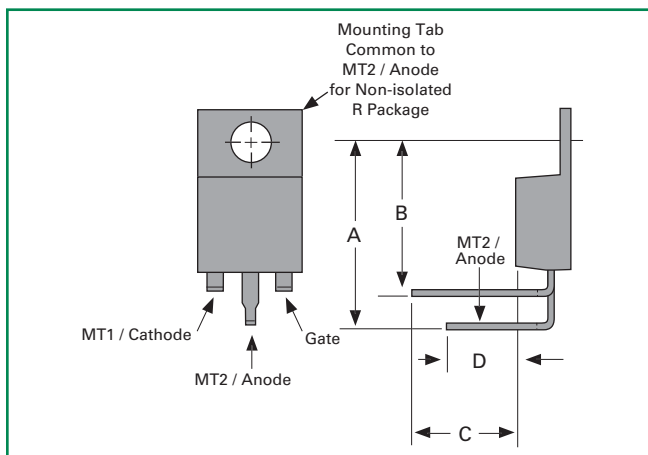
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.570	0.590	14.48	14.99
B	0.120	0.130	3.05	3.30
C	0.172	0.202	4.37	5.13

TO-220 Type 58 — R or L Package



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.175		4.45	
B	0.542	0.582	13.77	14.78
C	0.167	0.207	4.24	5.26
D	0.355	0.395	9.02	10.03

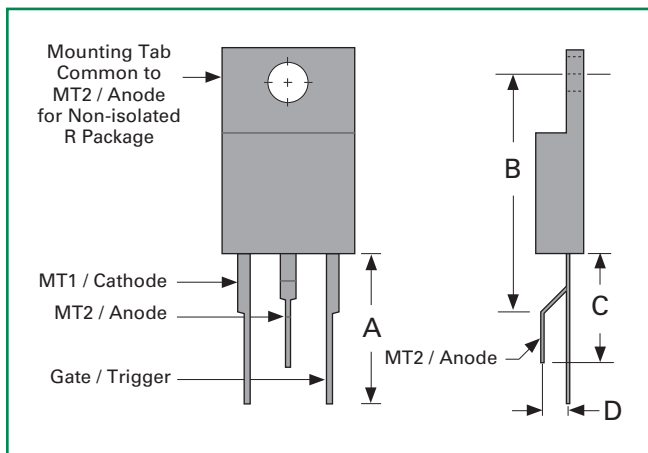
TO-220 Type 59 — R or L Package



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.685	0.725	17.40	18.42
B	0.558	0.598	14.17	15.19
C	0.375		9.53	
D	0.250		6.35	

TO-220 Type 65 — R or L Package

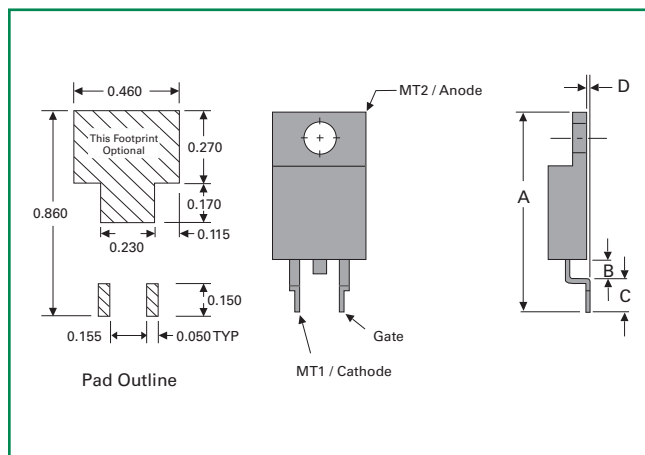
Replaces RCA 6210



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.550	0.580	12.70	14.27
B	0.820	0.260	14.73	15.75
C	0.530	0.570	7.62	
D	0.080	0.120	2.03	3.05

TO-220 Type 67 — R Package

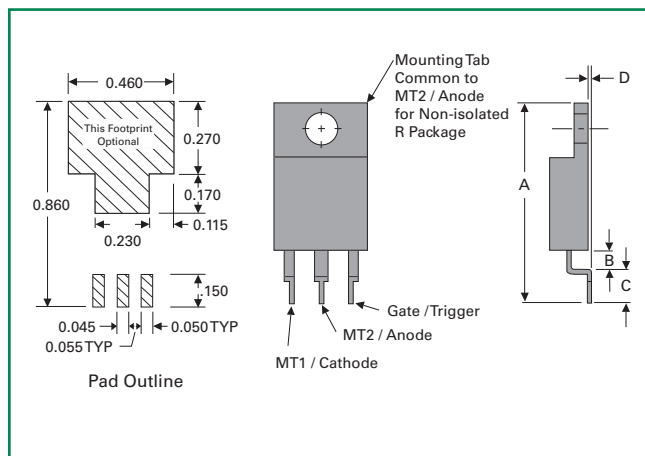
Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.780	0.850	19.05	21.59
B	0.080	0.100	2.03	2.54
C	0.110	0.130	2.79	3.30
D		0.013		0.33

TO-220 Type 68 — R or L Package

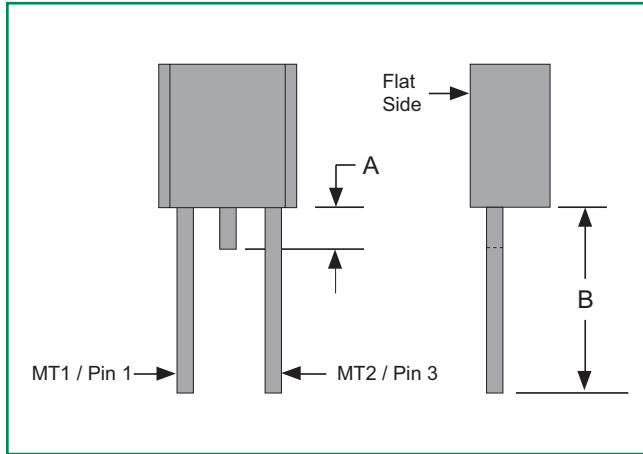
Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.780	0.850	19.05	21.59
B	0.080	0.100	2.03	2.54
C	0.110	0.130	2.79	3.30
D		0.013		0.33

TO-92 Type 70 — E Package

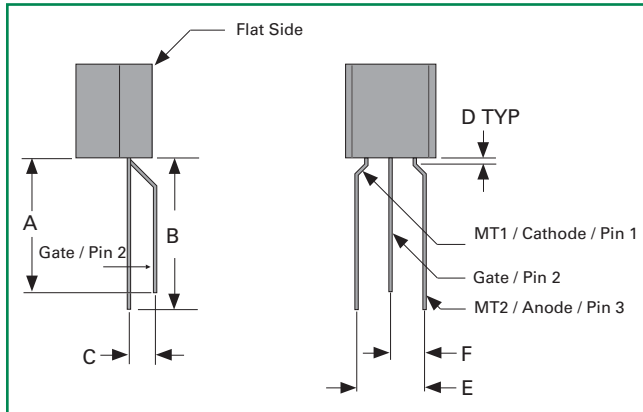
SIDAC Only



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A		0.060		1.52
B	0.50		12.7	

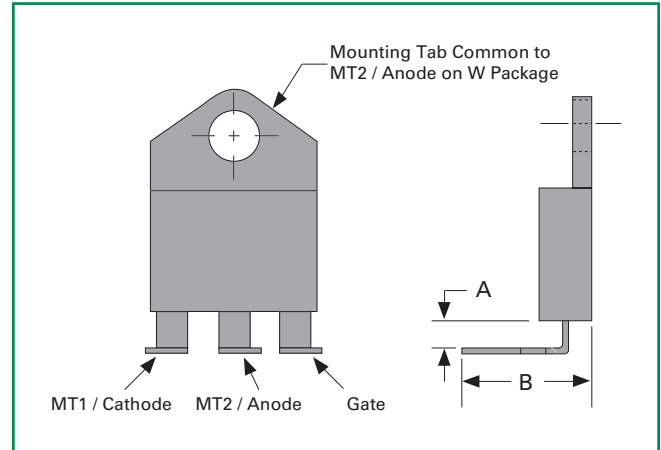
TO-92 Type 75 — E Package

Replaces TO-5 Pinout



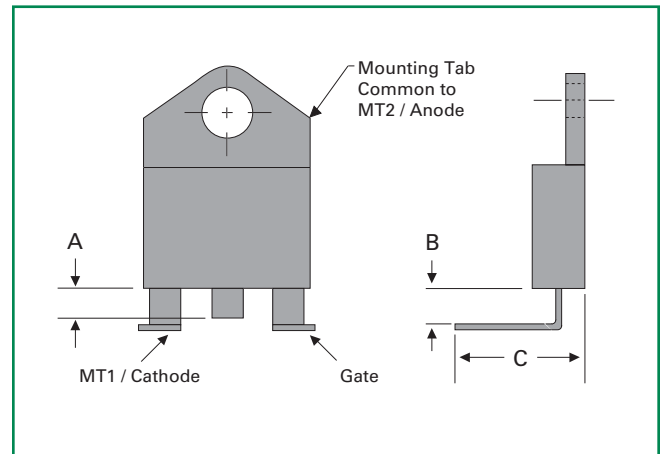
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.400		10.16	
B	0.500		12.70	
C	0.080	0.120	2.03	3.05
D	0.045	0.085	1.14	2.16
E	0.180	0.220	4.57	5.59
F	0.080	0.120	2.03	3.05

TO-218 Type 81 — K, M, J, or W Packages



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.080	0.120	2.03	3.05
B	0.580	0.640	14.73	16.26

TO-218 Type 82 — M and W Packages



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A		0.095		2.41
B	0.080	0.120	2.03	3.05
C	0.580	0.640	14.73	16.26

Fundamental Characteristics of Thyristors

Introduction

The Thyristor family of semiconductors consists of several very useful devices. The most widely used of this family are silicon controlled rectifiers (SCRs), Triacs, SIDACs, and DIACs. In many applications these devices perform key functions and are real assets in meeting environmental, speed, and reliability specifications which their electro-mechanical counterparts cannot fulfill.

This application note presents the basic fundamentals of SCR, Triac, SIDAC, and DIAC Thyristors so the user understands how they differ in characteristics and parameters from their electro-mechanical counterparts. Also, Thyristor terminology is defined.

SCR

Basic Operation

Figure AN1001.1 shows the simple block construction of an SCR.

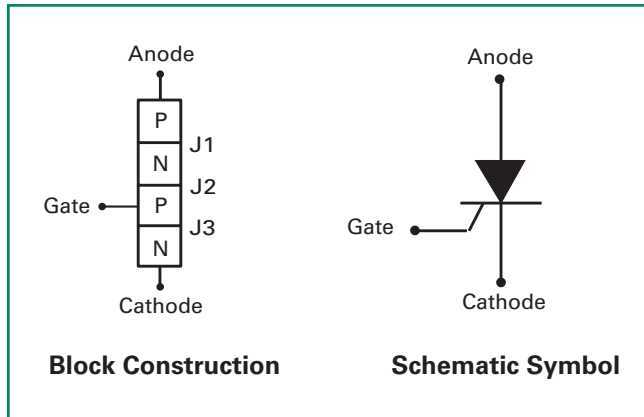


Figure AN1001.1 SCR Block Construction

The operation of a PNP device can best be visualized as a specially coupled pair of transistors as shown in Figure AN1001.2.

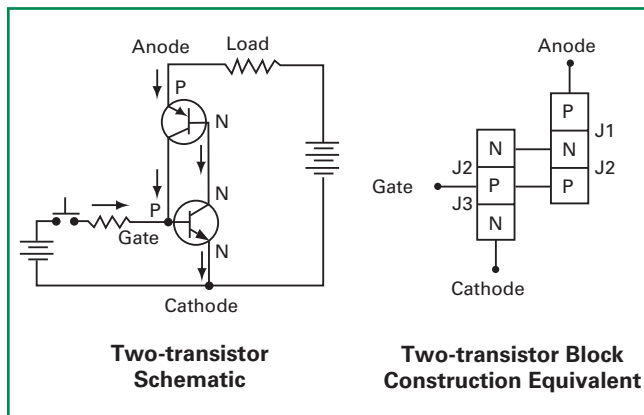


Figure AN1001.2 Coupled Pair of Transistors as a SCR

The connections between the two transistors trigger the occurrence of regenerative action when a proper gate signal is applied to the base of the NPN transistor. Normal leakage current is so low that the combined h_{FE} of the specially coupled two-transistor feedback amplifier is less than unity, thus keeping the circuit in an off-state condition. A momentary positive pulse applied to the gate biases the NPN transistor into conduction which, in turn, biases the PNP transistor into conduction. The effective h_{FE} momentarily becomes greater than unity so that the specially coupled transistors saturate. Once saturated, current through the transistors is enough to keep the combined h_{FE} greater than unity. The circuit remains "on" until it is "turned off" by reducing the anode-to-cathode current (I_T) so that the combined h_{FE} is less than unity and regeneration ceases. This threshold anode current is the holding current of the SCR.

Geometric Construction

Figure AN1001.3 shows cross-sectional views of an SCR chip and illustrations of current flow and junction biasing in both the blocking and triggering modes.

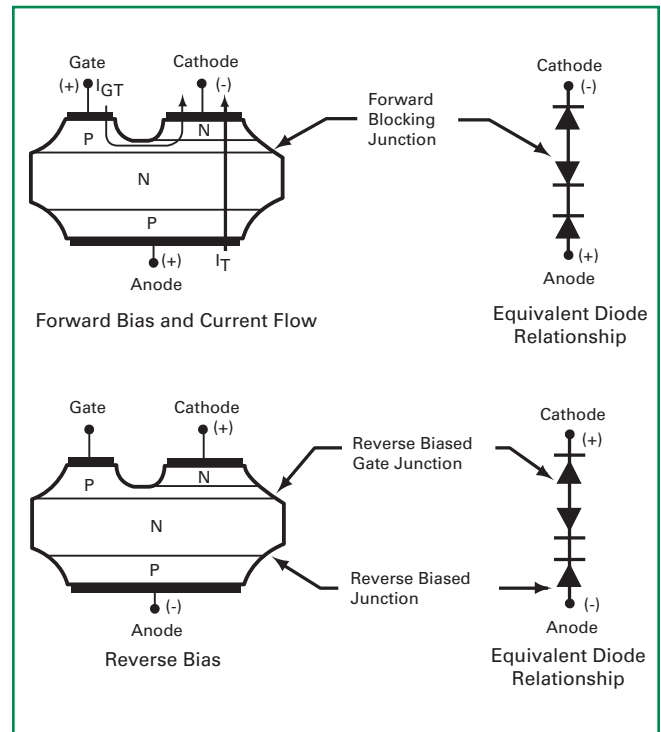


Figure AN1001.3 Cross-sectional View of SCR Chip

Triac

Basic Operation

Figure AN1001.4 shows the simple block construction of a Triac. Its primary function is to control power bilaterally in an AC circuit.

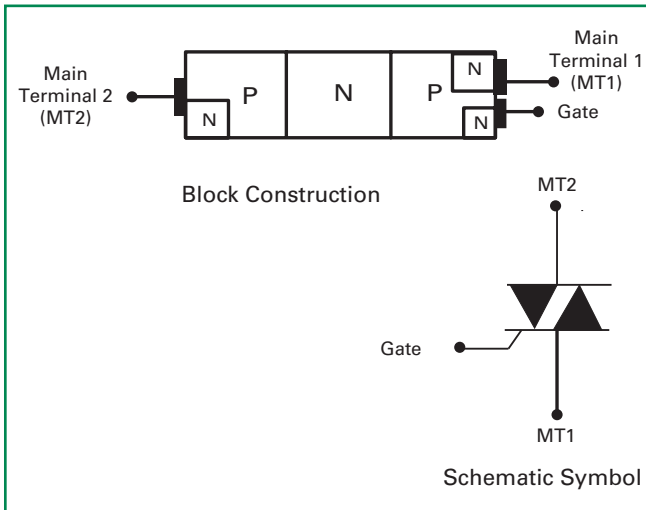


Figure AN1001.4 Triac Block Construction

Operation of a Triac can be related to two SCRs connected in parallel in opposite directions as shown in Figure AN1001.5.

Although the gates are shown separately for each SCR, a Triac has a single gate and can be triggered by either polarity.

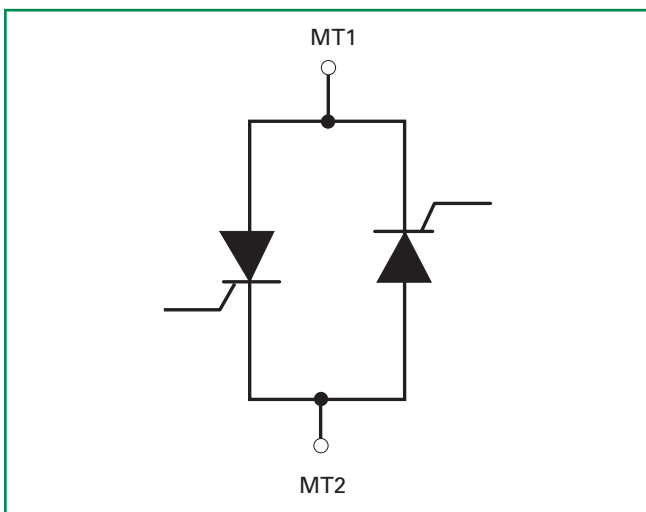


Figure AN1001.5 SCRs Connected as a Triac

Since a Triac operates in both directions, it behaves essentially the same in either direction as an SCR would behave in the forward direction (blocking or operating).

Geometric Construction

Figure AN1001.6 show simplified cross-sectional views of a Triac chip in various gating quadrants and blocking modes.

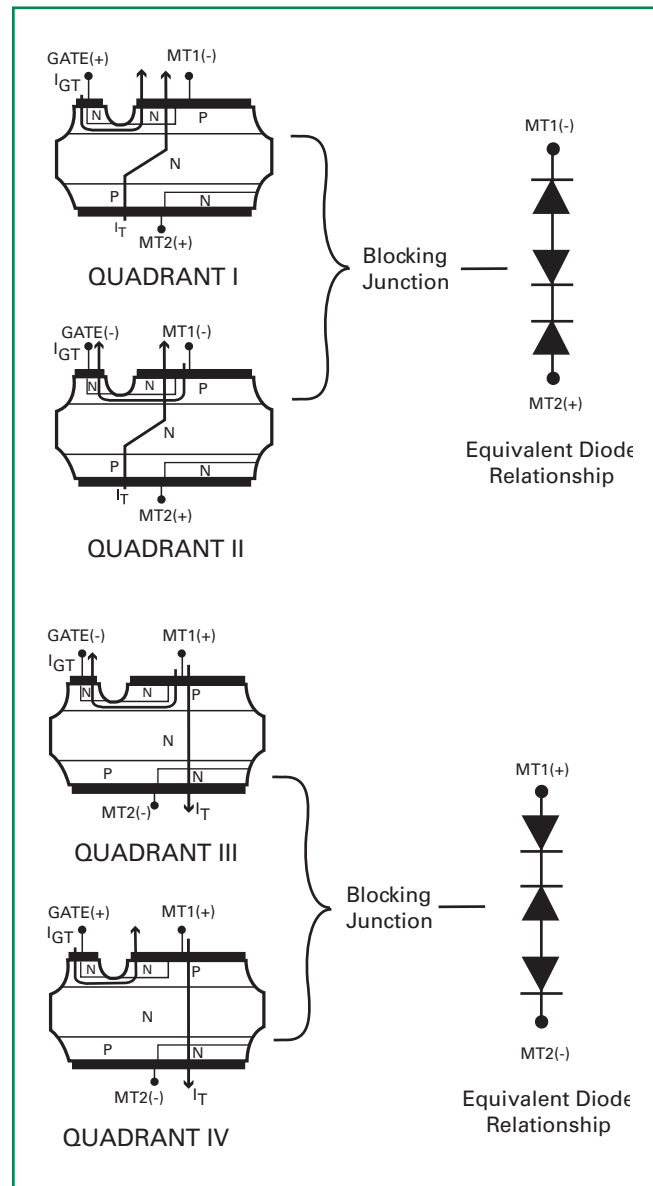


Figure AN1001.6 Simplified Cross-sectional of Triac Chip

SIDAC

Basic Operation

The SIDAC is a multi-layer silicon semiconductor switch. Figure AN1001.7 illustrates its equivalent block construction using two Shockley diodes connected inverse parallel. Figure AN1001.7 also shows the schematic symbol for the SIDAC.

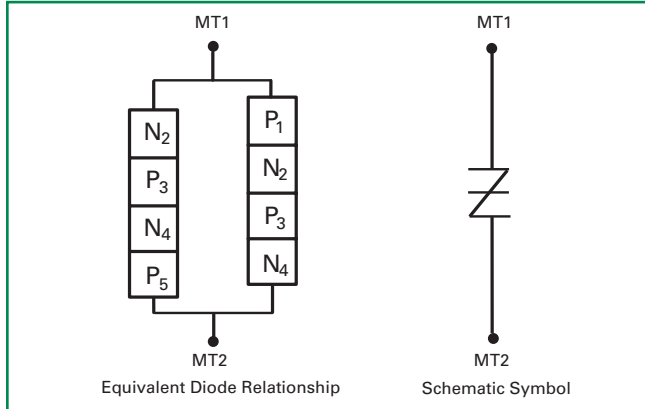


Figure AN1001.7 SIDAC Block Construction

The SIDAC operates as a bidirectional switch activated by voltage. In the off state, the SIDAC exhibits leakage currents (I_{DRM}) less than 5 μA . As applied voltage exceeds the SIDAC V_{BO} , the device begins to enter a negative resistance switching mode with characteristics similar to an avalanche diode. When supplied with enough current (I_S), the SIDAC switches to an on state, allowing high current to flow. When it switches to on state, the voltage across the device drops to less than 5 V, depending on magnitude of the current flow. When the SIDAC switches on and drops into regeneration, it remains on as long as holding current is less than maximum value (150 mA, typical value of 30 mA to 65 mA). The switching current (I_S) is very near the holding current (I_H) value. When the SIDAC switches, currents of 10 A to 100 A are easily developed by discharging small capacitor into primary or small, very high-voltage transformers for 10 μs to 20 μs .

The main application for SIDACs is ignition circuits or inexpensive high voltage power supplies.

Geometric Construction

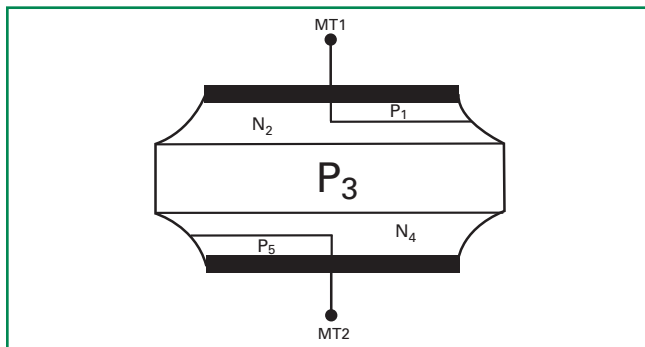


Figure AN1001.8 Cross-sectional View of a Bidirectional SIDAC Chip with Multi-layer Construction

DIAC

Basic Operation

The construction of a DIAC is similar to an open base NPN transistor. Figure AN1001.9 shows a simple block construction of a DIAC and its schematic symbol.

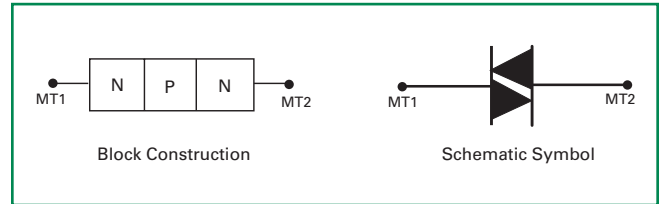


Figure AN1001.9 DIAC Block Construction

The bidirectional transistor-like structure exhibits a high-impedance blocking state up to a voltage breakover point (V_{BO}) above which the device enters a negative-resistance region. These basic DIAC characteristics produce a bidirectional pulsing oscillator in a resistor-capacitor AC circuit. Since the DIAC is a bidirectional device, it makes a good economical trigger for firing Triacs in phase control circuits such as light dimmers and motor speed controls. Figure AN1001.10 shows a simplified AC circuit using a DIAC and a Triac in a phase control application.

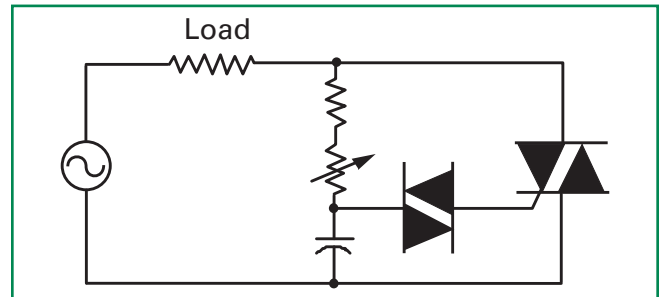


Figure AN1001.10 AC Phase Control Circuit

Geometric Construction

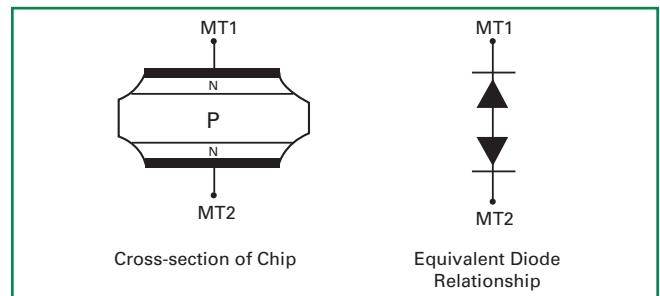


Figure AN1001.11 Cross-sectional View of DIAC Chip

Electrical Characteristic Curves of Thyristors

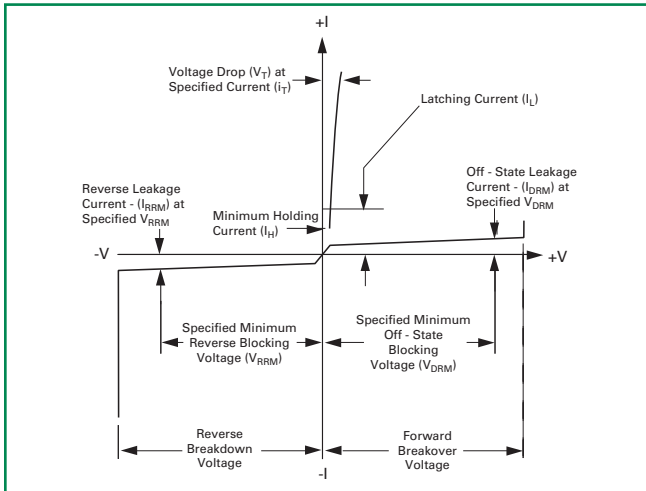


Figure AN1001.12 V-I Characteristics of SCR Device

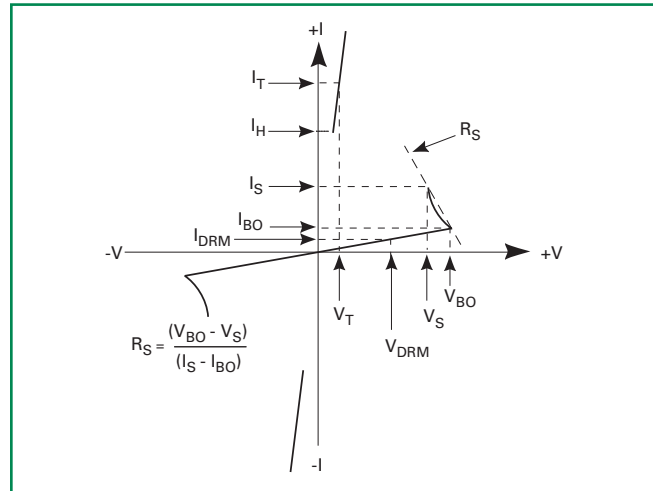


Figure AN1001.15 V-I Characteristics of a SIDAC Chip

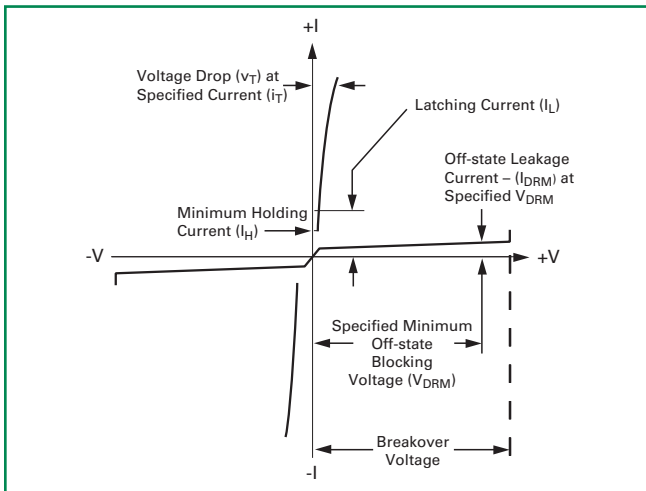


Figure AN1001.13 V-I Characteristics of Triac Device

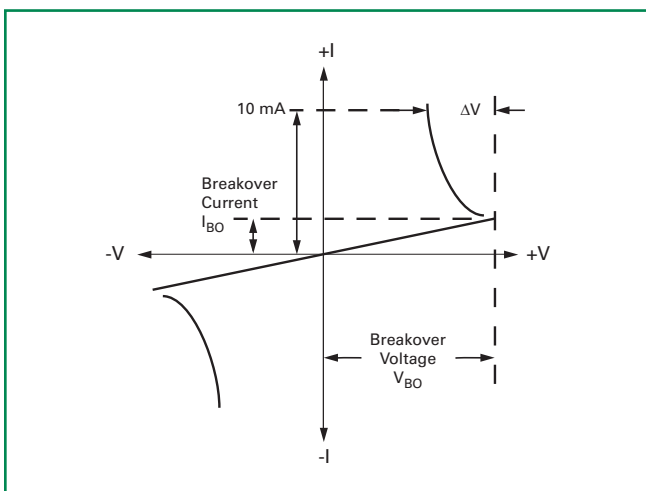


Figure AN1001.14 V-I Characteristics of Bilateral Trigger DIAC

Methods of Switching on Thyristors

Three general methods are available for switching Thyristors to on-state condition:

- Application of gate signal
- Static dv/dt turn-on
- Voltage breakover turn-on

Application Of Gate Signal

Gate signal must exceed I_{GT} and V_{GT} requirements of the Thyristor used. For an SCR (unilateral device), this signal must be positive with respect to the cathode polarity. A Triac (bilateral device) can be turned on with gate signal of either polarity; however, different polarities have different requirements of I_{GT} and V_{GT} which must be satisfied. Since DIACs and SIDACs do not have a gate, this method of turn-on is not applicable. In fact, the single major application of DIACs is to switch on Triacs.

Static dv/dt Turn-on

Static dv/dt turn-on comes from a fast-rising voltage applied across the anode and cathode terminals of an SCR or the main terminals of a Triac. Due to the nature of Thyristor construction, a small junction capacitor is formed across each PN junction. Figure AN1001.16 shows how typical internal capacitors are linked in gated Thyristors.

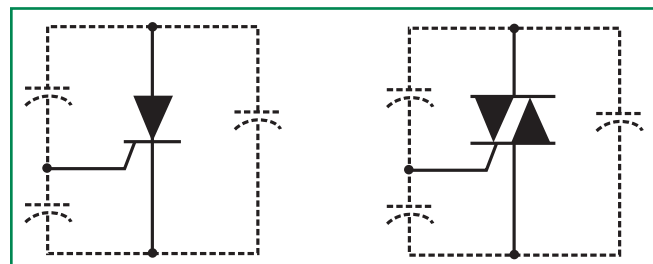


Figure AN1001.16 Internal Capacitors Linked in Gated Thyristors

When voltage is impressed suddenly across a PN junction, a charging current flows, equal to:

$$i = C \left(\frac{dv}{dt} \right)$$

When $C \left(\frac{dv}{dt} \right)$ becomes greater or equal to Thyristor I_{GT}

the Thyristor switches on. Normally, this type of turn-on does not damage the device, providing the surge current is limited.

Generally, Thyristor application circuits are designed with static dv/dt snubber networks if fast-rising voltages are anticipated.

Voltage Breakover Turn-on

This method is used to switch on SIDACs and DIACs. However, exceeding voltage breakover of SCRs and Triacs is definitely not recommended as a turn-on method.

In the case of SCRs and Triacs, leakage current increases until it exceeds the gate current required to turn on these gated Thyristors in a small localized point. When turn-on occurs by this method, localized heating in a small area may melt the silicon or damage the device if di/dt of the increasing current is not sufficiently limited.

DIACs used in typical phase control circuits are basically protected against excessive current at breakover as long as the firing capacitor is not excessively large. When DIACs are used in a zener function, current limiting is necessary.

SIDACs are typically pulse-firing, high-voltage transformers and are current limited by the transformer primary. The SIDAC should be operated so peak current amplitude, current duration, and di/dt limits are not exceeded.

Triac Gating Modes Of Operation

Triacs can be gated in four basic gating modes as shown in Figure AN1001.17.

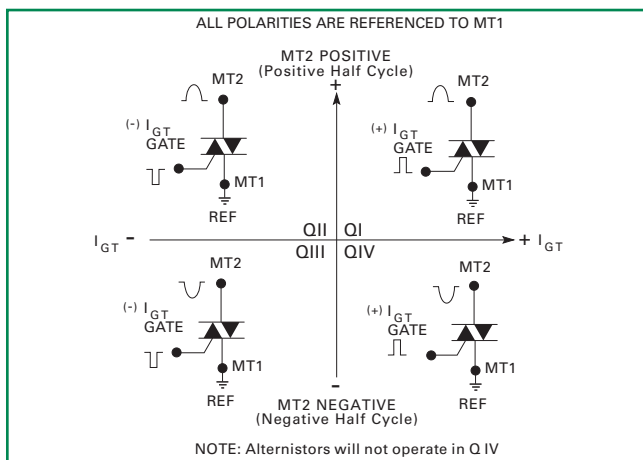


Figure AN1001.17 Gating Modes

The most common quadrants for Triac gating-on are Quadrants I and III, where the gate supply is synchronized with the main terminal supply (gate positive – MT2 positive, gate negative – MT2 negative). Gate sensitivity of Triacs is

most optimum in Quadrants I and III due to the inherent Thyristor chip construction. If Quadrants I and III cannot be used, the next best operating modes are Quadrants II and III where the gate has a negative polarity supply with an AC main terminal supply. Typically, Quadrant II is approximately equal in gate sensitivity to Quadrant I; however, latching current sensitivity in Quadrant II is lowest. Therefore, it is difficult for Triacs to latch on in Quadrant II when the main terminal current supply is very low in value.

Special consideration should be given to gating circuit design when Quadrants I and IV are used in actual application, because Quadrant IV has the lowest gate sensitivity of all four operating quadrants.

General Terminology

The following definitions of the most widely-used Thyristor terms, symbols, and definitions conform to existing EIA-JEDEC standards:

Breakover Point – Any point on the principal voltage-current characteristic for which the differential resistance is zero and where the principal voltage reaches a maximum value

Principal Current – Generic term for the current through the collector junction (the current through main terminal 1 and main terminal 2 of a Triac or anode and cathode of an SCR)

Principal Voltage – Voltage between the main terminals:

- (1) In the case of reverse blocking Thyristors, the principal voltage is called positive when the anode potential is higher than the cathode potential and negative when the anode potential is lower than the cathode potential.
- (2) For bidirectional Thyristors, the principal voltage is called positive when the potential of main terminal 2 is higher than the potential of main terminal 1.

Off State – Condition of the Thyristor corresponding to the high-resistance, low-current portion of the principal voltage-current characteristic between the origin and the breakover point(s) in the switching quadrant(s)

On State – Condition of the Thyristor corresponding to the low-resistance, low-voltage portion of the principal voltage-current characteristic in the switching quadrant(s).

Specific Terminology

Average Gate Power Dissipation ($P_{G(AV)}$) – Value of gate power which may be dissipated between the gate and main terminal 1 (or cathode) averaged over a full cycle

Breakover Current (I_{BO}) – Principal current at the breakover point

Breakover Voltage (V_{BO}) – Principal voltage at the breakover point

Circuit-commutated Turn-off Time (t_q) – Time interval between the instant when the principal current has decreased to zero after external switching of the principal voltage circuit and the instant when the Thyristor is capable of supporting a specified principal voltage without turning on

Critical Rate-of-rise of Commutation Voltage of a Triac (Commutating dv/dt) – Minimum value of the rate-of-rise of principal voltage which will cause switching from the off state to the on state immediately following on-state current conduction in the opposite quadrant

Critical Rate-of-rise of Off-state Voltage or Static dv/dt (dv/dt) – Minimum value of the rate-of-rise of principal voltage which will cause switching from the off state to the on state

Critical Rate-of-rise of On-state Current (di/dt) – Maximum value of the rate-of-rise of on-state current that a Thyristor can withstand without harmful effect

Gate-controlled Turn-on Time (t_{gt}) – Time interval between a specified point at the beginning of the gate pulse and the instant when the principal voltage (current) has dropped to a specified low value (or risen to a specified high value) during switching of a Thyristor from off state to the on state by a gate pulse.

Gate Trigger Current (I_{GT}) – Minimum gate current required to maintain the Thyristor in the on state

Gate Trigger Voltage (V_{GT}) – Gate voltage required to produce the gate trigger current

Holding Current (I_H) – Minimum principal current required to maintain the Thyristor in the on state

Latching Current (I_L) – Minimum principal current required to maintain the Thyristor in the on state immediately after the switching from off state to on state has occurred and the triggering signal has been removed

On-state Current (I_T) – Principal current when the Thyristor is in the on state

On-state Voltage (V_T) – Principal voltage when the Thyristor is in the on state

Peak Gate Power Dissipation (P_{GM}) – Maximum power which may be dissipated between the gate and main terminal 1 (or cathode) for a specified time duration

Repetitive Peak Off-state Current (I_{DRM}) – Maximum instantaneous value of the off-state current that results from the application of repetitive peak off-state voltage

Repetitive Peak Off-state Voltage (V_{DRM}) – Maximum instantaneous value of the off-state voltage which occurs across a Thyristor, including all repetitive transient voltages and excluding all non-repetitive transient voltages

Repetitive Peak Reverse Current of an SCR (I_{RRM}) – Maximum instantaneous value of the reverse current resulting from the application of repetitive peak reverse voltage

Repetitive Peak Reverse Voltage of an SCR (V_{RRM}) – Maximum instantaneous value of the reverse voltage which occurs across the Thyristor, including all repetitive transient voltages and excluding all non-repetitive transient voltages

Surge (Non-repetitive) On-state Current (I_{TSM}) – On-state current of short-time duration and specified waveshape

Thermal Resistance, Junction to Ambient ($R_{\theta JA}$) – Temperature difference between the Thyristor junction and ambient divided by the power dissipation causing the temperature difference under conditions of thermal equilibrium

Note: Ambient is the point at which temperature does not change as the result of dissipation.

Thermal Resistance, Junction to Case ($R_{\theta JC}$) – Temperature difference between the Thyristor junction and the Thyristor case divided by the power dissipation causing the temperature difference under conditions of thermal equilibrium

Gating, Latching, and Holding of SCRs and Triacs

Introduction

Gating, latching, and holding currents of Thyristors are some of the most important parameters. These parameters and their interrelationship determine whether the SCRs and Triacs will function properly in various circuit applications.

This application note describes how the SCR and Triac parameters are related. This knowledge helps users select best operating modes for various circuit applications.

Gating of SCRs and Triacs

Three general methods are available to switch Thyristors to on-state condition:

- Applying proper gate signal
- Exceeding Thyristor static dv/dt characteristics
- Exceeding voltage breakover point

This application note examines only the application of proper gate signal. Gate signal must exceed the I_{GT} and V_{GT} requirements of the Thyristor being used. I_{GT} (gate trigger current) is the minimum gate current required to switch a Thyristor from the off state to the on state. V_{GT} (gate trigger voltage) is the voltage required to produce the gate trigger current.

SCRs (unilateral devices) require a positive gate signal with respect to the cathode polarity. Figure AN1002.1 shows the current flow in a cross-sectional view of the SCR chip.

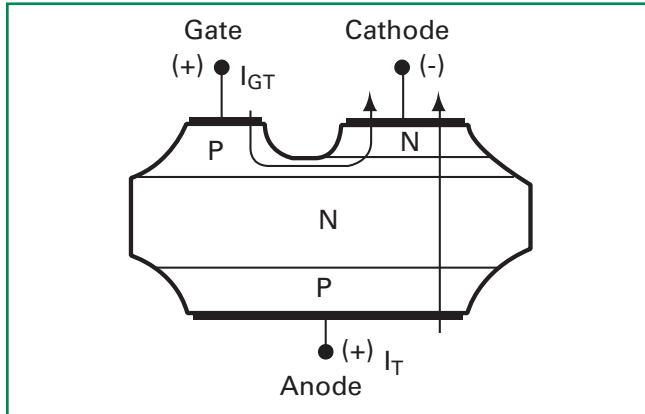


Figure AN1002.1 SCR Current Flow

In order for the SCR to latch on, the anode-to-cathode current (I_T) must exceed the latching current (I_L) requirement. Once latched on, the SCR remains on until it is turned off when anode-to-cathode current drops below holding current (I_H) requirement.

Triacs (bilateral devices) can be gated on with a gate signal of either polarity with respect to the MT1 terminal; however, different polarities have different requirements of I_{GT} and V_{GT} . Figure AN1002.2 illustrates current flow through the Triac chip in various gating modes.

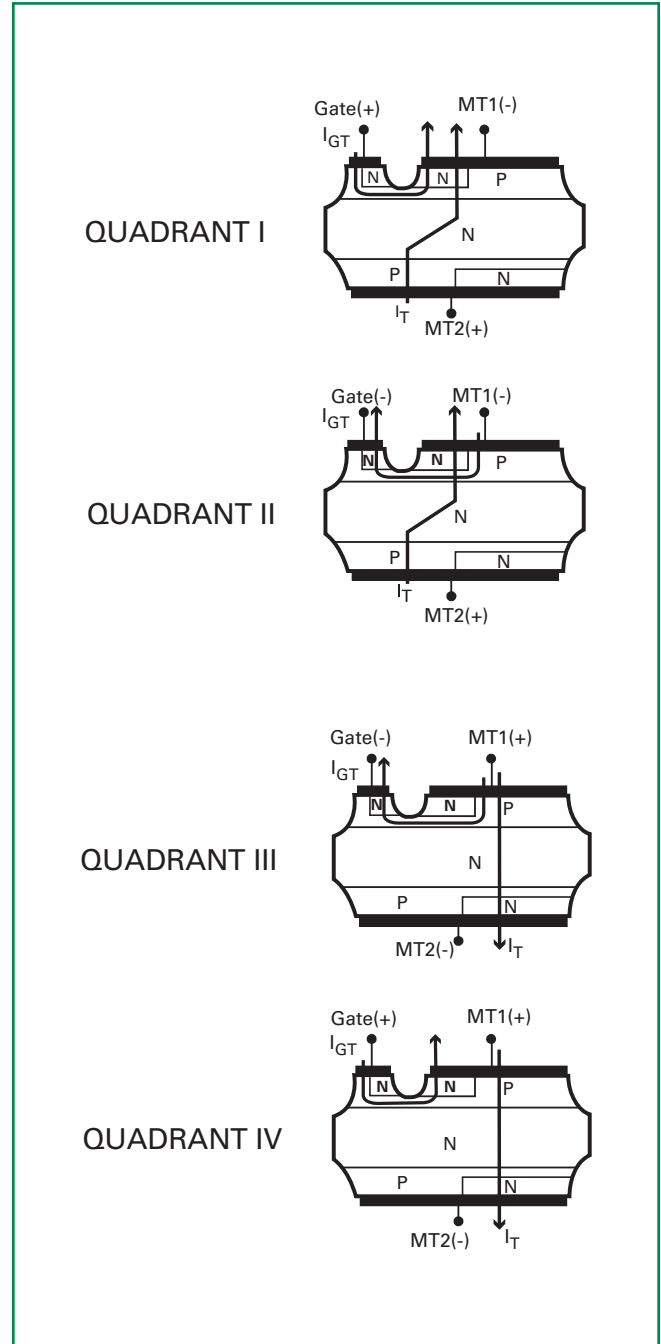


Figure AN1002.2 Triac Current Flow (Four Operating Modes)

Triacs can be gated on in one of four basic gating modes as shown in Figure AN1002.3. The most common quadrants for gating on Triacs are Quadrants I and III, where the gate supply is synchronized with the main terminal supply (gate positive – MT2 positive, gate negative – MT2 negative). Optimum Triac gate sensitivity is achieved when operating in Quadrants I and III due to the inherent Thyristor chip construction. If Quadrants I and III cannot be used, the next best operating modes are Quadrants II and III where the gate supply has a negative polarity with an AC main terminal supply. Typically, Quadrant II is approximately equal in gate sensitivity to Quadrant I; however, latching current sensitivity in Quadrant II is lowest. Therefore, it is difficult for Triacs to latch on in Quadrant II when the main terminal current supply is very low in value.

Special consideration should be given to gating circuit design when Quadrants I and IV are used in actual application, because Quadrant IV has the lowest gate sensitivity of all four operating quadrants.

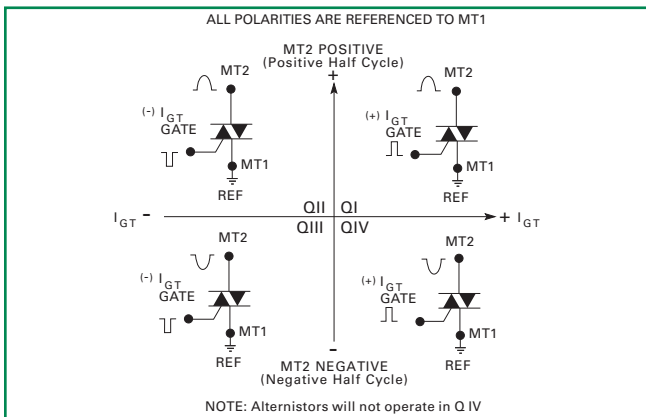


Figure AN1002.3 Definition of Operating Quadrants in Triacs

The following table shows the relationships between different gating modes in current required to gate on Triacs.

Type	Typical Ratio of $\frac{I_{GT}(\text{in given Quadrant})}{I_{GT}(\text{Quadrant 1})}$ at 25°C			
	Operating Mode			
	Quadrant I	Quadrant II	Quadrant III	Quadrant IV
4 A Triac	1	1.6	2.5	2.7
10 A Triac	1	1.5	1.4	3.1

Example of 4 A Triac:

$$\begin{aligned} \text{If } I_{GT(I)} &= 10 \text{ mA, then} \\ I_{GT(II)} &= 16 \text{ mA} \\ I_{GT(III)} &= 25 \text{ mA} \\ I_{GT(IV)} &= 27 \text{ mA} \end{aligned}$$

Gate trigger current is temperature-dependent as shown in Figure AN1002.4. Thyristors become less sensitive with decreasing temperature and more sensitive with increasing temperature.

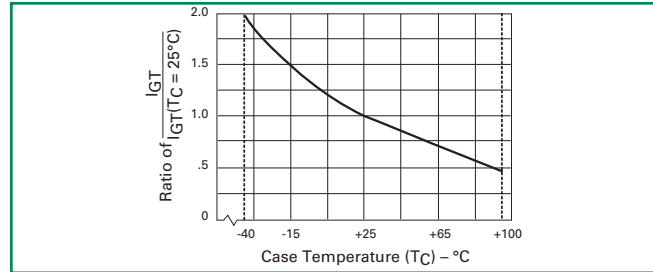


Figure AN1002.4 Typical DC Gate Trigger Current versus Case Temperature

For applications where low temperatures are expected, gate current supply should be increased to at least two to eight times the gate trigger current requirements at 25 °C. The actual factor varies by Thyristor type and the environmental temperature.

Example of a 10 A Triac:

$$\begin{aligned} \text{If } I_{GT(I)} &= 10 \text{ mA at } 25^\circ\text{C, then} \\ I_{GT(I)} &= 20 \text{ mA at } -40^\circ\text{C} \end{aligned}$$

In applications where high di/dt, high surge, and fast turn-on are expected, gate drive current should be steep rising (1 μs rise time) and at least twice rated I_{GT} or higher with minimum 3 μs pulse duration. However, if gate drive current magnitude is very high, then duration may have to be limited to keep from overstressing (exceeding the power dissipation limit of) gate junction.

Latching Current of SCRs and Triacs

Latching current (I_L) is the minimum principal current required to maintain the Thyristor in the on state immediately after the switching from off state to on state has occurred and the triggering signal has been removed. Latching current can best be understood by relating to the “pick-up” or “pull-in” level of a mechanical relay. Figure AN1002.5 and Figure AN1002.6 illustrate typical Thyristor latching phenomenon.

In the illustrations in Figure AN1002.5, the Thyristor does not stay on after gate drive is removed due to insufficient available principal current (which is lower than the latching current requirement).

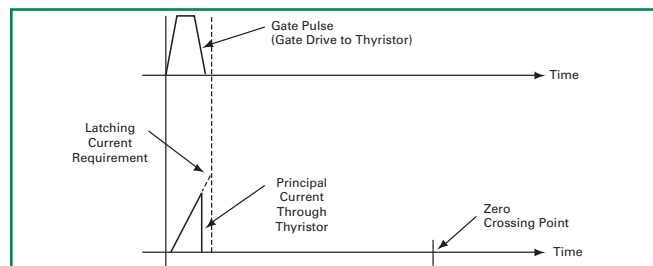


Figure AN1002.5 Latching Characteristic of Thyristor (Device Not Latched)

In the illustration in Figure AN1002.6 the device stays on for the remainder of the half cycle until the principal current falls below the holding current level. Figure AN1002.5 shows the characteristics of the same device if gate drive is removed or shortened before latching current requirement has been met.

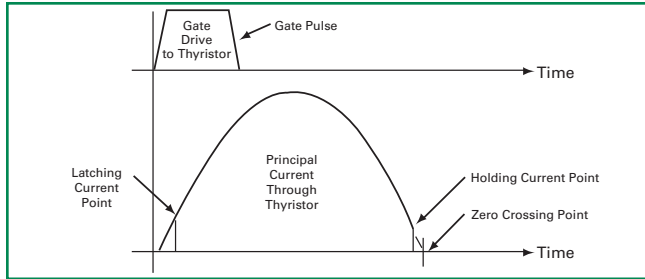


Figure AN1002.6 Latching and Holding Characteristics of Thyristor

Similar to gating, latching current requirements for Triacs are different for each operating mode (quadrant). Definitions of latching modes (quadrants) are the same as gating modes. Therefore, definitions shown in Figure AN1002.2 and Figure AN1002.3 can be used to describe latching modes (quadrants) as well. The following table shows how different latching modes (quadrants) relate to each other. As previously stated, Quadrant II has the lowest latching current sensitivity of all four operating quadrants.

Type	Typical Ratio of $\frac{I_L(\text{in given Quadrant})}{I_L(\text{Quadrant I})}$ at 25°C			
	Operating Mode			
	Quadrant I	Quadrant II	Quadrant III	Quadrant IV
4 A Triac	1	4	1.2	1.1
10 A Triac	1	4	1.1	1

Example of a 4 Amp Triac:

$$\begin{aligned} \text{If } I_L(\text{I}) &= 10 \text{ mA, then} \\ I_L(\text{II}) &= 40 \text{ mA} \\ I_L(\text{III}) &= 12 \text{ mA} \\ I_L(\text{IV}) &= 11 \text{ mA} \end{aligned}$$

Latching current has even somewhat greater temperature dependence compared to the DC gate trigger current. Applications with low temperature requirements should have sufficient principal current (anode current) available to ensure Thyristor latch-on.

Two key test conditions on latching current specifications are gate drive and available principal (anode) current durations. Shortening the gate drive duration can result in higher latching current values.

Holding Current of SCRs and Triacs

Holding current (I_H) is the minimum principal current required to maintain the Thyristor in the on state. Holding current can best be understood by relating it to the “drop-out” or “must release” level of a mechanical relay. Figure AN1002.6 shows the sequences of gate, latching, and holding currents. Holding current will always be less than latching. However, the more sensitive the device, the closer the holding current value approaches its latching current value.

Holding current is independent of gating and latching, but the device must be fully latched on before a holding current limit can be determined.

Holding current modes of the Thyristor are strictly related to the voltage polarity across the main terminals. The following table illustrates how the positive and negative holding current modes of Triacs relate to each other.

Type	Typical Triac Holding Current Ratio	
	Operating Mode	
	$I_H(+)$	$I_H(-)$
4 A Triac	1	1.1
10 A Triac	1	1.3

Example of a 10 A Triac:

$$\begin{aligned} \text{If } I_H(+) &= 10 \text{ mA, then} \\ I_H(-) &= 13 \text{ mA} \end{aligned}$$

Holding current is also temperature-dependent like gating and latching shown in Figure AN1002.7. The initial on-state current is 200 mA to ensure that the Thyristor is fully latched on prior to holding current measurement. Again, applications with low temperature requirements should have sufficient principal (anode) current available to maintain the Thyristor in the on-state condition.

Both minimum and maximum holding current specifications may be important, depending on application. Maximum holding current must be considered if the Thyristor is to stay in conduction at low principal (anode) current; the minimum holding current must be considered if the device is expected to turn off at a low principal (anode) current.

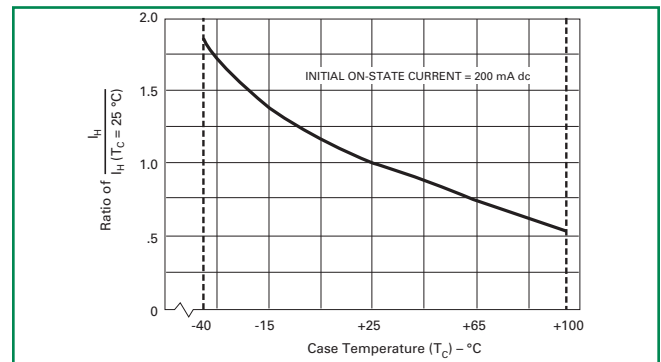


Figure AN1002.7 Typical DC Holding Current vs Case Temperatures

Example of a 10 A Triac:

$$\begin{aligned} \text{If } I_H(+) &= 10 \text{ mA at } 25^\circ\text{C, then} \\ I_H(+) &\approx 7.5 \text{ mA at } 65^\circ\text{C} \end{aligned}$$

Relationship of Gating, Latching, and Holding Currents

Although gating, latching, and holding currents are independent of each other in some ways, the parameter values are related. If gating is very sensitive, latching and holding will also be very sensitive and vice versa. One way to obtain a sensitive gate and not-so-sensitive latching-holding characteristic is to have an “amplified gate” as shown in Figure AN1002.8.

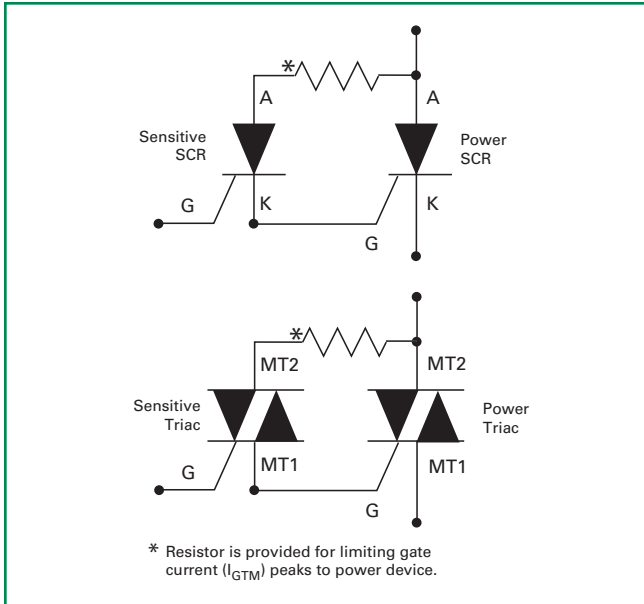


Figure AN1002.8 "Amplified Gate" Thyristor Circuit

The following table and Figure AN1002.9 show the relationship of gating, latching, and holding of a 4 A device.

Typical 4 A Triac Gating, Latching, and Holding Relationship				
Parameter	Quadrants or Operating Mode			
	Quadrant I	Quadrant II	Quadrant III	Quadrant IV
I_{GT} (mA)	10	17	18	27
I_L (mA)	12	48	12	13
I_H (mA)	10	10	12	12

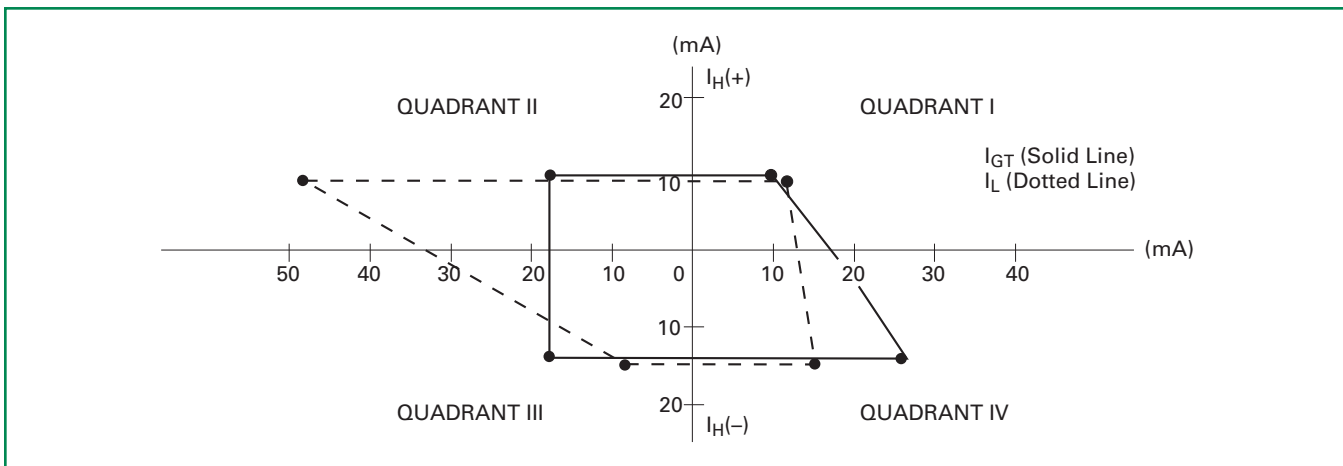


Figure AN1002.9 Typical Gating, Latching, and Holding Relationships of 4 A Triac at 25 °C

The relationships of gating, latching, and holding for several device types are shown in the following table. For convenience all ratios are referenced to Quadrant I gating.

Typical Ratio of Gating, Latching, and Holding Current at 25 °C									
Devices	Ratio								
	$\frac{I_{GT(III)}}{I_{GT(I)}}$	$\frac{I_{GT(III)}}{I_{GT(I)}}$	$\frac{I_{GT(IV)}}{I_{GT(I)}}$	$\frac{I_L(I)}{I_{GT(I)}}$	$\frac{I_L(II)}{I_{GT(I)}}$	$\frac{I_L(III)}{I_{GT(I)}}$	$\frac{I_L(IV)}{I_{GT(I)}}$	$\frac{I_H(+)}{I_{GT(I)}}$	$\frac{I_H(-)}{I_{GT(I)}}$
4A Triac	1.6	2.5	2.7	1.2	4.8	1.2	1.3	1.0	1.2
10A Triac	1.5	1.4	3.1	1.6	4.0	1.8	2.0	1.1	1.6
15A Alternistor	1.5	1.8	—	2.4	7.0	2.1	—	2.2	1.9
1A Sensitive SCR	—	—	—	25	—	—	—	25	—
6A SCR	—	—	—	3.2	—	—	—	2.6	—

Examples of a 10 A Triac:

- If $I_{GT}(I) = 10 \text{ mA}$, then
 $I_{GT}(II) = 15 \text{ mA}$
 $I_{GT}(III) = 14 \text{ mA}$
 $I_{GT}(IV) = 31 \text{ mA}$
- If $I_L(I) = 16 \text{ mA}$, then
 $I_L(II) = 40 \text{ mA}$
 $I_L(III) = 18 \text{ mA}$
 $I_L(IV) = 20 \text{ mA}$
- If $I_H(+) = 11 \text{ mA}$ at 25 °C, then
 $I_H(+) = 16 \text{ mA}$

Summary

Gating, latching, and holding current characteristics of Thyristors are quite important yet predictable (once a single parameter value is known). Their interrelationships (ratios) can also be used to help designers in both initial circuit application design as well as device selection.

Phase Control Using Thyristors

Introduction

Due to high-volume production techniques, Thyristors are now priced so that almost any electrical product can benefit from electronic control. A look at the fundamentals of SCR and Triac phase controls shows how this is possible.

Output Power Characteristics

Phase control is the most common form of Thyristor power control. The Thyristor is held in the off condition – that is, all current flow in the circuit is blocked by the Thyristor except a minute leakage current. Then the Thyristor is triggered into an “on” condition by the control circuitry.

For full-wave AC control, a single Triac or two SCRs connected in inverse parallel may be used. One of two methods may be used for full-wave DC control – a bridge rectifier formed by two SCRs or an SCR placed in series with a diode bridge as shown in Figure AN1003.1.

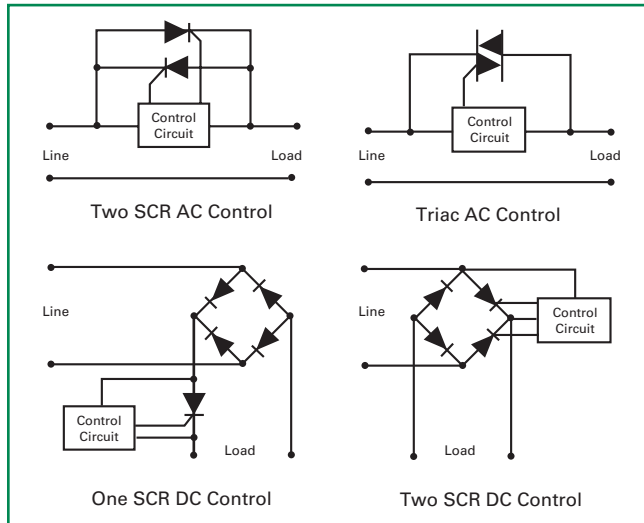


Figure AN1003.1 SCR/Triac Connections for Various Methods of Phase Control

Figure AN1003.2 illustrates voltage waveform and shows common terms used to describe Thyristor operation. Delay angle is the time during which the Thyristor blocks the line voltage. The conduction angle is the time during which the Thyristor is on.

It is important to note that the circuit current is determined by the load and power source. For simplification, assume the load is resistive; that is, both the voltage and current waveforms are identical.

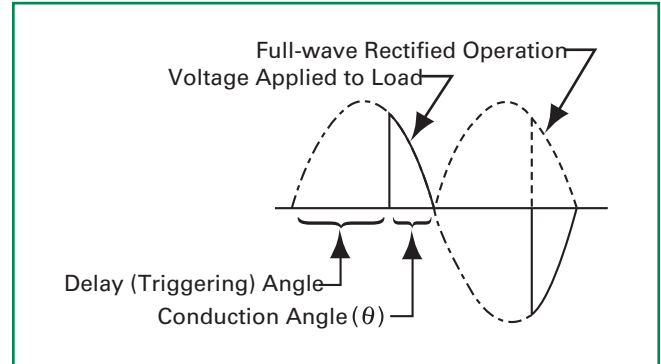


Figure AN1003.2 Sine Wave Showing Principles of Phase Control

Different loads respond to different characteristics of the AC waveform. For example, some are sensitive to average voltage, some to RMS voltage, and others to peak voltage. Various voltage characteristics are plotted against conduction angle for half- and full-wave phase control circuits in Figure AN1003.3 and Figure AN1003.4.

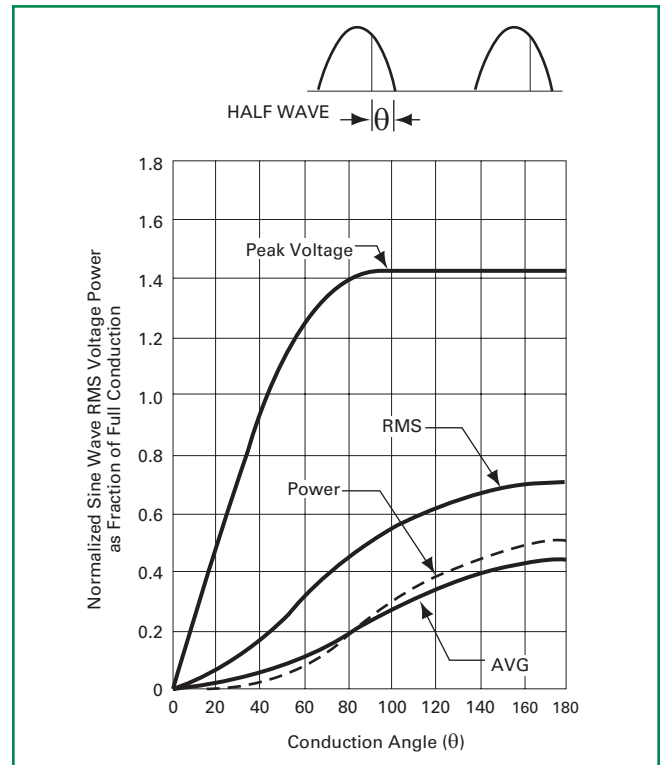


Figure AN1003.3 Half-Wave Phase Control (Sinusoidal)

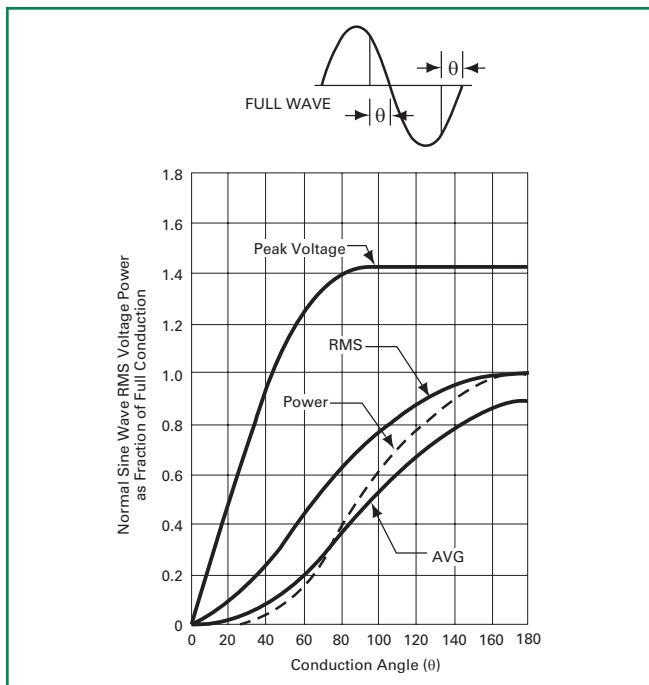


Figure AN1003.4 Symmetrical Full-Wave Phase Control (Sinusoidal)

Figure AN1003.3 and Figure AN1003.4 also show the relative power curve for constant impedance loads such as heaters. Because the relative impedance of incandescent lamps and motors change with applied voltage, they do not follow this curve precisely. To use the curves, find the full-wave rated power of the load, and then multiply by the ratio associated with the specific phase angle. Thus, a 180° conduction angle in a half-wave circuit provides 0.5 x full-wave conduction power.

In a full-wave circuit, a conduction angle of 150° provides 97% full power while a conduction angle of 30° provides only 3% of full power control. Therefore, it is usually pointless to obtain conduction angles less than 30° or greater than 150°.

Figure AN1003.5 and Figure AN1003.6 give convenient direct output voltage readings for 115 V/230 V input voltage. These curves also apply to current in a resistive circuit.

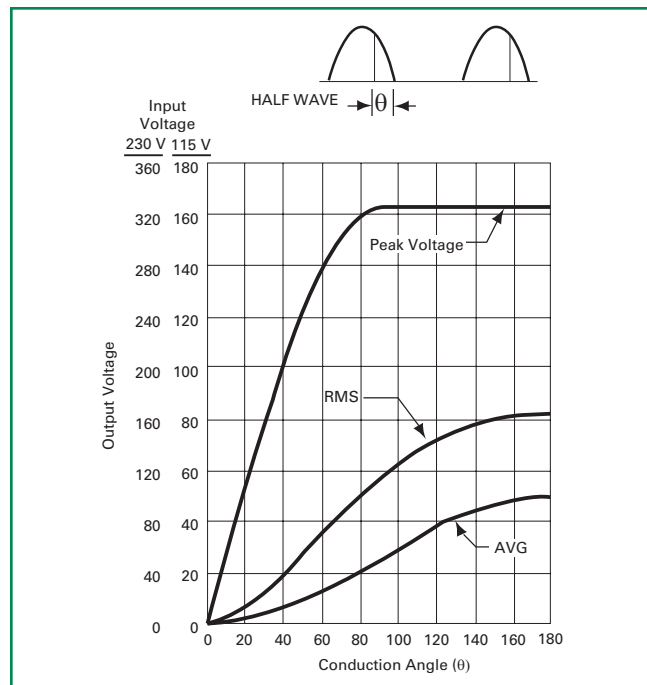


Figure AN1003.5 Output Voltage of Half-wave Phase Control

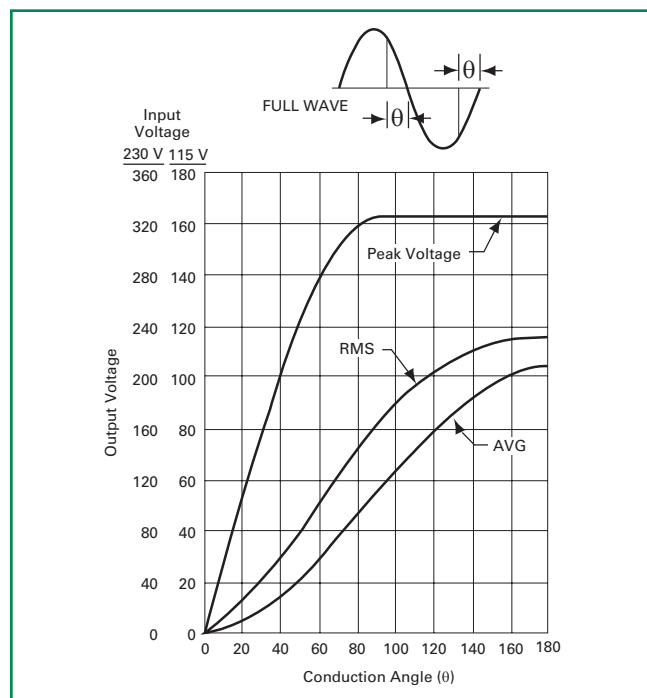


Figure AN1003.6 Output Voltage of Full-wave Phase Control

Control Characteristics

A relaxation oscillator is the simplest and most common control circuit for phase control. Figure AN1003.7 illustrates this circuit as it would be used with a Thyristor. Turn-on of the Thyristor occurs when the capacitor is charged through the resistor from a voltage or current source until the breakover voltage of the switching device is reached. Then, the switching device changes to its on state, and the capacitor is discharged through the Thyristor gate. Trigger devices used are neon bulbs, unijunction transistors, and three-, four-, or five-layer semiconductor trigger devices. Phase control of the output waveform is obtained by varying the RC time constant of the charging circuit so the trigger device breakdown occurs at different phase angles within the controlled half or full cycle.

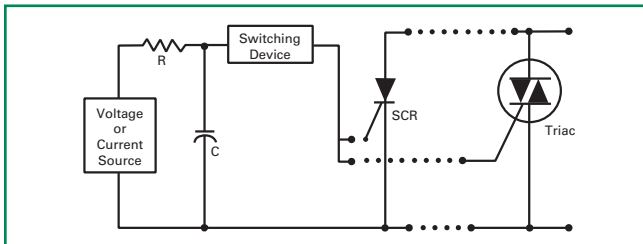


Figure AN1003.7 Relaxation Oscillator Thyristor Trigger Circuit

Figure AN1003.8 shows the capacitor voltage-time characteristic if the relaxation oscillator is to be operated from a pure DC source.

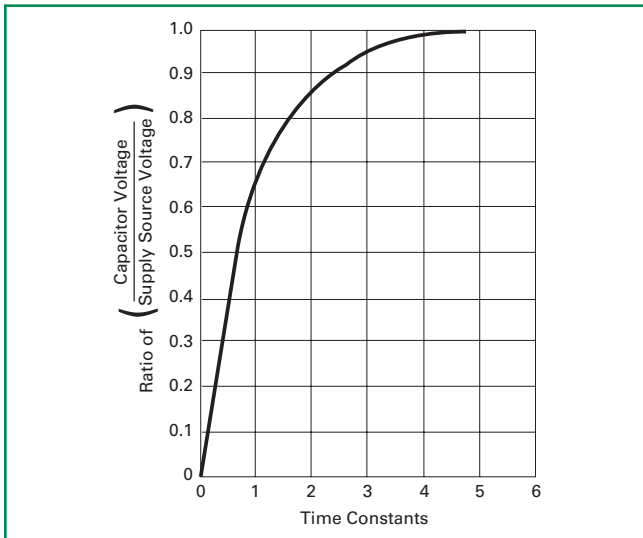


Figure AN1003.8 Capacitor Charging from DC Source

Usually, the design starting point is the selection of a capacitance value which will reliably trigger the Thyristor when the capacitance is discharged. Trigger devices and Thyristor gate triggering characteristics play a part in the selection. All the device characteristics are not always completely specified in applications, so experimental determination is sometimes needed.

Upon final selection of the capacitor, the curve shown in Figure AN1003.8 can be used in determining the

charging resistance needed to obtain the desired control characteristics.

Many circuits begin each half-cycle with the capacitor voltage at or near zero. However, most circuits leave a relatively large residual voltage on the capacitor after discharge. Therefore, the charging resistor must be determined on the basis of additional charge necessary to raise the capacitor to trigger potential.

For example, assume that we want to trigger an S2010L SCR with a 32 V trigger DIAC. A 0.1 μF capacitor will supply the necessary SCR gate current with the trigger DIAC. Assume a 50 V dc power supply, 30° minimum conduction angle, and 150° maximum conduction angle with a 60 Hz input power source. At approximately 32 V, the DIAC triggers leaving 0.66 V_{BO} of DIAC voltage on the capacitor. In order for DIAC to trigger, 22 V must be added to the capacitor potential, and 40 V additional (50-10) are available. The capacitor must be charged to 22/40 or 0.55 of the available charging voltage in the desired time. Looking at Figure AN1003.8, 0.55 of charging voltage represents 0.8 time constant. The 30° conduction angle required that the firing pulse be delayed 150° or 6.92 ms. (The period of 1/2 cycle at 60 Hz is 8.33 ms.) To obtain this time delay:

$$6.92 \text{ ms} = 0.8 \text{ RC}$$

$$\text{RC} = 8.68 \text{ ms}$$

$$\text{if } C = 0.10 \mu\text{F}$$

$$\text{then, } R = \frac{8.68 \times 10^{-3}}{0.1 \times 10^{-6}} = 86,000 \Omega$$

To obtain the minimum R (150° conduction angle), the delay is 30° or

$$(30/180) \times 8.33 = 1.39 \text{ ms}$$

$$1.39 \text{ ms} = 0.8 \text{ RC}$$

$$\text{RC} = 1.74 \text{ ms}$$

$$R = \frac{1.74 \times 10^{-3}}{0.1 \times 10^{-6}} = 17,400 \Omega$$

Using practical values, a 100 k potentiometer with up to 17 k minimum (residual) resistance should be used. Similar calculations using conduction angles between the maximum and minimum values will give control resistance versus power characteristic of this circuit.

Triac Phase Control

The basic full-wave Triac phase control circuit shown in Figure AN1003.9 requires only four components. Adjustable resistor R_1 and C_1 are a single-element phase-shift network. When the voltage across C_1 reaches breakover voltage (V_{BO}) of the DIAC, C_1 is partially discharged by the DIAC into the Triac gate. The Triac is then triggered into the conduction mode for the remainder of that half-cycle. In this circuit, triggering is in Quadrants I and III. The unique simplicity of this circuit makes it suitable for applications with small control range.

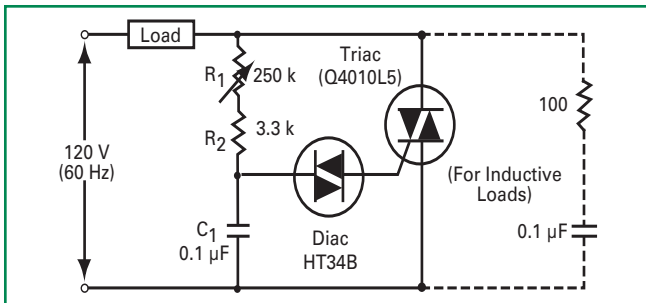


Figure AN1003.9 Basic DIAC-Triac Phase Control

The hysteresis (snap back) effect is somewhat similar to the action of a kerosene lantern. That is, when the control knob is first rotated from the off condition, the lamp can be lit only at some intermediate level of brightness, similar to turning up the wick to light the lantern. Brightness can then be turned down until it finally reaches the extinguishing point. If this occurs, the lamp can only be relit by turning up the control knob again to the intermediate level. Figure AN1003.10 illustrates the hysteresis effect in capacitor-DIAC triggering. As R_1 is brought down from its maximum resistance, the voltage across the capacitor increases until the DIAC first fires at point A, at the end of a half-cycle (conduction angle θ_i). After the gate pulse, however, the capacitor voltage drops suddenly to about half the triggering voltage, giving the capacitor a different initial condition. The capacitor charges to the DIAC, triggering voltage at point B in the next half-cycle and giving a steady-state conduction angle shown as θ for the Triac.

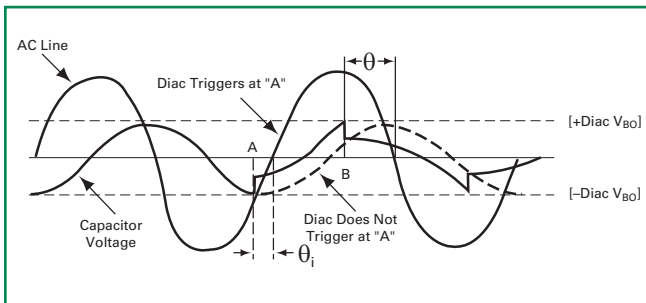


Figure AN1003.10 Relationship of AC Line Voltage and Triggering Voltage

In the Figure AN1003.11 illustration, the addition of a second RC phase-shift network extends the range on control and reduces the hysteresis effect to a negligible region. This circuit will control from 5% to 95% of full load power, but is subject to supply voltage variations. When R_1 is large, C_1 is charged primarily through R_3 from the phase-shifted voltage appearing across C_2 . This action provides additional range of phase-shift across C_1 and enables C_2 to partially recharge C_1 after the DIAC has triggered, thus reducing hysteresis. R_3 should be adjusted so that the circuit just drops out of conduction when R_1 is brought to maximum resistance.

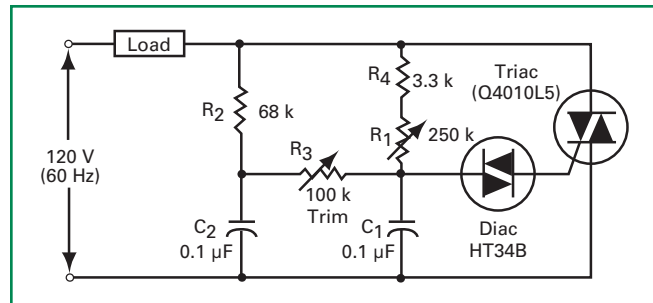


Figure AN1003.11 Extended Range Full-wave Phase Control

By using one of the circuits shown in Figure AN1003.12, the hysteresis effect can be eliminated entirely. The circuit (a) resets the timing capacitor to the same level after each positive half-cycle, providing a uniform initial condition for the timing capacitor. This circuit is useful only for resistive loads since the firing angle is not symmetrical throughout the range. If symmetrical firing is required, use the circuit (b) shown in Figure AN1003.12.

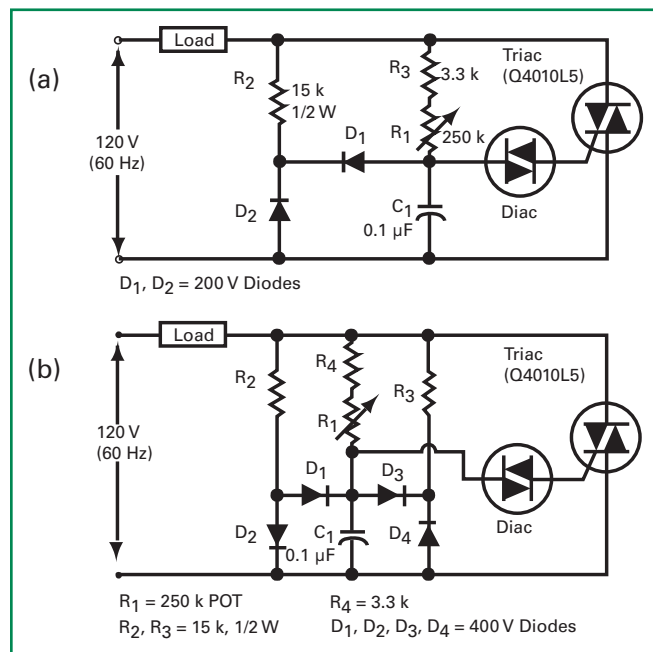


Figure AN1003.12 Wide-range Hysteresis Free Phase Control

For more complex control functions, particularly closed loop controls, the unijunction transistor may be used for the triggering device in a ramp and pedestal type of firing circuit as shown in Figure AN1003.13.

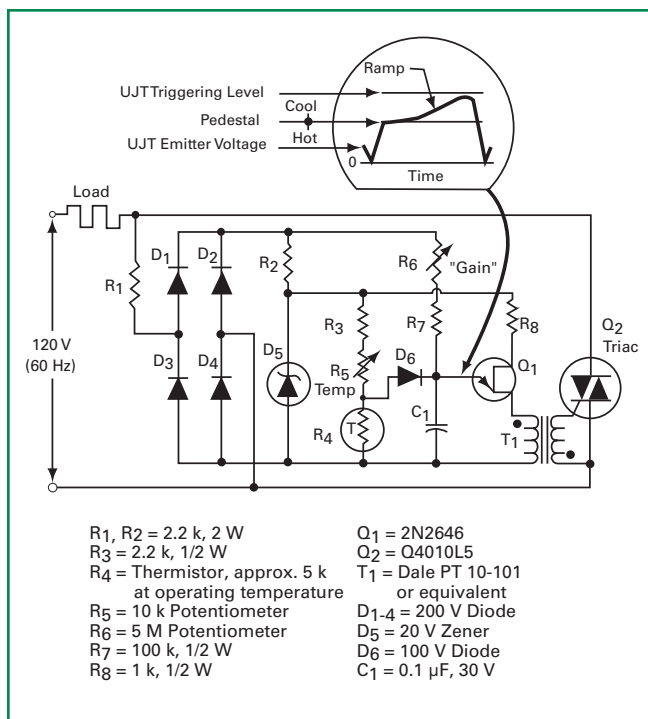


Figure AN1003.13 Precision Proportional Temperature Control

Several speed control and light dimming (phase) control circuits have been presented that give details for a complete 120 V application circuit but none for 240 V. Figure AN1003.14 and Figure AN1003.15 show some standard phase control circuits for 240 V, 60 Hz/50 Hz operation along with 120 V values for comparison. Even though there is very little difference, there are a few key things that must be remembered. First, capacitors and Triacs connected across the 240 V line must be rated at 400 V. Secondly, the potentiometer (variable resistor) value must change considerably to obtain the proper timing or triggering for 180° in each half-cycle.

Figure AN1003.14 shows a simple single-time-constant light dimmer (phase control) circuit, giving values for both 120 V and 240 V operation.

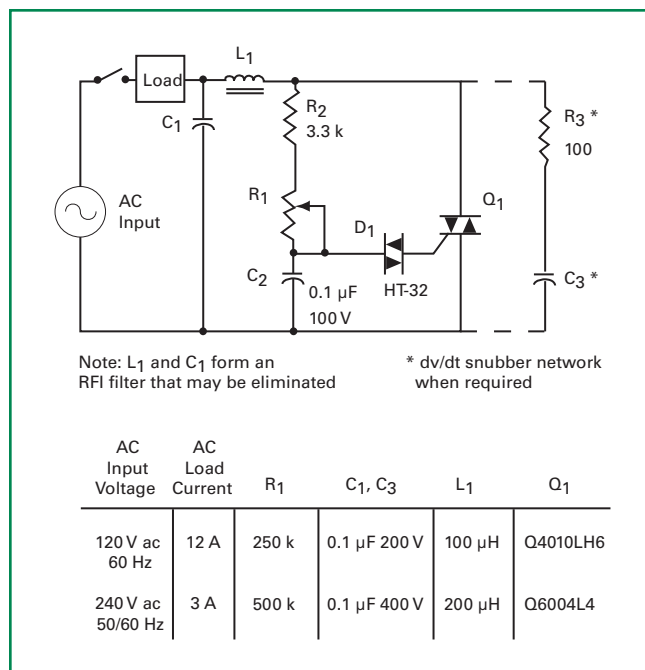


Figure AN1003.14 Single-time-constant Circuit for Incandescent Light Dimming, Heat Control, and Motor Speed Control

The circuit shown in Figure AN1003.15 is a double-time-constant circuit which has improved performance compared to the circuit shown in Figure AN1003.14. This circuit uses an additional RC network to extend the phase angle so that the Triac can be triggered at small conduction angles. The additional RC network also minimizes any hysteresis effect explained and illustrated in Figure AN1003.10 and Figure AN1003.11.

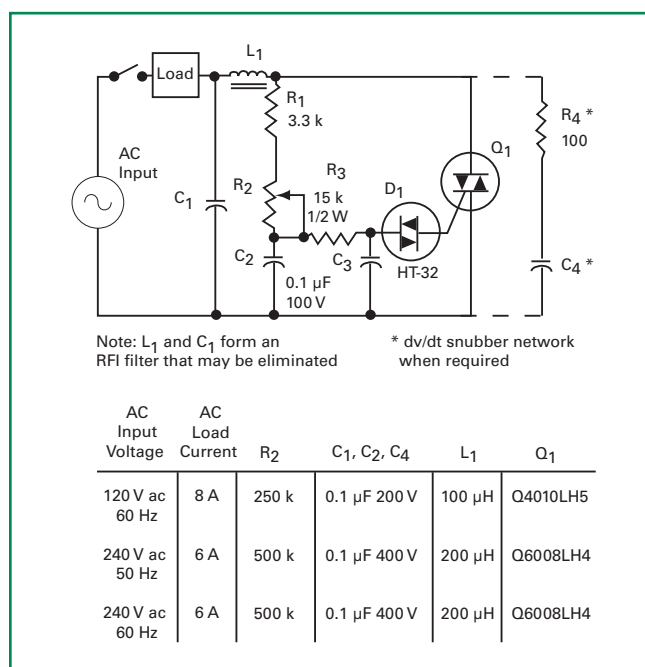


Figure AN1003.15 Double-time-constant Circuit for Incandescent Light Dimming, Heat Control, and Motor Speed Control

Permanent Magnet Motor Control

Figure AN1003.16 illustrates a circuit for phase controlling a permanent magnet (PM) motor. Since PM motors are also generators, they have characteristics that make them difficult for a standard Triac to commute properly. Control of a PM motor is easily accomplished by using an alternistor Triac with enhanced commutating characteristics.

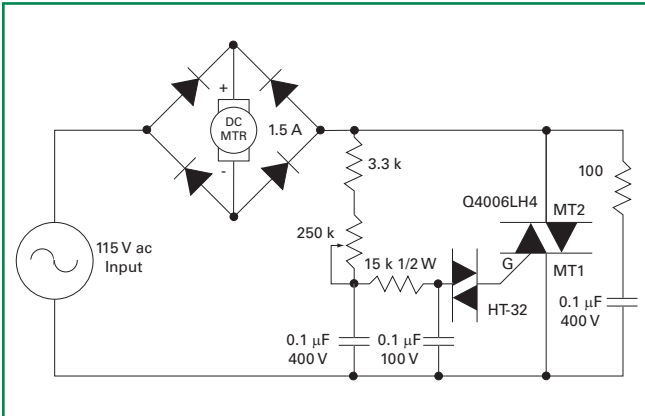
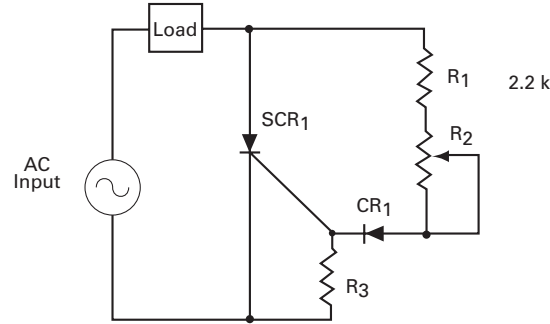


Figure AN1003.16 Circuit for Phase Controlling a Permanent Magnet Motor

PM motors normally require full-wave DC rectification. Therefore, the alternistor Triac controller should be connected in series with the AC input side of the rectifier bridge. The possible alternative of putting an SCR controller in series with the motor on the DC side of the rectifier bridge can be a challenge when it comes to timing and delayed turn-on near the end of the half cycle. The alternistor Triac controller shown in Figure AN1003.16 offers a wide range control so that the alternistor Triac can be triggered at a small conduction angle or low motor speed; the rectifiers and alternistors should have similar voltage ratings, with all based on line voltage and actual motor load requirements.

SCR Phase Control

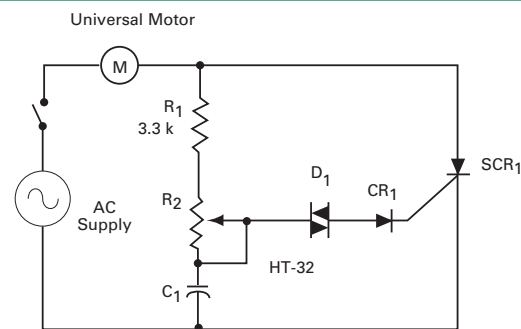
Figure AN1003.17 shows a very simple variable resistance half-wave circuit. It provides phase retard from essentially zero (SCR full on) to 90 electrical degrees of the anode voltage wave (SCR half on). Diode CR₁ blocks reverse gate voltage on the negative half-cycle of anode supply voltage. This protects the reverse gate junction of sensitive SCRs and keeps power dissipation low for gate resistors on the negative half cycle. The diode is rated to block at least the peak value of the AC supply voltage. The retard angle cannot be extended beyond the 90-degree point because the trigger circuit supply voltage and the trigger voltage producing the gate current to fire are in phase. At the peak of the AC supply voltage, the SCR can still be triggered with the maximum value of resistance between anode and gate. Since the SCR will trigger and latch into conduction the first time I_{GT} is reached, its conduction cannot be delayed beyond 90 electrical degrees with this circuit.



AC Input Voltage	AC Load Current	R ₂	CR ₁	SCR ₁	R ₃
120 V ac 60 Hz	0.8 A	500 k	IN4003	EC103D	1 k
120 V ac 60 Hz	8.5 A	100 k	IN4003	S4010R	Not Required
240 V ac 60 Hz	0.8 A	1 M	IN4004	EC103D	1 k
240 V ac 60 Hz	8.5 A	250 k	IN4004	S6010R	Not Required
240 V ac 50 Hz	2.5 A	1 M	IN4004	T106M1	1 k

Figure AN1003.17 Half-wave Control, 0° to 90° Conduction

Figure AN1003.18 shows a half-wave phase control circuit using an SCR to control a universal motor. This circuit is better than simple resistance firing circuits because the phase-shifting characteristics of the RC network permit the firing of the SCR beyond the peak of the impressed voltage, resulting in small conduction angles and very slow speed.



AC Input Voltage	AC Load Current	R ₂	CR ₁	SCR ₁	C ₁
120 V ac 60 Hz	8 A	150 k	IN4003	S6008L	0.1 μF 200 V
240 V ac 60 Hz	6.5 A	200 k	IN4004	S4015L	0.1 μF 400 V
240 V ac 50 Hz	6.5 A	200 k	IN4004	S6008L	0.1 μF 400 V

Figure AN1003.18 Half-wave Motor Control

Phase Control from Logic (DC) Inputs

Triacs can also be phase-controlled from pulsed DC unidirectional inputs such as those produced by a digital logic control system. Therefore, a microprocessor can be interfaced to AC load by using a sensitive gate Triac to control a lamp's intensity or a motor's speed.

There are two ways to interface the unidirectional logic pulse to control a Triac. Figure AN1003.19 illustrates one easy way if load current is approximately 5 A or less. The sensitive gate Triac serves as a direct power switch controlled by HTL, TTL, CMOS, or integrated circuit operational amplifier. A timed pulse from the system's logic can activate the Triac anywhere in the AC sine wave producing a phase-controlled load.

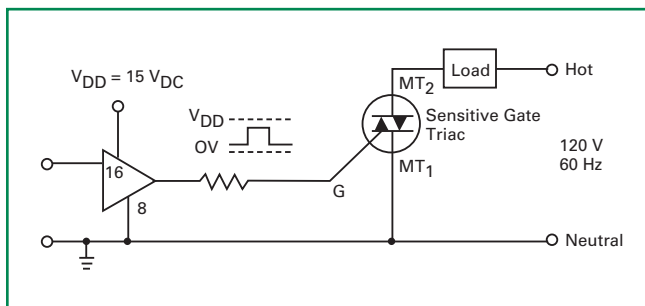


Figure AN1003.19 Sensitive Gate Triac Operating in Quadrants I and IV

The key to DC pulse control is correct grounding for DC and AC supply. As shown in Figure AN1003.19, **DC ground and AC ground/neutral must be common plus MT1 must be connected to common ground.** MT1 of the Triac is the return for both main terminal junctions as well as the gate junction.

Figure AN1003.20 shows an example of a unidirectional (all negative) pulse furnished from a special I.C. that is available from LSI Computer Systems in Melville, New York. Even though the circuit and load is shown to control a Halogen lamp, it could be applied to a common incandescent lamp for touch-controlled dimming.

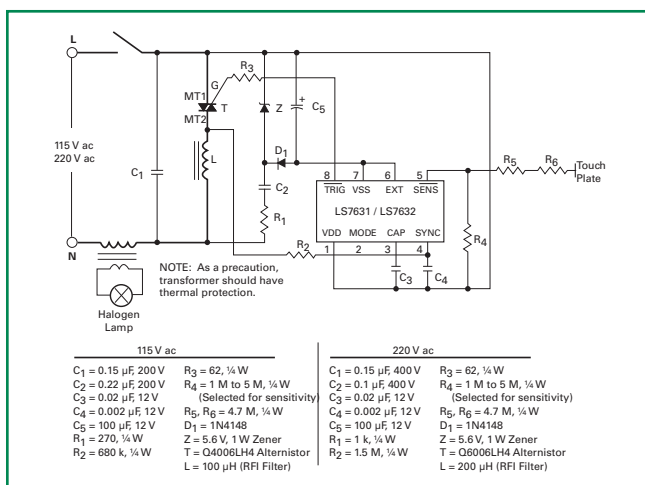


Figure AN1003.20 Typical Touch Plate Halogen Lamp Dimmer

For a circuit to control a heavy-duty inductive load where an alternistor is not compatible or available, two SCRs can be driven by an inexpensive TO-92 Triac to make a very high current Triac or alternistor equivalent, as shown in Figure AN1003.21. See "Relationship of IAV, IRMS, and IPK" in AN1009 for design calculations.

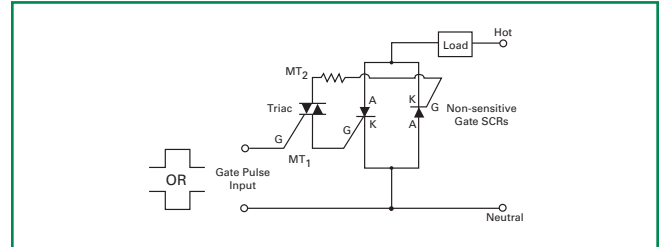


Figure AN1003.21 Triac Driving Two Inverse Parallel Non-Sensitive Gate SCRs

Figure AN1003.22 shows another way to interface a unidirectional pulse signal and activate AC loads at various points in the AC sine wave. This circuit has an electrically-isolated input which allows load placement to be flexible with respect to AC line. In other words, connection between DC ground and AC neutral is not required.

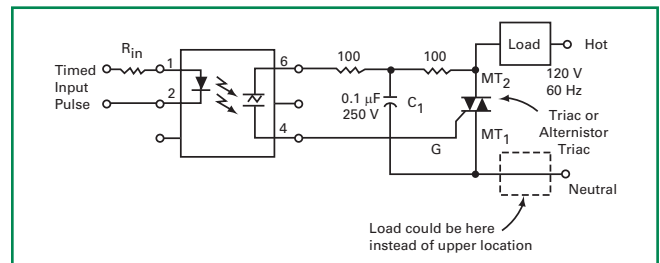


Figure AN1003.22 Opto-isolator Driving a Triac or Alternistor Triac

Microcontroller Phase Control

Traditionally, microcontrollers were too large and expensive to be used in small consumer applications such as a light dimmer. Microchip Technology Inc. of Chandler, Arizona has developed a line of 8-pin microcontrollers without sacrificing the functionality of their larger counterparts. These devices do not provide high drive outputs, but when combined with a sensitive Triac can be used in a cost-effective light dimmer.

Figure AN1003.23 illustrates a simple circuit using a transformerless power supply, PIC 12C508 microcontroller, and a sensitive Triac configured to provide a light dimmer control. R₃ is connected to the hot lead of the AC power line and to pin GP₄. The ESD protection diodes of the input structure allow this connection without damage. When the voltage on the AC power line is positive, the protection diode from the input to V_{DD} is forward biased, and the input buffer will see approximately V_{DD} + 0.7 V. The software will read this pin as high. When the voltage on the line is negative, the protection diode from V_{SS} to the input pin is forward biased, and the input buffer sees approximately V_{SS} - 0.7 V. The software will read the pin as low. By polling GP₄ for a change in state, the software can detect zero crossing.

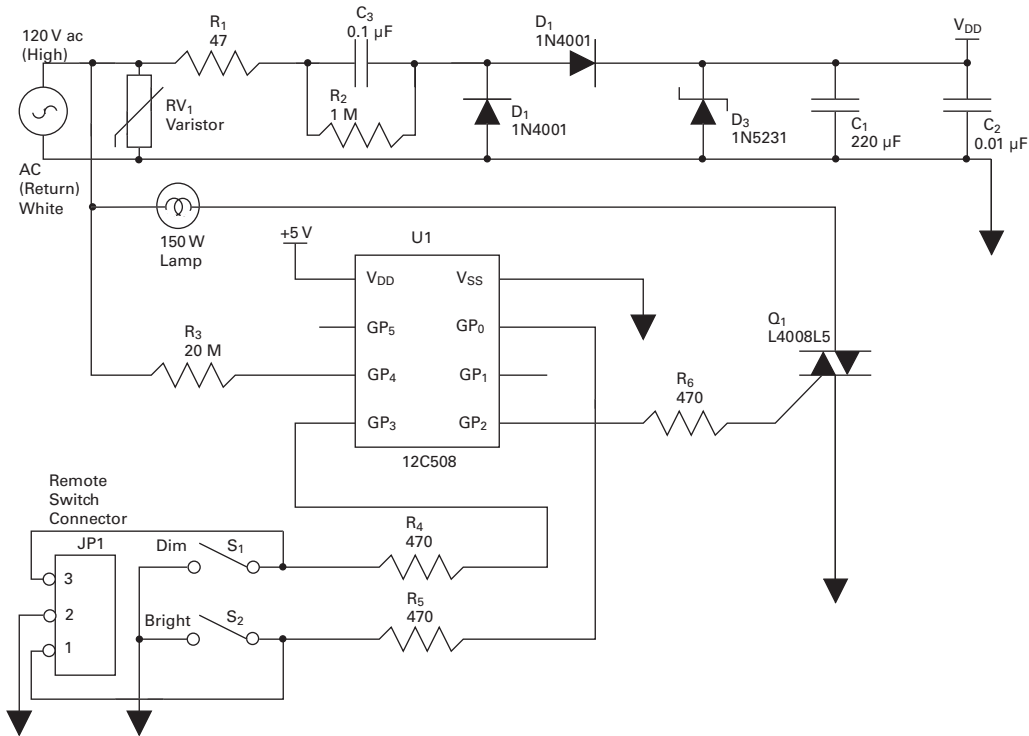


Figure AN1003.23 Microcontroller Light Dimmer Control

With a zero crossing state detected, software can be written to turn on the Triac by going from tri-state to a logic high on the gate and be synchronized with the AC phase cycles (Quadrants I and IV). Using pull-down switches connected to the microcontroller inputs, the user can signal the software to adjust the duty cycle of the Triac.

For higher amperage loads, a small 0.8 A, TO-92 Triac (operating in Quadrants I and IV) can be used to drive a 25 A alternistor Triac (operating in Quadrants I and III) as shown in the heater control illustration in Figure AN1003.24.

For a complete listing of the software used to control this circuit, see the Microchip application note PICREF-4. This application note can be downloaded from Microchip's Web site at www.microchip.com.

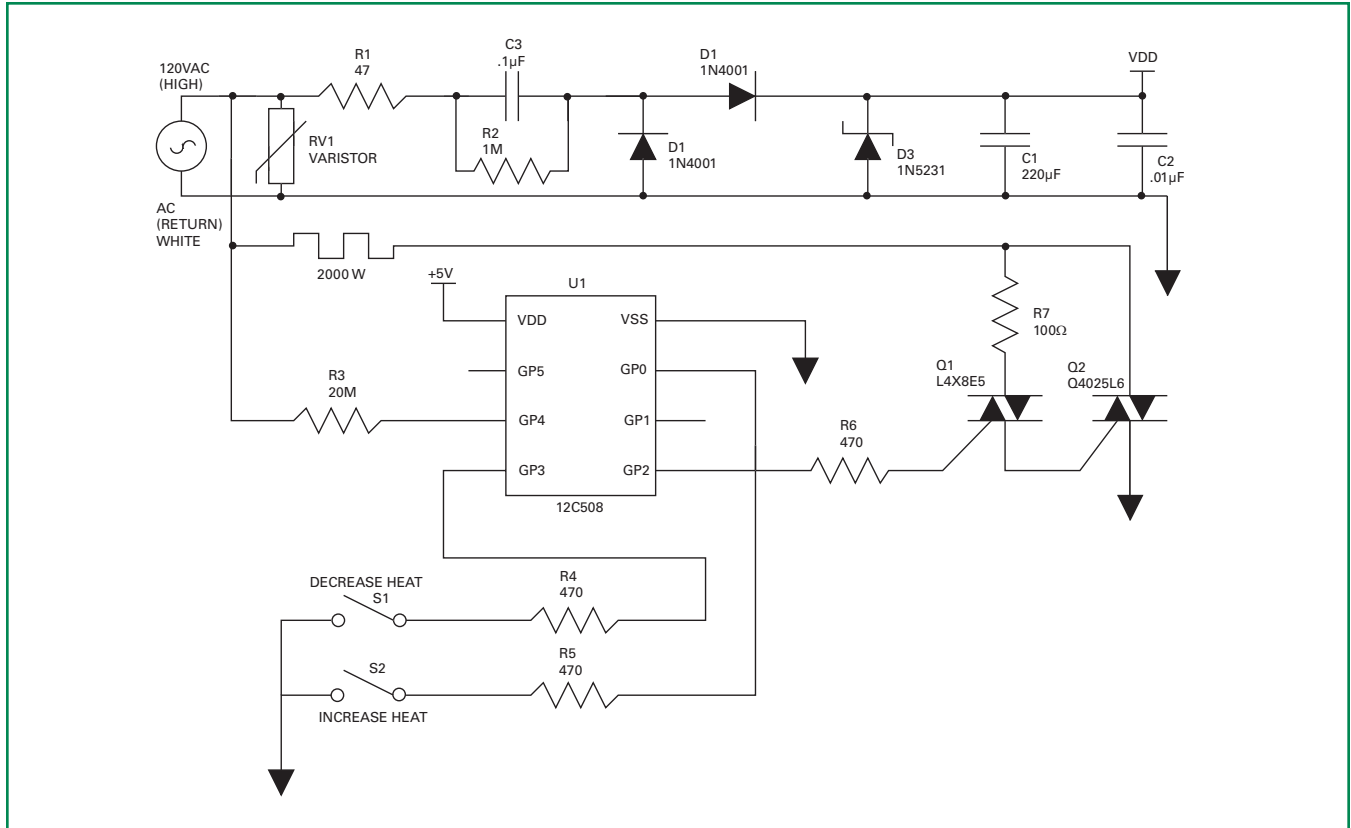


Figure AN1003.24 Microcontroller Heater Control

Summary

The load currents chosen for the examples in this application note were strictly arbitrary, and the component values will be the same regardless of load current except for the power Triac or SCR. The voltage rating of the power Thyristor devices must be a minimum of 200 V for 120 V input voltage and 400 V for 240 V input voltage.

The use of alternistors instead of Triacs may be much more acceptable in higher current applications and may eliminate the need for any dv/dt snubber network.

For many electrical products in the consumer market, competitive Thyristor prices and simplified circuits make automatic control a possibility. These simple circuits give the designer a good feel for the nature of Thyristor circuits and their design. More sophistication, such as speed and temperature feedback, can be developed as the control techniques become more familiar. A remarkable phenomenon is the degree of control obtainable with very simple circuits using Thyristors. As a result, industrial and consumer products will greatly benefit both in usability and marketability.

Mounting and Handling of Semiconductor Devices

Introduction

Proper mounting and handling of semiconductor devices, particularly those used in power applications, is an important, yet sometimes overlooked, consideration in the assembly of electronic systems. Power devices need adequate heat dissipation to increase operating life and reliability and allow the device to operate within manufacturers' specifications. Also, in order to avoid damage to the semiconductor chip or internal assembly, the devices should not be abused during assembly. Very often, device failures can be attributed directly to a heat sinking or assembly damage problem.

The information in this application note guides the semiconductor user in the proper use of Littelfuse devices, particularly the popular and versatile TO-220 and TO-218 epoxy packages.

Contact the Littelfuse Applications Engineering Group for further details or suggestions on use of Littelfuse devices.

Lead Forming – Typical Configurations

A variety of mounting configurations are possible with Littelfuse power semiconductor TO-92, DO-15, and TO-220 packages, depending upon such factors as power requirements, heat sinking, available space, and cost considerations. Figure AN1004.1 shows typical examples and basic design rules.

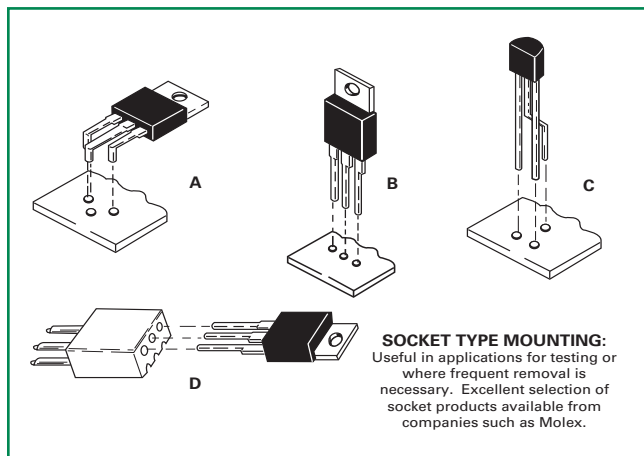


Figure AN1004.1 Component Mounting

These are suitable only for vibration-free environments and low-power, free-air applications. For best results, the device should be in a vertical position for maximum heat dissipation from convection currents.

Standard Lead Forms

Littelfuse encourages users to allow factory production of all lead and tab form options. Littelfuse has the automated machinery and expertise to produce pre-formed parts at minimum risk to the device and with greater convenience for the consumer. See the "Lead Form Dimensions" section of this catalog for a complete list of readily available lead form options. Contact Littelfuse for information regarding custom lead form designs.

Lead Bending Method

Leads may be bent easily and to any desired angle, provided that the bend is made at a minimum 0.063" (0.1" for TO-218 package) away from the package body with a minimum radius of 0.032" (0.040" for TO-218 package) or 1.5 times lead thickness rule. DO-15 device leads may be bent with a minimum radius of 0.050", and DO-35 device leads may be bent with a minimum radius of 0.028". Leads should be held firmly between the package body and the bend so that strain on the leads is not transmitted to the package body, as shown in Figure AN1004.2. Also, leads should be held firmly when trimming length.

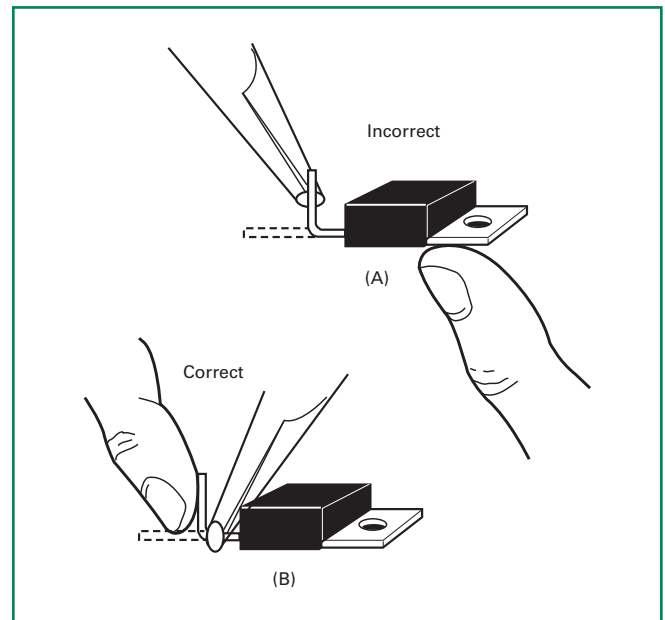


Figure AN1004.2 Lead Bending Method

When bending leads in the plane of the leads (spreading), bend only the narrow part. Sharp angle bends should be done only once as repetitive bending will fatigue and break the leads.

Heat Sinking

Use of the largest, most efficient heat sink as is practical and cost effective extends device life and increases reliability. In the illustration shown in Figure AN1004.3, each device is electrically isolated.

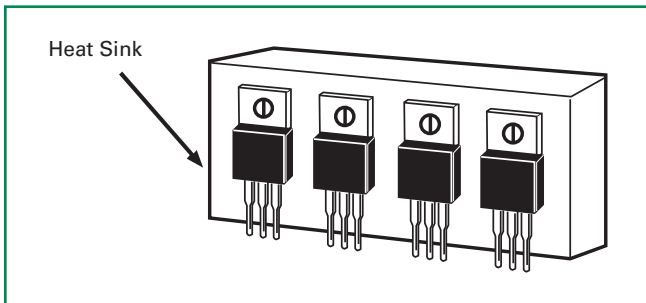


Figure AN1004.3 Several Isolated TO-220 Devices Mounted to a Common Heat Sink

Many power device failures are a direct result of improper heat dissipation. Heat sinks with a mating area smaller than the metal tab of the device are unacceptable. Heat sinking material should be at least 0.062" thick to be effective and efficient.

Note that in all applications the maximum case temperature (T_C) rating of the device must not be exceeded. Refer to the individual device data sheet rating curves (T_C versus I_T) as well as the individual device outline drawings for correct T_C measurement point.

Figure AN1004.4 through Figure AN1004.6 show additional examples of acceptable heat sinks.

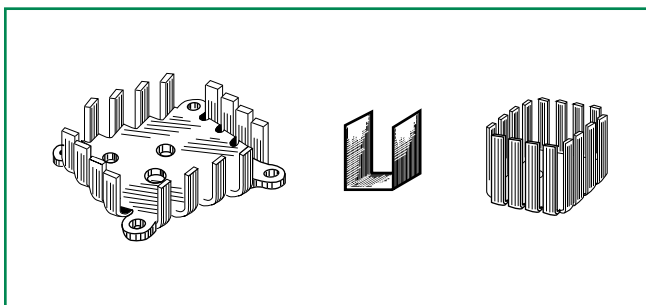


Figure AN1004.4 Examples of PC Board Mounts

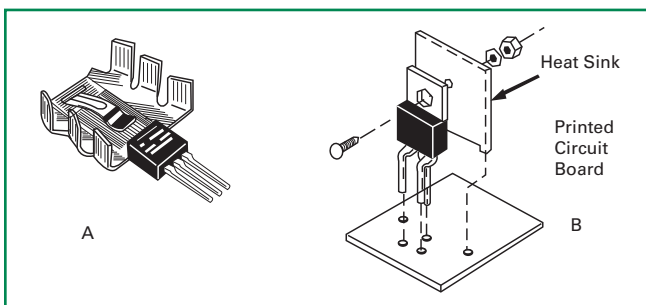


Figure AN1004.5 Vertical Mount Heat Sink

Several types of vertical mount heat sinks are available. Keep heat sink vertical for maximum convection.

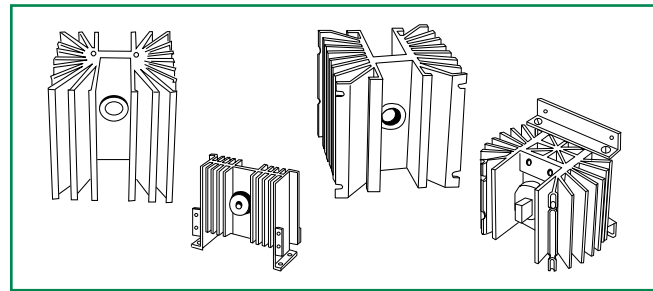


Figure AN1004.6 Examples of Extruded Aluminum

When coupled with fans, extruded aluminum mounts have the highest efficiency.

Heat Sinking Notes

Care should be taken not to mount heat sinks near other heat-producing elements such as power resistors, because black anodized heat sinks may absorb more heat than they dissipate.

Some heat sinks can hold several power devices. Make sure that if they are in electrical contact to the heat sink, the devices do not short-circuit the desired functions. Isolate the devices electrically or move to another location. Recall that the mounting tab of Littelfuse isolated TO-220 devices is electrically isolated so that several devices may be mounted on the same heat sink without extra insulating components. If using an external insulator such as mica, with a thickness of 0.004", an additional thermal resistance of 0.8° C/W for TO-220 or 0.5° C/W for TO-218 devices is added to the $R_{\theta JC}$ device rating.

Allow for adequate ventilation. If possible, route heat sinks to outside of assembly for maximum airflow.

Mounting Surface Selection

Proper mounting surface selection is essential to efficient transfer of heat from the semiconductor device to the heat sink and from the heat sink to the ambient. The most popular heat sinks are flat aluminum plates or finned extruded aluminum heat sinks.

The mounting surface should be clean and free from burrs or scratches. It should be flat within 0.002 inch per inch, and a surface finish of 30 to 60 microinches is acceptable. Surfaces with a higher degree of polish do not produce better thermal conductivity.

Many aluminum heat sinks are black anodized to improve thermal emissivity and prevent corrosion. Anodizing results in high electrical but negligible thermal insulation. This is an excellent choice for isolated TO-220 devices. For applications of non-isolated TO-220 devices where electrical connection to the common anode tab is required, the anodization

should be removed. Iridite or chromate acid dip finish offers low electrical and thermal resistance. Either TO-218, Fastpak or TO-220 devices may be mounted directly to this surface, regardless of application. Both finishes should be cleaned prior to use to remove manufacturing oils and films. Some of the more economical heat sinks are painted black. Due to the high thermal resistance of paint, the paint should be removed in the area where the semiconductor is attached.

Bare aluminum should be buffed with #000 steel wool and followed with an acetone or alcohol rinse. Immediately, thermal grease should be applied to the surface and the device mounted down to prevent dust or metal particles from lodging in the critical interface area.

For good thermal contact, the use of thermal grease is essential to fill the air pockets between the semiconductor and the mounting surface. This decreases the thermal resistance by 20%. For example, a typical TO-220 with $R_{\theta JC}$ of 1.2 °C/W may be lowered to 1 °C/W by using thermal grease.

Littelfuse recommends Dow-Corning 340 as a proven effective thermal grease. Fibrous applicators are not recommended as they may tend to leave lint or dust in the interface area. Ensure that the grease is spread adequately across the device mounting surface, and torque down the device to specification.

Contact Littelfuse Applications Engineering for assistance in choosing and using the proper heat sink for specific application.

Hardware And Methods

TO-220

The mounting hole for the Teccor TO-220 devices should not exceed 0.140" (6/32) clearance. (Figure AN1004.7) No insulating bushings are needed for the L Package (isolated) devices as the tab is electrically isolated from the semiconductor chip. 6/32 mounting hardware, especially round head or Fillister machine screws, is recommended and should be torqued to a value of 6 inch-lbs.

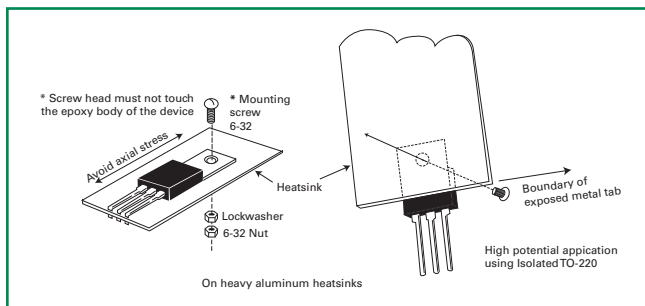


Figure AN1004.7 TO-220 Mounting

Punched holes are not acceptable due to cratering around the hole which can cause the device to be pulled into the crater by the fastener or can leave a significant portion

of the device out of contact with the heat sink. The first effect may cause immediate damage to the package and early failure, while the second can create higher operating temperatures which will shorten operating life. Punched holes are quite acceptable in thin metal plates where fine-edge blanking or sheared-through holes are employed.

Drilled holes must have a properly prepared surface. Excessive chamfering is not acceptable as it may create a crater effect. Edges must be deburred to promote good contact and avoid puncturing isolation materials.

For high-voltage applications, it is recommended that only the metal portion of the TO-220 package (as viewed from the bottom of the package) be in contact with the heat sink. This will provide maximum oversurface distance and prevent a high voltage path over the plastic case to a grounded heat sink.

TO-218

The mounting hole for the TO-218 device should not exceed 0.164" (8/32) clearance. Isolated versions of TO-218 do not require any insulating material since mounting tab is electrically isolated from the semiconductor chip. Round lead or Fillister machine screws are recommended. Maximum torque to be applied to mounting tab should not exceed 8 inch-lbs.

The same precautions given for the TO-220 package concerning punched holes, drilled holes, and proper prepared heat sink mounting surface apply to the TO-218 package. Also for high-voltage applications, it is recommended that only the metal portion of the mounting surface of the TO-218 package be in contact with heat sink. This achieves maximum oversurface distance to prevent a high-voltage path over the device body to grounded heat sink.

General Mounting Notes

Care must be taken on TO-220 & TO-218 packages at all times to avoid strain to the mounting tab or leads. For easy insertion of the part onto the board or heat sink, avoid axial strain on the leads. Carefully measure holes for the mounting tab and the leads, and do any forming of the tab or leads before mounting. Refer to the "Lead Form Dimensions" section of this catalog before attempting lead form operations.

Rivets may be used for less demanding and more economical applications. 1/8" all-aluminum pop rivets can be used on both TO-220 and TO-218 packages. Use a 0.129"-0.133" (#30) drill for the hole and insert the rivet from the top side, as shown in Figure AN1004.9. An insertion tool, similar to a "USM" PRG 430 hand riveter, is recommended. A wide selection of grip ranges is available, depending upon the thickness of the heat sink material. Use an appropriate grip range to securely anchor the device, yet not deform the mounting tab. The recommended rivet tool has a protruding nipple that will

allow easy insertion of the rivet and keep the tool clear of the plastic case of the device.

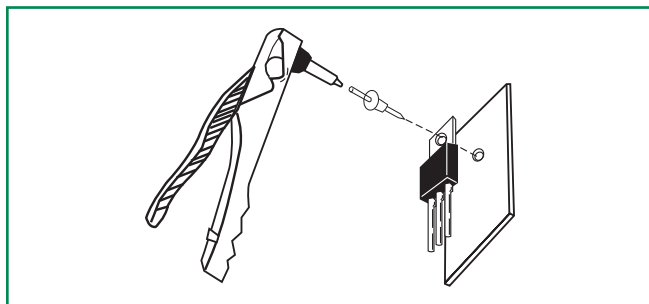


Figure AN1004.9 Pop Riveting Technique

A Milford #511 (Milford Group, Milford, CT) semi-tubular steel rivet set into a 0.129" receiving hole with a riveting machine similar to a Milford S256 is also acceptable. Contact the rivet machine manufacturer for exact details on application and set-up for optimum results.

Pneumatic or other impact riveting devices are not recommended due to the shock they may apply to the device.

Under no circumstance should any tool or hardware come into contact with the case. The case should not be used as a brace for any rotation or shearing force during mounting or in use. Non-standard size screws, nuts, and rivets are easily obtainable to avoid clearance problems.

Always use an accurate torque wrench to mount devices. No gain is achieved by overtorquing devices. In fact, overtorquing may cause the tab and case to deform or rupture, seriously damaging the device. The curve shown in Figure AN1004.10 illustrates the effect of proper torque.

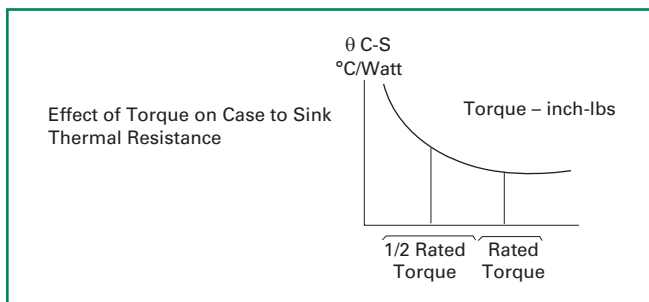


Figure AN1004.10 Effect of Torque to Sink Thermal Resistance

With proper care, the mounting tab of a device can be soldered to a surface. However, the heat required to accomplish this operation can damage or destroy the semiconductor chip or internal assembly. See "Surface Mount Soldering Recommendations" (AN1005) in this catalog.

Spring-steel clips can be used to replace torqued hardware in assembling Thyristors to heat sinks. Clips snap into heat sink slots to hold the device in place for PC board insertion. Clips are available in several sizes for various heat sink thicknesses and Thyristor case styles from *Aavid*

Thermalloy in Concord, New Hampshire. A typical heatsink is shown in Figure AN1004.11

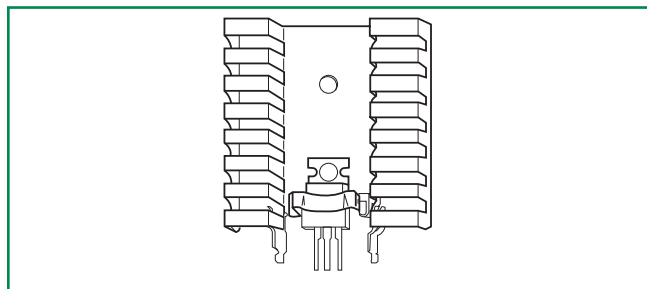


Figure AN1004.11 Typical Heat Sink Using Clips

Soldering Of Leads

A prime consideration in soldering leads is the soldering of device leads into PC boards, heat sinks, and so on. Significant damage can be done to the device through improper soldering. In any soldering process, do not exceed the data sheet lead solder temperature of +280 °C for 10 seconds, maximum, $\geq 1/16$ " from the case.

This application note presents details about the following three types of soldering:

- Hand soldering
- Wave soldering
- Dip soldering

Hand Soldering

This method is mostly used in prototype breadboarding applications and production of small modules. It has the greatest potential for misuse. The following recommendations apply to Littelfuse TO-92, TO-220, and TO-218 packages.

Select a small- to medium-duty electric soldering iron of 25 W to 45 W designed for electrical assembly application. Tip temperature should be rated from 600 °F to 800 °F (300 °C to 425 °C). The iron should have sufficient heat capacity to heat the joint quickly and efficiently in order to minimize contact time to the part. Pencil tip probes work very well. Neither heavy-duty electrical irons of greater than 45 W nor flame-heated irons and large heavy tips are recommended, as the tip temperatures are far too high and uncontrollable and can easily exceed the time-temperature limit of the part.

Littelfuse Fastpak devices require a different soldering technique. Circuit connection can be done by either quick-connect terminals or solder.

Since most quick-connect 0.250" female terminals have a maximum rating of 30 A, connection to terminals should be made by soldering wires instead of quick-connects.

Recommended wire is 10 AWG stranded wire for use with MT1 and MT2 for load currents above 30 A. Soldering

should be performed with a 100-watt soldering iron. The iron should not remain in contact with the wire and terminal longer than 40 seconds so the Fastpak Triac is not damaged.

For the Littelfuse TO-218X package, the basic rules for hand soldering apply; however, a larger iron may be required to apply sufficient heat to the larger leads to efficiently solder the joint.

Remember not to exceed the lead solder temperatures of +280 °C for 10 seconds, maximum, $\geq 1/16''$ (1.59mm) from the case.

A 60/40 or 63/37 Sn/Pb solder is acceptable. This low melting-point solder, used in conjunction with a mildly activated rosin flux, is recommended.

Insert the device into the PC board and, if required, attach the device to the heat sink before soldering. Each lead should be individually heat sunk as it is soldered. Commercially available heat sink clips are excellent for this use. Hemostats may also be used if available. Needle-nose pliers are a good heat sink choice; however, they are not as handy as stand-alone type clips.

In any case, the lead should be clipped or grasped between the solder joint and the case, as near to the joint as possible. Avoid straining or twisting the lead in any way.

Use a clean pre-tinned iron, and solder the joint as quickly as possible. Avoid overheating the joint or bringing the iron or solder into contact with other leads that are not heat sunk.

Wave Solder

Wave soldering is one of the most efficient methods of soldering large numbers of PC boards quickly and effectively. Guidelines for soldering by this method are supplied by equipment manufacturers. The boards should be pre-heated to avoid thermal shock to semiconductor components, and the time-temperature cycle in the solder wave should be regulated to avoid heating the device beyond the recommended temperature rating. A mildly activated resin flux is recommended. Figures AN1004.12 and .13 show typical heat and time conditions.

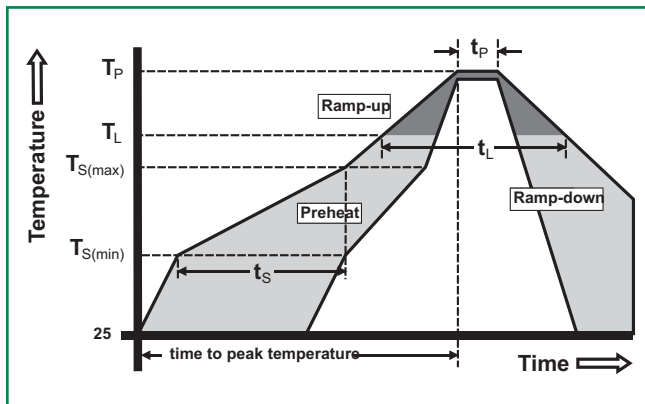


Figure AN1004.12 Reflow Soldering with Pre-heating

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_P)		260 °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		280°C

Figure AN1004.13 Heat and Time Table

Dip Soldering

Dip soldering is very similar to wave soldering, but it is a hand operation. Follow the same considerations as for wave soldering, particularly the time-temperature cycle which may become operator dependent because of the wide process variations that may occur. This method is not recommended.

Board or device clean-up is left to the discretion of the customer. Littelfuse devices are tolerant of a wide variety of solvents, and they conform to MIL-STD 202E method 215 "Resistance to Solvents."

Surface Mount Soldering Recommendations

Introduction

The most important consideration in reliability is achieving a good solder bond between surface mount device (SMD) and substrate since the solder provides the thermal path from the chip. A good bond is less subject to thermal fatiguing and will result in improved device reliability.

The most economic method of soldering is a process in which all different components are soldered simultaneously, such as DO-214, Compak, TO-252 devices, capacitors, and resistors.

Reflow Of Soldering

The preferred technique for mounting microminiature components on hybrid thick- and thin-film is reflow soldering.

The DO-214 is designed to be mounted directly to or on thick-film metallization which has been screened and fired on a substrate. The recommended substrates are Alumina or P.C. Board material.

Recommended metallization is silver palladium or molybdenum (plated with nickel or other elements to enhance solderability). For more information, consult Du Pont's Thick-Film handbook or the factory.

It is best to prepare the substrate by either dipping it in a solder bath or by screen printing a solder paste.

After the substrate is prepared, devices are put in place with vacuum pencils. The device may be laid in place without special alignment procedures since it is self-aligning during the solder reflow process and will be held in place by surface tension.

For reliable connections, keep the following in mind:

- (1) Maximum temperature of the leads or tab during the soldering cycle does not exceed 280 °C.
- (2) Flux must affect neither components nor connectors.
- (3) Residue of the flux must be easy to remove.

Good flux or solder paste with these properties is available on the market. A recommended flux is Alpha 5003 diluted with benzyl alcohol. Dilution used will vary with application and must be determined empirically.

Having first been fluxed, all components are positioned on the substrate. The slight adhesive force of the flux is sufficient to keep the components in place.

Because solder paste contains a flux, it has good inherent adhesive properties which eases positioning of the components. Allow flux to dry at room temperature or in a 70 °C oven. Flux should be dry to the touch. Time required will depend on flux used.

With the components in position, the substrate is heated to a point where the solder begins to flow. This can be done on a heating plate, on a conveyor belt running through an infrared tunnel, or by using vapor phase soldering.

In the vapor phase soldering process, the entire PC board is uniformly heated within a vapor phase zone at a temperature of approximately 215 °C. The saturated vapor phase zone is obtained by heating an inert (inactive) fluid to the boiling point. The vapor phase is locked in place by a secondary vapor. (Figure AN1005.1) Vapor phase soldering provides uniform heating and prevents overheating.

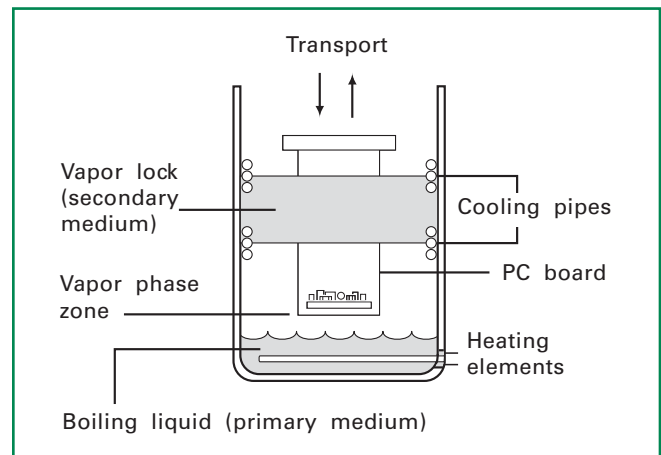


Figure AN1005.1 Principle of Vapor Phase Soldering

No matter which method of heating is used, the maximum allowed temperature of the plastic body must not exceed 250 °C during the soldering process. For additional information on temperature behavior during the soldering process, see Figure AN1005.2 and Figure AN1005.3.

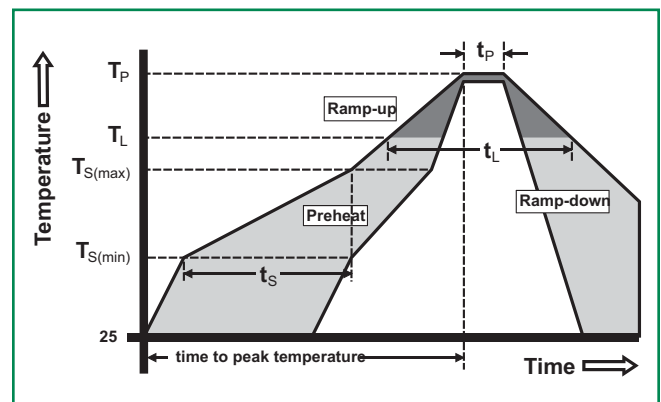


Figure AN1005.2 Reflow Soldering Profile

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_p)		260 °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C

Reflow Soldering Zones

Zone 1: Initial Pre-heating Stage (25 °C to 150 °C)

- Excess solvent is driven off.
- PCB and Components are gradually heated up.
- Temperature gradient shall be <2.5 °C/Sec.

Zone 2: Soak Stage (150 °C to 180 °C)

- Flux components start activation and begin to reduce the oxides on component leads and PCB pads.
- PCB components are brought nearer to the temperature at which solder bonding can occur.
- Soak allows different mass components to reach the same temperature.
- Activated flux keeps metal surfaces from re-oxidizing.

Zone 3: Reflow Stage (180 °C to 235 °C)

- Paste is brought to the alloy's melting point.
- Activated flux reduces surface tension at the metal interface so metallurgical bonding occurs.

Zone 4: Cool-down Stage (180 °C to 25 °C)

Assembly is cooled evenly so thermal shock to the components or PCB is reduced.

The surface tension of the liquid solder tends to draw the leads of the device towards the center of the soldering area and so has a correcting effect on slight mispositionings. However, if the layout is not optimized, the same effect can result in undesirable shifts, particularly if the soldering areas on the substrate and the components are not concentrically arranged. This problem can be solved by using a standard contact pattern which leaves sufficient scope for the self-positioning effect (Figure AN1005.3 and Figure AN1005.4) Figure AN1005.5 shows the reflow soldering procedure.

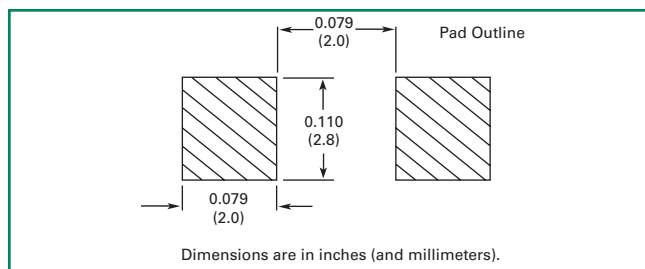


Figure AN1005.3 Minimum Required Dimensions of Metal Connection of Typical DO-214 Pads on Hybrid Thick- and Thin-film Substrates

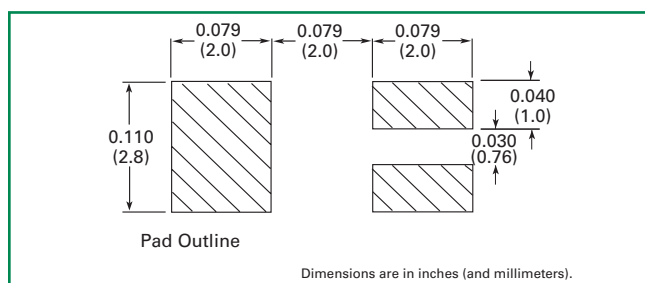


Figure AN1005.4 Modified DO-214 Compak — Three-leaded Surface Mount Package

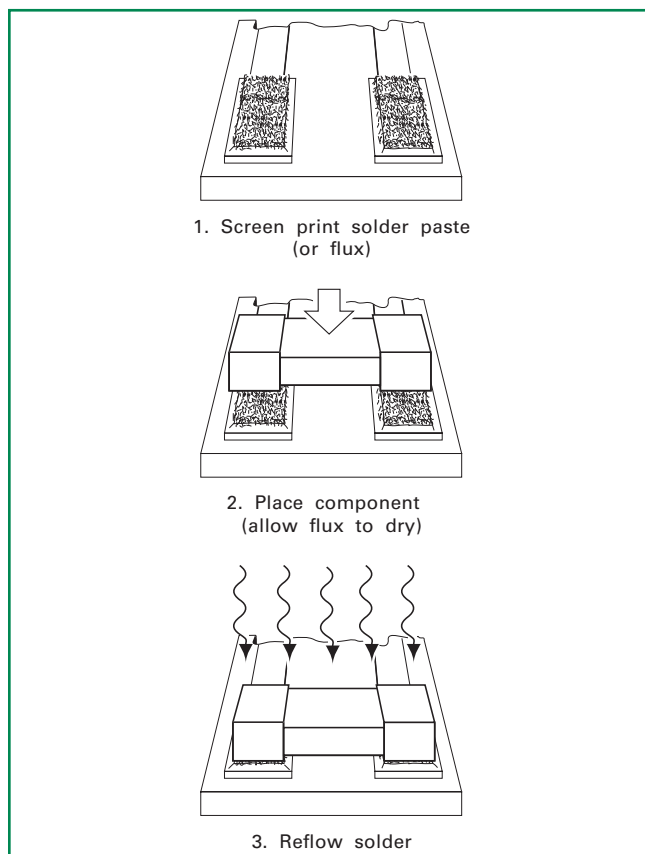


Figure AN1005.5 Reflow Soldering Procedure

After the solder is set and cooled, visually inspect the connections and, where necessary, correct with a soldering iron. Finally, the remnants of the flux must be removed carefully.

Use vapor degrease with an azeotrope solvent or equivalent to remove flux. Allow to dry.

After the drying procedure is complete, the assembly is ready for testing and/or further processing.

Wave Soldering

Wave soldering is the most commonly used method for soldering components in PCB assemblies. As with other soldering processes, a flux is applied before soldering. After the flux is applied, the surface mount devices are glued into place on a PC board. The board is then placed in contact with a molten wave of solder at a temperature between 240 °C and 260 °C, which affixes the component to the board.

Dual wave solder baths are also in use. This procedure is the same as mentioned above except a second wave of solder removes excess solder.

Although wave soldering is the most popular method of PCB assembly, drawbacks exist. The negative features include solder bridging and shadows (pads and leads not completely wetted) as board density increases. Also, this method has the sharpest thermal gradient. To prevent thermal shock, some sort of pre-heating device must be used. Figure AN1005.6 shows the procedure for wave soldering PCBs with surface mount devices only. Figure AN1005.7 shows the procedure for wave soldering PCBs with both surface mount and leaded components.

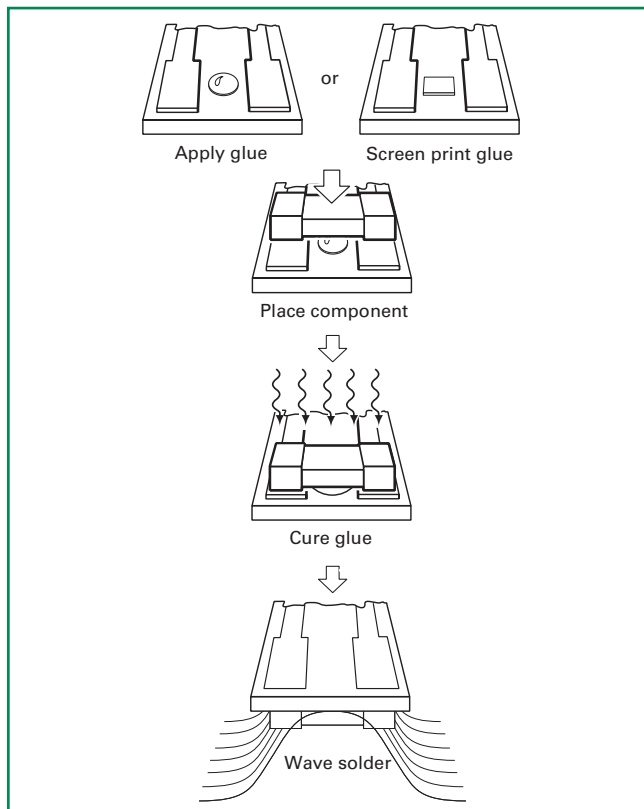


Figure AN1005.6 Wave Soldering PCBs With Surface Mount Devices Only

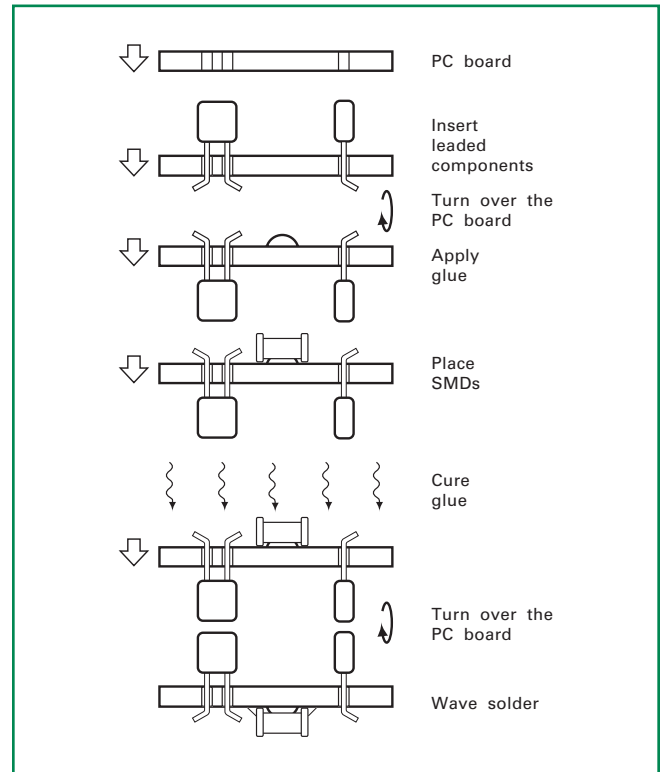


Figure AN1005.7 Wave Soldering PCBs With Both Surface Mount and Leaded Components

Immersion Soldering

Maximum allowed temperature of the soldering bath is 235 °C. Maximum duration of soldering cycle is five seconds, and forced cooling must be applied.

Hand Soldering

It is possible to solder the DO-214, Compak, and TO-252 devices with a miniature hand-held soldering iron, but this method has particular drawbacks and should be restricted to laboratory use and/or incidental repairs on production circuits.

Recommended Metal-alloy

- (1) 63/37 Sn/Pb - non - RoHS
- (2) (SAC 305) 96.5/3/0.5 Sn/Ag/Cu - RoHS

Pre-Heating

Pre-heating is recommended for good soldering and to avoid damage to the DO-214, Compak, TO-252 devices, other components, and the substrate. Maximum pre-heating temperature is 165 °C while the maximum pre-heating duration may be 10 seconds. However, atmospheric pre-heating is permissible for several minutes provided temperature does not exceed 125 °C.

Gluing Recommendations

Prior to wave soldering, surface mount devices (SMDs) must be fixed to the PCB or substrate by means of an appropriate adhesive. The adhesive (in most cases a multicomponent adhesive) has to fulfill the following demands:

- Uniform viscosity to ensure easy coating
- No chemical reactions upon hardening in order not to deteriorate component and PC board
- Straightforward exchange of components in case of repair

Low-temperature Solder for Reducing PC Board Damage

In testing and troubleshooting surface-mounted components, changing parts can be time consuming. Moreover, desoldering and soldering cycles can loosen and damage circuit-board pads. Use low-temperature solder to minimize damage to the PC board and to quickly remove a component. One low-temperature alloy is indium-tin, in a 50/50 mixture. It melts between 118 °C and 125 °C, and tin-lead melts at 183 °C. If a component needs replacement, holding the board upside down and heating the area with a heat gun will cause the component to fall off. Performing the operation quickly minimizes damage to the board and component.

Proper surface preparation is necessary for the In-Sn alloy to wet the surface of the copper. The copper must be clean, and you must add flux to allow the alloy to flow freely. You can use rosin dissolved in alcohol. Perform the following steps:

- (1) Cut a small piece of solder and flow it onto one of the pads.
- (2) Place the surface-mount component on the pad and melt the soldered pad to its pin while aligning the part. (This operation places all the pins flat onto their pads.)

- (3) Cut small pieces of the alloy solder and flow each piece onto each of the other legs of the component.

Indium-tin solder is available from ACI Alloys, San Jose, CA and Indium Corporation of America, Utica, NY.

Multi-use Footprint

Package soldering footprints can be designed to accommodate more than one package. Figure AN1005.8 shows a footprint design for using both the Compak and an SOT-223. Using the dual pad outline makes it possible to use more than one supplier source.

Cleaning Recommendations

Using solvents for PC board or substrate cleaning is permitted from approximately 70 °C to 80 °C.

The soldered parts should be cleaned with azeotrope solvent followed by a solvent such as methol, ethyl, or isopropyl alcohol.

Ultrasonic cleaning of surface mount components on PCBs or substrates is possible.

The following guidelines are recommended when using ultrasonic cleaning:

- Cleaning agent: Isopropanol
- Bath temperature: approximately 30 °C
- Duration of cleaning: MAX 30 seconds
- Ultrasonic frequency: 40 kHz
- Ultrasonic changing pressure: approximately 0.5 bar

Cleaning of the parts is best accomplished using an ultrasonic cleaner which has approximately 20 W of output per one liter of solvent. Replace the solvent on a regular basis.

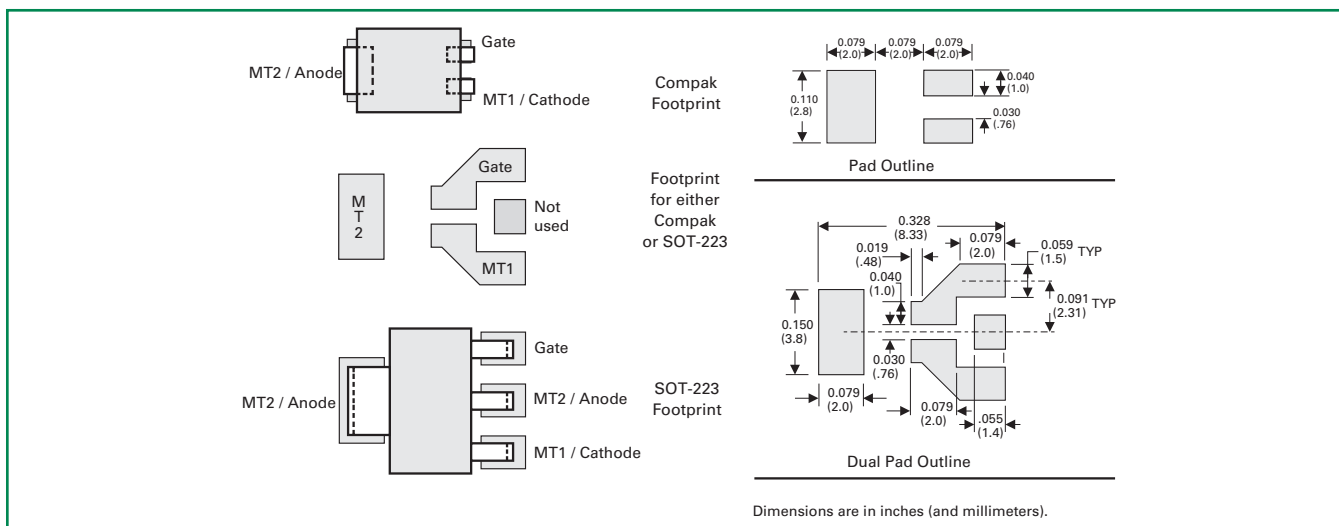


Figure AN10058 Dual Footprint for Compak Package

Thyristor and Rectifier Testing Using Curve Tracers

Introduction

One of the most useful and versatile instruments for testing semiconductor devices is the curve tracer (CT). Tektronix is the best known manufacturer of curve tracers and produces four basic models: 575, 576, 577 and 370. These instruments are specially adapted CRT display screens with associated electronics such as power supplies, amplifiers, and variable input and output functions that allow the user to display the operating characteristics of a device in an easy-to-read, standard graph form. Operation of Tektronix CTs is simple and straightforward and easily taught to non-technical personnel. Although widely used by semiconductor manufacturers for design and analytical work, the device consumer will find many uses for the curve tracer, such as incoming quality control, failure analysis, and supplier comparison. Curve tracers may be easily adapted for go-no go production testing. Tektronix also supplies optional accessories for specific applications along with other useful hardware.

Tektronix Equipment

Although Tektronix no longer produces curve tracer model 575, many of the units are still operating in the field, and it is still an extremely useful instrument. The 576, 577 and 370 are current curve tracer models and are more streamlined in their appearance and operation. The 577 is a less elaborate version of the 576, yet retains all necessary test functions.

The following basic functions are common to all curve tracers:

- **Power supply** supplies positive DC voltage, negative DC voltage, or AC voltage to bias the device. Available power is varied by limiting resistors.
- **Step generator** supplies current or voltage in precise steps to control the electrode of the device. The number, polarity, and frequency of steps are selectable.
- **Horizontal amplifier** displays power supply voltage as applied to the device. Scale calibration is selectable.
- **Vertical amplifier** displays current drawn from the supply by the device. Scale calibration is selectable.

Curve tracer controls for beam position, calibration, pulse operation, and other functions vary from model to model. The basic theory of operation is that for each curve one terminal is driven with a constant voltage or current and the other one is swept with a half sinewave of voltage. The driving voltage is stepped through several values, and a different trace is drawn on each sweep to generate a family of curves.

Limitations, Accuracy, and Correlation

Although the curve tracer is a highly versatile device, it is not capable of every test that one may wish to perform on semiconductor devices such as dv/dt , secondary reverse breakdown, switching speeds, and others. Also, tests at very high currents and/or voltages are difficult to conduct accurately and without damaging the devices. A special high-current test fixture available from Tektronix can extend operation to 200 A pulsed peak. Kelvin contacts available on the 576 and 577 eliminate inaccuracy in voltage measured at high current (V_{TM}) by sensing voltage drop due to contact resistance and subtracting from the reading.

Accuracy of the unit is within the published manufacturer's specification. Allow the curve tracer to warm up and stabilize before testing begins. Always expand the horizontal or vertical scale as far as possible to increase the resolution. Be judicious in recording data from the screen, as the trace line width and scale resolution factor somewhat limit the accuracy of what may be read. Regular calibration checks of the instrument are recommended. Some users keep a selection of calibrated devices on hand to verify instrument operation when in doubt. Re-calibration or adjustment should be performed only by qualified personnel.

Often discrepancies exist between measurements taken on different types of instrument.

In particular, most semiconductor manufacturers use high-speed, computerized test equipment to test devices. They test using very short pulses. If a borderline unit is then measured on a curve tracer, it may appear to be out of specification. The most common culprit here is heat. When a semiconductor device increases in temperature due to current flow, certain characteristics may change, notably gate characteristics on SCRs, gain on transistors, leakage, and so on. It is very difficult to operate the curve tracer in such a way as to eliminate the heating effect. Pulsed or single-trace operation helps reduce this problem, but care should be taken in comparing curve tracer measurements to computer tests. Other factors such as stray capacitances, impedance matching, noise, and device oscillation also may create differences.

Safety (Cautions and Warnings)

Adhere rigidly to Tektronix safety rules supplied with each curve tracer. No attempt should be made to defeat any of the safety interlocks on the device as the curve tracer can produce a lethal shock. Also, older 575 models do not have the safety interlocks as do the new models. Take care never to touch any device or open the terminal while energized.

WARNING: Devices on the curve tracer may be easily damaged from electrical overstress.

Follow these rules to avoid destroying devices:

- Familiarize yourself with the expected maximum limits of the device.
- Limit the current with the variable resistor to the minimum necessary to conduct the test.
- Increase power slowly to the specified limit.
- Watch for device “runaway” due to heating.
- Apply and increase gate or base drive slowly and in small steps.
- Conduct tests in the minimum time required.

General Test Procedures

Read all manuals before operating a curve tracer.

Perform the following manufacturer’s equipment check:

1. Turn on and warm up curve tracer, but turn off, or down, all power supplies.
2. Correctly identify terminals of the device to be tested. Refer to the manufacturer’s guide if necessary.
3. Insert the device into the test fixture, matching the device and test terminals.
4. Remove hands from the device and/or close interlock cover.
5. Apply required bias and/or drive.
6. Record results as required.
7. Disconnect all power to the device before removing.

Model 576 Curve Tracer Procedures

The following test procedures are written for use with the model 576 curve tracer. (Figure AN1006.1)

See “Model 370 Curve Tracer Procedure Notes” on page AN1006-16 and “Model 577 Curve Tracer Procedure Notes” on page AN1006-18 for setting adjustments required when using model 370 and 577 curve tracers.

The standard 575 model lacks AC mode, voltage greater than 200 V, pulse operations, DC mode, and step offset controls. The 575 MOD122C does allow voltage up to 400 V, including 1500 V in an AC mode. Remember that at the time of design, the 575 was built to test only transistors and diodes. Some ingenuity, experience, and external hardware may be required to test other types of devices.

For further information or assistance in device testing on Tektronix curve tracers, contact the Littelfuse Applications Engineering group.

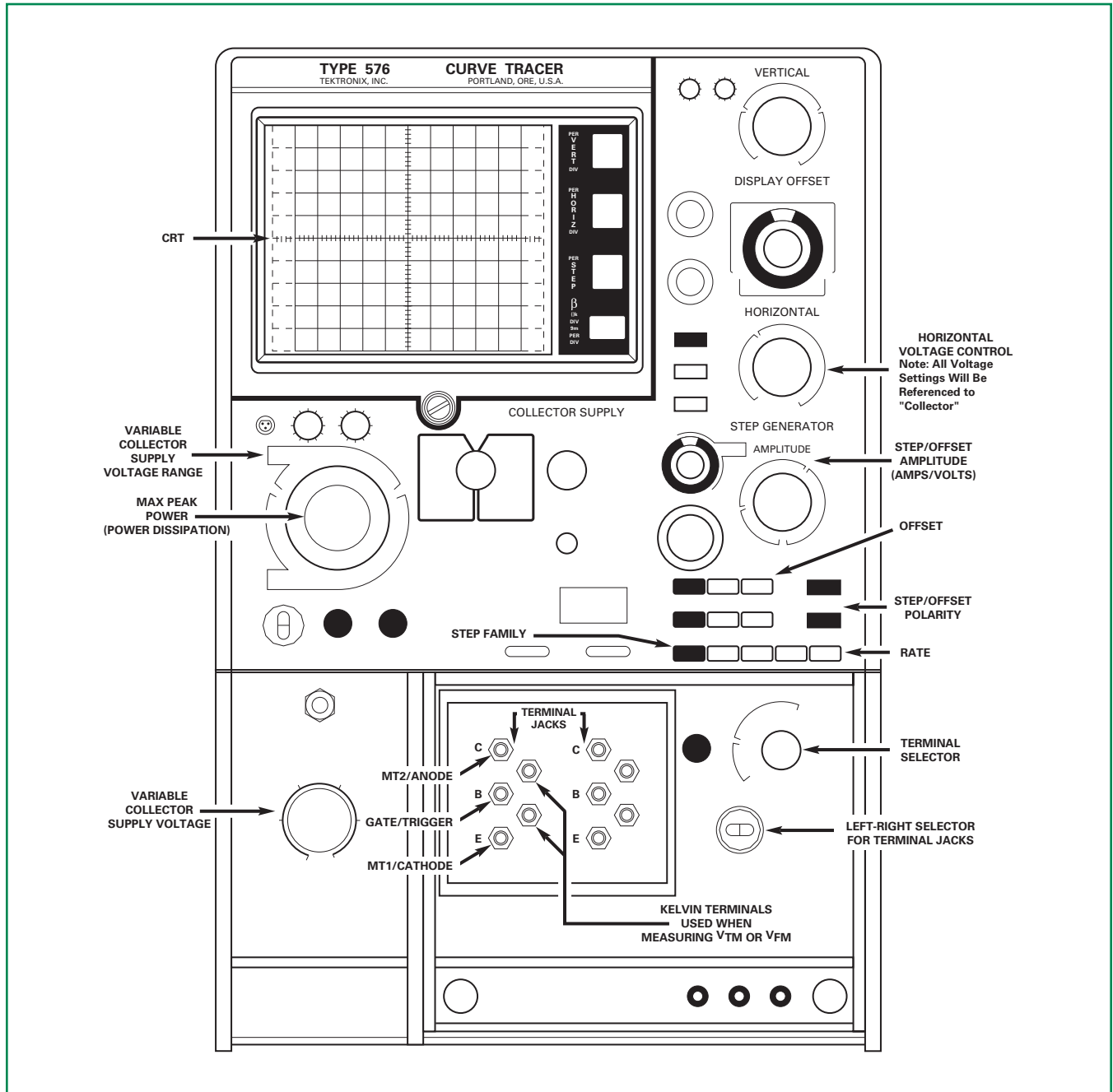


Figure AN1006.1 Tektronix Model 576 Curve Tracer

Power Rectifiers

The rectifier is a unidirectional device which conducts when forward voltage (above 0.7 V) is applied.

To connect the rectifier:

1. Connect *Anode to Collector Terminal (C)*.
2. Connect *Cathode to Emitter Terminal (E)*.

To begin testing, perform the following procedures.

Procedure 1: V_{RRM} and I_{RM}

To measure the V_{RRM} and I_{RM} parameter:

1. Set **Variable Collector Supply Voltage Range** to 1500 V. (2000 V on 370)
2. Set **Horizontal** knob to sufficient scale to allow viewing of trace at the required voltage level (100 V/DIV for 400 V and 600 V devices and 50 V/DIV for 200 V devices).
3. Set **Mode** to *Leakage*.
4. Set **Vertical** knob to 100 μ A/DIV. (Due to leakage setting, the CRT readout will be 100 nA per division.)
5. Set **Terminal Selector** to *Emitter Grounded-Open Base*.
6. Set **Polarity** to (-).
7. Set **Power Dissipation** to 2.2 W. (2 W on 370)
8. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
9. Increase **Variable Collector Supply Voltage** to the rated V_{RRM} of the device and observe the dot on the CRT. Read across horizontally from the dot to the vertical current scale. This measured value is the leakage current. (Figure AN1006.2)

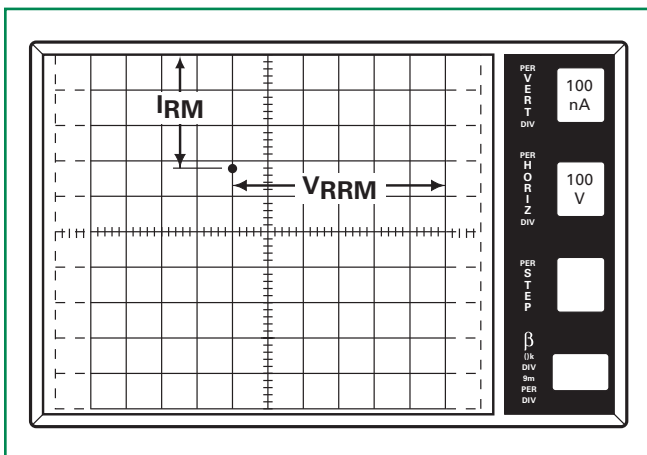


Figure AN1006.2 $I_{RM} = 340 \text{ nA}$ at $V_{RRM} = 600 \text{ V}$

Procedure 2: V_{FM}

Before testing, note the following:

- A Kelvin test fixture is required for this test. If a

Kelvin fixture is not used, an error in measurement of V_{FM} will result due to voltage drop in fixture. If a Kelvin fixture is not available, Figure AN1006.3 shows necessary information to wire a test fixture with Kelvin connections.

- Due to the current limitations of standard curve tracer model 576, V_{FM} cannot be tested at rated current without a Tektronix model 176 high-current module. The procedure below is done at $I_{T(RMS)} = 10 \text{ A}$ (20 A_{PK}). This test parameter allows the use of a standard curve tracer and still provides an estimate of whether V_{FM} is within specification.

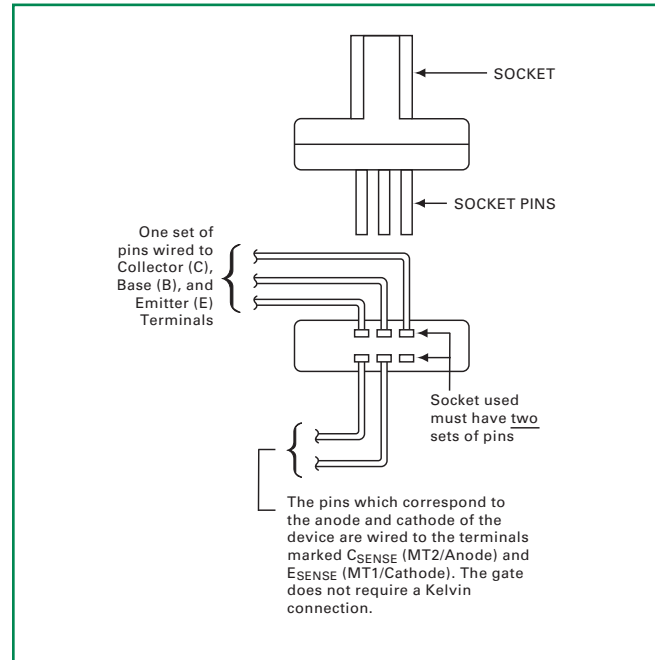


Figure AN1006.3 Instructions for Wiring Kelvin Socket

To measure the V_{FM} parameter:

1. Set **Variable Collector Supply Voltage Range** to 15 Max Peak Volts. (16 V on 370)
2. Set **Horizontal** knob to 0.5 V/DIV.
3. Set **Mode** to *Norm*.
4. Set **Vertical** knob to 2 A/DIV.
5. Set **Power Dissipation** to 220 W (100 W on 577).
6. Set **Polarity** to (+).
7. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
8. Increase **Variable Collector Supply Voltage** until current reaches 20 A.

WARNING: Limit test time to 15 seconds maximum.

To measure V_{FM} , follow along horizontal scale to the point where the trace crosses the 20 A axis. The distance from the left-hand side of scale to the crossing point is the V_{FM} value. (Figure AN1006.4)

Note: Model 370 current is limited to 10 A.

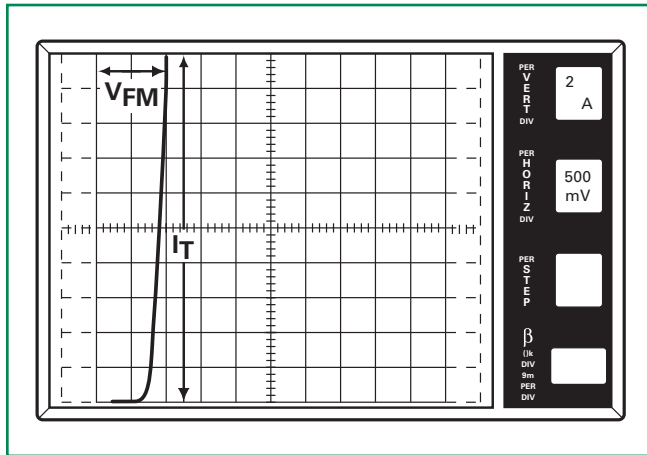


Figure AN1006.4 $V_{FM} = 1 \text{ V}$ at $I_{PK} = 20 \text{ A}$

SCRs

SCRs are half-wave unidirectional rectifiers turned on when current is supplied to the gate terminal. If the current supplied to the gate is to be in the range of 12 μA and 500 μA , then a sensitive SCR is required; if the gate current is between 1 mA and 50 mA, then a non-sensitive SCR is required.

To connect the rectifier:

1. Connect *Anode to Collector Terminal (C)*.
2. Connect *Cathode to Emitter Terminal (E)*.

Note: When sensitive SCR's are being tested, a 1 k Ω resistor must be connected between the gate and the cathode, except when testing I_{GT} .

To begin testing, perform the following procedures.

Procedure 1: $V_{DRM} / V_{RRM} / I_{DRM} / I_{RRM}$

To measure the $V_{DRM} / V_{RRM} / I_{DRM}$ and I_{RRM} parameter:

1. Set **Variable Collector Supply Voltage Range** to appropriate *Max Peak Volts* for device under test. (Value selected should be equal to or greater than the device's V_{DRM} rating.)
2. Set **Horizontal** knob to sufficient scale to allow viewing of trace at the required voltage level. (The 100 V/DIV scale should be used for testing devices having a V_{DRM} value of 600 V or greater; the 50 V/DIV scale for testing parts rated from 300 V to 500 V, and so on.)
3. Set **Mode** to *Leakage*.
4. Set **Polarity** to (+).
5. Set **Power Dissipation** to 0.5 W (0.4 W on 370)
6. Set **Terminal Selector** to *Emitter Grounded-Open Base*.
7. Set **Vertical** knob to approximately ten times the maximum leakage current (I_{DRM} , I_{RRM}) specified for the device. (For sensitive SCR's, set to 50 μA .)

Note: The CRT screen readout should show 1% of the maximum leakage current if the vertical scale is divided by 1,000 when leakage current mode is used.

Procedure 2: V_{DRM} / I_{DRM}

To measure the V_{DRM} and I_{DRM} parameter:

1. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
2. Set **Variable Collector Supply Voltage** to the rated V_{DRM} of the device and observe the dot on CRT. Read across horizontally from the dot to the vertical current scale. This measured value is the leakage current. (Figure AN1006.5)

WARNING: Do NOT exceed V_{DRM} / V_{RRM} rating of SCR's, Triacs, or Quadracs. These devices can be damaged.

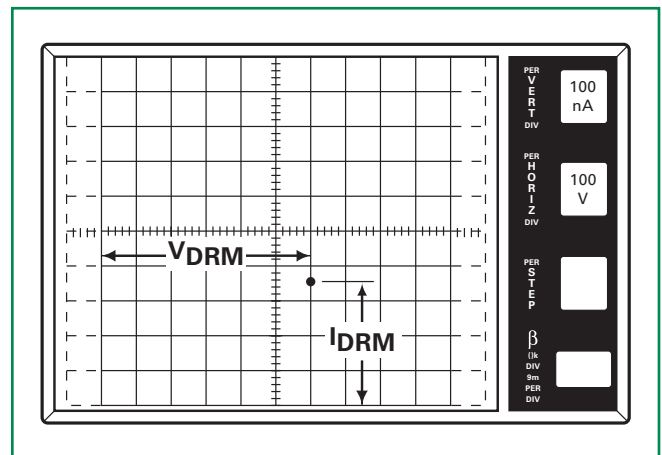


Figure AN1006.5 $I_{DRM} = 350 \text{ nA}$ at $V_{DRM} = 600 \text{ V}$

Procedure 3: V_{RRM} / I_{RRM}

To measure the V_{RRM} and I_{RRM} parameter:

1. Set **Polarity** to (-).
2. Repeat Steps 1 and 2 (V_{DRM} , I_{DRM}) except substitute V_{RRM} value for V_{DRM} . (Figure AN1006.6)

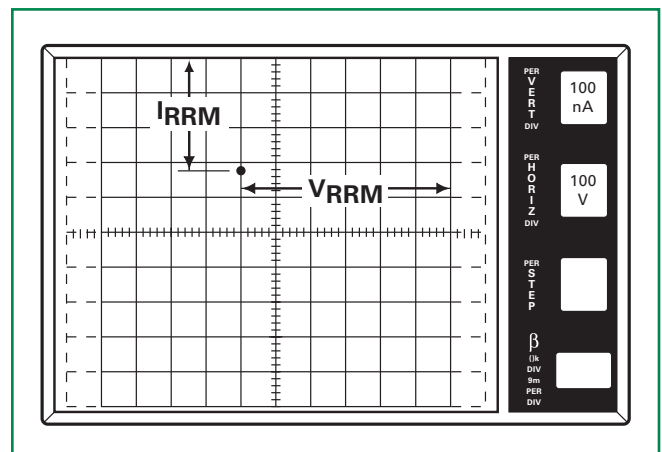


Figure AN1006.6 $I_{RRM} = 340 \text{ nA}$ at $V_{RRM} = 600 \text{ V}$

Procedure 4: V_{TM}

To measure the V_{TM} parameter:

1. Set **Terminal Selector** to *Step Generator-Emitter Grounded*.
2. Set **Polarity** to (+).
3. Set **Step/Offset Amplitude** to twice the maximum I_{GT} rating of the device (to ensure the device turns on). For sensitive SCRs, set to 2 mA.
4. Set **Max Peak Volts** to 15 V. (16 V on 370)
5. Set **Offset** by depressing 0 (zero).
6. Set **Rate** by depressing *Norm*.
7. Set **Step Family** by depressing *Rep* (repetitive).
8. Set **Mode** to DC.

9. Set **Horizontal** knob to 0.5 V/DIV.
10. Set **Power Dissipation** to 220 W (100 W on 577).
11. Set **Number of Steps** to 1. (Set steps to 0 (zero) on 370.)
12. Set **Vertical** knob to a sufficient setting to allow the viewing of 2 times the $I_{T(RMS)}$ rating of the device ($I_{T(peak)}$) on CRT.

Before continuing with testing, note the following:

- (1) Due to the excessive amount of power that can be generated in this test, only parts with an $I_{T(RMS)}$ rating of 6 A or less should be tested on standard curve tracer. If testing devices above 6 A, a Tektronix model 176 high-current module is required.
- (2) A Kelvin test fixture is required for this test. If a Kelvin fixture is not used, an error in measurement of V_{TM} will result due to voltage drop in the fixture. If a Kelvin fixture is not available, Figure AN1006.3 shows necessary information to wire a test fixture with Kelvin connectors.

13. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
14. Increase **Variable Collector Supply Voltage** until current reaches rated $I_{T(peak)}$, which is twice the $I_{T(RMS)}$ rating of the SCR under test.

Note: Model 370 current is limited to 10 A.

WARNING: Limit test time to 15 seconds maximum after the Variable Collector Supply has been set to $I_{T(peak)}$. After the Variable Collector Supply Voltage has been set to $I_{T(peak)}$, the test time can automatically be shortened by changing Step Family from repetitive to single by depressing the Single button.

To measure V_{TM} , follow along horizontal scale to the point where the trace crosses the $I_{T(peak)}$ value. The distance from the left-hand side of scale to the intersection point is the V_{TM} value. (Figure AN1006.7)

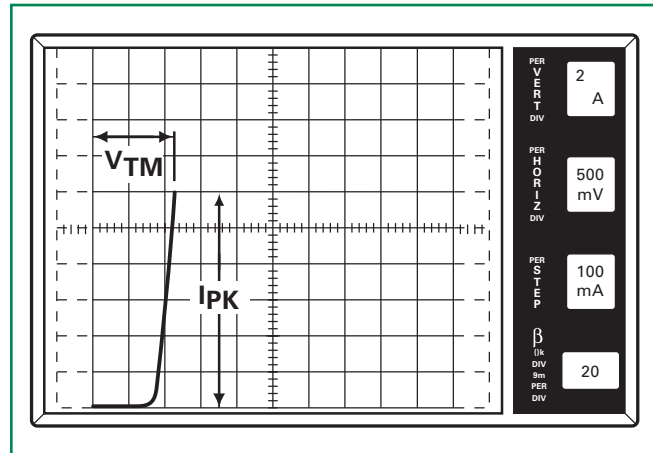


Figure AN1006.7 $V_{TM} = 1.15 \text{ V}$ at $I_{T(peak)} = 12 \text{ A}$

Procedure 5: I_H

To measure the I_H parameter:

1. Set **Polarity** to (+).
 2. Set **Power Dissipation** to 2.2 W. (2 W on 370)
 3. Set **Max Peak Volts** to 75 V. (80 V on 370)
 4. Set **Mode** to DC.
 5. Set **Horizontal** knob to *Step Generator*.
 6. Set **Vertical** knob to approximately 10 percent of the maximum I_H specified.
- Note: Due to large variation of holding current values, the scale may have to be adjusted to observe holding current.
7. Set **Number of Steps** to 1.
 8. Set **Offset** by depressing 0 (zero). (Press *Aid* and *Oppose* at the same time on 370.)
 9. Set **Step/Offset Amplitude** to twice the maximum I_{GT} of the device.
 10. Set **Terminal Selector** to *Step Generator-Emitter Grounded*.
 11. Set **Step Family** by depressing *Single*.
 12. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
 13. Increase **Variable Collector Supply Voltage** to maximum position (100).
 14. Set **Step Family** by depressing *Single*. (This could possibly cause the dot on CRT to disappear, depending on the vertical scale selected.)
 15. Change **Terminal Selector** from *Step Generator-Emitter Grounded* to *Open Base-Emitter Grounded*.
 16. Decrease **Variable Collector Supply Voltage** to the point where the line on the CRT changes to a dot. The position of the beginning point of the line, just before the line becomes a dot, represents the holding current value. (Figure AN1006.8)

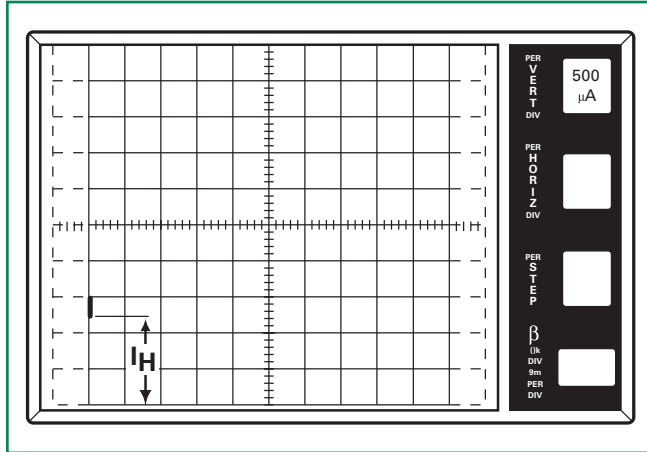


Figure AN1006.8 $I_H = 1.2 \text{ mA}$

Procedure 6: I_{GT} and V_{GT}

To measure the I_{GT} and V_{GT} parameter:

1. Set **Polarity** to (+).
2. Set **Number of Steps** to 1.
3. Set **Offset** by depressing *Aid*.
4. Set **Offset Multiplier** to 0 (zero). (Press *Aid* and *Oppose* at the same time on 370.)
5. Set **Terminal Selector** to *Step Generator-Emitter Grounded*.
6. Set **Mode** to *Norm*.
7. Set **Max Peak Volts** to 15 V. (16 V on 370)
8. Set **Power Dissipation** to 2.2 W. (2 W on 370) For sensitive SCRs, set at 0.5 W. (0.4 W on 370)
9. Set **Horizontal** knob to 2 V/DIV.
10. Set **Vertical** knob to 50 mA/DIV.
11. Increase **Variable Collector Supply Voltage** until voltage reaches 12 V on CRT.
12. After 12 V setting is completed, change **Horizontal** knob to *Step Generator*.

Procedure 7: I_{GT}

To measure the I_{GT} parameter:

1. Set **Step/Offset Amplitude** to 20% of maximum rated I_{GT}
Note: R_{GK} should be removed when testing I_{GT}
2. Set **Left-Right Terminal Jack Selector** to correspond with location of the test fixture.
3. Gradually increase **Offset Multiplier** until device reaches the conduction point. (Figure AN1006.9) Measure I_{GT} by following horizontal axis to the point where the vertical line crosses axis. This measured value is I_{GT} (On 370, I_{GT} will be numerically displayed on screen under offset value.)

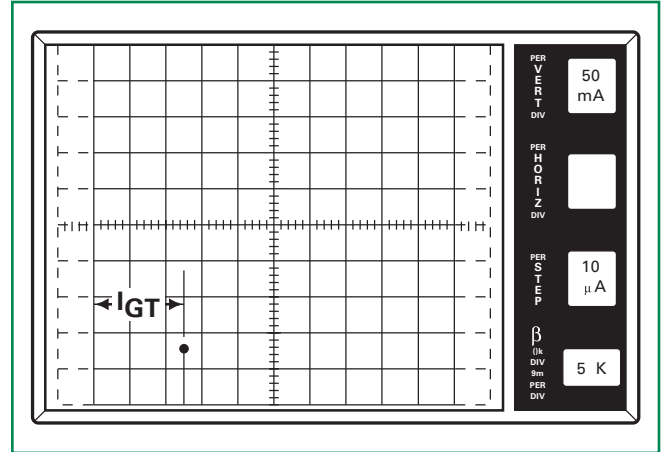


Figure AN1006.9 $I_{GT} = 25 \mu\text{A}$

Procedure 8: V_{GT}

To measure the V_{GT} parameter:

1. Set **Offset Multiplier** to 0 (zero). (Press *Aid* and *Oppose* at the same time on 370.)
2. Set **Step Offset Amplitude** to 20% rated V_{GT} .
3. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
4. Gradually increase **Offset Multiplier** until device reaches the conduction point. (Figure AN1006.10) Measure V_{GT} by following horizontal axis to the point where the vertical line crosses axis. This measured value is V_{GT} . (On 370, V_{GT} will be numerically displayed on screen, under offset value.)

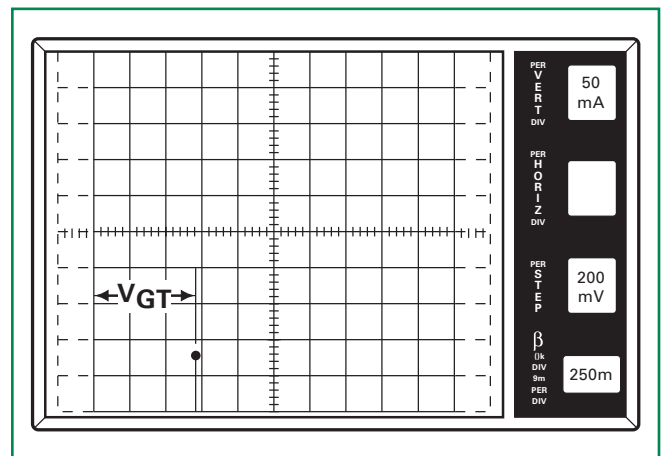


Figure AN1006.10 $V_{GT} = 580 \text{ mV}$

Triacs

Triacs are full-wave bidirectional AC switches turned on when current is supplied to the gate terminal of the device. If gate control in all four quadrants is required, then a sensitive gate Triac is needed, whereas a standard Triac can be used if gate control is only required in Quadrants I through III.

To connect the Triac:

1. Connect the *Gate* to the *Base Terminal* (B).
2. Connect *MT1* to the *Emitter Terminal* (E).
3. Connect *MT2* to the *Collector Terminal* (C).

To begin testing, perform the following procedures.

Procedure 1: (+) V_{DRM} , (+) I_{DRM} , (-) V_{DRM} , (-) I_{DRM}

Note: The (+) and (-) symbols are used to designate the polarity MT2 with reference to MT1.

To measure the (+) V_{DRM} , (+) I_{DRM} , (-) V_{DRM} , and (-) I_{DRM} parameter:

1. Set **Variable Collector Supply Voltage Range** to appropriate *Max Peak Volts* for device under test. (Value selected should be equal to the device's V_{DRM} rating.)

WARNING: DO NOT exceed V_{DRM}/V_{RRM} rating of SCRs, Triacs, or Quadracs. These devices can be damaged.

2. Set **Horizontal** knob to sufficient scale to allow viewing of trace at the required voltage level. (The 100 V/DIV scale should be used for testing devices having a V_{DRM} rating of 600 V or greater; the 50 V/DIV scale for testing parts rated from 30 V to 500 V, and so on.)
3. Set **Mode** to *Leakage*.
4. Set **Polarity** to (+).
5. Set **Power Dissipation** to 0.5 W. (0.4 W on 370)
6. Set **Terminal Selector** to *Emitter Grounded-Open Base*.
7. Set **Vertical** knob to ten times the maximum leakage current (I_{DRM}) specified for the device.

Note: The CRT screen readout should show 1% of the maximum leakage current. The vertical scale is divided by 1,000 when leakage mode is used.

Procedure 2: (+) V_{DRM} , (+) I_{DRM}

To measure the (+) V_{DRM} and (+) I_{DRM} parameter:

1. Set Left-Right Terminal Jack Selector to correspond with location of the test fixture.
2. Increase Variable Collector Supply Voltage to the rated V_{DRM} of the device and observe the dot on the CRT. Read across horizontally from the dot to the vertical current scale. This measured value is the leakage

current. (Figure AN1006.11)

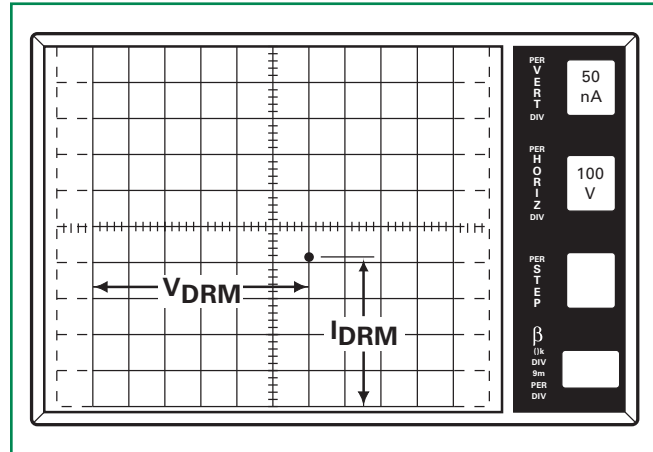


Figure AN1006.11 (+) I_{DRM} = 205 nA at (+) V_{DRM} = 600 V

Procedure 3: (-) V_{DRM} , (-) I_{DRM}

To measure the (-) V_{DRM} and (-) I_{DRM} parameter:

1. Set **Polarity** to (-).
2. Repeat Procedures 1 and 2. (Read measurements from upper right corner of the screen.)

Procedure 4: V_{TM} (Forward and Reverse)

To measure the V_{TM} (Forward and Reverse) parameter:

1. Set **Terminal Selector** to Step Generator-Emitter Grounded.
2. Set **Step/Offset Amplitude** to twice the maximum I_{GT} rating of the device (to insure the device turns on).
3. Set **Variable Collector Supply Voltage Range** to 15 V *Max Peak volts*. (16 V on 370)
4. Set **Offset** by depressing 0 (zero).
5. Set **Rate** by depressing *Norm*.
6. Set **Step Family** by depressing *Rep* (Repetitive).
7. Set **Mode** to *Norm*.
8. Set **Horizontal** knob to 0.5 V/DIV.
9. Set **Power Dissipation** to 220 W (100 W on 577).
10. Set **Number of Steps** to 1.
11. Set **Step/Offset Polarity** to non-inverted (button extended; on 577 button depressed).
12. Set **Vertical** knob to a sufficient setting to allow the viewing of 1.4 times the $I_{T(RMS)}$ rating of the device [$I_{T(peak)}$ on CRT].

Note the following:

- Due to the excessive amount of power that can be generated in this test, only parts with an $I_{T(RMS)}$ rating of 8 A or less should be tested on standard curve tracer. If testing devices above 8 A, a Tektronix model 176 high-current module is required.
- A Kelvin test fixture is required for this test. If a

Kelvin fixture is not used, an error in measurement of V_{TM} will result due to voltage drop in fixture. If a Kelvin fixture is not available, Figure AN1006.3 shows necessary information to wire a test fixture with Kelvin connections.

Procedure 5: V_{TM} (Forward)

To measure the V_{TM} (Forward) parameter:

1. Set **Polarity** to (+).
2. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
3. Increase **Variable Collector Supply Voltage** until current reaches rated $I_{T(peak)}$, which is 1.4 times $I_{T(RMS)}$ rating of the Triac under test.

Note: Model 370 current is limited to 10 A.

WARNING: Limit test time to 15 seconds maximum. After the Variable Collector Supply Voltage has been set to $I_{T(peak)}$, the test time can automatically be set to a short test time by changing Step Family from repetitive to single by depressing the Single button.

To measure V_{TM} , follow along horizontal scale to the point where the trace crosses the $I_{T(peak)}$ value. The distance from the left-hand side of scale to the crossing point is the V_{TM} value. (Figure AN1006.12)

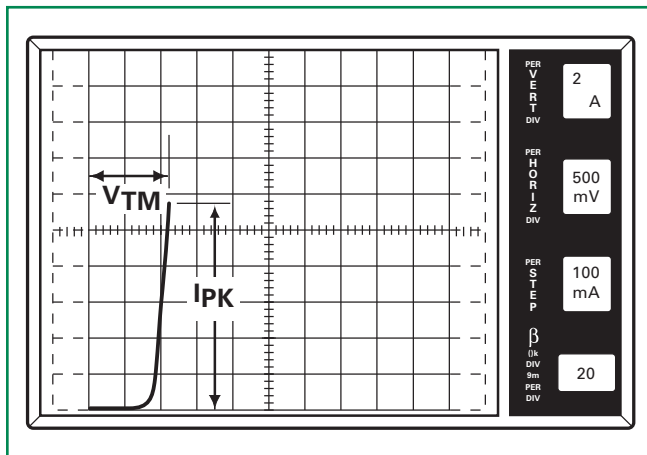


Figure AN1006.12 V_{TM} (forward) = 1.1 V at I_{PK} = 11.3 A (8 A rms)

Procedure 6: V_{TM} (Reverse)

To measure the V_{TM} (Reverse) parameter:

1. Set **Polarity** to (-).
2. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
3. Increase **Variable Collector Supply Voltage** until current reaches rated $I_{T(peak)}$.
4. Measure $V_{TM(Reverse)}$ similar to Figure AN1006.12, except from upper right hand corner of screen.

Procedure 7: I_H (Forward and Reverse)

To measure the I_H (Forward and Reverse) parameter:

1. Set **Step/Offset Amplitude** to twice the I_{GT} rating of the device.
2. Set **Power Dissipation** to 10 W.
3. Set **Max Peak Volts** to 75 V. (80 V on 370)
4. Set **Mode** to DC.
5. Set **Horizontal** knob to Step Generator.
6. Set **Vertical** knob to approximately 10% of the maximum I_H specified.

Note: Due to large variation of holding current values, the scale may have to be adjusted to observe holding current.

7. Set **Number of Steps** to 1.
8. Set **Step/Offset Polarity** to non-inverted (button extended, on 577 button depressed).
9. Set **Offset** by depressing 0 (zero). (Press Aid and Oppose at same time on 370.)
10. Set **Terminal Selector** to Step Generator-Emitter Grounded.

Procedure 8: I_H (Forward)

To measure the I_H (Forward) parameter:

1. Set **Polarity** to (+).
 2. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
 3. Increase **Variable Collector Supply Voltage** to maximum position (100).
 4. Set **Step Family** by depressing Single.
- This could possibly cause the dot on the CRT to disappear, depending on the vertical scale selected).
5. Decrease **Variable Collector Supply Voltage** to the point where the line on the CRT changes to a dot. The position of the beginning point of the line, just before the line becomes a dot, represents the holding current value. (Figure AN1006.13)

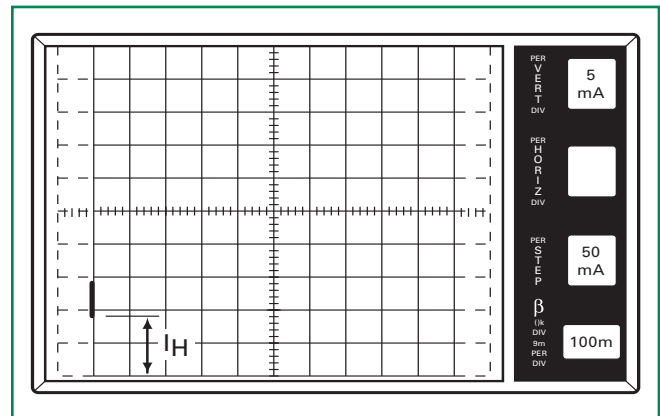


Figure AN1006.13 I_H (Forward) = 8.2 mA

Procedure 9: $I_{H(Reverse)}$

To measure the $I_{H(Reverse)}$ parameter:

1. Set **Polarity** to (-).
2. Repeat Procedure 7 measuring $I_{H(Reverse)}$. (Read measurements from upper right corner of the screen.)

Procedure 10: I_{GT}

To measure the I_{GT} parameter:

1. Set **Polarity** to (+).
2. Set **Number of Steps** to 1. (Set number of steps to 0 (zero) on 370.)
3. Set **Offset** by depressing *Aid*. (On 577, also set **Zero** button to *Offset*. Button is extended.)
4. Set **Offset Multiplier** to 0 (zero). (Press *Aid* and *Oppose* at same time on 370.)
5. Set **Terminal Selector** to *Step Generator-Emitter Grounded*.
6. Set **Mode** to **Norm**.
7. Set **Max Peak Volts** to 15 V. (16 V on 370)
8. Set **Power Dissipation** to 10 W.
9. Set **Step Family** by depressing *Single*.
10. Set **Horizontal** knob to 2 V/DIV.
11. Set **Vertical** knob to 50 mA/DIV.
12. Set **Step/Offset Polarity** to non-inverted position (button extended, on 577 button depressed).
13. Set **Variable Collector Supply Voltage** until voltage reaches 12 V on CRT.
14. After 12 V setting is completed, change **Horizontal** knob to *Step Generator*.

Procedure 11: I_{GT} - Quadrant I [MT2 (+) Gate (+)]

To measure the I_{GT} - Quadrant I parameter:

1. Set **Step/Offset Amplitude** to approximately 10% of rated I_{GT} .
2. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
3. Gradually increase **Offset Multiplier** until device reaches conduction point. (Figure AN1006.14) Measure I_{GT} by following horizontal axis to the point where the vertical line passes through the axis. This measured value is I_{GT} . (On 370, I_{GT} is numerically displayed on screen under offset value.)

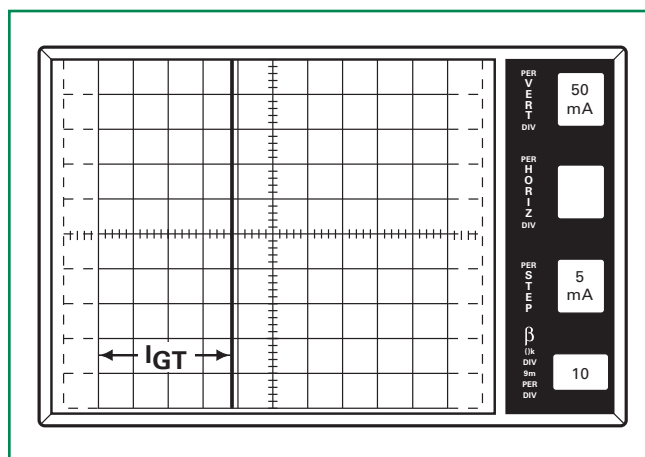


Figure AN1006.14 I_{GT} in Quadrant I = 18.8 mA

Procedure 12: I_{GT} - Quadrant II [MT2 (+) Gate (-)]

To measure the I_{GT} - Quadrant II parameter:

1. Set **Step/Offset Polarity** by depressing *Invert* (release button on 577).
2. Set **Polarity** to (+).
3. Set observed dot to bottom right corner of CRT grid by turning the horizontal position knob. When Quadrant II testing is complete, return dot to original position.
4. Repeat Procedure 11.

Procedure 13: I_{GT} - Quadrant III [MT2 (-) Gate (-)]

To measure the I_{GT} - Quadrant III parameter:

1. Set **Polarity** to (-).
2. Set **Step/Offset Polarity** to non-inverted position (button extended, on 577 button depressed).
3. Repeat Procedure 11. (Figure AN1006.15)

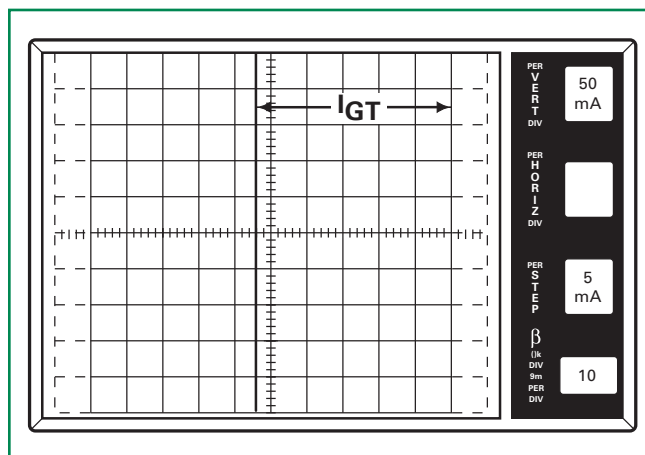


Figure AN1006.15 I_{GT} in Quadrant III = 27 mA

Procedure 14: I_{GT} - Quadrant IV [MT2 (-) Gate (+)]

To measure the I_{GT} - Quadrant IV parameter:

1. Set **Polarity** to (-).
2. Set **Step/Offset Polarity** by depressing *Invert* (release button on 577).
3. Set observed dot to top left corner of CRT grid by turning the **Horizontal** position knob. When Quadrant IV testing is complete, return dot to original position.
4. Repeat Procedure 11.

Procedure 15: V_{GT}

To measure the V_{GT} parameter:

1. Set **Polarity** to (+).
2. Set **Number of Steps** to 1. (Set steps to 0 (zero) on 370.)
3. Set **Offset** by depressing *Aid*. (On 577, also set 0 (zero) button to *Offset*. Button is extended.)
4. Set **Offset Multiplier** to 0 (zero). (Press *Aid* and *Oppose* at same time on 370.)
5. Set **Terminal Selector** to *Step Generator-Emitter Grounded*.
6. Set **Mode** to *Norm*.
7. Set **Max Peak Volts** to 15 V. (16 V on 370)
8. Set **Power Dissipation** to 10 W.
9. Set **Step Family** by depressing *Single*.
10. Set **Horizontal** knob to 2 V/DIV.
11. Set **Step/Offset Polarity** to non-inverted position (button extended, on 577 button depressed).
12. Set **Current Limit** to 500 mA (not available on 577).
13. Increase **Variable Collector Supply Voltage** until voltage reaches 12 V on CRT.
14. After 12 V setting is complete, change **Horizontal** knob to *Step Generator*.

Procedure 16: V_{GT} - Quadrant I [MT2 (+) Gate (+)]

To measure the V_{GT} - Quadrant I parameter:

1. Set **Step/Offset Amplitude** to 20% of rated V_{GT} .
2. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.
3. Gradually increase **Offset Multiplier** until device reaches conduction point. (Figure AN1006.16) Measure V_{GT} by following horizontal axis to the point where the vertical line passes through the axis. This measured value will be V_{GT} . (On 370, V_{GT} will be numerically displayed on screen under offset value.)

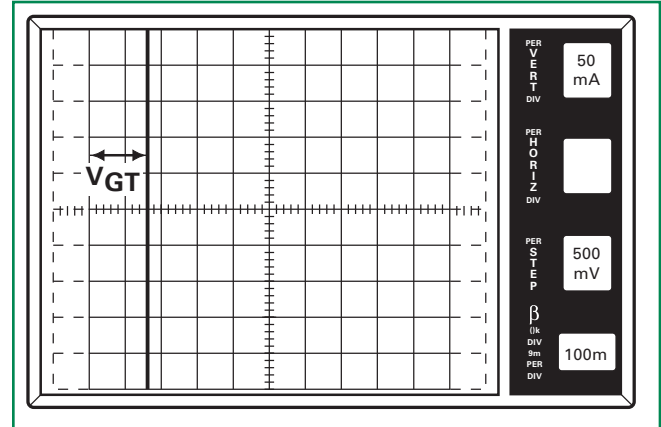


Figure AN1006.16 V_{GT} in Quadrant I = 780 mV

Procedure 17: V_{GT} - Quadrant II [MT2 (+) Gate (-)]

To measure the V_{GT} - Quadrant II parameter:

1. Set **Step/Offset Polarity** by depressing *Invert* (release button on 577).
2. Set **Polarity** to (+).
3. Set observed dot to bottom right corner of CRT grid by turning the **Horizontal** position knob. When Quadrant II testing is complete, return dot to original position.
4. Repeat Procedure 16.

Procedure 18: V_{GT} - Quadrant III [MT2 (-) Gate (-)]

To measure the V_{GT} - Quadrant III parameter:

1. Set **Polarity** to (-).
2. Set **Step/Offset Polarity** to non-inverted position (button extended, on 577 button depressed).
3. Repeat Procedure 16. (Figure AN1006.17)

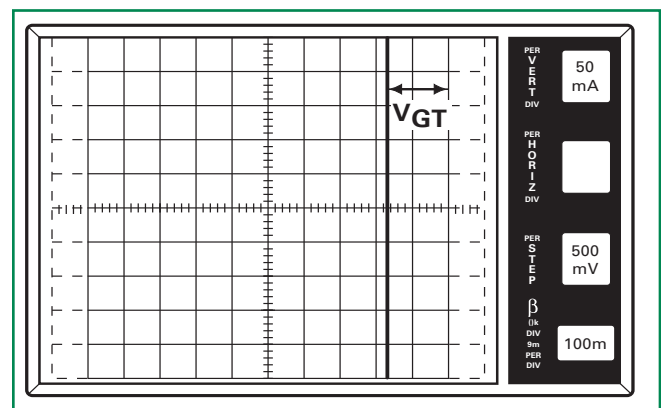


Figure AN1006.17 V_{GT} in Quadrant III = 820 mV

Procedure 19: V_{GT} - Quadrant IV [MT2 (-) Gate (+)]

To measure the V_{GT} - Quadrant IV parameter:

1. Set **Polarity** to (-).
2. Set **Step/Offset Polarity** by depressing *Invert* (release button on 577).

- Set observed dot to top left corner of CRT grid by turning the **Horizontal** position knob. When testing is complete in Quadrant IV, return dot to original position.
- Repeat Procedure 16.

Quadracs

Quadracs are simply Triacs with an internally-mounted DIAC. As with Triacs, Quadracs are bidirectional AC switches which are gate controlled for either polarity of main terminal voltage.

To connect the Quadrac:

- Connect *Trigger* to *Base Terminal* (B).
- Connect *MT1* to *Emitter Terminal* (E).
- Connect *MT2* to *Collector Terminal* (C).

To begin testing, perform the following procedures.

Procedure 1: (+) V_{DRM} , (+) I_{DRM} , (-) V_{DRM} , (-) I_{DRM}

Note: The (+) and (-) symbols are used to designate the polarity of MT2 with reference to MT1.

To measure the (+) V_{DRM} , (+) I_{DRM} , (-) V_{DRM} , and (-) I_{DRM} parameter:

- Set **Variable Collector Supply Voltage Range** to appropriate *Max Peak Volts* for device under test. (Value selected should be equal to or greater than the device's V_{DRM} rating).
- Set **Horizontal** knob to sufficient scale to allow *viewing of trace at the required voltage level*. (The 100 V/DIV scale should be used for testing devices having a V_{DRM} rating of 600 V or greater; the 50 V/DIV scale for testing parts rated from 300 V to 500 V, and so on).
- Set **Mode** to Leakage.
- Set **Polarity** to (+).
- Set **Power Dissipation** to 0.5 W. (0.4 W on 370)
- Set **Terminal Selector** to *Emitter Grounded-Open Base*.
- Set **Vertical** knob to ten times the maximum leakage current (I_{DRM}) specified for the device.

Note: The CRT readout should show 1% of the maximum leakage current. The vertical scale is divided by 1,000 when the leakage mode is used.

Procedure 2: (+) V_{DRM} and (+) I_{DRM}

To measure the (+) V_{DRM} and (+) I_{DRM} parameter:

- Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
- Increase **Variable Collector Supply Voltage** to the rated V_{DRM} of the device and observe the dot on the CRT. (Read across horizontally from the dot to the

vertical current scale.) This measured value is the leakage current. (Figure AN1006.18)

WARNING: Do NOT exceed V_{DRM}/V_{RRM} rating of SCRs, Triacs, or Quadracs. These devices can be damaged.

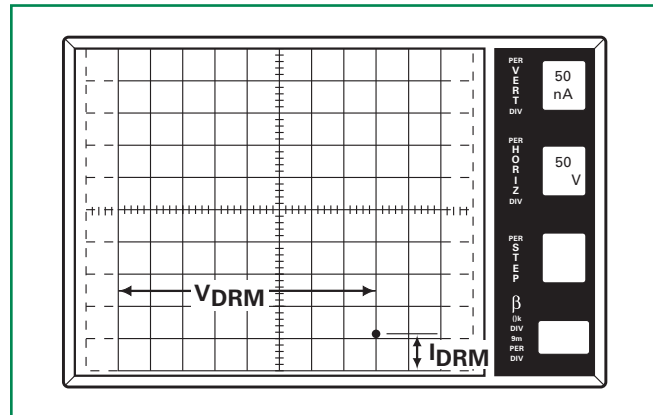


Figure AN1006.18 (+) I_{DRM} = 51 nA at (+) V_{DRM} = 400 V

Procedure 3: (-) V_{DRM} and (-) I_{DRM}

To measure the (-) V_{DRM} and (-) I_{DRM} parameter:

- Set **Polarity** to (-).
- Repeat Procedures 1 and 2. (Read measurements from upper right corner of screen).

Procedure 4: V_{BO} , I_{BO} , V_{BO}

(Quadrac Trigger DIAC or Discrete DIAC)

To connect the Quadrac:

- Connect *MT1* to *Emitter Terminal* (E).
- Connect *MT2* to *Collector Terminal* (C).
- Connect *Trigger Terminal* to *MT2 Terminal* through a 10 Ω resistor.

To measure the V_{BO} , I_{BO} , and ΔV_{BO} parameter:

- Set **Variable Collector Supply Voltage Range** to 75 *Max Peak Volts*. (80 V on 370)
- Set **Horizontal** knob to 10 V/DIV.
- Set **Vertical** knob to 50 μA /DIV.
- Set **Polarity** to AC.
- Set **Mode** to Norm.
- Set **Power Dissipation** to 0.5 W. (0.4 W on 370)
- Set **Terminal Selector** to *Emitter Grounded-Open Base*.

Procedure 5: V_{BO} (Positive and Negative)

To measure the V_{BO} (Positive and Negative) parameter:

1. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
2. Set **Variable Collector Supply Voltage** to 55 V (65 V on 370) and apply voltage to the device under test (D.U.T.) using the **Left Hand Selector Switch**. The peak voltage at which current begins to flow is the V_{BO} value. (Figure AN1006.19)

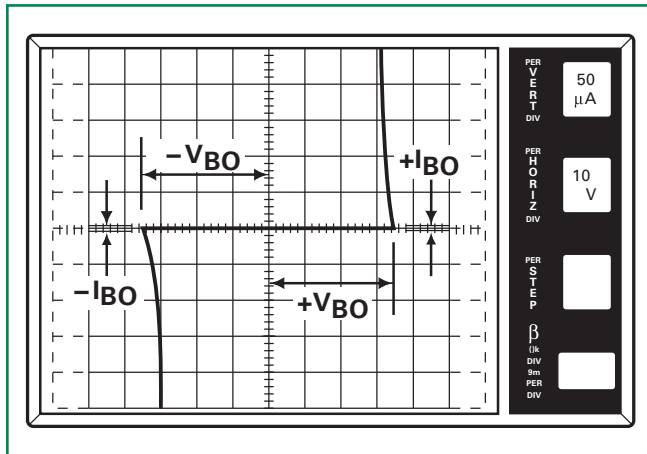


Figure AN1006.19 $(+V_{BO} = 35 \text{ V}; -V_{BO} = 36 \text{ V}; (\pm)I_{BO} < 10 \text{ A}$

Procedure 6: I_{BO} (Positive and Negative)

To measure the I_{BO} (Positive and Negative) parameter, at the V_{BO} point, measure the amount of device current just before the device reaches the breakover point. The measured current at this point is the I_{BO} value.

Note: If I_{BO} is less than 10 μA , the current cannot readily be seen on curve tracer.

Procedure 7: ΔV_{BO} (Voltage Breakover Symmetry)

To measure the ΔV_{BO} (Voltage Breakover Symmetry) parameter:

1. Measure positive and negative V_{BO} values per Procedure 5.
2. Subtract the absolute value of V_{BO} (-) from V_{BO} (+).

The absolute value of the result is:

$$\Delta V_{BO} = | +V_{BO} | - | -V_{BO} |$$

Procedure 8: V_{TM} (Forward and Reverse)

To test V_{TM} , the Quadrac must be connected the same as when testing V_{BO} , I_{BO} , and ΔV_{BO} .

To connect the Quadrac:

1. Connect *MT1* to *Emitter Terminal (E)*.
2. Connect *MT2* to *Collector Terminal (C)*.
3. Connect *Trigger Terminal* to *MT2 Terminal* through a 10 Ω resistor.

Note the following:

Due to the excessive amount of power that can be generated in this test, only parts with an $I_{T(RMS)}$ rating of 8 A or less should be tested on standard curve tracer. If testing devices above 8 A, a Tektronix model 176 high-current module is required.

A Kelvin test fixture is required for this test. If a Kelvin fixture is not used, an error in measurement of V_{TM} will result due to voltage drop in fixture. If a Kelvin fixture is not available, Figure AN1006.3 shows necessary information to wire a test fixture with Kelvin connections.

To measure the V_{TM} (Forward and Reverse) parameter:

1. Set **Terminal Selector** to *Emitter Grounded-Open Base*.
2. Set **Max Peak Volts** to 75 V. (80 V on 370)
3. Set **Mode** to *Norm*.
4. Set **Horizontal** knob to 0.5 V/DIV.
5. Set **Power Dissipation** to 220 watts (100 watts on a 577).
6. Set **Vertical** knob to a sufficient setting to allow the viewing of 1.4 times the $I_{T(RMS)}$ rating of the device $I_{T(peak)}$ on the CRT.

Procedure 9: V_{TM} (Forward)

To measure the V_{TM} (Forward) parameter:

1. Set **Polarity** to (+).
2. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
3. Increase **Variable Collector Supply Voltage** until current reaches rated $I_{T(peak)}$, which is 1.4 times the $I_{T(RMS)}$ rating of the Triac under test.

Note: Model 370 current is limited to 10 A.

WARNING: Limit test time to 15 seconds maximum.

4. To measure V_{TM} , follow along horizontal scale to the point where the trace crosses the $I_{T(peak)}$ value. This horizontal distance is the V_{TM} value. (Figure AN1006.20)

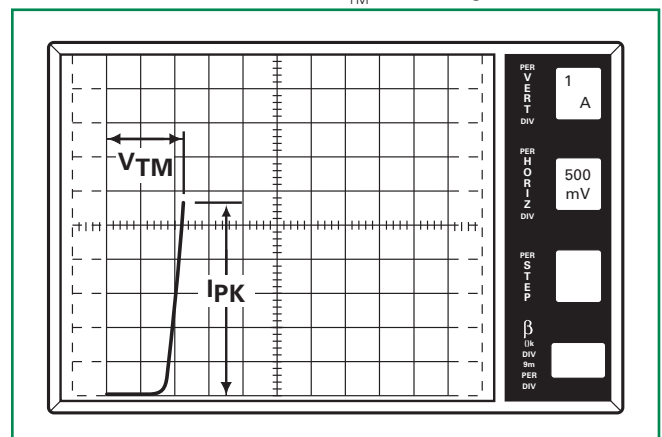


Figure AN1006.20 $V_{TM} \text{ (Forward)} = 1.1 \text{ V at } I_{PK} = 5.6 \text{ A}$

Procedure 10: $V_{TM(Reverse)}$

To measure the $V_{TM(Reverse)}$ parameter:

1. Set **Polarity** to (-).
2. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
3. Increase **Variable Collector Supply Voltage** until current reaches rated $I_{T(peak)}$.
4. Measure $V_{TM(Reverse)}$ the same as in Procedure 8. (Read measurements from upper right corner of screen).

Procedure 11: $I_{H(Forward and Reverse)}$

For these steps, it is again necessary to connect the *Trigger* to *MT2* through a 10 Ω resistor. The other connections remain the same.

To measure the $I_{H(Forward and Reverse)}$ parameter:

1. Set **Power Dissipation** to 50 W.
2. Set **Max Peak Volts** to 75 V. (80 V on 370)
3. Set **Mode** to DC.
4. Set **Horizontal** knob to 5 V/DIV.
5. Set **Vertical** knob to approximately 10% of the maximum I_H specified.

Note: Due to large variations of holding current values, the scale may have to be adjusted to observe holding current.

6. Set **Terminal Selector** to *Emitter Grounded-Open Base*.

Procedure 12: $I_{H(Forward)}$

To measure the $I_{H(Forward)}$ parameter:

1. Set **Polarity** to (+).
2. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
3. Increase **Variable Collector Supply Voltage** to maximum position (100).

Note: Depending on the vertical scale being used, the dot may disappear completely from the screen.

4. Decrease **Variable Collector Supply Voltage** to the point where the line on the CRT changes to a dot. The position of the beginning point of the line, just before the line changes to a dot, represents the I_H value. (Figure AN1006.21)

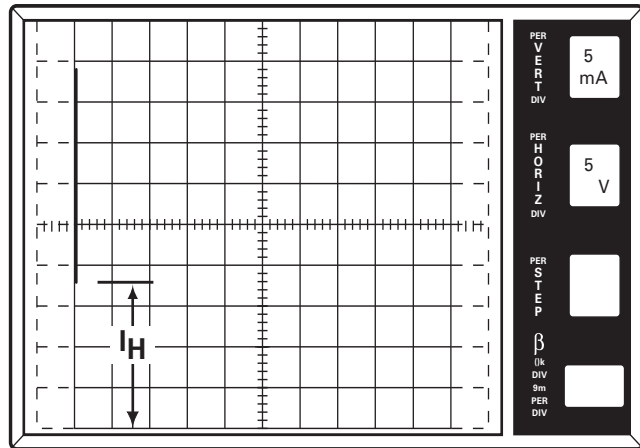


Figure AN1006.21 $I_{H(Forward)} = 18 \text{ mA}$

Procedure 13: $I_{H(Reverse)}$

To measure the $I_{H(Reverse)}$ parameter:

1. Set **Polarity** to (-).
2. Continue testing per Procedure 12 for measuring $I_{H(Reverse)}$.

SIDACs

The SIDAC is a bidirectional voltage-triggered switch. Upon application of a voltage exceeding the SIDAC breakover voltage point, the SIDAC switches on through a negative resistance region (similar to a DIAC) to a low on-state voltage. Conduction continues until current is interrupted or drops below minimum required holding current.

To connect the SIDAC:

1. Connect *MT1* to the *Emitter Terminal* (E).
2. Connect *MT2* to the *Collector Terminal* (C).

To begin testing, perform the following procedures.

Procedure 1: (+) V_{DRM} , (+) I_{DRM} , (-) V_{DRM} , (-) I_{DRM}

Note: The (+) and (-) symbols are used to designate the polarity of *MT2* with reference to *MT1*.

To measure the (+) V_{DRM} , (+) I_{DRM} , (-) V_{DRM} , and (-) I_{DRM} parameter:

1. Set **Variable Collector Supply Voltage Range** to 1500 Max Peak Volts.
2. Set **Horizontal** knob to 50 V/DIV.
3. Set **Mode** to Leakage.
4. Set **Polarity** to (+).
5. Set **Power Dissipation** to 2.2 W. (2 W on 370)
6. Set **Terminal Selector** to *Emitter Grounded-Open Base*.
7. Set **Vertical** knob to 50 $\mu\text{A}/\text{DIV}$. (Due to leakage mode, the CRT readout will show 50 nA.)

Procedure 2: (+)V_{DRM} and (+)I_{DRM}

To measure the (+)V_{DRM} and (+)I_{DRM} parameter:

1. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
2. Increase **Variable Collector Supply Voltage** to the rated V_{DRM} of the device and observe the dot on the CRT. Read across horizontally from the dot to the vertical current scale. This measured value is the leakage current. (Figure AN1006.22)

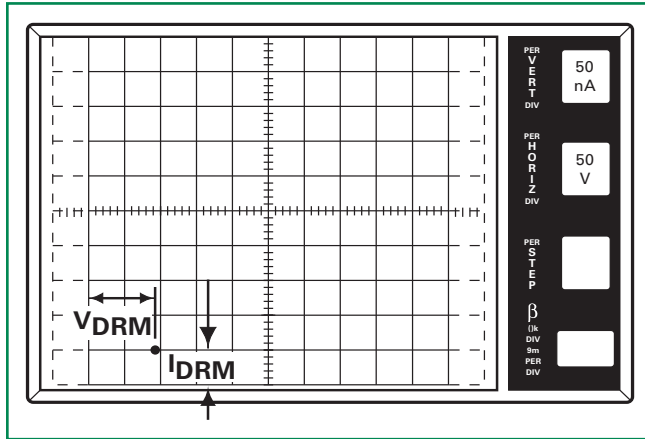


Figure AN1006.22 I_{DRM} = 50 nA at V_{DRM} = 90 V

Procedure 3: (-)V_{DRM} and (-)I_{DRM}

To measure the (-)V_{DRM} and (-)I_{DRM} parameter:

1. Set **Polarity** to (-).
2. Repeat Procedures 1 and 2. (Read measurements from upper right corner of the screen).

Procedure 4: V_{BO} and I_{BO}

To measure the V_{BO} and I_{BO} parameter:

1. Set **Variable Collector Supply Voltage Range** to 1500 Max Peak Volts. (2000 V on 370)
2. Set **Horizontal** knob to a sufficient scale to allow viewing of trace at the required voltage level (50 V/DIV for 95 V to 215 V V_{BO} range devices and 100 V/DIV for devices having V_{BO} ≥ 15 V).
3. Set **Vertical** knob to 50 A/DIV.
4. Set **Polarity** to AC.
5. Set **Mode** to Norm.
6. Set **Power Dissipation** to 10 W.
7. Set **Terminal Selector** to Emitter Grounded-Open Base.
8. Set **Left-Right Terminal Jack Selector** to correspond with location of test fixture.

Procedure 5: V_{BO}

To measure the V_{BO} parameter, increase **Variable Collector Supply Voltage** until breakover occurs. (Figure AN1006.23) The voltage at which current begins to flow and voltage on CRT does not increase is the V_{BO} value.

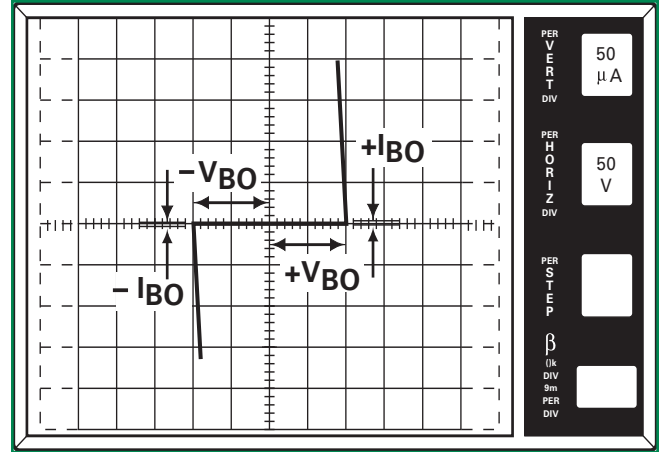


Figure AN1006.23 (+)V_{BO} = 100 V; (-)V_{BO} = 100 V; (±)I_{BO} < 10 μA

Procedure 6: I_{BO}

To measure the I_{BO} parameter, at the V_{BO} point, measure the amount of device current just before the device reaches the breakover mode. The measured current at this point is the I_{BO} value.

Note: If I_{BO} is less than 10 μA, the current cannot readily be seen on the curve tracer.

Procedure 7: I_H (Forward and Reverse)

To measure the I_H (Forward and Reverse) parameter:

1. Set **Variable Collector Supply Voltage Range** to 1500 Max Peak Volts (400 V on 577; 2000 V on 370).
2. Set **Horizontal** knob to a sufficient scale to allow viewing of trace at the required voltage level (50 V/DIV for devices with V_{BO} range from 95 V to 215 V and 100 V/DIV for devices having V_{BO} ≥ 215 V).
3. Set **Vertical** knob to 20% of maximum holding current specified.
4. Set **Polarity** to AC.
5. Set **Mode** to Norm.
6. Set **Power Dissipation** to 220 W (100 W on 577).
7. Set **Terminal Selector** to Emitter Grounded-Open Base.
8. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.

WARNING: Limit test time to 15 seconds maximum.

9. Increase **Variable Collector Supply Voltage** until device breaks over and turns on. (Figure AN1006.24)

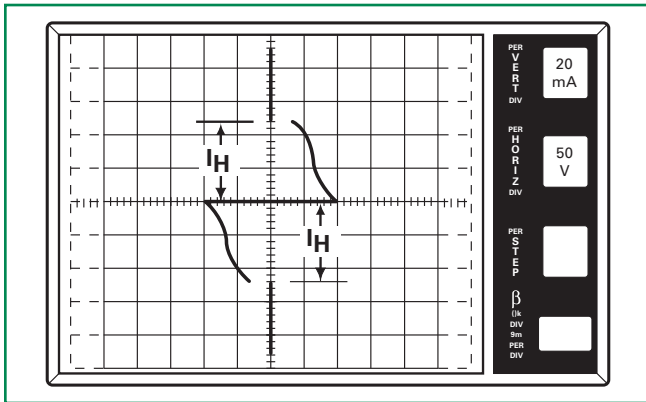


Figure AN1006.24 $I_H = 48 \text{ mA}$ in both forward and reverse directions

I_H is the vertical distance between the center horizontal axis and the beginning of the line located on center vertical axis.

Procedure 8: $V_{TM(Forward \text{ and } Reverse)}$

To measure the $V_{TM(Forward \text{ and } Reverse)}$ parameter:

1. Set **Variable Collector Supply Voltage Range** to **350 Max Peak Volts. (400 V on 370)**
2. Set **Horizontal** knob to **0.5 V/DIV.**
3. Set **Vertical** knob to **0.5 A/DIV.**
4. Set **Polarity** to **(+).**
5. Set **Mode** to **Norm.**
6. Set **Power Dissipation** to **220 W (100 W on 577).**
7. Set **Terminal Selector** to **Emitter Grounded-Open Base.**

Before continuing with testing, note the following:

- A Kelvin test fixture is required for this test. If a Kelvin fixture is not used, an error in measurement of V_{TM} will result due to voltage drop in fixture. If a Kelvin fixture is not available, Figure AN1006.3 shows necessary information to wire a test fixture with Kelvin Connections.

To continue testing, perform the following procedures.

Procedure 9: $V_{TM(Forward)}$

To measure the $V_{TM(Forward)}$ parameter:

1. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
2. Increase **Variable Collector Supply Voltage** until current reaches rated $I_{T(peak)}$, which is 1.4 times the $I_{T(RMS)}$ rating of the SIDAC.

Note: Model 370 current is limited. Set to 400 mA. Check for 1.1 V MAX.

WARNING: Limit test time to 15 seconds.

3. To measure V_{TM} , follow along horizontal scale to the point where the trace crosses the $I_{T(peak)}$ value. This horizontal distance is the V_{TM} value. (Figure AN1006.25)

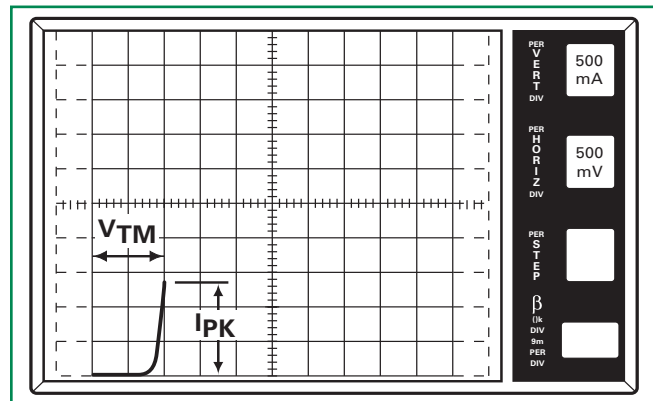


Figure AN1006.25 $V_{TM(Forward)} = 950 \text{ mV}$ at $I_{PK} = 1.4 \text{ A}$

Procedure 10: $V_{TM(Reverse)}$

To measure the $V_{TM(Reverse)}$ parameter:

Set **Polarity** to **(-).**

Repeat Procedure 8 to measure $V_{TM(Reverse)}$.

DIACs

DIACs are voltage breakdown switches used to trigger-on Triacs and non-sensitive SCRs in phase control circuits.

Note: DIACs are bi-directional devices and can be connected in either direction.

To connect the DIAC:

Connect one side of the DIAC to the Collector Terminal (C). Connect other side of the DIAC to the Emitter Terminal (E). To begin testing, perform the following procedures.

Procedure 1: Curve Tracer Setup

To set the curve tracer and begin testing:

1. Set **Variable Collector Supply Voltage Range** to **75 Max Peak Volts. (80 V on 370)**
2. Set **Horizontal** knob to sufficient scale to allow viewing of trace at the required voltage level (**10 V to 20 V/DIV** depending on device being tested).
3. Set **Vertical** knob to **50 $\mu\text{A/DIV}$.**
4. Set **Polarity** to **AC.**
5. Set **Mode** to **Norm.**
6. Set **Power Dissipation** to **0.5 W. (0.4 W on 370)**
7. Set **Terminal Selector** to **Emitter Grounded-Open Base.**

Procedure 2: V_{BO}

To measure the V_{BO} parameter:

1. Set **Left-Right Terminal Jack Selector** to correspond with the location of the test fixture.
2. Set **Variable Collector Supply Voltage** to 55 V (65 V for 370) and apply voltage to device under test (D.U.T.), using **Left-Right-Selector Switch**. The peak voltage at which current begins to flow is the V_{BO} value. (Figure AN1006.26)

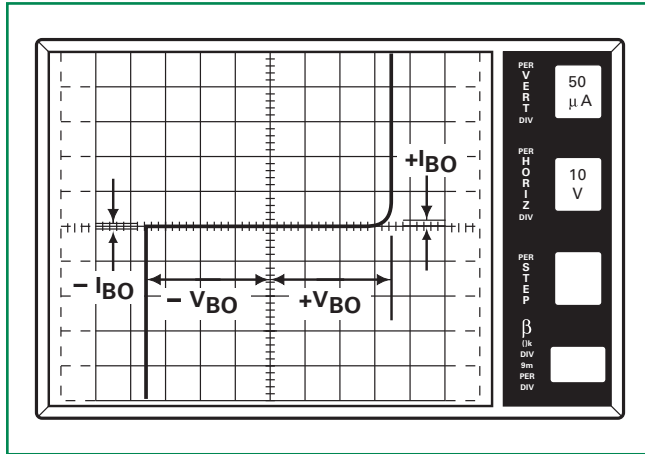


Figure AN1006.26 (+) V_{BO} = 35 V; (-) V_{BO} = 36 V; (\pm) I_{BO} < 15 μ A; (-) I_{BO} < 10 μ A and Cannot Be Read Easily

Procedure 3: I_{BO}

To measure the I_{BO} parameter, at the V_{BO} point, measure the amount of device current just before the device reaches the breakover mode. The measured current at this point is the I_{BO} value.

Note: If I_{BO} is less than 10 μ A, the current cannot readily be seen on the curve tracer.

Procedure 4: ΔV_{BO} (Voltage Breakover Symmetry)

To measure the ΔV_{BO} (Voltage Breakover Symmetry) parameter:

1. Measure positive and negative values of V_{BO} as shown in Figure AN1006.26.
2. Subtract the absolute value of V_{BO} (-) from V_{BO} (+).

The absolute value of the result is:

$$\Delta V_{BO} = [| +V_{BO} | - | -V_{BO} |]$$

Model 370 Curve Tracer Procedure Notes

Because the curve tracer procedures in this application note are written for the Tektronix model 576 curve tracer, certain settings must be adjusted when using model 370. Variable Collector Supply Voltage Range and Power Dissipation controls have different scales than model 576. The following table shows the guidelines for setting Power Dissipation when using model 370. (Figure AN1006.27)

Model 576	Model 370
If power dissipation is 0.1 W,	set at 0.08 W.
If power dissipation is 0.5 W,	set at 0.4 W.
If power dissipation is 2.2 W,	set at 2 W.
If power dissipation is 10 W,	set at 10 W.
If power dissipation is 50 W,	set at 50 W.
If power dissipation is 220 W,	set at 220 W.

Although the maximum power setting on the model 370 curve tracer is 200 W, the maximum collector voltage available is only 400 V at 220 W. The following table shows the guidelines for adapting Collector Supply Voltage Range settings for model 370 curve tracer procedures:

Model 576	Model 370
If voltage range is 15 V	set at 16 V.
If voltage range is 75 V	set at 80 V.
If voltage range is 350 V	set at 400 V.
If voltage range is 1500 V	set at 2000 V.

The following table shows the guidelines for adapting terminal selector knob settings for model 370 curve tracer procedures:

Model 576	Model 370
If Step generator (base) is emitter grounded	then Base Step generator is emitter common.
If Emitter grounded is open base	then Base open is emitter common.

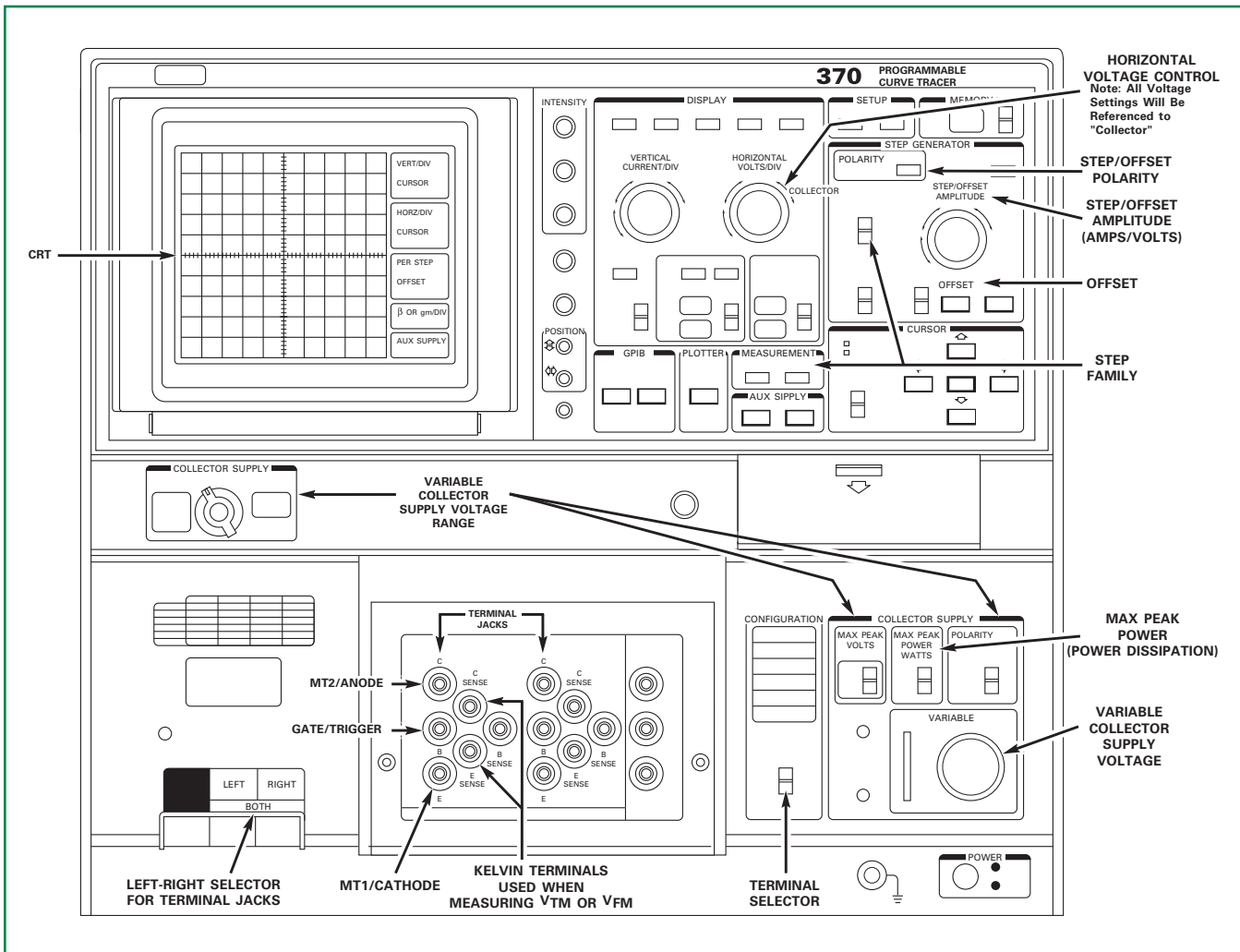


Figure AN1006.27 Tektronix Model 370 Curve Tracer

Model 577 Curve Tracer Procedure Notes

Because the curve tracer procedures in this application note are written for the Tektronix model 576 curve tracer, certain settings must be adjusted when using model 577. Model 576 curve tracer has separate controls for polarity (AC, +, -) and mode (Norm, DC, Leakage), whereas Model 577 has only a polarity control. The following table shows the guidelines for setting Collector Supply Polarity when using model 577. (Figure AN1006.28)

Model 576	Model 577
If using Leakage mode along with polarity setting of +(NPN) and -(PNP), [vertical scale divided by 1,000],	set Collector Supply Polarity to either +DC or -DC , depending on polarity setting specified in the procedure. The vertical scale is read directly from the scale on the control knob.
If using DC mode along with either +(NPN) or -(PNP) polarity,	set Collector Supply Polarity to either +DC or -DC depending on polarity specified.
If using Norm mode along with either +(NPN) or -(PNP) polarity,	set Collector Supply Polarity to either +(NPN) or -(PNP) per specified procedure.
If using Norm mode with AC polarity,	set Collector Supply Polarity to AC .

One difference between models 576 and 577 is the Step/Offset Polarity setting. The polarity is inverted when the button is depressed on the Model 576 curve tracer. The Model 577 is opposite — the Step/Offset Polarity is “inverted” when the button is extended and “Normal”

when the button is depressed. The Step/Offset Polarity is used only when measuring I_{GT} and V_{GT} of Triacs and Quadracs in Quadrants I through IV.

Also, the Variable Collector Supply Voltage Range and Power Dissipation controls have different scales than model 576. The following table shows the guidelines for setting Power Dissipation when using model 577.

Model 576	Model 577
If power dissipation is 0.1 W,	set at 0.15 W.
If power dissipation is 0.5 W,	set at 0.6 W.
If power dissipation is 2.2 W,	set at 2.3 W.
If power dissipation is 10 W,	set at 9 W.
If power dissipation is 50 W,	set at 30 W.
If power dissipation is 220 W,	set at 100 W.

Although the maximum power setting on model 576 curve tracer is 220 W (compared to 100 W for model 577), the maximum collector current available is approximately the same. This is due to the minimum voltage range on model 577 curve tracer being 6.5 V compared to 15 V for model 576. The following table shows the guidelines for adapting Collector Voltage Supply Range settings for model 577 curve tracer procedures:

Model 576	Model 577
If voltage range is 15 V	set at either 6.5 V or 25 V, depending on parameter being tested. Set at 6.5 V when measuring V_{TM} (to allow maximum collector current) and set at 25 V when measuring I_{GT} and V_{GT} .
If voltage range is 75 V	set at 100 V.
If voltage range is 1500 V,	set at 1600 V.

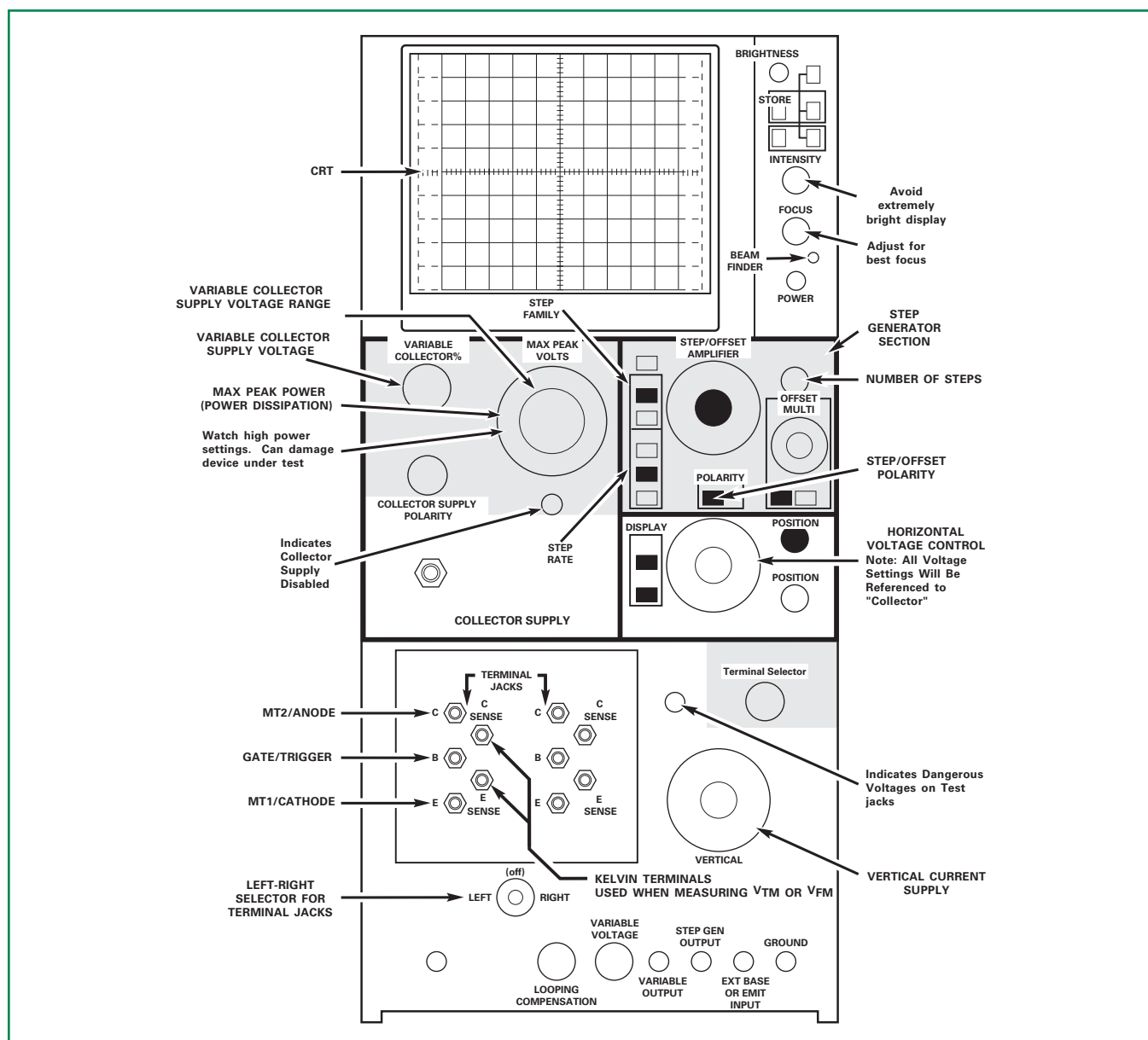


Figure AN1006.28 Tektronix Model 577 Curve Tracer

Thyristors Used as AC Static Switches and Relays

Introduction

Since the SCR and the Triac are bistable devices, one of their broad areas of application is in the realm of signal and power switching. This application note describes circuits in which these Thyristors are used to perform simple switching functions of a general type that might also be performed non-statically by various mechanical and electromechanical switches. In these applications, the Thyristors are used to open or close a circuit completely, as opposed to applications in which they are used to control the magnitude of average voltage or energy being delivered to a load. These latter types of applications are described in detail in "Phase Control Using Thyristors" (AN1003).

Static AC Switches

Normally Open Circuit

The circuit shown in Figure AN1007.1 provides random (anywhere in half-cycle), fast turn-on ($<10 \mu s$) of AC power loads and is ideal for applications with a high-duty cycle. It eliminates completely the contact sticking, bounce, and wear associated with conventional electromechanical relays, contactors, and so on. As a substitute for control relays, Thyristors can overcome the differential problem; that is, the spread in current or voltage between pickup and dropout because Thyristors effectively drop out every half cycle. Also, providing resistor R_1 is chosen correctly, the circuits are operable over a much wider voltage range than is a comparable relay. Resistor R_1 is provided to limit gate current (I_{GTM}) peaks. Its resistance plus any contact resistance (R_C) of the control device and load resistance (R_L) should be just greater than the peak supply voltage divided by the peak gate current rating of the Triac. If R_1 is set too high, the Triacs may not trigger at the beginning of each cycle, and phase control of the load will result with consequent loss of load voltage and waveform distortion. For inductive loads, an RC snubber circuit, as shown in Figure AN1007.1, is required. However, a snubber circuit is not required when an alternistor Triac is used.

Figure AN1007.2 illustrates an analysis to better understand a typical static switch circuit. The circuit operation occurs when switch S_1 is closed, since the Triac Q_1 will initially be in the blocking condition. Current flow will be through load R_L , S_1 , R_1 , and gate to MT1 junction of the Thyristor. When this current reaches the required value of I_{GT} , the MT2 to MT1 junctions will switch to the conduction state and the voltage from MT2 to MT1 will be V_T . As the current approaches the zero crossing, the load current will fall below holding current turning the Triac Q_1 device off until it is refired in the next half cycle. Figure AN1007.3 illustrates the voltage waveform appearing across the MT2 to MT1 terminals of Q_1 . Note that the maximum peak value of current which S_1 will carry would be 25 mA since Q_1 has a 25 mA maximum I_{GT} rating. Additionally, no arcing of a

current value greater than 25 mA when opening S_1 will occur when controlling an inductive load. It is important also to note that the Triac Q_1 is operating in Quadrants I and III, the more sensitive and most suitable gating modes for Triacs. The voltage rating of S_1 (mechanical switch or reed switch) must be equivalent to or greater than line voltage applied.

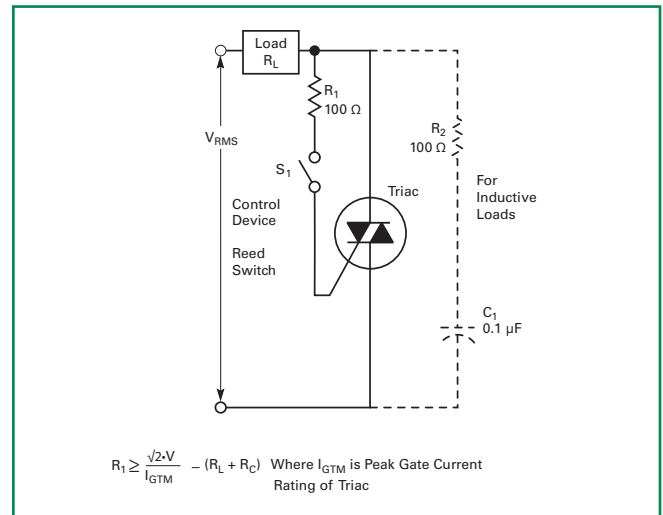


Figure AN1007.1 Basic Triac Static Switch

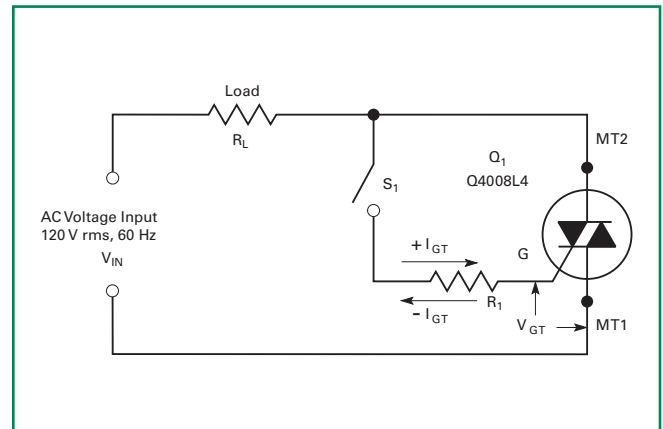


Figure AN1007.2 Analysis of Static Switch

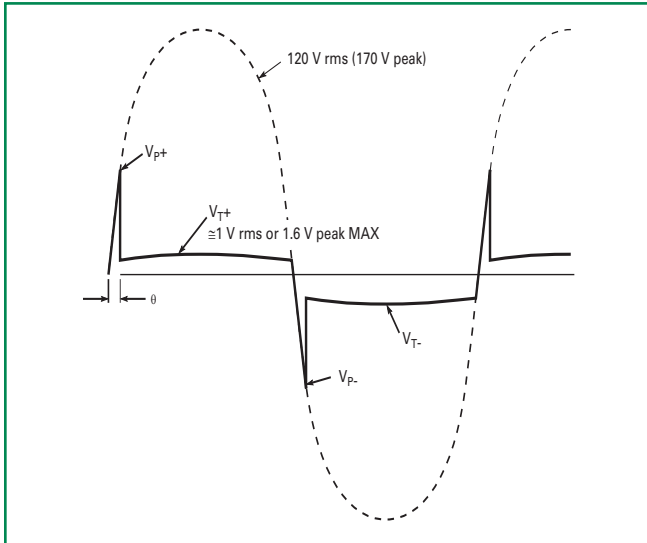


Figure AN1007.3 Waveform Across Static Switch

A typical example would be in the application of this type circuit for the control of 5 A resistive load with 120 V rms input voltage. Choosing a value of 100 Ω for R_1 and assuming a typical value of 1 V for the gate to MT1 (V_{GT}) voltage, we can solve for V_p by the following:

$$V_p = I_{GT} (R_L + R_1) + V_{GT}$$

Note: R_c is not included since it is negligible.

$$V_p = 0.025 (24 + 100) + 1.0 = 4.1 \text{ V}$$

Additionally the turn-on angle is

$$\theta = \sin^{-1} \frac{4.1}{170 V_{PK}} = 1.4^\circ$$

The power lost by the turn-on angle is essentially zero. The power dissipation in the gate resistor is very minute. A 100 Ω, 0.25 W rated resistor may safely be used. The small turn-on angle also ensures that no appreciable RFI is generated.

The relay circuit shown in Figure AN1007.1 and Figure AN1007.2 has several advantages in that it eliminates contact bounce, noise, and additional power consumption by an energizing coil and can carry an in-rush current of many times its steady state rating.

The control device S_1 indicated can be either electrical or mechanical in nature. Light-dependent resistors and light-activated semiconductors, optocoupler, magnetic cores, and magnetic reed switches are all suitable control elements. Regardless of the switch type chosen, it must have a voltage rating equal to or greater than the peak line voltage applied. In particular, the use of hermetically sealed reed switches as control elements in combination with Triacs offers many advantages. The reed switch can be actuated by passing DC current through a small coiled wire or by the proximity of a small magnet. In either case, complete electrical isolation exists between the control signal input, which may be derived from many sources,

and the switched power output. Long life of the Triac/reed switch combination is ensured by the minimal volt-ampere switching load placed on the reed switch by the Triac triggering requirements. The Thyristor ratings determine the amount of load power that can be switched.

Normally Closed Circuit

With a few additional components, the Thyristor can provide a normally closed static switch function. The critical design portion of this static switch is a clamping device to turn off/eliminate gate drive and maintain very low power dissipation through the clamping component plus have low by-pass leakage around the power Thyristor device. In selecting the power Thyristor for load requirements, gate sensitivity becomes critical to maintain low power requirements. Either sensitive SCRs or sensitive logic Triacs must be considered, which limits the load in current capacity and type. However, this can be broader if an extra stage of circuitry for gating is permitted.

Figure AN1007.4 illustrates an application using a normally closed circuit driving a sensitive SCR for a simple but precise temperature controller. The same basic principle could be applied to a water level controller for a motor or solenoid. Of course, SCR and diode selection would be changed depending on load current requirements.

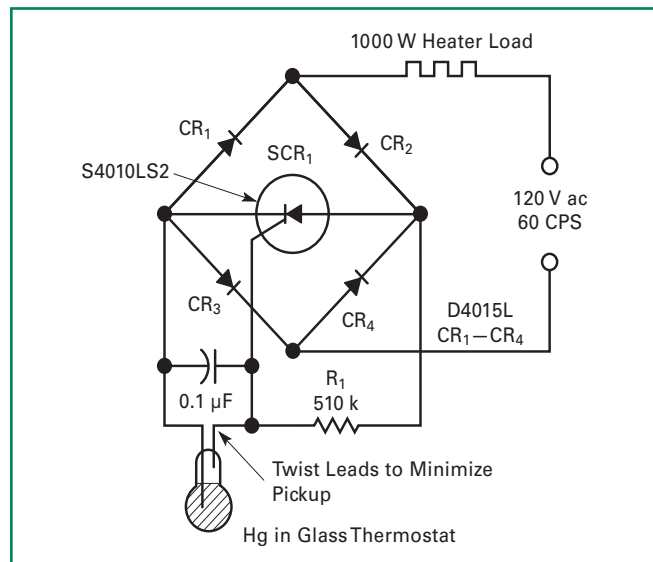


Figure AN1007.4 Normally Closed Temperature Controller

A mercury-in-glass thermostat is an extremely sensitive measuring instrument, capable of sensing changes in temperature as small as 0.1 °C. Its major limitation lies in its very low current-handling capability for reliability and long life, and contact current should be held below 1 mA. In the circuit of Figure AN1007.4, the S2010LS2 SCR serves as both current amplifier for the Hg thermostat and as the main load switching element.

With the thermostat open, the SCR will trigger each half cycle and deliver power to the heater load. When the thermostat closes, the SCR can no longer trigger and the heater shuts off. Maximum current through the thermostat

in the closed position is less than 250 μ A rms.

Figure AN1007.5 shows an all solid state, optocoupled, normally closed switch circuit. By using a low voltage SBS triggering device, this circuit can turn on with only a small delay in each half cycle and also keep gating power low. When the optocoupled transistor is turned on, the gate drive is removed with only a few milliamps of bypass current around the Triac power device. Also, by use of the BS08D and 0.1 μ F, less sensitive Triacs and alternistors can be used to control various types of high current loads.

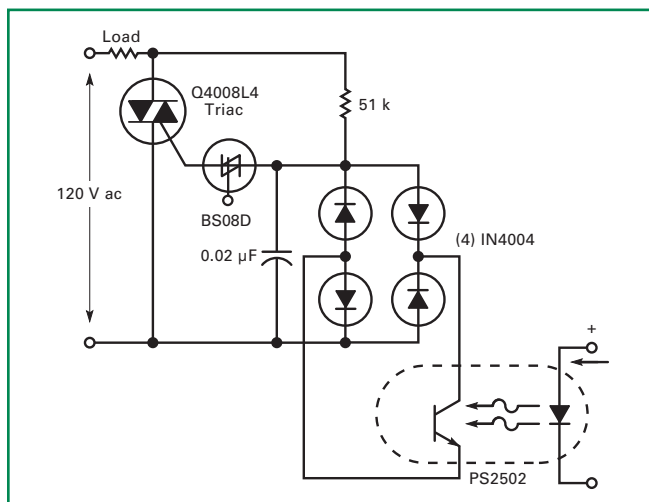


Figure AN1007.5 Normally Closed Switch Circuit

Optocoupled Driver Circuits

Random Turn-on, Normally Open

Many applications use optocouplers to drive Thyristors. The combination of a good optocoupler and a Triac or alternistor makes an excellent, inexpensive solid state relay. Application information provided by the optocoupler manufacturers is not always best for application of the power Thyristor. Figure AN1007.6 shows a standard circuit for a resistive load.

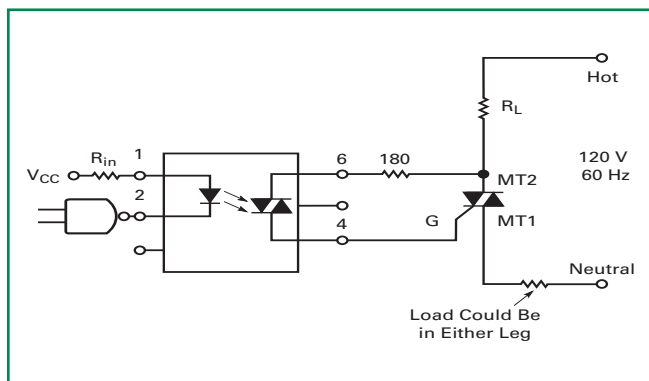


Figure AN1007.6 Optocoupled Circuit for Resistive Loads (Triac or Alternistor Triac)

A common mistake in this circuit is to make the series gate resistor too large in value. A value of 180 Ω is shown in a typical application circuit by optocoupler manufacturers. The 180 Ω is based on limiting the current to 1 A peak at the peak of a 120 V line input for Fairchild and Toshiba optocoupler I_{TSM} rating. This is good for protection of the optocoupler output Triac, as well as the gate of the power Triac on a 120 V line; however, it must be lowered if a 24 V line is being controlled, or if the R_L (resistive load) is 200 W or less. This resistor limits current for worst case turn-on at the peak line voltage, but it also sets turn-on point (conduction angle) in the sine wave, since Triac gate current is determined by this resistor and produced from the sine wave voltage as illustrated in Figure AN1007.2. The load resistance is also important, since it can also limit the amount of available Triac gate current. A 100 Ω gate resistor would be a better choice in most 120 V applications with loads greater than 200 W and optocouplers from Quality Technologies or Vishay with optocoupler output Triacs that can handle 1.7 A_{PK} (I_{TSM} rating) for a few microseconds at the peak of the line. For loads less than 200 W, the resistor can be dropped to 22 Ω . Remember that if the gate resistor is too large in value, the Triac will not turn on at all or not turn on fully, which can cause excessive power dissipation in the gate resistor, causing it to burn out. Also, the voltage and dv/dt rating of the optocoupler's output device must be equal to or greater than the voltage and dv/dt rating of the Triac or alternistor it is driving.

Figure AN1007.7 illustrates a circuit with a dv/dt snubber network included. This is a typical circuit presented by optocoupler manufacturers.

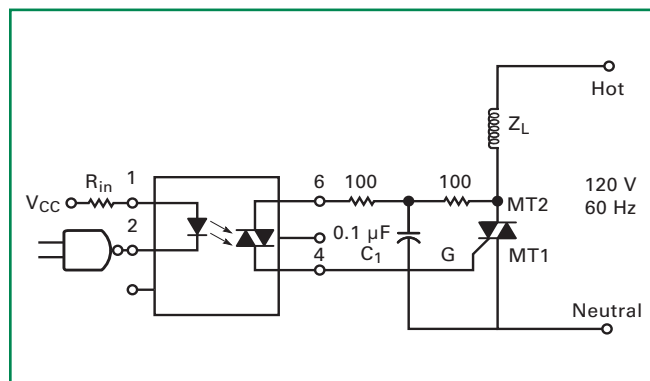


Figure AN1007.7 Optocoupler Circuit for Inductive Loads (Triac or Alternistor Triac)

This "T" circuit hinges around one capacitor to increase dv/dt capability to either the optocoupler output Triac or the power Triac. The sum of the two resistors then forms the Triac gate resistor.

Both resistors should then be standardized and lowered to 100 Ω . Again, this sum resistance needs to be low, allowing as much gate current as possible without exceeding the instantaneous current rating of the opto output Triac or Triac gate junction. By having 100 Ω for current limit in either direction from the capacitor, the optocoupler output Triac and power Triac can be protected

against di/dt produced by the capacitor. Of course, it is most important that the capacitor be connected between proper terminals of Triac. For example, if the capacitor and series resistor are accidentally connected between the gate and MT2, the Triac will turn on from current produced by the capacitor, resulting in loss of control.

For low current (mA) and/or highly inductive loads, it may be necessary to have a latching network ($3.3\text{ k}\Omega + 0.047\text{ }\mu\text{F}$) connected directly across the power Triac. The circuit shown in Figure AN1007.8 illustrates the additional latching network.

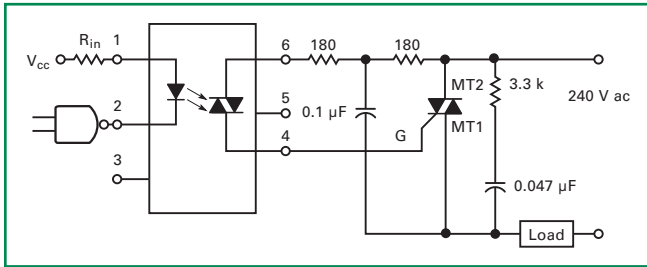


Figure AN1007.8 Optocoupler Circuit for Lower Current Inductive Loads (Triac or Alternistor Triac)

In this circuit, the series gate resistors are increased to $180\text{ }\Omega$ each, since a 240 V line is applied. Note that the load is placed on the MT1 side of the power Triac to illustrate that load placement is **not** important for the circuit to function properly.

Also note that with standard U.S. residential 240 V home wiring, both sides of the line are hot with respect to ground (no neutral). Therefore, for some 240 V line applications, it will be necessary to have a Triac switch circuit in both sides of the 240 V line input.

If an application requires back-to-back SCRs instead of a Triac or alternistor, the circuit shown in Figure AN1007.9 may be used.

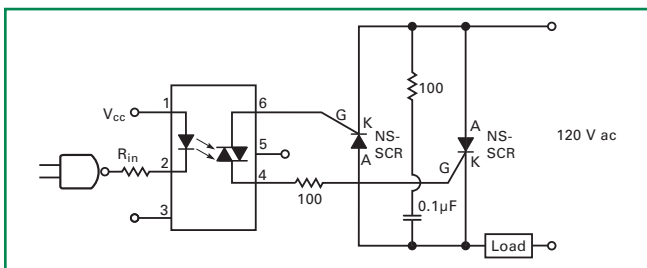


Figure AN1007.9 Optocoupled Circuit for Heavy-duty Inductive Loads

All application comments and recommendations for optocoupled switches apply to this circuit. However, the snubber network can be applied only across the SCRs as shown in the illustration. The optocoupler should be chosen for best noise immunity. Also, the voltage rating of the optocoupler output Triac must be equal to or greater than the voltage rating of SCRs.

Summary of Random Turn-on Relays

As shown in Figure AN1007.10, if the voltage across the load is to be phase controlled, the input control circuitry must be synchronized to the line frequency and the trigger pulses delayed from zero crossing every half cycle. If the series gate resistor is chosen to limit the peak current through the opto-driver to less than 1 A, then on a 120 V ac line the peak voltage is 170 V; therefore, the resistor is $180\text{ }\Omega$. On a 240 V ac line the peak voltage is 340 V; therefore, the resistor should be $360\text{ }\Omega$. These gate pulses are only as long as the device takes to turn on (typically, 5 μs to 6 μs); therefore, 0.25 W resistor is adequate.

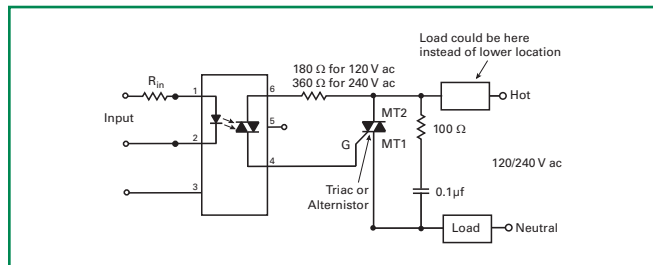


Figure AN1007.10 Random Turn-on Triac Driver

Select the Triac for the voltage of the line being used, the current through the load, and the type of load. Since the G_{peak} voltage of a 120 V ac line is 170 V, you would choose a 200 V (MIN) device. If the application is used in an electrically noisy industrial environment, a 400 V device should be used. If the line voltage to be controlled is 240 V ac with a peak voltage of 340 V, then use at least a 400 V rated part or 600 V for more design margin. Selection of the voltage rating of the opto-driver must be the same or higher than the rating of the power Triac. In electrically noisy industrial locations, the dv/dt rating of the opto-driver and the Triac must be considered.

The RMS current through the load and main terminals of the Triac should be approximately 70% of the maximum rating of the device. However, a 40 A Triac should not be chosen to control a 1 A load due to low latching and holding current requirements. Remember that the case temperature of the Triac must be maintained at or below the current versus temperature curve specified on its data sheet. As with all semiconductors the lower the case temperature the better the reliability. Opto-driven gates normally do not use a sensitive gate Triac. The opto-driver can supply up to 1 A gate pulses and less sensitive gate Triacs have better dv/dt capability. If the load is resistive, it is acceptable to use a standard Triac. However, if the load is a heavy inductive type, then an alternistor Triac, or back-to-back SCRs as shown in Figure AN1007.9, is recommended. A series RC snubber network may or may not be necessary when using an alternistor Triac. Normally a snubber network is not needed when using an alternistor because of its high dv/dt and $dv/dt(c)$ capabilities. However, latching network as described in Figure AN1007.8 may be needed for low current load variations.

Zero Crossing Turn-on, Normally Open Relay Circuits

When a power circuit is mechanically switched on and off mechanically, generated high-frequency components are generated that can cause interference problems such as RFI. When power is initially applied, a step function of voltage is applied to the circuit which causes a shock excitation. Random switch opening stops current off, again generating high frequencies. In addition, abrupt current interruption in an inductive circuit can lead to high induced-voltage transients.

The latching characteristics of Thyristors are ideal for eliminating interference problems due to current interruption since these devices can only turn off when the on-state current approaches zero, regardless of load power factor.

On the other hand, interference-free turn-on with Thyristors requires special trigger circuits. It has been proven experimentally that general purpose AC circuits will generate minimum electromagnetic interference (EMI) if energized at zero voltage.

The ideal AC circuit switch, therefore, consists of a contact which closes at the instant when voltage across it is zero and opens at the instant when current through it is zero. This has become known as “zero-voltage switching.”

For applications that require synchronized zero-crossing turn-on, the illustration in Figure AN1007.11 shows a circuit which incorporates an optocoupler with a built-in zero-crossing detector

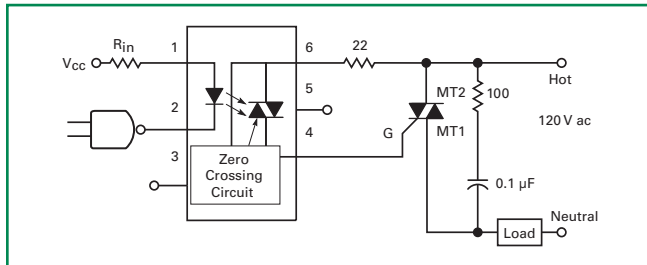


Figure AN1007.11 Optocoupled Circuit with Zero-crossing Turn-on (Triac or Alternistor Triac)

Also, this circuit includes a dv/dt snubber network connected across the power Triac. This typical circuit illustrates switching the hot line; however, the load may be connected to either the hot or neutral line. Also, note that the series gate resistor is low in value (22 Ω), which is possible on a 120 V line and above, since zero-crossing turn-on is ensured in any initial half cycle.

Zero Voltage Switch Power Controller

The UAA2016 (at www.onsemi.com) is designed to drive Triacs with the Zero Voltage technique which allows RFI-free power regulation of resistive loads. Operating directly on the AC power line, its main application is the precision regulation of electrical heating systems such as panel heaters or irons. It is available in eight-pin I.C. package variations.

A built-in digital sawtooth waveform permits proportional temperature regulation action over a $\pm 1^\circ\text{C}$ band around the set point. For energy savings there is a programmable temperature reduction function, and for security a sensor failsafe inhibits output pulses when the sensor connection is broken. Preset temperature (in other words, defrost) application is also possible. In applications where high hysteresis is needed, its value can be adjusted up to 5°C around the set point. All these features are implemented with a very low external component count.

Triac Choice and R_{out} Determination

The power switching Triac is chosen depending on power through load and adequate peak gate trigger current. The illustration in Figure AN1007.12 shows a typical heating control.

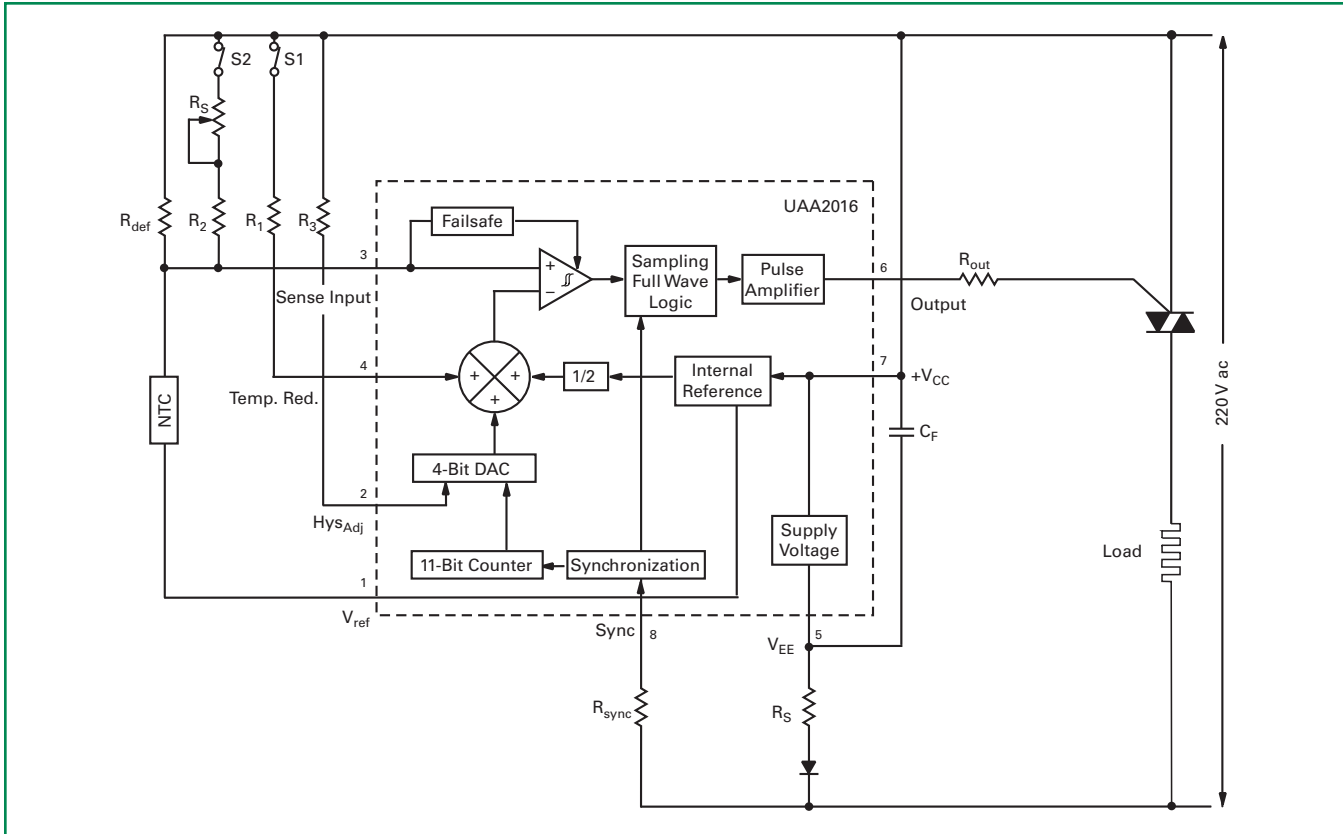


Figure AN1007.12 Heater Control Schematic

R_{out} limits the output current from UAA2016. Determine R_{out} according to the Triac maximum gate current (I_{GT}) and the application low temperature limit. For a 2 kw load at 220 V rms, a good Triac choice is Q6012LH5. Its maximum peak gate trigger current at 25 °C is 50 mA.

For an application to work down to -20 °C, R_{out} should be 68 Ω . since I_{GT} Q6012LH5 can typically be 80 mA and minimum current output from UAA2016 pin 6 is -90 mA at -8 V, -20 °C.

Output Pulse Width, R_{sync}

Figure AN1007.13 shows the output pulse width T_p determined by the Triac's I_H , I_L together with the load value, characteristics, and working conditions (frequency and voltage).

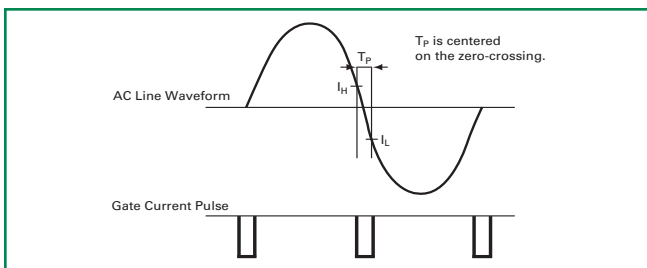


Figure AN1007.13 Zero Voltage Technique

To ensure best latching, T_p should be 200 μ s, which means R_{sync} will have typical value >390 k Ω .

To ensure best latching, T_p should be 200 μ s, which means R_{sync} will have typical value >390 k Ω .

R_S and Filter Capacitor (C_F)

For better UAA2016 power supply, typical value for R_S could be 27 k Ω , 2 W with C_F of 75 μ F to keep ripple <1 V.

Summary of Zero Crossing Turn-on Circuits

Zero voltage crossing turn-on opto-drivers are designed to limit turn-on voltage to less than 20 V. This reduces the amount of RFI and EMI generated when the Thyristor switches on. Because of this zero turn-on, these devices cannot be used to phase control loads. Therefore, speed control of a motor and dimming of a lamp cannot be accomplished with zero turn-on opto-couplers.

Since the voltage is limited to 20 V or less, the series gate resistor that limits the gate drive current has to be much lower with a zero crossing opto-driver. With typical inhibit voltage of 5 V, an alternistor Triac gate could require a 160 mA at -30 °C ($5 \text{ V}/0.16 \text{ A} = 31 \Omega$ gate resistor). If the load has a high inrush current, then drive the gate of the Triac with as much current as reliably possible but stay under the I_{TSM} rating of the opto-driver. By using 22 Ω for the gate resistor, a current of at least 227 mA is supplied with only 5 V, but limited to 909 mA if the voltage goes to 20 V. As shown in Figure AN1007.14, Figure AN1007.15, and Figure AN1007.16, a 22 Ω gate resistor is a good choice for various zero crossing controllers.

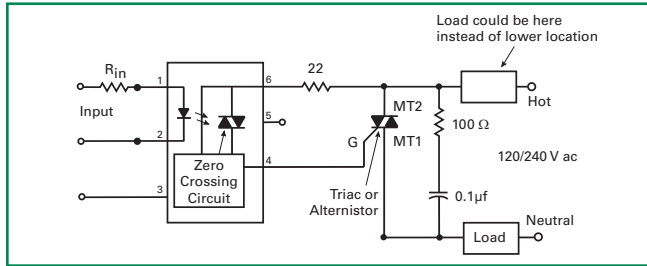


Figure AN1007.14 Zero Crossing Turn-on Opto Triac Driver

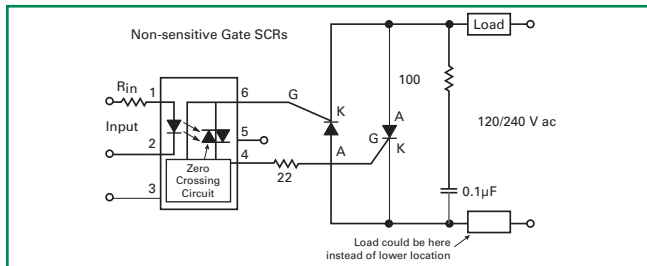


Figure AN1007.15 Zero Crossing Turn-on Non-sensitive SCR Driver

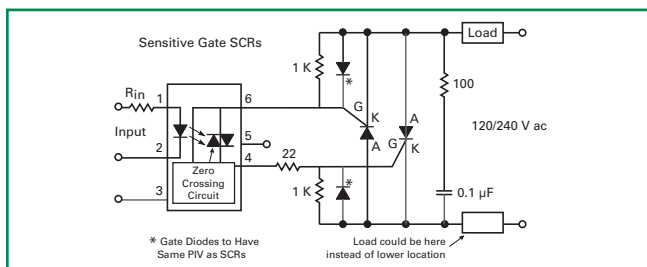


Figure AN1007.16 Zero Crossing Turn-on Opto-sensitive Gate SCR Driver

Time Delay Relay Circuit

By combining a 555 timer IC with a sensitive gate Triac, various time delays of several seconds can be achieved for delayed activation of solid state relays or switches. Figure AN1007.17 shows a solid state timer delay relay using a sensitive gate Triac and a 555 timer IC. The 555 timer precisely controls time delay of operation using an external resistor and capacitor, as illustrated by the resistor and capacitor combination curves. (Figure AN1007.18)

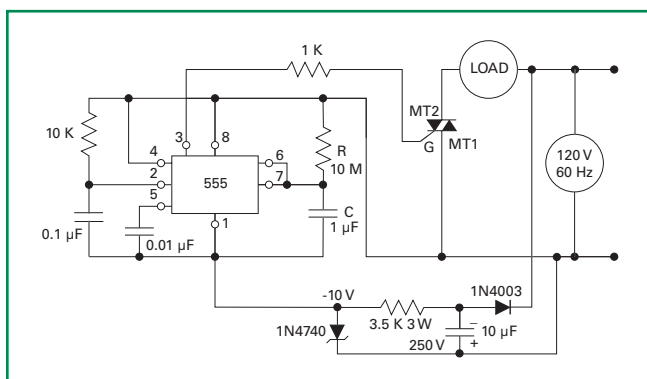


Figure AN1007.17 555 timer circuit with 10 second delay

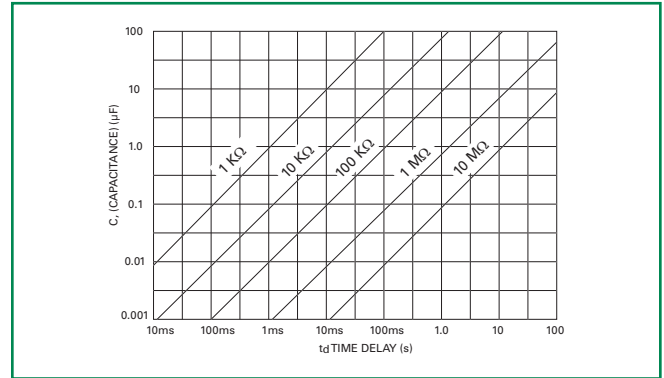


Figure AN1007.18 Resistor (R) and capacitor (C) combination curves

IR Motion Control

An example of a more complex Triac switch is an infrared (IR) motion detector controller circuit. Some applications for this circuit are alarm systems, automatic lighting, and auto doorbells.

Figure AN1007.19 shows an easy-to-implement automatic lighting system using an infrared motion detector control circuit. A commercially available LSI circuit HT761XB, from *Holtek*, integrates most of the analog functions. This LSI chip, U2, contains the op amps, comparators, zero crossing detection, oscillators, and a Triac output trigger. An external RC that is connected to the OSCD pin determines the output trigger pulse width. (*Holtek Semiconductor Inc.* is located at No.3, Creation Road II, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C.) Device U1 provides the infrared sensing. Device R13 is a photo sensor that serves to prevent inadvertent triggering under daylight or other high light conditions.

Choosing the right Triac depends on the load characteristics. For example, an incandescent lamp operating at 110 V requires a 200 V, 8 A Triac. This gives sufficient margin to allow for the high current state during lamp burn out. U2 provides a minimum output Triac negative gate trigger current of 40 mA, thus operating in QII & QIII. This meets the requirements of a 25 mA gate Triac. Teccor also offers alternistor Triacs for inductive load conditions.

This circuit has three operating modes (ON, AUTO, OFF), which can be set through the mode pin. While the LSI chip is working in the auto mode, the user can override it and switch to the test mode, or manual on mode, or return to the auto mode by switching the power switch. More information on this circuit, such as mask options for the infrared trigger pulse and flash options, are available in the *Holtek* HT761X General Purpose PIR Controller specifications.

Explanation of Maximum Ratings and Characteristics for Thyristors

Introduction

Data sheets for SCRs and Triacs give vital information regarding maximum ratings and characteristics of Thyristors. If the **maximum ratings** of the Thyristors are surpassed, possible irreversible damage may occur. The **characteristics** describe various pertinent device parameters which are guaranteed as either minimums or maximums. Some of these characteristics relate to the ratings but are not ratings in themselves. The characteristic does not define what the circuit must provide or be restricted to, but defines the device characteristic. For example, a minimum value is indicated for the dv/dt because this value depicts the guaranteed worst-case limit for all devices of the specific type. This minimum dv/dt value represents the maximum limit that the circuit should allow.

Maximum Ratings

V_{RRM} : Peak Repetitive Reverse Voltage -- SCR

The peak repetitive reverse voltage rating is the maximum peak reverse voltage that may be continuously applied to the main terminals (anode, cathode) of an SCR. (Figure AN1008.1) An open-gate condition and gate resistance termination is designated for this rating. An increased reverse leakage can result due to a positive gate bias during the reverse voltage exposure time of the SCR. The repetitive peak reverse voltage rating relates to case temperatures up to the maximum rated junction temperature.

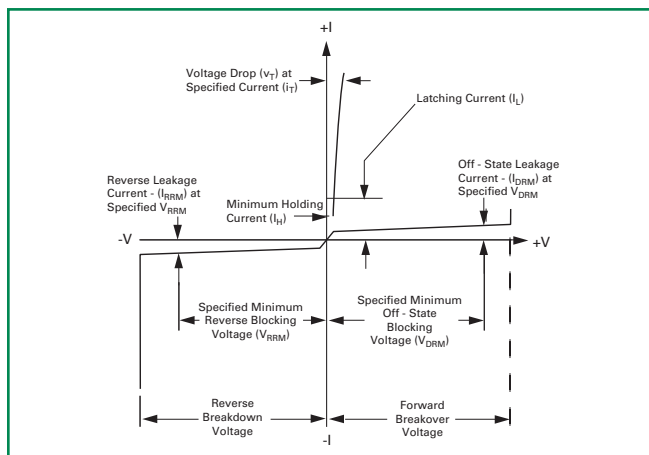


Figure AN1008.1 V-I Characteristics of SCR Device

V_{DRM} : Peak Repetitive Forward (Off-state) Voltage

SCR

The peak repetitive forward (off-state) voltage rating (Figure AN1008.1) refers to the maximum peak forward voltage which may be applied continuously to the main terminals

(anode, cathode) of an SCR. This rating represents the maximum voltage the SCR should be required to block in the forward direction. The SCR may or may not go into conduction at voltages above the V_{DRM} rating. This rating is specified for an open-gate condition and gate resistance termination. A positive gate bias should be avoided since it will reduce the forward-voltage blocking capability. The peak repetitive forward (off-state) voltage rating applies for case temperatures up to the maximum rated junction temperature.

Triac

The peak repetitive off-state voltage rating should not be surpassed on a typical, non-transient, working basis. (Figure AN1008.2) V_{DRM} should not be exceeded even instantaneously. This rating applies for either positive or negative bias on main terminal 2 at the rated junction temperature. This voltage is less than the minimum breakover voltage so that breakover will not occur during operation. Leakage current is controlled at this voltage so that the temperature rise due to leakage power does not contribute significantly to the total temperature rise at rated current.

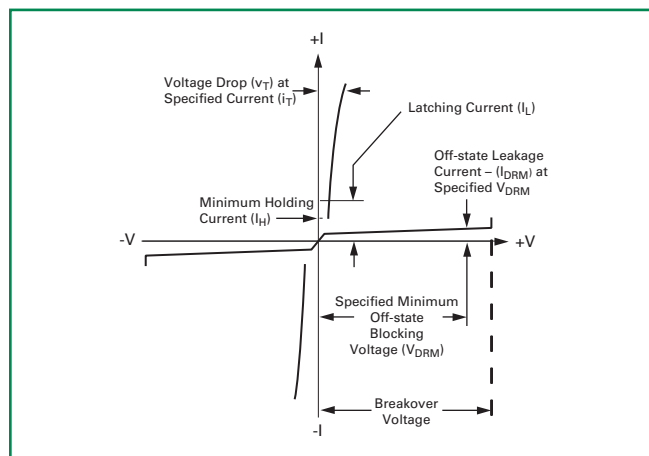


Figure AN1008.2 V-I Characteristics of Triac Device

I_T : Current Rating

SCR

For RMS and average currents, the restricting factor is usually confined so that the power dissipated during the on state and as a result of the junction-to-case thermal resistance will not produce a junction temperature in excess of the maximum junction temperature rating. Power dissipation is changed to RMS and average current ratings for a 60 Hz sine wave with a 180° conduction angle. The average current for conduction angles less than 180° is derated because of the higher RMS current connected with high peak currents. The DC current rating is higher than the average value for 180° conduction since no RMS component is present.

The dissipation for non-sinusoidal waveshapes can be determined in several ways. Graphically plotting instantaneous dissipation as a function of time is one method. The total maximum allowable power dissipation (P_D) may be determined using the following equation for temperature rise:

$$P_D = \frac{T_{J(MAX)} - T_C}{R_{\theta JC}}$$

where $T_{J(max)}$ is the maximum rated junction temperature (at zero rated current), T_C is the actual operating case temperature, and $R_{\theta JC}$ is the published junction-to-case thermal resistance. Transient thermal resistance curves are required for short interval pulses.

Triac

The limiting factor for RMS current is determined by multiplying power dissipation by thermal resistance. The resulting current value will ensure an operating junction temperature within maximum value. For convenience, dissipation is converted to RMS current at a 360° conduction angle. The same RMS current can be used at a conduction angle of less than 360°. For information on non-sinusoidal waveshapes and a discussion of dissipation, refer to the preceding description of SCR current rating.

I_{TSM} : Peak Surge (Non-repetitive) On-state Current -- SCR and Triac

The peak surge current is the maximum peak current that may be applied to the device for one full cycle of conduction without device degradation. The maximum peak current is usually specified as sinusoidal at 50 Hz or 60 Hz. This rating applies when the device is conducting rated current before the surge and, thus, with the junction temperature at rated values before the surge. The junction temperature will surpass the rated operating temperature during the surge, and the blocking capacity may be decreased until the device reverts to thermal equilibrium.

The surge-current curve in Figure AN1008.3 illustrates the peak current that may be applied as a function of surge duration. This surge curve is not intended to depict an exponential current decay as a function of applied overload. Instead, the peak current shown for a given number of cycles is the maximum peak surge permitted for that time period. The current must be derated so that the peak junction temperature during the surge overload does not exceed maximum rated junction temperature if blocking is to be retained after a surge.

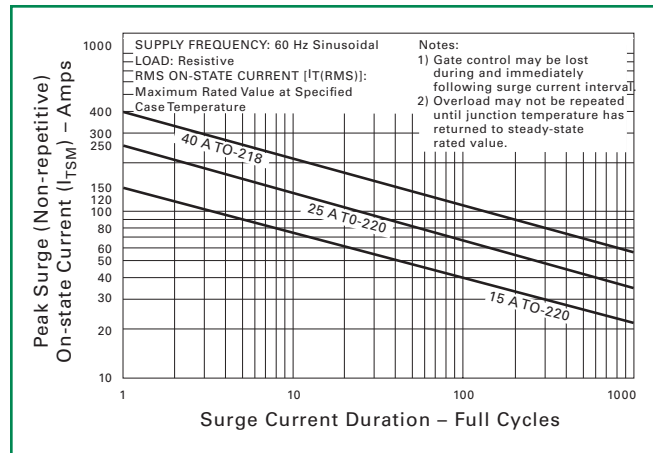


Figure AN1008.3 Peak Surge Current versus Surge Current Duration

I_{TM} : Peak Repetitive On-state Current – SCR and Triac

The I_{TM} rating specifies the maximum peak current that may be applied to the device during brief pulses. When the device operates under these circumstances, blocking capability is maintained. The minimum pulse duration and shape are defined and control the applied di/dt. The operating voltage, the duty factor, the case temperature, and the gate waveform are also defined. This rating must be followed when high repetitive peak currents are employed, such as in pulse modulators, capacitive-discharge circuits, and other applications where snubbers are required.

di/dt: Rate-of-change of On-state Current – SCR and Triac

The di/dt rating specifies the maximum rate-of-rise of current through a Thyristor device during turn-on. The value of principal voltage prior to turn-on and the magnitude and rise time of the gate trigger waveform during turn-on are among the conditions under which the rating applies. If the rate-of-change of current (di/dt) exceeds this maximum value, or if turn-on with high di/dt during minimum gate drive occurs (such as dv/dt or overvoltage events), then localized heating may cause device degradation.

During the first few microseconds of initial turn-on, the effect of di/dt is more pronounced. The di/dt capability of the Thyristor is greatly increased as soon as the total area of the pellet is in full conduction.

The di/dt effects that can occur as a result of voltage or transient turn-on (non-gated) is not related to this rating. The di/dt rating is specified for maximum junction temperature.

As shown in Figure AN1008.4, the di/dt of a surge current can be calculated by means of the following equation.

$$\frac{di}{dt} = \frac{I_{TM}}{2t_1}$$

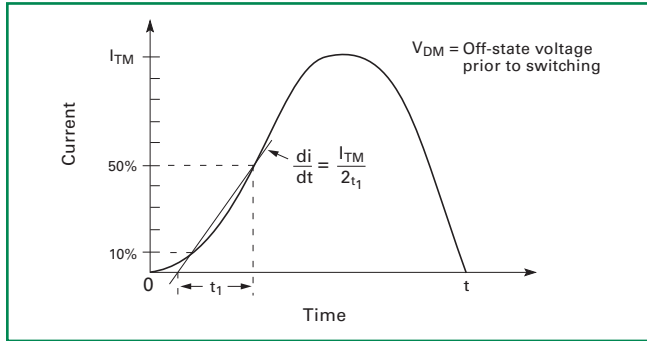


Figure AN1008.4 Relationship of Maximum Current Rating to Time

I²t Rating -- SCR and Triac

The I²t rating gives an indication of the energy-absorbing capability of the Thyristor device during surge-overload conditions. The rating is the product of the square of the RMS current (I_{RMS})² that flows through the device and the time during which the current is present and is expressed in A²s. This rating is given for fuse selection purposes. It is important that the I²t rating of the fuse is less than that of the Thyristor device. Without proper fuse or current limit, overload or surge current will permanently damage the device due to excessive junction heating.

P_G: Gate Power Dissipation -- SCR and Triac

Gate power dissipation ratings define both the peak power (P_{GM}) forward or reverse and the average power ($P_{G(AV)}$) that may be applied to the gate. Damage to the gate can occur if these ratings are not observed. The width of the applied gate pulses must be considered in calculating the voltage and current allowed since the peak power allowed is a function of time. The peak power that results from a given signal source relies on the gate characteristics of the specific unit. The average power resulting from high peak powers must not exceed the average-power rating.

T_S, T_J: Temperature Range -- SCR and Triac

The maximum storage temperature (T_S) is greater than the maximum operating temperature (actually maximum junction temperature). Maximum storage temperature is restricted by material limits defined not so much by the silicon but by peripheral materials such as solders used on the chip/die and lead attachments as well as the encapsulating epoxy. The forward and off-state blocking capability of the device determines the maximum junction (T_J) temperature. Maximum blocking voltage and leakage current ratings are established at elevated temperatures near maximum junction temperature; therefore, operation in excess of these limits may result in unreliable operation of the Thyristor.

Characteristics

V_{BO}: Instantaneous Breakover Voltage -- SCR and Triac

Breakover voltage is the voltage at which a device turns on (switches to on state by voltage breakover). (Figure AN1008.1) This value applies for open-gate or gate-

resistance termination. Positive gate bias lowers the breakover voltage. Breakover is temperature sensitive and will occur at a higher voltage if the junction temperature is kept below maximum T_J value. If SCRs and Triacs are turned on as a result of an excess of breakover voltage, instantaneous power dissipations may be produced that can damage the chip or die.

I_{DRM}: Peak Repetitive Off-state (Blocking) Current

SCR

I_{DRM} is the maximum leakage current permitted through the SCR when the device is forward biased with rated positive voltage on the anode (DC or instantaneous) at rated junction temperature and with the gate open or gate resistance termination. A 1000 Ω resistor connected between gate and cathode is required on all sensitive SCRs. Leakage current decreases with decreasing junction temperatures. Effects of the off-state leakage currents on the load and other circuitry must be considered for each circuit application. Leakage currents can usually be ignored in applications that control high power.

Triac

The description of peak off-state (blocking/leakage) current for the Triac is the same as for the SCR except that it applies with either positive or negative bias on main terminal 2. (Figure AN1008.2)

I_{RRM}: Peak Repetitive Reverse Current – SCR

This characteristic is essentially the same as the peak forward off-state (blocking/leakage) current except negative voltage is applied to the anode (reverse biased).

V_{TM}: Peak On-State Voltage -- SCR and Triac

The instantaneous on-state voltage (forward drop) is the principal voltage at a specified instantaneous current and case temperature when the Thyristor is in the conducting state. To prevent heating of the junction, this characteristic is measured with a short current pulse. The current pulse should be at least 100 μ s duration to ensure the device is in full conduction. The forward-drop characteristic determines the on-state dissipation. See Figure AN1008.5, and refer to "IT: Current Rating" on page AN1008-2.

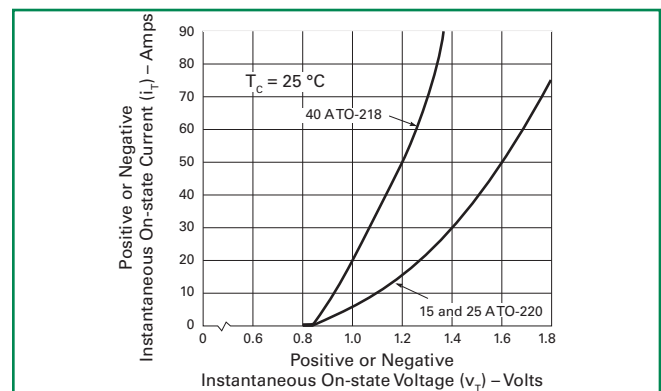


Figure AN1008.5 On-state Current versus On-state Voltage (Typical)

I_{GT} : DC Gate Trigger Current

SCR

I_{GT} is the minimum DC gate current required to cause the Thyristor to switch from the non-conducting to the conducting state for a specified load voltage and current as well as case temperature. The characteristic curve illustrated in Figure AN1008.6 shows that trigger current is temperature dependent. The Thyristor becomes less sensitive (requires more gate current) with decreasing junction temperatures. The gate current should be increased by a factor of two to five times the minimum threshold DC trigger current for best operation. Where fast turn-on is demanded and high di/dt is present or low temperatures are expected, the gate pulse may be 10 times the minimum I_{GT} , plus it must be fast-rising and of sufficient duration in order to properly turn on the Thyristor.

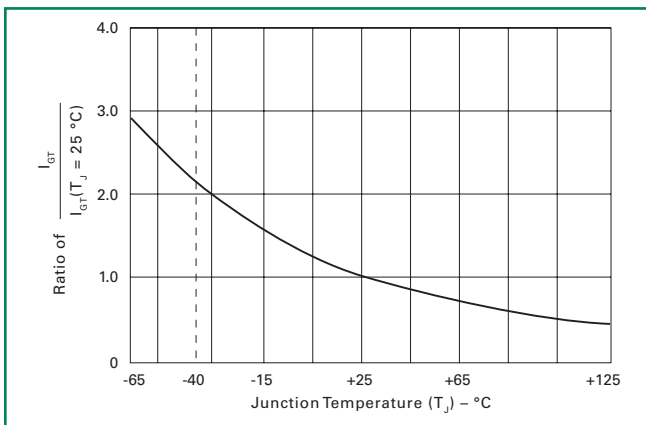


Figure AN1008.6 Normalized DC Gate Trigger Current for All Quadrants versus Case Temperature

Triac

The description for the SCR applies as well to the Triac with the addition that the Triac can be fired in four possible modes (Figure AN1008.7):

- Quadrant I (main terminal 2 positive, gate positive)
- Quadrant II (main terminal 2 positive, gate negative)
- Quadrant III (main terminal 2 negative, gate negative)
- Quadrant IV (main terminal 2 negative, gate positive)

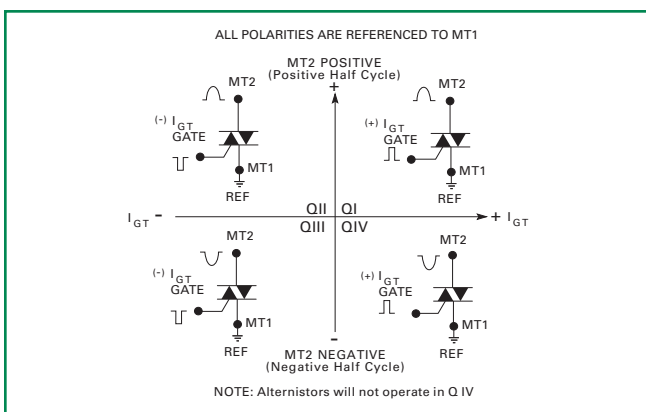


Figure AN1008.7 Definition of Operating Quadrants

V_{GT} : DC Gate Trigger Voltage

SCR

V_{GT} is the DC gate-cathode voltage that is present just prior to triggering when the gate current equals the DC trigger current. As shown in the characteristic curve in Figure AN1008.8, the gate trigger voltage is higher at lower temperatures. The gate-cathode voltage drop can be higher than the DC trigger level if the gate is driven by a current higher than the trigger current.

Triac

The difference in V_{GT} for the SCR and the Triac is that the Triac can be fired in four possible modes. The threshold trigger voltage can be slightly different, depending on which of the four operating modes is actually used.

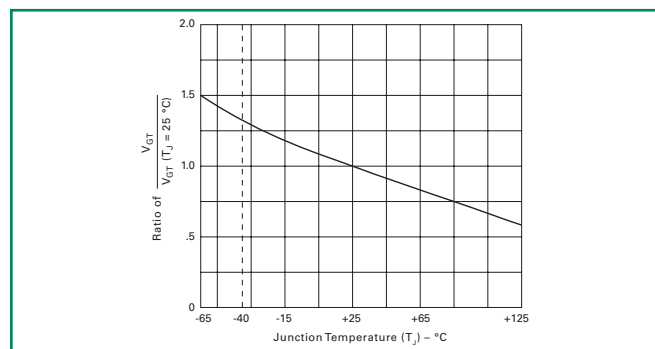


Figure AN1008.8 Normalized DC Gate Trigger Voltage for All Quadrants versus Case Temperature

I_L : Latching Current

SCR

Latching current is the DC anode current above which the gate signal can be withdrawn and the device stays on. It is related to, has the same temperature dependence as, and is somewhat greater than the DC gate trigger current. (Figure AN1008.1 and Figure AN1008.2) Latching current is at least equal to or much greater than the holding current, depending on the Thyristor type.

Latching current is greater for fast-rise-time anode currents since not all of the chip/die is in conduction. It is this dynamic latching current that determines whether a device will stay on when the gate signal is replaced with very short gate pulses. The dynamic latching current varies with the magnitude of the gate drive current and pulse duration. In some circuits, the anode current may oscillate and drop back below the holding level or may even go negative; hence, the unit may turn off and not latch if the gate signal is removed too quickly.

Triac

The description of this characteristic for the Triac is the same as for the SCR, with the addition that the Triac can be latched on in four possible modes (quadrants). Also, the required latching is significantly different depending on which gating quadrants are used. Figure AN1008.9 illustrates typical latching current requirements for the four possible quadrants of operation.

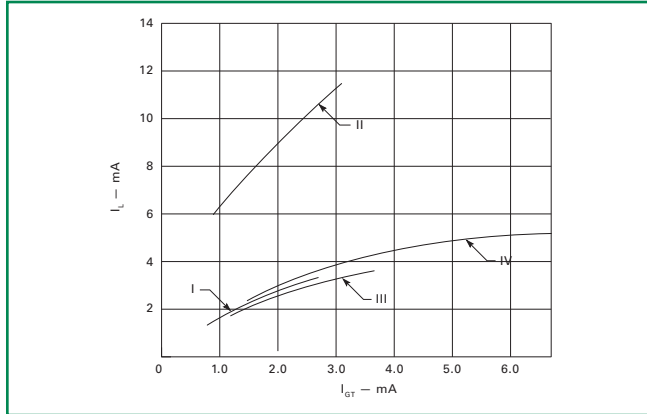


Figure AN1008.9 Typical Triac Latching (I_L) Requirements for Four Quadrants versus Gate Current (I_{GT})

I_H : Holding Current -- SCR and Triac

The holding current is the DC principal on-state current below which the device will not stay in regeneration/on state after latching and gate signal is removed. This current is equal to or lower in value than the latching current (Figure AN1008.1 and Figure AN1008.2) and is related to and has the same temperature dependence as the DC gate trigger current shown in Figure AN1008.10. Both minimum and maximum holding current may be important. If the device is to stay in conduction at low-anode currents, the maximum holding current of a device for a given circuit must be considered. The minimum holding current of a device must be considered if the device is expected to turn off at a low DC anode current. Note that the low DC principal current condition is a DC turn-off mode, and that an initial on-state current (latching current) is required to ensure that the Thyristor has been fully turned on prior to a holding current measurement.

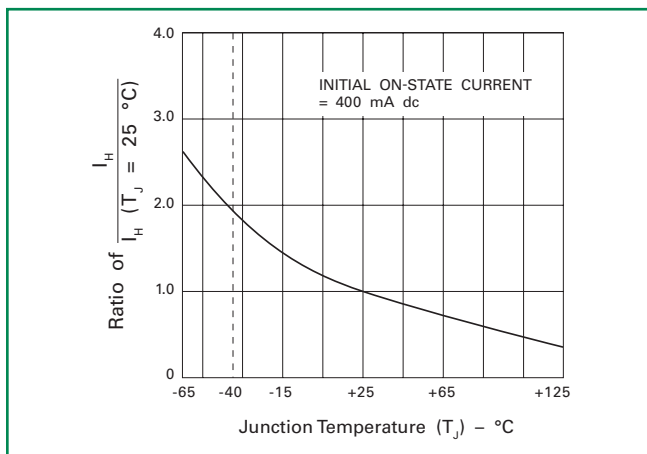


Figure AN1008.10 Normalized DC Holding Current versus Case Temperature

dv/dt, Static: Critical Rate-of-rise of Off-state Voltage -- SCR and Triac

Static dv/dt is the minimum rate-of-rise of off-state voltage that a device will hold off, with gate open, without turning on. Figure AN1008.11 illustrates the exponential definition.

This value will be reduced by a positive gate signal. This characteristic is temperature-dependent and is lowest at the maximum-rated junction temperature. Therefore, the characteristic is determined at rated junction temperature and at rated forward off-state voltage which is also a worst-case situation. Line or other transients which might be applied to the Thyristor in the off state must be reduced, so that neither the rate-of-rise nor the peak voltage are above specifications if false firing is to be prevented. Turn-on as result of dv/dt is non-destructive as long as the follow current remains within current ratings of the device being used.

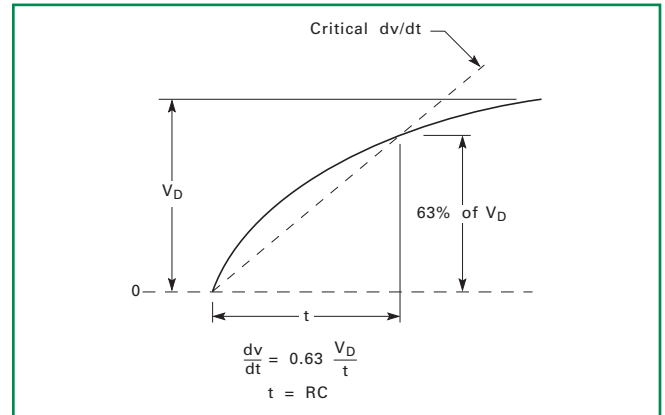


Figure AN1008.11 Exponential Rate-of-rise of Off-state Voltage Defining dv/dt

dv/dt, Commutating: Critical Rate-of-rise of Commutation Voltage -- Triac

Commutating dv/dt is the rate-of-rise of voltage across the main terminals that a Triac can support (block without switching back on) when commutating from the on state in one half cycle to the off state in the opposite half cycle. This parameter is specified at maximum rated case temperature (equal to T_J) since it is temperature-dependent. It is also dependent on current (commutating di/dt) and peak reapplied voltage (line voltage) and is specified at rated current and voltage. All devices are guaranteed to commute rated current with a resistive load at 50 Hz to 60 Hz. Commutation of rated current is not guaranteed at higher frequencies, and no direct relationship can be made with regard to current/temperature derating for higher-frequency operation. With inductive loading, when the voltage is out of phase with the load current, a voltage stress (dv/dt) occurs across the main terminals of the Triac during the zero-current crossing. (Figure AN1008.12) A snubber (series RC across the Triac) should be used with inductive loads to decrease the applied dv/dt to an amount below the minimum value which the Triac can be guaranteed to commute off each half cycle.

Commutating dv/dt is specified for a half sinewave current at 60 Hz which fixes the di/dt of the commutating current. The commutating di/dt for 50 Hz is approximately 20% lower while I_{RMS} rating remains the same. (Figure AN1008.4)

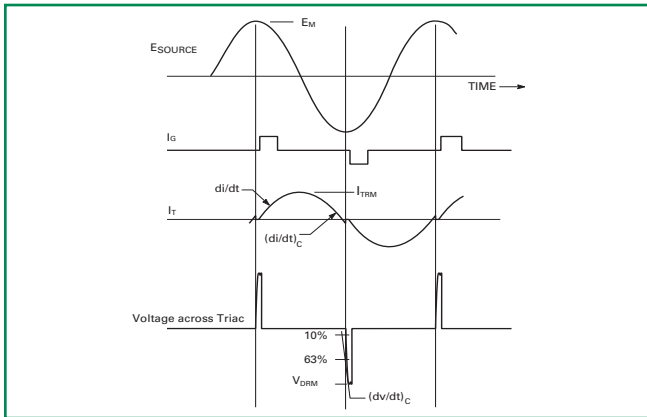


Figure AN1008.12 Waveshapes of Commutating dv/dt and Associated Conditions

t_{gt} : Gate-controlled Turn-on Time -- SCR and Triac

The t_{gt} is the time interval between the application of a gate pulse and the on-state current reaching 90% of its steady-state value. (Figure AN1008.13) As would be expected, turn-on time is a function of gate drive. Shorter turn-on times occur for increased gate drives. This turn-on time is actually only valid for resistive loading. For example, inductive loading would restrict the rate-of-rise of anode current. For this reason, this parameter does not indicate the time that must be allowed for the device to stay on if the gate signal is removed. (Refer to the description of "IL: Latching Current" on page AN1008-4.) However, if the load was resistive and equal to the rated load current value, the device definitely would be operating at a current above the dynamic latching current in the turn-on time interval since current through the device is at 90% of its peak value during this interval.

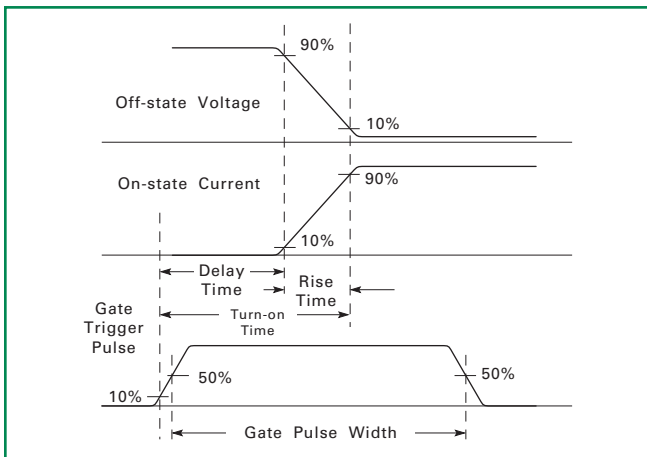


Figure AN1008.13 Waveshapes for Turn-on Time and Associated Conditions

t_q : Circuit-commutated Turn-off Time -- SCR

The circuit-commutated turn-off time of the device is the time during which the circuit provides reverse bias to the device (negative anode) to commutate it off. The turn-off time occurs between the time when the anode current goes negative and when the anode positive voltage may

be reapplied. (Figure AN1008.14) Turn-off time is a function of many parameters and very dependent on temperature and gate bias during the turn-off interval. Turn-off time is lengthened for higher temperature so a high junction temperature is specified. The gate is open during the turn-off interval. Positive bias on the gate will lengthen the turn-off time; negative bias on the gate will shorten it.

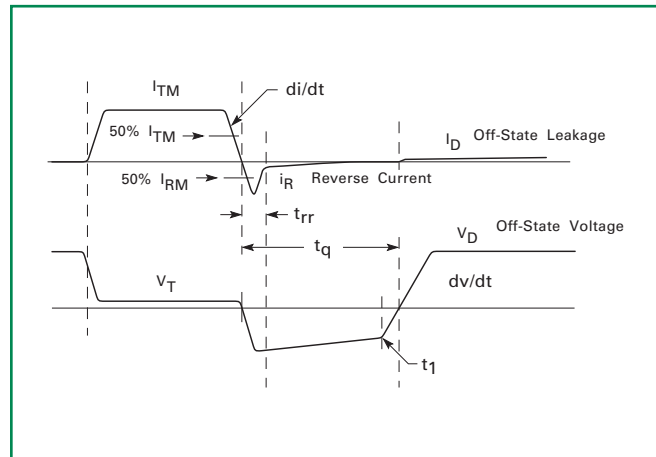


Figure AN1008.14 Waveshapes of t_q Rating Test and Associated Conditions

$R_{\theta JC}$, $R_{\theta JA}$: Thermal Resistance (Junction-to-case, Junction-to-ambient) -- SCR and Triac

The thermal-resistance characteristic defines the steady-state temperature difference between two points at a given rate of heat-energy transfer (dissipation) between the points. The thermal-resistance system is an analog to an electrical circuit where thermal resistance is equivalent to electrical resistance, temperature difference is equivalent to voltage difference, and rate of heat-energy transfer (dissipation) is equivalent to current. Dissipation is represented by a constant current generator since generated heat must flow (steady-state) no matter what the resistance in its path. Junction-to-case thermal resistance establishes the maximum case temperature at maximum rated steady-state current. The case temperature must be held to the maximum at maximum ambient temperature when the device is operating at rated current. Junction-to-ambient thermal resistance is established at a lower steady-state current, where the device is in free air with only the external heat sinking offered by the device package itself. For $R_{\theta JA}$, power dissipation is limited by what the device package can dissipate in free air without any additional heat sink:

$$R_{\theta JC} = \frac{T_J - T_C}{P_{(AV)}}$$

$$R_{\theta JA} = \frac{T_J - T_A}{P_{(AV)}}$$

Miscellaneous Design Tips and Facts

Introduction

This application note presents design tips and facts on the following topics:

- Relationship of I_{AV} , I_{RMS} , and I_{PK}
- dv/dt Definitions
- Examples of gate terminations
- Curves for Average Current at Various Conduction Angles
- Double-exponential Impulse Waveform
- Failure Modes of Thyristor
- Characteristics Formulas for Phase Control Circuits

Relationship of I_{AV} , I_{RMS} , and I_{PK}

Since a single rectifier or SCR passes current in one direction only, it conducts for only half of each cycle of an AC sine wave. The average current (I_{AV}) then becomes half of the value determined for full-cycle conduction, and the RMS current (I_{RMS}) is equal to the square root of half the mean-square value for full-cycle conduction or half the peak current (I_{PK}). In terms of half-cycle sine wave conduction (as in a single-phase half-wave circuit), the relationships of the rectifier currents can be shown as follows:

$$I_{PK} = \pi \cdot I_{AV} = 3.14 \cdot I_{AV}$$

$$I_{AV} = (1/\pi) I_{PK} = 0.32 \cdot I_{PK}$$

$$I_{PK} = 2 \cdot I_{RMS}$$

$$I_{RMS} = 0.5 \cdot I_{PK}$$

$$I_{AV} = (2/\pi) I_{RMS} = 0.64 \cdot I_{RMS}$$

$$I_{RMS} = (\pi/2) I_{AV} = 1.57 \cdot I_{AV}$$

When two identically rated SCRs are connected inverse parallel for full-wave operation, as shown in Figure AN1009.1, they can handle 1.41 times the RMS current rating of either single SCR. Therefore, the RMS value of two half sine wave current pulses in one cycle is $\sqrt{2}$ times the RMS value of one such pulse per cycle.

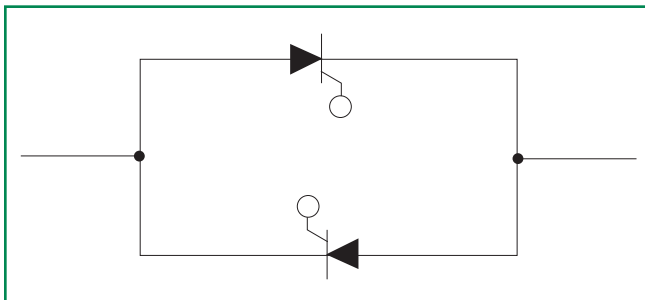


Figure AN1009.1 SCR Anti-parallel Circuit

dv/dt Definitions

The rate-of-rise of voltage (dv/dt) of an exponential waveform is 63% of peak voltage (excluding any overshoots) divided by the time at 63% minus 10% peak voltage. (Figure AN1009.2)

$$\text{Exponential dv/dt} = 0.63 \cdot [V_{PK}] = (t_2 - t_1)$$

$$\text{Resistor Capacitor circuit } t = RC = (t_2 - t_1)$$

$$\text{Resistor Capacitor circuit } 4 \cdot RC = (t_3 - t_2)$$

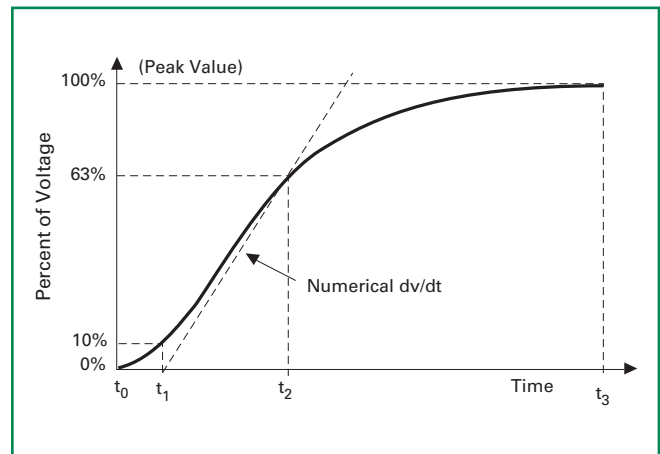


Figure AN1009.2 Exponential dv/dt Waveform

The rate-of-rise of voltage (dv/dt) of a linear waveform is 80% of peak voltage (excluding any overshoots) divided by the time at 90% minus 10% peak voltage. (Figure AN1009.3)

$$\text{Linear dv/dt} = 0.8 \cdot [V_{PK}] = (t_2 - t_1)$$

$$\text{Linear dv/dt} = [0.9 \cdot V_{PK} - 0.1 \cdot V_{PK}] = (t_2 - t_1)$$

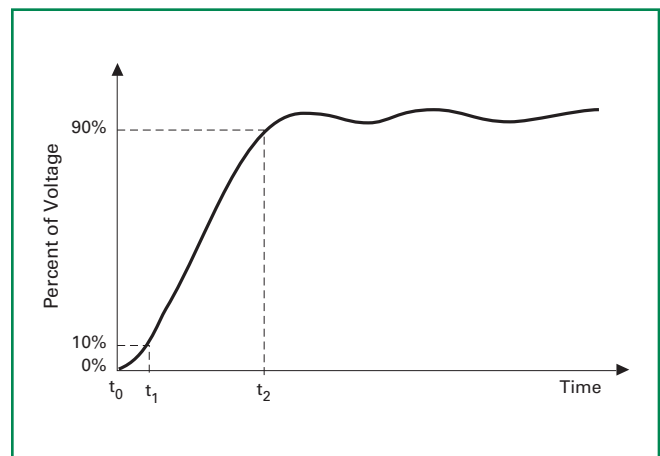
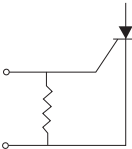
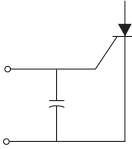
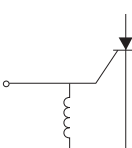
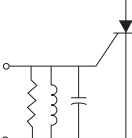
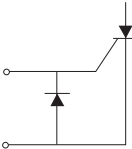
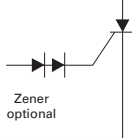
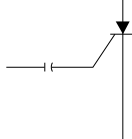


Figure AN1009.3 Linear dv/dt Waveform

Examples of Gate Terminations

	<p>Primary Purpose</p> <ol style="list-style-type: none"> (1) Increase dv/dt capability (2) Keep gate clamped to ensure V_{DRM} capability (3) Lower t_q time <p>Related Effect – Raises the device latching and holding current</p>
	<p>Primary Purpose</p> <ol style="list-style-type: none"> (1) Increase dv/dt capability (2) Remove high frequency noise <p>Related Effects</p> <ol style="list-style-type: none"> (1) Increases delay time (2) Increases turn-on interval (3) Lowers gate signal rise time (4) Lowers di/dt capability (5) Increases t_q time
	<p>Primary Purpose</p> <ol style="list-style-type: none"> (1) Decrease DC gate sensitivity (2) Decrease t_q time <p>Related Effects</p> <ol style="list-style-type: none"> (1) Negative gate current increases holding current and causes gate area to drop out of conduction (2) In pulse gating gate signal tail may cause device to drop out of conduction
	<p>Primary Purpose – Select frequency</p> <p>Related Effects – Unless circuit is “damped,” positive and negative gate current may inhibit conduction or bring about sporadic anode current</p>
	<p>Primary Purpose</p> <ol style="list-style-type: none"> (1) Supply reverse bias in off period (2) Protect gate and gate supply for reverse transients (3) Lower t_q time <p>Related Effects – Isolates the gate if high impedance signal source is used without sustained diode current in the negative cycle</p>
	<p>Primary Purpose – Decrease threshold sensitivity</p> <p>Related Effects</p> <ol style="list-style-type: none"> (1) Affects gate signal rise time and di/dt rating (2) Isolates the gate
	<p>Primary Purpose – Isolate gate circuit DC component</p> <p>Related Effects – In narrow gate pulses and low impedance sources, I_{gr} followed by reverse gate signals which may inhibit conduction</p>

Curves for Average Current at Various Conduction Angles

SCR maximum average current curves for various conduction angles can be established using the factors for maximum average current at conduction angle of:

$$30^\circ = 0.40 \times \text{Avg } 180^\circ$$

$$60^\circ = 0.56 \times \text{Avg } 180^\circ$$

$$90^\circ = 0.70 \times \text{Avg } 180^\circ$$

$$120^\circ = 0.84 \times \text{Avg } 180^\circ$$

The reason for different ratings is that the average current for conduction angles less than 180° is derated because of the higher RMS current connected with high peak currents.

Note that maximum allowable case temperature (T_c) remains the same for each conduction angle curve but is established from average current rating at 180° conduction as given in the data sheet for any particular device type. The maximum T_c curve is then derated down to the maximum junction (T_j). The curves illustrated in Figure AN1009.4 are derated to 125°C since the maximum T_j for the non-sensitive SCR series is 125°C .

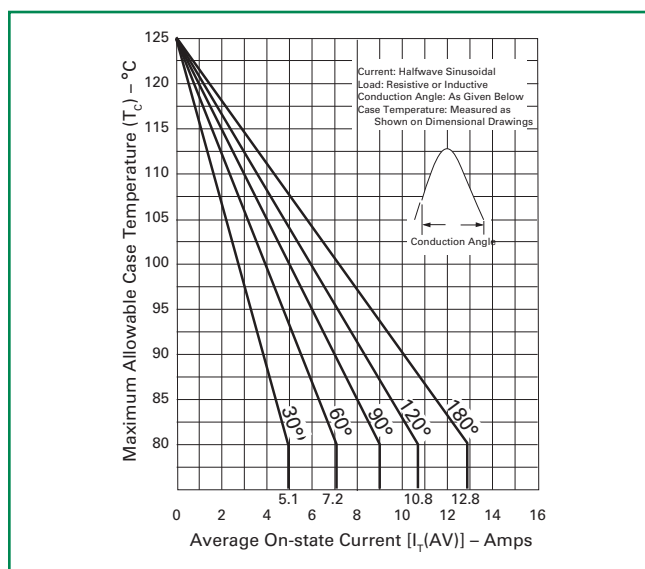


Figure AN1009.4 Typical Curves for Average On-state Current at Various Conduction Angles versus T_c for a SXX20L SCR.

Double-Exponential Impulse Waveform

A double-exponential impulse waveform or waveshape of current or voltage is designated by a combination of two numbers (t_r/t_d or $t_r \times t_d \mu\text{s}$). The first number is an exponential rise time (t_r) or wave front and the second number is an exponential decay time (t_d) or wave tail. The rise time (t_r) is the maximum rise time permitted. The decay time (t_d) is the minimum time permitted. Both the t_r and the t_d are in the same units of time, typically microseconds, designated at the end of the waveform description as defined by ANSI/IEEE C62.1-1989.

The rise time (t_r) of a current waveform is 1.25 times the time for the current to increase from 10% to 90% of peak value. See Figure AN1009.5.

$$t_r = \text{Rise Time} = 1.25 \cdot [t_c - t_a]$$

$$t_r = 1.25 \cdot [t(0.9 I_{PK}) - t(0.1 I_{PK})] = T_1 - T_0$$

The rise time (t_r) of a voltage waveform is 1.67 times the time for the voltage to increase from 30% to 90% of peak value. (Figure AN1009.5)

$$t_r = \text{Rise Time} = 1.67 \cdot [t_c - t_b]$$

$$t_r = 1.67 \cdot [t(0.9 V_{PK}) - t(0.3 V_{PK})] = T_1 - T_0$$

The decay time (t_d) of a waveform is the time from virtual zero (10% of peak for current or 30% of peak for voltage) to the time at which one-half (50%) of the peak value is reached on the wave tail. (Figure AN1009.5)

$$\text{Current Waveform } t_d = \text{Decay Time}$$

$$= [t(0.5 I_{PK}) - t(0.1 I_{PK})] = T_2 - T_0$$

$$\text{Voltage Waveform } t_d = \text{Decay Time}$$

$$= [t(0.5 V_{PK}) - t(0.3 V_{PK})] = T_2 - T_0$$

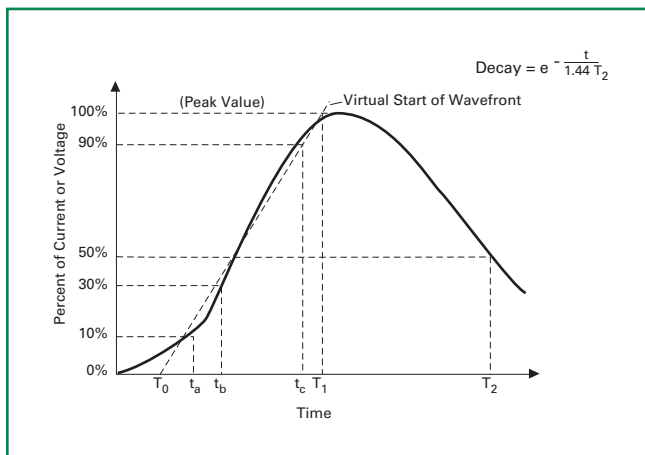


Figure AN1009.5 Double-exponential Impulse Waveform

Failure Modes of Thyristor

Thyristor failures may be broadly classified as either degrading or catastrophic. A degrading type of failure is defined as a change in some characteristic which may or may not cause a catastrophic failure, but could show up as a latent failure. Catastrophic failure is when a device exhibits a sudden change in characteristic that renders it inoperable. To minimize degrading and catastrophic failures, devices must be operated within maximum ratings at all times.

Degradation Failures

A significant change of on-state, gate, or switching characteristics is quite rare. The most vulnerable characteristic is blocking voltage. This type of degradation increases with rising operating voltage and temperature levels.

Catastrophic Failures

A catastrophic failure can occur whenever the Thyristor is operated beyond its published ratings. The most common failure mode is an electrical short between the main terminals, although a Triac can fail in a half-wave condition. It is possible, but not probable, that the resulting short-circuit current could melt the internal parts of the device which could result in an open circuit.

Failure Causes

Most Thyristor failures occur due to exceeding the maximum operating ratings of the device. Overvoltage or overcurrent operations are the most probable cause for failure. Overvoltage failures may be due to excessive voltage transients or may also occur if inadequate cooling allows the operating temperature to rise above the maximum allowable junction temperature. Overcurrent failures are generally caused by improper fusing or circuit protection, surge current from load initiation, load abuse, or load failure. Another common cause of device failure is incorrect handling procedures used in the manufacturing process. Mechanical damage in the form of excessive mounting torque and/or force applied to the terminals or leads can transmit stresses to the internal Thyristor chip and cause cracks in the chip which may not show up until the device is thermally cycled.

Prevention of Failures

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should also limit the maximum current through the main terminals to 75% of the device rating. Correct mounting and forming of the leads also help ensure against infant mortality and latent failures. The two best ways to ensure long life of a Thyristor is by proper heat sink methods and correct voltage rating selection for worst case conditions. Overheating, overvoltage, and surge currents are the main killers of semiconductors.

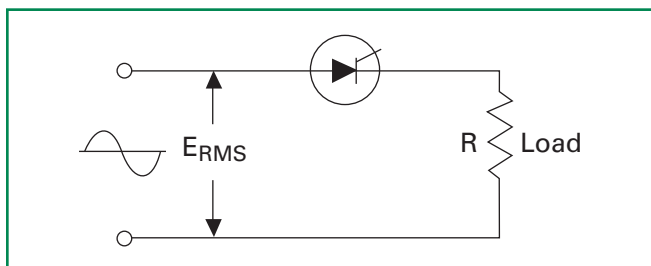
Most Common Thyristor Failure Mode

When a Thyristor is electrically or physically abused and fails either by degradation or a catastrophic means, it will short (full-wave or half-wave) as its normal failure mode. Rarely does it fail open circuit. The circuit designer should add line breaks, fuses, over-temperature interrupters or whatever is necessary to protect the end user and property if a shorted or partially shorted Thyristor offers a safety hazard.

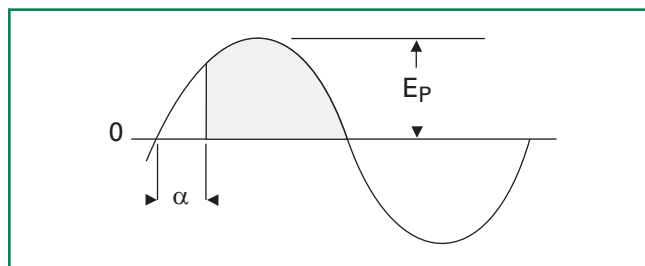
Characteristics Formulas for Phase Control Circuits

Circuit Name	Max Thyristor Voltage	PRV	Max. Load Voltage $E_d = \text{Avg. } E_a = \text{RMS Load}$	Load Voltage with Delayed Firing	Max. Average Thyristor or Rectifier Current	
		SCR			Avg. Amps	Conduction Period
Half-wave Resistive Load	$1.4 E_{\text{RMS}}$	E_p	$E_d = \frac{E_p}{\pi}$ $E_a = \frac{E_p}{2}$	$E_d = \frac{E_p}{2\pi} (1 + \cos \alpha)$ $E_a = \frac{E_p}{2\sqrt{\pi}} \sqrt{(\pi - \alpha + \frac{1}{2} \sin 2\alpha)}$	$\frac{E_p}{\pi R}$	180°
Full-wave Bridge	$1.4 E_{\text{RMS}}$	E_p	$E_d = \frac{2E_p}{\pi}$	$E_d = \frac{E_p}{2\sqrt{\pi}} (1 + \cos \alpha)$	$\frac{E_p}{\pi R}$	180°
Full-wave AC Switch Resistive Load	$1.4 E_{\text{RMS}}$	E_p	$E_a = \frac{E_p}{1.4}$	$E_a = \frac{E_p}{\sqrt{2\pi}} \sqrt{(\pi - \alpha + \frac{1}{2} \sin 2\alpha)}$	$\frac{E_p}{\pi R}$	180°

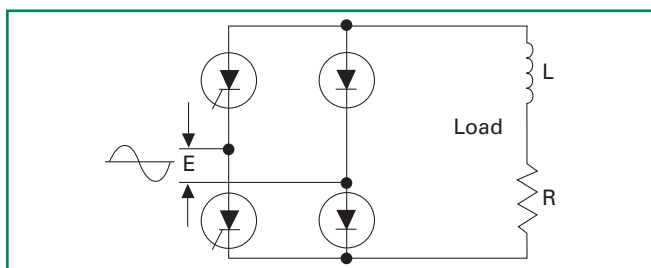
NOTE: Angle alpha (α) is in radians.



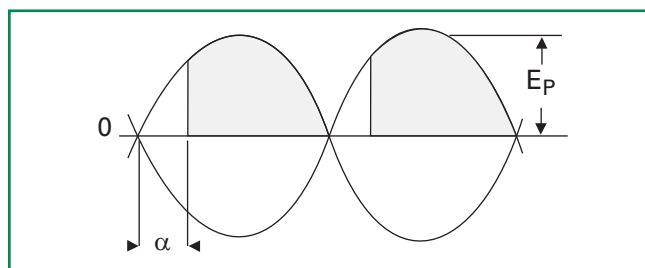
Half-wave Resistive Load - Schematic



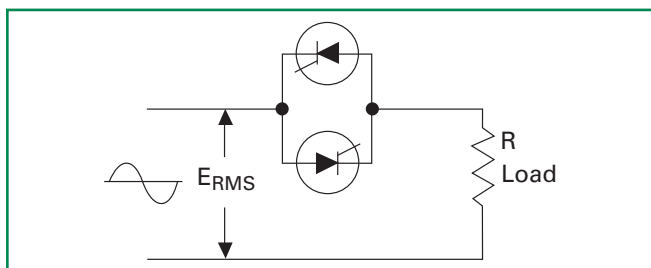
Half-wave Resistive Load - Waveform



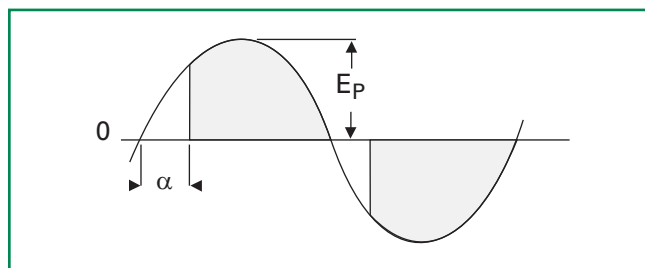
Full-wave Bridge - Schematic



Full-wave Bridge - Waveform



Full-wave AC Switch Resistive Load - Schematic



Full-wave AC Switch Resistive Load - Waveform

Thyristors for Ignition of Fluorescent Lamps

Introduction

One of the many applications for Thyristors is in fluorescent lighting. Standard conventional and circular fluorescent lamps with filaments can be ignited easily and much more quickly by using Thyristors instead of the mechanical starter switch, and solid state Thyristors are more reliable. Thyristors produce a pure solid state igniting circuit with no mechanical parts in the fluorescent lamp fixture. Also, because the lamp ignites much faster, the life of the fluorescent lamp can be increased since the filaments are activated for less time during the ignition. The Thyristor ignition eliminates any audible noise or flashing off and on which most mechanical starters possess.

Standard Fluorescent Circuit

The standard starter assembly is a glow switch mechanism with option small capacitor in parallel. (Figure AN1010.1)

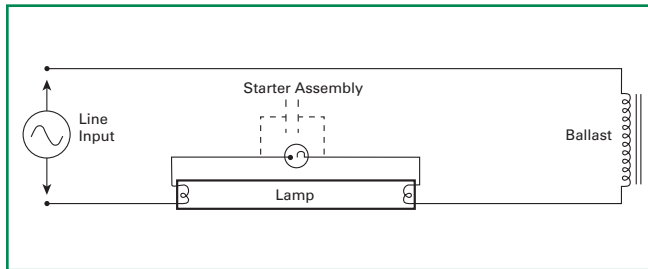


Figure AN1010.1 Typical Standard Fluorescent Circuit

The glow switch is made in a small glass bulb containing neon or argon gas. Inside the bulb is a U-shaped bimetallic strip and a fixed post. When the line input current is applied, the voltage between the bimetallic strip and the fixed post is high enough to ionize and produce a glow similar to a standard neon lamp. The heat from the ionization causes the bimetallic strip to move and make contact to the fixed post. At this time the ionization ceases and current can flow through and pre-heat the filaments of the fluorescent lamp.

Since ionization (glowing) has ceased, the bimetallic strip begins to cool down and in a few seconds opens to start ionization (glowing) again. The instant the bimetallic ceases to make contact (opens), an inductive kick from the ballast produces some high voltage spikes 400 V to 600 V, which can ignite (strike) the fluorescent lamp. If the lamp fails to ignite or start, the glow switch mechanically repeats its igniting cycle over and over until the lamp ignites, usually within a few seconds.

In this concept the ballast (inductor) is able to produce high voltage spikes using a mechanical switch opening and closing, which is fairly slow.

Since Thyristors (solid state switches) do not mechanically open and close, the conventional fluorescent lighting circuit concept must be changed in order to use Thyristors. In order to ignite (strike) a fluorescent lamp, a high voltage spike must be produced. The spike needs to be several hundred volts to quickly initiate ionization in the fluorescent lamp. A series ballast can only produce high voltage if a mechanical switch is used in conjunction with it. Therefore, with a Thyristor, a standard series ballast (inductor) is only useful as a current limiter.

Methods for Producing High Voltage

The circuits illustrated in Figure AN1010.2 through Figure AN1010.5 show various methods for producing high voltage to ignite fluorescent lamps using Thyristors (solid state switches).

Note: Due to many considerations in designing a fluorescent fixture, the illustrated circuits are not necessarily the optimum design.

One 120 V ac circuit consists of Triac and DIAC Thyristors with a capacitor to ignite the fluorescent lamp. (Figure AN1010.2)

This circuit allows the 5 μF ac capacitor to be charged and added to the peak line voltage, developing close to 300 V peak or 600 V peak to peak. This is accomplished by using a Triac and DIAC phase control network set to fire near the 90° point of the input line. A capacitor-charging network is added to ensure that the capacitor is charged immediately, letting tolerances of components or temperature changes in the Triac and DIAC circuit to be less critical. By setting the Triac and DIAC phase control to fire at near the 90° point of the sinewave, maximum line voltages appear across the lamp for ignition. As the Triac turns on during each half cycle, the filaments are pre-heated and in less than a second the lamp is lit. Once the lamp is lit the voltage is clamped to approximately 60 V peak across the 15 W to 20 W lamp, and the Triac and DIAC circuit no longer functions until the lamp is required to be ignited again.

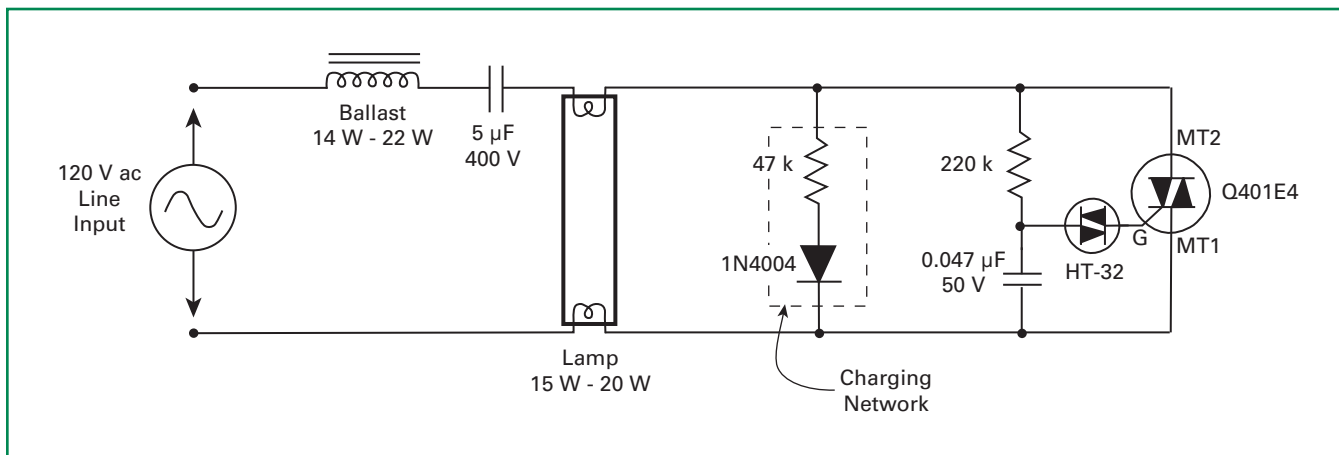


Figure AN1010.2 120 V ac Triac/DIAC Circuit

Figure AN1010.3 illustrates a circuit using a SIDAC (a simpler Thyristor) phase control network to ignite a 120 V ac fluorescent lamp. As in the Triac/DIAC circuit, the 5 μ F ac capacitor is charged and added to the peak line voltage, developing greater than 200 V peak or 400 V peak to peak. Since the SIDAC is a voltage breakover (V_{BO}) activated device with no gate, a charging network is essential in this circuit to charge the capacitor above the peak of the line in order to break over (turn on) the SIDAC with a V_{BO} of 220 V to 250 V.

As the SIDAC turns on each half cycle, the filaments are pre-heated and in less than 1.5 seconds the lamp is lit. Once the lamp is lit, the voltage across it clamps to approximately 60 V peak (for a 15 W to 20 W lamp), and the SIDAC ceases to function until the lamp is required to be ignited again.

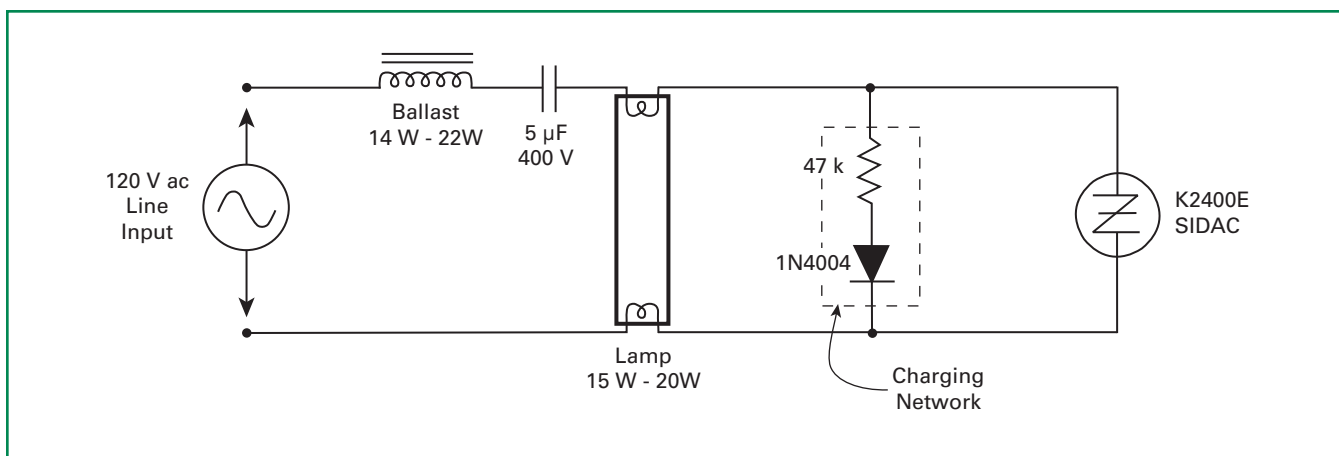


Figure AN1010.3 120 V ac SIDAC Circuit

The circuits illustrated in Figure AN1010.2 and Figure AN1010.3 use 15 W to 20 W lamps. The same basic circuits can be applied to higher wattage lamps. However, with higher wattage lamps the voltage developed to fire (light) the lamp will need to be somewhat higher. For instance, a 40 W lamp is critical on line input voltage to ignite, and after it is lit the voltage across the lamp will clamp to approximately 130 V peak. For a given type of lamp, the current must be limited to constant current regardless of the wattage of the lamp.

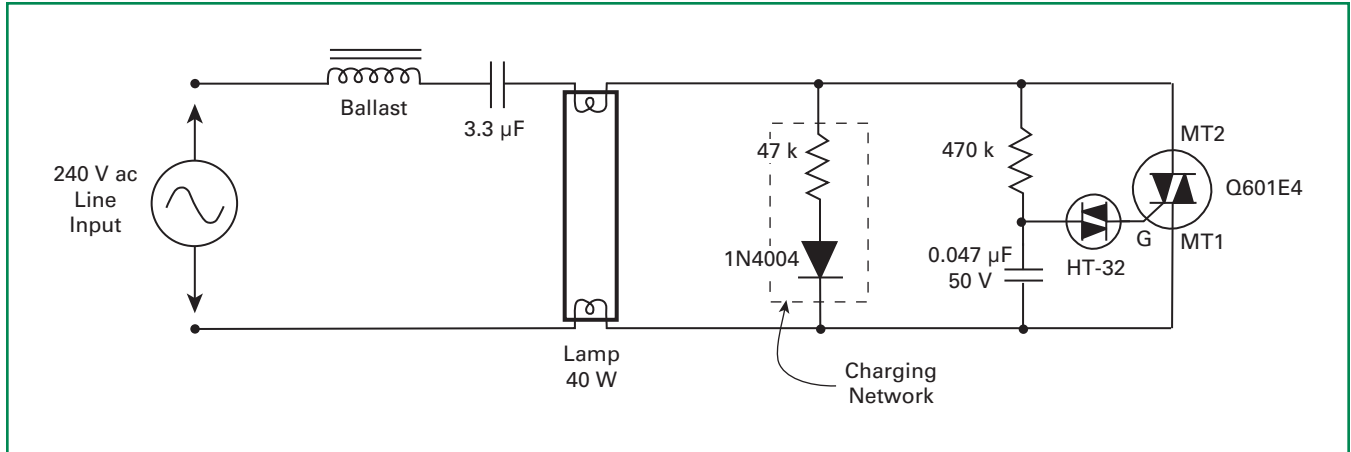


Figure AN1010.4 240 V ac Triac/DIAC Circuit

Figure AN1010.4 shows a circuit for igniting a fluorescent lamp with 240 V line voltage input using Triac and DIAC networks.

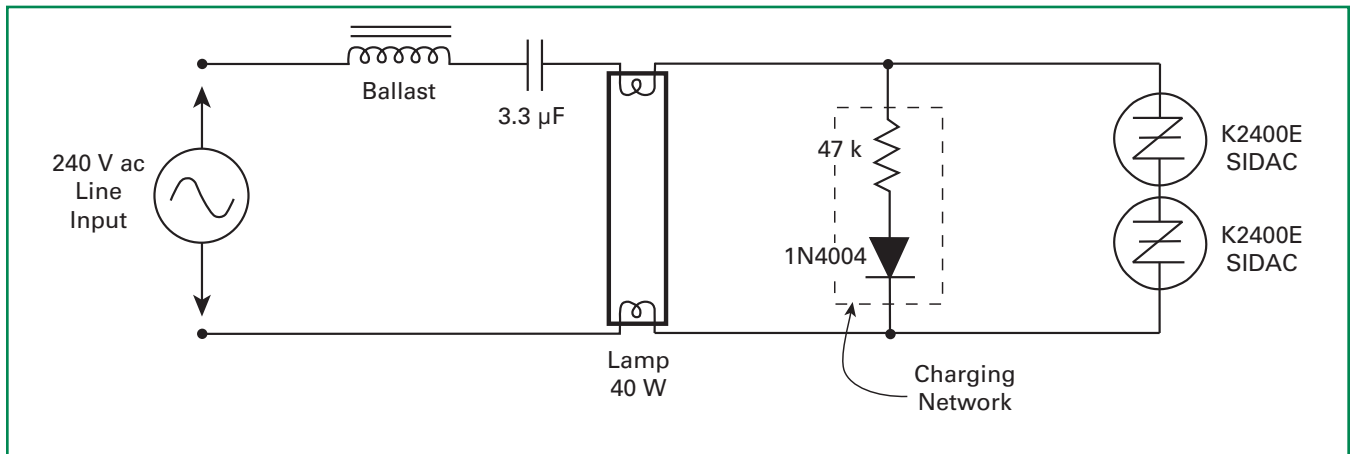


Figure AN1010.5 240 V ac SIDAC Circuit

Figure AN1010.5 illustrates a circuit using a SIDAC phase control network to ignite a 240 V ac fluorescent lamp. This circuit works basically the same as the 120 V circuit shown in Figure AN1010.3, except that component values are changed to compensate for higher voltage. The one major change is that two K2400E devices in series are used to accomplish high firing voltage for a fluorescent lamp.

Cross Reference Guide

Triacs, SCRs, DIACs, SIDACs, and Rectifiers

(Suggested Littelfuse Replacements for JEDEC and Industry House Numbers)

How To Use This Guide

This Cross Reference Guide will help you determine the competitive products that Littelfuse supplies on either a DIRECT REPLACEMENT or SUGGESTED REPLACEMENT basis.

Littelfuse offers replacements for most competitive devices. If you do not find a desired competitive product type listed, please contact the factory for information on recent additions to this list.

On the following pages, listed in alphanumeric order, you will find:

- Competitive product number
- Littelfuse device part number
- “D” indicating the Direct replacement (Littelfuse device meets or exceeds the electrical and mechanical specifications of the competitive device); “S” indicates a Suggested replacement (The suggested replacements in this guide represent the nearest Littelfuse equivalent for the product listed and in most instances are replacements. However, Littelfuse assumes no responsibility and does not guarantee that the replacements are exact; only that the replacements will meet the terms of its applicable published written specifications. The pertinent Littelfuse specification sheet should be used as the principle tool for actual replacements.)
- Littelfuse package type

For additional assistance, contact your nearest Littelfuse distributor, sales representative, or the factory.

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
40431	RCA	Q4006LT	S	TO-220 (ISOL)
03P05M	NEC	S4X8ES	S	TO-92 (ISOL)
03P1M	NEC	S4X8ES	S	TO-92 (ISOL)
03P2M	NEC	S4X8ES	S	TO-92 (ISOL)
03P3M	NEC	S4X8ES	S	TO-92 (ISOL)
03P4M	NEC	S4X8ES	S	TO-92 (ISOL)
03P5M	NEC	S6X8ES	S	TO-92 (ISOL)
10TTS08S	IR	S8012D	S	TO-252 (SMT)
16TTS08	IR	S8016R	D	TO-220 (N.ISOL)
16TTS08S	IR	S8016N	S	TO-263 (SMT)
25TTS08	IR	S8025R	D	TO-220 (N.ISOL)
25TTS08FP	IR	S8025L	D	TO-220 (ISOL)
25TTS08S	IR	S8025N	S	TO-263 (SMT)
2N1595	JEDEC	S401E	S	TO-92 (ISOL)
2N1596	JEDEC	S401E	S	TO-92 (ISOL)
2N1597	JEDEC	S401E	S	TO-92 (ISOL)
2N1598	JEDEC	S401E	S	TO-92 (ISOL)
2N1599	JEDEC	S401E	S	TO-92 (ISOL)
2N2323	JEDEC	S402ES	S	TO-92 (ISOL)
2N3001	JEDEC	S4X8ES1	S	TO-92 (ISOL)
2N3002	JEDEC	S4X8ES1	S	TO-92 (ISOL)
2N3003	JEDEC	S4X8ES1	S	TO-92 (ISOL)
2N3004	JEDEC	S4X8ES1	S	TO-92 (ISOL)
2N3005	JEDEC	S4X8ES	D	TO-92 (ISOL)
2N3006	JEDEC	S4X8ES	D	TO-92 (ISOL)
2N3007	JEDEC	S4X8ES	D	TO-92 (ISOL)
2N3008	JEDEC	S4X8ES	D	TO-92 (ISOL)
2N3228	JEDEC	S4008R	S	TO-220 (N.ISOL)
2N3525	JEDEC	S4008R	S	TO-220 (N.ISOL)
2N3528	JEDEC	S4006V	S	TO-251 (N.ISOL)
2N3529	JEDEC	S4006V	S	TO-251 (N.ISOL)
2N4101	JEDEC	S6008R	S	TO-220 (N.ISOL)
2N4102	JEDEC	S6006V	S	TO-251 (N.ISOL)
2N4441	JEDEC	S4008R	S	TO-220 (N.ISOL)
2N4442	JEDEC	S4008R	S	TO-220 (N.ISOL)
2N4443	JEDEC	S4008R	S	TO-220 (N.ISOL)
2N4444	JEDEC	S6008R	S	TO-220 (N.ISOL)
2N5060	JEDEC	2N6565	D	TO-92 (ISOL)
2N5061	JEDEC	2N6565	D	TO-92 (ISOL)
2N5062	JEDEC	2N6565	D	TO-92 (ISOL)
2N5063	JEDEC	2N6565	D	TO-92 (ISOL)
2N5064	JEDEC	2N6565	D	TO-92 (ISOL)
2N5754	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N5755	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N5756	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6068	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6068A	JEDEC	L4004R5	S	TO-220 (N.ISOL)
2N6068B	JEDEC	L4004R3	S	TO-220 (N.ISOL)
2N6069	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6069A	JEDEC	L4004R5	S	TO-220 (N.ISOL)
2N6069B	JEDEC	L4004R3	S	TO-220 (N.ISOL)
2N6070	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6070A	JEDEC	L4004R5	S	TO-220 (N.ISOL)
2N6070B	JEDEC	L4004R3	S	TO-220 (N.ISOL)
2N6071	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6071A	JEDEC	L4004R5	S	TO-220 (N.ISOL)
2N6071B	JEDEC	L4004R3	S	TO-220 (N.ISOL)
2N6072	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6072A	JEDEC	L4004R5	S	TO-220 (N.ISOL)
2N6072B	JEDEC	L4004R3	S	TO-220 (N.ISOL)
2N6073	JEDEC	Q4004R4	S	TO-220 (N.ISOL)
2N6073A	JEDEC	L4004R5	S	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
2N6073B	JEDEC	L4004R3	S	TO-220 (N.ISOL)
2N6074	JEDEC	Q6004R4	S	TO-220 (N.ISOL)
2N6074A	JEDEC	L6004R5	S	TO-220 (N.ISOL)
2N6074B	JEDEC	L6004R3	S	TO-220 (N.ISOL)
2N6075	JEDEC	Q6004R4	S	TO-220 (N.ISOL)
2N6075A	JEDEC	L6004R5	S	TO-220 (N.ISOL)
2N6075B	JEDEC	L6004R3	S	TO-220 (N.ISOL)
2N6236	JEDEC	S4006LS2	S	TO-220 (ISOL)
2N6237	JEDEC	S4006LS2	S	TO-220 (ISOL)
2N6238	JEDEC	S4006LS2	S	TO-220 (ISOL)
2N6239	JEDEC	S4006LS2	S	TO-220 (ISOL)
2N6240	JEDEC	S4006LS2	S	TO-220 (ISOL)
2N6241	JEDEC	S6006LS2	S	TO-220 (ISOL)
2N6342	JEDEC	Q4008R4	S	TO-220 (N.ISOL)
2N6342A	JEDEC	Q4012RH5	S	TO-220 (N.ISOL)
2N6343	JEDEC	Q4008R4	S	TO-220 (N.ISOL)
2N6343A	JEDEC	Q4012RH5	S	TO-220 (N.ISOL)
2N6344	JEDEC	Q6008R5	S	TO-220 (N.ISOL)
2N6344A	JEDEC	Q6012RH5	S	TO-220 (N.ISOL)
2N6345	JEDEC	Q8008R5	S	TO-220 (N.ISOL)
2N6345A	JEDEC	Q8012RH5	S	TO-220 (N.ISOL)
2N6346A	JEDEC	Q4015R5	S	TO-220 (N.ISOL)
2N6347A	JEDEC	Q4015R5	S	TO-220 (N.ISOL)
2N6348A	JEDEC	Q6015R5	S	TO-220 (N.ISOL)
2N6349	JEDEC	Q8010R5	S	TO-220 (N.ISOL)
2N6349A	JEDEC	Q8015R5	S	TO-220 (N.ISOL)
2N6394	JEDEC	S4012R	D	TO-220 (N.ISOL)
2N6395	JEDEC	S4012R	D	TO-220 (N.ISOL)
2N6396	JEDEC	S4012R	D	TO-220 (N.ISOL)
2N6397	JEDEC	S4012R	D	TO-220 (N.ISOL)
2N6398	JEDEC	S6012R	D	TO-220 (N.ISOL)
2N6399	JEDEC	S8012R	D	TO-220 (N.ISOL)
2N6400	JEDEC	S4016R	D	TO-220 (N.ISOL)
2N6401	JEDEC	S4016R	D	TO-220 (N.ISOL)
2N6402	JEDEC	S4016R	D	TO-220 (N.ISOL)
2N6403	JEDEC	S4016R	D	TO-220 (N.ISOL)
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2N6405	JEDEC	S8016R	D	TO-220 (N.ISOL)
2N6504	JEDEC	S4025R	D	TO-220 (N.ISOL)
2N6505	JEDEC	S4025R	D	TO-220 (N.ISOL)
2N6506	JEDEC	S4025R	D	TO-220 (N.ISOL)
2N6507	JEDEC	S4025R	D	TO-220 (N.ISOL)
2N6508	JEDEC	S6025R	D	TO-220 (N.ISOL)
2N6509	JEDEC	S8025R	D	TO-220 (N.ISOL)
2N6564	JEDEC	2N6565	D	TO-92 (ISOL)
2N6565	JEDEC	EC103D	S	TO-92 (ISOL)
2N877	JEDEC	EC103D	S	TO-92 (ISOL)
2N878	JEDEC	EC103D	S	TO-92 (ISOL)
2N879	JEDEC	EC103D	S	TO-92 (ISOL)
2N880	JEDEC	EC103D	S	TO-92 (ISOL)
2N881	JEDEC	EC103D	S	TO-92 (ISOL)
2N885	JEDEC	2N6565	D	TO-92 (ISOL)
2N886	JEDEC	2N6565	D	TO-92 (ISOL)
2N887	JEDEC	2N6565	D	TO-92 (ISOL)
2N888	JEDEC	2N6565	D	TO-92 (ISOL)
2N889	JEDEC	2N6565	D	TO-92 (ISOL)
2P05M	NEC	S4006LS2	S	TO-220 (ISOL)
2P1M	NEC	S4006LS2	S	TO-220 (ISOL)
2P2M	NEC	S4006LS2	S	TO-220 (ISOL)
2P4M	NEC	S4006LS2	S	TO-220 (ISOL)
2P5M	NEC	S6006LS2	S	TO-220 (ISOL)
2P6M	NEC	S6006LS2	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
30TPS08	IR	S8035K	S	TO-218AC (ISOL) "K"
3P4J	NEC	S4004D2	S	TO-252 (SMT)
40TPS08	IR	S8035K	S	TO-218AC (ISOL) "K"
5P05M	NEC	S2008R	S	TO-220 (N.ISOL)
5P1M	NEC	S2008R	S	TO-220 (N.ISOL)
5P2M	NEC	S2008R	S	TO-220 (N.ISOL)
5P4M	NEC	S4008R	S	TO-220 (N.ISOL)
5P5M	NEC	S6008R	S	TO-220 (N.ISOL)
5P6M	NEC	S6008R	S	TO-220 (N.ISOL)
8T04HA	HUTSON	Q4004R4	D	TO-220 (N.ISOL)
8T04SH	HUTSON	L4004R8	S	TO-220 (N.ISOL)
8T14HA	HUTSON	Q4004R4	D	TO-220 (N.ISOL)
8T14SH	HUTSON	L4004R8	S	TO-220 (N.ISOL)
8T24HA	HUTSON	Q4004R4	D	TO-220 (N.ISOL)
8T24SH	HUTSON	L4004R8	S	TO-220 (N.ISOL)
8T34HA	HUTSON	Q4004R4	S	TO-220 (N.ISOL)
8T34SH	HUTSON	L4004R8	S	TO-220 (N.ISOL)
8T44HA	HUTSON	Q4004R4	S	TO-220 (N.ISOL)
8T44SH	HUTSON	L4004R8	S	TO-220 (N.ISOL)
8T54HA	HUTSON	Q6004R4	S	TO-220 (N.ISOL)
8T64HA	HUTSON	Q6004R4	S	TO-220 (N.ISOL)
8T64SH	HUTSON	L6004R8	S	TO-220 (N.ISOL)
AC03BGM	NEC	Q4004R4	S	TO-220 (N.ISOL)
AC03DGM	NEC	Q4004R4	S	TO-220 (N.ISOL)
AC03EGM	NEC	Q6004R4	S	TO-220 (N.ISOL)
AC03FGM	NEC	Q6004R4	S	TO-220 (N.ISOL)
AC08BGM	NEC	Q4008R4	S	TO-220 (N.ISOL)
AC08BSM	NEC	Q4008LH4	S	TO-220 (ISOL)
AC08DGM	NEC	Q4008R4	S	TO-220 (N.ISOL)
AC08DSM	NEC	Q4008LH4	S	TO-220 (ISOL)
AC08EGM	NEC	Q6008R5	S	TO-220 (N.ISOL)
AC08ESM	NEC	Q6008LH4	S	TO-220 (ISOL)
AC08FGM	NEC	Q6008R5	S	TO-220 (N.ISOL)
AC08FSM	NEC	Q6008LH4	S	TO-220 (ISOL)
AC08FSMA	NEC	Q6008LH4	S	TO-220 (ISOL)
AC10BGML	NEC	Q4010RH5	S	TO-220 (N.ISOL)
AC10BSM	NEC	Q4010LH5	S	TO-220 (ISOL)
AC10DGM	NEC	Q4010RH5	S	TO-220 (N.ISOL)
AC10DSM	NEC	Q4010LH5	S	TO-220 (ISOL)
AC10DSMA	NEC	Q4010LH5	S	TO-220 (ISOL)
AC10EGML	NEC	Q6010RH5	S	TO-220 (N.ISOL)
AC10ESM	NEC	Q6010LH5	S	TO-220 (ISOL)
AC10FGML	NEC	Q6010RH5	S	TO-220 (N.ISOL)
AC10FSM	NEC	Q6010LH5	S	TO-220 (ISOL)
AC10FSMA	NEC	Q6010LH5	S	TO-220 (ISOL)
AC12BGML	NEC	Q4012RH5	S	TO-220 (N.ISOL)
AC12BSM	NEC	Q4012LH5	S	TO-220 (ISOL)
AC12DGM	NEC	Q4012RH5	S	TO-220 (N.ISOL)
AC12DSM	NEC	Q4012LH5	S	TO-220 (ISOL)
AC12DSMA	NEC	Q4012LH2	S	TO-220 (ISOL)
AC12EGML	NEC	Q6012RH5	S	TO-220 (N.ISOL)
AC12ESM	NEC	Q6012LH5	S	TO-220 (ISOL)
AC12FGML	NEC	Q6012RH5	S	TO-220 (N.ISOL)
AC12FSM	NEC	Q6012LH5	S	TO-220 (ISOL)
AC12FSMA	NEC	Q6012LH2	S	TO-220 (ISOL)
AC16BGM	NEC	Q4015R5	S	TO-220 (N.ISOL)
AC16BSM	NEC	Q4015L5	S	TO-220 (ISOL)
AC16DGM	NEC	Q4015R5	S	TO-220 (N.ISOL)
AC16DSM	NEC	Q4015L5	S	TO-220 (ISOL)
AC16DSMA	NEC	Q4016LH4	S	TO-220 (ISOL)
AC16EGM	NEC	Q6015R5	S	TO-220 (N.ISOL)
AC16ESM	NEC	Q6015L5	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
AC16FGM	NEC	Q6015R5	S	TO-220 (N.ISOL)
AC16FSM	NEC	Q6015L5	S	TO-220 (ISOL)
AC16FSMA	NEC	Q6016LH4	S	TO-220 (ISOL)
AC25B1FL	NEC	Q6025P5	S	FASTPAK (ISOL)
AC25D1FL	NEC	Q6025P5	S	FASTPAK (ISOL)
AC25E1FL	NEC	Q6025P5	S	FASTPAK (ISOL)
AC25F1FL	NEC	Q6025P5	S	FASTPAK (ISOL)
BCR3AS-12	POWEREX	Q6006DH3	D	TO-252 (SMT)
BCR3AS-8	POWEREX	Q4006DH3	D	TO-252 (SMT)
BT131W-500	PHILIPS	L0103MT	S	SOT-223 (SMT)
BT131W-600	PHILIPS	L0103MT	S	SOT-223 (SMT)
BT136-500	PHILIPS	Q6004R4	S	TO-220 (N.ISOL)
BT136-500D	PHILIPS	L6004R6	S	TO-220 (N.ISOL)
BT136-500E	PHILIPS	L6004R8	S	TO-220 (N.ISOL)
BT136-500F	PHILIPS	Q6004R4	S	TO-220 (N.ISOL)
BT136-500G	PHILIPS	Q6004R4	S	TO-220 (N.ISOL)
BT136-600	PHILIPS	Q6004R4	S	TO-220 (N.ISOL)
BT136-600D	PHILIPS	L6004R6	S	TO-220 (N.ISOL)
BT136-600E	PHILIPS	L6004R8	S	TO-220 (N.ISOL)
BT136-600F	PHILIPS	Q6004R4	S	TO-220 (N.ISOL)
BT136-600G	PHILIPS	Q6004R4	S	TO-220 (N.ISOL)
BT136-800	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136-800F	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136-800G	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136F-500	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136F-500D	PHILIPS	L6004L6	S	TO-220 (ISOL)
BT136F-500E	PHILIPS	L6004L8	S	TO-220 (ISOL)
BT136F-500F	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136F-500G	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136F-600	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136F-600D	PHILIPS	L6004L6	S	TO-220 (ISOL)
BT136F-600E	PHILIPS	L6004L8	S	TO-220 (ISOL)
BT136F-600F	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136F-600G	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136F-800	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136F-800F	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136F-800G	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136S-600D	PHILIPS	L6004D6	S	TO-252 (SMT)
BT136S-600E	PHILIPS	L6004D8	S	TO-252 (SMT)
BT136S-600F	PHILIPS	L6004D8	S	TO-252 (SMT)
BT136X-500	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136X-500D	PHILIPS	L6004L6	S	TO-220 (ISOL)
BT136X-500E	PHILIPS	L6004L8	S	TO-220 (ISOL)
BT136X-500F	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136X-500G	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136X-600	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136X-600D	PHILIPS	L6004L6	S	TO-220 (ISOL)
BT136X-600E	PHILIPS	L6004L8	S	TO-220 (ISOL)
BT136X-600F	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136X-600G	PHILIPS	Q6004L4	S	TO-220 (ISOL)
BT136X-800	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136X-800F	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT136X-800G	PHILIPS	Q8004L4	S	TO-220 (ISOL)
BT137-500	PHILIPS	Q6008R5	S	TO-220 (N.ISOL)
BT137-500D	PHILIPS	L6008L6	S	TO-220 (ISOL)
BT137-500E	PHILIPS	L6008L8	S	TO-220 (ISOL)
BT137-500F	PHILIPS	Q6008R5	S	TO-220 (N.ISOL)
BT137-500G	PHILIPS	Q6008R5	S	TO-220 (N.ISOL)
BT137-600D	PHILIPS	L6008L6	S	TO-220 (ISOL)
BT137-600E	PHILIPS	L6008L8	S	TO-220 (ISOL)
BT137-600G	PHILIPS	Q6008R5	S	TO-220 (N.ISOL)
BT137-800G	PHILIPS	Q8008R5	S	TO-220 (N.ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BT137B-600	PHILIPS	Q6010N4	S	TO-263 (SMT)
BT137B-600F	PHILIPS	Q6010N4	S	TO-263 (SMT)
BT137F-500	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137F-500D	PHILIPS	L6008L6	S	TO-220 (ISOL)
BT137F-500E	PHILIPS	L6008L8	S	TO-220 (ISOL)
BT137F-500F	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137F-500G	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137F-600D	PHILIPS	L6008L6	S	TO-220 (ISOL)
BT137F-600E	PHILIPS	L6008L8	S	TO-220 (ISOL)
BT137F-600G	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137F-800G	PHILIPS	Q8008L5	S	TO-220 (ISOL)
BT137S-600D	PHILIPS	L6008D6	S	TO-252 (SMT)
BT137S-600E	PHILIPS	L6008D8	S	TO-252 (SMT)
BT137X-500	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137X-500D	PHILIPS	L6008L6	S	TO-220 (ISOL)
BT137X-500E	PHILIPS	L6008L8	S	TO-220 (ISOL)
BT137X-500F	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137X-500G	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137X-600D	PHILIPS	L6008L6	S	TO-220 (ISOL)
BT137X-600E	PHILIPS	L6008L8	S	TO-220 (ISOL)
BT137X-600G	PHILIPS	Q6008L5	S	TO-220 (ISOL)
BT137X-800G	PHILIPS	Q8008L5	S	TO-220 (ISOL)
BT138-500G	PHILIPS	Q6015R5	S	TO-220 (N.ISOL)
BT138-600G	PHILIPS	Q6015R5	S	TO-220 (N.ISOL)
BT138-800G	PHILIPS	Q8015R5	S	TO-220 (N.ISOL)
BT138F-500G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT138F-600G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT138F-800G	PHILIPS	Q8015L5	S	TO-220 (ISOL)
BT138X-500G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT138X-600G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT138X-800G	PHILIPS	Q8015L5	S	TO-220 (ISOL)
BT139-500G	PHILIPS	Q6015R5	S	TO-220 (N.ISOL)
BT139-600G	PHILIPS	Q6015R5	S	TO-220 (N.ISOL)
BT139-800G	PHILIPS	Q8015R5	S	TO-220 (N.ISOL)
BT139F-500G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT139F-600	PHILIPS	Q6016LH4	S	TO-220 (ISOL)
BT139F-600G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT139F-800G	PHILIPS	Q8015L5	S	TO-220 (ISOL)
BT139X-500G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT139X-500H	PHILIPS	Q6016LH6	S	TO-220 (ISOL)
BT139X-600G	PHILIPS	Q6015L5	S	TO-220 (ISOL)
BT139X-600H	PHILIPS	Q6016LH6	S	TO-220 (ISOL)
BT139X-800G	PHILIPS	Q8015L5	S	TO-220 (ISOL)
BT139X-800H	PHILIPS	Q8016LH6	S	TO-220 (ISOL)
BT145-500R	PHILIPS	S6025R	S	TO-220 (N.ISOL)
BT145-600R	PHILIPS	S6025R	S	TO-220 (N.ISOL)
BT145-800R	PHILIPS	S8025R	S	TO-220 (N.ISOL)
BT148W-400R	PHILIPS	S4X8TS	S	SOT-223 (SMT)
BT148W-600R	PHILIPS	S6X8TS	S	SOT-223 (SMT)
BT149B	PHILIPS	S4X8ES	S	TO-92 (ISOL)
BT149D	PHILIPS	S4X8ES	S	TO-92 (ISOL)
BT149E	PHILIPS	S6X8ES	S	TO-92 (ISOL)
BT149G	PHILIPS	S6X8ES	S	TO-92 (ISOL)
BT150-500R	PHILIPS	S6006LS2	S	TO-220 (ISOL)
BT150-600R	PHILIPS	S6006LS2	S	TO-220 (ISOL)
BT150S-600R	PHILIPS	S6004DS2	S	TO-252 (SMT)
BT151-500R	PHILIPS	S6010R	S	TO-220 (N.ISOL)
BT151-650R	PHILIPS	S8010R	S	TO-220 (N.ISOL)
BT151-800R	PHILIPS	S8010R	S	TO-220 (N.ISOL)
BT151S-500R	PHILIPS	S6012D	S	TO-252 (SMT)
BT151S-650R	PHILIPS	S8012D	S	TO-252 (SMT)
BT151X-500	PHILIPS	S6010L	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BT151X-650	PHILIPS	S8010L	S	TO-220 (ISOL)
BT151X-800	PHILIPS	S8010L	S	TO-220 (ISOL)
BT152-400R	PHILIPS	S4020L	S	TO-220 (ISOL)
BT152-600R	PHILIPS	S6020L	S	TO-220 (ISOL)
BT152-800R	PHILIPS	S8020L	S	TO-220 (ISOL)
BT152B-400R	PHILIPS	S4025N	S	TO-263 (SMT)
BT152B-600R	PHILIPS	S6025N	S	TO-263 (SMT)
BT152B-800R	PHILIPS	S8025N	S	TO-263 (SMT)
BT152X-400R	PHILIPS	S4020L	D	TO-220 (ISOL)
BT152X-600R	PHILIPS	S6020L	D	TO-220 (ISOL)
BT152X-800R	PHILIPS	S8020L	D	TO-220 (ISOL)
BT168B	PHILIPS	S4X8ES	S	TO-92 (ISOL)
BT168D	PHILIPS	S4X8ES	S	TO-92 (ISOL)
BT168E	PHILIPS	S6X8ES	S	TO-92 (ISOL)
BT168G	PHILIPS	S6X8ES	S	TO-92 (ISOL)
BT169B	PHILIPS	S4X8ES	D	TO-92 (ISOL)
BT169D	PHILIPS	S4X8ES	D	TO-92 (ISOL)
BT169E	PHILIPS	S6X8ES	D	TO-92 (ISOL)
BT169G	PHILIPS	S6X8ES	D	TO-92 (ISOL)
BT300-500R	PHILIPS	S6008R	S	TO-220 (N.ISOL)
BT300-600R	PHILIPS	S6008R	S	TO-220 (N.ISOL)
BT300-800R	PHILIPS	S8008R	S	TO-220 (N.ISOL)
BT300S-600R	PHILIPS	S6008D	D	TO-252 (SMT)
BTA04-200A	STMicro	L4004L8	D	TO-220 (ISOL)
BTA04-200D	STMicro	L4004L6	D	TO-220 (ISOL)
BTA04-200GP	STMicro	L4004L6	S	TO-220 (ISOL)
BTA04-200S	STMicro	L4004L6	D	TO-220 (ISOL)
BTA04-200T	STMicro	L4004L5	D	TO-220 (ISOL)
BTA04-400A	STMicro	L4004L8	D	TO-220 (ISOL)
BTA04-400D	STMicro	L4004L6	D	TO-220 (ISOL)
BTA04-400GP	STMicro	L4004L6	S	TO-220 (ISOL)
BTA04-400S	STMicro	L4004L6	D	TO-220 (ISOL)
BTA04-400T	STMicro	L4004L5	D	TO-220 (ISOL)
BTA04-600A	STMicro	L6004L8	D	TO-220 (ISOL)
BTA04-600D	STMicro	L6004L6	D	TO-220 (ISOL)
BTA04-600GP	STMicro	L6004L6	S	TO-220 (ISOL)
BTA04-600S	STMicro	L6004L6	D	TO-220 (ISOL)
BTA04-600T	STMicro	L6004L5	D	TO-220 (ISOL)
BTA06-200A	STMicro	L4006L8	D	TO-220 (ISOL)
BTA06-200B	STMicro	Q4006L4	S	TO-220 (ISOL)
BTA06-200C	STMicro	Q4006L4	S	TO-220 (ISOL)
BTA06-200D	STMicro	L4006L6	D	TO-220 (ISOL)
BTA06-200GP	STMicro	L4006L6	S	TO-220 (ISOL)
BTA06-200S	STMicro	L4006L6	D	TO-220 (ISOL)
BTA06-200SW	STMicro	L4006L8	D	TO-220 (ISOL)
BTA06-200T	STMicro	L4006L5	S	TO-220 (ISOL)
BTA06-200TV	STMicro	L4006L6	D	TO-220 (ISOL)
BTA06-400A	STMicro	L4006L8	D	TO-220 (ISOL)
BTA06-400B	STMicro	Q4006L4	S	TO-220 (ISOL)
BTA06-400BV	STMicro	Q4006LH4	S	TO-220 (ISOL)
BTA06-400C	STMicro	Q4006L4	S	TO-220 (ISOL)
BTA06-400CW	STMicro	Q4006LH4	D	TO-220 (ISOL)
BTA06-400D	STMicro	L4006L6	D	TO-220 (ISOL)
BTA06-400GP	STMicro	L4006L6	S	TO-220 (ISOL)
BTA06-400S	STMicro	L4006L6	D	TO-220 (ISOL)
BTA06-400SV	STMicro	L4006L8	D	TO-220 (ISOL)
BTA06-400T	STMicro	L4006L5	S	TO-220 (ISOL)
BTA06-400TV	STMicro	L4006L6	D	TO-220 (ISOL)
BTA06-600A	STMicro	L6006L8	D	TO-220 (ISOL)
BTA06-600B	STMicro	Q6006L5	S	TO-220 (ISOL)
BTA06-600BW	STMicro	Q6006LH4	S	TO-220 (ISOL)
BTA06-600C	STMicro	Q6006L5	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTA06-600CW	STMicro	Q6006LH4	S	TO-220 (ISOL)
BTA06-600D	STMicro	L6006L6	D	TO-220 (ISOL)
BTA06-600GP	STMicro	L6006L6	S	TO-220 (ISOL)
BTA06-600S	STMicro	L6006L6	D	TO-220 (ISOL)
BTA06-600SW	STMicro	L6006L8	D	TO-220 (ISOL)
BTA06-600T	STMicro	L6006L5	S	TO-220 (ISOL)
BTA06-600TW	STMicro	L6006L6	D	TO-220 (ISOL)
BTA06-700B	STMicro	Q8006L5	S	TO-220 (ISOL)
BTA06-700BW	STMicro	Q8006LH4	S	TO-220 (ISOL)
BTA06-700C	STMicro	Q8006L5	D	TO-220 (ISOL)
BTA06-700CW	STMicro	Q8006LH4	D	TO-220 (ISOL)
BTA06-800B	STMicro	Q8006L5	S	TO-220 (ISOL)
BTA06-800BW	STMicro	Q8006LH4	S	TO-220 (ISOL)
BTA06-800C	STMicro	Q8006L5	S	TO-220 (ISOL)
BTA06-800CW	STMicro	Q8006LH4	D	TO-220 (ISOL)
BTA08-200A	STMicro	L4008L8	D	TO-220 (ISOL)
BTA08-200B	STMicro	Q4008L4	S	TO-220 (ISOL)
BTA08-200C	STMicro	Q4008L4	S	TO-220 (ISOL)
BTA08-200S	STMicro	L4008L6	D	TO-220 (ISOL)
BTA08-200SW	STMicro	L4008L8	D	TO-220 (ISOL)
BTA08-200TW	STMicro	L4008L6	D	TO-220 (ISOL)
BTA08-400A	STMicro	L4008L8	D	TO-220 (ISOL)
BTA08-400B	STMicro	Q4008L4	S	TO-220 (ISOL)
BTA08-400BW	STMicro	Q4008LH4	S	TO-220 (ISOL)
BTA08-400C	STMicro	Q4008L4	S	TO-220 (ISOL)
BTA08-400CW	STMicro	Q4008LH4	D	TO-220 (ISOL)
BTA08-400S	STMicro	L4008L6	D	TO-220 (ISOL)
BTA08-400SW	STMicro	L4008L8	D	TO-220 (ISOL)
BTA08-400TW	STMicro	L4008L6	D	TO-220 (ISOL)
BTA08-600A	STMicro	L6008L8	D	TO-220 (ISOL)
BTA08-600B	STMicro	Q6008L5	S	TO-220 (ISOL)
BTA08-600BW	STMicro	Q6008LH4	S	TO-220 (ISOL)
BTA08-600C	STMicro	Q6008L5	S	TO-220 (ISOL)
BTA08-600CW	STMicro	Q6008LH4	D	TO-220 (ISOL)
BTA08-600S	STMicro	L6008L6	D	TO-220 (ISOL)
BTA08-600SW	STMicro	L6008L8	D	TO-220 (ISOL)
BTA08-600TW	STMicro	L6008L6	D	TO-220 (ISOL)
BTA08-700B	STMicro	Q8008L5	S	TO-220 (ISOL)
BTA08-700BW	STMicro	Q8008LH4	S	TO-220 (ISOL)
BTA08-700C	STMicro	Q8008L5	S	TO-220 (ISOL)
BTA08-700CW	STMicro	Q8008LH4	D	TO-220 (ISOL)
BTA08-800B	STMicro	Q8008L5	S	TO-220 (ISOL)
BTA08-800BW	STMicro	Q8008LH4	S	TO-220 (ISOL)
BTA08-800C	STMicro	Q8008L5	S	TO-220 (ISOL)
BTA08-800CW	STMicro	Q8008LH4	D	TO-220 (ISOL)
BTA10-200AW	STMicro	Q4010L5	S	TO-220 (ISOL)
BTA10-200B	STMicro	Q4010L5	S	TO-220 (ISOL)
BTA10-200BW	STMicro	Q4010LH5	D	TO-220 (ISOL)
BTA10-200C	STMicro	Q4010L5	S	TO-220 (ISOL)
BTA10-200CW	STMicro	Q4010LH5	S	TO-220 (ISOL)
BTA10-400AW	STMicro	Q4010L5	S	TO-220 (ISOL)
BTA10-400B	STMicro	Q4010L5	S	TO-220 (ISOL)
BTA10-400BW	STMicro	Q4010LH5	D	TO-220 (ISOL)
BTA10-400C	STMicro	Q4010L5	S	TO-220 (ISOL)
BTA10-400CW	STMicro	Q4010LH5	S	TO-220 (ISOL)
BTA10-400GP	STMicro	Q4010L4	S	TO-220 (ISOL)
BTA10-600AW	STMicro	Q6010L5	S	TO-220 (ISOL)
BTA10-600B	STMicro	Q6010L5	S	TO-220 (ISOL)
BTA10-600BW	STMicro	Q6010LH5	D	TO-220 (ISOL)
BTA10-600C	STMicro	Q6010L5	S	TO-220 (ISOL)
BTA10-600CW	STMicro	Q6010LH5	S	TO-220 (ISOL)
BTA10-600GP	STMicro	Q6010L4	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTA10-700AV	STMicro	Q8010L5	S	TO-220 (ISOL)
BTA10-700B	STMicro	Q8010L5	S	TO-220 (ISOL)
BTA10-700BW	STMicro	Q8010LH5	D	TO-220 (ISOL)
BTA10-700C	STMicro	Q8010L5	S	TO-220 (ISOL)
BTA10-700CW	STMicro	Q8010LH5	S	TO-220 (ISOL)
BTA10-800B	STMicro	Q8010L5	S	TO-220 (ISOL)
BTA10-800BW	STMicro	Q8010LH5	D	TO-220 (ISOL)
BTA10-800C	STMicro	Q8010L5	S	TO-220 (ISOL)
BTA10-800CW	STMicro	Q8010LH5	S	TO-220 (ISOL)
BTA12-200AV	STMicro	Q4012LH5	D	TO-220 (ISOL)
BTA12-200B	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA12-200BW	STMicro	Q4012LH5	D	TO-220 (ISOL)
BTA12-200C	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA12-400AV	STMicro	Q4012LH5	D	TO-220 (ISOL)
BTA12-400B	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA12-400BW	STMicro	Q4012LH5	D	TO-220 (ISOL)
BTA12-400C	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA12-600AV	STMicro	Q6012LH5	D	TO-220 (ISOL)
BTA12-600B	STMicro	Q6015L5	S	TO-220 (ISOL)
BTA12-600BW	STMicro	Q6012LH5	D	TO-220 (ISOL)
BTA12-600C	STMicro	Q6015L5	S	TO-220 (ISOL)
BTA12-600CW	STMicro	Q6012LH5	S	TO-220 (ISOL)
BTA12-700AV	STMicro	Q8012LH5	D	TO-220 (ISOL)
BTA12-700B	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA12-700BW	STMicro	Q8012LH5	D	TO-220 (ISOL)
BTA12-700C	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA12-700CW	STMicro	Q8012LH5	S	TO-220 (ISOL)
BTA12-800B	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA12-800BW	STMicro	Q8012LH5	S	TO-220 (ISOL)
BTA12-800C	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA12-800CW	STMicro	Q8012LH5	S	TO-220 (ISOL)
BTA13-200B	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA13-400B	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA13-600B	STMicro	Q6015L5	S	TO-220 (ISOL)
BTA13-700B	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA13-800B	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA140-500	STMicro	Q6025R5	S	TO-220 (N.ISOL)
BTA140-600	STMicro	Q6025R5	S	TO-220 (N.ISOL)
BTA140-800	STMicro	Q8025R5	S	TO-220 (N.ISOL)
BTA16-200AV	STMicro	Q4016LH6	S	TO-220 (ISOL)
BTA16-200B	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA16-200BW	STMicro	Q4016LH4	S	TO-220 (ISOL)
BTA16-400AV	STMicro	Q4016LH6	S	TO-220 (ISOL)
BTA16-400B	STMicro	Q4015L5	S	TO-220 (ISOL)
BTA16-400BW	STMicro	Q4016LH4	S	TO-220 (ISOL)
BTA16-400CW	STMicro	Q4016LH4	S	TO-220 (ISOL)
BTA16-600AV	STMicro	Q6016LH6	S	TO-220 (ISOL)
BTA16-600B	STMicro	Q6015L5	S	TO-220 (ISOL)
BTA16-600BW	STMicro	Q6016LH4	S	TO-220 (ISOL)
BTA16-600CW	STMicro	Q6016LH4	S	TO-220 (ISOL)
BTA16-700AV	STMicro	Q8016LH6	S	TO-220 (ISOL)
BTA16-700B	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA16-700BW	STMicro	Q8016LH4	S	TO-220 (ISOL)
BTA16-700CW	STMicro	Q8016LH4	S	TO-220 (ISOL)
BTA16-800AV	STMicro	Q8016LH6	S	TO-220 (ISOL)
BTA16-800B	STMicro	Q8015L5	S	TO-220 (ISOL)
BTA16-800BW	STMicro	Q8016LH4	S	TO-220 (ISOL)
BTA16-800CW	STMicro	Q8016LH4	S	TO-220 (ISOL)
BTA20-400BW	STMicro	Q4025L6	S	TO-220 (ISOL)
BTA20-400CW	STMicro	Q4025L6	S	TO-220 (ISOL)
BTA204S-600C	STMicro	Q6006DH4	D	TO-252 (SMT)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTA204S-600E	STMicro	Q6006DH3	D	TO-252 (SMT)
BTA20-600BW	STMicro	Q6025L6	S	TO-220 (ISOL)
BTA20-600CW	STMicro	Q6025L6	S	TO-220 (ISOL)
BTA20-700BW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA20-700CW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA20-800BW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA20-800CW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA208-600B	STMicro	Q6008RH4	S	TO-220 (N.ISOL)
BTA208-800B	STMicro	Q8008RH4	S	TO-220 (N.ISOL)
BTA208S-600E	STMicro	Q6008DH3	D	TO-252 (SMT)
BTA208S-800C	STMicro	Q8008DH4	D	TO-252 (SMT)
BTA208X-600B	STMicro	Q6008LH4	S	TO-220 (ISOL)
BTA208X-800B	STMicro	Q8008LH4	S	TO-220 (ISOL)
BTA20C	STMicro	Q4006R4	D	TO-220 (N.ISOL)
BTA20D	STMicro	Q4006R4	D	TO-220 (N.ISOL)
BTA20E	STMicro	Q6006R5	S	TO-220 (N.ISOL)
BTA20M	STMicro	Q6006R5	D	TO-220 (N.ISOL)
BTA20N	STMicro	Q8006R5	D	TO-220 (N.ISOL)
BTA212-600B	STMicro	Q6012RH5	S	TO-220 (N.ISOL)
BTA212-800B	STMicro	Q8012RH5	S	TO-220 (N.ISOL)
BTA212B-600B	STMicro	Q6012NH5	D	TO-263 (SMT)
BTA212B-800B	STMicro	Q8012NH5	D	TO-263 (SMT)
BTA212X-600B	STMicro	Q6012LH5	S	TO-220 (ISOL)
BTA212X-800B	STMicro	Q8012LH5	S	TO-220 (ISOL)
BTA216-600B	STMicro	Q6016LH6	S	TO-220 (N.ISOL)
BTA216-800B	STMicro	Q8016LH6	S	TO-220 (N.ISOL)
BTA216B-600	STMicro	Q6016NH4	S	TO-263 (SMT)
BTA216X-600B	STMicro	Q6016LH6	S	TO-220 (ISOL)
BTA216X-800B	STMicro	Q8016LH6	S	TO-220 (ISOL)
BTA21C	STMicro	Q4008R4	D	TO-220 (N.ISOL)
BTA21D	STMicro	Q4008R4	D	TO-220 (N.ISOL)
BTA21E	STMicro	Q6008R5	S	TO-220 (N.ISOL)
BTA21M	STMicro	Q6008R5	S	TO-220 (N.ISOL)
BTA21N	STMicro	Q8008R5	S	TO-220 (N.ISOL)
BTA225-600B	STMicro	Q6025R6	S	TO-220 (N.ISOL)
BTA225-800B	STMicro	Q8025R6	S	TO-220 (N.ISOL)
BTA225B-600B	STMicro	Q6025NH6	S	TO-263 (SMT)
BTA225B-800B	STMicro	Q8025NH6	S	TO-263 (SMT)
BTA22B	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTA22C	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTA22D	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTA22E	STMicro	Q6010R5	S	TO-220 (N.ISOL)
BTA22M	STMicro	Q6010R5	S	TO-220 (N.ISOL)
BTA23B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTA23C	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTA23D	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTA23E	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTA23M	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTA24-600BW	STMicro	Q6025L6	S	TO-220 (ISOL)
BTA24-600CW	STMicro	Q6025L6	S	TO-220 (ISOL)
BTA24-700BW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA24-700CW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA24-800BW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA24-800CW	STMicro	Q8025L6	S	TO-220 (ISOL)
BTA25-200A	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-200B	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-400A	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-400B	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-600A	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-600B	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-600BW	STMicro	Q6025P5	S	FASTPAK (ISOL)
BTA25-600CW	STMicro	Q6025P5	S	FASTPAK (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTA25-700A	STMicro	Q8025P5	S	FASTPAK (ISOL)
BTA25-700B	STMicro	Q8025P5	S	FASTPAK (ISOL)
BTA25-800A	STMicro	Q8025P5	S	FASTPAK (ISOL)
BTA25-800B	STMicro	Q8025P5	S	FASTPAK (ISOL)
BTA25-800BW	STMicro	Q8025P5	S	FASTPAK (ISOL)
BTA25-800CW	STMicro	Q8025P5	S	FASTPAK (ISOL)
BTA26-200A	STMicro	Q4025K6	S	TO-218 (ISOL)
BTA26-200B	STMicro	Q4025K6	S	TO-218 (ISOL)
BTA26-400A	STMicro	Q4025K6	S	TO-218 (ISOL)
BTA26-400B	STMicro	Q4025K6	S	TO-218 (ISOL)
BTA26-400BW	STMicro	Q4025K6	S	TO-218 (ISOL)
BTA26-400CW	STMicro	Q4025K6	S	TO-218 (ISOL)
BTA26-600A	STMicro	Q6025K6	S	TO-218 (ISOL)
BTA26-600B	STMicro	Q6025K6	S	TO-218 (ISOL)
BTA26-600BW	STMicro	Q6025K6	S	TO-218 (ISOL)
BTA26-600CW	STMicro	Q6025K6	S	TO-218 (ISOL)
BTA26-700A	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-700B	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-700BW	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-700CW	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-800A	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-800B	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-800BW	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA26-800CW	STMicro	Q8025K6	S	TO-218 (ISOL)
BTA40-200A	STMicro	Q6035P5	S	FASTPAK (ISOL)
BTA40-200B	STMicro	Q6035P5	S	FASTPAK (ISOL)
BTA40-400A	STMicro	Q6035P5	S	FASTPAK (ISOL)
BTA40-400B	STMicro	Q6035P5	S	FASTPAK (ISOL)
BTA40-600A	STMicro	Q6035P5	S	FASTPAK (ISOL)
BTA40-600B	STMicro	Q6035P5	S	FASTPAK (ISOL)
BTA40-700A	STMicro	Q8035P5	S	FASTPAK (ISOL)
BTA40-700B	STMicro	Q8035P5	S	FASTPAK (ISOL)
BTA41-200A	STMicro	Q4040K7	S	TO-218 (ISOL)
BTA41-200B	STMicro	Q4040K7	S	TO-218 (ISOL)
BTA41-400A	STMicro	Q4040K7	S	TO-218 (ISOL)
BTA41-400B	STMicro	Q4040K7	S	TO-218 (ISOL)
BTA41-600A	STMicro	Q6040K7	S	TO-218 (ISOL)
BTA41-600B	STMicro	Q6040K7	S	TO-218 (ISOL)
BTA41-700A	STMicro	Q8040K7	S	TO-218 (ISOL)
BTA41-700B	STMicro	Q8040K7	S	TO-218 (ISOL)
BTA41-800A	STMicro	Q8040K7	S	TO-218 (ISOL)
BTA41-800B	STMicro	Q8040K7	S	TO-218 (ISOL)
BTB04-200A	STMicro	L4004R8	S	TO-220 (N.ISOL)
BTB04-200D	STMicro	L4004R6	S	TO-220 (N.ISOL)
BTB04-200S	STMicro	L4004R6	S	TO-220 (N.ISOL)
BTB04-200T	STMicro	L4004R5	S	TO-220 (N.ISOL)
BTB04-400A	STMicro	L4004R8	S	TO-220 (N.ISOL)
BTB04-400D	STMicro	L4004R6	S	TO-220 (N.ISOL)
BTB04-400S	STMicro	L4004R6	S	TO-220 (N.ISOL)
BTB04-400T	STMicro	L4004R5	S	TO-220 (N.ISOL)
BTB04-600A	STMicro	L6004R8	S	TO-220 (N.ISOL)
BTB04-600D	STMicro	L6004R6	S	TO-220 (N.ISOL)
BTB04-600S	STMicro	L6004R6	S	TO-220 (N.ISOL)
BTB04-600T	STMicro	L6004R51	S	TO-220 (N.ISOL)
BTB06-200A	STMicro	L4006R8	S	TO-220 (N.ISOL)
BTB06-200B	STMicro	Q4006R4	S	TO-220 (N.ISOL)
BTB06-200C	STMicro	Q4006R4	S	TO-220 (N.ISOL)
BTB06-200D	STMicro	L4006R6	S	TO-220 (N.ISOL)
BTB06-200S	STMicro	L4006R6	S	TO-220 (N.ISOL)
BTB06-200T	STMicro	L4006R5	S	TO-220 (N.ISOL)
BTB06-400A	STMicro	L4006R8	S	TO-220 (N.ISOL)
BTB06-400B	STMicro	Q4006R4	S	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTB06-400BW	STMicro	Q4006RH4	S	TO-220 (N.ISOL)
BTB06-400C	STMicro	Q4006R4	S	TO-220 (N.ISOL)
BTB06-400CW	STMicro	Q4006RH4	S	TO-220 (N.ISOL)
BTB06-400D	STMicro	L4006R6	S	TO-220 (N.ISOL)
BTB06-400S	STMicro	L4006R6	S	TO-220 (N.ISOL)
BTB06-400T	STMicro	L4006R5	S	TO-220 (N.ISOL)
BTB06-600A	STMicro	L6006R8	S	TO-220 (N.ISOL)
BTB06-600B	STMicro	Q6006R5	S	TO-220 (N.ISOL)
BTB06-600BW	STMicro	Q6006RH4	S	TO-220 (N.ISOL)
BTB06-600C	STMicro	Q6006R5	S	TO-220 (N.ISOL)
BTB06-600CW	STMicro	Q6006RH4	S	TO-220 (N.ISOL)
BTB06-600D	STMicro	L6006N6	S	TO-220 (N.ISOL)
BTB06-600S	STMicro	L6006R6	S	TO-220 (N.ISOL)
BTB06-600T	STMicro	L6006R5	S	TO-220 (N.ISOL)
BTB06-700B	STMicro	Q8006R5	S	TO-220 (N.ISOL)
BTB06-700BW	STMicro	Q8006RH4	S	TO-220 (N.ISOL)
BTB06-700C	STMicro	Q8006R5	S	TO-220 (N.ISOL)
BTB06-700CW	STMicro	Q8006RH4	S	TO-220 (N.ISOL)
BTB06-800B	STMicro	Q8006R5	S	TO-220 (N.ISOL)
BTB06-800BW	STMicro	Q8006RH4	S	TO-220 (N.ISOL)
BTB06-800C	STMicro	Q8006R5	S	TO-220 (N.ISOL)
BTB06-800CW	STMicro	Q8006RH4	S	TO-220 (N.ISOL)
BTB08-200A	STMicro	L4008R8	S	TO-220 (N.ISOL)
BTB08-200B	STMicro	Q4008R4	S	TO-220 (N.ISOL)
BTB08-200C	STMicro	Q4008R4	S	TO-220 (N.ISOL)
BTB08-200S	STMicro	L4008R6	S	TO-220 (N.ISOL)
BTB08-400A	STMicro	L4008R8	S	TO-220 (N.ISOL)
BTB08-400B	STMicro	Q4008R4	S	TO-220 (N.ISOL)
BTB08-400BW	STMicro	Q4008RH4	S	TO-220 (N.ISOL)
BTB08-400C	STMicro	Q4008R4	S	TO-220 (N.ISOL)
BTB08-400CW	STMicro	Q4008RH4	S	TO-220 (N.ISOL)
BTB08-400S	STMicro	L4008R6	S	TO-220 (N.ISOL)
BTB08-600A	STMicro	L6008R8	S	TO-220 (N.ISOL)
BTB08-600B	STMicro	Q6008R5	S	TO-220 (N.ISOL)
BTB08-600BW	STMicro	Q6008RH4	S	TO-220 (N.ISOL)
BTB08-600C	STMicro	Q6008R5	S	TO-220 (N.ISOL)
BTB08-600CW	STMicro	Q6008RH4	S	TO-220 (N.ISOL)
BTB08-600S	STMicro	L6008R6	S	TO-220 (N.ISOL)
BTB08-700B	STMicro	Q8008R5	S	TO-220 (N.ISOL)
BTB08-700BW	STMicro	Q8008RH4	S	TO-220 (N.ISOL)
BTB08-700C	STMicro	Q8008R5	S	TO-220 (N.ISOL)
BTB08-700CW	STMicro	Q8008RH4	S	TO-220 (N.ISOL)
BTB08-800B	STMicro	Q8008R5	S	TO-220 (N.ISOL)
BTB08-800BW	STMicro	Q8008RH4	S	TO-220 (N.ISOL)
BTB08-800C	STMicro	Q8008R5	S	TO-220 (N.ISOL)
BTB08-800CW	STMicro	Q8008RH4	S	TO-220 (N.ISOL)
BTB10-200B	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTB10-200C	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTB10-400B	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTB10-400BW	STMicro	Q4010RH5	S	TO-220 (N.ISOL)
BTB10-400C	STMicro	Q4010R5	S	TO-220 (N.ISOL)
BTB10-400CW	STMicro	Q4010RH5	S	TO-220 (N.ISOL)
BTB10-600B	STMicro	Q6010R5	S	TO-220 (N.ISOL)
BTB10-600BW	STMicro	Q6010RH5	S	TO-220 (N.ISOL)
BTB10-600C	STMicro	Q6010R5	S	TO-220 (N.ISOL)
BTB10-600CW	STMicro	Q6010RH5	S	TO-220 (N.ISOL)
BTB10-700B	STMicro	Q8010R5	S	TO-220 (N.ISOL)
BTB10-700BW	STMicro	Q8010RH5	S	TO-220 (N.ISOL)
BTB10-700C	STMicro	Q8010R5	S	TO-220 (N.ISOL)
BTB10-700CW	STMicro	Q8010RH5	S	TO-220 (N.ISOL)
BTB10-800B	STMicro	Q8010R5	S	TO-220 (N.ISOL)
BTB10-800BW	STMicro	Q8010RH5	S	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTB10-800C	STMicro	Q8010R5	S	TO-220 (N.ISOL)
BTB10-800CW	STMicro	Q8010RH5	S	TO-220 (N.ISOL)
BTB12-200B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB12-200C	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB12-400B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB12-400BW	STMicro	Q4012RH5	S	TO-220 (N.ISOL)
BTB12-400C	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB12-400CW	STMicro	Q4012RH5	S	TO-220 (N.ISOL)
BTB12-400SW	STMicro	Q4012RH2	S	TO-220 (N.ISOL)
BTB12-600B	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTB12-600BW	STMicro	Q6012RH5	S	TO-220 (N.ISOL)
BTB12-600C	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTB12-600CW	STMicro	Q6012RH5	S	TO-220 (N.ISOL)
BTB12-600SW	STMicro	Q6012RH2	S	TO-220 (N.ISOL)
BTB12-700B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB12-700BW	STMicro	Q8012RH5	S	TO-220 (N.ISOL)
BTB12-700C	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB12-700CW	STMicro	Q8012RH5	S	TO-220 (N.ISOL)
BTB12-700SW	STMicro	Q8012RH2	S	TO-220 (N.ISOL)
BTB12-800B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB12-800BW	STMicro	Q8012RH5	S	TO-220 (N.ISOL)
BTB12-800C	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB12-800CW	STMicro	Q8012RH5	S	TO-220 (N.ISOL)
BTB13-200B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB13-400B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB13-600B	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTB13-700B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB13-800B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB15-200B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB15-400B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB15-600B	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTB15-700B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB16-200B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB16-400B	STMicro	Q4015R5	S	TO-220 (N.ISOL)
BTB16-400CW	STMicro	Q4016RH4	S	TO-220 (N.ISOL)
BTB16-600B	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTB16-600BW	STMicro	Q6016RH6	S	TO-220 (N.ISOL)
BTB16-600C	STMicro	Q6015R5	S	TO-220 (N.ISOL)
BTB16-600CW	STMicro	Q6016RH4	S	TO-220 (N.ISOL)
BTB16-700B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB16-700BW	STMicro	Q8016RH6	S	TO-220 (N.ISOL)
BTB16-700C	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB16-700CW	STMicro	Q8016RH4	S	TO-220 (N.ISOL)
BTB16-800B	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB16-800BW	STMicro	Q8016RH6	S	TO-220 (N.ISOL)
BTB16-800C	STMicro	Q8015R5	S	TO-220 (N.ISOL)
BTB16-800CW	STMicro	Q8016RH4	S	TO-220 (N.ISOL)
BTB19-200B	STMicro	Q4025R5	S	TO-220 (N.ISOL)
BTB19-400B	STMicro	Q4025R5	S	TO-220 (N.ISOL)
BTB19-600B	STMicro	Q6025R5	S	TO-220 (N.ISOL)
BTB19-700B	STMicro	Q8025R5	S	TO-220 (N.ISOL)
BTB20-400BW	STMicro	Q4025R6	S	TO-220 (N.ISOL)
BTB20-400CW	STMicro	Q4025R6	S	TO-220 (N.ISOL)
BTB20-600BW	STMicro	Q6025R6	S	TO-220 (N.ISOL)
BTB20-600CW	STMicro	Q6025R6	S	TO-220 (N.ISOL)
BTB20-700BW	STMicro	Q8025R6	S	TO-220 (N.ISOL)
BTB20-700CW	STMicro	Q8025R6	S	TO-220 (N.ISOL)
BTB20-800BW	STMicro	Q8025R6	S	TO-220 (N.ISOL)
BTB20-800CW	STMicro	Q8025R6	S	TO-220 (N.ISOL)
BTB24-200B	STMicro	Q4025R5	S	TO-220 (N.ISOL)
BTB24-400B	STMicro	Q4025R5	S	TO-220 (N.ISOL)
BTB24-600B	STMicro	Q6025R5	S	TO-220 (N.ISOL)

Teccor® brand Thyristors

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Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
BTB24-600BW	STMicro	Q6025R6	S	TO-220 (N.ISOL)
BTB24-700B	STMicro	Q8025R5	S	TO-220 (N.ISOL)
BTB24-800B	STMicro	Q8025R5	S	TO-220 (N.ISOL)
BTB26-200A	STMicro	Q4025K6	S	TO-218 (ISOL)
BTB26-200B	STMicro	Q4025K6	S	TO-218 (ISOL)
BTB26-400A	STMicro	Q4025K6	S	TO-218 (ISOL)
BTB26-400B	STMicro	Q4025K6	S	TO-218 (ISOL)
BTB26-600A	STMicro	Q6025K6	S	TO-218 (ISOL)
BTB26-600B	STMicro	Q6025K6	S	TO-218 (ISOL)
BTB26-700A	STMicro	Q8025K6	S	TO-218 (ISOL)
BTB26-700B	STMicro	Q8025K6	S	TO-218 (ISOL)
BTB26-800B	STMicro	Q8025K6	S	TO-218 (ISOL)
BTB41-200A	STMicro	Q4040K7	S	TO-218 (ISOL)
BTB41-200B	STMicro	Q4040K7	S	TO-218 (ISOL)
BTB41-400A	STMicro	Q4040K7	S	TO-218 (ISOL)
BTB41-400B	STMicro	Q4040K7	S	TO-218 (ISOL)
BTB41-600A	STMicro	Q6040K7	S	TO-218 (ISOL)
BTB41-600B	STMicro	Q6040K7	S	TO-218 (ISOL)
BTB41-700A	STMicro	Q8040K7	S	TO-218 (ISOL)
BTB41-700B	STMicro	Q8040K7	S	TO-218 (ISOL)
BTB41-800A	STMicro	Q8040K7	S	TO-218 (ISOL)
BTB41-800B	STMicro	Q8040K7	S	TO-218 (ISOL)
BTW41-500G	Valvo GmBH	Q6035P5	S	FASTPAK (ISOL)
BTW41-600G	Valvo GmBH	Q6035P5	S	FASTPAK (ISOL)
BTW66-200	STMicro	S4035J	S	TO-218 (ISOL)
BTW66-400	STMicro	S4035J	S	TO-218 (ISOL)
BTW66-600	STMicro	S6035J	S	TO-218 (ISOL)
BTW66-800	STMicro	S8035J	S	TO-218 (ISOL)
BTW67-200	STMicro	S4065J	S	TO-218 (ISOL)
BTW67-400	STMicro	S4065J	S	TO-218 (ISOL)
BTW67-600	STMicro	S6065J	S	TO-218 (ISOL)
BTW67-800	STMicro	S8065J	S	TO-218 (ISOL)
BTW68-200	STMicro	S4035K	D	TO-218 (ISOL)
BTW68-200N	STMicro	S4035K	S	TO-218 (ISOL)
BTW68-400	STMicro	S4035K	D	TO-218 (ISOL)
BTW68-400N	STMicro	S4035K	S	TO-218 (ISOL)
BTW68-600	STMicro	S6035K	D	TO-218 (ISOL)
BTW68-600N	STMicro	S6035K	S	TO-218 (ISOL)
BTW68-800	STMicro	S8035K	D	TO-218 (ISOL)
BTW68-800N	STMicro	S8035K	S	TO-218 (ISOL)
BTW69-200	STMicro	S4065K	D	TO-218 (ISOL)
BTW69-200N	STMicro	S4055M	D	TO-218 (N.ISOL)
BTW69-400	STMicro	S4065K	D	TO-218 (ISOL)
BTW69-400N	STMicro	S4055M	D	TO-218 (N.ISOL)
BTW69-600	STMicro	S6065K	D	TO-218 (ISOL)
BTW69-600N	STMicro	S6055M	D	TO-218 (N.ISOL)
BTW69-800	STMicro	S8065K	D	TO-218 (ISOL)
BTW69-800N	STMicro	S8055M	D	TO-218 (N.ISOL)
BTW70-200N	Valvo GmBH	S4070W	S	TO-218 (N.ISOL)
BTW70-400N	Valvo GmBH	S4070W	S	TO-218 (N.ISOL)
BTW70-600N	Valvo GmBH	S6070W	S	TO-218 (N.ISOL)
C103A	GE	EC103D	S	TO-92 (ISOL)
C103B	GE	EC103D	S	TO-92 (ISOL)
C103D	GE	EC103D	S	TO-92 (ISOL)
C103E	GE	EC103M	S	TO-92 (ISOL)
C103M	GE	EC103M	S	TO-92 (ISOL)
C103Y	GE	EC103D	S	TO-92 (ISOL)
C103YY	GE	EC103D	S	TO-92 (ISOL)
C106A	GE	S4006LS2	S	TO-220 (ISOL)
C106A1	GE	S4006LS2	S	TO-220 (ISOL)
C106A11	GE	S4006LS265	S	TO-220 (ISOL)
C106A12	GE	S4006LS2	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
C106A2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106A21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106A3	GE	S4006LS2	S	TO-220 (ISOL)
C106A32	GE	S4006LS2	S	TO-220 (ISOL)
C106A4	GE	S4004DS2	S	TO-252 (SMT)
C106A41	GE	S4004DS2	S	TO-252 (SMT)
C106B	GE	S4006LS2	S	TO-220 (ISOL)
C106B1	GE	S4006LS2	S	TO-220 (ISOL)
C106B11	GE	S4006LS265	S	TO-220 (ISOL)
C106B12	GE	S4006LS2	S	TO-220 (ISOL)
C106B2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106B21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106B3	GE	S4006LS2	S	TO-220 (ISOL)
C106B32	GE	S4006LS2	S	TO-220 (ISOL)
C106B4	GE	S4004DS2	S	TO-252 (SMT)
C106B41	GE	S4004DS2	S	TO-252 (SMT)
C106C	GE	S4006LS2	S	TO-220 (ISOL)
C106C1	GE	S4006LS2	S	TO-220 (ISOL)
C106C11	GE	S4006LS265	S	TO-220 (ISOL)
C106C12	GE	S4006LS2	S	TO-220 (ISOL)
C106C2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106C21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106C3	GE	S4006LS2	S	TO-220 (ISOL)
C106C32	GE	S4006LS2	S	TO-220 (ISOL)
C106C4	GE	S4004DS2	S	TO-252 (SMT)
C106C41	GE	S4004DS2	S	TO-252 (SMT)
C106D	GE	S4006LS2	S	TO-220 (ISOL)
C106D1	GE	S4006LS2	S	TO-220 (ISOL)
C106D11	GE	S4006LS265	S	TO-220 (ISOL)
C106D12	GE	S4006LS2	S	TO-220 (ISOL)
C106D2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106D21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106D3	GE	S4006LS2	S	TO-220 (ISOL)
C106D32	GE	S4006LS2	S	TO-220 (ISOL)
C106D4	GE	S4004DS2	S	TO-252 (SMT)
C106D41	GE	S4004DS2	S	TO-252 (SMT)
C106E	GE	S6006LS2	S	TO-220 (ISOL)
C106E1	GE	S6006LS2	S	TO-220 (ISOL)
C106E11	GE	S6006LS265	S	TO-220 (ISOL)
C106E12	GE	S6006LS2	S	TO-220 (ISOL)
C106E2	GE	S6004VS2	S	TO-251 (N.ISOL)
C106E21	GE	S6004VS2	S	TO-251 (N.ISOL)
C106E3	GE	S6006LS2	S	TO-220 (ISOL)
C106E32	GE	S6006LS2	S	TO-220 (ISOL)
C106E4	GE	S6004DS2	S	TO-252 (SMT)
C106E41	GE	S6004DS2	S	TO-252 (SMT)
C106F	GE	S4006LS2	S	TO-220 (ISOL)
C106F1	GE	S4006LS2	S	TO-220 (ISOL)
C106F11	GE	S4006LS265	S	TO-220 (ISOL)
C106F12	GE	S4006LS2	S	TO-220 (ISOL)
C106F2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106F21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106F3	GE	S4006LS2	S	TO-220 (ISOL)
C106F32	GE	S4006LS2	S	TO-220 (ISOL)
C106F4	GE	S4004DS2	S	TO-252 (SMT)
C106F41	GE	S4004DS2	S	TO-252 (SMT)
C106M	GE	S6006LS2	S	TO-220 (ISOL)
C106M1	GE	S6006LS2	S	TO-220 (ISOL)
C106M11	GE	S6006LS265	S	TO-220 (ISOL)
C106M12	GE	S6006LS2	S	TO-220 (ISOL)
C106M2	GE	S6004VS2	S	TO-251 (N.ISOL)
C106M21	GE	S6004VS2	S	TO-251 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
C106M3	GE	S6006LS2	S	TO-220 (ISOL)
C106M32	GE	S6006LS2	S	TO-220 (ISOL)
C106M4	GE	S6004DS2	S	TO-252 (SMT)
C106M41	GE	S6004DS2	S	TO-252 (SMT)
C106Q	GE	S4006LS2	S	TO-220 (ISOL)
C106Q1	GE	S4006LS2	S	TO-220 (ISOL)
C106Q11	GE	S4006LS265	S	TO-220 (ISOL)
C106Q12	GE	S4006LS2	S	TO-220 (ISOL)
C106Q2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106Q21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106Q3	GE	S4006LS2	S	TO-220 (ISOL)
C106Q32	GE	S4006LS2	S	TO-220 (ISOL)
C106Q4	GE	S4004DS2	S	TO-252 (SMT)
C106Q41	GE	S4004DS2	S	TO-252 (SMT)
C106Y	GE	S4006LS2	S	TO-220 (ISOL)
C106Y1	GE	S4006LS2	S	TO-220 (ISOL)
C106Y11	GE	S4006LS265	S	TO-220 (ISOL)
C106Y12	GE	S4006LS2	S	TO-220 (ISOL)
C106Y2	GE	S4004VS2	S	TO-251 (N.ISOL)
C106Y21	GE	S4004VS2	S	TO-251 (N.ISOL)
C106Y3	GE	S4006LS2	S	TO-220 (ISOL)
C106Y32	GE	S4006LS2	S	TO-220 (ISOL)
C106Y4	GE	S4004DS2	S	TO-252 (SMT)
C106Y41	GE	S4004DS2	S	TO-252 (SMT)
C107A	GE	S4006LS3	S	TO-220 (ISOL)
C107A1	GE	S4006LS3	S	TO-220 (ISOL)
C107A11	GE	S4006LS365	S	TO-220 (ISOL)
C107A12	GE	S4006LS3	S	TO-220 (ISOL)
C107A2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107A21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107A3	GE	S4006LS3	S	TO-220 (ISOL)
C107A32	GE	S4006LS3	S	TO-220 (ISOL)
C107A4	GE	S4004DS2	S	TO-252 (SMT)
C107A41	GE	S4004DS2	S	TO-252 (SMT)
C107B	GE	S4006LS3	S	TO-220 (ISOL)
C107B1	GE	S4006LS3	S	TO-220 (ISOL)
C107B11	GE	S4006LS365	S	TO-220 (ISOL)
C107B12	GE	S4006LS3	S	TO-220 (ISOL)
C107B2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107B21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107B3	GE	S4006LS3	S	TO-220 (ISOL)
C107B32	GE	S4006LS3	S	TO-220 (ISOL)
C107B4	GE	S4004DS2	S	TO-252 (SMT)
C107B41	GE	S4004DS2	S	TO-252 (SMT)
C107C	GE	S4006LS3	S	TO-220 (ISOL)
C107C1	GE	S4006LS3	S	TO-220 (ISOL)
C107C11	GE	S4006LS365	S	TO-220 (ISOL)
C107C12	GE	S4006LS3	S	TO-220 (ISOL)
C107C2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107C21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107C3	GE	S4006LS3	S	TO-220 (ISOL)
C107C32	GE	S4006LS3	S	TO-220 (ISOL)
C107C4	GE	S4004DS2	S	TO-252 (SMT)
C107C41	GE	S4004DS2	S	TO-252 (SMT)
C107D	GE	S4006LS3	S	TO-220 (ISOL)
C107D1	GE	S4006LS3	S	TO-220 (ISOL)
C107D11	GE	S4006LS365	S	TO-220 (ISOL)
C107D12	GE	S4006LS3	S	TO-220 (ISOL)
C107D2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107D21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107D3	GE	S4006LS3	S	TO-220 (ISOL)
C107D32	GE	S4006LS3	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
C107D4	GE	S4004DS2	S	TO-252 (SMT)
C107D41	GE	S4004DS2	S	TO-252 (SMT)
C107E	GE	S6006LS3	S	TO-220 (ISOL)
C107E1	GE	S6006LS3	S	TO-220 (ISOL)
C107E11	GE	S6006LS365	S	TO-220 (ISOL)
C107E12	GE	S6006LS3	S	TO-220 (ISOL)
C107E2	GE	S6004VS2	S	TO-251 (N.ISOL)
C107E21	GE	S6004VS2	S	TO-251 (N.ISOL)
C107E3	GE	S6006LS3	S	TO-220 (ISOL)
C107E32	GE	S6006LS3	S	TO-220 (ISOL)
C107E4	GE	S6004DS2	S	TO-252 (SMT)
C107E41	GE	S6004DS2	S	TO-252 (SMT)
C107F	GE	S4006LS3	S	TO-220 (ISOL)
C107F1	GE	S4006LS3	S	TO-220 (ISOL)
C107F11	GE	S4006LS365	S	TO-220 (ISOL)
C107F12	GE	S4006LS3	S	TO-220 (ISOL)
C107F2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107F21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107F3	GE	S4006LS3	S	TO-220 (ISOL)
C107F32	GE	S4006LS3	S	TO-220 (ISOL)
C107F4	GE	S4004DS2	S	TO-252 (SMT)
C107F41	GE	S4004DS2	S	TO-252 (SMT)
C107M	GE	S6006LS3	S	TO-220 (ISOL)
C107M1	GE	S6006LS3	S	TO-220 (ISOL)
C107M11	GE	S6006LS365	S	TO-220 (ISOL)
C107M12	GE	S6006LS3	S	TO-220 (ISOL)
C107M2	GE	S6004VS2	S	TO-251 (N.ISOL)
C107M21	GE	S6004VS2	S	TO-251 (N.ISOL)
C107M3	GE	S6006LS3	S	TO-220 (ISOL)
C107M32	GE	S6006LS3	S	TO-220 (ISOL)
C107M4	GE	S6004DS2	S	TO-252 (SMT)
C107M41	GE	S6004DS2	S	TO-252 (SMT)
C107Q	GE	S4006LS3	S	TO-220 (ISOL)
C107Q1	GE	S4006LS3	S	TO-220 (ISOL)
C107Q11	GE	S4006LS365	S	TO-220 (ISOL)
C107Q12	GE	S4006LS3	S	TO-220 (ISOL)
C107Q2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107Q21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107Q3	GE	S4006LS3	S	TO-220 (ISOL)
C107Q32	GE	S4006LS3	S	TO-220 (ISOL)
C107Q4	GE	S4004DS2	S	TO-252 (SMT)
C107Q41	GE	S4004DS2	S	TO-252 (SMT)
C107Y	GE	S4006LS3	S	TO-220 (ISOL)
C107Y1	GE	S4006LS3	S	TO-220 (ISOL)
C107Y11	GE	S4006LS365	S	TO-220 (ISOL)
C107Y12	GE	S4006LS3	S	TO-220 (ISOL)
C107Y2	GE	S4004VS2	S	TO-251 (N.ISOL)
C107Y21	GE	S4004VS2	S	TO-251 (N.ISOL)
C107Y3	GE	S4006LS3	S	TO-220 (ISOL)
C107Y32	GE	S4006LS3	S	TO-220 (ISOL)
C107Y4	GE	S4004DS2	S	TO-252 (SMT)
C107Y41	GE	S4004DS2	S	TO-252 (SMT)
C108A	GE	S4006LS2	S	TO-220 (ISOL)
C108A1	GE	S4006LS2	S	TO-220 (ISOL)
C108A11	GE	S4006LS265	S	TO-220 (ISOL)
C108A12	GE	S4006LS2	S	TO-220 (ISOL)
C108A2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108A21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108A3	GE	S4006LS2	S	TO-220 (ISOL)
C108A32	GE	S4006LS2	S	TO-220 (ISOL)
C108A4	GE	S4006DS2	S	TO-252 (SMT)
C108A41	GE	S4006DS2	S	TO-252 (SMT)

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Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
C108B	GE	S4006LS2	S	TO-220 (ISOL)
C108B1	GE	S4006LS2	S	TO-220 (ISOL)
C108B11	GE	S4006LS265	S	TO-220 (ISOL)
C108B12	GE	S4006LS2	S	TO-220 (ISOL)
C108B2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108B21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108B3	GE	S4006LS2	S	TO-220 (ISOL)
C108B32	GE	S4006LS2	S	TO-220 (ISOL)
C108B4	GE	S4006DS2	S	TO-252 (SMT)
C108B41	GE	S4006DS2	S	TO-252 (SMT)
C108C	GE	S4006LS2	S	TO-220 (ISOL)
C108C1	GE	S4006LS2	S	TO-220 (ISOL)
C108C11	GE	S4006LS265	S	TO-220 (ISOL)
C108C12	GE	S4006LS2	S	TO-220 (ISOL)
C108C2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108C21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108C3	GE	S4006LS2	S	TO-220 (ISOL)
C108C32	GE	S4006LS2	S	TO-220 (N.ISOL)
C108C4	GE	S4006DS2	S	TO-252 (SMT)
C108C41	GE	S4006DS2	S	TO-252 (SMT)
C108D	GE	S4006LS2	S	TO-220 (ISOL)
C108D1	GE	S4006LS2	S	TO-220 (ISOL)
C108D11	GE	S4006LS265	S	TO-220 (ISOL)
C108D12	GE	S4006LS2	S	TO-220 (ISOL)
C108D2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108D21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108D3	GE	S4006LS2	S	TO-220 (ISOL)
C108D32	GE	S4006LS2	S	TO-220 (ISOL)
C108D4	GE	S4006DS2	S	TO-252 (SMT)
C108D41	GE	S4006DS2	S	TO-252 (SMT)
C108E	GE	S6006LS2	S	TO-220 (ISOL)
C108E1	GE	S6006LS2	S	TO-220 (ISOL)
C108E11	GE	S6006LS265	S	TO-220 (ISOL)
C108E12	GE	S6006LS2	S	TO-220 (ISOL)
C108E2	GE	S6006VS2	S	TO-251 (N.ISOL)
C108E21	GE	S6006VS2	S	TO-251 (N.ISOL)
C108E3	GE	S6006LS2	S	TO-220 (ISOL)
C108E32	GE	S6006LS2	S	TO-220 (ISOL)
C108E4	GE	S6006DS2	S	TO-252 (SMT)
C108E41	GE	S6006DS2	S	TO-252 (SMT)
C108F	GE	S4006LS2	S	TO-220 (ISOL)
C108F1	GE	S4006LS2	S	TO-220 (ISOL)
C108F11	GE	S4006LS265	S	TO-220 (ISOL)
C108F12	GE	S4006LS2	S	TO-220 (ISOL)
C108F2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108F21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108F3	GE	S4006LS2	S	TO-220 (ISOL)
C108F32	GE	S4006LS2	S	TO-220 (ISOL)
C108F4	GE	S4006DS2	S	TO-252 (SMT)
C108F41	GE	S4006DS2	S	TO-252 (SMT)
C108M	GE	S6006LS2	S	TO-220 (ISOL)
C108M1	GE	S6006LS2	S	TO-220 (ISOL)
C108M11	GE	S6006LS265	S	TO-220 (ISOL)
C108M12	GE	S6006LS2	S	TO-220 (ISOL)
C108M2	GE	S6006VS2	S	TO-251 (N.ISOL)
C108M21	GE	S6006VS2	S	TO-251 (N.ISOL)
C108M3	GE	S6006LS2	S	TO-220 (ISOL)
C108M32	GE	S6006LS2	S	TO-220 (ISOL)
C108M4	GE	S6006DS2	S	TO-252 (SMT)
C108M41	GE	S6006DS2	S	TO-252 (SMT)
C108Q	GE	S4006LS2	S	TO-220 (ISOL)
C108Q1	GE	S4006LS2	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
C108Q11	GE	S4006LS265	S	TO-220 (ISOL)
C108Q12	GE	S4006LS2	S	TO-220 (ISOL)
C108Q2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108Q21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108Q3	GE	S4006LS2	S	TO-220 (ISOL)
C108Q32	GE	S4006LS2	S	TO-220 (ISOL)
C108Q4	GE	S4006DS2	S	TO-252 (SMT)
C108Q41	GE	S4006DS2	S	TO-252 (SMT)
C108Y	GE	S4006LS2	S	TO-220 (ISOL)
C108Y1	GE	S4006LS2	S	TO-220 (ISOL)
C108Y11	GE	S4006LS265	S	TO-220 (ISOL)
C108Y12	GE	S4006LS2	S	TO-220 (ISOL)
C108Y2	GE	S4006VS2	S	TO-251 (N.ISOL)
C108Y21	GE	S4006VS2	S	TO-251 (N.ISOL)
C108Y3	GE	S4006LS2	S	TO-220 (ISOL)
C108Y32	GE	S4006LS2	S	TO-220 (ISOL)
C108Y4	GE	S4006DS2	S	TO-252 (SMT)
C108Y41	GE	S4006DS2	S	TO-252 (SMT)
C116A1	GE	S4008R	S	TO-220 (N.ISOL)
C116B1	GE	S4008R	S	TO-220 (N.ISOL)
C116C1	GE	S4008R	S	TO-220 (N.ISOL)
C116D1	GE	S4008R	S	TO-220 (N.ISOL)
C116E1	GE	S6008R	S	TO-220 (N.ISOL)
C116F1	GE	S4008R	S	TO-220 (N.ISOL)
C116M1	GE	S6008R	S	TO-220 (N.ISOL)
C122A	GE	S4008R	S	TO-220 (N.ISOL)
C122B	GE	S4008R	S	TO-220 (N.ISOL)
C122C	GE	S4008R	S	TO-220 (N.ISOL)
C122D	GE	S4008R	S	TO-220 (N.ISOL)
C122E	GE	S6008R	S	TO-220 (N.ISOL)
C122F	GE	S4008R	S	TO-220 (N.ISOL)
C122M	GE	S6008R	S	TO-220 (N.ISOL)
C122N	GE	S8008R	S	TO-220 (N.ISOL)
C122S	GE	S8008R	S	TO-220 (N.ISOL)
C123A	GE	S4008L	S	TO-220 (ISOL)
C123B	GE	S4008L	S	TO-220 (ISOL)
C123C	GE	S4008L	S	TO-220 (ISOL)
C123D	GE	S4008L	S	TO-220 (ISOL)
C123E	GE	S6008L	S	TO-220 (ISOL)
C123F	GE	S4008L	S	TO-220 (ISOL)
C123M	GE	S6008L	S	TO-220 (ISOL)
C126A	GE	S4012R	S	TO-220 (N.ISOL)
C126B	GE	S4012R	S	TO-220 (N.ISOL)
C126C	GE	S4012R	S	TO-220 (N.ISOL)
C126D	GE	S4012R	S	TO-220 (N.ISOL)
C126E	GE	S6012R	S	TO-220 (N.ISOL)
C126F	GE	S4012R	S	TO-220 (N.ISOL)
C126M	GE	S6012R	S	TO-220 (N.ISOL)
C127A	GE	S4016R	D	TO-220 (N.ISOL)
C127B	GE	S4016R	D	TO-220 (N.ISOL)
C127D	GE	S4016R	D	TO-220 (N.ISOL)
C127E	GE	S6016R	D	TO-220 (N.ISOL)
C127F	GE	S4016R	D	TO-220 (N.ISOL)
C127M	GE	S6016R	D	TO-220 (N.ISOL)
C203A	GE	S4X8ES	S	TO-92 (ISOL)
C203B	GE	S4X8ES	S	TO-92 (ISOL)
C203C	GE	S4X8ES	S	TO-92 (ISOL)
C203D	GE	S4X8ES	S	TO-92 (ISOL)
C203Y	GE	S4X8ES	S	TO-92 (ISOL)
C203YY	GE	S4X8ES	S	TO-92 (ISOL)
C205A	GE	S402ES	D	TO-92 (ISOL)
C205B	GE	S402ES	D	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
C205C	GE	S402ES	D	TO-92 (ISOL)
C205D	GE	S402ES	D	TO-92 (ISOL)
C205Y	GE	S402ES	D	TO-92 (ISOL)
C205YY	GE	S402ES	D	TO-92 (ISOL)
CQ220-8B	Central Semi	Q4008R4	D	TO-220 (N.ISOL)
CQ220-8D	Central Semi	Q4008R4	D	TO-220 (N.ISOL)
CQ220-8M	Central Semi	Q6008R5	S	TO-220 (N.ISOL)
CQ220-8N	Central Semi	Q8008R5	S	TO-220 (N.ISOL)
CQ220I-8B	Central Semi	Q4008L4	D	TO-220 (ISOL)
CQ220I-8D	Central Semi	Q4008L4	D	TO-220 (ISOL)
CQ220I-8M	Central Semi	Q6008L5	S	TO-220 (ISOL)
CQ220I-8N	Central Semi	Q8008L5	S	TO-220 (ISOL)
CR08AS-8	Mitsubishi	S4X8BS	S	SOT-89 (SMT)
CR08AS-12	Mitsubishi	S6X8BS	S	SOT-89 (SMT)
D30	HUTSON	HT32	D	DO-35 (AXIAL)
D40	HUTSON	HT40	D	DO-35 (AXIAL)
DB3	STMicro	HT32	S	DO-35 (AXIAL)
DB4	STMicro	HT40	D	DO-35 (AXIAL)
DB1050G	JIFU	K1050G	D	DO-15 (AXIAL)
DB1100G	JIFU	K1100G	D	DO-15 (AXIAL)
DB1200G	JIFU	K1200G	D	DO-15 (AXIAL)
DB1300G	JIFU	K1300G	D	DO-15 (AXIAL)
DB1400G	JIFU	K1400G	D	DO-15 (AXIAL)
DB1500G	JIFU	K1500G	D	DO-15 (AXIAL)
DB1050S	JIFU	K1050S	D	DO-214 (SMT)
DB1100S	JIFU	K1100S	D	DO-214 (SMT)
DB1200S	JIFU	K1200S	D	DO-214 (SMT)
DB1300S	JIFU	K1300S	D	DO-214 (SMT)
DB1400S	JIFU	K1400S	D	DO-214 (SMT)
DB1500S	JIFU	K1500S	D	DO-214 (SMT)
DB2000F1	JIFU	K2000G	S	DO-15 (AXIAL)
DB2200F1	JIFU	K2200G	S	DO-15 (AXIAL)
DB2400F1	JIFU	K2400G	S	DO-15 (AXIAL)
DB2401F1	JIFU	K2401G	S	DO-15 (AXIAL)
DB2500F1	JIFU	K2500G	S	DO-15 (AXIAL)
DB3000F1	JIFU	K3000G	S	DO-15 (AXIAL)
DB2000G	JIFU	K2000G	D	DO-15 (AXIAL)
DB2200G	JIFU	K2200G	D	DO-15 (AXIAL)
DB2400G	JIFU	K2400G	D	DO-15 (AXIAL)
DB2500G	JIFU	K2500G	D	DO-15 (AXIAL)
DB3000G	JIFU	K3000G	D	DO-15 (AXIAL)
DB2000S	JIFU	K2000S	D	DO-214 (SMT)
DB2200S	JIFU	K2200S	D	DO-214 (SMT)
DB2400S	JIFU	K2400S	D	DO-214 (SMT)
DB2500S	JIFU	K2500S	D	DO-214 (SMT)
DB3000S	JIFU	K3000S	D	DO-214 (SMT)
DC34	JIFU	HT32	S	DO-35 (AXIAL)
DC38	JIFU	HT40	S	DO-35 (AXIAL)
DC42	JIFU	HT40	S	DO-35 (AXIAL)
DO201YR	TAG	HT32B	D	DO-35 (AXIAL)
FKN08PN40	Fairchild Sem	LX807DE	D	TO-92 (ISOL)
FKN08PN60	Fairchild Sem	LX807ME	D	TO-92 (ISOL)
FKN08PN40S	Fairchild Sem	LX807DE	D	TO-92 (ISOL)
FKN08PN60S	Fairchild Sem	LX807ME	D	TO-92 (ISOL)
FKN1N60SA	Fairchild Sem	L0107ME	D	TO-92 (ISOL)
FKPF2N80	Fairchild Sem	Q8004L4	S	TO-220 (ISOL)
FKPF3N80	Fairchild Sem	Q8004L4	S	TO-220 (ISOL)
FKPF5N80	Fairchild Sem	Q8006LH4	S	TO-220 (ISOL)
FKPF8N80	Fairchild Sem	Q8008LH4	S	TO-220 (ISOL)
FKPF10N80	Fairchild Sem	Q8010LH5	S	TO-220 (ISOL)
FKPF12N80	Fairchild Sem	Q8012LH5	S	TO-220 (ISOL)
FS0118BA	FAGOR	SEX8ES1	D	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
FS0118DA	FAGOR	SEX8ES1	D	TO-92 (ISOL)
FS0118MA	FAGOR	S6X8ES1	D	TO-92 (ISOL)
FS0102BA	FAGOR	S4X8ES	D	TO-92 (ISOL)
FS0102DA	FAGOR	S4X8ES	D	TO-92 (ISOL)
FS0102MA	FAGOR	S6X8ES1	D	TO-92 (ISOL)
FS0202BA	FAGOR	S402ES	D	TO-92 (ISOL)
FS0202DA	FAGOR	S402ES	D	TO-92 (ISOL)
FS0202MA	FAGOR	S602ES	D	TO-92 (ISOL)
FS0118BB	FAGOR	S4X8ES1	S	TO-92 (ISOL)
FS0118DB	FAGOR	S4X8ES1	S	TO-92 (ISOL)
FS0118MB	FAGOR	S6X8ES1	S	TO-92 (ISOL)
FS0102BB	FAGOR	S4X8ES	S	TO-92 (ISOL)
FS0102DB	FAGOR	S4X8ES	S	TO-92 (ISOL)
FS010SMB	FAGOR	S6X8ES	S	TO-92 (ISOL)
FS0202BB	FAGOR	S402ES	S	TO-92 (ISOL)
FS0202DB	FAGOR	S402ES	S	TO-92 (ISOL)
FS0202MB	FAGOR	S602ES	S	TO-92 (ISOL)
FS0118BN	FAGOR	S4X8TS1	D	SOT-223 (SMT)
FS0118DN	FAGOR	S4X8TS1	D	SOT-223 (SMT)
FS0118MN	FAGOR	S6X8TS1	D	SOT-223 (SMT)
FS0102BN	FAGOR	S4X8TS1	D	SOT-223 (SMT)
FS0102DN	FAGOR	S4X8TS1	D	SOT-223 (SMT)
FS0102MN	FAGOR	S6X8TS1	D	SOT-223 (SMT)
FS0202BN	FAGOR	S402TS	D	SOT-223 (SMT)
FS0202DN	FAGOR	S402TS	D	SOT-223 (SMT)
FS0202MN	FAGOR	S602TS	D	SOT-223 (SMT)
FS0802BI	FAGOR	S4008VS2	S	TO-251 (N.ISOL)
FS0802DI	FAGOR	S4008VS2	S	TO-251 (N.ISOL)
FS0802MI	FAGOR	S6008VS2	S	TO-251 (N.ISOL)
FS0808BI	FAGOR	S4008V	S	TO-251 (N.ISOL)
FS0808DI	FAGOR	S4008V	S	TO-251 (N.ISOL)
FS0808MI	FAGOR	S6008V	S	TO-251 (N.ISOL)
FS0808NI	FAGOR	S8008V	S	TO-251 (N.ISOL)
FS0809BI	FAGOR	S4008V	S	TO-251 (N.ISOL)
FS0809DI	FAGOR	S4008V	S	TO-251 (N.ISOL)
FS0809MI	FAGOR	S6008V	S	TO-251 (N.ISOL)
FS0809NI	FAGOR	S8008V	S	TO-251 (N.ISOL)
HI03SC	HUTSON	L4004L3	S	TO-220 (ISOL)
HI03SD	HUTSON	L4004V5	S	TO-251 (N.ISOL)
HI03SG	HUTSON	L4004V6	S	TO-251 (N.ISOL)
HI03SH	HUTSON	L4004V8	S	TO-251 (N.ISOL)
HI03SS	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI13SC	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI13SD	HUTSON	L4004V5	S	TO-251 (N.ISOL)
HI13SG	HUTSON	L4004V6	S	TO-251 (N.ISOL)
HI13SH	HUTSON	L4004V8	S	TO-251 (N.ISOL)
HI13SS	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI23SC	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI23SD	HUTSON	L4004V5	S	TO-251 (N.ISOL)
HI23SG	HUTSON	L4004V6	S	TO-251 (N.ISOL)
HI23SH	HUTSON	L4004V8	S	TO-251 (N.ISOL)
HI23SS	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI33SC	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI33SD	HUTSON	L4004V5	S	TO-251 (N.ISOL)
HI33SG	HUTSON	L4004V6	S	TO-251 (N.ISOL)
HI33SH	HUTSON	L4004V8	S	TO-251 (N.ISOL)
HI33SS	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI43SC	HUTSON	L4004V3	S	TO-251 (N.ISOL)
HI43SD	HUTSON	L4004V5	S	TO-251 (N.ISOL)
HI43SG	HUTSON	L4004V6	S	TO-251 (N.ISOL)
HI43SH	HUTSON	L4004V8	S	TO-251 (N.ISOL)
HI43SS	HUTSON	L4004V3	S	TO-251 (N.ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
HI63SC	HUTSON	L6004V3	S	TO-251 (N.ISOL)
HI63SD	HUTSON	L6004V5	S	TO-251 (N.ISOL)
HI63SG	HUTSON	L6004V6	S	TO-251 (N.ISOL)
HI63SH	HUTSON	L6004V8	S	TO-251 (N.ISOL)
HI63SS	HUTSON	L6004V3	S	TO-251 (N.ISOL)
HT06	HUTSON	Q4006V4	S	TO-251 (N.ISOL)
HT16	HUTSON	Q4006V4	S	TO-251 (N.ISOL)
HT26	HUTSON	Q4006V4	S	TO-251 (N.ISOL)
HT36	HUTSON	Q4006V4	S	TO-251 (N.ISOL)
HT46	HUTSON	Q4006V4	S	TO-251 (N.ISOL)
HT66	HUTSON	Q6006V5	S	TO-251 (N.ISOL)
ID100	UNITRODE	S4X8ES	S	TO-92 (ISOL)
ID101	UNITRODE	S4X8ES	S	TO-92 (ISOL)
ID102	UNITRODE	S4X8ES	S	TO-92 (ISOL)
ID103	UNITRODE	S4X8ES	S	TO-92 (ISOL)
ID104	UNITRODE	S4X8ES	S	TO-92 (ISOL)
ID105	UNITRODE	S4X8ES	S	TO-92 (ISOL)
ID106	UNITRODE	S4X8ES	S	TO-92 (ISOL)
IP100	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IP101	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IP102	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IP103	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IP104	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IP105	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IP106	UNITRODE	S4X8ES	D	TO-92 (ISOL)
IS010	HUTSON	S4010L	D	TO-220 (ISOL)
IS010X	HUTSON	S4010L	D	TO-220 (ISOL)
IS020	HUTSON	S4020L	S	TO-220 (ISOL)
IS020X	HUTSON	S4020L	D	TO-220 (ISOL)
IS08	HUTSON	S4008L	D	TO-220 (ISOL)
IS08X	HUTSON	S4008L	D	TO-220 (ISOL)
IS110	HUTSON	S4010L	D	TO-220 (ISOL)
IS110X	HUTSON	S4010L	D	TO-220 (ISOL)
IS120	HUTSON	S4020L	S	TO-220 (ISOL)
IS120X	HUTSON	S4020L	D	TO-220 (ISOL)
IS18	HUTSON	S4008L	D	TO-220 (ISOL)
IS18X	HUTSON	S4008L	D	TO-220 (ISOL)
IS210	HUTSON	S4010L	D	TO-220 (ISOL)
IS210X	HUTSON	S4010L	D	TO-220 (ISOL)
IS220	HUTSON	S4020L	S	TO-220 (ISOL)
IS220X	HUTSON	S4020L	D	TO-220 (ISOL)
IS28	HUTSON	S4008L	D	TO-220 (ISOL)
IS28X	HUTSON	S4008L	D	TO-220 (ISOL)
IS310	HUTSON	S4010L	D	TO-220 (ISOL)
IS310X	HUTSON	S4010L	D	TO-220 (ISOL)
IS320	HUTSON	S4020L	S	TO-220 (ISOL)
IS320X	HUTSON	S4020L	D	TO-220 (ISOL)
IS38	HUTSON	S4008L	D	TO-220 (ISOL)
IS38X	HUTSON	S4008L	D	TO-220 (ISOL)
IS410	HUTSON	S4010L	D	TO-220 (ISOL)
IS410X	HUTSON	S4010L	D	TO-220 (ISOL)
IS420	HUTSON	S4020L	S	TO-220 (ISOL)
IS420X	HUTSON	S4020L	D	TO-220 (ISOL)
IS48	HUTSON	S4008L	D	TO-220 (ISOL)
IS48X	HUTSON	S4008L	D	TO-220 (ISOL)
IS510	HUTSON	S6010L	D	TO-220 (ISOL)
IS510X	HUTSON	S6010L	D	TO-220 (ISOL)
IS520	HUTSON	S6020L	S	TO-220 (ISOL)
IS520X	HUTSON	S6020L	D	TO-220 (ISOL)
IS58	HUTSON	S6008L	D	TO-220 (ISOL)
IS58X	HUTSON	S6008L	D	TO-220 (ISOL)
IS610	HUTSON	S6010L	D	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
IS610X	HUTSON	S6010L	D	TO-220 (ISOL)
IS620	HUTSON	S6020L	S	TO-220 (ISOL)
IS620X	HUTSON	S6020L	D	TO-220 (ISOL)
IS68	HUTSON	S6008L	D	TO-220 (ISOL)
IS68X	HUTSON	S6008L	D	TO-220 (ISOL)
IT010	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT010A	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT010B	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT010HA	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT010HX	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT015	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT015A	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT015B	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT015HA	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT015HX	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT06	HUTSON	Q4006L4	D	TO-220 (ISOL)
IT08	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT08A	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT08B	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT08HA	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT08HX	HUTSON	Q4008L4	S	TO-220 (ISOL)
IT110	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT110A	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT110B	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT110HA	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT110HX	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT115	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT115A	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT115B	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT115HA	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT115HX	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT16	HUTSON	Q4006L4	D	TO-220 (ISOL)
IT18	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT18A	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT18B	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT18HA	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT18HX	HUTSON	Q4008L4	S	TO-220 (ISOL)
IT210	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT210A	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT210B	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT210HA	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT210HX	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT215	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT215A	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT215B	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT215HA	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT215HX	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT26	HUTSON	Q4006L4	D	TO-220 (ISOL)
IT28	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT28A	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT28B	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT28HA	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT28HX	HUTSON	Q4008L4	S	TO-220 (ISOL)
IT310	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT310A	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT310B	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT310HA	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT310HX	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT315	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT315A	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT315B	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT315HA	HUTSON	Q4015L5	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
IT315HX	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT36	HUTSON	Q4006L4	D	TO-220 (ISOL)
IT38	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT38A	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT38B	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT38HA	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT38HX	HUTSON	Q4008L4	S	TO-220 (ISOL)
IT410	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT410A	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT410B	HUTSON	Q4010L5	D	TO-220 (ISOL)
IT410HA	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT410HX	HUTSON	Q4010L5	S	TO-220 (ISOL)
IT415	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT415A	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT415B	HUTSON	Q4015L5	D	TO-220 (ISOL)
IT415HA	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT415HX	HUTSON	Q4015L5	S	TO-220 (ISOL)
IT46	HUTSON	Q4006L4	D	TO-220 (ISOL)
IT48	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT48A	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT48B	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT48HA	HUTSON	Q4008L4	D	TO-220 (ISOL)
IT48HX	HUTSON	Q4008L4	S	TO-220 (ISOL)
IT510	HUTSON	Q6010L5	D	TO-220 (ISOL)
IT510A	HUTSON	Q6010L5	D	TO-220 (ISOL)
IT510B	HUTSON	Q6010L5	D	TO-220 (ISOL)
IT510HA	HUTSON	Q6010L5	S	TO-220 (ISOL)
IT510HX	HUTSON	Q6010L5	S	TO-220 (ISOL)
IT515	HUTSON	Q6015L5	D	TO-220 (ISOL)
IT515A	HUTSON	Q6015L5	D	TO-220 (ISOL)
IT515B	HUTSON	Q6015L5	D	TO-220 (ISOL)
IT515HA	HUTSON	Q6015L5	S	TO-220 (ISOL)
IT515HX	HUTSON	Q6015L5	S	TO-220 (ISOL)
IT56	HUTSON	Q6006L5	S	TO-220 (ISOL)
IT58	HUTSON	Q6008L5	S	TO-220 (ISOL)
IT58A	HUTSON	Q6008L5	S	TO-220 (ISOL)
IT58B	HUTSON	Q6008L5	S	TO-220 (ISOL)
IT58HA	HUTSON	Q6008L5	S	TO-220 (ISOL)
IT58HX	HUTSON	Q6008L5	S	TO-220 (ISOL)
IT610	HUTSON	Q6010L5	D	TO-220 (ISOL)
IT610A	HUTSON	Q6010L5	D	TO-220 (ISOL)
IT610B	HUTSON	Q6010L5	D	TO-220 (ISOL)
IT610HA	HUTSON	Q6010L5	S	TO-220 (ISOL)
IT610HX	HUTSON	Q6010L5	S	TO-220 (ISOL)
IT615	HUTSON	Q6015L5	D	TO-220 (ISOL)
IT615A	HUTSON	Q6015L5	D	TO-220 (ISOL)
IT615B	HUTSON	Q6015L5	D	TO-220 (ISOL)
IT615HA	HUTSON	Q6015L5	S	TO-220 (ISOL)
IT615HX	HUTSON	Q6015L5	S	TO-220 (ISOL)
IT66	HUTSON	Q6006L5	D	TO-220 (ISOL)
IT68	HUTSON	Q6008L5	D	TO-220 (ISOL)
IT68A	HUTSON	Q6008L5	D	TO-220 (ISOL)
IT68B	HUTSON	Q6008L5	D	TO-220 (ISOL)
IT68HA	HUTSON	Q6008L5	S	TO-220 (ISOL)
IT68HX	HUTSON	Q6008L5	S	TO-220 (ISOL)
K1V10	SHINDENGEN	K1050G	S	DO-15X (AXIAL)
K1V11	SHINDENGEN	K1100G	S	DO-15X (AXIAL)
K1V12	SHINDENGEN	K1200G	S	DO-15X (AXIAL)
K1V14	SHINDENGEN	K1300G	S	DO-15X (AXIAL)
K1V16	SHINDENGEN	K1500G	S	DO-15X (AXIAL)
K1V18	SHINDENGEN	K1500G	S	DO-15X (AXIAL)
K1V22	SHINDENGEN	K2200G	S	DO-15X (AXIAL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
K1V24	SHINDENGEN	K2400G	S	DO-15X (AXIAL)
K1V26	SHINDENGEN	K2500G	S	DO-15X (AXIAL)
K1VA10	SHINDENGEN	K1050E70	S	TO-92 (ISOL)
K1VA11	SHINDENGEN	K1100E70	S	TO-92 (ISOL)
K1VA12	SHINDENGEN	K1200E70	S	TO-92 (ISOL)
K1VA14	SHINDENGEN	K1300E70	S	TO-92 (ISOL)
K1VA16	SHINDENGEN	K1500E70	S	TO-92 (ISOL)
L2004L7	TECCOR	L4004L6	D	TO-220 (ISOL)
L2004L9	TECCOR	L4004L8	D	TO-220 (ISOL)
L2006L7	TECCOR	L4006L6	D	TO-220 (ISOL)
L2006L9	TECCOR	L4006L8	D	TO-220 (ISOL)
L2008L7	TECCOR	L4008L6	D	TO-220 (ISOL)
L2008L9	TECCOR	L4008L8	D	TO-220 (ISOL)
L201E7	TECCOR	L401E6	D	TO-92 (ISOL)
L201E9	TECCOR	L401E8	D	TO-92 (ISOL)
L4004L7	TECCOR	L4004L6	D	TO-220 (ISOL)
L4004L9	TECCOR	L4004L8	D	TO-220 (ISOL)
L4006L7	TECCOR	L4006L6	D	TO-220 (ISOL)
L4006L9	TECCOR	L4006L8	D	TO-220 (ISOL)
L4008L7	TECCOR	L4008L6	D	TO-220 (ISOL)
L4008L9	TECCOR	L4008L8	D	TO-220 (ISOL)
L401E7	TECCOR	L401E6	D	TO-92 (ISOL)
L401E9	TECCOR	L401E8	D	TO-92 (ISOL)
L6004L7	TECCOR	L6004L6	D	TO-220 (ISOL)
L6004L9	TECCOR	L6004L8	D	TO-220 (ISOL)
L6006L7	TECCOR	L6006L6	D	TO-220 (ISOL)
L6006L9	TECCOR	L6006L8	D	TO-220 (ISOL)
L6008L7	TECCOR	L6008L6	D	TO-220 (ISOL)
L6008L9	TECCOR	L6008L8	D	TO-220 (ISOL)
L2004N31	TECCOR	L4004L3	S	TO-220 (ISOL)
L4004N31	TECCOR	L4004L3	S	TO-220 (ISOL)
L2004N51	TECCOR	L4004L5	S	TO-220 (ISOL)
L4004N51	TECCOR	L4004L5	S	TO-220 (ISOL)
L2004N71	TECCOR	L4004L6	S	TO-220 (ISOL)
L4004N71	TECCOR	L4004L6	S	TO-220 (ISOL)
L2004N91	TECCOR	L4004L8	S	TO-220 (ISOL)
L4004N91	TECCOR	L4004L8	S	TO-220 (ISOL)
L601E7	TECCOR	L601E6	D	TO-92 (ISOL)
L601E9	TECCOR	L601E8	D	TO-92 (ISOL)
LLDB3	JIFU	HTM32B	D	MINIMELF
MAC08BT1	MOTOROLA	LX807DT	S	SOT-223 (SMT)
MAC08DT1	MOTOROLA	LX807DT	S	SOT-223 (SMT)
MAC08MT1	MOTOROLA	LX807MT	S	SOT-223 (SMT)
MAC12D	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC12HCD	MOTOROLA	Q4012RH5	S	TO-220 (N.ISOL)
MAC12HCM	MOTOROLA	Q6012RH5	S	TO-220 (N.ISOL)
MAC12HCN	MOTOROLA	Q8012RH5	S	TO-220 (N.ISOL)
MAC12M	MOTOROLA	Q6015R5	S	TO-220 (N.ISOL)
MAC12N	MOTOROLA	Q8015R5	S	TO-220 (N.ISOL)
MAC15-10	MOTOROLA	Q8015R5	D	TO-220 (N.ISOL)
MAC15-10FP	MOTOROLA	Q8015L5	D	TO-220 (ISOL)
MAC15-4	MOTOROLA	Q4015R5	D	TO-220 (N.ISOL)
MAC15-4FP	MOTOROLA	Q4015L5	D	TO-220 (ISOL)
MAC15-5	MOTOROLA	Q4015R5	D	TO-220 (N.ISOL)
MAC15-6	MOTOROLA	Q4015R5	D	TO-220 (N.ISOL)
MAC15-6FP	MOTOROLA	Q4015L5	D	TO-220 (ISOL)
MAC15-7	MOTOROLA	Q6015R5	D	TO-220 (N.ISOL)
MAC15-8	MOTOROLA	Q6015R5	D	TO-220 (N.ISOL)
MAC15-8FP	MOTOROLA	Q6015L5	D	TO-220 (ISOL)
MAC15-9	MOTOROLA	Q8015R5	D	TO-220 (N.ISOL)
MAC15A10	MOTOROLA	Q8015R5	S	TO-220 (N.ISOL)
MAC15A10FP	MOTOROLA	Q8015L5	S	TO-220 (ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC15A4	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC15A4FP	MOTOROLA	Q4015L5	S	TO-220 (ISOL)
MAC15A5	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC15A5FP	MOTOROLA	Q4015L5	S	TO-220 (ISOL)
MAC15A6	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC15A6FP	MOTOROLA	Q4015L5	S	TO-220 (ISOL)
MAC15A7	MOTOROLA	Q6015R5	S	TO-220 (N.ISOL)
MAC15A7FP	MOTOROLA	Q6015L5	S	TO-220 (ISOL)
MAC15A8	MOTOROLA	Q6015R5	S	TO-220 (N.ISOL)
MAC15A8FP	MOTOROLA	Q6015L5	S	TO-220 (ISOL)
MAC15A9	MOTOROLA	Q8015R5	S	TO-220 (N.ISOL)
MAC15A9FP	MOTOROLA	Q8015L5	S	TO-220 (ISOL)
MAC15M	MOTOROLA	Q6015R5	D	TO-220 (N.ISOL)
MAC15N	MOTOROLA	Q8015R5	D	TO-220 (N.ISOL)
MAC16-10	MOTOROLA	Q8016RH6	D	TO-220 (N.ISOL)
MAC16-4	MOTOROLA	Q4016RH6	D	TO-220 (N.ISOL)
MAC16-6	MOTOROLA	Q4016RH6	D	TO-220 (N.ISOL)
MAC16-8	MOTOROLA	Q6016RH6	D	TO-220 (N.ISOL)
MAC16CD	MOTOROLA	Q4016RH6	S	TO-220 (N.ISOL)
MAC16CM	MOTOROLA	Q6016RH6	S	TO-220 (N.ISOL)
MAC16CN	MOTOROLA	Q8016RH6	S	TO-220 (N.ISOL)
MAC16D	MOTOROLA	Q4016RH6	S	TO-220 (N.ISOL)
MAC16M	MOTOROLA	Q6016RH6	S	TO-220 (N.ISOL)
MAC16N	MOTOROLA	Q8016RH6	S	TO-220 (N.ISOL)
MAC20-10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC20-4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20-5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20-6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20-7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20-8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20-9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC20A10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC20A4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20A5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20A6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20A7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20A8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC20A9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC210-10	MOTOROLA	Q8010R5	D	TO-220 (N.ISOL)
MAC210-10FP	MOTOROLA	Q8010L5	D	TO-220 (ISOL)
MAC210-4	MOTOROLA	Q4010R5	D	TO-220 (N.ISOL)
MAC210-4FP	MOTOROLA	Q4010L5	D	TO-220 (ISOL)
MAC210-5	MOTOROLA	Q4010R5	D	TO-220 (N.ISOL)
MAC210-6	MOTOROLA	Q4010R5	D	TO-220 (N.ISOL)
MAC210-6FP	MOTOROLA	Q4010L5	D	TO-220 (ISOL)
MAC210-7	MOTOROLA	Q6010R5	D	TO-220 (N.ISOL)
MAC210-8	MOTOROLA	Q6010R5	D	TO-220 (N.ISOL)
MAC210-8FP	MOTOROLA	Q6010L5	D	TO-220 (ISOL)
MAC210A10	MOTOROLA	Q8010R5	S	TO-220 (N.ISOL)
MAC210A10F	MOTOROLA	Q8010L5	S	TO-220 (ISOL)
MAC210A4	MOTOROLA	Q4010R5	S	TO-220 (N.ISOL)
MAC210A4FP	MOTOROLA	Q4010L5	S	TO-220 (ISOL)
MAC210A5	MOTOROLA	Q4010R5	S	TO-220 (N.ISOL)
MAC210A5FP	MOTOROLA	Q4010L5	S	TO-220 (ISOL)
MAC210A6	MOTOROLA	Q4010R5	S	TO-220 (N.ISOL)
MAC210A6FP	MOTOROLA	Q4010L5	S	TO-220 (ISOL)
MAC210A7	MOTOROLA	Q6010R5	S	TO-220 (N.ISOL)
MAC210A7FP	MOTOROLA	Q6010L5	S	TO-220 (ISOL)
MAC210A8	MOTOROLA	Q6010R5	S	TO-220 (N.ISOL)
MAC210A8FP	MOTOROLA	Q6010L5	S	TO-220 (ISOL)
MAC210A9	MOTOROLA	Q8010R5	S	TO-220 (N.ISOL)
MAC210A9FP	MOTOROLA	Q8010L5	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC212-10	MOTOROLA	Q8012RH5	D	TO-220 (N.ISOL)
MAC212-10FP	MOTOROLA	Q8012LH5	D	TO-220 (ISOL)
MAC212-4	MOTOROLA	Q4012RH5	D	TO-220 (N.ISOL)
MAC212-4FP	MOTOROLA	Q4012LH5	D	TO-220 (ISOL)
MAC212-6	MOTOROLA	Q4012RH5	D	TO-220 (N.ISOL)
MAC212-6FP	MOTOROLA	Q4012LH5	D	TO-220 (ISOL)
MAC212-8	MOTOROLA	Q6012RH5	D	TO-220 (N.ISOL)
MAC212-8FP	MOTOROLA	Q6012LH5	D	TO-220 (ISOL)
MAC212A10	MOTOROLA	Q8012RH5	S	TO-220 (N.ISOL)
MAC212A10FP	MOTOROLA	Q8012LH5	S	TO-220 (ISOL)
MAC212A4	MOTOROLA	Q4012RH5	S	TO-220 (N.ISOL)
MAC212A4FP	MOTOROLA	Q4012LH5	S	TO-220 (ISOL)
MAC212A6	MOTOROLA	Q4012RH5	S	TO-220 (N.ISOL)
MAC212A6FP	MOTOROLA	Q4012LH5	S	TO-220 (ISOL)
MAC212A8	MOTOROLA	Q6012RH5	S	TO-220 (N.ISOL)
MAC212A8FP	MOTOROLA	Q6012LH5	S	TO-220 (ISOL)
MAC213-10	MOTOROLA	Q8012RH5	D	TO-220 (N.ISOL)
MAC213-4	MOTOROLA	Q4012RH5	D	TO-220 (N.ISOL)
MAC213-6	MOTOROLA	Q4012RH5	D	TO-220 (N.ISOL)
MAC213-8	MOTOROLA	Q6012RH5	D	TO-220 (N.ISOL)
MAC218-10	MOTOROLA	Q8008R5	D	TO-220 (N.ISOL)
MAC218-10FP	MOTOROLA	Q8008L5	D	TO-220 (ISOL)
MAC218-2	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC218-3	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC218-4	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC218-4FP	MOTOROLA	Q4008L4	D	TO-220 (ISOL)
MAC218-5	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC218-6	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC218-6FP	MOTOROLA	Q4008L4	D	TO-220 (ISOL)
MAC218-7	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC218-8	MOTOROLA	Q6008R5	D	TO-220 (N.ISOL)
MAC218-8FP	MOTOROLA	Q6008L5	S	TO-220 (ISOL)
MAC218-A10	MOTOROLA	Q8008R5	S	TO-220 (N.ISOL)
MAC218-A10FP	MOTOROLA	Q8008L5	S	TO-220 (ISOL)
MAC218-A2	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC218-A3	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC218-A4	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC218-A4FP	MOTOROLA	Q4008L4	S	TO-220 (ISOL)
MAC218-A5	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC218-A6	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC218-A6FP	MOTOROLA	Q4008L4	S	TO-220 (ISOL)
MAC218-A7	MOTOROLA	Q6008R5	S	TO-220 (N.ISOL)
MAC218-A8	MOTOROLA	Q6008R5	S	TO-220 (N.ISOL)
MAC218-A8FP	MOTOROLA	Q6008L5	S	TO-220 (ISOL)
MAC219-10	MOTOROLA	Q8008R5	D	TO-220 (N.ISOL)
MAC219-4	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC219-6	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC219-8	MOTOROLA	Q6008R5	D	TO-220 (N.ISOL)
MAC220-2	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC220-3	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC220-5	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC220-7	MOTOROLA	Q6008R5	D	TO-220 (N.ISOL)
MAC220-9	MOTOROLA	Q8008R5	D	TO-220 (N.ISOL)
MAC221-2	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC221-3	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC221-5	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC221-7	MOTOROLA	Q6008R5	D	TO-220 (N.ISOL)
MAC221-9	MOTOROLA	Q8008R5	D	TO-220 (N.ISOL)
MAC222-1	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC222-10	MOTOROLA	Q8008R5	D	TO-220 (N.ISOL)
MAC222-2	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC222-3	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC222-4	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC222-5	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC222-6	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC222-7	MOTOROLA	Q6008R5	D	TO-220 (N.ISOL)
MAC222-8	MOTOROLA	Q6008R5	D	TO-220 (N.ISOL)
MAC222-9	MOTOROLA	Q8008R5	D	TO-220 (N.ISOL)
MAC222A1	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC222A10	MOTOROLA	Q8008R5	S	TO-220 (N.ISOL)
MAC222A2	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC222A3	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC222A4	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC222A5	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC222A6	MOTOROLA	Q4008R4	S	TO-220 (N.ISOL)
MAC222A7	MOTOROLA	Q6008R5	S	TO-220 (N.ISOL)
MAC222A8	MOTOROLA	Q6008R5	S	TO-220 (N.ISOL)
MAC222A9	MOTOROLA	Q8008R5	S	TO-220 (N.ISOL)
MAC223-10	MOTOROLA	Q8025R5	S	TO-220 (N.ISOL)
MAC223-10FP	MOTOROLA	Q8025L6	S	TO-220 (ISOL)
MAC223-3	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223-4	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223-4FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC223-5	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223-6	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223-6FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC223-7	MOTOROLA	Q6025R5	S	TO-220 (N.ISOL)
MAC223-8	MOTOROLA	Q6025R5	S	TO-220 (N.ISOL)
MAC223-8FP	MOTOROLA	Q6025L6	S	TO-220 (ISOL)
MAC223-9	MOTOROLA	Q8025R5	S	TO-220 (N.ISOL)
MAC223A10	MOTOROLA	Q8025R5	S	TO-220 (N.ISOL)
MAC223A10FP	MOTOROLA	Q8025L6	S	TO-220 (ISOL)
MAC223A3	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223A4	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223A4FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC223A5	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223A5FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC223A6	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC223A6FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC223A7	MOTOROLA	Q6025R5	S	TO-220 (N.ISOL)
MAC223A7FP	MOTOROLA	Q6025L6	S	TO-220 (ISOL)
MAC223A8	MOTOROLA	Q6025R5	S	TO-220 (N.ISOL)
MAC223A8FP	MOTOROLA	Q6025L6	S	TO-220 (ISOL)
MAC223A9	MOTOROLA	Q8025R5	S	TO-220 (N.ISOL)
MAC223A9FP	MOTOROLA	Q8025L6	S	TO-220 (ISOL)
MAC224-10	MOTOROLA	Q8040K7	S	TO-218 (ISOL)
MAC224-4	MOTOROLA	Q4040K7	S	TO-218 (ISOL)
MAC224-5	MOTOROLA	Q4040K7	S	TO-218 (ISOL)
MAC224-6	MOTOROLA	Q4040K7	S	TO-218 (ISOL)
MAC224-7	MOTOROLA	Q6040K7	S	TO-218 (ISOL)
MAC224-8	MOTOROLA	Q6040K7	S	TO-218 (ISOL)
MAC224A10	MOTOROLA	Q8040K7	S	TO-218 (ISOL)
MAC224A4	MOTOROLA	Q4040K7	S	TO-218 (ISOL)
MAC224A5	MOTOROLA	Q4040K7	S	TO-218 (ISOL)
MAC224A6	MOTOROLA	Q4040K7	S	TO-218 (ISOL)
MAC224A7	MOTOROLA	Q6040K7	S	TO-218 (ISOL)
MAC224A8	MOTOROLA	Q6040K7	S	TO-218 (ISOL)
MAC224A9	MOTOROLA	Q8040K7	S	TO-218 (ISOL)
MAC228-2	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228-3	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228-4	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228-4FP	MOTOROLA	L4008L6	D	TO-220 (ISOL)
MAC228-5	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228-6	MOTOROLA	L4008L6	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC228-6FP	MOTOROLA	L4008L6	D	TO-220 (ISOL)
MAC228-7	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC228-8	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC228-8FP	MOTOROLA	L6008L6	D	TO-220 (ISOL)
MAC228A2	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A3	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A4	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A4FP	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A5	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A6	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A6FP	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC228A7	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC228A8	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC228A8FP	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC229-4	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC229-4FP	MOTOROLA	L4008L6	D	TO-220 (ISOL)
MAC229-6	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC229-6FP	MOTOROLA	L4008L6	D	TO-220 (ISOL)
MAC229-8	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC229-8FP	MOTOROLA	L6008L6	D	TO-220 (ISOL)
MAC229A4	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC229A4FP	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC229A6	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC229A6FP	MOTOROLA	L4008L6	S	TO-220 (ISOL)
MAC229A8	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC229A8FP	MOTOROLA	L6008L6	S	TO-220 (ISOL)
MAC25-10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC25-4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25-5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25-6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25-7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25-8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25-9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC25A10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC25A4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25A5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25A6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25A7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25A8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC25A9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC3010-15	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC3010-25	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC3010-4	MOTOROLA	Q4004R3	S	TO-220 (N.ISOL)
MAC3010-8	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC3020-15	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC3020-25	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC3020-4	MOTOROLA	Q4004R4	S	TO-220 (N.ISOL)
MAC3020-8	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC3030-15	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC3030-25	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC3030-4	MOTOROLA	Q4004R4	S	TO-220 (N.ISOL)
MAC3030-8	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC3040-15	MOTOROLA	Q4015R5	S	TO-220 (N.ISOL)
MAC3040-25	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC3040-4	MOTOROLA	Q4004R4	S	TO-220 (N.ISOL)
MAC3040-8	MOTOROLA	Q4008R4	D	TO-220 (N.ISOL)
MAC320-10	MOTOROLA	Q8025R5	S	TO-220 (N.ISOL)
MAC320-10FP	MOTOROLA	Q8025L6	S	TO-220 (ISOL)
MAC320-4	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC320-4FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC320-6	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)

Teccor® brand Thyristors

Cross Reference Guide



Littelfuse®

Expertise Applied | Answers Delivered

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC320-6FP	MOTOROLA	Q4025L6	S	TO-220 (ISOL)
MAC320-8	MOTOROLA	Q6025R5	S	TO-220 (N.ISOL)
MAC320-8FP	MOTOROLA	Q6025L6	S	TO-220 (ISOL)
MAC320A10	MOTOROLA	Q8025R5	S	TO-220 (N.ISOL)
MAC320A4	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC320A6	MOTOROLA	Q4025R5	S	TO-220 (N.ISOL)
MAC320A8	MOTOROLA	Q6025R5	S	TO-220 (N.ISOL)
MAC321-10	MOTOROLA	Q8025R5	D	TO-220 (N.ISOL)
MAC321-4	MOTOROLA	Q4025R5	D	TO-220 (N.ISOL)
MAC321-6	MOTOROLA	Q4025R5	D	TO-220 (N.ISOL)
MAC321-8	MOTOROLA	Q6025R5	D	TO-220 (N.ISOL)
MAC4DCM	MOTOROLA	Q6006DH4	S	TO-252 (SMT)
MAC4DCM1	MOTOROLA	Q6006VH4	S	TO-251 (N.ISOL)
MAC4DCN	MOTOROLA	Q8006DH4	S	TO-252 (SMT)
MAC4DCN1	MOTOROLA	Q8006VH4	S	TO-251 (N.ISOL)
MAC4DHM	MOTOROLA	L6004D6	S	TO-252 (SMT)
MAC4DHM1	MOTOROLA	L6004V6	S	TO-251 (N.ISOL)
MAC4DLM	MOTOROLA	L6004D5	S	TO-252 (SMT)
MAC4DLM1	MOTOROLA	L6004V5	S	TO-251 (N.ISOL)
MAC4DSM	MOTOROLA	Q6006DH3	S	TO-252 (SMT)
MAC4DSM1	MOTOROLA	Q6006VH3	S	TO-251 (N.ISOL)
MAC4DSN	MOTOROLA	Q8006DH4	S	TO-252 (SMT)
MAC4DSN1	MOTOROLA	Q8006VH4	S	TO-251 (N.ISOL)
MAC50-4	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50-5	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50-6	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50-7	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50-8	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50-9	MOTOROLA	Q8035P5	S	FASTPAK (ISOL)
MAC50A4	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50A5	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50A6	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50A7	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50A8	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC50A9	MOTOROLA	Q8035P5	S	FASTPAK (ISOL)
MAC515-10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC515-4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515-5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515-6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515-7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515-8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515-9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC515A10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC515A4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515A5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515A6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515A7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515A8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC515A9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC525-10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC525-4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525-5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525-6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525-7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525-8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525-9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC525A10	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC525A4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525A5	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525A6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525A7	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC525A8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC525A9	MOTOROLA	Q8025P5	S	FASTPAK (ISOL)
MAC625-4	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC625-6	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC625-8	MOTOROLA	Q6025P5	S	FASTPAK (ISOL)
MAC635-4	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC635-6	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC635-8	MOTOROLA	Q6035P5	S	FASTPAK (ISOL)
MAC8D	MOTOROLA	Q4008RH4	D	TO-220 (N.ISOL)
MAC8M	MOTOROLA	Q6008RH4	D	TO-220 (N.ISOL)
MAC8N	MOTOROLA	Q8008RH4	D	TO-220 (N.ISOL)
MAC91-1	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC91-2	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC91-3	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC91-4	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC91-5	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC91-6	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC91-7	MOTOROLA	Q6X8E3	D	TO-92 (ISOL)
MAC91-8	MOTOROLA	Q6X8E3	D	TO-92 (ISOL)
MAC91A1	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC91A2	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC91A3	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC91A4	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC91A5	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC91A6	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC91A7	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC91A8	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC92-1	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC92-2	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC92-3	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC92-4	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC92-5	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC92-6	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC92-7	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC92-8	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC92A1	MOTOROLA	LX803DE	S	TO-92 (ISOL)
MAC92A2	MOTOROLA	LX803DE	S	TO-92 (ISOL)
MAC92A3	MOTOROLA	LX803DE	S	TO-92 (ISOL)
MAC92A4	MOTOROLA	LX803DE	S	TO-92 (ISOL)
MAC92A5	MOTOROLA	LX803DE	S	TO-92 (ISOL)
MAC92A6	MOTOROLA	LX803DE	S	TO-92 (ISOL)
MAC92A7	MOTOROLA	LX803ME	S	TO-92 (ISOL)
MAC92A8	MOTOROLA	LX803ME	S	TO-92 (ISOL)
MAC93-1	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC93-2	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC93-3	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC93-4	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC93-5	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC93-6	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC93-7	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC93-8	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC93A1	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC93A2	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC93A3	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC93A4	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC93A5	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC93A6	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC93A7	MOTOROLA	L6X8E3	D	TO-92 (ISOL)
MAC93A8	MOTOROLA	L6X8E3	D	TO-92 (ISOL)
MAC94-1	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC94-2	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC94-3	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC94-4	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC94-5	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC94-6	MOTOROLA	Q4X8E3	D	TO-92 (ISOL)
MAC94-7	MOTOROLA	Q6X8E3	D	TO-92 (ISOL)
MAC94-8	MOTOROLA	Q6X8E3	D	TO-92 (ISOL)
MAC94A1	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC94A2	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC94A3	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC94A4	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC94A5	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC94A6	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC94A7	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC94A8	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC95-1	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC95-2	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC95-3	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC95-4	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC95-5	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC95-6	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC95-7	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC95-8	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC95A1	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC95A2	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC95A3	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC95A4	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC95A5	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC95A6	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC95A7	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC95A8	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC96-1	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC96-2	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC96-3	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC96-4	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC96-5	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC96-6	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC96-7	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC96-8	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC96A1	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC96A2	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC96A3	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC96A4	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC96A5	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC96A6	MOTOROLA	L4X8E3	D	TO-92 (ISOL)
MAC96A7	MOTOROLA	L6X8E3	D	TO-92 (ISOL)
MAC96A8	MOTOROLA	L6X8E3	D	TO-92 (ISOL)
MAC97-2	MOTOROLA	L4X8E6	D	TO-92 (ISOL)
MAC97-3	MOTOROLA	L4X8E6	D	TO-92 (ISOL)
MAC97-4	MOTOROLA	L4X8E6	D	TO-92 (ISOL)
MAC97-5	MOTOROLA	L4X8E6	D	TO-92 (ISOL)
MAC97-6	MOTOROLA	L4X8E6	D	TO-92 (ISOL)
MAC97-7	MOTOROLA	L6X8E6	D	TO-92 (ISOL)
MAC97-8	MOTOROLA	L6X8E6	D	TO-92 (ISOL)
MAC97A2	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC97A3	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC97A4	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC97A5	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC97A6	MOTOROLA	LX807DE	D	TO-92 (ISOL)
MAC97A7	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC97A8	MOTOROLA	LX807ME	D	TO-92 (ISOL)
MAC97B2	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC97B3	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC97B4	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC97B5	MOTOROLA	LX803DE	D	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MAC97B6	MOTOROLA	LX803DE	D	TO-92 (ISOL)
MAC97B7	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC97B8	MOTOROLA	LX803ME	D	TO-92 (ISOL)
MAC9D	MOTOROLA	Q4008RH4	S	TO-220 (N.ISOL)
MAC9M	MOTOROLA	Q6008RH4	S	TO-220 (N.ISOL)
MAC9N	MOTOROLA	Q8008RH4	S	TO-220 (N.ISOL)
MCR08BT1	MOTOROLA	S4X8TS	D	SOT-223 (SMT)
MCR08DT1	MOTOROLA	S4X8TS	D	SOT-223 (SMT)
MCR08MT1	MOTOROLA	S4X8TS	D	SOT-223 (SMT)
MCR100-3	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR100-4	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR100-5	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR100-6	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR100-7	MOTOROLA	S6X8ES	D	TO-92 (ISOL)
MCR100-8	MOTOROLA	S6X8ES	D	TO-92 (ISOL)
MCR101	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR102	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR103	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR106-1	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR106-2	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR106-3	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR106-4	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR106-5	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR106-6	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR106-7	MOTOROLA	S6006LS2	S	TO-220 (ISOL)
MCR106-8	MOTOROLA	S6006LS2	S	TO-220 (ISOL)
MCR115	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR120	MOTOROLA	S4X8ES	D	TO-92 (ISOL)
MCR12DSM	MOTOROLA	S6010DS2	S	TO-252 (SMT)
MCR12DSM1	MOTOROLA	S6010VS2	S	TO-251 (N.ISOL)
MCR12M	MOTOROLA	S6012R	S	TO-220 (N.ISOL)
MCR12N	MOTOROLA	S8012R	S	TO-220 (N.ISOL)
MCR16D	MOTOROLA	S4016R	S	TO-220 (N.ISOL)
MCR16M	MOTOROLA	S6016R	S	TO-220 (N.ISOL)
MCR16N	MOTOROLA	S8016R	S	TO-220 (N.ISOL)
MCR202	MOTOROLA	S4X8ES	S	TO-92 (ISOL)
MCR203	MOTOROLA	S4X8ES	S	TO-92 (ISOL)
MCR204	MOTOROLA	S4X8ES	S	TO-92 (ISOL)
MCR206	MOTOROLA	S4X8ES	S	TO-92 (ISOL)
MCR218-10FP	MOTOROLA	S8008L	D	TO-220 (ISOL)
MCR218-2	MOTOROLA	S4008R	D	TO-220 (N.ISOL)
MCR218-2FP	MOTOROLA	S4008L	D	TO-220 (ISOL)
MCR218-3	MOTOROLA	S4008R	D	TO-220 (N.ISOL)
MCR218-3FP	MOTOROLA	S4008L	D	TO-220 (ISOL)
MCR218-4	MOTOROLA	S4008R	D	TO-220 (N.ISOL)
MCR218-4FP	MOTOROLA	S4008L	D	TO-220 (ISOL)
MCR218-5	MOTOROLA	S4008R	D	TO-220 (N.ISOL)
MCR218-6	MOTOROLA	S4008R	D	TO-220 (N.ISOL)
MCR218-6FP	MOTOROLA	S4008L	D	TO-220 (ISOL)
MCR218-7	MOTOROLA	S6008R	D	TO-220 (N.ISOL)
MCR218-8	MOTOROLA	S6008R	D	TO-220 (N.ISOL)
MCR218-8FP	MOTOROLA	S6008L	D	TO-220 (ISOL)
MCR220-5	MOTOROLA	S4012R	D	TO-220 (N.ISOL)
MCR220-7	MOTOROLA	S6012R	D	TO-220 (N.ISOL)
MCR220-9	MOTOROLA	S8012R	D	TO-220 (N.ISOL)
MCR22-1	MOTOROLA	S402ES	S	TO-92 (ISOL)
MCR221-5	MOTOROLA	S4016R	D	TO-220 (N.ISOL)
MCR221-7	MOTOROLA	S6016R	D	TO-220 (N.ISOL)
MCR221-9	MOTOROLA	S8016R	D	TO-220 (N.ISOL)
MCR22-2	MOTOROLA	S402ES	D	TO-92 (ISOL)
MCR22-3	MOTOROLA	S402ES	D	TO-92 (ISOL)
MCR22-4	MOTOROLA	S402ES	D	TO-92 (ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MCR225-10FP	MOTOROLA	S8025L	S	TO-220 (ISOL)
MCR225-2FP	MOTOROLA	S4025L	S	TO-220 (ISOL)
MCR225-4FP	MOTOROLA	S4025L	S	TO-220 (ISOL)
MCR225-5	MOTOROLA	S4025R	S	TO-220 (N.ISOL)
MCR225-6FP	MOTOROLA	S4025L	S	TO-220 (ISOL)
MCR225-7	MOTOROLA	S6025R	S	TO-220 (N.ISOL)
MCR225-8FP	MOTOROLA	S6025L	S	TO-220 (ISOL)
MCR225-9	MOTOROLA	S8025R	S	TO-220 (N.ISOL)
MCR22-5	MOTOROLA	S402ES	D	TO-92 (ISOL)
MCR22-6	MOTOROLA	S402ES	D	TO-92 (ISOL)
MCR22-7	MOTOROLA	S602ES	D	TO-92 (ISOL)
MCR22-8	MOTOROLA	S602ES	D	TO-92 (ISOL)
MCR25D	MOTOROLA	S4025R	D	TO-220 (N.ISOL)
MCR25M	MOTOROLA	S6025R	D	TO-220 (N.ISOL)
MCR25N	MOTOROLA	S8025R	D	TO-220 (N.ISOL)
MCR264-10	MOTOROLA	S8040R	D	TO-220 (N.ISOL)
MCR264-2	MOTOROLA	S4040R	D	TO-220 (N.ISOL)
MCR264-3	MOTOROLA	S4040R	D	TO-220 (N.ISOL)
MCR264-4	MOTOROLA	S4040R	D	TO-220 (N.ISOL)
MCR264-6	MOTOROLA	S4040R	D	TO-220 (N.ISOL)
MCR264-8	MOTOROLA	S6040R	D	TO-220 (N.ISOL)
MCR265-10	MOTOROLA	S8055R	D	TO-220 (N.ISOL)
MCR265-2	MOTOROLA	S4055R	D	TO-220 (N.ISOL)
MCR265-3	MOTOROLA	S4055R	D	TO-220 (N.ISOL)
MCR265-4	MOTOROLA	S4055R	D	TO-220 (N.ISOL)
MCR265-6	MOTOROLA	S4055R	D	TO-220 (N.ISOL)
MCR265-8	MOTOROLA	S6055R	D	TO-220 (N.ISOL)
MCR3000-1	MOTOROLA	S4008R	S	TO-220 (N.ISOL)
MCR3000-10	MOTOROLA	S8008R	S	TO-220 (N.ISOL)
MCR3000-2	MOTOROLA	S4008R	S	TO-220 (N.ISOL)
MCR3000-3	MOTOROLA	S4008R	S	TO-220 (N.ISOL)
MCR3000-4	MOTOROLA	S4008R	S	TO-220 (N.ISOL)
MCR3000-5	MOTOROLA	S4008R	S	TO-220 (N.ISOL)
MCR3000-6	MOTOROLA	S4008R	S	TO-220 (N.ISOL)
MCR3000-7	MOTOROLA	S6008R	S	TO-220 (N.ISOL)
MCR3000-8	MOTOROLA	S6008R	S	TO-220 (N.ISOL)
MCR3000-9	MOTOROLA	S8008R	S	TO-220 (N.ISOL)
MCR310-1	MOTOROLA	S4010LS2	S	TO-220 (ISOL)
MCR310-2	MOTOROLA	S4010LS2	S	TO-220 (ISOL)
MCR310-3	MOTOROLA	S4010LS2	S	TO-220 (ISOL)
MCR310-4	MOTOROLA	S4010LS2	S	TO-220 (ISOL)
MCR310-5	MOTOROLA	S4010LS2	S	TO-220 (ISOL)
MCR310-6	MOTOROLA	S4010LS2	S	TO-220 (ISOL)
MCR310-7	MOTOROLA	S6010LS2	S	TO-220 (ISOL)
MCR310-8	MOTOROLA	S6010LS2	S	TO-220 (ISOL)
MCR506-1	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR506-2	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR506-3	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR506-4	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR506-6	MOTOROLA	S4006LS2	S	TO-220 (ISOL)
MCR506-8	MOTOROLA	S6006LS2	S	TO-220 (ISOL)
MCR525-1	MOTOROLA	S4035J	S	TO-218 (ISOL)
MCR525-2	MOTOROLA	S4035J	S	TO-218 (ISOL)
MCR525-3	MOTOROLA	S4035J	S	TO-218 (ISOL)
MCR525-6	MOTOROLA	S4035J	S	TO-218 (ISOL)
MCR68-1	MOTOROLA	S4012R	D	TO-220 (N.ISOL)
MCR68-2	MOTOROLA	S4012R	D	TO-220 (N.ISOL)
MCR68-3	MOTOROLA	S4012R	D	TO-220 (N.ISOL)
MCR68-6	MOTOROLA	S4012R	D	TO-220 (N.ISOL)
MCR69-1	MOTOROLA	S4025R	D	TO-220 (N.ISOL)
MCR69-2	MOTOROLA	S4025R	D	TO-220 (N.ISOL)
MCR69-3	MOTOROLA	S4025R	D	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
MCR69-6	MOTOROLA	S4025R	D	TO-220 (N.ISOL)
MCR704A	MOTOROLA	S4004DS2	S	TO-252 (SMT)
MCR704A1	MOTOROLA	S4004VS2	S	TO-251 (N.ISOL)
MCR706A	MOTOROLA	S4004DS2	S	TO-252 (SMT)
MCR706A1	MOTOROLA	S4004VS2	S	TO-251 (N.ISOL)
MCR708A	MOTOROLA	S6004DS2	S	TO-252 (SMT)
MCR708A1	MOTOROLA	S6004VS2	S	TO-251 (N.ISOL)
MCR716	MOTOROLA	S4004DS1	D	TO-252 (SMT)
MCR718	MOTOROLA	S6004DS1	D	TO-252 (SMT)
MCR72-1	MOTOROLA	S4008LS2	S	TO-220 (ISOL)
MCR72-2	MOTOROLA	S4008LS2	S	TO-220 (ISOL)
MCR72-3	MOTOROLA	S4008LS2	S	TO-220 (ISOL)
MCR72-4	MOTOROLA	S4008LS2	S	TO-220 (ISOL)
MCR72-5	MOTOROLA	S4008LS2	S	TO-220 (ISOL)
MCR72-6	MOTOROLA	S4008LS2	S	TO-220 (ISOL)
MCR72-7	MOTOROLA	S6008LS2	S	TO-220 (ISOL)
MCR72-8	MOTOROLA	S6008LS2	S	TO-220 (ISOL)
MCR8DCM	MOTOROLA	S6008D	D	TO-252 (SMT)
MCR8DCM1	MOTOROLA	S6008V	D	TO-251 (N.ISOL)
MCR8DCN	MOTOROLA	S8008D	D	TO-252 (SMT)
MCR8DCN1	MOTOROLA	S8008V	D	TO-251 (N.ISOL)
MCR8DSM	MOTOROLA	S6008DS2	D	TO-252 (SMT)
MCR8DSM1	MOTOROLA	S6008VS2	D	TO-251 (N.ISOL)
MCR8SD	MOTOROLA	S4008FS21	S	TO-202 (N.ISOL)
MCR8SM	MOTOROLA	S6008FS21	S	TO-202 (N.ISOL)
MK1V115	MOTOROLA	K1100G	S	DO-15X (AXIAL)
MK1V125	MOTOROLA	K1200G	S	DO-15X (AXIAL)
MK1V135	MOTOROLA	K1300G	S	DO-15X (AXIAL)
MK1V240	MOTOROLA	K2400G	S	DO-15X (AXIAL)
MK1V260	MOTOROLA	K2500G	S	DO-15X (AXIAL)
MK1V270	MOTOROLA	K2500G	S	DO-15X (AXIAL)
MK1V280	MOTOROLA	K2500G	S	DO-15X (AXIAL)
MKP1V120	MOTOROLA	K1200E70	S	TO-92 (ISOL)
MKP1V130	MOTOROLA	K1300E70	S	TO-92 (ISOL)
MKP1V240	MOTOROLA	K2400E70	S	TO-92 (ISOL)
MKP3V110	MOTOROLA	K1100G	S	DO-15X (AXIAL)
MKP3V120	MOTOROLA	K1200G	S	DO-15X (AXIAL)
MKP3V130	MOTOROLA	K1300G	S	DO-15X (AXIAL)
MKP9V120	MOTOROLA	K1200E70	S	TO-92 (ISOL)
MKP9V130	MOTOROLA	K1300E70	S	TO-92 (ISOL)
MKP9V240	MOTOROLA	K2400E70	S	TO-92 (ISOL)
MKP9V260	MOTOROLA	K2500E70	S	TO-92 (ISOL)
MKP9V270	MOTOROLA	K2500E70	S	TO-92 (ISOL)
MN611A		K1050E70	S	TO-92 (ISOL)
P0100AA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0100AB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0100BA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0100BB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0100CA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0100CB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0100DA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0100DB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0101AA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0101AB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0101BA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0101BB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0101CA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0101CB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0101DA	TAG	S4X8ES1	D	TO-92 (ISOL)
P0101DB	TAG	S4X8ES1	S	TO-92 (ISOL)
P0102AA	TAG	S4X8ES	D	TO-92 (ISOL)
P0102AB	TAG	S4X8ES	S	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
P0102AD	TAG	S4X8ES	S	TO-92 (ISOL)
P0102AN	TAG	S4X8TS	D	SOT-223 (SMT)
P0102BA	TAG	S4X8ES	D	TO-92 (ISOL)
P0102BB	TAG	S4X8ES	S	TO-92 (ISOL)
P0102BD	TAG	S4X8ES	S	TO-92 (ISOL)
P0102BN	TAG	S4X8TS	D	SOT-223 (SMT)
P0102CA	TAG	S4X8ES	D	TO-92 (ISOL)
P0102CB	TAG	S4X8ES	S	TO-92 (ISOL)
P0102CD	TAG	S4X8ES	S	TO-92 (ISOL)
P0102CN	TAG	S4X8TS	D	SOT-223 (SMT)
P0102DA	TAG	S4X8ES	D	TO-92 (ISOL)
P0102DB	TAG	S4X8ES	S	TO-92 (ISOL)
P0102DD	TAG	S4X8ES	S	TO-92 (ISOL)
P0102DN	TAG	S4X8TS	D	SOT-223 (SMT)
P0103AA	TAG	S4X8ES	D	TO-92 (ISOL)
P0103AB	TAG	S4X8ES	S	TO-92 (ISOL)
P0103BA	TAG	S4X8ES	D	TO-92 (ISOL)
P0103BB	TAG	S4X8ES	S	TO-92 (ISOL)
P0103CA	TAG	S4X8ES	D	TO-92 (ISOL)
P0103CB	TAG	S4X8ES	S	TO-92 (ISOL)
P0103DA	TAG	S4X8ES	D	TO-92 (ISOL)
P0103DB	TAG	S4X8ES	S	TO-92 (ISOL)
P0104AA	TAG	EC103D2	D	TO-92 (ISOL)
P0104AB	TAG	EC103D2	S	TO-92 (ISOL)
P0104BA	TAG	EC103D2	D	TO-92 (ISOL)
P0104BB	TAG	EC103D2	S	TO-92 (ISOL)
P0104CA	TAG	EC103D2	D	TO-92 (ISOL)
P0104CB	TAG	EC103D2	S	TO-92 (ISOL)
P0104DA	TAG	EC103D2	D	TO-92 (ISOL)
P0104DB	TAG	EC103D2	S	TO-92 (ISOL)
P0105AA	TAG	EC103D2	S	TO-92 (ISOL)
P0105AB	TAG	EC103D2	S	TO-92 (ISOL)
P0105BA	TAG	EC103D2	S	TO-92 (ISOL)
P0105BB	TAG	EC103D2	S	TO-92 (ISOL)
P0105CA	TAG	EC103D2	S	TO-92 (ISOL)
P0105CB	TAG	EC103D2	S	TO-92 (ISOL)
P0105DA	TAG	EC103D2	S	TO-92 (ISOL)
P0105DB	TAG	EC103D2	S	TO-92 (ISOL)
P0110AA	TAG	EC103D1	S	TO-92 (ISOL)
P0110AB	TAG	EC103D1	S	TO-92 (ISOL)
P0110BA	TAG	EC103D1	S	TO-92 (ISOL)
P0110BB	TAG	EC103D2	S	TO-92 (ISOL)
P0110CA	TAG	EC103D2	S	TO-92 (ISOL)
P0110CB	TAG	EC103D1	S	TO-92 (ISOL)
P0110DA	TAG	EC103D1	S	TO-92 (ISOL)
P0110DB	TAG	EC103D1	S	TO-92 (ISOL)
P0111AN	STMicro	S4X8TS1	S	SOT-223 (SMT)
P0111BN	STMicro	S4X8TS1	S	SOT-223 (SMT)
P0111CN	STMicro	S4X8TS1	S	SOT-223 (SMT)
P0111DN	STMicro	S4X8TS1	S	SOT-223 (SMT)
Q2015L9	TECCOR	Q4016LH6	D	TO-220 (ISOL)
Q2015R9	TECCOR	Q4016RH6	D	TO-220 (N.ISOL)
Q2025L9	TECCOR	Q4025L6	S	TO-220 (ISOL)
Q2025R9	TECCOR	Q4025R6	S	TO-220 (N.ISOL)
Q2040J9	TECCOR	Q4040J7	D	TO-218X (ISOL)
Q2040K9	TECCOR	Q4040K7	D	TO-218AC (ISOL)
Q4015L9	TECCOR	Q4016LH6	D	TO-220 (ISOL)
Q4015R9	TECCOR	Q4016RH6	D	TO-220 (N.ISOL)
Q4025L9	TECCOR	Q4025L6	S	TO-220 (ISOL)
Q4025R9	TECCOR	Q4025R6	S	TO-220 (N.ISOL)
Q4040J9	TECCOR	Q4040J7	D	TO-218X (ISOL)
Q4040K9	TECCOR	Q4040K7	D	TO-218AC (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
Q5015L9	TECCOR	Q6016LH6	D	TO-220 (ISOL)
Q5015R9	TECCOR	Q6016RH6	D	TO-220 (N.ISOL)
Q5025L9	TECCOR	Q6025L6	S	TO-220 (ISOL)
Q5025R9	TECCOR	Q6025R6	S	TO-220 (N.ISOL)
Q5040J9	TECCOR	Q6040J7	D	TO-218X (ISOL)
Q5040K9	TECCOR	Q6040K7	D	TO-218AC (ISOL)
Q6015L9	TECCOR	Q6016LH6	D	TO-220 (ISOL)
Q6015R9	TECCOR	Q6016RH6	D	TO-220 (N.ISOL)
Q6025L9	TECCOR	Q6025L6	S	TO-220 (ISOL)
Q6025R9	TECCOR	Q6025R6	S	TO-220 (N.ISOL)
Q6040J9	TECCOR	Q6040J7	D	TO-218X (ISOL)
Q6040K9	TECCOR	Q6040K7	D	TO-218AC (ISOL)
Q7015L9	TECCOR	Q8016LH6	D	TO-220 (ISOL)
Q7015R9	TECCOR	Q8016RH6	D	TO-220 (N.ISOL)
Q7025L9	TECCOR	Q8025L6	S	TO-220 (ISOL)
Q7025R9	TECCOR	Q8025R6	S	TO-220 (N.ISOL)
Q7040J9	TECCOR	Q8040J7	D	TO-218X (ISOL)
Q7040K9	TECCOR	Q8040K7	D	TO-218AC (ISOL)
Q8015L9	TECCOR	Q8016LH6	D	TO-220 (ISOL)
Q8015R9	TECCOR	Q8016RH6	D	TO-220 (N.ISOL)
Q8025L9	TECCOR	Q8025L6	S	TO-220 (ISOL)
Q8025R9	TECCOR	Q8025R6	S	TO-220 (N.ISOL)
Q8040J9	TECCOR	Q8040J7	D	TO-218X (ISOL)
Q8040K9	TECCOR	Q8040K7	D	TO-218AC (ISOL)
Q2004N31	TECCOR	Q4004L3	S	TO-220 (ISOL)
Q4004N31	TECCOR	Q4004L3	S	TO-220 (ISOL)
Q2004N41	TECCOR	Q4004L4	S	TO-220 (ISOL)
Q4004N41	TECCOR	Q4004L4	S	TO-220 (ISOL)
Q5004N41	TECCOR	Q6004L4	S	TO-220 (ISOL)
Q6004N41	TECCOR	Q6004L4	S	TO-220 (ISOL)
S0402BH	STMicro	S4004VS2	S	TO-251 (N.ISOL)
S0402DH	STMicro	S4004VS2	S	TO-251 (N.ISOL)
S0402MH	STMicro	S6004VS2	S	TO-251 (N.ISOL)
S0405BH	TAG	S4006L	D	TO-220 (ISOL)
S0405DH	TAG	S4006L	D	TO-220 (ISOL)
S0405MH	TAG	S6006L	D	TO-220 (ISOL)
S0406BH	STMicro	S4006L	S	TO-220 (ISOL)
S0406DH	STMicro	S4006L	S	TO-220 (ISOL)
S0406MH	STMicro	S6006L	S	TO-220 (ISOL)
S0406NH	STMicro	S8006L	S	TO-220 (ISOL)
S0407BH	TAG	S4006L	S	TO-220 (ISOL)
S0407DH	TAG	S4006L	S	TO-220 (ISOL)
S0407MH	TAG	S6006L	S	TO-220 (ISOL)
S0410BH	TAG	S4006L	S	TO-220 (ISOL)
S0410DH	TAG	S4006L	S	TO-220 (ISOL)
S0410MH	TAG	S6006L	S	TO-220 (ISOL)
S0410NH	TAG	S8006L	S	TO-220 (ISOL)
S0417BH	STMicro	S4006L	S	TO-220 (ISOL)
S0417DH	STMicro	S4006L	S	TO-220 (ISOL)
S0417MH	STMicro	S6006L	S	TO-220 (ISOL)
S0417NH	STMicro	S8006L	S	TO-220 (ISOL)
S0602BH	TAG	S4006LS2	S	TO-220 (ISOL)
S0602DH	TAG	S4006LS2	S	TO-220 (ISOL)
S0602MH	TAG	S6006LS2	S	TO-220 (ISOL)
S0605BH	TAG	S4006L	S	TO-220 (ISOL)
S0605DH	TAG	S4006L	S	TO-220 (ISOL)
S0605MH	TAG	S6006L	S	TO-220 (ISOL)
S0606BH	STMicro	S4006L	S	TO-220 (ISOL)
S0606DH	STMicro	S4006L	S	TO-220 (ISOL)
S0606MH	STMicro	S6006L	S	TO-220 (ISOL)
S0606NH	STMicro	S8006L	S	TO-220 (ISOL)
S0607BH	TAG	S4006L	S	TO-220 (ISOL)

Teccor® brand Thyristors

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Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
S0607DH	TAG	S4006L	S	TO-220 (ISOL)
S0607MH	TAG	S6006L	S	TO-220 (ISOL)
S0610BH	STMicro	S4006L	S	TO-220 (ISOL)
S0610DH	STMicro	S4006L	S	TO-220 (ISOL)
S0610MH	STMicro	S6006L	S	TO-220 (ISOL)
S0610NH	STMicro	S8006L	S	TO-220 (ISOL)
S0617BH	STMicro	S4006L	S	TO-220 (ISOL)
S0617DH	STMicro	S4006L	S	TO-220 (ISOL)
S0617MH	STMicro	S6006L	S	TO-220 (ISOL)
S0617NH	STMicro	S8006L	S	TO-220 (ISOL)
S0802BH	STMicro	S4008LS2	S	TO-220 (ISOL)
S0802DH	STMicro	S4008LS2	S	TO-220 (ISOL)
S0802MH	STMicro	S6008LS2	S	TO-220 (ISOL)
S0805BH	TAG	S4008R	S	TO-220 (N.ISOL)
S0805DH	TAG	S4008R	S	TO-220 (N.ISOL)
S0805MH	TAG	S6008R	S	TO-220 (N.ISOL)
S0805NH	TAG	S8008R	S	TO-220 (N.ISOL)
S0806DH	STMicro	S4008R	S	TO-220 (N.ISOL)
S0806MH	STMicro	S6008R	S	TO-220 (N.ISOL)
S0806NH	STMicro	S8008R	S	TO-220 (N.ISOL)
S0807BH	TAG	S4008R	S	TO-220 (N.ISOL)
S0807DH	TAG	S4008R	S	TO-220 (N.ISOL)
S0807MH	TAG	S6008R	S	TO-220 (N.ISOL)
S0807NH	TAG	S8008R	S	TO-220 (N.ISOL)
S0810BH	STMicro	S4008R	S	TO-220 (N.ISOL)
S0810DH	STMicro	S4008R	S	TO-220 (N.ISOL)
S0810MH	STMicro	S6008R	S	TO-220 (N.ISOL)
S0810NH	STMicro	S8008R	S	TO-220 (N.ISOL)
S0817BH	STMicro	S4008R	S	TO-220 (N.ISOL)
S0817DH	STMicro	S4008R	S	TO-220 (N.ISOL)
S0817MH	STMicro	S6008R	S	TO-220 (N.ISOL)
S0817NH	STMicro	S8008R	S	TO-220 (N.ISOL)
S08M02100A	LITEON	S4X8ES	S	TO-92 (ISOL)
S08M02200A	LITEON	S4X8ES	S	TO-92 (ISOL)
S08M02200D	LITEON	S4X8TS	D	SOT-223 (SMT)
S08M02400A	LITEON	S4X8ES	D	TO-92 (ISOL)
S08M02600A	LITEON	S6X8ES	D	TO-92 (ISOL)
S08M02600D	LITEON	S6X8TS	D	SOT-223 (SMT)
S1M02100A	LITEON	S402ES	S	TO-92 (ISOL)
S1M02200A	LITEON	S402ES	S	TO-92 (ISOL)
S1M02400A	LITEON	S402ES	S	TO-92 (ISOL)
S1M02600A	LITEON	S602ES	S	TO-92 (ISOL)
S1005BH	TAG	S4010R	S	TO-220 (N.ISOL)
S1005DH	TAG	S4010R	S	TO-220 (N.ISOL)
S1005MH	TAG	S6010R	S	TO-220 (N.ISOL)
S1006BH	STMicro	S4010R	S	TO-220 (N.ISOL)
S1006DH	STMicro	S4010R	S	TO-220 (N.ISOL)
S1006MH	STMicro	S6010R	S	TO-220 (N.ISOL)
S1006NH	STMicro	S8010R	S	TO-220 (N.ISOL)
S1007BH	TAG	S4010R	S	TO-220 (N.ISOL)
S1007DH	TAG	S4010R	S	TO-220 (N.ISOL)
S1007MH	TAG	S6010R	S	TO-220 (N.ISOL)
S1010BH	STMicro	S4010R	S	TO-220 (N.ISOL)
S1010DH	STMicro	S4010R	S	TO-220 (N.ISOL)
S1010MH	STMicro	S6010R	S	TO-220 (N.ISOL)
S1010NH	STMicro	S8010R	S	TO-220 (N.ISOL)
S1017BH	STMicro	S4010R	S	TO-220 (N.ISOL)
S1017DH	STMicro	S4010R	S	TO-220 (N.ISOL)
S1017MH	STMicro	S6010R	S	TO-220 (N.ISOL)
S1017NH	STMicro	S8010R	S	TO-220 (N.ISOL)
S106A1	HUTSON	S4006LS2	S	TO-220 (ISOL)
S106B1	HUTSON	S4006LS2	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
S106C1	HUTSON	S4006LS2	S	TO-220 (ISOL)
S106D1	HUTSON	S4006LS2	S	TO-220 (ISOL)
S106E1	HUTSON	S6006LS2	S	TO-220 (ISOL)
S106F1	HUTSON	S4006LS2	S	TO-220 (ISOL)
S106M1	HUTSON	S6006LS2	S	TO-220 (ISOL)
S106Y1	HUTSON	S4006LS2	S	TO-220 (ISOL)
S107A1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S107B1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S107C1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S107D1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S107E1	HUTSON	S6006LS3	S	TO-220 (ISOL)
S107F1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S107M1	HUTSON	S6006LS3	S	TO-220 (ISOL)
S107Q1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S107Y1	HUTSON	S4006LS3	S	TO-220 (ISOL)
S1205BH	TAG	S4012R	S	TO-220 (N.ISOL)
S1205DH	TAG	S4012R	S	TO-220 (N.ISOL)
S1205MH	TAG	S6012R	S	TO-220 (N.ISOL)
S1206BH	STMicro	S4012R	S	TO-220 (N.ISOL)
S1206DH	STMicro	S4012R	S	TO-220 (N.ISOL)
S1206MH	STMicro	S6012R	S	TO-220 (N.ISOL)
S1206NH	STMicro	S8012R	S	TO-220 (N.ISOL)
S1207BH	TAG	S4012R	S	TO-220 (N.ISOL)
S1207DH	TAG	S4012R	S	TO-220 (N.ISOL)
S1207MH	TAG	S6012R	S	TO-220 (N.ISOL)
S1210BH	STMicro	S4012R	S	TO-220 (N.ISOL)
S1210DH	STMicro	S4012R	S	TO-220 (N.ISOL)
S1210MH	STMicro	S6012R	S	TO-220 (N.ISOL)
S1210NH	STMicro	S8012R	S	TO-220 (N.ISOL)
S1217BH	STMicro	S4012R	S	TO-220 (N.ISOL)
S1217DH	STMicro	S4012R	S	TO-220 (N.ISOL)
S1217MH	STMicro	S6012R	S	TO-220 (N.ISOL)
S1217NH	STMicro	S8012R	S	TO-220 (N.ISOL)
S12M15400B	LITEON	S4012R	S	TO-220 (N.ISOL)
S12M15600B	LITEON	S6012R	S	TO-220 (N.ISOL)
S12M15800B	LITEON	S8012R	S	TO-220 (N.ISOL)
S1610BH	TAG	S4016R	S	TO-220 (N.ISOL)
S1610DH	TAG	S4016R	S	TO-220 (N.ISOL)
S1610MH	TAG	S6016R	S	TO-220 (N.ISOL)
S1610NH	TAG	S8016R	S	TO-220 (N.ISOL)
S1612BH	TAG	S4016R	S	TO-220 (N.ISOL)
S1612DH	TAG	S4016R	S	TO-220 (N.ISOL)
S1612MH	TAG	S6016R	S	TO-220 (N.ISOL)
S1612NH	TAG	S8016R	S	TO-220 (N.ISOL)
S1616BH	STMicro	S4016R	S	TO-220 (N.ISOL)
S1616DH	STMicro	S4016R	S	TO-220 (N.ISOL)
S1616MH	STMicro	S6016R	S	TO-220 (N.ISOL)
S1616NH	STMicro	S8016R	S	TO-220 (N.ISOL)
S1A	HUTSON	EC103D	D	TO-92 (ISOL)
S1B	HUTSON	EC103D	D	TO-92 (ISOL)
S1D	HUTSON	EC103D	D	TO-92 (ISOL)
S1M	HUTSON	EC103M	D	TO-92 (ISOL)
S1Y	HUTSON	EC103D	D	TO-92 (ISOL)
S1YY	HUTSON	EC103D	D	TO-92 (ISOL)
S0304N1	TECCOR	S4006L	S	TO-202 (N.ISOL)
S0504N1	TECCOR	S4006L	S	TO-202 (N.ISOL)
S1004N1	TECCOR	S4006L	S	TO-202 (N.ISOL)
S2004N1	TECCOR	S4006L	S	TO-202 (N.ISOL)
S4004N1	TECCOR	S4006L	S	TO-202 (N.ISOL)
S6004N1	TECCOR	S6006L	S	TO-202 (N.ISOL)
S0304NS11	TECCOR	S4004VS1	S	TO-251 (N.ISOL)
S0304NS21	TECCOR	S4004VS2	S	TO-251 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
S0304NS31	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S0504NS11	TECCOR	S4004VS1	S	TO-251 (N.ISOL)
S0504NS21	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S0504NS31	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S1004NS11	TECCOR	S4004VS1	S	TO-251 (N.ISOL)
S1004NS21	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S1004NS31	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S2004NS11	TECCOR	S4004VS1	S	TO-251 (N.ISOL)
S2004NS21	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S2004NS31	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S2004NS11	TECCOR	S4004VS1	S	TO-251 (N.ISOL)
S4004NS21	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S4004NS31	TECCOR	S4004VS2	S	TO-251 (N.ISOL)
S2060A	GE	S4006LS2	S	TO-220 (ISOL)
S2060B	GE	S4006LS2	S	TO-220 (ISOL)
S2060C	GE	S4006LS2	S	TO-220 (ISOL)
S2060D	GE	S4006LS2	S	TO-220 (ISOL)
S2060E	GE	S6006LS2	S	TO-220 (ISOL)
S2060F	GE	S4006LS2	S	TO-220 (ISOL)
S2060M	GE	S6006LS2	S	TO-220 (ISOL)
S2060Y	GE	S4006LS2	S	TO-220 (ISOL)
S2061A	GE	S4006LS3	S	TO-220 (ISOL)
S2061B	GE	S4006LS3	S	TO-220 (ISOL)
S2061C	GE	S4006LS3	S	TO-220 (ISOL)
S2061D	GE	S4006LS3	S	TO-220 (ISOL)
S2061E	GE	S6006LS3	S	TO-220 (ISOL)
S2061F	GE	S4006LS3	S	TO-220 (ISOL)
S2061Q	GE	S4006LS3	S	TO-220 (ISOL)
S2061Y	GE	S4006LS3	S	TO-220 (ISOL)
S2062A	RCA	S4006LS3	S	TO-220 (ISOL)
S2062B	RCA	S4006LS3	S	TO-220 (ISOL)
S2062C	RCA	S4006LS3	S	TO-220 (ISOL)
S2062D	RCA	S4006LS3	S	TO-220 (ISOL)
S2062E	RCA	S6006LS3	S	TO-220 (ISOL)
S2062F	RCA	S4006LS3	S	TO-220 (ISOL)
S2062M	RCA	S6006LS3	S	TO-220 (ISOL)
S2062Q	RCA	S4006LS3	S	TO-220 (ISOL)
S2062Y	RCA	S4006LS3	S	TO-220 (ISOL)
S2512BH	TAG	S4025R	S	TO-220 (N.ISOL)
S2512BK	TAG	S4035J	S	TO-218 (ISOL)
S2512DH	TAG	S4025R	S	TO-220 (N.ISOL)
S2512DK	TAG	S4035J	S	TO-218 (ISOL)
S2512MH	TAG	S6025R	S	TO-220 (N.ISOL)
S2512MK	TAG	S6035J	S	TO-218 (ISOL)
S2512NH	TAG	S8025R	S	TO-220 (N.ISOL)
S2512NK	TAG	S8035J	S	TO-218 (ISOL)
S2514BH	STMicro	S4025R	S	TO-220 (N.ISOL)
S2514BK	TAG	S4035J	S	TO-218 (ISOL)
S2514DH	STMicro	S4025R	S	TO-220 (N.ISOL)
S2514DK	TAG	S4035J	S	TO-218 (ISOL)
S2514MH	STMicro	S6025R	S	TO-220 (N.ISOL)
S2514MK	TAG	S6035J	S	TO-218 (ISOL)
S2514NH	STMicro	S8025R	S	TO-220 (N.ISOL)
S2514NK	TAG	S8035J	S	TO-218 (ISOL)
S2516BH	STMicro	S4025R	S	TO-220 (N.ISOL)
S2516DH	STMicro	S4025R	S	TO-220 (N.ISOL)
S2516MH	STMicro	S6025R	S	TO-220 (N.ISOL)
S2516NH	STMicro	S8025R	S	TO-220 (N.ISOL)
S2600B	RCA	S4006L	S	TO-220 (ISOL)
S2600D	RCA	S4006L	S	TO-220 (ISOL)
S2600M	RCA	S6006L	S	TO-220 (ISOL)
S2800A	RCA	S4010R	D	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
S2800B	RCA	S4010R	D	TO-220 (N.ISOL)
S2800C	RCA	S4010R	S	TO-220 (N.ISOL)
S2800D	RCA	S4010R	D	TO-220 (N.ISOL)
S2800E	RCA	S6010R	S	TO-220 (N.ISOL)
S2800F	RCA	S4010R	D	TO-220 (N.ISOL)
S2800M	RCA	S6010R	D	TO-220 (N.ISOL)
S2800N	RCA	S8010R	D	TO-220 (N.ISOL)
S3014NH	STMicro	S8040R	S	TO-220 (N.ISOL)
S3016NH	STMicro	S8040R	S	TO-220 (N.ISOL)
S4012BH	TAG	S4040R	S	TO-220 (N.ISOL)
S4012BK	TAG	S4035J	S	TO-218 (ISOL)
S4012DH	TAG	S4040R	S	TO-220 (N.ISOL)
S4012DK	TAG	S4035J	S	TO-218 (ISOL)
S4012MH	TAG	S6040R	S	TO-220 (N.ISOL)
S4012MK	TAG	S6035J	S	TO-218 (ISOL)
S4012NH	TAG	S8040R	S	TO-220 (N.ISOL)
S4012NK	TAG	S8035J	S	TO-218 (ISOL)
S4014BH	STMicro	S4040R	S	TO-220 (N.ISOL)
S4014BK	TAG	S4035J	S	TO-218 (ISOL)
S4014DH	STMicro	S4040R	S	TO-220 (N.ISOL)
S4014DK	TAG	S4035J	S	TO-218 (ISOL)
S4014MH	STMicro	S6040R	S	TO-220 (N.ISOL)
S4014MK	TAG	S6035J	S	TO-218 (ISOL)
S4014NH	STMicro	S8040R	S	TO-220 (N.ISOL)
S4014NK	TAG	S8065J	S	TO-218 (ISOL)
S4016BH	STMicro	S4040R	S	TO-220 (N.ISOL)
S4016DH	STMicro	S4040R	S	TO-220 (N.ISOL)
S4016MH	STMicro	S6040R	S	TO-220 (N.ISOL)
S4016NH	STMicro	S8040R	S	TO-220 (N.ISOL)
S4060A	GE	S4010LS2	S	TO-220 (ISOL)
S4060B	GE	S4010LS2	S	TO-220 (ISOL)
S4060C	GE	S4010LS2	S	TO-220 (ISOL)
S4060D	GE	S4010LS2	S	TO-220 (ISOL)
S4060F	GE	S4010LS2	S	TO-220 (ISOL)
S4060U	GE	S4010LS2	S	TO-220 (ISOL)
S5800B	GE	S4008R	S	TO-220 (N.ISOL)
S5800C	GE	S4008R	S	TO-220 (N.ISOL)
S5800D	GE	S4008R	S	TO-220 (N.ISOL)
S5800E	GE	S6008R	S	TO-220 (N.ISOL)
S5800M	GE	S6008R	S	TO-220 (N.ISOL)
S8M02400B	LITEON	S4008LS2	S	TO-220 (ISOL)
S8M02600B	LITEON	S6008LS2	S	TO-220 (ISOL)
S8M02800B	LITEON	S6008LS2	S	TO-220 (ISOL)
S8M15400B	LITEON	S4008R	D	TO-220 (N.ISOL)
S8M15600B	LITEON	S6008R	D	TO-220 (N.ISOL)
S8M15800B	LITEON	S8008R	D	TO-220 (N.ISOL)
SC129B	GE	Q4025R5	D	TO-220 (N.ISOL)
SC129D	GE	Q4025R5	D	TO-220 (N.ISOL)
SC129E	GE	Q6025R5	D	TO-220 (N.ISOL)
SC129M	GE	Q6025R5	D	TO-220 (N.ISOL)
SC136A	GE	Q4004R4	S	TO-220 (N.ISOL)
SC136B	GE	Q4004R4	S	TO-220 (N.ISOL)
SC136C	GE	Q4004R4	S	TO-220 (N.ISOL)
SC136D	GE	Q4004R4	S	TO-220 (N.ISOL)
SC136E	GE	Q6004R4	S	TO-220 (N.ISOL)
SC136M	GE	Q6004R4	S	TO-220 (N.ISOL)
SC140B	GE	Q4006L4	D	TO-220 (ISOL)
SC140D	GE	Q4006L4	D	TO-220 (ISOL)
SC140E	GE	Q6006L5	S	TO-220 (ISOL)
SC140M	GE	Q6006L5	D	TO-220 (ISOL)
SC141A	GE	Q4006R4	S	TO-220 (N.ISOL)
SC141B	GE	Q4006R4	D	TO-220 (N.ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
SC141C	GE	Q4006R4	S	TO-220 (N.ISOL)
SC141D	GE	Q4006R4	D	TO-220 (N.ISOL)
SC141E	GE	Q6006R5	S	TO-220 (N.ISOL)
SC141M	GE	Q6006R5	D	TO-220 (N.ISOL)
SC141N	GE	Q8006R5	D	TO-220 (N.ISOL)
SC142B	GE	Q4008L4	D	TO-220 (ISOL)
SC142D	GE	Q4008L4	D	TO-220 (ISOL)
SC142E	GE	Q6008L5	S	TO-220 (ISOL)
SC142M	GE	Q6008L5	D	TO-220 (ISOL)
SC143B	GE	Q4008R4	D	TO-220 (N.ISOL)
SC143D	GE	Q4008R4	D	TO-220 (N.ISOL)
SC143E	GE	Q6008R5	S	TO-220 (N.ISOL)
SC143M	GE	Q6008R5	D	TO-220 (N.ISOL)
SC146B	GE	Q4010R5	D	TO-220 (N.ISOL)
SC146D	GE	Q4010R5	D	TO-220 (N.ISOL)
SC146E	GE	Q6010R5	D	TO-220 (N.ISOL)
SC146M	GE	Q6010R5	D	TO-220 (N.ISOL)
SC146N	GE	Q8010R5	D	TO-220 (N.ISOL)
SC147B	GE	Q4010L5	D	TO-220 (ISOL)
SC147D	GE	Q4010L5	D	TO-220 (ISOL)
SC147E	GE	Q6010L5	D	TO-220 (ISOL)
SC147M	GE	Q6010L5	D	TO-220 (ISOL)
SC148B	GE	Q4010L5	D	TO-220 (ISOL)
SC148D	GE	Q4010L5	D	TO-220 (ISOL)
SC148E	GE	Q6010L5	D	TO-220 (ISOL)
SC148M	GE	Q6010L5	D	TO-220 (ISOL)
SC149B	GE	Q4015R5	D	TO-220 (N.ISOL)
SC149D	GE	Q4015R5	D	TO-220 (N.ISOL)
SC149E	GE	Q6015R5	D	TO-220 (N.ISOL)
SC149M	GE	Q6015R5	D	TO-220 (N.ISOL)
SC150B	GE	Q4015L5	D	TO-220 (ISOL)
SC150D	GE	Q4015L5	D	TO-220 (ISOL)
SC150E	GE	Q6015L5	D	TO-220 (ISOL)
SC150M	GE	Q6015L5	D	TO-220 (ISOL)
SC151B	GE	Q4015R5	D	TO-220 (N.ISOL)
SC151D	GE	Q4015R5	D	TO-220 (N.ISOL)
SC151E	GE	Q6015R5	D	TO-220 (N.ISOL)
SC151M	GE	Q6015R5	D	TO-220 (N.ISOL)
SC160B	GE	Q6025P5	S	FASTPAK (ISOL)
SC160D	GE	Q6025P5	S	FASTPAK (ISOL)
SC160E	GE	Q6025P5	S	FASTPAK (ISOL)
SC160M	GE	Q6025P5	S	FASTPAK (ISOL)
SC92A	GE	Q401E3	D	TO-92 (ISOL)
SC92B	GE	Q401E3	D	TO-92 (ISOL)
SC92D	GE	Q401E3	D	TO-92 (ISOL)
SC92F	GE	Q401E3	D	TO-92 (ISOL)
SD3A120	LITEON	K1200G	S	DO-15X (AXIAL)
SD3A240	LITEON	K2400G	S	DO-15X (AXIAL)
SF0R1A42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R1B42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R1D42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R1G42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R3B42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R3D42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R3G42	TOSHIBA	S4X8ES	S	TO-92 (ISOL)
SF0R3J42	TOSHIBA	S6X8ES	S	TO-92 (ISOL)
SF0R5B43	TOSHIBA	S4X8ES	D	TO-92 (ISOL)
SF0R5D43	TOSHIBA	S4X8ES	D	TO-92 (ISOL)
SF0R5G43	TOSHIBA	S4X8ES	D	TO-92 (ISOL)
SF0R5H43	TOSHIBA	S4X8ES	D	TO-92 (ISOL)
SF0R5J43	TOSHIBA	S4X8ES	D	TO-92 (ISOL)
SF10D41A	TOSHIBA	S4016R	S	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
SF10G41A	TOSHIBA	S4016R	S	TO-220 (N.ISOL)
SF10J41A	TOSHIBA	S6016R	S	TO-220 (N.ISOL)
SF1B12	TOSHIBA	S402ES	S	TO-92 (ISOL)
SF1D12	TOSHIBA	S402ES	S	TO-92 (ISOL)
SF1G12	TOSHIBA	S402ES	S	TO-92 (ISOL)
SF3B41	TOSHIBA	S4006R	S	TO-220 (N.ISOL)
SF3B42	TOSHIBA	S4006LS2	S	TO-220 (ISOL)
SF3D41	TOSHIBA	S4006R	S	TO-220 (N.ISOL)
SF3D42	TOSHIBA	S4006LS2	S	TO-220 (ISOL)
SF3D42C	TOSHIBA	S4006LS2	S	TO-220 (ISOL)
SF3G41	TOSHIBA	S4006R	S	TO-220 (N.ISOL)
SF3G42	TOSHIBA	S4006LS2	S	TO-220 (ISOL)
SF3G42C	TOSHIBA	S4006LS2	S	TO-220 (ISOL)
SF3H42LC2	TOSHIBA	S6006LS2	S	TO-220 (ISOL)
SF3J41	TOSHIBA	S6006R	S	TO-220 (N.ISOL)
SF3J42	TOSHIBA	S6006LS2	S	TO-220 (ISOL)
SF5B41	TOSHIBA	S4008R	S	TO-220 (N.ISOL)
SF5B42	TOSHIBA	S4008LS2	S	TO-220 (ISOL)
SF5D41	TOSHIBA	S4008R	S	TO-220 (N.ISOL)
SF5D41A	TOSHIBA	S4012R	S	TO-220 (N.ISOL)
SF5D42	TOSHIBA	S4008LS2	S	TO-220 (ISOL)
SF5G41	TOSHIBA	S4008R	S	TO-220 (N.ISOL)
SF5G41A	TOSHIBA	S6012R	S	TO-220 (N.ISOL)
SF5G42	TOSHIBA	S4008LS2	S	TO-220 (ISOL)
SF5J41	TOSHIBA	S6008R	S	TO-220 (N.ISOL)
SF5J41A	TOSHIBA	S6012R	S	TO-220 (N.ISOL)
SF5J42	TOSHIBA	S6008LS2	S	TO-220 (ISOL)
SF8B41	TOSHIBA	S4012R	S	TO-220 (N.ISOL)
SF8D41	TOSHIBA	S4012R	S	TO-220 (N.ISOL)
SF8D41A	TOSHIBA	S4012R	S	TO-220 (N.ISOL)
SF8G41	TOSHIBA	S4012R	S	TO-220 (N.ISOL)
SF8G41A	TOSHIBA	S4012R	S	TO-220 (N.ISOL)
SF8J41	TOSHIBA	S6012R	S	TO-220 (N.ISOL)
SF8J41A	TOSHIBA	S6012R	S	TO-220 (N.ISOL)
SMG04C60	SANREX	S6X8ES	S	TO-92 (ISOL)
SMG05C60	SANREX	S6X8ES	S	TO-92 (ISOL)
SMG05C60A	SANREX	S6X8BS	S	SOT-89 (SMT)
SMG08C60A	SANREX	S6X8BS	S	SOT-89 (SMT)
SMG05CB60	SANREX	S6X8ES	S	TO-92 (ISOL)
SM0R5B42	TOSHIBA	LX807DE	S	TO-92 (ISOL)
SM0R5D42	TOSHIBA	LX807DE	S	TO-92 (ISOL)
SM0R5G42	TOSHIBA	LX807DE	S	TO-92 (ISOL)
SM12D41	TOSHIBA	Q4012RH5	S	TO-220 (N.ISOL)
SM12G41	TOSHIBA	Q4012RH5	S	TO-220 (N.ISOL)
SM12J41	TOSHIBA	Q6012RH5	S	TO-220 (N.ISOL)
SM16DZ41	TOSHIBA	Q6025P5	S	FASTPAK (ISOL)
SM16G45	TOSHIBA	Q4016RH4	S	TO-220 (N.ISOL)
SM16G45A	TOSHIBA	Q4016RH3	S	TO-220 (N.ISOL)
SM16GZ41	TOSHIBA	Q6025P5	S	FASTPAK (ISOL)
SM16GZ47	TOSHIBA	Q4016LH4	S	TO-220 (ISOL)
SM16GZ47A	TOSHIBA	Q4016LH3	S	TO-220 (ISOL)
SM16J45	TOSHIBA	Q6016RH4	S	TO-220 (N.ISOL)
SM16J45A	TOSHIBA	Q6016RH3	S	TO-220 (N.ISOL)
SM16JZ41	TOSHIBA	Q6025P5	S	FASTPAK (ISOL)
SM16JZ47	TOSHIBA	Q6016LH4	S	TO-220 (ISOL)
SM16JZ47A	TOSHIBA	Q6016LH3	S	TO-220 (ISOL)
SM1D43	TOSHIBA	L0107DE	D	TO-92 (ISOL)
SM1G43	TOSHIBA	L0107DE	D	TO-92 (ISOL)
SM1J43	TOSHIBA	L0107ME	D	TO-92 (ISOL)
SM25DZ41	TOSHIBA	Q6025P5	S	FASTPAK (ISOL)
SM25GZ41	TOSHIBA	Q6025P5	S	FASTPAK (ISOL)
SM25JZ41	TOSHIBA	Q6025P5	S	FASTPAK (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
SM2B41	TOSHIBA	Q4004R3	S	TO-220 (N.ISOL)
SM2D41	TOSHIBA	Q4004R3	S	TO-220 (N.ISOL)
SM2G41	TOSHIBA	Q4004R3	S	TO-220 (N.ISOL)
SM3B41	TOSHIBA	Q4004R4	S	TO-220 (N.ISOL)
SM3D41	TOSHIBA	Q4004R4	S	TO-220 (N.ISOL)
SM3G41	TOSHIBA	Q4004R4	S	TO-220 (N.ISOL)
SM3G45	TOSHIBA	Q4004L3	D	TO-220 (ISOL)
SM3GZ46	TOSHIBA	Q4004L3	S	TO-220 (ISOL)
SM3J41	TOSHIBA	Q6004R4	S	TO-220 (N.ISOL)
SM3J45	TOSHIBA	Q6004L3	D	TO-220 (ISOL)
SM3JZ46	TOSHIBA	Q6004L3	S	TO-220 (ISOL)
SM6D45	TOSHIBA	Q4006R4	S	TO-220 (N.ISOL)
SM6D45A	TOSHIBA	Q4006R4	S	TO-220 (N.ISOL)
SM6DZ46	TOSHIBA	Q4006L4	S	TO-220 (ISOL)
SM6DZ46A	TOSHIBA	Q4006L4	S	TO-220 (ISOL)
SM6G45	TOSHIBA	Q4006R4	S	TO-220 (N.ISOL)
SM6G45A	TOSHIBA	Q4006R4	S	TO-220 (N.ISOL)
SM6GZ46	TOSHIBA	Q4006L4	S	TO-220 (ISOL)
SM6GZ46A	TOSHIBA	Q4006L4	S	TO-220 (ISOL)
SM6GZ47	TOSHIBA	Q4006L4	S	TO-220 (ISOL)
SM6GZ47A	TOSHIBA	Q4006L4	S	TO-220 (ISOL)
SM6J45	TOSHIBA	Q6006R5	S	TO-220 (N.ISOL)
SM6J45A	TOSHIBA	Q6006R5	S	TO-220 (N.ISOL)
SM6JZ46	TOSHIBA	Q6006L5	S	TO-220 (ISOL)
SM6JZ46A	TOSHIBA	Q6006L5	S	TO-220 (ISOL)
SM6JZ47	TOSHIBA	Q6006L5	S	TO-220 (ISOL)
SM6JZ47A	TOSHIBA	Q6006L5	S	TO-220 (ISOL)
SM8D41	TOSHIBA	Q4008R4	D	TO-220 (N.ISOL)
SM8D45	TOSHIBA	Q4010R4	S	TO-220 (N.ISOL)
SM8D45A	TOSHIBA	L4008R8	S	TO-220 (N.ISOL)
SM8DZ46	TOSHIBA	Q4010L4	S	TO-220 (ISOL)
SM8DZ46A	TOSHIBA	L4008L8	S	TO-220 (ISOL)
SM8G41	TOSHIBA	Q4008R4	D	TO-220 (N.ISOL)
SM8G45	TOSHIBA	Q4010R4	S	TO-220 (N.ISOL)
SM8G45A	TOSHIBA	L4008R8	S	TO-220 (N.ISOL)
SM8GZ46	TOSHIBA	Q4010L4	S	TO-220 (ISOL)
SM8GZ46A	TOSHIBA	L4008L8	S	TO-220 (ISOL)
SM8GZ47	TOSHIBA	Q4008LH4	S	TO-220 (ISOL)
SM8GZ47A	TOSHIBA	Q4008LH4	S	TO-220 (ISOL)
SM8J41	TOSHIBA	Q6008R5	D	TO-220 (N.ISOL)
SM8J45	TOSHIBA	Q6010R4	S	TO-220 (N.ISOL)
SM8J45A	TOSHIBA	L6008R8	S	TO-220 (N.ISOL)
SM8JZ46	TOSHIBA	Q6010L4	S	TO-220 (ISOL)
SM8JZ46A	TOSHIBA	L6008L8	S	TO-220 (ISOL)
SM8JZ47	TOSHIBA	Q6008LH4	S	TO-220 (ISOL)
SM8JZ47A	TOSHIBA	Q6008LH4	S	TO-220 (ISOL)
ST2	GE	HT32	D	DO-35 (AXIAL)
T0505MH	TAG	L6006L5	S	TO-220 (ISOL)
T0509MH	TAG	L6006L6	S	TO-220 (ISOL)
T0510DH	TAG	L4006L8	S	TO-220 (ISOL)
T0510MH	TAG	L6006L8	S	TO-220 (ISOL)
T0605DH	TAG	L4006L5	S	TO-220 (ISOL)
T0605MH	TAG	L6006L5	S	TO-220 (ISOL)
T0609DH	TAG	L4006L6	S	TO-220 (ISOL)
T0609MH	TAG	L6006L6	S	TO-220 (ISOL)
T0612BH	TAG	Q4006R4	D	TO-220 (N.ISOL)
T0612DH	TAG	Q4006R4	D	TO-220 (N.ISOL)
T0612MH	TAG	Q6006R5	D	TO-220 (N.ISOL)
T0805DH	TAG	L4008L6	S	TO-220 (ISOL)
T0805MH	TAG	L6008L6	S	TO-220 (ISOL)
T0809DH	TAG	L4008L8	S	TO-220 (ISOL)
T0809MH	TAG	L6008L8	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T0810DH	TAG	Q4008R4	S	TO-220 (N.ISOL)
T0810MH	TAG	Q6008R5	S	TO-220 (N.ISOL)
T0810NH	TAG	Q8008R5	S	TO-220 (N.ISOL)
T0810SH	TAG	Q8008R5	S	TO-220 (N.ISOL)
T0812DH	TAG	Q4008R4	S	TO-220 (N.ISOL)
T0812MH	TAG	Q6008R5	S	TO-220 (N.ISOL)
T0812NH	TAG	Q8008R5	S	TO-220 (N.ISOL)
T0812SH	TAG	Q8008R5	S	TO-220 (N.ISOL)
T08M3F400A	LITEON	LX803DE	D	TO-92 (ISOL)
T08M3F600A	LITEON	LX803ME	D	TO-92 (ISOL)
T08M5F400A	LITEON	LX807DE	D	TO-92 (ISOL)
T08M5F600A	LITEON	LX807ME	D	TO-92 (ISOL)
T1M3F400A	LITEON	L0103DE	D	TO-92 (ISOL)
T1M3F600A	LITEON	L0103ME	D	TO-92 (ISOL)
T1M5F400A	LITEON	L0107DE	D	TO-92 (ISOL)
T1M5F400A	LITEON	L0107ME	D	TO-92 (ISOL)
T1M10F600D	LITEON	L0109MT	D	SOT-223 (SMT)
T1010BH	TAG	Q4010R5	S	TO-220 (N.ISOL)
T1010BJ	TAG	Q4010L5	D	TO-220 (ISOL)
T1010DH	TAG	Q4010R5	S	TO-220 (N.ISOL)
T1010DJ	TAG	Q4010L5	D	TO-220 (ISOL)
T1010MH	TAG	Q6010R5	S	TO-220 (N.ISOL)
T1010MJ	TAG	Q6010L5	D	TO-220 (ISOL)
T1010NH	TAG	Q8010R5	S	TO-220 (N.ISOL)
T1010NJ	TAG	Q8010L5	D	TO-220 (ISOL)
T1012BH	TAG	Q4010R5	D	TO-220 (N.ISOL)
T1012BJ	TAG	Q4010L5	D	TO-220 (ISOL)
T1012DH	TAG	Q4010R5	D	TO-220 (N.ISOL)
T1012DJ	TAG	Q4010L5	D	TO-220 (ISOL)
T1012MH	TAG	Q6010R5	D	TO-220 (N.ISOL)
T1012MJ	TAG	Q6010L5	D	TO-220 (ISOL)
T1012NH	TAG	Q8010R5	S	TO-220 (N.ISOL)
T1012NJ	TAG	Q8010L5	S	TO-220 (ISOL)
T1013BH	TAG	Q4010R5	D	TO-220 (N.ISOL)
T1013BJ	TAG	Q4010L5	D	TO-220 (ISOL)
T1013DH	TAG	Q4010R5	D	TO-220 (N.ISOL)
T1013DJ	TAG	Q4010L5	D	TO-220 (ISOL)
T1013MH	TAG	Q6010R5	D	TO-220 (N.ISOL)
T1013MJ	TAG	Q6010L5	D	TO-220 (ISOL)
T1013NH	TAG	Q8010R5	D	TO-220 (N.ISOL)
T1013NJ	TAG	Q8010L5	D	TO-220 (ISOL)
T106A1SC	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106A1SD	Hutson	L4004R5	S	TO-220 (N.ISOL)
T106A1SG	Hutson	L4004R6	S	TO-220 (N.ISOL)
T106A1SH	Hutson	L4004R8	S	TO-220 (N.ISOL)
T106A1SHA	Hutson	Q4004R4	S	TO-220 (N.ISOL)
T106A1SS	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106A2SS	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106B1SC	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106B1SD	Hutson	L4004R5	S	TO-220 (N.ISOL)
T106B1SG	Hutson	L4004R6	S	TO-220 (N.ISOL)
T106B1SGA	Hutson	Q4004R3	S	TO-220 (N.ISOL)
T106B1SH	Hutson	L4004R8	S	TO-220 (N.ISOL)
T106B1SHA	Hutson	Q4004R4	S	TO-220 (N.ISOL)
T106B1SS	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106B2SD	Hutson	L4004V5	S	TO-251 (N.ISOL)
T106B2SG	Hutson	L4004V6	S	TO-251 (N.ISOL)
T106B2SGA	Hutson	Q4004V3	S	TO-251 (N.ISOL)
T106B2SH	Hutson	L4004V8	S	TO-251 (N.ISOL)
T106B2SHA	Hutson	Q4004V4	S	TO-251 (N.ISOL)
T106B2SS	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106C1SC	Hutson	L4004R3	S	TO-220 (N.ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T106C1SD	Hutson	L4004R5	S	TO-220 (N.ISOL)
T106C1SG	Hutson	L4004R6	S	TO-220 (N.ISOL)
T106C1SGA	Hutson	Q4004R3	S	TO-220 (N.ISOL)
T106C1SH	Hutson	L4004R8	S	TO-220 (N.ISOL)
T106C1SHA	Hutson	Q4004R4	S	TO-220 (N.ISOL)
T106C1SS	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106C2SD	Hutson	L4004V5	S	TO-251 (N.ISOL)
T106C2SG	Hutson	L4004V6	S	TO-251 (N.ISOL)
T106C2SGA	Hutson	Q4004V3	S	TO-251 (N.ISOL)
T106C2SH	Hutson	L4004V8	S	TO-251 (N.ISOL)
T106C2SHA	Hutson	Q4004V4	S	TO-251 (N.ISOL)
T106C2SS	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106D1SC	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106D1SD	Hutson	L4004R5	S	TO-220 (N.ISOL)
T106D1SG	Hutson	L4004R6	S	TO-220 (N.ISOL)
T106D1SGA	Hutson	Q4004R3	S	TO-220 (N.ISOL)
T106D1SH	Hutson	L4004R8	S	TO-220 (N.ISOL)
T106D1SHA	Hutson	Q4004R4	S	TO-220 (N.ISOL)
T106D1SS	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106D2SD	Hutson	L4004V5	S	TO-251 (N.ISOL)
T106D2SG	Hutson	L4004V6	S	TO-251 (N.ISOL)
T106D2SGA	Hutson	Q4004V3	S	TO-251 (N.ISOL)
T106D2SH	Hutson	L4004V8	S	TO-251 (N.ISOL)
T106D2SHA	Hutson	Q4004V4	S	TO-251 (N.ISOL)
T106D2SS	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106E1SC	Hutson	L6004R3	S	TO-220 (N.ISOL)
T106E1SD	Hutson	L6004R5	S	TO-220 (N.ISOL)
T106E1SG	Hutson	L6004R6	S	TO-220 (N.ISOL)
T106E1SGA	Hutson	Q6004R3	S	TO-220 (N.ISOL)
T106E1SH	Hutson	L6004R8	S	TO-220 (N.ISOL)
T106E1SHA	Hutson	Q6004R4	S	TO-220 (N.ISOL)
T106E1SS	Hutson	L6004R3	S	TO-220 (N.ISOL)
T106E2SD	Hutson	L6004V5	S	TO-251 (N.ISOL)
T106E2SG	Hutson	L6004V6	S	TO-251 (N.ISOL)
T106E2SGA	Hutson	Q6004V3	S	TO-251 (N.ISOL)
T106E2SH	Hutson	L6004V8	S	TO-251 (N.ISOL)
T106E2SHA	Hutson	Q6004V4	S	TO-251 (N.ISOL)
T106E2SS	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106F1SC	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106F1SD	Hutson	L4004R5	S	TO-220 (N.ISOL)
T106F1SG	Hutson	L4004R6	S	TO-220 (N.ISOL)
T106F1SGA	Hutson	Q4004R3	S	TO-220 (N.ISOL)
T106F1SH	Hutson	L4004R8	S	TO-220 (N.ISOL)
T106F1SHA	Hutson	Q4004R4	S	TO-220 (N.ISOL)
T106F1SS	Hutson	L4004R3	S	TO-220 (N.ISOL)
T106F2SC	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106F2SD	Hutson	L4004V5	S	TO-251 (N.ISOL)
T106F2SG	Hutson	L4004V6	S	TO-251 (N.ISOL)
T106F2SGA	Hutson	Q4004V3	S	TO-251 (N.ISOL)
T106F2SH	Hutson	L4004V8	S	TO-251 (N.ISOL)
T106F2SHA	Hutson	Q4004V4	S	TO-251 (N.ISOL)
T106F2SS	Hutson	L4004V3	S	TO-251 (N.ISOL)
T106M1SD	Hutson	L6004R5	S	TO-220 (N.ISOL)
T106M1SG	Hutson	L6004R6	S	TO-220 (N.ISOL)
T106M1SGA	Hutson	Q6004R3	S	TO-220 (N.ISOL)
T106M1SH	Hutson	L6004R8	S	TO-220 (N.ISOL)
T106M1SHA	Hutson	Q6004R4	S	TO-220 (N.ISOL)
T106M1SS	Hutson	L6004R3	S	TO-220 (N.ISOL)
T106M2SD	Hutson	L6004V5	S	TO-251 (N.ISOL)
T106M2SG	Hutson	L6004V6	S	TO-251 (N.ISOL)
T106M2SGA	Hutson	Q6004V3	S	TO-251 (N.ISOL)
T106M2SH	Hutson	L6004V8	S	TO-251 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T106M2SHA	Hutson	Q6004V4	S	TO-251 (N.ISOL)
T106M2SS	Hutson	L6004V3	S	TO-251 (N.ISOL)
T1210BH	TAG	Q4015R5	S	TO-220 (N.ISOL)
T1210DH	TAG	Q4015R5	S	TO-220 (N.ISOL)
T1210MH	TAG	Q6015R5	S	TO-220 (N.ISOL)
T1210NH	TAG	Q8015R5	S	TO-220 (N.ISOL)
T1212BH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1212BJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1212DH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1212DJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1212MH	TAG	Q6015R5	D	TO-220 (N.ISOL)
T1212MJ	TAG	Q6015L5	D	TO-220 (ISOL)
T1212NH	TAG	Q8015R5	D	TO-220 (N.ISOL)
T1212NJ	TAG	Q8015L5	D	TO-220 (ISOL)
T1213BH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1213BJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1213DH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1213DJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1213MH	TAG	Q6015R5	D	TO-220 (N.ISOL)
T1213MJ	TAG	Q6015L5	D	TO-220 (ISOL)
T1213NH	TAG	Q8015R5	D	TO-220 (N.ISOL)
T1213NJ	TAG	Q8015L5	D	TO-220 (ISOL)
T1235-600G	STMicro	Q6012NH5	S	TO-263 (SMT)
T1235-800G	STMicro	Q8012NH5	S	TO-263 (SMT)
T1512BJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1512DJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1512MJ	TAG	Q6015L5	D	TO-220 (ISOL)
T1512NJ	TAG	Q8015L5	D	TO-220 (ISOL)
T1513BJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1513DJ	TAG	Q4015L5	D	TO-220 (ISOL)
T1513MJ	TAG	Q6015L5	D	TO-220 (ISOL)
T1513NJ	TAG	Q8015L5	D	TO-220 (ISOL)
T1612BH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1612DH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1612MH	TAG	Q6015R5	D	TO-220 (N.ISOL)
T1612NH	TAG	Q8015R5	D	TO-220 (N.ISOL)
T1612NJ	TAG	Q8015L5	D	TO-220 (ISOL)
T1613BH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1613DH	TAG	Q4015R5	D	TO-220 (N.ISOL)
T1613MH	TAG	Q6015R5	D	TO-220 (N.ISOL)
T1613NH	TAG	Q8015R5	S	TO-220 (N.ISOL)
T1620-600W	STMicro	Q6016LH3	D	TO-220 (ISOL)
T1620-800W	STMicro	Q6016LH3	D	TO-220 (ISOL)
T1630-600W	STMicro	Q6016LH4	S	TO-220 (ISOL)
T1630-800W	STMicro	Q8016LH4	S	TO-220 (ISOL)
T1635-600G	STMicro	Q6016NH4	D	TO-263 (SMT)
T1635-800G	STMicro	Q8016NH4	D	TO-263 (SMT)
T2300A	RCA	L4004L365	S	TO-220 (ISOL)
T2300B	RCA	L4004F365	S	TO-220 (ISOL)
T2300D	RCA	L4004F365	S	TO-220 (ISOL)
T2300F	RCA	L4004F365	S	TO-220 (ISOL)
T2300PA	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2300PB	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2300PC	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2300PD	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2300PE	MOTOROLA	L6004L3	S	TO-220 (ISOL)
T2300PF	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2300PM	MOTOROLA	L6004L3	S	TO-220 (ISOL)
T2301A	RCA	L4004L365	S	TO-220 (ISOL)
T2301B	RCA	L4004L365	S	TO-220 (ISOL)
T2301D	RCA	L4004L365	S	TO-220 (ISOL)
T2301F	RCA	L4004L365	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T2301PA	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2301PB	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2301PC	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2301PD	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2301PE	MOTOROLA	L6004L3	S	TO-220 (ISOL)
T2301PF	MOTOROLA	L4004L3	S	TO-220 (ISOL)
T2301PM	MOTOROLA	L6004L3	S	TO-220 (ISOL)
T2302A	RCA	L4004L665	S	TO-220 (ISOL)
T2302B	RCA	L4004L665	S	TO-220 (ISOL)
T2302D	RCA	L4004L665	S	TO-220 (ISOL)
T2302F	RCA	L4004L665	S	TO-220 (ISOL)
T2302PA	MOTOROLA	L4004L6	S	TO-220 (ISOL)
T2302PB	MOTOROLA	L4004L6	S	TO-220 (ISOL)
T2302PC	MOTOROLA	L4004L6	S	TO-220 (ISOL)
T2302PD	MOTOROLA	L4004L6	S	TO-220 (ISOL)
T2302PE	MOTOROLA	L6004L6	S	TO-220 (ISOL)
T2302PF	MOTOROLA	L4004L6	S	TO-220 (ISOL)
T2302PM	MOTOROLA	L6004L6	S	TO-220 (ISOL)
T2303F	RCA	Q4004L465	S	TO-220 (ISOL)
T2306A	RCA	Q4004L465	S	TO-220 (ISOL)
T2306B	RCA	Q4004L465	S	TO-220 (ISOL)
T2306D	RCA	Q4004L465	S	TO-220 (ISOL)
T2310A	RCA	L4004L365	S	TO-220 (ISOL)
T2310B	RCA	L4004L365	S	TO-220 (ISOL)
T2310D	RCA	L4004L365	S	TO-220 (ISOL)
T2310F	RCA	L4004L365	S	TO-220 (ISOL)
T2311A	RCA	L4004L365	S	TO-220 (ISOL)
T2311B	RCA	L4004L365	S	TO-220 (ISOL)
T2311D	RCA	L4004L365	S	TO-220 (ISOL)
T2311F	RCA	L4004L365	S	TO-220 (ISOL)
T2312A	RCA	L4004L665	S	TO-220 (ISOL)
T2312B	RCA	L4004L665	S	TO-220 (ISOL)
T2312D	RCA	L4004L665	S	TO-220 (ISOL)
T2312F	RCA	L4004L665	S	TO-220 (ISOL)
T2313A	RCA	Q4004L465	S	TO-220 (ISOL)
T2313B	RCA	Q4004L465	S	TO-220 (ISOL)
T2313D	RCA	Q4004L465	S	TO-220 (ISOL)
T2313F	RCA	Q4004L465	S	TO-220 (ISOL)
T2316A	RCA	Q4004L465	S	TO-220 (ISOL)
T2316B	RCA	Q4004L465	S	TO-220 (ISOL)
T2316D	RCA	Q4004L465	S	TO-220 (ISOL)
T2320A	RCA	L4004L3	S	TO-220 (ISOL)
T2320B	RCA	L4004L3	S	TO-220 (ISOL)
T2320C	RCA	L4004L3	S	TO-220 (ISOL)
T2320D	RCA	L4004L3	S	TO-220 (ISOL)
T2320E	RCA	L6004L3	S	TO-220 (ISOL)
T2320F	RCA	L4004L3	S	TO-220 (ISOL)
T2320M	RCA	L6004L3	S	TO-220 (ISOL)
T2322A	RCA	L4004L6	S	TO-220 (ISOL)
T2322B	RCA	L4004L6	S	TO-220 (ISOL)
T2322C	RCA	L4004L6	S	TO-220 (ISOL)
T2322D	RCA	L4004L6	S	TO-220 (ISOL)
T2322E	RCA	L6004L6	S	TO-220 (ISOL)
T2322F	RCA	L4004L6	S	TO-220 (ISOL)
T2322M	RCA	L6004L6	S	TO-220 (ISOL)
T2323A	RCA	L4004L8	S	TO-220 (ISOL)
T2323B	RCA	L4004L8	S	TO-220 (ISOL)
T2323C	RCA	L4004L8	S	TO-220 (ISOL)
T2323D	RCA	L4004L8	S	TO-220 (ISOL)
T2323E	RCA	L6004L8	S	TO-220 (ISOL)
T2323F	RCA	L4004L8	S	TO-220 (ISOL)
T2323M	RCA	L6004L8	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T2327A	RCA	L4004L5	S	TO-220 (ISOL)
T2327B	RCA	L4004L5	S	TO-220 (ISOL)
T2327C	RCA	L4004L5	S	TO-220 (ISOL)
T2327D	RCA	L4004L5	S	TO-220 (ISOL)
T2327E	RCA	L6004L5	S	TO-220 (ISOL)
T2327F	RCA	L4004L5	S	TO-220 (ISOL)
T2327M	RCA	L6004L5	S	TO-220 (ISOL)
T2500A	MOTOROLA	Q4006R4	D	TO-220 (N.ISOL)
T2500AFP	MOTOROLA	Q4006L4	D	TO-220 (ISOL)
T2500B	MOTOROLA	Q4006R4	D	TO-220 (N.ISOL)
T2500BFP	MOTOROLA	Q4006L4	D	TO-220 (ISOL)
T2500C	MOTOROLA	Q4006R4	D	TO-220 (N.ISOL)
T2500CFP	MOTOROLA	Q4006L4	D	TO-220 (ISOL)
T2500D	MOTOROLA	Q4006R4	D	TO-220 (N.ISOL)
T2500DFP	MOTOROLA	Q4006L4	D	TO-220 (ISOL)
T2500E	MOTOROLA	Q6006R5	S	TO-220 (N.ISOL)
T2500EFP	MOTOROLA	Q6006L5	S	TO-220 (ISOL)
T2500M	MOTOROLA	Q6006R5	D	TO-220 (N.ISOL)
T2500MFP	MOTOROLA	Q6006L5	D	TO-220 (ISOL)
T2500N	MOTOROLA	Q8006R5	D	TO-220 (N.ISOL)
T2500NFP	MOTOROLA	Q8006L5	D	TO-220 (ISOL)
T2500S	MOTOROLA	Q8006R5	D	TO-220 (N.ISOL)
T2500SFP	MOTOROLA	Q8006L5	D	TO-220 (ISOL)
T2506B	RCA	Q4006R4	D	TO-220 (N.ISOL)
T2506D	RCA	Q4006R4	D	TO-220 (N.ISOL)
T2512BH	TAG	Q4025R5	S	TO-220 (N.ISOL)
T2512BK	TAG	Q6025P5	S	FASTPAK (ISOL)
T2512DH	TAG	Q4025R5	S	TO-220 (N.ISOL)
T2512DK	TAG	Q6025P5	S	FASTPAK (ISOL)
T2512MH	TAG	Q6025R5	S	TO-220 (N.ISOL)
T2512MK	TAG	Q6025P5	S	FASTPAK (ISOL)
T2512NH	TAG	Q8025R5	S	TO-220 (N.ISOL)
T2512NK	TAG	Q8025P5	S	FASTPAK (ISOL)
T2513BH	TAG	Q4025R5	S	TO-220 (N.ISOL)
T2513BK	TAG	Q6025P5	S	FASTPAK (ISOL)
T2513DH	TAG	Q4025R5	S	TO-220 (N.ISOL)
T2513DK	TAG	Q6025P5	S	FASTPAK (ISOL)
T2513MH	TAG	Q6025R5	S	TO-220 (N.ISOL)
T2513MK	TAG	Q6025P5	S	FASTPAK (ISOL)
T2513NH	TAG	Q8025R5	S	TO-220 (N.ISOL)
T2513NK	TAG	Q8025P5	S	FASTPAK (ISOL)
T2535-600G	STMicro	Q6025NH6	S	TO-263 (SMT)
T2535-800G	STMicro	Q8025NH6	S	TO-263 (SMT)
T2700B	RCA	Q4006R4	S	TO-220 (N.ISOL)
T2700D	RCA	Q4006R4	S	TO-220 (N.ISOL)
T2800A	RCA	Q4008R4	S	TO-220 (N.ISOL)
T2800B	RCA	Q4008R4	S	TO-220 (N.ISOL)
T2800C	RCA	Q4008R4	S	TO-220 (N.ISOL)
T2800D	RCA	Q4008R4	S	TO-220 (N.ISOL)
T2800E	RCA	Q6008R5	S	TO-220 (N.ISOL)
T2800M	RCA	Q6008R5	S	TO-220 (N.ISOL)
T2801A	RCA	Q4006R4	D	TO-220 (N.ISOL)
T2801B	RCA	Q4006R4	D	TO-220 (N.ISOL)
T2801C	RCA	Q4006R4	D	TO-220 (N.ISOL)
T2801D	RCA	Q4006R4	D	TO-220 (N.ISOL)
T2801E	RCA	Q6006R5	D	TO-220 (N.ISOL)
T2801M	RCA	Q6006R5	D	TO-220 (N.ISOL)
T2801N	RCA	Q8006R5	D	TO-220 (N.ISOL)
T2801S	RCA	Q8006R5	D	TO-220 (N.ISOL)
T2802A	RCA	Q4008RH4	D	TO-220 (N.ISOL)
T2802B	RCA	Q4008RH4	D	TO-220 (N.ISOL)
T2802C	RCA	Q4008RH4	D	TO-220 (N.ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T2802D	RCA	Q4008RH4	D	TO-220 (N.ISOL)
T2802E	RCA	Q6008RH4	D	TO-220 (N.ISOL)
T2802M	RCA	Q6008RH4	D	TO-220 (N.ISOL)
T2806B	RCA	Q4008R4	D	TO-220 (N.ISOL)
T2806D	RCA	Q4008R4	D	TO-220 (N.ISOL)
T2806M	RCA	Q6008R5	S	TO-220 (N.ISOL)
T2850A	RCA	Q4008L4	D	TO-220 (ISOL)
T2850B	RCA	Q4008L4	D	TO-220 (ISOL)
T2850D	RCA	Q4008L4	D	TO-220 (ISOL)
T2850E	RCA	Q6008L5	S	TO-220 (ISOL)
T2850F	RCA	Q4008L4	D	TO-220 (ISOL)
T2856B	RCA	Q4008L4	D	TO-220 (ISOL)
T2856D	RCA	Q4008L4	D	TO-220 (ISOL)
T4012DKS	TAG	Q6035P5	S	FASTPAK (ISOL)
T4012MKS	TAG	Q6035P5	S	FASTPAK (ISOL)
T4012NKS	TAG	Q8035P5	S	FASTPAK (ISOL)
T4012SKS	TAG	Q8035P5	S	FASTPAK (ISOL)
T4013DKS	TAG	Q6035P5	S	FASTPAK (ISOL)
T4013MKS	TAG	Q6035P5	S	FASTPAK (ISOL)
T4013NKS	TAG	Q8035P5	S	FASTPAK (ISOL)
T4013SKS	TAG	Q8035P5	S	FASTPAK (ISOL)
T405-400T	STMicro	L4004L6	S	TO-220 (ISOL)
T405-400W	STMicro	L4004L6	D	TO-220 (ISOL)
T405-600B	STMicro	L6004D6	S	TO-252 (SMT)
T405-600H	STMicro	L6004V6	S	TO-251 (N.ISOL)
T405-600T	STMicro	L6004L6	S	TO-220 (ISOL)
T405-600W	STMicro	L6004L6	D	TO-220 (ISOL)
T410-400T	STMicro	L4004L8	S	TO-220 (ISOL)
T410-400W	STMicro	L4004L8	D	TO-220 (ISOL)
T410-600B	STMicro	Q6006DH3	S	TO-252 (SMT)
T410-600H	STMicro	Q6006VH3	S	TO-251 (N.ISOL)
T410-600T	STMicro	L6004L8	S	TO-220 (ISOL)
T410-600W	STMicro	L6004L8	D	TO-220 (ISOL)
T435-400T	STMicro	Q4006RH4	D	TO-220 (N.ISOL)
T435-400W	STMicro	Q4006LH4	D	TO-220 (ISOL)
T435-600B	STMicro	Q6006DH4	S	TO-252 (SMT)
T435-600H	STMicro	Q6006VH4	S	TO-251 (N.ISOL)
T435-600T	STMicro	Q6006RH4	D	TO-220 (N.ISOL)
T435-600W	STMicro	Q6006LH4	D	TO-220 (ISOL)
T435-700T	STMicro	Q8006RH4	D	TO-220 (N.ISOL)
T435-700W	STMicro	Q8006LH4	D	TO-220 (ISOL)
T435-800T	STMicro	Q8006RH4	D	TO-220 (N.ISOL)
T435-800W	STMicro	Q8006LH4	D	TO-220 (ISOL)
T4M3F600B	LITEON	L6004L3	S	TO-220 (ISOL)
T4M3F800B	LITEON	L6004L3	S	TO-220 (ISOL)
T4M10T600B	LITEON	Q6004L3	S	TO-220 (ISOL)
T4M10T800B	LITEON	Q6004L3	S	TO-220 (ISOL)
T4M35T600B	LITEON	Q6004L4	S	TO-220 (ISOL)
T4M35T800B	LITEON	Q8004L4	S	TO-220 (ISOL)
T6000B	RCA	Q4015R5	D	TO-220 (N.ISOL)
T6000D	RCA	Q4015R5	D	TO-220 (N.ISOL)
T6000M	RCA	Q6015R5	D	TO-220 (N.ISOL)
T6001B	RCA	Q4015R5	D	TO-220 (N.ISOL)
T6001D	RCA	Q4015R5	D	TO-220 (N.ISOL)
T6001M	RCA	Q6015R5	D	TO-220 (N.ISOL)
T6006B	RCA	Q4015R5	S	TO-220 (N.ISOL)
T6006D	RCA	Q4015R5	S	TO-220 (N.ISOL)
T6006M	RCA	Q6015R5	S	TO-220 (N.ISOL)
T620-400W	STMicro	Q4006LH4	S	TO-220 (ISOL)
T620-600W	STMicro	Q6006LH4	S	TO-220 (ISOL)
T620-700W	STMicro	Q8006LH4	S	TO-220 (ISOL)
T630-400W	STMicro	Q4006LH4	S	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T630-600W	STMicro	Q6006LH4	S	TO-220 (ISOL)
T630-700W	STMicro	Q8006LH4	S	TO-220 (ISOL)
T810-400B	STMicro	Q4008DH3	D	TO-252 (SMT)
T810-600B	STMicro	Q6008DH3	D	TO-252 (SMT)
T820-400W	STMicro	Q4008LH4	S	TO-220 (ISOL)
T820-600W	STMicro	Q6008LH4	S	TO-220 (ISOL)
T820-700W	STMicro	Q8008LH4	S	TO-220 (ISOL)
T830-400W	STMicro	Q4008LH4	S	TO-220 (ISOL)
T830-600W	STMicro	Q6008LH4	S	TO-220 (ISOL)
T830-700W	STMicro	Q8008LH4	S	TO-220 (ISOL)
T835-600B	STMicro	Q6008DH4	D	TO-252 (SMT)
T835-600G	STMicro	Q6008NH4	D	TO-263 (SMT)
T850-600G	STMicro	Q6010NH5	D	TO-263 (SMT)
T8M5F200B	LITEON	L4008L5	S	TO-220 (ISOL)
T8M5F400B	LITEON	L4008L5	S	TO-220 (ISOL)
T8M5F600B	LITEON	L6008L5	S	TO-220 (ISOL)
T8M5F800B	LITEON	L6008L5	S	TO-220 (ISOL)
T8M5T400B	LITEON	L4008L5	S	TO-220 (ISOL)
T8M5T600B	LITEON	L6008L5	S	TO-220 (ISOL)
T8M5T800B	LITEON	L6008L5	S	TO-220 (ISOL)
T8M25F400B	LITEON	Q4008R4	S	TO-220 (N.ISOL)
T8M25F600B	LITEON	Q6008R5	S	TO-220 (N.ISOL)
T8M25F800B	LITEON	Q8008R5	S	TO-220 (N.ISOL)
T8M35T400B	LITEON	Q4008RH4	S	TO-220 (N.ISOL)
T8M35T600B	LITEON	Q6008RH4	S	TO-220 (N.ISOL)
T8M35T800B	LITEON	Q8008RH4	S	TO-220 (N.ISOL)
T8M50T400B	LITEON	Q4008RH4	S	TO-220 (N.ISOL)
T8M50T600B	LITEON	Q6008RH4	S	TO-220 (N.ISOL)
T8M50T800B	LITEON	Q8008RH4	S	TO-220 (N.ISOL)
TIC106D	TI	S4006LS2	S	TO-220 (ISOL)
TIC106M	TI	S6006LS2	S	TO-220 (ISOL)
TIC108D	TI	S4006LS3	S	TO-220 (ISOL)
TIC108M	TI	S6006LS3	S	TO-220 (ISOL)
TIC116D	TI	S4008R	D	TO-220 (N.ISOL)
TIC116M	TI	S6008R	D	TO-220 (N.ISOL)
TIC116N	TI	S8008R	D	TO-220 (N.ISOL)
TIC116S	TI	S8008R	D	TO-220 (N.ISOL)
TIC126D	TI	S4012R	D	TO-220 (N.ISOL)
TIC126M	TI	S6012R	D	TO-220 (N.ISOL)
TIC126N	TI	S8012R	D	TO-220 (N.ISOL)
TIC126S	TI	S8012R	D	TO-220 (N.ISOL)
TIC201D	TI	L4004L6	S	TO-220 (ISOL)
TIC201M	TI	L6004L6	S	TO-220 (ISOL)
TIC206D	TI	L4004L6	S	TO-220 (ISOL)
TIC206M	TI	L6004L6	S	TO-220 (ISOL)
TIC216D	TI	L4006L6	S	TO-220 (ISOL)
TIC216M	TI	L6006L6	S	TO-220 (ISOL)
TIC225D	TI	L4008L6	S	TO-220 (ISOL)
TIC225M	TI	L6008L6	S	TO-220 (ISOL)
TIC226D	TI	Q4008R4	D	TO-220 (N.ISOL)
TIC226M	TI	Q6008R5	D	TO-220 (N.ISOL)
TIC226N	TI	Q8008R5	D	TO-220 (N.ISOL)
TIC226S	TI	Q8008R5	D	TO-220 (N.ISOL)
TIC236D	TI	Q4015R5	D	TO-220 (N.ISOL)
TIC236M	TI	Q6015R5	D	TO-220 (N.ISOL)
TIC236N	TI	Q8015R5	D	TO-220 (N.ISOL)
TIC236S	TI	Q8015R5	D	TO-220 (N.ISOL)
TIC246D	TI	Q4015R5	S	TO-220 (N.ISOL)
TIC246M	TI	Q6015R5	S	TO-220 (N.ISOL)
TIC246N	TI	Q8015R5	S	TO-220 (N.ISOL)
TIC246S	TI	Q8015R5	S	TO-220 (N.ISOL)
TIC253B	TI	Q4025M6	S	TO-218AC (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
TIC253D	TI	Q4025M6	S	TO-218AC (N.ISOL)
TIC253E	TI	Q6025M6	S	TO-218AC (N.ISOL)
TIC253M	TI	Q6025M6	S	TO-218AC (N.ISOL)
TIC256D	TI	Q4025R5	S	TO-220 (N.ISOL)
TIC256M	TI	Q6025R5	S	TO-220 (N.ISOL)
TIC256N	TI	Q8025R5	S	TO-220 (N.ISOL)
TIC256S	TI	Q8025R5	S	TO-220 (N.ISOL)
TIC263B	TI	Q4025M6	S	TO-218AC (N.ISOL)
TIC263D	TI	Q4025M6	S	TO-218AC (N.ISOL)
TIC263E	TI	Q6025M6	S	TO-218AC (N.ISOL)
TIC263M	TI	Q6025M6	S	TO-218AC (N.ISOL)
TICP106D	TI	S402ES	D	TO-92 (ISOL)
TICP106M	TI	S602ES	D	TO-92 (ISOL)
TICP107D	TI	S402ES	D	TO-92 (ISOL)
TICP107M	TI	L0107DE	D	TO-92 (ISOL)
TICP206D	TI	L0107DE	S	TO-92 (ISOL)
TICP206M	TI	L0107ME	S	TO-92 (ISOL)
TL1003	STMicro	S4006V	S	TO-251 (N.ISOL)
TL1006	STMicro	S4006V	S	TO-251 (N.ISOL)
TL106-05	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL106-1	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL106-2	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL106-4	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL106-6	STMicro	S6004VS2	S	TO-251 (N.ISOL)
TL107-05	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL107-1	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL107-2	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL107-4	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TL107-6	STMicro	S6004VS2	S	TO-251 (N.ISOL)
TL2003	STMicro	S4006V	S	TO-251 (N.ISOL)
TL2006	STMicro	S4006V	S	TO-251 (N.ISOL)
TL4003	STMicro	S4006V	S	TO-251 (N.ISOL)
TL4006	STMicro	S4006V	S	TO-251 (N.ISOL)
TL6003	STMicro	S6006V	S	TO-251 (N.ISOL)
TL6006	STMicro	S6006V	S	TO-251 (N.ISOL)
TLC111A	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC111B	STMicro	Q4004V42	S	TO-251 (N.ISOL)
TLC111D	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC111S	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC111T	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC113B	STMicro	Q4004V42	S	TO-251 (N.ISOL)
TLC116S	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC116A	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC116B	STMicro	Q4004V42	S	TO-251 (N.ISOL)
TLC116D	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC116T	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC221A	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC221B	STMicro	Q4004V42	S	TO-251 (N.ISOL)
TLC221D	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC221S	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC221T	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC223A	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC223B	STMicro	Q4004V42	S	TO-251 (N.ISOL)
TLC223D	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC226A	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC226B	STMicro	Q4004V42	S	TO-251 (N.ISOL)
TLC226D	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC226S	STMicro	L4004V62	S	TO-251 (N.ISOL)
TLC226T	STMicro	L4004V52	S	TO-251 (N.ISOL)
TLC331A	STMicro	L6004V62	S	TO-251 (N.ISOL)
TLC331B	STMicro	Q6004V42	S	TO-251 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
TLC331D	STMicro	L6004V52	S	TO-251 (N.ISOL)
TLC331S	STMicro	L6004V62	S	TO-251 (N.ISOL)
TLC331T	STMicro	L6004V52	S	TO-251 (N.ISOL)
TLC333A	STMicro	L6004V62	S	TO-251 (N.ISOL)
TLC333B	STMicro	Q6004V42	S	TO-251 (N.ISOL)
TLC333D	STMicro	L6004V52	S	TO-251 (N.ISOL)
TLC336A	STMicro	L6004V62	S	TO-251 (N.ISOL)
TLC336B	STMicro	Q6004V42	S	TO-251 (N.ISOL)
TLC336D	STMicro	L6004V52	S	TO-251 (N.ISOL)
TLC336S	STMicro	L6004V62	S	TO-251 (N.ISOL)
TLC336T	STMicro	L6004V52	S	TO-251 (N.ISOL)
TLC386B	STMicro	Q6004V42	S	TO-251 (N.ISOL)
TLS106-05	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS106-1	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS106-2	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS106-4	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS106-6	STMicro	S6004VS2	S	TO-251 (N.ISOL)
TLS107-05	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS107-1	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS107-2	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS107-4	STMicro	S4004VS2	S	TO-251 (N.ISOL)
TLS107-6	STMicro	S6004VS2	S	TO-251 (N.ISOL)
TN1215-600B	STMicro	S6012D	S	TO-252 (SMT)
TN1215-600H	STMicro	S6012V	S	TO-251 (N.ISOL)
TN1215-800B	STMicro	S8012D	S	TO-252 (SMT)
TN1215-800H	STMicro	S8012V	S	TO-251 (N.ISOL)
TN1625-1000G	STMicro	SK016N	S	TO-263 (SMT)
TN1625-600G	STMicro	S6016N	S	TO-263 (SMT)
TN1625-800G	STMicro	S8016N	S	TO-263 (SMT)
TN2540-600G	STMicro	S6025N	S	TO-263 (SMT)
TN2540-800G	STMicro	S8025N	S	TO-263 (SMT)
TN2540-1000G	STMicro	SK025N	S	TO-263 (SMT)
TN815-600B	STMicro	S6008D	D	TO-252 (SMT)
TN815-600H	STMicro	S6008V	D	TO-251 (N.ISOL)
TN815-800B	STMicro	S8008D	D	TO-252 (SMT)
TN815-800H	STMicro	S8008V	D	TO-251 (N.ISOL)
T01013BJ	TAG	Q4010L5	D	TO-220 (ISOL)
T01013DJ	TAG	Q4010L5	D	TO-220 (ISOL)
T01013MJ	TAG	Q6010L5	D	TO-220 (ISOL)
T01013NJ	TAG	Q8010L5	D	TO-220 (ISOL)
T0409BJ	TAG	L4004L6	D	TO-220 (ISOL)
T0409DJ	TAG	L4004L6	D	TO-220 (ISOL)
T0409MJ	TAG	L6004L6	D	TO-220 (ISOL)
T0410BJ	TAG	L4004L8	D	TO-220 (ISOL)
T0410DJ	TAG	L4004L8	D	TO-220 (ISOL)
T0410MJ	TAG	L6004L8	D	TO-220 (ISOL)
T0505BH	TAG	L4006L5	S	TO-220 (ISOL)
T0505DH	TAG	L4006L5	S	TO-220 (ISOL)
T0509BH	TAG	L4006L6	S	TO-220 (ISOL)
T0509DH	TAG	L4006L6	S	TO-220 (ISOL)
T0510BH	TAG	L4006L8	S	TO-220 (ISOL)
T0512BH	TAG	Q4006R4	D	TO-220 (N.ISOL)
T0512DH	TAG	Q4006R4	D	TO-220 (N.ISOL)
T0512MH	TAG	Q6006R5	S	TO-220 (N.ISOL)
T0605BH	TAG	L4006L5	S	TO-220 (ISOL)
T0605DH	TAG	L4006L5	S	TO-220 (ISOL)
T0605MH	TAG	L6006L5	S	TO-220 (ISOL)
T0609BH	TAG	L4006L6	S	TO-220 (ISOL)
T0609BJ	TAG	L4006L6	D	TO-220 (ISOL)
T0609DH	TAG	L4006L6	S	TO-220 (ISOL)
T0609DJ	TAG	L4006L6	D	TO-220 (ISOL)
T0609MH	TAG	L6006L6	S	TO-220 (ISOL)

Teccor® brand Thyristors

Cross Reference Guide

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
T0609MJ	TAG	L6006L6	D	TO-220 (ISOL)
T0610BH	TAG	L4006L8	S	TO-220 (ISOL)
T0610BJ	TAG	L4006L8	D	TO-220 (ISOL)
T0610DH	TAG	L4006L8	S	TO-220 (ISOL)
T0610DJ	TAG	L4006L8	D	TO-220 (ISOL)
T0610MH	TAG	L6006L8	S	TO-220 (ISOL)
T0610MJ	TAG	L6006L8	D	TO-220 (ISOL)
T0612BJ	TAG	Q4006L4	S	TO-220 (ISOL)
T0612DJ	TAG	Q4006L4	S	TO-220 (ISOL)
T0612MJ	TAG	Q6006L5	S	TO-220 (ISOL)
T0805BH	TAG	L4008L6	S	TO-220 (ISOL)
T0805DH	TAG	L4008L6	S	TO-220 (ISOL)
T0805MH	TAG	L6008L6	S	TO-220 (ISOL)
T0809BH	TAG	L4008L6	S	TO-220 (ISOL)
T0809DH	TAG	L4008L6	S	TO-220 (ISOL)
T0809MH	TAG	L6008L6	S	TO-220 (ISOL)
T0810BH	TAG	L4008L8	S	TO-220 (ISOL)
T0810BJ	TAG	L4008L8	D	TO-220 (ISOL)
T0810DH	TAG	L4008L8	S	TO-220 (ISOL)
T0810DJ	TAG	L4008L8	D	TO-220 (ISOL)
T0810MH	TAG	L6008L8	S	TO-220 (ISOL)
T0810MJ	TAG	L6008L8	D	TO-220 (ISOL)
T0812BH	TAG	Q4008R4	S	TO-220 (N.ISOL)
T0812BJ	TAG	Q4008L4	S	TO-220 (ISOL)
T0812DH	TAG	Q4008R4	S	TO-220 (N.ISOL)
T0812DJ	TAG	Q4008L4	S	TO-220 (ISOL)
T0812MH	TAG	Q6008R5	S	TO-220 (N.ISOL)
T0812MJ	TAG	Q6008L5	S	TO-220 (ISOL)
T0812NH	TAG	Q8008L5	S	TO-220 (ISOL)
T0813BJ	TAG	Q4008L4	S	TO-220 (ISOL)
T0813DJ	TAG	Q4008L4	S	TO-220 (ISOL)
T0813MJ	TAG	Q6008L5	S	TO-220 (ISOL)
T0813NJ	TAG	Q8008L5	S	TO-220 (ISOL)
TPDV125	STMicro	Q4025L6	S	TO-220 (ISOL)
TPDV140	STMicro	Q4040K7	D	TO-218 (ISOL)
TPDV225	STMicro	Q4025L6	S	TO-220 (ISOL)
TPDV240	STMicro	Q4040K7	D	TO-218 (ISOL)
TPDV425	STMicro	Q4025L6	S	TO-220 (ISOL)
TPDV440	STMicro	Q4040J7	D	TO-218 (ISOL)
TPDV625	STMicro	Q6025L6	S	TO-220 (ISOL)
TPDV640	STMicro	Q6040K7	D	TO-218 (ISOL)
TPDV825	STMicro	Q8025L6	S	TO-220 (ISOL)
TPDV840	STMicro	Q8040K7	D	TO-218 (ISOL)
TS420-400T	STMicro	S4006LS2	S	TO-220 (ISOL)
TS420-600B	STMicro	S6004DS2	S	TO-252 (SMT)
TS420-600H	STMicro	S6004VS2	S	TO-251 (N.ISOL)
TS420-600T	STMicro	S6006LS2	S	TO-220 (ISOL)
TS820-400T	STMicro	S4008LS2	S	TO-220 (ISOL)
TS820-600B	STMicro	S6008DS2	S	TO-252 (SMT)
TS820-600H	STMicro	S6008VS2	S	TO-251 (N.ISOL)
TS820-600T	STMicro	S6008LS2	S	TO-220 (ISOL)
TXDV208	STMicro	Q4016LH6	D	TO-220 (ISOL)
TXDV408	STMicro	Q4016LH6	D	TO-220 (ISOL)
TXDV608	STMicro	Q6016LH6	D	TO-220 (ISOL)
TXDV808	STMicro	Q8016LH6	D	TO-220 (ISOL)
TXDV212	STMicro	Q4016LH6	D	TO-220 (ISOL)
TXDV412	STMicro	Q4016LH6	D	TO-220 (ISOL)
TXDV612	STMicro	Q6016LH6	D	TO-220 (ISOL)
TXDV812	STMicro	Q8016LH6	D	TO-220 (ISOL)
TXN0510	STMicro	S4010L	D	TO-220 (ISOL)
TXN0512	STMicro	S4015L	S	TO-220 (ISOL)
TXN056	STMicro	S4006L	D	TO-220 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
TXN058	STMicro	S4008L	D	TO-220 (ISOL)
TXN058G	STMicro	S4008L	D	TO-220 (ISOL)
TXN106	STMicro	S4006L	D	TO-220 (ISOL)
TXN108	STMicro	S4008L	S	TO-220 (ISOL)
TXN108G	STMicro	S4008L	D	TO-220 (ISOL)
TXN110	STMicro	S4010L	D	TO-220 (ISOL)
TXN112	STMicro	S4015L	S	TO-220 (ISOL)
TXN204	STMicro	S4006L	S	TO-220 (ISOL)
TXN206	STMicro	S4006L	D	TO-220 (ISOL)
TXN208	STMicro	S4008L	D	TO-220 (ISOL)
TXN208G	STMicro	S4008L	D	TO-220 (ISOL)
TXN210	STMicro	S4010L	D	TO-220 (ISOL)
TXN212	STMicro	S4015L	S	TO-220 (ISOL)
TXN404	STMicro	S4006L	S	TO-220 (ISOL)
TXN406	STMicro	S4006L	D	TO-220 (ISOL)
TXN408	STMicro	S4008L	D	TO-220 (ISOL)
TXN408G	STMicro	S4008L	D	TO-220 (ISOL)
TXN410	STMicro	S4010L	D	TO-220 (ISOL)
TXN412	STMicro	S4015L	S	TO-220 (ISOL)
TXN604	STMicro	S6006L	S	TO-220 (ISOL)
TXN606	STMicro	S6006L	D	TO-220 (ISOL)
TXN608	STMicro	S6008L	D	TO-220 (ISOL)
TXN608G	STMicro	S6008L	D	TO-220 (ISOL)
TXN610	STMicro	S6010L	D	TO-220 (ISOL)
TXN612	STMicro	S6015L	S	TO-220 (ISOL)
TXN812	STMicro	S8015L	S	TO-220 (ISOL)
TYN0510	STMicro	S4010R	D	TO-220 (N.ISOL)
TYN0512	STMicro	S4012R	D	TO-220 (N.ISOL)
TYN0516	STMicro	S4016R	D	TO-220 (N.ISOL)
TYN054	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN056	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN058	STMicro	S4008R	D	TO-220 (N.ISOL)
TYN058G	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN058K	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN104	STMicro	S4006L	S	TO-220 (ISOL)
TYN106	STMicro	S4006L	S	TO-220 (ISOL)
TYN108	STMicro	S4008R	D	TO-220 (N.ISOL)
TYN108G	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN110	STMicro	S4010R	D	TO-220 (N.ISOL)
TYN112	STMicro	S4012R	D	TO-220 (N.ISOL)
TYN116	STMicro	S4016R	D	TO-220 (N.ISOL)
TYN204	STMicro	S4006L	S	TO-220 (ISOL)
TYN206	STMicro	S4006L	S	TO-220 (ISOL)
TYN208	STMicro	S4008R	D	TO-220 (N.ISOL)
TYN208G	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN208K	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN210	STMicro	S4010R	D	TO-220 (N.ISOL)
TYN212	STMicro	S4012R	D	TO-220 (N.ISOL)
TYN216	STMicro	S4016R	D	TO-220 (N.ISOL)
TYN404	STMicro	S4006L	S	TO-220 (ISOL)
TYN406	STMicro	S4006L	S	TO-220 (ISOL)
TYN408	STMicro	S4008R	D	TO-220 (N.ISOL)
TYN408G	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN408K	STMicro	S4008R	S	TO-220 (N.ISOL)
TYN410	STMicro	S4010R	D	TO-220 (N.ISOL)
TYN412	STMicro	S4012R	S	TO-220 (N.ISOL)
TYN416	STMicro	S4016R	D	TO-220 (N.ISOL)
TYN604	STMicro	S6006L	S	TO-220 (ISOL)
TYN606	STMicro	S6006L	S	TO-220 (ISOL)
TYN608	STMicro	S6008R	D	TO-220 (N.ISOL)
TYN608G	STMicro	S6008R	S	TO-220 (N.ISOL)
TYN608K	STMicro	S6008R	S	TO-220 (N.ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
TYN610	STMicro	S6010R	D	TO-220 (N.ISOL)
TYN612	STMicro	S6012R	D	TO-220 (N.ISOL)
TYN616	STMicro	S6016R	D	TO-220 (N.ISOL)
TYN625	STMicro	S6025R	S	TO-220 (N.ISOL)
TYN640	STMicro	S6040R	S	TO-220 (N.ISOL)
TYN682	STMicro	S4025R	D	TO-220 (N.ISOL)
TYN683	STMicro	S4025R	D	TO-220 (N.ISOL)
TYN685	STMicro	S4025R	D	TO-220 (N.ISOL)
TYN688	STMicro	S4025R	D	TO-220 (N.ISOL)
TYN690	STMicro	S6025R	D	TO-220 (N.ISOL)
TYN808	STMicro	S8008R	D	TO-220 (N.ISOL)
TYN808G	STMicro	S8008R	S	TO-220 (N.ISOL)
TYN808K	STMicro	S8008R	S	TO-220 (N.ISOL)
TYN810	STMicro	S8010R	S	TO-220 (N.ISOL)
TYN812	STMicro	S8012R	D	TO-220 (N.ISOL)
TYN816	STMicro	S8016R	D	TO-220 (N.ISOL)
TYN825	STMicro	S8025R	S	TO-220 (N.ISOL)
TYN840	STMicro	S8040R	S	TO-220 (N.ISOL)
TYN1025	STMicro	SK025R	S	TO-220 (N.ISOL)
TYN1040	STMicro	SK040R	S	TO-220 (N.ISOL)
TYS1006-05	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS1006-1	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS1006-2	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS1006-4	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS1007-05	STMicro	S4010LS3	S	TO-220 (ISOL)
TYS1007-1	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS1007-2	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS1007-4	STMicro	S4010LS2	S	TO-220 (ISOL)
TYS406-05	STMicro	S4006LS2	S	TO-220 (ISOL)
TYS406-1	STMicro	S4006LS2	S	TO-220 (ISOL)
TYS406-2	STMicro	S4006LS2	S	TO-220 (ISOL)
TYS406-4	STMicro	S4006LS2	S	TO-220 (ISOL)
TYS406-6	STMicro	S6006LS2	S	TO-220 (ISOL)
TYS407-05	STMicro	S4006LS3	S	TO-220 (ISOL)
TYS407-1	STMicro	S4006LS3	S	TO-220 (ISOL)
TYS407-2	STMicro	S4006LS3	S	TO-220 (ISOL)
TYS407-4	STMicro	S4006LS3	S	TO-220 (ISOL)
TYS407-6	STMicro	S6006LS3	S	TO-220 (ISOL)
TYS606-05	STMicro	S4006LS2	D	TO-220 (ISOL)
TYS606-1	STMicro	S4006LS2	D	TO-220 (ISOL)
TYS606-2	STMicro	S4006LS2	D	TO-220 (ISOL)
TYS606-4	STMicro	S4006LS2	D	TO-220 (ISOL)
TYS606-6	STMicro	S6006LS2	S	TO-220 (ISOL)
TYS607-05	STMicro	S4006LS3	D	TO-220 (ISOL)
TYS607-1	STMicro	S4006LS3	D	TO-220 (ISOL)
TYS607-2	STMicro	S4006LS3	D	TO-220 (ISOL)
TYS607-4	STMicro	S4006LS3	D	TO-220 (ISOL)
TYS607-6	STMicro	S6006LS3	S	TO-220 (ISOL)
TYS806-05	STMicro	S4008LS2	D	TO-220 (ISOL)
TYS806-1	STMicro	S4008LS2	D	TO-220 (ISOL)
TYS806-2	STMicro	S4008LS2	D	TO-220 (ISOL)
TYS806-4	STMicro	S4008LS2	D	TO-220 (ISOL)
TYS806-6	STMicro	S6008LS2	S	TO-220 (ISOL)
TYS807-05	STMicro	S4008LS3	D	TO-220 (ISOL)
TYS807-1	STMicro	S4008LS3	D	TO-220 (ISOL)
TYS807-2	STMicro	S4008LS3	D	TO-220 (ISOL)
TYS807-4	STMicro	S4008LS3	D	TO-220 (ISOL)
TYS807-6	STMicro	S6008LS3	S	TO-220 (ISOL)
X0101BA	TAG	S4X8ES1	S	TO-92 (ISOL)
X0101DA	TAG	S4X8ES1	S	TO-92 (ISOL)
X0101MA	TAG	S6X8ES1	S	TO-92 (ISOL)
X0102BA	TAG	S4X8ES	D	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
X0102DA	TAG	S4X8ES	D	TO-92 (ISOL)
X0102MA	TAG	S6X8ES	D	TO-92 (ISOL)
X0102NA	TAG	S8X8ES	D	TO-92 (ISOL)
X0103BA	TAG	S4X8ES	S	TO-92 (ISOL)
X0103DA	TAG	S4X8ES	S	TO-92 (ISOL)
X0103MA	TAG	S6X8ES	S	TO-92 (ISOL)
X0103NA	TAG	S8X8ES	S	TO-92 (ISOL)
X0104BA	TAG	S4X8ES2	D	TO-92 (ISOL)
X0104DA	TAG	S4X8ES2	D	TO-92 (ISOL)
X0104MA	TAG	S6X8ES2	D	TO-92 (ISOL)
X0105BA	TAG	S4X8ES2	S	TO-92 (ISOL)
X0105DA	TAG	S4X8ES2	S	TO-92 (ISOL)
X0105MA	TAG	S6X8ES2	S	TO-92 (ISOL)
X0106BA	TAG	S4X8ES	S	TO-92 (ISOL)
X0106DA	TAG	S4X8ES	S	TO-92 (ISOL)
X0106MA	TAG	S6X8ES	S	TO-92 (ISOL)
X0106NA	TAG	S8X8ES	S	TO-92 (ISOL)
X0110BA	TAG	S4X8ES2	S	TO-92 (ISOL)
X0110DA	TAG	S4X8ES2	S	TO-92 (ISOL)
X0110MA	TAG	S6X8ES2	S	TO-92 (ISOL)
X0202BA	TAG	TCR22-6	D	TO-92 (ISOL)
X0202DA	TAG	TCR22-6	D	TO-92 (ISOL)
X0202MA	TAG	TCR22-8	D	TO-92 (ISOL)
X0203BA	TAG	TCR22-6	S	TO-92 (ISOL)
X0203DA	TAG	TCR22-6	S	TO-92 (ISOL)
X0203MA	TAG	TCR22-8	S	TO-92 (ISOL)
X0204BA	TAG	TCR22-6	S	TO-92 (ISOL)
X0204DA	TAG	TCR22-6	S	TO-92 (ISOL)
X0204MA	TAG	TCR22-8	S	TO-92 (ISOL)
X0205BA	TAG	TCR22-6	S	TO-92 (ISOL)
X0205DA	TAG	TCR22-6	S	TO-92 (ISOL)
X0205MA	TAG	TCR22-8	S	TO-92 (ISOL)
X0206BA	TAG	TCR22-6	S	TO-92 (ISOL)
X0206DA	TAG	TCR22-6	S	TO-92 (ISOL)
X0206MA	TAG	TCR22-8	S	TO-92 (ISOL)
X0402BE	TAG	S4006LS2	S	TO-220 (ISOL)
X0402BF	TAG	S4004VS2	S	TO-251 (N.ISOL)
X0402DE	TAG	S4006LS2	S	TO-220 (ISOL)
X0402DF	TAG	S4004VS2	S	TO-251 (N.ISOL)
X0402ME	TAG	S6006LS2	S	TO-220 (ISOL)
X0402MF	TAG	S6004VS2	S	TO-251 (N.ISOL)
X0403BE	TAG	S4006LS2	S	TO-220 (ISOL)
X0403BF	TAG	S4004VS2	S	TO-251 (N.ISOL)
X0403DE	TAG	S4006LS2	S	TO-220 (ISOL)
X0403DF	TAG	S4004VS2	S	TO-251 (N.ISOL)
X0403ME	TAG	S6006LS2	S	TO-220 (ISOL)
X0403MF	TAG	S6004VS2	S	TO-251 (N.ISOL)
X0405BE	TAG	S4006LS2	S	TO-220 (ISOL)
X0405BF	TAG	S4004VS1	S	TO-251 (N.ISOL)
X0405DE	TAG	S4006LS2	S	TO-220 (ISOL)
X0405DF	TAG	S4004VS1	S	TO-251 (N.ISOL)
X0405ME	TAG	S6006LS2	S	TO-220 (ISOL)
X0405MF	TAG	S6004VS1	S	TO-251 (N.ISOL)
Z00607DA	STMicro	LX807DE	S	TO-92 (ISOL)
Z00607MA	STMicro	LX807ME	S	TO-92 (ISOL)
Z0102BA	TAG	L401E3	D	TO-92 (ISOL)
Z0102DA	TAG	L401E3	D	TO-92 (ISOL)
Z0102MA	TAG	L601E3	D	TO-92 (ISOL)
Z0103DN	STMicro	L0103DT	D	SOT-223 (SMT)
Z0103MA	STMicro	L0103ME	D	TO-92 (ISOL)
Z0103MN	STMicro	L0103MT	D	SOT-223 (SMT)
Z0105BA	TAG	L401E5	D	TO-92 (ISOL)

Part Number	Source/ Competitor	Teccor Device	Direct or Suggested Replace- ment	Teccor Package
Z0105DA	TAG	L401E5	D	TO-92 (ISOL)
Z0105MA	TAG	L601E5	D	TO-92 (ISOL)
Z0107DN	STMicro	L0107DT	D	SOT-223 (SMT)
Z0107MN	STMicro	L0107MT	D	SOT-223 (SMT)
Z0109BA	STMicro	L0109DE	D	TO-92 (ISOL)
Z0109DA	STMicro	L0109DE	D	TO-92 (ISOL)
Z0109MA	STMicro	L0109ME	D	TO-92 (ISOL)
Z0109MN	STMicro	L0107MT	D	SOT-223 (SMT)
Z0110DA	TAG	L401E8	D	TO-92 (ISOL)
Z0110MA	TAG	L601E8	D	TO-92 (ISOL)
Z0302BG	TAG	L4004V3	S	TO-251 (N.ISOL)
Z0302DG	TAG	L4004V3	S	TO-251 (N.ISOL)
Z0302MG	TAG	L6004V3	S	TO-251 (N.ISOL)
Z0305BG	TAG	L4004V5	S	TO-251 (N.ISOL)
Z0305DG	TAG	L4004V5	S	TO-251 (N.ISOL)
Z0305MG	TAG	L6004V5	S	TO-251 (N.ISOL)
Z0309BG	TAG	L4004V6	S	TO-251 (N.ISOL)
Z0309DG	TAG	L4004V6	S	TO-251 (N.ISOL)
Z0309MG	TAG	L6004V6	S	TO-251 (N.ISOL)
Z0310BG	TAG	L4004V8	S	TO-251 (N.ISOL)
Z0310DG	TAG	L4004V8	S	TO-251 (N.ISOL)
Z0310MG	TAG	L6004V8	S	TO-251 (N.ISOL)
Z0402BE	TAG	L4004L3	S	TO-220 (ISOL)
Z0402BF	TAG	L4004V3	D	TO-251 (N.ISOL)
Z0402DE	STMicro	L4004L3	S	TO-220 (ISOL)
Z0402DF	STMicro	L4004V3	D	TO-251 (N.ISOL)
Z0402ME	STMicro	L6004L3	S	TO-220 (ISOL)
Z0402MF	STMicro	L6004V3	D	TO-251 (N.ISOL)
Z0405BE	TAG	L4004L5	S	TO-220 (ISOL)
Z0405BF	TAG	L4004V5	D	TO-251 (N.ISOL)
Z0405DE	STMicro	L4004L5	S	TO-220 (ISOL)
Z0405DF	STMicro	L4004V5	D	TO-251 (N.ISOL)
Z0405ME	STMicro	L6004L5	S	TO-220 (ISOL)
Z0405MF	STMicro	L6004V5	D	TO-251 (N.ISOL)
Z0409BE	TAG	L4004L6	S	TO-220 (ISOL)
Z0409BF	TAG	L4004V6	D	TO-251 (N.ISOL)
Z0409DE	STMicro	L4004L6	S	TO-220 (ISOL)
Z0409DF	STMicro	L4004V6	D	TO-251 (N.ISOL)
Z0409ME	STMicro	L6004L6	S	TO-220 (ISOL)
Z0409MF	STMicro	L6004V6	D	TO-251 (N.ISOL)
Z0410BE	TAG	L4004L8	S	TO-220 (ISOL)
Z0410BF	TAG	L4004V8	D	TO-251 (N.ISOL)
Z0410DE	TAG	L4004L8	S	TO-220 (ISOL)
Z0410DF	TAG	L4004V8	D	TO-251 (N.ISOL)
Z0410ME	TAG	L6004L8	S	TO-220 (ISOL)
Z0410MF	TAG	L6004V8	D	TO-251 (N.ISOL)



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Littelfuse offers several technologies to protect sensitive electronic circuits from excess current resulting from overloads, short circuits, power cross or ground faults. Our overcurrent protection product line includes:

Fuses Littelfuse offers the world's broadest range of fuse types and ratings, including cartridge, leaded, surface mount and thin film designs

PTC Protectors Positive Temperature Coefficient thermistor technology provides resettable current-limiting protection



Littelfuse offers multiple technologies for overvoltage suppression and switching to protect sensitive electronic circuits from excessive voltage resulting from electrostatic discharge (ESD), load switching or lightning strikes. Our overvoltage protection product line includes:

Varistors Littelfuse offers surface mount Multi-Layer Varistors (MLVs) and industrial Metal Oxide Varistors (MOVs) to protect against transients

GDTs Gas Discharge Tubes (GDTs) to dissipate voltage through a contained plasma gas

Thyristors Littelfuse's solid state switches control the flow of current in a wide range of appliances, tools and equipment

SIDACtor® Devices Overvoltage protection specifically designed for telecom and datacom requirements

TVS Diodes Silicon transient voltage suppression (TVS) devices

SPAs Silicon Protection Arrays designed for analog and digital signal line protection

PulseGuard® ESD Suppressors Small, fast-acting Electrostatic Discharge (ESD) suppressors

